TEXAS INSTRUMENTS

Low-Voltage Logic

ALB, ALVC, LV, LVC, LVT Families

Data Book

1998 Advanced System Logic Products

INTRODUCTION

The 3.3-V era has arrived! The combination of continuous advancement in semiconductor wafer fabrication technologies and the proliferation of battery-powered computing devices has changed system-design methodologies of the past, and indeed our entire industry. This new era brings a new set of possibilities for computing and hand-held instruments: products that run faster, consume less power, and use fewer total system components than ever before; products that are smaller and lighter, yet maintain interface compatibility with existing industry standard bus architectures; and products that will bring on the next era in the computer industry.

Welcome to the 1996 Texas Instruments Low-Voltage Logic Data Book. A single family of 3.3-V logic products could not possibly cover the diverse needs of all of the end-equipment segments. Products ranging from hand-held point-of-sale terminals, notebook and laptop personal computers, low-power environmentally conscious desktop computers and peripherals, and high-performance RISC and CISC workstation platforms share the need for low-voltage technology, but have radically different price, performance, and feature requirements for the logic they employ. As a response to these diverse needs, Texas Instruments has developed four independent logic families:

Advanced Low-Voltage CMOS (ALVC)
Low-Voltage HCMOS (LV)
Low-Voltage CMOS (LVC)
Low-Voltage Technology (LVT)

These products span four generations of CMOS and BiCMOS process technologies and years of fine-pitch packaging and innovative circuit developments to deliver a set of products for each of these end-equipment segments. In addition to popular octal and Widebus™ bus-interface circuits, two of the families also include SSI and MSI logic functions to help streamline design and facilitate time to market.

Voltage translators are provided to bridge the gap between the 5-V and 3.3-V environments. In addition to the LVT family, the LVC family also is 5 V tolerant. This creates even more flexibility in the mixed-signal environments. Also new this year is the addition of the 2.5-V specification to the ALVC family. Designers of high-speed backplane applications will have great interest in the GTL family of transceivers.

Some of the information in this data book is in product-preview or advance-information form. For more information on these products including availability dates, pricing, and final timing specifications, please contact your local Texas Instruments field sales representative, authorized distributor, or call our Advanced System Logic hotline at (903) 868-5202.

We are sure you will agree that Texas Instruments has developed the most complete line of low-voltage logic products in the industry. We hope that these products will meet your system and design needs. Texas Instruments has been and will continue to be the logic leader for bus-interface products.

Low-Voltage Logic Data Book

ALB, ALVC, LV, LVC, LVT Families

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TI SC European Product Information Center

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TEXAS INSTRUMENTS

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Product stage statements are used on Texas Instruments data sheets to indicate the development stage(s) of the product(s) specified in the data sheets.

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If not all products specified in a data sheet are at the PRODUCTION DATA stage, then the first statement below is placed in the lower left corner of the first page of the data sheet. Subsequent pages of the data sheet containing PRODUCT PREVIEW information or ADVANCE INFORMATION are then marked in the lower left-hand corner with the appropriate statement given below:

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ADVANCE INFORMATION concerns new products in the sampling or preproduction phase of development. Characteristic data and other specifications are subject to change without notice.

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Contents

ALPHANUMERIC INDEX

INTRODUCTION

These symbols, terms, and definitions are in accordance with those currently agreed upon by the JEDEC Council of the Electronic Industries Association (EIA) for use in the USA and by the International Electrotechnical Commission (IEC) for international use.

operating conditions and characteristics (in sequence by letter symbols)

C_i **Input capacitance**
The internal capacitance at an input of the device

C_{io} **Input/output capacitance**
Input-to-output internal capacitance; transcapacitance

C_o **Output capacitance**
The internal capacitance at an output of the device

C_{pd} **Power dissipation capacitance**
Used to determine the no-load dynamic power dissipation per logic function (see individual circuit pages):
$P_D = C_{pd} V_{CC}^2 f + I_{CC} V_{CC}$

f_{max} **Maximum clock frequency**
The highest rate at which the clock input of a bistable circuit can be driven through its required sequence while maintaining stable transitions of logic level at the output with input conditions established that should cause changes of output logic level in accordance with the specification

I_{CC} **Supply current**
The current into* the V_{CC} supply terminal of an integrated circuit

ΔI_{CC} **Supply current change**
The increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}

I_{CEX} **Output high leakage current**
The maximum leakage current into the collector of the pulldown output transistor when the output is high and the output forcing condition $V_O = 5.5$ V

$I_{I(hold)}$ **Input hold current**
Input current that holds the input at the previous state when the driving device goes to a high-impedance state

I_{IH} **High-level input current**
The current into* an input when a high-level voltage is applied to that input

I_{IL} **Low-level input current**
The current into* an input when a low-level voltage is applied to that input

I_{off} **Input/output power-off leakage current**
The current into a circuit mode when the device or a portion of the device affecting that circuit node is in the off state

I_{OH} **High-level output current**
The current into* an output with input conditions applied that, according to the product specification, will establish a high level at the output

*Current out of a terminal is given as a negative value.

I_{OL} **Low-level output current**

The current into* an output with input conditions applied that, according to the product specification, will establish a low level at the output

$I_{OZPU/PD}$ **Off-state (high-impedance-state) output current (of a 3-state output)**

The current flowing into* an output having 3-state capability with input conditions established that, according to the product specification, will establish the high-impedance state at the output

t_a **Access time**

The time interval between the application of a specified input pulse and the availability of valid signals at an output

t_c **Clock cycle time**

Clock cycle time is $1/f_{max}$

t_{dis} **Disable time (of a 3-state or open-collector output)**

The propagation time between the specified reference points on the input and output voltage waveforms with the output changing from either of the defined active levels (high or low) to a high-impedance (off) state

NOTE: For 3-state outputs, $t_{dis} = t_{PHZ}$ or t_{PLZ}. Open-collector outputs will change only if they are low at the time of disabling, so $t_{dis} = t_{PLH}$.

t_{en} **Enable time (of a 3-state or open-collector output)**

The propagation time between the specified reference points on the input and output voltage waveforms with the output changing from a high-impedance (off) state to either of the defined active levels (high or low)

NOTE: In the case of memories, this is the access time from an enable input (e.g., $\overline{OE}$). For 3-state outputs, $t_{en} = t_{PZH}$ or t_{PZL}. Open-collector outputs will change only if they are responding to data that would cause the output to go low, so $t_{en} = t_{PHL}$.

t_h **Hold time**

The time interval during which a signal is retained at a specified input terminal after an active transition occurs at another specified input terminal

NOTES: 1. The hold time is the actual time interval between two signal events and is determined by the system in which the digital circuit operates. A minimum value is specified that is the shortest interval for which correct operation of the digital circuit is to be expected.

2. The hold time may have a negative value in which case the minimum limit defines the longest interval (between the release of the signal and the active transition) for which correct operation of the digital circuit is to be expected.

t_{pd} **Propagation delay time**

The time between the specified reference points on the input and output voltage waveforms with the output changing from one defined level (high or low) to the other defined level ($t_{pd} = t_{PHL}$ or t_{PLH})

t_{PHL} **Propagation delay time, high-to-low level output**

The time between the specified reference points on the input and output voltage waveforms with the output changing from the defined high level to the defined low level

t_{PHZ} **Disable time (of a 3-state output) from high level**

The time interval between the specified reference points on the input and the output voltage waveforms with the 3-state output changing from the defined high level to the high-impedance (off) state

*Current out of a terminal is given as a negative value.

t_{PLH} **Propagation delay time, low-to-high level output**

The time between the specified reference points on the input and output voltage waveforms with the output changing from the defined low level to the defined high level

t_{PLZ} **Disable time (of a 3-state output) from low level**

The time interval between the specified reference points on the input and the output voltage waveforms with the 3-state output changing from the defined low level to the high-impedance (off) state

t_{PZH} **Enable time (of a 3-state output) to high level**

The time interval between the specified reference points on the input and output voltage waveforms with the 3-state output changing from the high-impedance (off) state to the defined high leve

t_{PZL} **Enable time (of a 3-state output) to low level**

The time interval between the specified reference points on the input and output voltage waveforms with the 3-state output changing from the high-impedance (off) state to the defined low level

$t_{sk(o)}$ **Output Skew**

The difference between any two propagation delay times when a single switching input or multiple inputs switching simultaneously cause multiple outputs to switch, as observed across all switching output. This parameter is used to describe the fanout capability of a clock driver and is of concern when making decisions on clock buffering and distribution networks.

t_{su} **Setup time**

The time interval between the application of a signal at a specified input terminal and a subsequent active transition at another specified input terminal

NOTES: 1. The setup time is the actual time interval between two signal events and is determined by the system in which the digital circuit operates. A minimum value is specified that is the shortest interval for which correct operation of the digital circuit is guaranteed.

2. The setup time may have a negative value, in which case the minimum limit defines the longest interval (between the active transition and the application of the other signal) for which correct operation of the digital circuit is guaranteed.

t_w **Pulse duration (width)**

The time interval between specified reference points on the leading and trailing edges of the pulse waveform

V_{IH} **High-level input voltage**

An input voltage within the more positive (less negative) of the two ranges of values used to represent the binary variables

NOTE: A minimum is specified that is the least-positive value of high-level input voltage for which operation of the logic element within specification limits is to be expected.

V_{IL} **Low-level input voltage**

An input voltage within the less positive (more negative) of the two ranges of values used to represent the binary variables

NOTE: A maximum is specified that is the most-positive value of low-level input voltage for which operation of the logic element within specification limits is to be expected.

V_{OH} **High-level output voltage**

The voltage at an output terminal with input conditions applied that, according to product specification, will establish a high level at the output

V_{OL} **Low-level output voltage**

The voltage at an output terminal with input conditions applied that, according to product specification, will establish a low level at the output

V_{IT+} **Positive-going input threshold level**

The voltage level at a transition-operated input that causes operation of the logic element according to specification as the input voltage rises from a level below the negative-going threshold voltage, V_{IT-}

V_{IT-} **Negative-going input threshold level**

The voltage level at a transition-operated input that causes operation of the logic element according to specification as the input voltage falls from a level above the positive-going threshold voltage, V_{IT+}

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The following symbols are used in function tables on TI data sheets:

H	=	high level (steady state)
L	=	low level (steady state)
↑	=	transition from low to high level
↓	=	transition from high to low level
→	=	value/level or resulting value/level is routed to indicated destination
↶	=	value/level is re-entered
X	=	irrelevant (any input, including transitions)
Z	=	off (high-impedance) state of a 3-state output
a . . . h	=	the level of steady-state inputs A through H respectively
Q_0	=	level of Q before the indicated steady-state input conditions were established
$\overline{Q}_0$	=	complement of Q_0 or level of $\overline{Q}$ before the indicated steady-state input conditions were established
Q_n	=	level of Q before the most recent active transition indicated by ↓ or ↑
⎍	=	one high-level pulse
⎌	=	one low-level pulse
Toggle	=	each output changes to the complement of its previous level on each active transition indicated by ↓ or ↑

If, in the input columns, a row contains only the symbols H, L, and/or X, this means the indicated output is valid whenever the input configuration is achieved and regardless of the sequence in which it is achieved. The output persists so long as the input configuration is maintained.

If, in the input columns, a row contains H, L, and/or X together with ↑ and/or ↓, this means the output is valid whenever the input configuration is achieved but the transition(s) must occur following the achievement of the steady-state levels. If the output is shown as a level (H, L, Q_0, or $\overline{Q}_0$), it persists so long as the steady-state input levels and the levels that terminate indicated transitions are maintained. Unless otherwise indicated, input transitions in the opposite direction to those shown have no effect at the output. (If the output is shown as a pulse, ⎍ or ⎌, the pulse follows the indicated input transition and persists for an interval dependent on the circuit.)

EXPLANATION OF FUNCTION TABLES

Among the most complex function tables are those of the shift registers. These embody most of the symbols used in any of the function tables, plus more. Below is the function table of a 4-bit bidirectional universal shift register, e.g., type SN74194.

FUNCTION TABLE

INPUTS										OUTPUTS			
CLEAR	MODE		CLOCK	SERIAL		PARALLEL				Q_A	Q_B	Q_C	Q_D
	S1	S0		LEFT	RIGHT	A	B	C	D				
L	X	X	X	X	X	X	X	X	X	L	L	L	L
H	X	X	L	X	X	X	X	X	X	Q_{A0}	Q_{B0}	Q_{C0}	Q_{D0}
H	H	H	↑	X	X	a	b	c	d	a	b	c	d
H	L	H	↑	X	H	H	H	H	H	H	Q_{An}	Q_{Bn}	Q_{Cn}
H	L	H	↑	X	L	L	L	L	L	L	Q_{An}	Q_{Bn}	Q_{Cn}
H	H	L	↑	H	X	X	X	X	X	Q_{Bn}	Q_{Cn}	Q_{Dn}	H
H	H	L	↑	L	X	X	X	X	X	Q_{Bn}	Q_{Cn}	Q_{Dn}	L
H	L	L	X	X	X	X	X	X	X	Q_{A0}	Q_{B0}	Q_{C0}	Q_{D0}

The first line of the table represents a synchronous clearing of the register and says that if clear is low, all four outputs will be reset low regardless of the other inputs. In the following lines, clear is inactive (high) and so has no effect.

The second line shows that so long as the clock input remains low (while clear is high), no other input has any effect and the outputs maintain the levels they assumed before the steady-state combination of clear high and clock low was established. Since on other lines of the table only the rising transition of the clock is shown to be active, the second line implicitly shows that no further change in the outputs will occur while the clock remains high or on the high-to-low transition of the clock.

The third line of the table represents synchronous parallel loading of the register and says that if S1 and S0 are both high then, without regard to the serial input, the data entered at A will be at output Q_A, data entered at B will be at Q_B, and so forth, following a low-to-high clock transition.

The fourth and fifth lines represent the loading of high- and low-level data, respectively, from the shift-right serial input and the shifting of previously entered data one bit; data previously at Q_A is now at Q_B, the previous levels of Q_B and Q_C are now at Q_C and Q_D, respectively, and the data previously at Q_D is no longer in the register. This entry of serial data and shift takes place on the low-to-high transition of the clock when S1 is low and S0 is high and the levels at inputs A through D have no effect.

The sixth and seventh lines represent the loading of high- and low-level data, respectively, from the shift-left serial input and the shifting of previously entered data one bit; data previously at Q_B is now at Q_A, the previous levels of Q_C and Q_D are now at Q_B and Q_C, respectively, and the data previously at Q_A is no longer in the register. This entry of serial data and shift takes place on the low-to-high transition of the clock when S1 is high and S0 is low and the levels at inputs A through D have no effect.

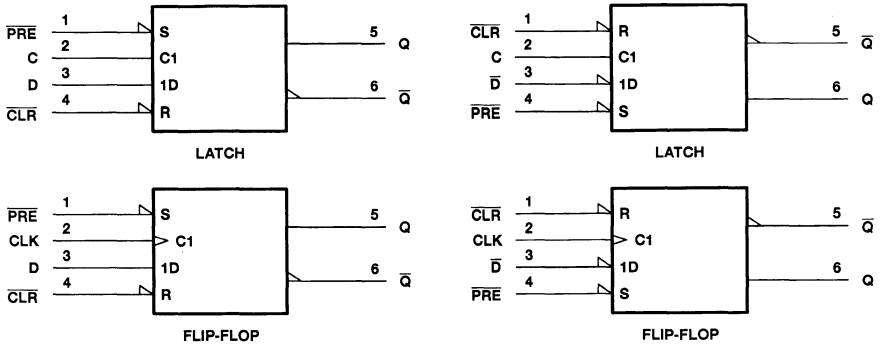
The last line shows that as long as both inputs are low, no other input has any effect and, as in the second line, the outputs maintain the levels they assumed before the steady-state combination of clear high and both mode inputs low was established.

The function table functional tests do not reflect all possible combinations or sequential modes.

It is normal TI practice to name the outputs and other inputs of a D-type flip-flop or latch and to draw its logic symbol based on the assumption of true data (D) inputs. Outputs that produce data in phase with the data inputs are called Q and those producing complementary data are called $\overline{Q}$. An input that causes a Q output to go high or a $\overline{Q}$ output to go low is called preset (PRE). An input that causes a $\overline{Q}$ output to go high or a Q output to go low is called clear (CLR). Bars are used over these pin names (PRE and CLR) if they are active low.

The devices on several data sheets are second-source designs, and the pin name conventions used by the original manufacturers have been retained. That makes it necessary to designate the inputs and outputs of the inverting circuits $\overline{D}$ and Q.

In some applications, it may be advantageous to redesignate the data input from D to $\overline{D}$ or vice versa. In that case, all the other inputs and outputs should be renamed as shown below. Also shown are corresponding changes in the graphical symbols. Arbitrary pin numbers are shown.



The figures show that when Q and $\overline{Q}$ exchange names, the preset and clear pins also exchange names. The polarity indicators ($\triangleright$) on $\overline{PRE}$ and $\overline{CLR}$ remain, as these inputs are still active low, but the presence or absence of the polarity indicator changes at D (or $\overline{D}$), Q, and $\overline{Q}$. Pin 5 (Q or $\overline{Q}$) is still in phase with the data input (D or $\overline{D}$); their active levels change together.

THERMAL INFORMATION

In digital system design, consideration must be given to thermal management of components. The small size of the small-outline package makes this even more critical. Figure 1 shows the thermal resistance of these packages for various rates of air flow. Figures 2, 3, 4, and 5 are derating curves for the DB package.

The thermal resistances in Figure 1 can be used to approximate typical and maximum virtual junction temperatures for the LVL family. In general, the junction temperature for any device can be calculated using the following equation.

$$T_J = R_{\theta JA} \times P_T + T_A$$

Where:

T_J = virtual junction temperature
$R_{\theta JA}$ = thermal resistance, junction to free air
P_T = total power dissipation of the device
T_A = free-air temperature

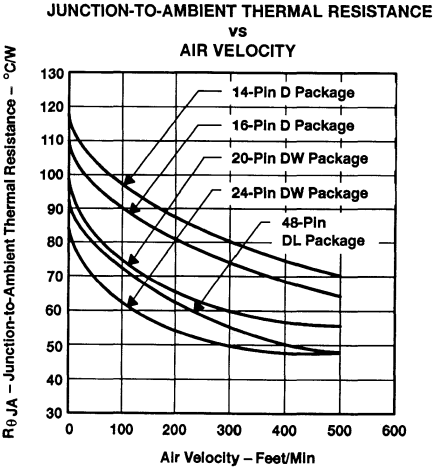


Figure 1

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DERATING CURVES FOR 210-MIL SHRINK SMALL-OUTLINE PACKAGE (DB)

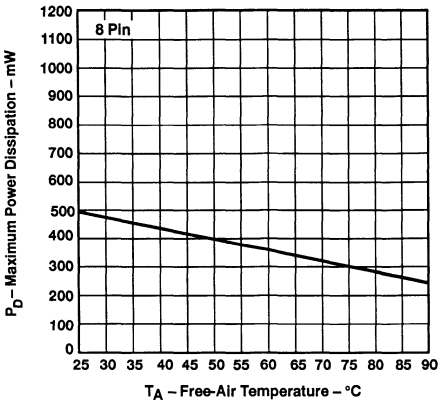

Figure 2

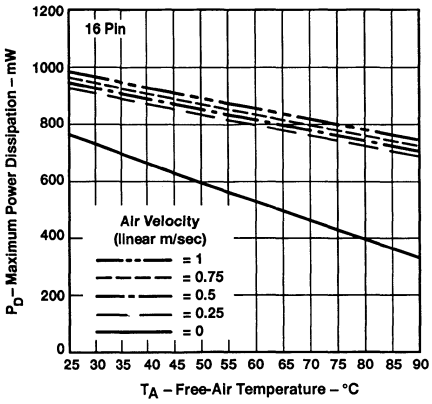

Figure 3

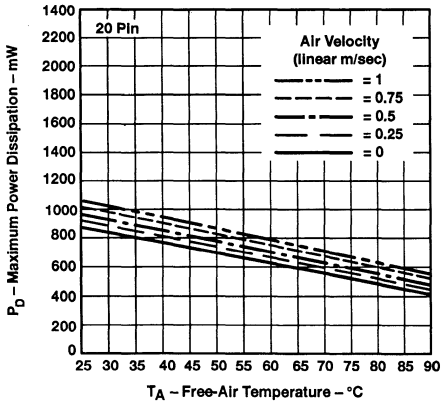

Figure 4

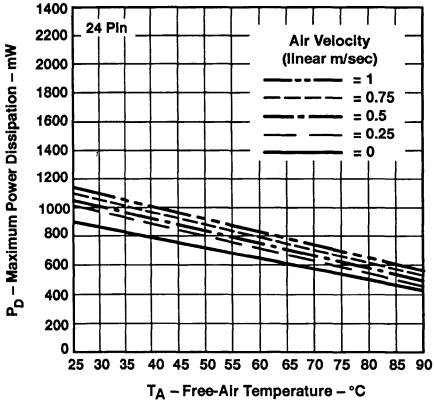

Figure 5

Current Texas Instruments Advanced Logic Publications

Listed below is the current collection of Texas Instruments logic technical documentation. The alphanumeric code is the literature number for each item listed. These documents can be ordered through a TI representative or authorized distributor by referencing the literature number.

Document	*Literature Number*
Advanced BiCMOS Technology Data Book (1994)	SCBD002B
Advanced Bus-Interface SPICE I/O Models Data Book (1995)	SCBD004A
Advanced CMOS Logic Data Book (1993)	SCAD001C
Advanced Logic and Bus-Interface Logic Data Book (1991)	SCYD001
ALS/AS Logic Data Book (1995)	SDAD001C
BCT BiCMOS Bus-Interface Logic Data Book (1994)	SCBD001B
Boundary-Scan Logic, IEEE Std. 1149.1 (JTAG) 5-V and 3.3-V Bus-Interface and Scan-Support Products Data Book (1994)	SCTD002
CBT Bus Switches Crossbar Technology Data Book (1995)	SCDD001
CDC Clock-Distribution Circuits Data Book (1994)	SCAD004
F Logic Data Book (1994)	SDFD001B
High-Performance FIFO Memories Data Book (1996)	SCAD003C
High-Performance FIFO Memories Designer's Handbook (1996)	SCAA012A
High-Speed CMOS Logic Data Book (1989)	SCLD001C
Low-Voltage Logic Data Book (1996)	SCBD003B
TTL Logic Data Book (TTL, LS, S) (1988)	SDLD001A
Semiconductor Group Package Outlines Reference Guide	SSYU001A

In addition to the books listed above, the following documents are available only in Europe.

Document	*Literature Number*
Advanced BiCMOS Technology Data Book (1994)	SCBDE08
CBT Crossbar Technology Data Book (1995)	SCDDE01
CDC Data and Applications Manual (1995)	SCBTE07B
Packaging Data Book (1995)	SCYDE04
ASL SCOPE™ Products Data and Applications Manual (1994)	SCBDE09

Positive-NAND Gates

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
8 Input		'30	✔	✔	✔	✔	✔	✔								
13 Input		'133	✔				✔									
Dual 4 Input		'20	✔	✔	✔	✔	✔						✔			
Triple 3 Input		'10	✔	✔	✔	✔	✔		✔	✔			✔			✔
Quad 2 Input		'00	✔	✔	✔	✔	✔	✔	✔•	✔	✔	✔	✔	✔	✔	✔
		'37	✔			✔	✔	✔								
	OC	'38	✔		✔	✔	✔	✔								
		'132				✔	✔	✔					✔			
		'1000		✔												
Hex 2 Input		'804	✔	✔												
		'1804		✔												
Quad 2 Input	OC	'03	✔			✔							✔			
Dual 2 Input		'8003	✔													

Positive-AND Gates

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
Quad 2 Input	OC	'09	✔			✔	✔									
		'7001											✔			
Dual 4 Input		'21	✔	✔	✔	✔							✔			
Triple 3 Input		'11	✔	✔	✔	✔	✔		✔	✔			✔			
Quad 2 Input		'08	✔	✔	✔	✔	✔		✔•	✔•	✔	✔	✔	✔	✔	✔
		'1008		✔												
Hex 2 Input		'808		✔												
		'1808		✔												

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
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Positive-OR/NOR Gates

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
Quad 2 Input		'32	✔	✔	✔	✔	✔	✔	✔•	✔•	✔	✔	✔	✔	✔	✔
		'1032		✔												
Hex 2 Input		'832	✔	✔												
		'1832		✔												
Dual 5 Input		'260			✔		✔									
Triple 3 Input		'27	✔	✔	✔	✔							✔			
Quad 2 Input		'02	✔	✔	✔	✔	✔						✔	✔	✔	✔
	OC	'33				✔										
		'7002											✔			
Hex 2 Input		'805	✔	✔												
		'1805		✔												

OR/NOR Gates

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
Quad 2-Input Exclusive-OR Gates With Totem-Pole Outputs		'86	✔		✔	✔			✔•	✔	✔	✔	✔			✔
Quad 2-Input Exclusive-NOR Gates	OD	'266				✔							✔			

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
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INVERTING/NONINVERTING BUFFERS

Hex Inverters/Noninverters

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
Hex Inverters		'04	✔	✔	✔	✔	✔	✔	✔•	✔•	✔	✔	✔	✔	✔	✔
		'U04									✔		✔		✔	✔
	OC	'05	✔			✔	✔	✔					✔			
		'06						✔								
		'14				✔		✔	✔	✔	✔	✔	✔		✔	✔
		'1004	✔	✔												
		'1005	✔													
Hex Noninverters	OC	'35	✔													
		'1034	✔	✔												
	OC	'1035	✔													

BUFFERS/DRIVERS AND BUS TRANSCEIVERS

Buffers/Drivers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																	
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
2-Bit Buffers	3S	'306		✔																	
Quad Buffers/Drivers	3S	'125	✔	✔	✔			✔	✔					+	+		✔	✔	✔	✔	
		'126	✔	✔				✔	✔					+	+		✔				
Hex Buffers	OC	'07									✔										
Noninverting Hex Buffers/Drivers	3S	'365							✔								✔				
	3S	'367							✔		✔						✔				
Inverting Hex Buffers/Drivers	3S	'368							✔		✔						✔				

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
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Buffers/Drivers (Continued)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																		
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Noninverting Octal Buffers/Drivers	3S	'241	✔	✔	✔	✔	✔	✔	✔	✔		✔	✔				✔				
		'244	✔	✔	✔	✔	✔	✔	✔	✔		✔•	✔•	✔	✔		✔	✔	✔	✔	+LVCH
		'1240				✔															
		'1244				✔															
		'25244		✔																	
		'541	✔	✔		✔		✔	✔					✔	✔		✔	✔		✔	
	OC	'757					✔														
		'760		✔		✔	✔														
Inverting Octal Buffers/Drivers	3S	'240	✔	✔	✔	✔	✔	✔	✔	✔		✔•	✔•	✔	✔		✔	✔	✔	✔	
		'540	✔	✔		✔			✔					✔	✔		✔	✔		✔	
	OC	'756		✔			✔														
Inverting and Noninverting Octal Buffers/Drivers	3S	'230					✔														
Noninverting 10-Bit Buffers/Drivers	3S	'827	✔																	✔	
		'29827		✔		✔															
Inverting 10-Bit Buffers/Drivers	3S	'828																		✔	
		'29828		✔		✔															
Noninverting 16-Bit Buffers/Drivers	3S	'16241	✔										✔			✔				✔	
		'16244	✔		✔							✔	✔			✔				✔	
		'16541	✔										✔							✔	
Inverting 16-Bit Buffers/Drivers	3S	'16240	✔									✔	✔			✔				✔	
		'16540	✔										✔							✔	
Noninverting 18-Bit Buffers/Drivers	3S	'16825	✔										✔			✔					
		'16835			✔											✔					
Noninverting 20-Bit Buffers/Drivers	3S	'16827	✔										✔			✔					

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

Universal Bus Transceivers (UBT™)/Universal Bus Exchangers (UBE™)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY						
			ABT	BCT	LVT	LV	LVC	ALVC	OTHER
Noninverting 9-Bit 4-Port UBE™	3S	'16409						✔	
Noninverting 17-Bit UBT™ With Buffered Clock Outputs and Output Edge Control (OEC™)	OD	'16616							✔GTL
Noninverting 18-Bit UBT™	3S	'16500	✔		✔			✔	
		'16501	✔		✔			✔	
		'16600	✔					✔	
		'16601	✔					✔	
Noninverting 18-Bit UBT™ With Output Edge Control (OEC™)	OD	'16612							✔GTL
Noninverting 18-Bit UBT™	OD	'16622							+GTL
Noninverting 36-Bit UBT™	3S	'32501	✔						
Noninverting 16-Bit Tri-Port UBE™	3S	'32316	✔						
Noninverting 18-Bit Tri-Port UBE™	3S	'32318	✔						
18-Bit UBT™ With Series Resistors on B Port	3S	'162500	✔						
		'162501	✔						
		'162601	✔					✔	
Noninverting 18-Bit UBT™ With Parity Generators /Checkers	3S	'16901						✔	
SCOPE™ 18-Bit UBT™	3S	'18502	✔		✔				
SCOPE™ 20-Bit UBT™	3S	'18504	✔		✔				

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

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Bus Transceivers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																		
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Inverting Quad Transceivers	OC	'758				✔															
Noninverting Quad Transceivers	3S	'243				✔		✔	✔												
Noninverting Octal Transceivers	3S	'245	✔	✔	✔	✔	✔	✔	✔			✔•	✔•	✔	✔		✔	✔	✔	✔	+LVCH
		'1245				✔															
		'25245	✔	✔																	
		'645				✔	✔		✔								✔	✔			
		'1645				✔															
	OC	'621				✔															
		'641				✔	✔		✔												
	OC/3S	'639				✔	✔														
Inverting Octal Transceivers	3S	'620	✔			✔															
		'623	✔	✔		✔		✔	✔								✔	✔			
		'640	✔	✔		✔	✔		✔								✔				
		'1640				✔															
	OC	'642				✔			✔												
	OC/3S	'638				✔	✔														
Noninverting 9-Bit Transceivers	3S	'863	✔																	✔	
		'29863		✔		✔															
Noninverting 10-Bit Transceivers	3S	'861	✔																	✔	
Noninverting 16-Bit Transceivers	3S	'16245	✔		✔							✔	✔			✔				✔	✔ABTE
		'16623	✔										✔								
Noninverting 16-Bit Transceivers, 3.3-V-to-5-V Level Shifter	3S	'164245														✔					
Inverting 16-Bit Transceivers	3S	'16640	✔									✔	✔								
		'16620										✔	✔								
Noninverting 18-Bit Transceivers	3S	'16863	✔										✔			✔					

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

Bus Transceivers (Continued)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																		
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Inverting 18-Bit Transceivers	3S	'16864											✔								
Noninverting 20-Bit Transceivers	3S	'16861											✔								
Noninverting Octal Registered Transceivers	3S	'543	✔	✔	✔			✔												✔	
		'646	✔	✔	✔	✔	✔		✔								✔	✔		✔	
		'652	✔	✔	✔	✔	✔		✔			•	•				✔	✔		✔	
		'2952	✔		✔															✔	
	OC/3S	'653				✔															
		'654				✔															
Inverting Octal Registered Transceivers	3S	'648				✔	✔		✔												
		'651	✔			✔	✔														
		'2953		✔																	
Noninverting 16-Bit Registered Transceivers	3S	'16470	✔										✔								
		'16543	✔		✔							✔	✔			✔				✔	
		'16646	✔		✔							✔	✔			✔				✔	
		'16652	✔		✔							✔	✔							✔	
		'16952	✔		✔								✔							+	
Inverting 16-Bit Registered Transceivers	3S	'16544											✔								
		'16648											✔								
		'16651											✔								
Noninverting 18-Bit Registered Transceivers	3S	'16474											✔								
		'16500	✔		✔											✔					
		'16501	✔		✔											✔					
		'16600	✔													✔					
		'16601	✔													✔					
Noninverting 36-Bit Transceivers	3S	'32245	✔																		
Noninverting 36-Bit Registered Transceivers	3S	'32501	✔																		
		'32543	✔																		

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
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Bus Transceivers (Continued)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																		
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
8-/9-Bit Bus Transceivers With Parity Checkers/ Generators	3S	'657	✔																		
		'833	✔																		
		'853	✔																		
	3S/OC	'29833				✔															
		'29834		✔																	
		'29854		✔																	
Dual 8-/9-Bit Bus Transceivers With Parity Checkers/ Generators	3S	'16833	✔										✔								
		'16657	✔										✔								
		'16853	✔																		
Noninverting 16-Bit Tri-Port Registered Bus Exchangers	3S	'32316	✔																		
Noninverting 18-Bit Tri-Port Registered Bus Exchangers	3S	'32318	✔																		
7-Bit TTL/BTL Transceivers	OC	'2041																			✔FB
8-Bit TTL/BTL Transceivers	OC	'2040																			✔FB
8-Bit TTL/BTL Registered Transceivers	OC	'2033																			✔FB
9-Bit TTL/BTL Competition Transceivers	OC	'2032																			+FB
9-Bit TTL/BTL Address/ Data Transceivers	OC	'2031																			✔FB
17-Bit TTL/BTL Universal Storage Transceivers	OC	'1651																			✔FB
18-Bit TTL/BTL Universal Storage Transceivers	OC	'1650																			✔FB

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

MOS Memory Drivers/Transceivers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY											
			ABT	BCT	LVT	ALS	AS	F	AC	ACT	ALVC	LV	LVC	OTHER
Octal Buffers/Drivers With Series Resistors on Output	3S	'2240	✔	✔		✔								
		'2241	✔											
		'2244	✔	✔				✔						
		'2541				✔								
Octal Transceivers With Series Resistors on B Port	3S	'2245	✔	✔				✔						
10-Bit Buffers/Drivers With Series Resistors	3S	'2827		✔										
		'2828		✔										
10-Bit Flip-Flops With Dual Outputs and Series Resistors	3S	'162820									✔			
11-Bit Buffers/Drivers With Series Resistors	3S	'5400	✔											
		'5401	✔											
12-Bit Buffers/Drivers With Series Resistors	3S	'5402	✔											
		'5403	✔											
16-Bit Buffers/Drivers With Series Resistors	3S	'162244	✔		✔						✔		✔	
16-Bit Transceivers With Series Resistors	3S	'162245	✔		✔						✔			✔LVTH
16-Bit D-Type Latches With Series Resistors	3S	'162373			✔									
16-Bit D-Type Flip-Flops With Series Resistors	3S	'162374			✔									
4-to-1 Multiplexed/Demultiplexed Registered Transceivers With Series Resistors	3S	'162460	✔											
18-Bit UBT™ With Series Resistors on B Port	3S	'162500	✔											
		'162501	✔											
		'162601	✔								✔			
18-Bit Bus-Interface Flip-Flops With Series Resistors	3S	'162823	✔											
18-Bit Buffers/Drivers With Series Resistors	3S	'162825	✔											
20-Bit Buffers/Drivers With Series Resistors	3S	'162827	✔											
12-to-24 Multiplexed D-Type Latches With Series Resistors on B Port	3S	'162260	✔											

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
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TESTABILITY BUS-INTERFACE CIRCUITS

IEEE 1149.1 (JTAG) Boundary-Scan Logic

DESCRIPTION	NO. OF BITS	OUTPUT	TYPE	TECHNOLOGY									
				ABT	BCT	LVT	F	LS	S	TTL	AC	ACT	OTHER
Buffers/Drivers	8	3S	'8240	+	✔								
			'8244	+	✔								
Transceivers	8	3S	'8245	✔	✔								
	18	3S	'18245	✔		✔							
Transparent Latches	8	3S	'8373	+	✔								
Flip-Flops	8	3S	'8374	+	✔								
Registered Transceivers	8	3S	'8543	✔									
			'8646	✔									
			'8652	✔									
			'8952	✔									
	18	3S	'18502	✔		✔							
			'18646	✔		✔							
			'18652	✔		✔							
	20	3S	'18504	✔		✔							
Test Bus Controllers		3S	'8990									✔	

FLIP-FLOPS AND LATCHES

Flip-Flops

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																	
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Dual J-K Edge Triggered		'109				✔	✔	✔	✔								✔				
		'112				✔		✔	✔	✔							✔			+	+CDC
		'113				✔															
Dual D-Type		'74				✔	✔	✔	✔	✔	✔	✔•	✔•	✔	✔		✔	✔	✔	✔	
Dual 4 Bit D-Type Edge Triggered	3S	'874				✔	✔														
		'876				✔	✔														
Quad D-Type		'175				✔	✔	✔	✔	✔	✔						✔				
Hex D-Type		'174				✔	✔	✔	✔	✔							✔		✔		
		'378						✔													

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

Flip-Flops (Continued)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																		
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Octal D-Type True Data	3S	'374	✔	✔		✔	✔	✔	✔	✔		✔•	✔•	+	+		✔	✔	✔	✔	
		'574	✔		✔	✔	✔	✔				✔	✔	✔	✔		✔	✔	✔	✔	
Octal D-Type True Data With Clear		'273	✔		✔	✔			✔								✔	✔	✔		
	3S	'575				✔	✔														
		'874				✔	✔														
Octal D-Type True Data With Clock Enable		'377	✔					✔	✔								✔	✔			
Octal D-Type Inverting	3S	'534	✔			✔						✔	✔				✔				
		'564			•	✔						✔	✔								
		'576				✔	✔														
Octal Dual Ranked True Data	3S	'4374					✔														
Octal Inverting With Clear	3S	'577				✔															
Octal Inverting With Preset	3S	'876				✔	✔														
Octal True Data	3S	'825					✔														
9 Bit True Data	3S	'823	✔				✔													✔	
		'29823		✔																	
10 Bit Noninverting	3S	'16820														✔					
10 Bit True Data	3S	'821	✔				✔													+	
		'29821		✔		✔															
16 Bit Noninverting	3S	'16374	✔		✔							✔	✔			✔				✔	
18 Bit Noninverting	3S	'16823	✔									✔	✔			✔					
20 Bit Noninverting	3S	'16721														✔					
		'16821	✔										✔			✔					
20 Bit Noninverting With GTL I/O Levels	OD	'16921																			+GTL

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

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Latches

DESCRIPTION	NO. OF BITS	OUTPUT	TYPE	TECHNOLOGY																		
				ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
D-Type Edge Triggered Inverting and Noninverting	8	3S	'996				✔															
D-Type Transparent Readback Latch, True	8	3S	'990				✔															
	9	3S	'992				✔															
	10	3S	'994				✔															
D-Type Transparent With Clear, True Outputs	8	3S	'666				✔															
D-Type Transparent With Clear, Inverting Outputs	8	3S	'667				✔															
D-Type Transparent True	8	3S	'373	✔	✔		✔	✔	✔	✔	✔		✔•	✔•	+	+		✔	✔	✔	✔	
			'573	✔		✔	✔	✔	✔				✔	✔	✔	✔		✔	✔	✔	✔	
	16	3S	'16373	✔		✔							✔	✔			✔				✔	
D-Type Dual 4 Bit Transparent True	8	3S	'873				✔	✔														
D-Type Transparent Inverting	8	3S	'533	✔			✔	✔					✔	✔								
			'563				✔						✔	✔				✔				
			'580				✔															
Addressable	8	2S	'259				✔			✔								✔				
D-Type True Inputs	8	3S	'845				✔															
	9	3S	'843	✔			✔														+	
			'29843		✔																	
	10	3S	'841	✔			✔														✔	
			'29841		✔		✔															
	18	3S	'16843	+													✔					
	20	3S	'16841	✔										✔			✔					
D-Type Inverting Inputs	10	3S	'842				✔															

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

REGISTERS

Shift Registers

DESCRIPTION	NO. OF BITS	OUTPUT	TYPE	TECHNOLOGY													
				ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AHC	AHCT	HC	HCT	LV
Parallel In, Parallel Out, Bidirectional	4		'194					✔		✔	✔						
	8		'299				✔		✔	✔	✔						
			'323				✔			✔							
Parallel In, Parallel Out	4		'195							✔	✔						
Serial In, Parallel Out	8		'164				✔			✔					✔		✔
Parallel In, Serial Out	8		'165				✔			✔					✔		
			'166				✔			✔					✔		
Serial In, Parallel Out With Output Latches	8	3S	'594							✔					✔		
			'595							✔					✔		
Noninverting	8	3S	'299				✔		✔	✔	✔						
	9	3S	'29823		✔												

Register Files

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY										
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT
Dual 16 Word × 4 Bits	3S	'870				✔							

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Synchronous Counters – Positive Edge Triggered

DESCRIPTION	PARALLEL LOAD	TYPE	TECHNOLOGY												
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AHC	AHCT	HC	HCT
4 Bit Decade Up/Down	Sync	'568				✔									
4 Bit Binary	Sync	'161				✔	✔	✔	✔					✔	
		'163				✔	✔	✔	✔	✔				✔	
		'561				✔									
4 Bit Binary Up/Down	Sync	'169				✔	✔	✔	✔	✔					
		'569				✔									
		'191				✔			✔					✔	
		'193				✔			✔		✔			✔	
8 Bit Up/Down	Sync Clear	'869				✔	✔								
	Async Clear	'867				✔	✔								

Asynchronous Counters (Ripple Clock) – Negative Edge Triggered

DESCRIPTION	PARALLEL LOAD	TYPE	TECHNOLOGY												
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AHC	AHCT	HC	HCT
Dual 4 Bit Binary	None	'393							✔					✔	
12 Bit Binary	Async	'4040												✔	
14 Bit Binary	Async	'4020												✔	
		'4060												✔	

8-Bit Binary Counters With Registers

DESCRIPTION	PARALLEL LOAD	TYPE	TECHNOLOGY												
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AHC	AHCT	HC	HCT
Parallel Register Outputs	3S	'590							✔					✔	
Parallel Register Inputs	3S	'593							✔						

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

DECODERS, ENCODERS, DATA SELECTORS/MULTIPLEXERS

Encoders/Data Selectors/Multiplexers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																	
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC
Quad 2-to-1		'157				✔	✔	✔	✔	✔	✔			+	+		✔	✔		✔
		'158				✔	✔	✔	✔	✔				+	+		✔			
		'298					✔		✔											
	3S	'257				✔	✔	✔	✔	✔			•	+	+		✔	✔		✔
	3S	'258				✔	✔	✔	✔					+	+					
Hex 2-to-1 Universal Multiplexers	3S	'857				✔														
Dual 4-to-1		'153				✔	✔	✔	✔	✔							✔			
	3S	'253				✔	✔	✔	✔								✔			
	3S	'353					✔													
4-to-1 Registered Transceivers	3S	'16460	✔																	
Cascadable Octals		'148							✔		✔						✔			
8-to-1		'151				✔	✔	✔	✔	✔							✔			
	3S	'251				✔		✔	✔	✔							✔			
16-to-1	3S	'250					✔													
12-to-24 Multiplexed D-Type Latches	3S	'16260	✔													✔				
12-to-24 Registered Bus Exchangers	3S	'16269														✔				
	3S	'16270														✔				

Decoders/Demultiplexers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY														
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Dual 2-to-4		'131		✔														
		'139	✔			✔	✔		•	•	+	+		✔	✔			
	OC	'156	✔			✔		✔										
Dual 2-to-4 for Battery Backed-Up Memories		'2414																
3-to-8		'138	✔	✔	✔	✔	✔		•		+	+		✔	✔	✔	✔	
3-to-8 With Address Registers		'137	✔	✔		✔											+	
4-to-10 BCD-to-Decimal		'42				✔								✔				

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

COMPARATORS AND PARITY GENERATORS/CHECKERS

Comparators

DESCRIPTION								TYPE	TECHNOLOGY							
INPUT	P=Q	$\overline{P=Q}$	P>Q	$\overline{P>Q}$	P<Q	OUTPUT	ENABLE		ALS	AS	F	LS	AC	ACT	HC	HCT
8 Bit With 20-kΩ Pullup	No	Yes	No	No	No	2S	Yes	'520	✔				•			
	No	Yes	No	Yes	No	2S	No	'682				✔			✔	
8 Bit Standard	No	Yes	No	No	No	2S	Yes	'521	✔		✔					
	No	Yes	No	Yes	No	2S	No	'684				✔			✔	
	No	Yes	No	No	No	2S	Yes	'688	✔			✔			✔	
8 Bit Latched P	No	No	Yes	No	Yes	2S	Yes	'885		✔						

Parity Generators/Checkers

DESCRIPTION	NO. OF BITS	TYPE	TECHNOLOGY									
			ALS	AS	F	LS	S	TTL	AC	ACT	HC	HCT
Odd/Even	9	'280	✔	✔	✔	✔	✔					
		'286		✔						•		

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

BUS SWITCHES AND 5-V/3-V VOLTAGE TRANSLATORS

Bus Switches

DESCRIPTION	TYPE	TECHNOLOGY			
		CBT	CBTS	CBTD	OTHER
Quad Bus Switches	'3125	✔			
Dual 4-Bit Bus Switches With '244 Pinout	'3244	✔			
8-Bit Bus Switches With '245 Pinout	'3245	✔			
Quad 2-to-1-Bit FET Multiplexers/Demultiplexers	'3257	✔			
Dual Bus Switches	'3306	✔	✔	✔	
8-Bit Bus Switches	'3345	✔			
10-Bit Bus-Exchange Switches	'3383	✔			
Dual 5-Bit Bus Switches	'3384	✔	✔	✔	
10 Bit With Precharged Outputs for Live Insertion	'6800	✔			
18-Bit Bus-Exchange Switches	'16209	✔			
24-Bit Bus-Exchange Switches	'16211	✔			
	'16212	✔			
	'16213	✔			
12-Bit 3-to-1 Bus Select	'16214	✔			
Synchronous 16-Bit-to-32-Bit FET Multiplexers	'16232	✔			
16-Bit-to-32-Bit FET Multiplexers/Demultiplexers	'16233	✔			

ARITHMETIC CIRCUITS

Parallel Binary Adders

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY											
			ALS	AS	F	LS	S	TTL	HC	HCT	AC	ACT	LV	LVC
4 Bit		'283			✔	✔	✔							

Arithmetic Logic Units

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY											
			ALS	AS	F	LS	S	TTL	HC	HCT	AC	ACT	LV	LVC
4-Bit Arithmetic Logic Units: Function Generator		'181		✔										

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

First-In, First-Out (FIFO) Memories

DESCRIPTION		OUTPUT	TYPE	TECHNOLOGY											
SIZE	TYPE†			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	ALVC
16 Words × 4 Bits	U	3S	'232				✔								
16 Words × 5 Bits	U	3S	'225								✔				
			'233				✔								
32 Words × 9 Bits	B	3S	'2238				✔								
64 Words × 4 Bits	U	3S	'234				✔								
			'236				✔								
64 Words × 5 Bits	U	3S	'235				✔								
64 Words × 8 Bits	U	3S	'2232				✔								
64 Words × 9 Bits	U	3S	'2233				✔								
64 Words × 18 Bits	U, C	3S	'7813											✔	✔
	U	3S	'7814											✔	✔
64 Words × 36 Bits	B, C	3S	'3612	✔											
			'3614	✔											
	U, C	3S	'3611	✔											
			'3613	✔											
Dual 64 × 1	C	3S	'2226											✔	
			'2227											✔	
Dual 256 × 1	C	3S	'2228											✔	
			'2229											✔	
256 Words × 9 Bits	U	3S	'7200L											✔	
256 Words × 18 Bits	U, C	3S	'7805											✔	
	U	3S	'7806											✔	✔
256 × 36 × 2 Bits	B, C	3S	'3622											✔	
512 Words × 9 Bits	U	3S	'7201LA											✔	

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

† U = Unidirectional
B = Bidirectional
C = Clocked
S = Synchronized

First-In, First-Out (FIFO) Memories (Continued)

DESCRIPTION		OUTPUT	TYPE	TECHNOLOGY											
SIZE	TYPE†			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	ALVC
512 Words × 18 Bits	U, C	3S	'7803											✔	✔
	U	3S	'7804											✔	✔
	B, C	3S	'7819	✔											
	B	3S	'7820	✔											
512 Words × 32 Bits	B, C	3S	'3638											✔	
512 Words × 36 Bits	U, C	3S	'3631											✔	
	B, C	3S	'3632											✔	
1K Words × 9 Bits	B	3S	'2235											✔	
			'2236											✔	
	U	3S	'7202LA											✔	
1K Words × 18 Bits	U, C	3S	'7811											✔	
			'7881											✔	
	U	3S	'7802											✔	
1K Words × 36 Bits	U, C	3S	'3641											✔	
1K × 36 × 2 Bits	B, C	3S	'3642											+	
2K Words × 9 Bits	U, C	3S	'7807											✔	
	U	3S	'7203L											✔	
			'7808											✔	
2K Words × 18 Bits	U, C	3S	'7882											✔	
2K Words × 36 Bits	U, C	3S	'3651											+	
4K Words × 9 Bits	U	3S	'7204L											✔	
4K Words × 18 Bits	U, C	3S	'7884											✔	

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

† U = Unidirectional
B = Bidirectional
C = Clocked
S = Synchronized

TEXAS INSTRUMENTS
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3.3-V Clock-Distribution Circuits (CDC)

DESCRIPTION	I/O LEVELS	TYPE	TECHNOLOGY			
			AS	AC	ACT	ABT
3.3-V Hex Inverting Clock Drivers/Buffers	CMOS/CMOS	'203		✔		
1-to-9 Differential LVPECL Buffers	LVPECL/LVPECL	'111				+
1-to-9 Differential LVPECL Buffers With Output Enable	LVPECL/LVPECL	'112				+
1-to-10 Buffers With Output Enable	TTL/TTL	'351				✔
		'2351				✔
1-to-6 PLL Clock Drivers	TTL/TTL	'536				+
		'2536				+
1-to-12 PLL Clock Drivers	TTL/TTL	'586				✔
		'2586				✔
	LVPECL/TTL	'582				+
		'2582				+
Phase-Locked-Loop 1-to-16 Clock Drivers	SSTL/TTL	'587				+
		'2587				+
P5 Motherboard Clock Synthesizers/Drivers	TTL/TTL	'9841				✔
		'9842				✔
		'9843				✔
P6 Motherboard Clock Synthesizers/Drivers	TTL/TTL	'916				+
PC Motherboard Clock Generators With Dual 1-to-4 Buffers	TTL/TTL	'913				+

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

5-V Clock-Distribution Circuits (CDC)

DESCRIPTION	I/O LEVELS	TYPE	TECHNOLOGY			
			AS	AC	ACT	ABT
Hex Inverters	CMOS/CMOS	'204		✔		
		'204-7		✔		
1-to-6 Exclusive ORs	TTL/TTL	'328				✔
	TTL/CMOS	'329				✔
1-to-6 Exclusive ORs With Output Enable	TTL/TTL	'391				✔
	TTL/CMOS	'392				✔
Dual 1-to-4 Buffers (2 inputs, 8 outputs)	TTL/CMOS	'208			✔	
		'208-7			✔	
	CMOS/CMOS	'209		✔		
		'209-7		✔		
1-to-8 Divide-by-2 Flip-Flops (6 inverting, 2 noninverting)	TTL/TTL	'303	✔			
1-to-8 Divide-by-2 Flip-Flops (8 noninverting)	TTL/TTL	'304	✔			
1-to-8 Divide-by-2 Flip-Flops (4 inverting, 4 noninverting)	TTL/TTL	'305	✔			
1-to-8 Fanouts (4 noninverting buffers, 4 divide-by-2 flip-flops)	TTL/CMOS	'337				✔
	TTL/TTL	'339				✔
1-to-8 NANDs	TTL/TTL	'340				✔
1-to-8 ANDs	TTL/TTL	'341				✔
3-Way Fanout Buffers (dual 1-to-3 noninverting buffers, 1-to-4 divide-by-2 flip-flops)	TTL/TTL	'330				✔

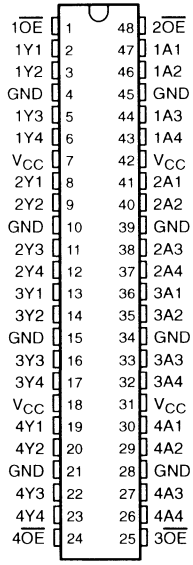
✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Contents

- **Member of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced Low-Voltage BiCMOS (ALB) Technology Design for 3.3-V Operation**
- **Schottky Diodes on All Inputs to Eliminate Overshoot and Undershoot**
- **Industry Standard '16244 Pinout**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

The SN74ALB16244 16-bit buffer and line driver is designed for high-speed, low-voltage (3.3-V) V_{CC} operation. This device is intended to replace the conventional driver in any speed-critical path. The small propagation delay is achieved using a unity gain amplifier on the input and feedback resistors from input to output, which allows the output to track the input with a small offset voltage.

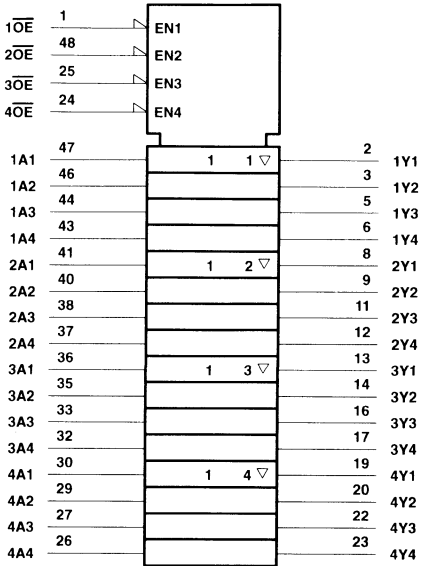
The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. This device provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

The SN74ALB16244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

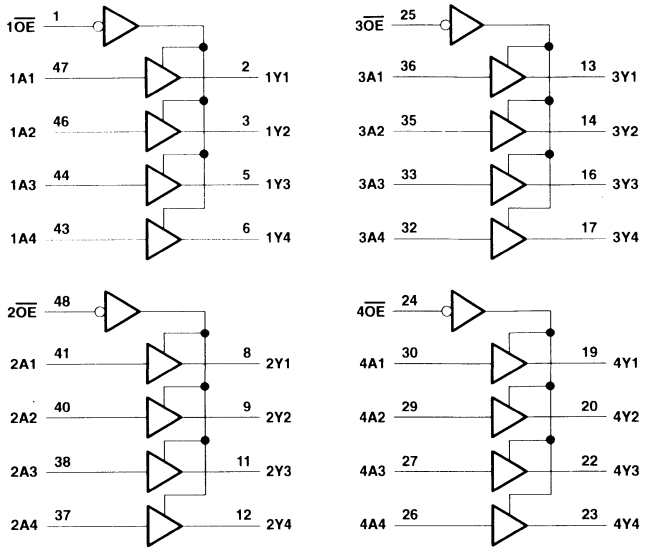
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			MIN	MAX	UNIT
V_{CC}	Supply voltage		3	3.6	V
I_{OH}†	High-level output current			–25	mA
I_{OL}†	Low-level output current			25	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		5	ns/V
T_A	Operating free-air temperature		–40	85	°C

† Refer to Figures 1 and 2 for typical I/O ranges.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP‡	MAX	UNIT
V_{IK}	Data inputs	V_{CC} = 3 V	I_I = 18 mA			3.6	V_{CC}–1.2	V
			I_I = –18 mA			–0.9	–1.2	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND				±10	µA
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}	$\overline{OE}$ low		0.4	0.6	mA
				$\overline{OE}$ high			25	µA
			V_I = 0	$\overline{OE}$ low		–0.8	–1	mA
				$\overline{OE}$ high			–60	µA
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			0.6	20	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–0.1	–50	µA
I_{CC}/buffer		V_{CC} = 3.6 V,	I_O = 0,	V_I = V_{CC} or GND		3.7	5.6	mA
I_{CCZ}		V_{CC} = 3.6 V,	Control inputs = V_{CC} or GND				0.8	mA
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND					600	µA
C_i		V_I = 3 V or 0				4.5		pF
C_o		V_O = 3 V or 0				5.5		pF

‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			UNIT
			MIN	TYP‡	MAX	
t_{pd}	A	Y	0.6	1.3	2	ns
t_{en}	$\overline{OE}$	Y	1.3	2.5	4.7	ns
t_{dis}	$\overline{OE}$	Y	1.8	2.8	4.2	ns

‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

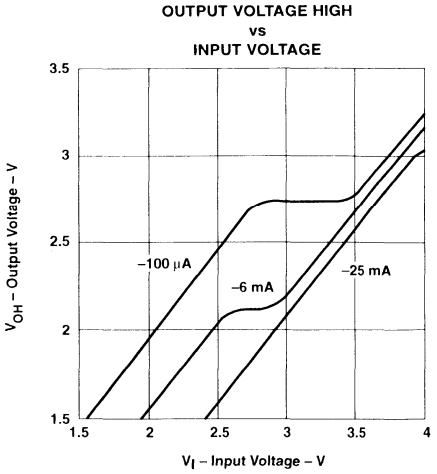


Figure 1. V_{OH} Over Recommended Free-Air Temperature Range

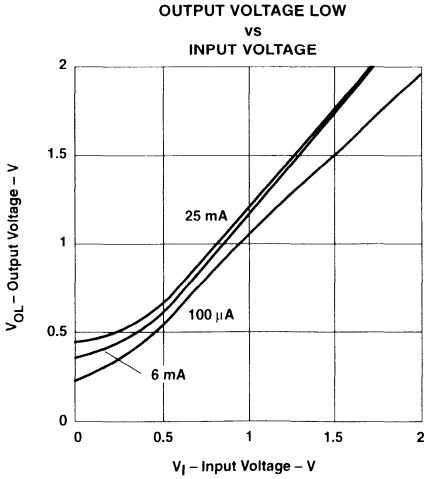
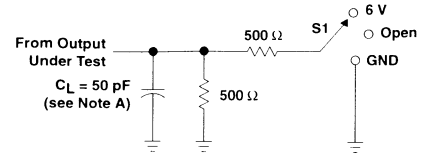


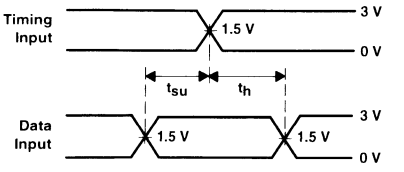
Figure 2. V_{OL} Over Recommended Free-Air Temperature Range

PARAMETER MEASUREMENT INFORMATION

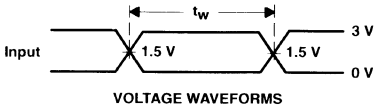


LOAD CIRCUIT

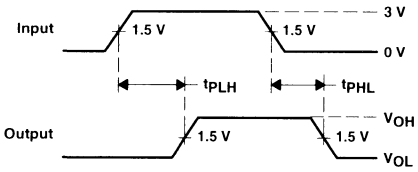
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



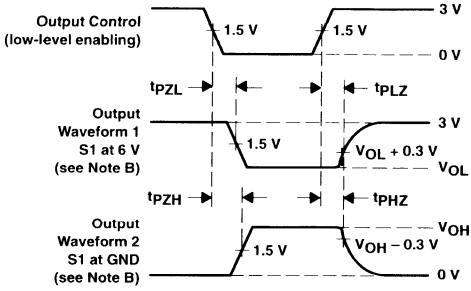
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



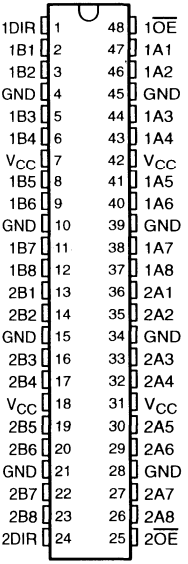
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced Low-Voltage BiCMOS (ALB) Technology Design for 3.3-V Operation**
- **Schottky Diodes on All Inputs to Eliminate Overshoot and Undershoot**
- **Industry Standard '16245 Pinout**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

The SN74ALB16245 is a 16-bit transceiver designed for high-speed, low-voltage (3.3-V) V_{CC} operation. This device is intended to replace the conventional transceiver in any speed-critical path. The small propagation delay is achieved using a unity gain amplifier on the input and feedback resistors from input to output, which allows the output to track the input with a small offset voltage.

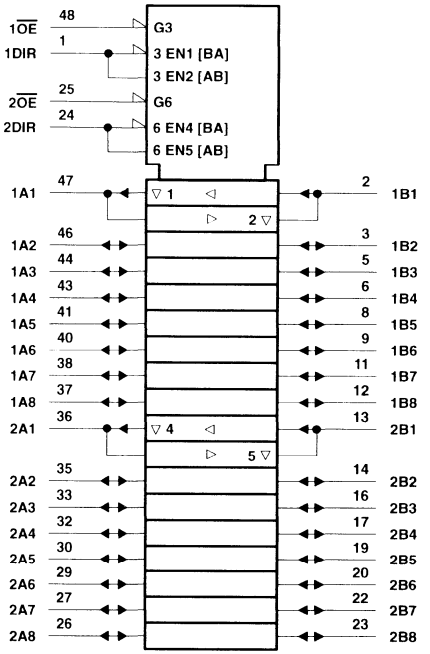
This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

The SN74ALB16245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

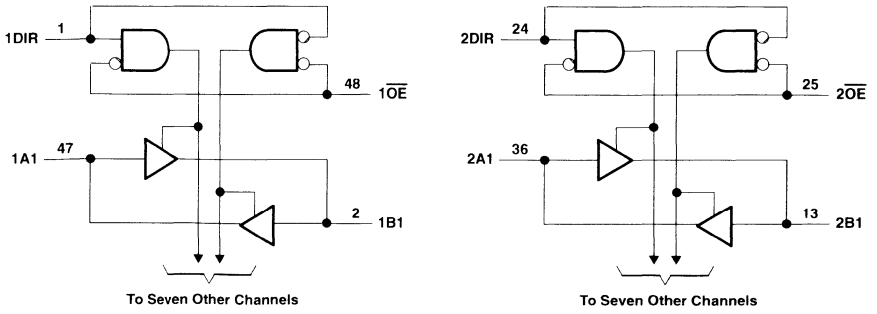
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			MIN	MAX	UNIT
V_{CC}	Supply voltage		3	3.6	V
I_{OH}‡	High-level output current			–25	mA
I_{OL}‡	Low-level output current			25	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		5	ns/V
T_A	Operating free-air temperature		–40	85	°C

‡ Refer to Figures 1 and 2 for typical I/O ranges.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP§	MAX	UNIT
V_{IK}	A or B ports	V_{CC} = 3 V	I_I = 18 mA			3.7	V_{CC}+1.2	V
			I_I = –18 mA			–0.9	–1.2	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND				±10	µA
	A or B ports	V_{CC} = 3.6 V	V_I = V_{CC}	$\overline{OE}$ low		0.4	0.6	mA
				$\overline{OE}$ high			25	µA
			V_I = 0	$\overline{OE}$ low		–0.7	–1	mA
				$\overline{OE}$ high			–60	µA
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			0.7	20	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–0.2	–50	µA
I_{CC}/buffer		V_{CC} = 3.6 V,	I_O = 0,	V_I = V_{CC} or GND		3.7	5.6	mA
I_{CCZ}		V_{CC} = 3.6 V,	Control inputs = V_{CC} or GND				0.8	mA
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND					600	µA
C_i		V_I = 3 V or 0				3.5		pF
C_{io}		V_O = 3 V or 0				7.5		pF

§ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			UNIT
			MIN	TYP†	MAX	
t_{pd}	A or B	B or A	0.6	1.3	2	ns
t_{en}	$\overline{OE}$	A or B	1.5	3.2	6	ns
t_{dis}	$\overline{OE}$	A or B	1.8	2.8	4.2	ns

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

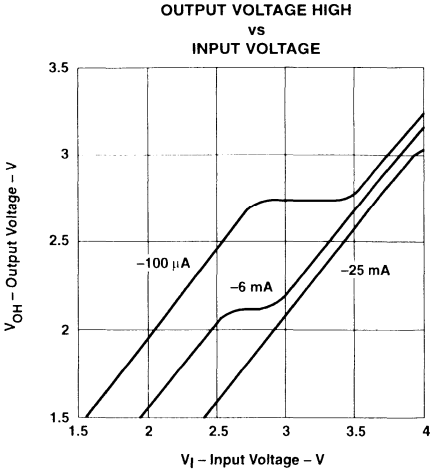


Figure 1. V_{OH} Over Recommended Free-Air Temperature Range

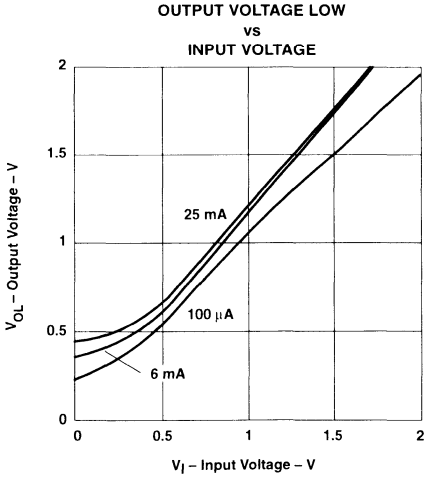
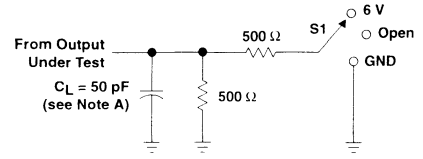


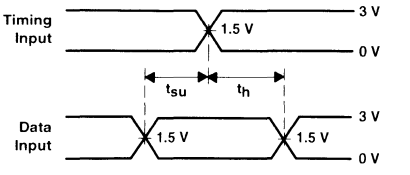
Figure 2. V_{OL} Over Recommended Free-Air Temperature Range

PARAMETER MEASUREMENT INFORMATION

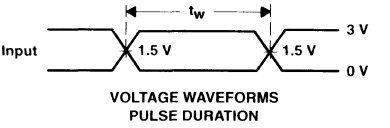


LOAD CIRCUIT

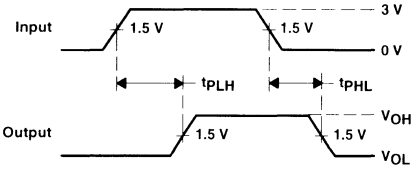
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



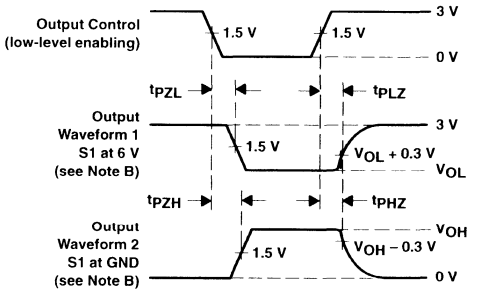
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

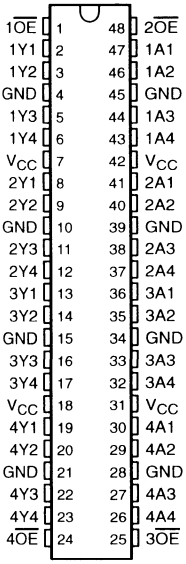
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms

Contents

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16240 is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides inverting outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

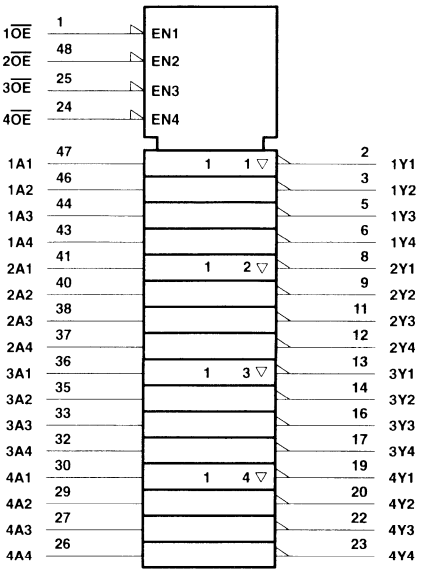
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

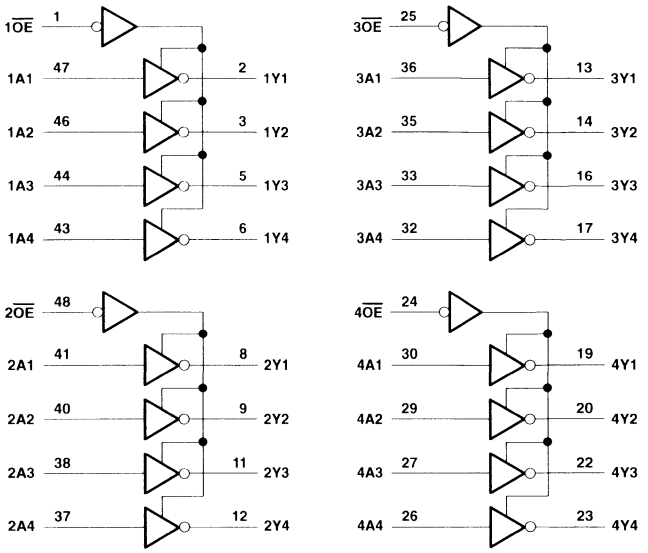
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

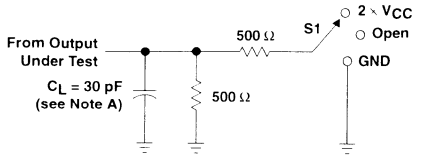
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	5.3		5.3	1	3.9	ns
t_{en}	$\overline{OE}$	Y	1	6.4		6.1	1	5	ns
t_{dis}	$\overline{OE}$	Y	1	5.4		4.8	1	4.4	ns

operating characteristics, T_A = 25°C

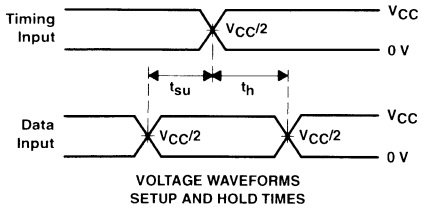
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	19	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

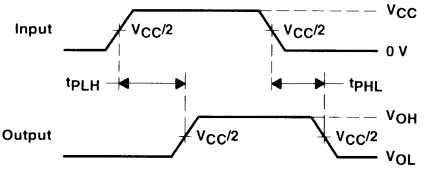


LOAD CIRCUIT

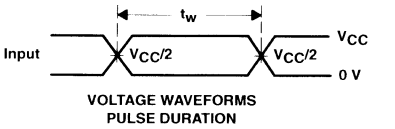
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



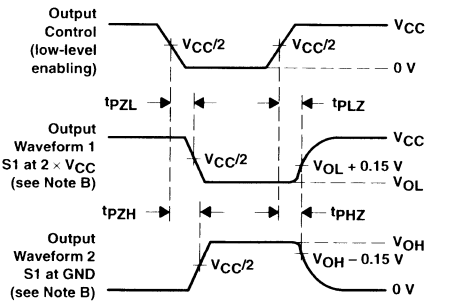
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

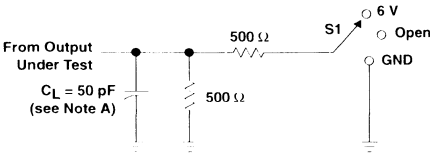


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

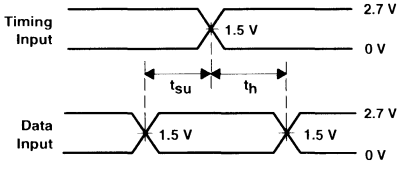
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

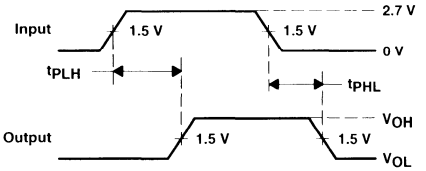


LOAD CIRCUIT

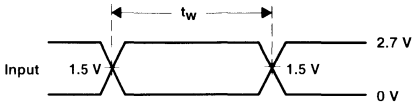
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



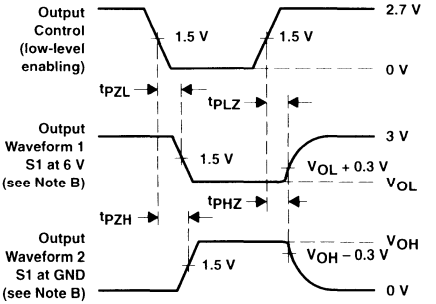
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



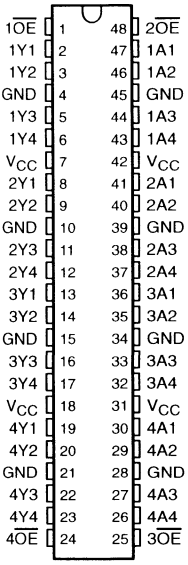
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVC16244A is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVC16244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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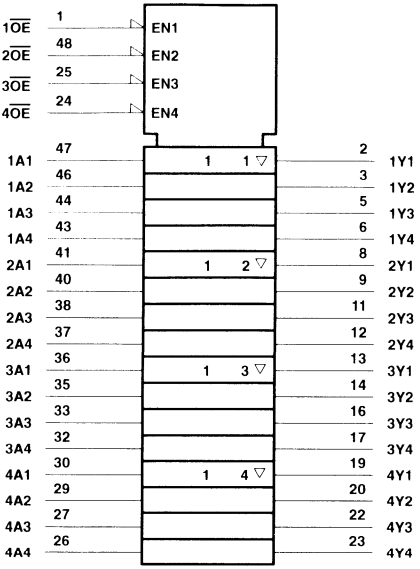
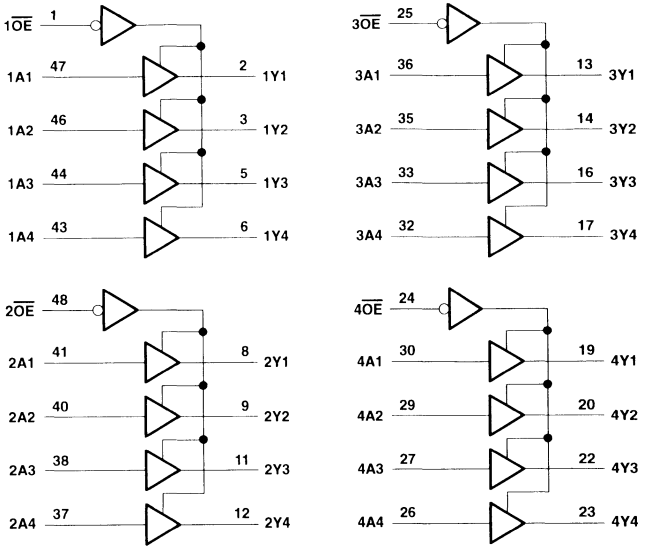
TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265
POST OFFICE BOX 1443 • HOUSTON, TEXAS 77251–1443

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

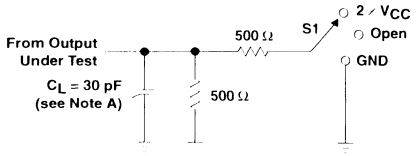
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.4		4	1	3.6	ns
t_{en}	$\overline{OE}$	Y	1	6.3		6	1	5	ns
t_{dis}	$\overline{OE}$	Y	1	5.8		5.2	1	5	ns

operating characteristics, T_A = 25°C

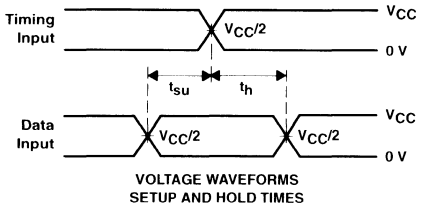
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	19	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

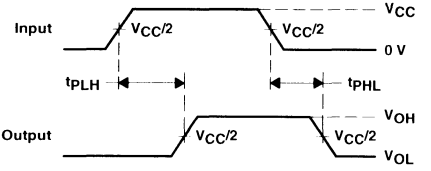


LOAD CIRCUIT

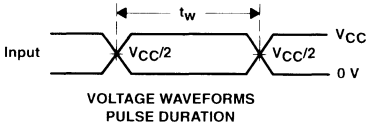
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



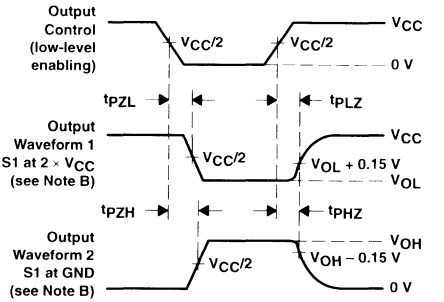
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

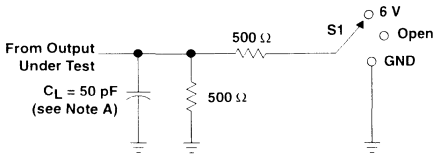


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

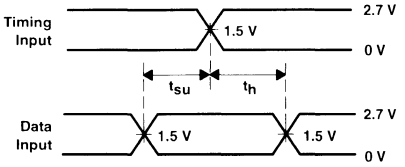
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

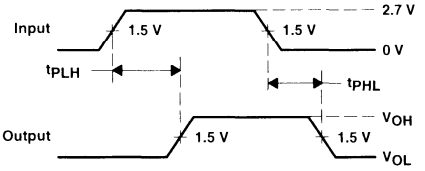


LOAD CIRCUIT

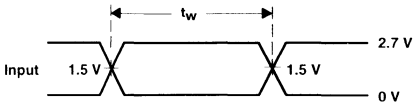
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



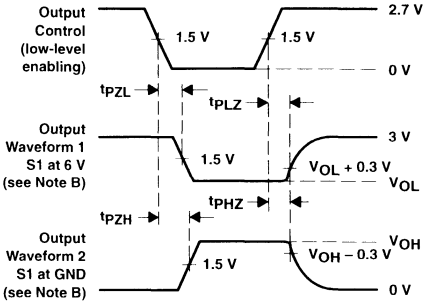
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



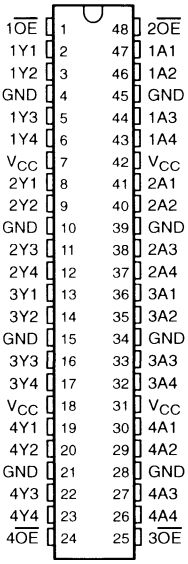
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16244 is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

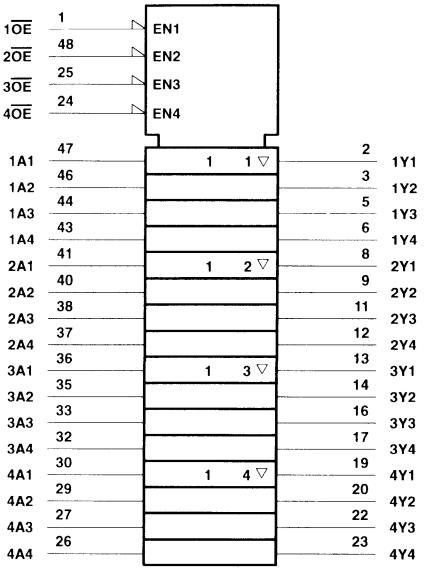
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

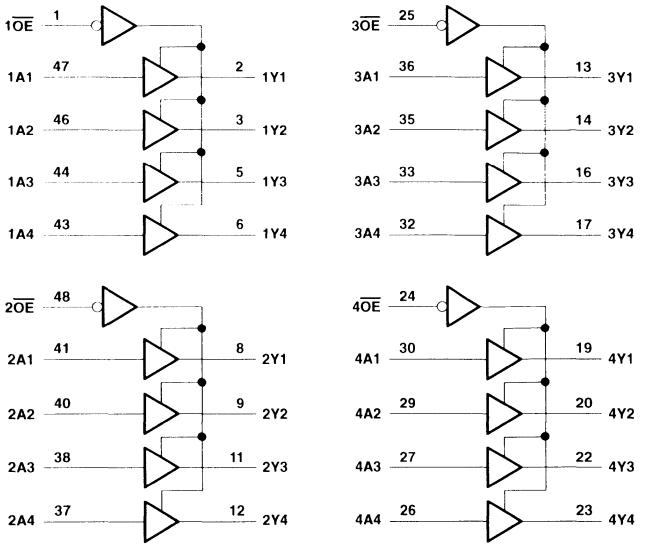
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DGV package . . . . . 93°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

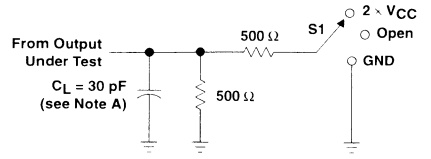
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	3.7		3.6	1	3	ns
t_{en}	$\overline{OE}$	Y	1	5.7		5.4	1	4.4	ns
t_{dis}	$\overline{OE}$	Y	1	5.2		4.6	1	4.1	ns

operating characteristics, T_A = 25°C

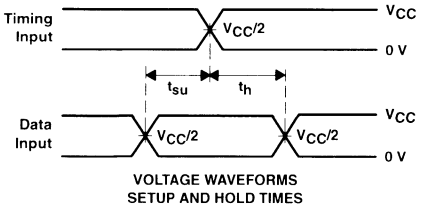
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	19	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

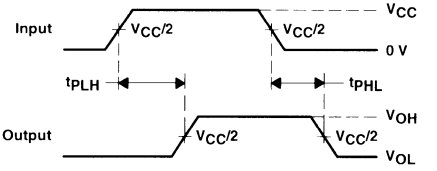


LOAD CIRCUIT

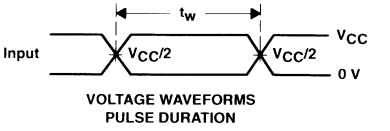
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



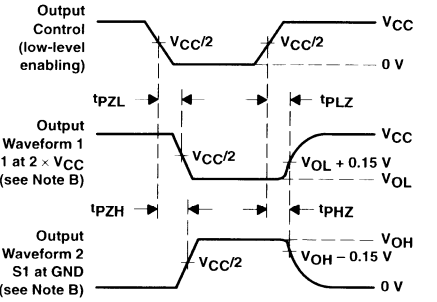
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

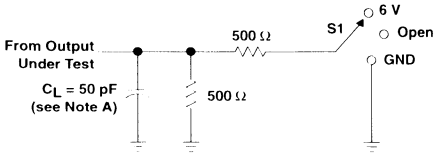


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

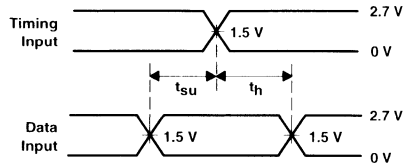
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

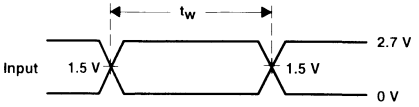


LOAD CIRCUIT

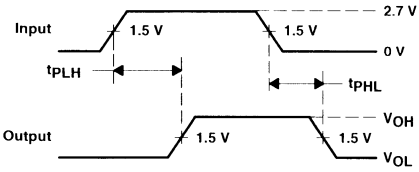
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



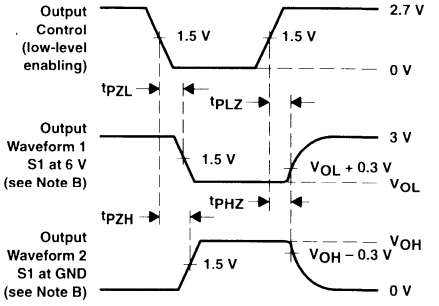
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



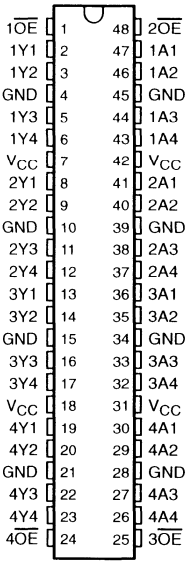
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162244 is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

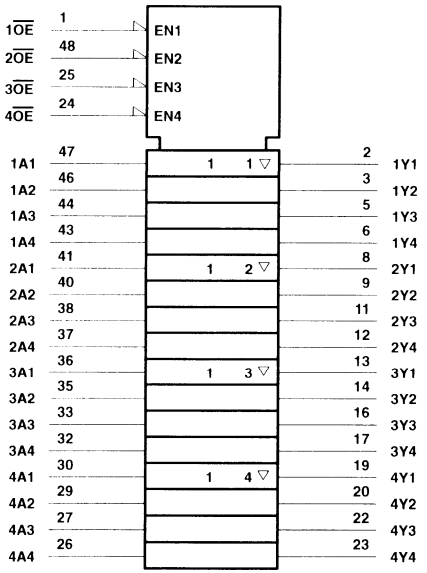
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

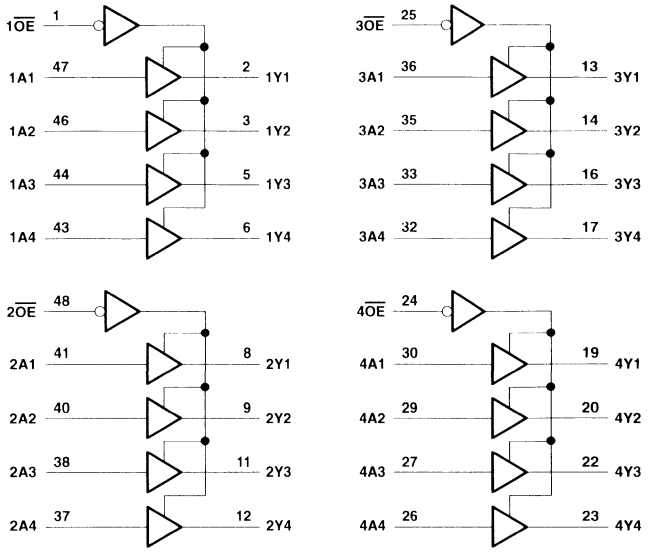
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

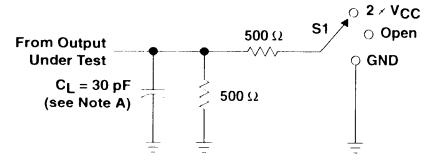
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.9		4.7	1	4.2	ns
t_{en}	$\overline{OE}$	Y	1	6.8		6.7	1	5.6	ns
t_{dis}	$\overline{OE}$	Y	1	6.3		5.7	1	5.5	ns

operating characteristics, T_A = 25°C

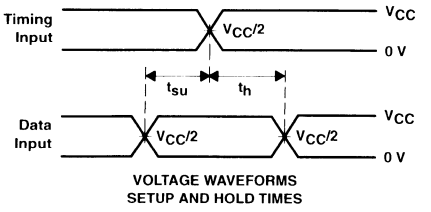
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	19	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

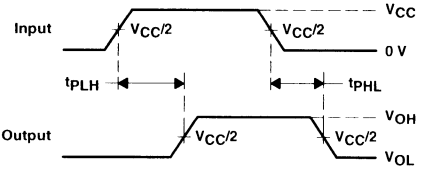


LOAD CIRCUIT

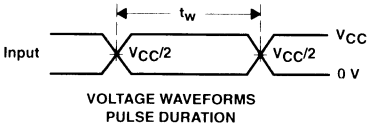
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



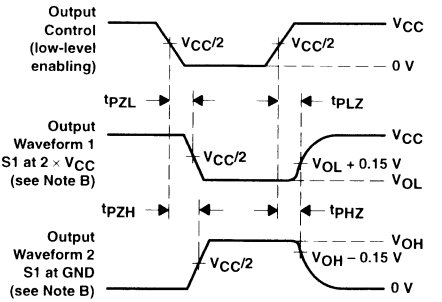
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

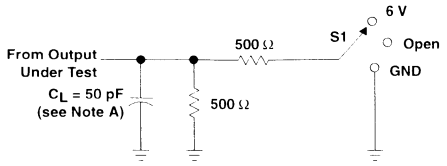


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

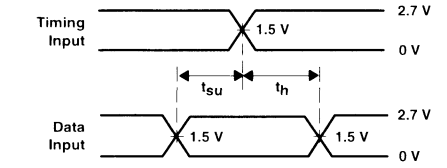
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

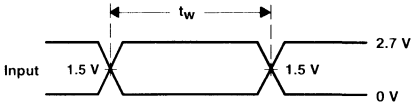


LOAD CIRCUIT

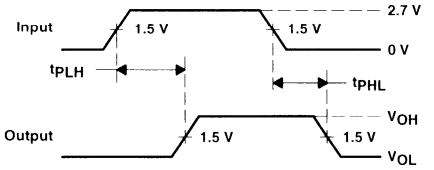
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



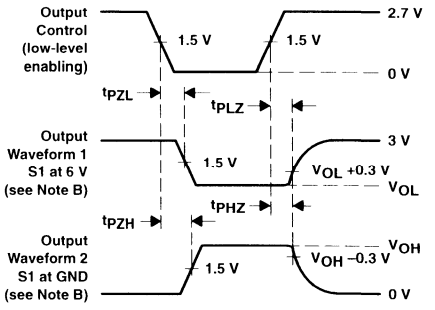
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



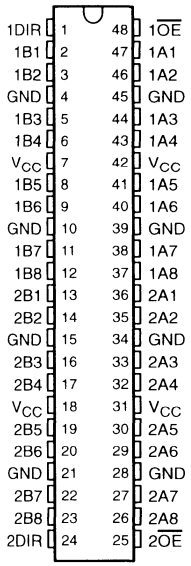
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16245 is designed for asynchronous communication between data buses. The control-function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

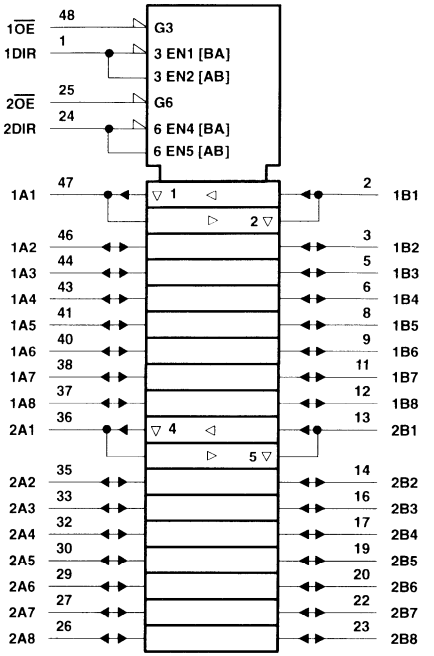
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

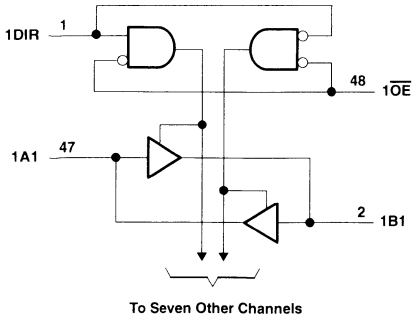
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

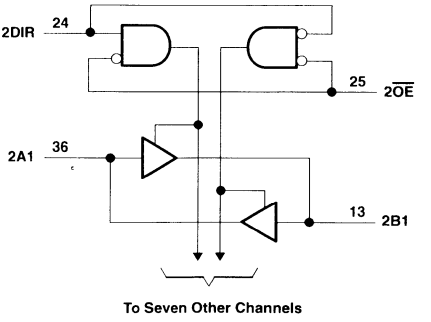
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output-voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DGV package . . . . . 93°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

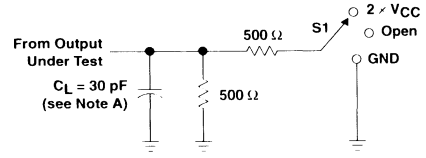
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	3.7		3.6	1	3	ns
t_{en}	$\overline{OE}$	A or B	1	5.7		5.4	1	4.4	ns
t_{dis}	$\overline{OE}$	A or B	1	5.2		4.6	1	4.1	ns

operating characteristics, T_A = 25° C

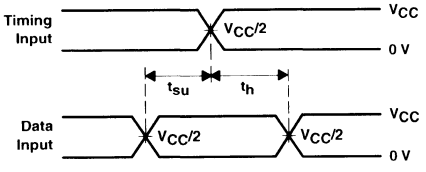
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	22	29	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

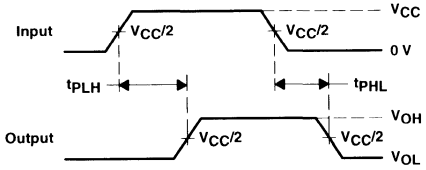


LOAD CIRCUIT

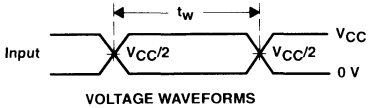
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



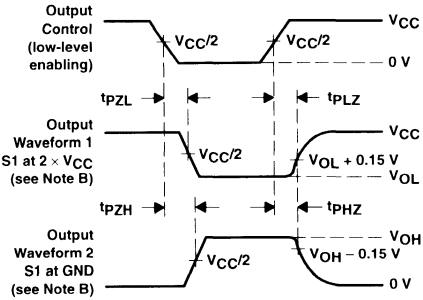
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

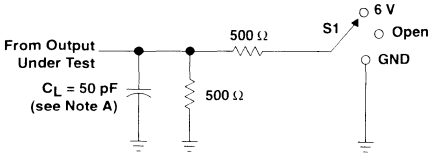


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

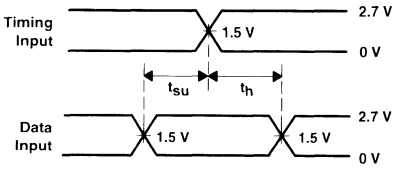
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

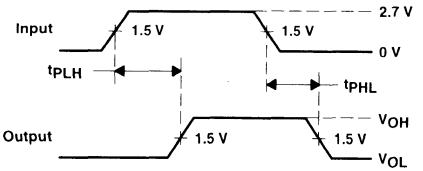


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

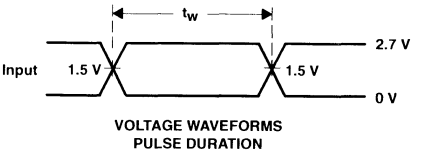
LOAD CIRCUIT



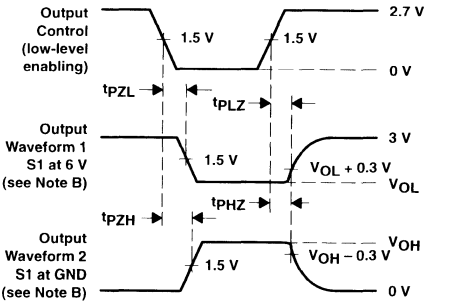
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



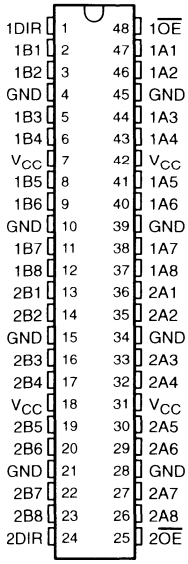
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **All Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCHR162245 is designed for asynchronous communication between data buses. The control-function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

All outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

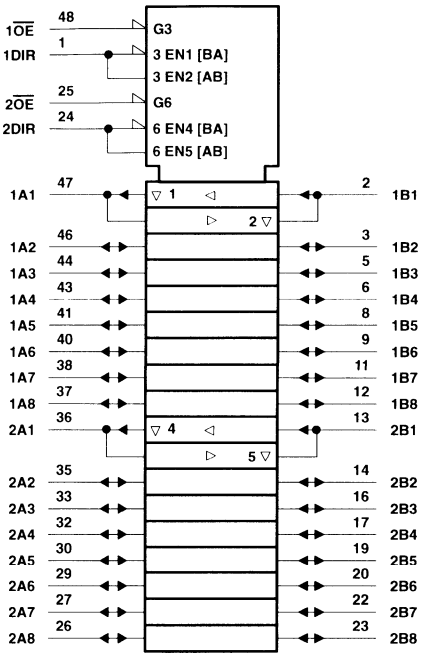
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCHR162245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

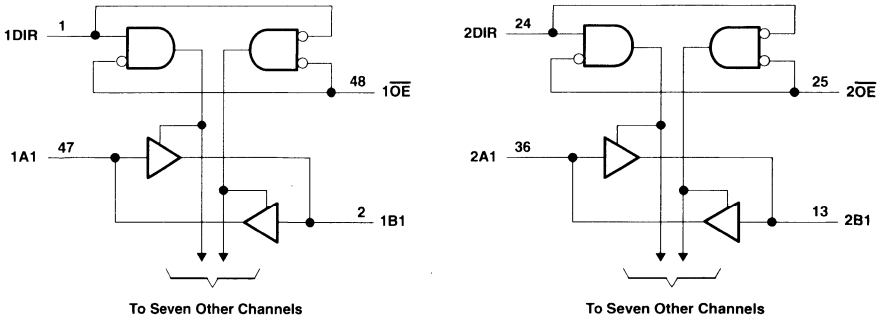
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA	V_{IH} = 1.7 V	2.3 V	1.9			
			V_{IH} = 2 V	2.7 V	2.2			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA	V_{IL} = 0.7 V	2.3 V			0.4	
			V_{IH} = 2 V	2.7 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

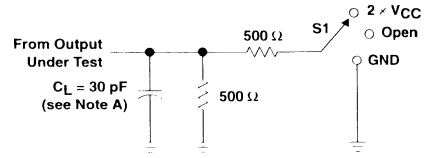
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	4.9		4.7	1	4.2	ns
t_{en}	$\overline{OE}$	B or A	1	6.8		6.7	1	5.6	ns
t_{dis}	$\overline{OE}$	B or A	1	6.3		5.7	1	5.5	ns

operating characteristics, T_A = 25°C

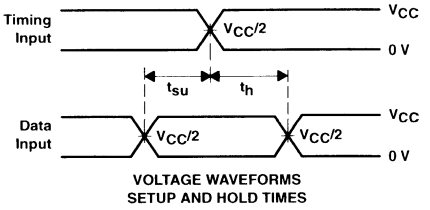
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	24	32	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

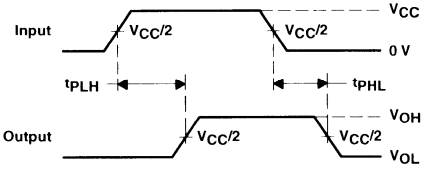


LOAD CIRCUIT

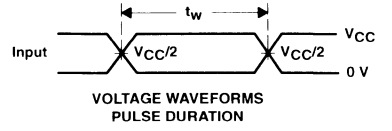
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



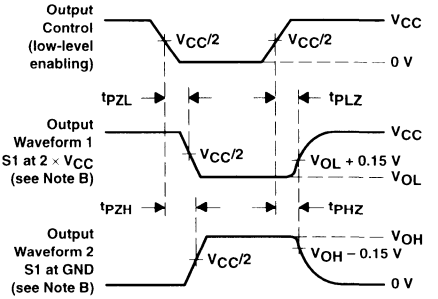
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

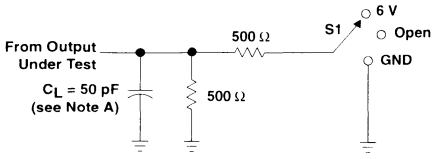


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

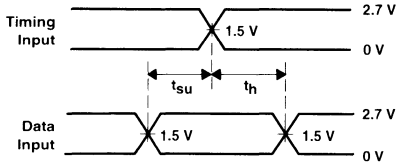
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

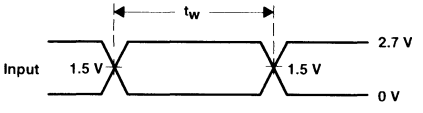


LOAD CIRCUIT

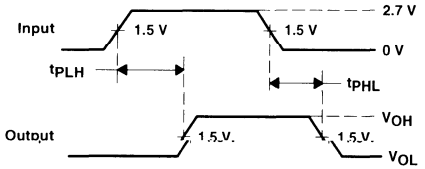
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



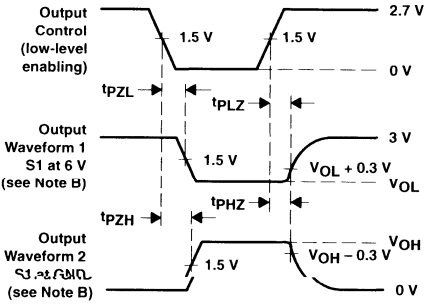
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



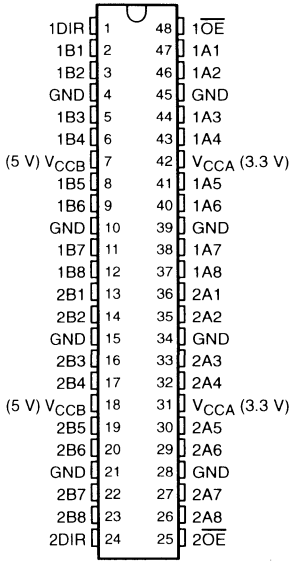
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver contains two separate supply rails; B port has V_{CCB}, which is set at 5 V, and A port has V_{CCA}, which is set to operate at 3.3 V. This allows for translation from a 3.3-V to a 5-V environment and vice-versa.

The SN74ALVC164245 is designed for asynchronous communication between data buses.

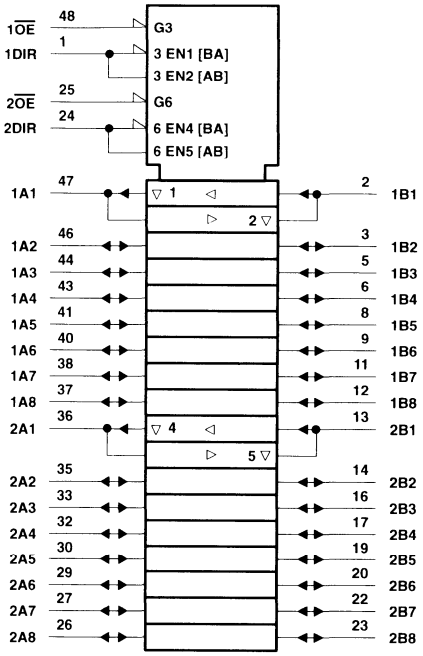
To ensure the high-impedance state during power up or power down, the output-enable ($\overline{OE}$) input should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVC164245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

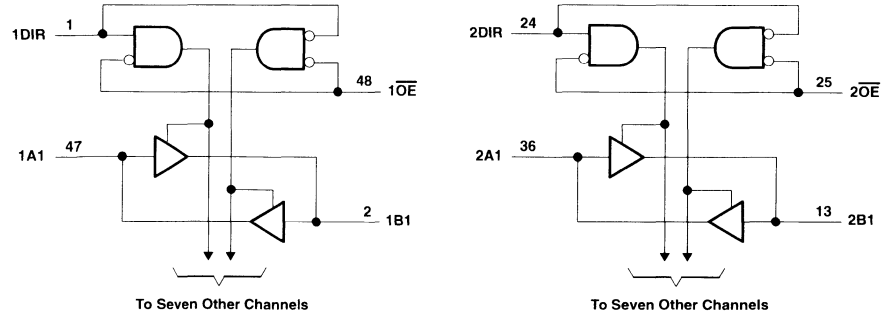
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range for V_{CCB} at 5 V (unless otherwise noted)†

Supply voltage range, V_{CCB} ..... –0.5 V to 6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6 V
Output voltage range, V_O (see Note 1) ..... –0.5 V to V_{CCB} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CCB}$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CCB}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CCB}) ..... ±50 mA
Continuous current through each V_{CCB} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 2): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. This value is limited to 6 V maximum.
2. The package thermal impedance is calculated in accordance with JESD 51.

absolute maximum ratings over operating free-air temperature range for V_{CCA} at 3.3 V (unless otherwise noted)†

Supply voltage range, V_{CCA} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 3) ..... –0.5 V to 4.6 V
I/O ports (see Note 3) ..... –0.5 V to V_{CCA} + 0.5 V
Output voltage range, V_O (see Note 3) ..... –0.5 V to V_{CCA} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CCA}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CCA}) ..... ±50 mA
Continuous current through each V_{CCA} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 2): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 2. The package thermal impedance is calculated in accordance with JESD 51.
3. This value is limited to 4.6 V maximum.

recommended operating conditions for V_{CCB} at 5 V (see Note 3)

		MIN	MAX	UNIT
V_{CCB}	Supply voltage	4.5	5.5	V
V_{IH}	High-level input voltage	2		V
V_{IL}	Low-level input voltage		0.8	V
V_{IA}	Input voltage	0	V_{CCB}	V
V_{OB}	Output voltage	0	V_{CCB}	V
I_{OH}	High-level output current		–24	mA
I_{OL}	Low-level output current		24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_A	Operating free-air temperature	–40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.

recommended operating conditions for V_{CCA} at 3.3 V (see Note 3)

			MIN	MAX	UNIT
V_{CCA}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CCA} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CCA} = 2.7 V to 3.6 V		0.8	V
V_{IB}	Input voltage		0	V_{CCA}	V
V_{OA}	Output voltage		0	V_{CCA}	V
I_{OH}	High-level output current	V_{CCA} = 2.7 V		–12	mA
		V_{CCA} = 3 V		–24	
I_{OL}	Low-level output current	V_{CCA} = 2.7 V		12	mA
		V_{CCA} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range for V_{CCB} = 5 V (unless otherwise noted) (see Note 4)

PARAMETER		TEST CONDITIONS	V_{CCB}	MIN	TYP†	MAX	UNIT
V_{OH} (A to B)		I_{OH} = –100 µA	4.5 V	4.3			V
			5.5 V	5.3			
		I_{OH} = –24 mA	4.5 V	3.7			
			5.5 V	4.7			
V_{OL} (A to B)		I_{OL} = 100 µA	4.5 V			0.2	V
			5.5 V			0.2	
		I_{OL} = 24 mA	4.5 V			0.55	
			5.5 V			0.55	
I_I	Control inputs	V_I = V_{CCB} or GND	5.5 V			±5	µA
I_{OZ}‡	A or B ports	V_O = V_{CCB} or GND	5.5 V				µA
I_{CC}		V_I = V_{CCB} or GND, I_O = 0	5.5 V				µA
ΔI_{CC}§		One input at 3.4 V, Other inputs at V_{CCB} or GND	4.5 V to 5.5 V				µA
C_i	Control inputs	V_I = V_{CCB} or GND	5 V		6.5		pF
C_{io}	A or B ports	V_O = V_{CCB} or GND	5 V		6.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather then at 0 V or V_{CCA}.
NOTE 4: V_{CCA} = 2.7 V to 3.6 V

electrical characteristics over recommended operating free-air temperature range for V_{CCA} = 3.3 V (unless otherwise noted) (see Note 5)

PARAMETER		TEST CONDITIONS	V_{CCA}¶	MIN	TYP†	MAX	UNIT
V_{OH} (B to A)		I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA	2.7 V	2.2			
			3 V	2.4			
		I_{OH} = –24 mA	3 V	2			
V_{OL} (B to A)		I_{OL} = 100 µA	MIN to MAX			0.2	V
		I_{OL} = 12 mA	2.7 V			0.4	
		I_{OL} = 24 mA	3 V			0.55	
I_I	Control inputs	V_I = V_{CCA} or GND	3.6 V			±5	µA
I_{OZ}‡		V_O = V_{CCA} or GND	3.6 V			±10	µA
I_{CC}		V_I = V_{CCA} or GND, I_O = 0	3.6 V			40	µA
ΔI_{CC}§		One input at V_{CCA} – 0.6 V, Other inputs at V_{CCA} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CCA} or GND	3.3 V		6.5		pF
C_{io}	A or B ports	V_O = V_{CCA} or GND	3.3 V		8.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather then at 0 V or V_{CCA}.
¶ For conditions shown as MIN to MAX, use the appropriate values under recommended operating conditions.
NOTE 5: V_{CCB} = 5 V ± 0.5 V

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

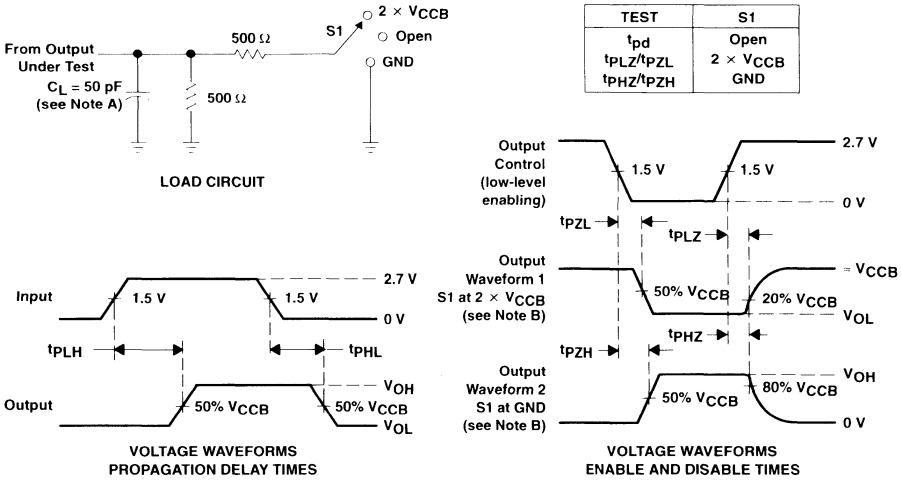
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 5 V ± 0.5 V				UNIT
			V_{CCA} = 2.7 V		V_{CCA} = 3.3 V ± 0.3 V		
			MIN	MAX†	MIN†	MAX†	
t_{pd}	A	B		5.9	1	5.8	ns
	B	A		6.7	1.2	5.8	
t_{en}	$\overline{OE}$	B		9.3	1	8.9	ns
t_{dis}	$\overline{OE}$	B		9.2	2.1	9.5	ns
t_{en}	$\overline{OE}$	A		10.2	2	9.1	ns
t_{dis}	$\overline{OE}$	A		9	2.9	8.6	ns

† This datasheet limit can vary among suppliers.

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CCA} = 3.3 V V_{CCB} = 5 V	UNIT
				TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled (A or B)	C_L = 50 pF, f = 10 MHz	56	pF
		Outputs disabled (A or B)		6	

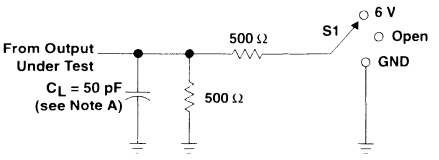
PARAMETER MEASUREMENT INFORMATION
V_{CCB} = 5 V ± 0.5 V



NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

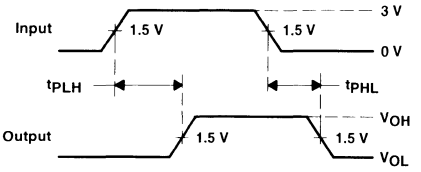
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CCA} = 2.7 V AND 3.3 V ± 0.3 V

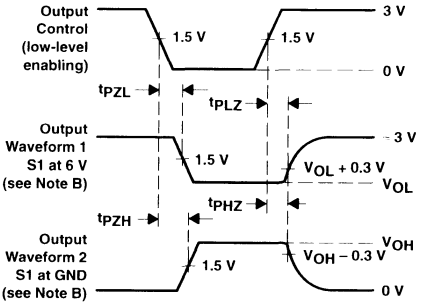


LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



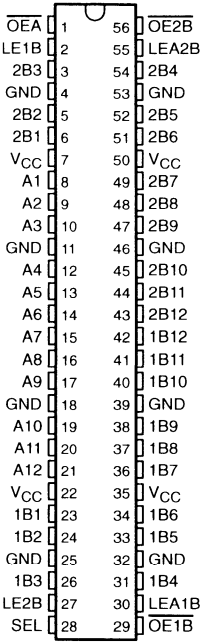
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 12-bit to 24-bit multiplexed D-type latch is designed for 2.3-V to 3.6-V_{CC} operation.

The SN74ALVCH16260 is used in applications in which two separate datapaths must be multiplexed onto, or demultiplexed from, a single datapath. Typical applications include multiplexing and/or demultiplexing address and data information in microprocessor or bus-interface applications. This device is also useful in memory-interleaving applications.

Three 12-bit I/O ports (A1–A12, 1B1–1B12, and 2B1–2B12) are available for address and/or data transfer. The output-enable ($\overline{OE1B}$, $\overline{OE2B}$, and $\overline{OEA}$) inputs control the bus transceiver functions. The $\overline{OE1B}$ and $\overline{OE2B}$ control signals also allow bank control in the A-to-B direction.

Address and/or data information can be stored using the internal storage latches. The latch-enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch-enable input is high, the latch is transparent. When the latch-enable input goes low, the data present at the inputs is latched and remains latched until the latch-enable input is returned high.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16260 is characterized for operation from –40°C to 85°C.

Function Tables

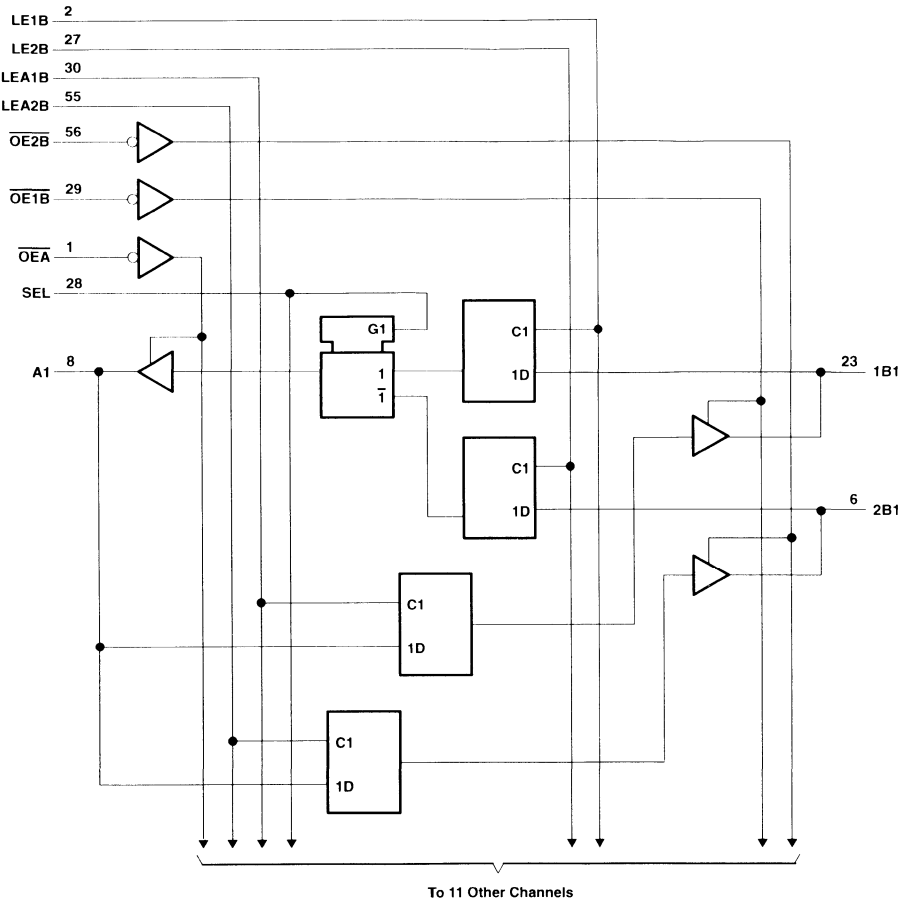
B TO A ($\overline{OEB}$ = H)

INPUTS						OUTPUT
1B	2B	SEL	LE1B	LE2B	$\overline{OEA}$	A
H	X	H	H	X	L	H
L	X	H	H	X	L	L
X	X	H	L	X	L	A_0
X	H	L	X	H	L	H
X	L	L	X	H	L	L
X	X	L	X	L	L	A_0
X	X	X	X	X	H	Z

A TO B ($\overline{OEA}$ = H)

INPUTS					OUTPUTS	
A	LEA1B	LEA2B	$\overline{OE1B}$	$\overline{OE2B}$	1B	2B
H	H	H	L	L	H	H
L	H	H	L	L	L	L
H	H	L	L	L	H	$2B_0$
L	H	L	L	L	L	$2B_0$
H	L	H	L	L	$1B_0$	H
L	L	H	L	L	$1B_0$	L
X	L	L	L	L	$1B_0$	$2B_0$
X	X	X	H	H	Z	Z
X	X	X	L	H	Active	Z
X	X	X	H	L	Z	Active
X	X	X	L	L	Active	Active

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high	3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B	1.4		1.1		1.1		ns
t_h	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B	1.6		1.9		1.5		ns

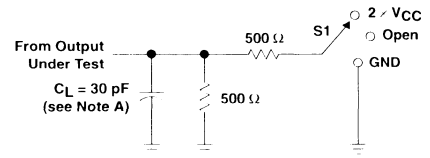
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	5.4		5.1	1.2	4.3	ns
	LE	A or B	1	5.6		5.2	1	4.4	
	SEL	A	1	6.9		6.6	1.1	5.6	
t_{en}	$\overline{OE}$	A or B	1	6.7		6.4	1	5.4	ns
t_{dis}	$\overline{OE}$	A or B	1	5.7		5	1.3	4.6	ns

operating characteristics, T_A = 25°C

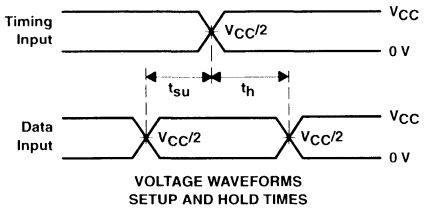
PARAMETER		TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
			TYP	TYP	
C_{pd} Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	87	120	pF
	Outputs disabled		80.5	118	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

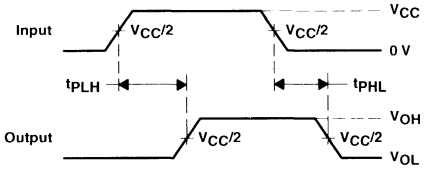


LOAD CIRCUIT

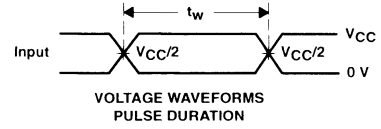
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



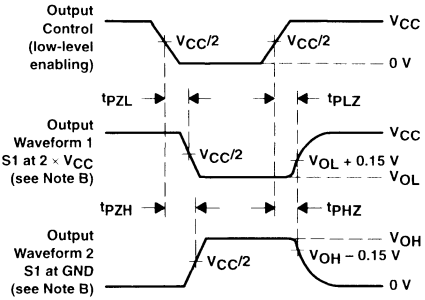
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

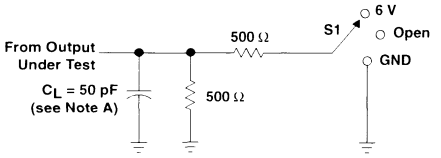


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

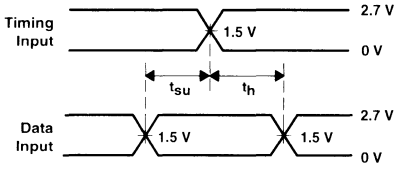
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

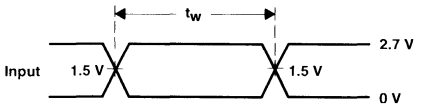


LOAD CIRCUIT

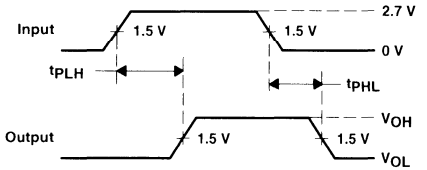
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



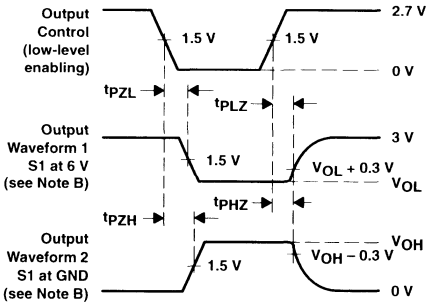
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



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ENABLE AND DISABLE TIMES

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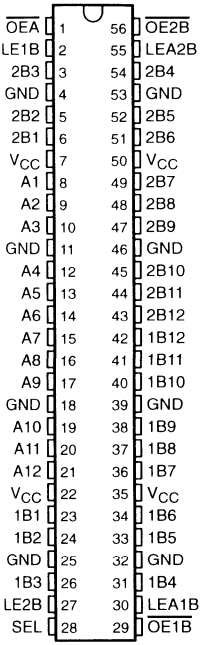
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **B-Port Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Thin-Shrink Small-Outline (DGG) and Plastic Shrink Small-Outline (DL) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

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Three 12-bit I/O ports (A1–A12, 1B1–1B12, and 2B1–2B12) are available for address and/or data transfer. The output-enable ($\overline{OE1B}$, $\overline{OE2B}$, and $\overline{OEA}$) inputs control the bus transceiver functions. The $\overline{OE1B}$ and $\overline{OE2B}$ control signals also allow bank control in the A-to-B direction.

Address and/or data information can be stored using the internal storage latches. The latch-enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch-enable input is high, the latch is transparent. When the latch-enable input goes low, the data present at the inputs is latched and remains latched until the latch-enable input is returned high.

The B outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162260 is characterized for operation from –40°C to 85°C.

Function Tables

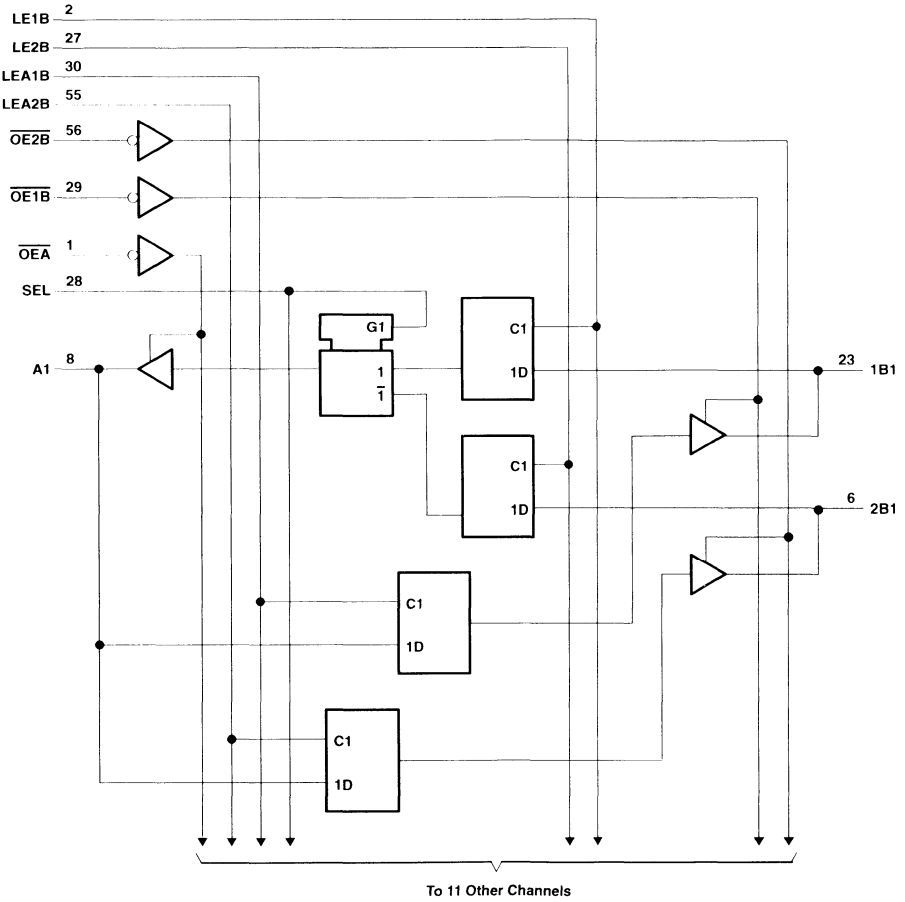
B TO A ($\overline{OEB}$ = H)

INPUTS						OUTPUT
1B	2B	SEL	LE1B	LE2B	$\overline{OEA}$	A
H	X	H	H	X	L	H
L	X	H	H	X	L	L
X	X	H	L	X	L	A_0
X	H	L	X	H	L	H
X	L	L	X	H	L	L
X	X	L	X	L	L	A_0
X	X	X	X	X	H	Z

A TO B ($\overline{OEA}$ = H)

INPUTS					OUTPUTS	
A	LEA1B	LEA2B	$\overline{OE1B}$	$\overline{OE2B}$	1B	2B
H	H	H	L	L	H	H
L	H	H	L	L	L	L
H	H	L	L	L	H	$2B_0$
L	H	L	L	L	L	$2B_0$
H	L	H	L	L	$1B_0$	H
L	L	H	L	L	$1B_0$	L
X	L	L	L	L	$1B_0$	$2B_0$
X	X	X	H	H	Z	Z
X	X	X	L	H	Active	Z
X	X	X	H	L	Z	Active
X	X	X	L	L	Active	Active

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current (A port)	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
	High-level output current (B port)	V_{CC} = 2.3 V		–6	
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current (A port)	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
	Low-level output current (B port)	V_{CC} = 2.3 V		6	
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	A port	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
	B port	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	A port	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
	B port	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		4.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high	3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B	1.4		1.1		1.1		ns
t_h	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B	1.6		1.9		1.5		ns

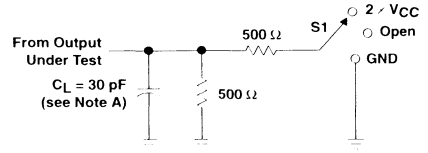
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	B	1	5.9		5.8	1.2	4.9	ns
	B	A	1	6.4		5.1	1.2	4.3	
	LE	A	1	5.6		5.2	1	4.4	
		B	1	6.1		5.9	1	5	
	SEL	A	1	6.9		6.6	1.1	5.6	
t_{en}	$\overline{OE}$	A	1	6.7		6.4	1	5.4	ns
		B	1	7.2		7.1	1	6	
t_{dis}	$\overline{OE}$	A	1	5.7		5	1.3	4.6	ns
		B	1	6.2		5.5	1.3	5.1	

operating characteristics, T_A = 25°C

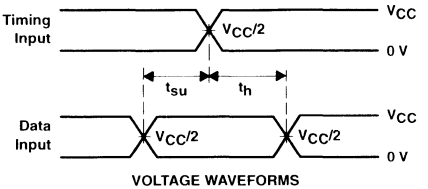
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	62	46	pF
		Outputs disabled		29	24	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

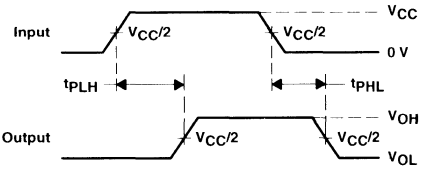


LOAD CIRCUIT

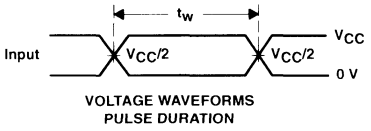
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



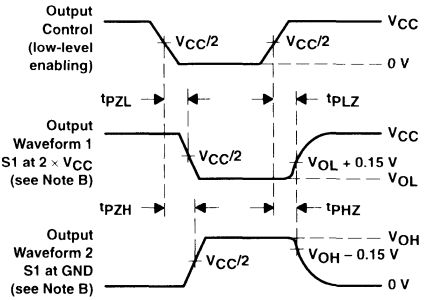
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

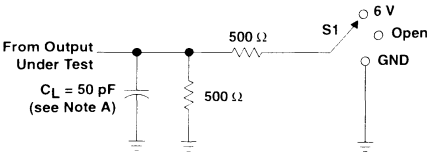


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

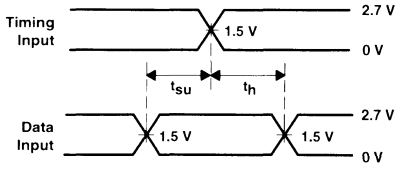
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

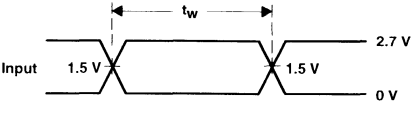


LOAD CIRCUIT

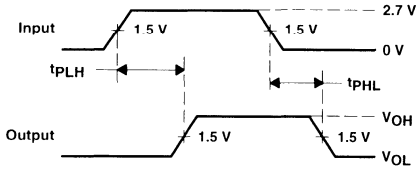
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



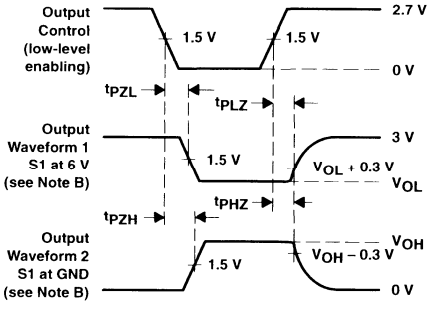
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



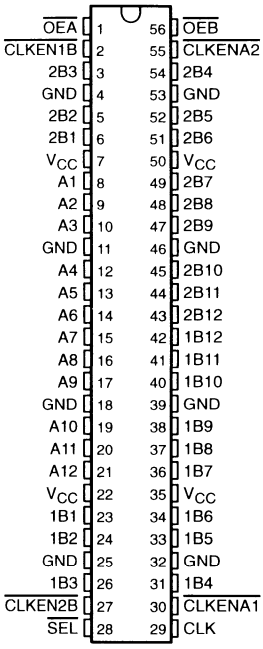
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **B-Port Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 12-bit to 24-bit registered bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162268 is used for applications in which data must be transferred from a narrow high-speed bus to a wide, lower-frequency bus.

The device provides synchronous data exchange between the two ports. Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input when the appropriate clock-enable ($\overline{CLKEN}$) inputs are low. The select ($\overline{SEL}$) line is synchronous with CLK and selects 1B or 2B input data for the A outputs.

For data transfer in the A-to-B direction, a two-stage pipeline is provided in the A-to-1B path, with a single storage register in the A-to-2B path. Proper control of these inputs allows two sequential 12-bit words to be presented synchronously as a 24-bit word on the B port. Data flow is controlled by the active-low output enables ($\overline{OEA}$, $\overline{OEB}$). These control terminals are registered so bus direction changes are synchronous with CLK.

The B outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, a clock pulse should be applied as soon as possible and $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. Due to $\overline{OE}$ being routed through a register, the active state of the outputs cannot be determined prior to the arrival of the first clock pulse.

description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162268 is characterized for operation from –40°C to 85°C.

Function Tables

OUTPUT ENABLE

INPUTS			OUTPUTS	
CLK	$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
↑	H	H	Z	Z
↑	H	L	Z	Active
↑	L	H	Active	Z
↑	L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
H	H	X	X	$1B_0$‡	$2B_0$‡
L	X	↑	L	L†	X
L	X	↑	H	H†	X
X	L	↑	L	X	L
X	L	↑	H	X	H

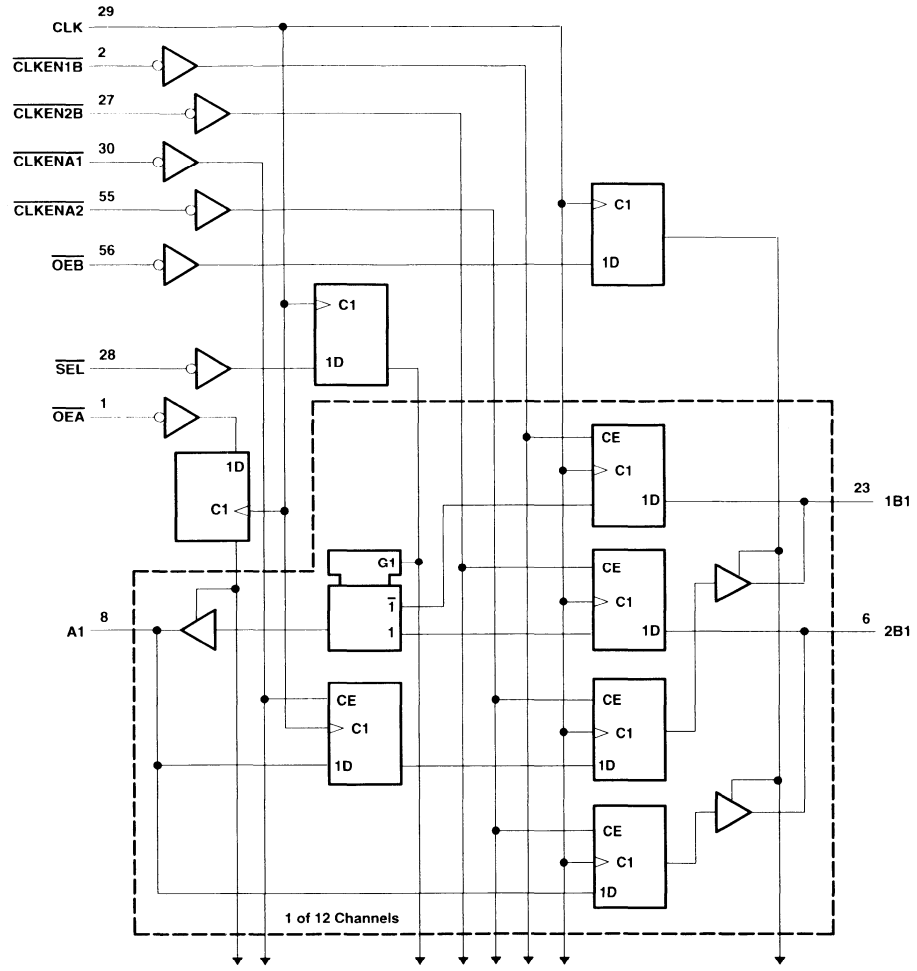
† Two CLK edges are needed to propagate data.
‡ Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS						OUTPUT
$\overline{CLKEN1B}$	$\overline{CLKEN2B}$	CLK	$\overline{SEL}$	1B	2B	A
H	X	X	H	X	X	A_0‡
X	H	X	L	X	X	A_0‡
L	X	↑	H	L	X	L
L	X	↑	H	H	X	H
X	L	↑	L	X	L	L
X	L	↑	L	X	H	H

‡ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current (A port)	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
	High-level output current (B port)	V_{CC} = 2.3 V		–6	
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current (A port)	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
	Low-level output current (B port)	V_{CC} = 2.3 V		6	
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	A port	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
	B port	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	A port	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
	B port	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input-leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	125	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	A data before CLK↑	4.5		4		3.4		ns
		B data before CLK↑	0.8		1.2		1		
		$\overline{SEL}$ before CLK↑	1.4		1.6		1.3		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ before CLK↑	3.6		3.4		2.8		
		$\overline{CLKENB1}$ or $\overline{CLKENB2}$ before CLK↑	3.2		3		2.5		
		$\overline{OE}$ before CLK↑	4.2		3.9		3.2		
t_h	Hold time	A data after CLK↑	0		0		0.2		ns
		B data after CLK↑	1.3		1.2		1.3		
		$\overline{SEL}$ after CLK↑	1		1		1		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ after CLK↑	0.1		0.1		0.4		
		$\overline{CLKENB1}$ or $\overline{CLKENB2}$ after CLK↑	0.1		0		0.5		
		$\overline{OE}$ after CLK↑ after CLK↑	0		0		0.2		

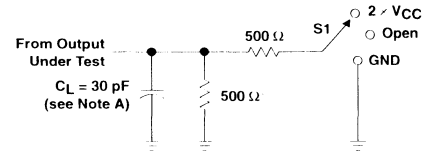
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		125		150		MHz
t_{pd}	CLK	B	1.6	6.1		5.9	1.8	5.4	ns
		A (1B)	1.6	5.8		5.4	1.7	4.8	
		A (2B)	1.6	5.8		5.3	1.8	4.8	
		A ($\overline{SEL}$)	2.5	7.3		6.5	2.4	5.8	
t_{en}	CLK	B	2.7	7.2		6.8	2.6	6.1	ns
t_{dis}	CLK	B	2.8	7.2		6.1	2.5	5.9	ns
t_{en}	CLK	A	2	6.2		5.6	1.8	5.1	ns
t_{dis}	CLK	A	2	6.5		5.4	2.1	5	ns

operating characteristics, T_A = 25°C

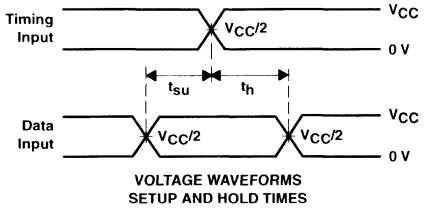
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	87	120	pF
		Outputs disabled		80.5	118	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

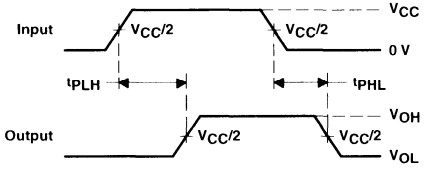


LOAD CIRCUIT

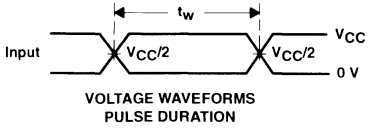
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



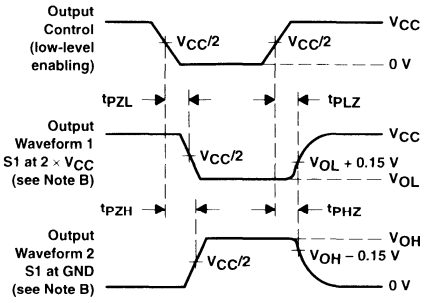
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

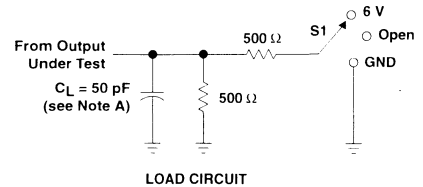


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

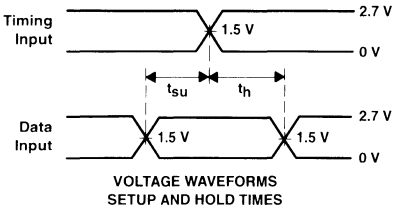
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

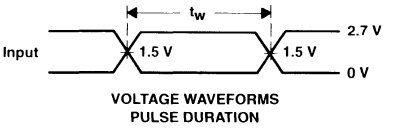


LOAD CIRCUIT

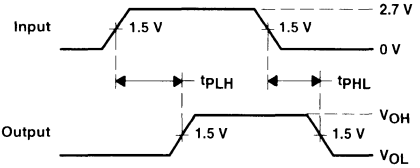
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



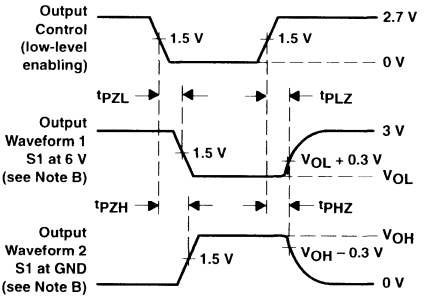
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



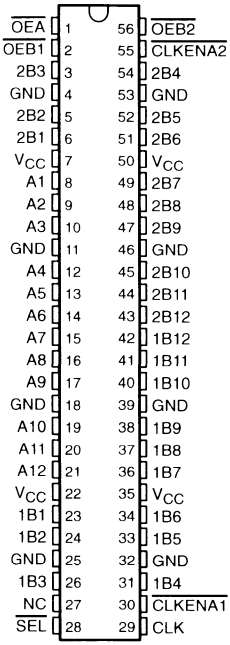
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 12-bit to 24-bit registered bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16269 is used in applications in which two separate ports must be multiplexed onto, or demultiplexed from, a single port. The device is particularly suitable as an interface between synchronous DRAMs and high-speed microprocessors.

Data is stored in the internal B-port registers on the low-to-high transition of the clock (CLK) input when the appropriate clock-enable ($\overline{\text{CLKENA}}$) inputs are low. Proper control of these inputs allows two sequential 12-bit words to be presented as a 24-bit word on the B port. For data transfer in the B-to-A direction, a single storage register is provided. The select ($\overline{\text{SEL}}$) line selects 1B or 2B data for the A outputs. The register on the A output permits the fastest possible data transfer, thus extending the period during which the data is valid on the bus. The control terminals are registered so that all transactions are synchronous with CLK. Data flow is controlled by the active-low output enables ($\overline{\text{OEA}}$, $\overline{\text{OEB1}}$, $\overline{\text{OEB2}}$).

To ensure the high-impedance state during power up or power down, a clock pulse should be applied as soon as possible and $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. Due to $\overline{\text{OE}}$ being routed through a register, the active state of the outputs cannot be determined prior to the arrival of the first clock pulse.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16269 is characterized for operation from –40°C to 85°C.

Function Tables

OUTPUT ENABLE

INPUTS			OUTPUTS	
CLK	$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
↑	H	H	Z	Z
↑	H	L	Z	Active
↑	L	H	Active	Z
↑	L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
H	H	X	X	$1B_0$†	$2B_0$†
L	X	↑	L	L	X
L	X	↑	H	H	X
X	L	↑	L	X	L
X	L	↑	H	X	H

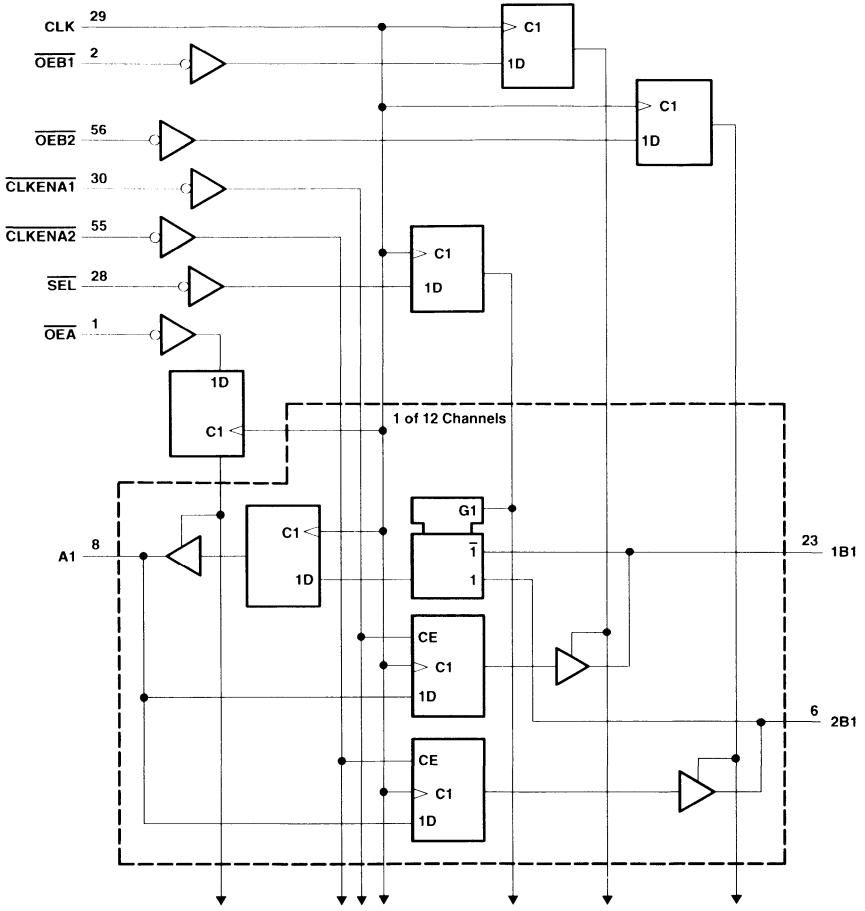
† Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS				OUTPUT
CLK	$\overline{SEL}$	1B	2B	A
X	H	X	X	A_0†
X	L	X	X	A_0†
↑	H	L	X	L
↑	H	H	X	H
↑	L	X	L	L
↑	L	X	H	H

† Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA,		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	135	0	135	0	135	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	A data before CLK↑	2		2		1.7		ns
		B data before CLK↑	2.2		2.1		1.8		
		$\overline{SEL}$ before CLK↑	1.6		1.6		1.3		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ before CLK↑	1		1.2		0.9		
		$\overline{OE}$ before CLK↑	1.5		1.6		1.3		
t_h	Hold time	A data after CLK↑	0.7		0.6		0.6		ns
		B data after CLK↑	0.7		0.6		0.6		
		$\overline{SEL}$ after CLK↑	1.1		0.7		0.7		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ after CLK↑	1		0.8		1.1		
		$\overline{OE}$ after CLK↑	0.8		0.8		0.8		

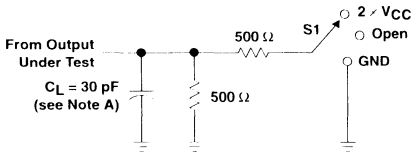
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			135		135		135		MHz
t_{pd}	CLK	B	1	8.2		7.3	1	6.2	ns
		A	1	6.4		5.8	1	5	
t_{en}	CLK	B	1	7.9		6.7	1	6.1	ns
		A	1	7.6		6.2	1	5.9	
t_{dis}	CLK	B	1	8.1		6.9	1	6.1	ns
		A	1	7.5		6.8	1	5.6	

operating characteristics, T_A = 25°C

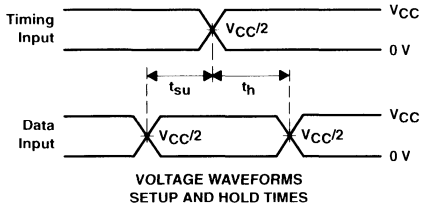
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	87	120	pF
		Outputs disabled		80.5	118	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

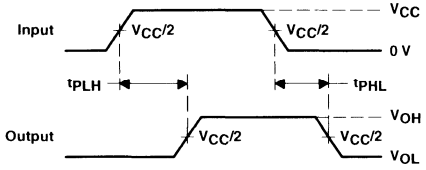


LOAD CIRCUIT

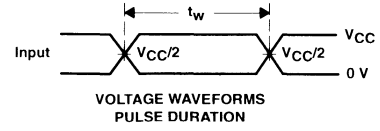
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



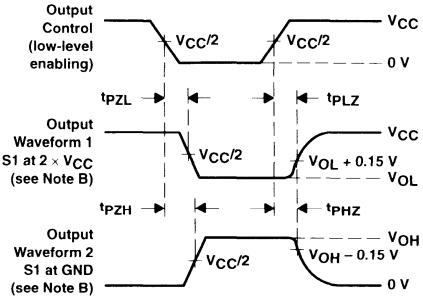
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

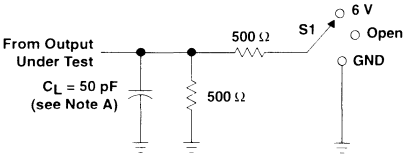


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

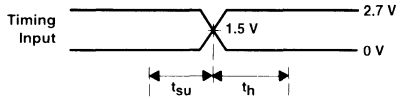
Figure 1. Load Circuit and Voltage Waveforms

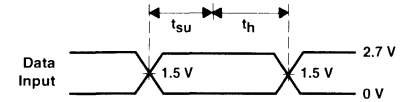
PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V



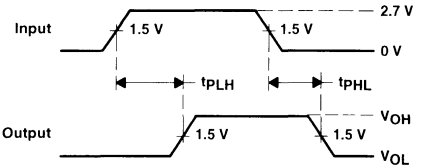
LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

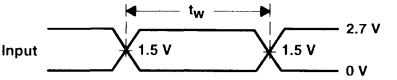




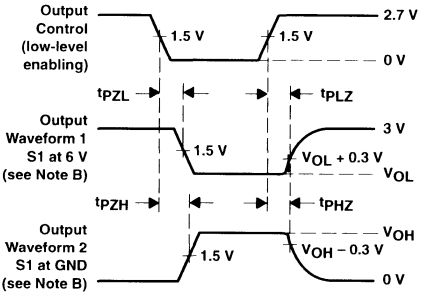
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



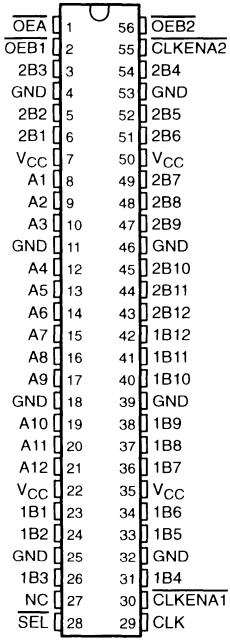
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **All Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV), and 300-mil Shrink Small-Outline (DL) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 12-bit to 24-bit registered bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCHR162269A is used in applications in which two separate ports must be multiplexed onto, or demultiplexed from, a single port. It is particularly suitable as an interface between synchronous DRAMs and high-speed microprocessors.

Data is stored in the internal B-port registers on the low-to-high transition of the clock (CLK) input when the appropriate clock-enable ($\overline{\text{CLKENA}}$) inputs are low. Proper control of these inputs allows two sequential 12-bit words to be presented as a 24-bit word on the B port. For data transfer in the B-to-A direction, a single storage register is provided. The select ($\overline{\text{SEL}}$) line selects 1B or 2B data for the A outputs. The register on the A output permits the fastest possible data transfer, thus extending the period during which the data is valid on the bus. The control terminals are registered so that all transactions are synchronous with CLK. Data flow is controlled by the active-low output enables ($\overline{\text{OEA}}$, $\overline{\text{OEB1}}$, and $\overline{\text{OEB2}}$).

To ensure the high-impedance state during power up or power down, a clock pulse should be applied as soon as possible and $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. Due to $\overline{\text{OE}}$ being routed through a register, the active state of the outputs cannot be determined prior to the arrival of the first clock pulse.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

description (continued)

All outputs are designed to sink up to 12 mA and include equivalent 26-Ω resistors to reduce overshoot and undershoot.

The SN74ALVCHR162269A is characterized for operation from –40°C to 85°C.

Function Tables

OUTPUT ENABLE

INPUTS			OUTPUTS	
CLK	$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
↑	H	H	Z	Z
↑	H	L	Z	Active
↑	L	H	Active	Z
↑	L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
L	H	↑	L	L	$2B_0$†
L	H	↑	H	H	$2B_0$†
L	L	↑	L	L	L
L	L	↑	H	H	H
H	L	↑	L	$1B_0$†	L
H	L	↑	H	$1B_0$†	H
H	H	X	X	$1B_0$†	$2B_0$†

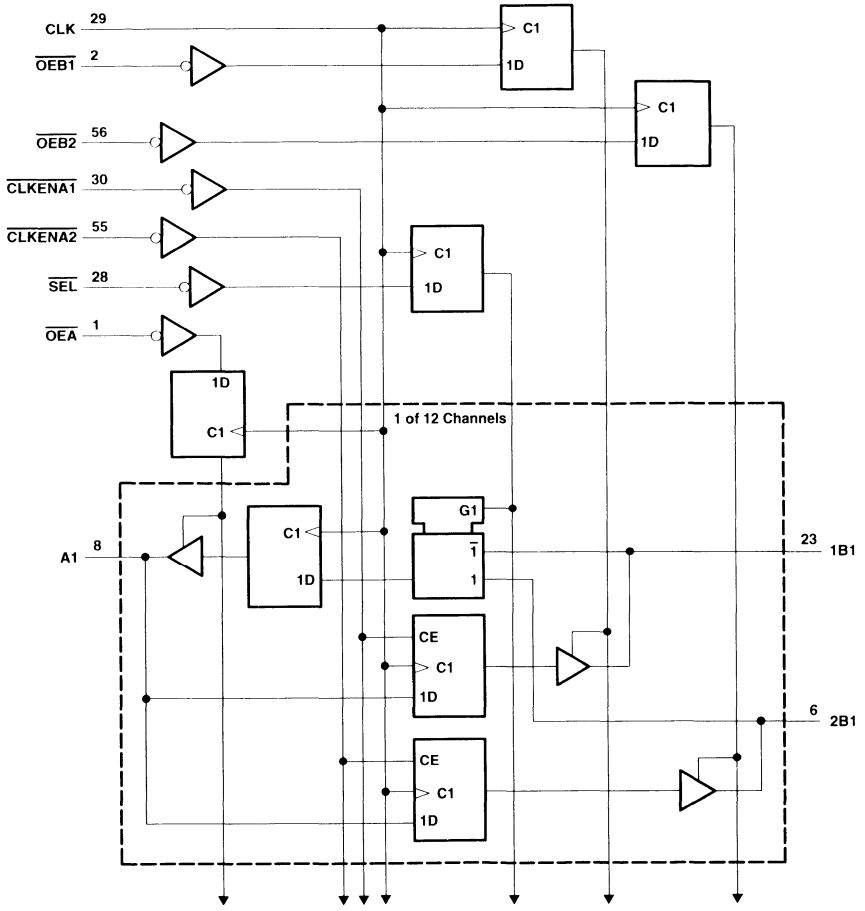
† Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS				OUTPUT
CLK	$\overline{SEL}$	1B	2B	A
X	H	X	X	A_0†
X	L	X	X	A_0†
↑	H	L	X	L
↑	H	H	X	H
↑	L	X	L	L
↑	L	X	H	H

† Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DGV package ..... 86°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA	V_{IH} = 1.7 V	2.3 V	1.9			
			V_{IH} = 2 V	2.7 V	2.2			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA	V_{IL} = 0.7 V	2.3 V			0.4	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.15 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	95	0	115	0	135	0	135	MHz
t_w	Pulse duration, CLK high or low		5.2		4.3		3.3		3.3		ns
t_{su}	Setup time	A data before CLK↑	1.4		1.4		0.9		1		ns
		B data before CLK↑	1.6		1.5		1		1.1		
		$\overline{SEL}$ before CLK↑	0.8		1.1		1.3		1.3		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ before CLK↑	0.8		1		0.7		0.8		
		$\overline{OE}$ before CLK↑	1.7		1.6		1.1		1.2		
t_h	Hold time	A data after CLK↑	0.9		0.9		1.1		1.2		ns
		B data after CLK↑	0.8		0.6		0.8		1		
		$\overline{SEL}$ after CLK↑	1.1		0.8		1.6		1.7		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ after CLK↑	1.4		1		1.4		1.6		
		$\overline{OE}$ after CLK↑	0.9		0.8		1		1.2		

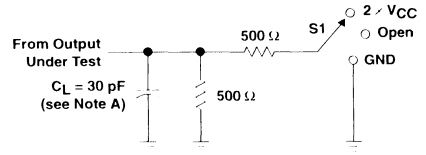
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.15 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			95		115		135		135		MHz
t_{pd}	CLK	B	1.8	7.1		6.9	2.3	5.6	2.2	5.8	ns
		A	1.4	5.8		5.8	2	5	2	5.2	
t_{en}	CLK	B	2.4	7.2		6.9	2.3	5.6	2.3	5.8	ns
		A	2.1	6.2		6	2.1	5.2	2.1	5.3	
t_{dis}	CLK	B	2.6	7.9		6.7	2.3	5.8	2.4	6	ns
		A	2	7.8		6.2	2.2	5.9	2.1	6	

operating characteristics, T_A = 25°C

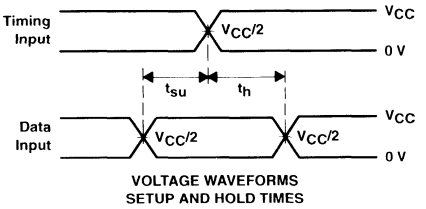
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.15 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	142	172	pF
		Outputs disabled		115	129	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

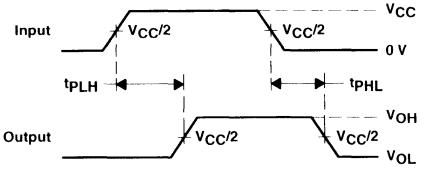


LOAD CIRCUIT

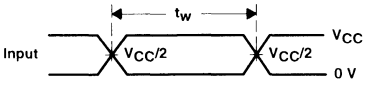
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



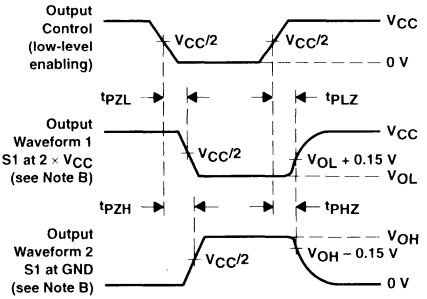
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

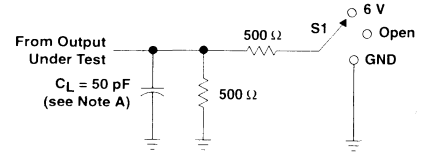


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

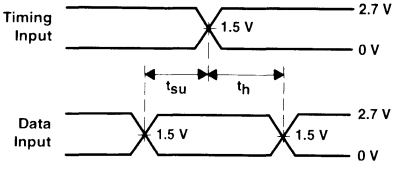
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

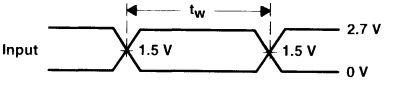


LOAD CIRCUIT

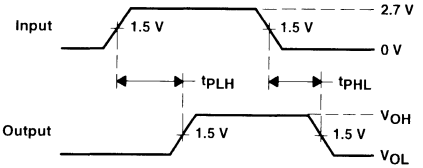
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



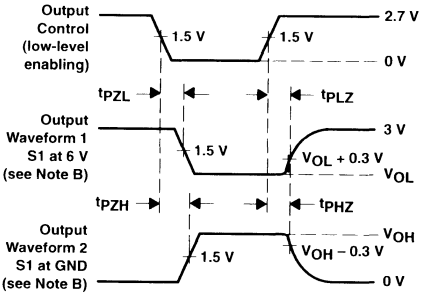
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



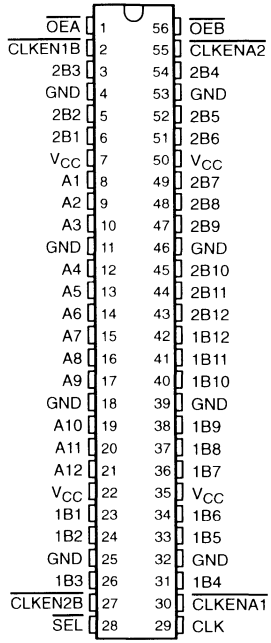
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 12-bit to 24-bit registered bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16270 is used in applications in which data must be transferred from a narrow high-speed bus to a wide lower-frequency bus.

The device provides synchronous data exchange between the two ports. Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input when the appropriate $\overline{\text{CLKEN}}$ inputs are low. The select ($\overline{\text{SEL}}$) line selects 1B or 2B data for the A outputs. For data transfer in the A-to-B direction, a two-stage pipeline is provided in the A-to-1B path, with a single storage register in the A-to-2B path. Proper control of the $\overline{\text{CLKENA}}$ inputs allows two sequential 12-bit words to be presented synchronously as a 24-bit word on the B port. Data flow is controlled by the active-low output enables ($\overline{\text{OEA}}$, $\overline{\text{OEB}}$). The control terminals are registered to synchronize the bus-direction changes with CLK.

To ensure the high-impedance state during power up or power down, a clock pulse should be applied as soon as possible and $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. Due to $\overline{\text{OE}}$ being routed through a register, the active state of the outputs cannot be determined prior to the arrival of the first clock pulse.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16270 is characterized for operation from –40°C to 85°C.

Function Tables

OUTPUT ENABLE

INPUTS			OUTPUTS	
CLK	$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
↑	H	H	Z	Z
↑	H	L	Z	Active
↑	L	H	Active	Z
↑	L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
L	H	↑	L	L†	$2B_0$‡
L	H	↑	H	H†	$2B_0$‡
L	L	↑	L	L†	L
L	L	↑	H	H†	H
H	L	↑	L	$1B_0$‡	L
H	L	↑	H	$1B_0$‡	H
H	H	X	X	$1B_0$‡	$2B_0$‡

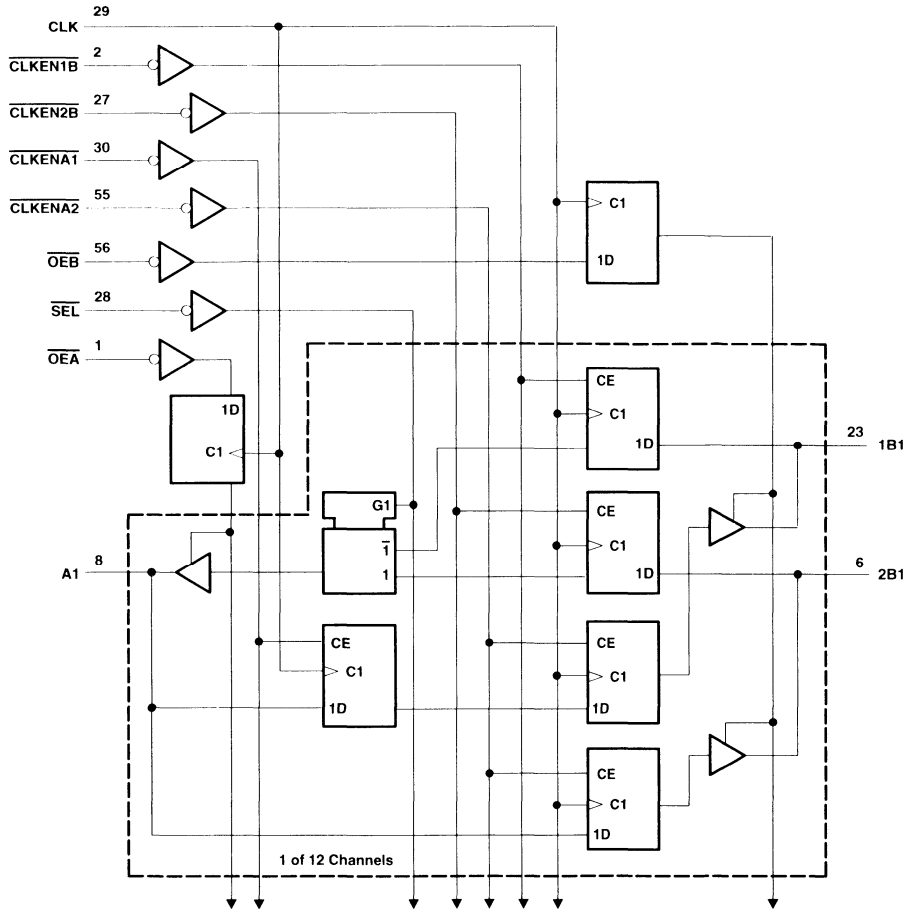
† Two CLK edges are needed to propagate data.
‡ Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS						OUTPUT
$\overline{CLKEN1B}$	$\overline{CLKEN2B}$	CLK	$\overline{SEL}$	1B	2B	A
H	X	X	H	X	X	A_0‡
X	H	X	L	X	X	A_0‡
L	X	↑	H	L	X	L
L	X	↑	H	H	X	H
X	L	↑	L	X	L	L
X	L	↑	L	X	H	H

‡ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
	I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
		V_{IH} = 2 V	2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
	I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
	I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
		V_{IL} = 0.8 V	2.7 V			0.4	
	I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I	V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.7 V		2.3 V	45			µA
	V_I = 1.7 V		2.3 V	–45			
	V_I = 0.8 V		3 V	75			
	V_I = 2 V		3 V	–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io} A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	A data before CLK↑	4.1		3.8		3.1		ns
		B data before CLK↑	0.9		1.2		0.9		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ before CLK↑	3.5		3.2		2.7		
		$\overline{CLKEN1B}$ or $\overline{CLKEN2B}$ before CLK↑	3.4		3		2.6		
		$\overline{OE}$ data before CLK↑	4.4		3.9		3.2		
t_h	Hold time	A data after CLK↑	0		0		0.2		ns
		B data after CLK↑	1.4		1		1.7		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ after CLK↑	0		0.1		0.3		
		$\overline{CLKEN1B}$ or $\overline{CLKEN2B}$ after CLK↑	0		0		0.6		
		$\overline{OE}$ after CLK↑	0		0		0.1		

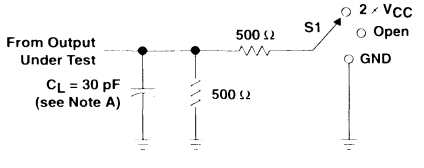
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	B	1.5	5.9		5.8	1.1	5.1	ns
		A	1.2	5.4		5.4	1	4.7	
	$\overline{SEL}$	A	1.4	6.2		6.4	1	5.5	
t_{en}	CLK	A or B	1.5	7		6.8	1	6	ns
t_{dis}	CLK	A or B	1.9	7.2		6.5	1.1	5.8	ns

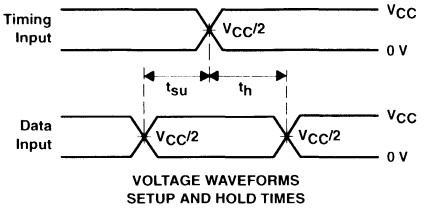
operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	87	120	pF
		Outputs disabled		80.5	118	

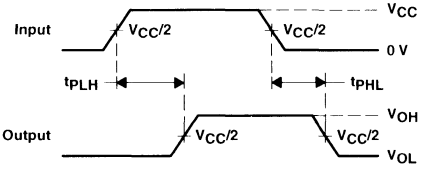
PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V



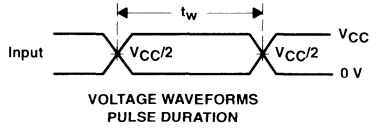
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



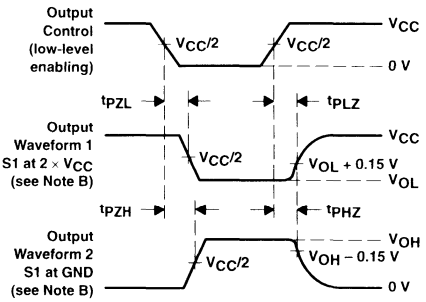
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

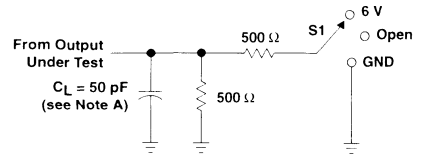


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

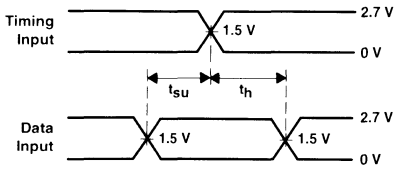
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

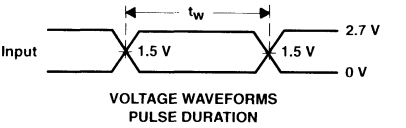


LOAD CIRCUIT

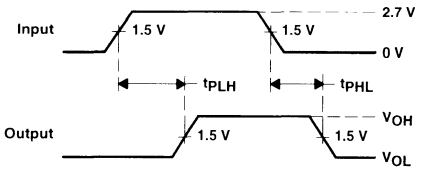
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



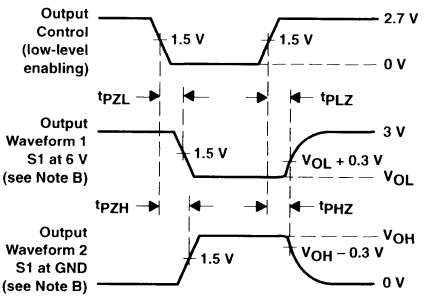
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



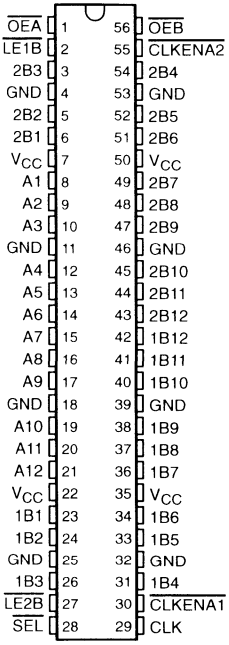
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 12-bit to 24-bit bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16271 is intended for applications in which two separate data paths must be multiplexed onto, or demultiplexed from, a single data path. This device is particularly suitable as an interface between conventional DRAMs and high-speed microprocessors.

A data is stored in the internal A-to-B registers on the low-to-high transition of the clock (CLK) input, provided that the clock-enable ($\overline{\text{CLKENA}}$) inputs are low. Proper control of these inputs allows two sequential 12-bit words to be presented as a 24-bit word on the B port.

Transparent latches in the B-to-A path allow asynchronous operation to maximize memory access throughput. These latches transfer data when the latch-enable ($\overline{\text{LE}}$) inputs are low. The select ($\overline{\text{SEL}}$) line selects 1B or 2B data for the A outputs. Data flow is controlled by the active-low output enables ($\overline{\text{OEA}}$, $\overline{\text{OEB}}$).

To ensure the high-impedance state during power up or power down, the output enables should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16271 is characterized for operation from –40°C to 85°C.

Function Tables

OUTPUT ENABLE

INPUTS		OUTPUTS	
$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
H	H	Z	Z
H	L	Z	Active
L	H	Active	Z
L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

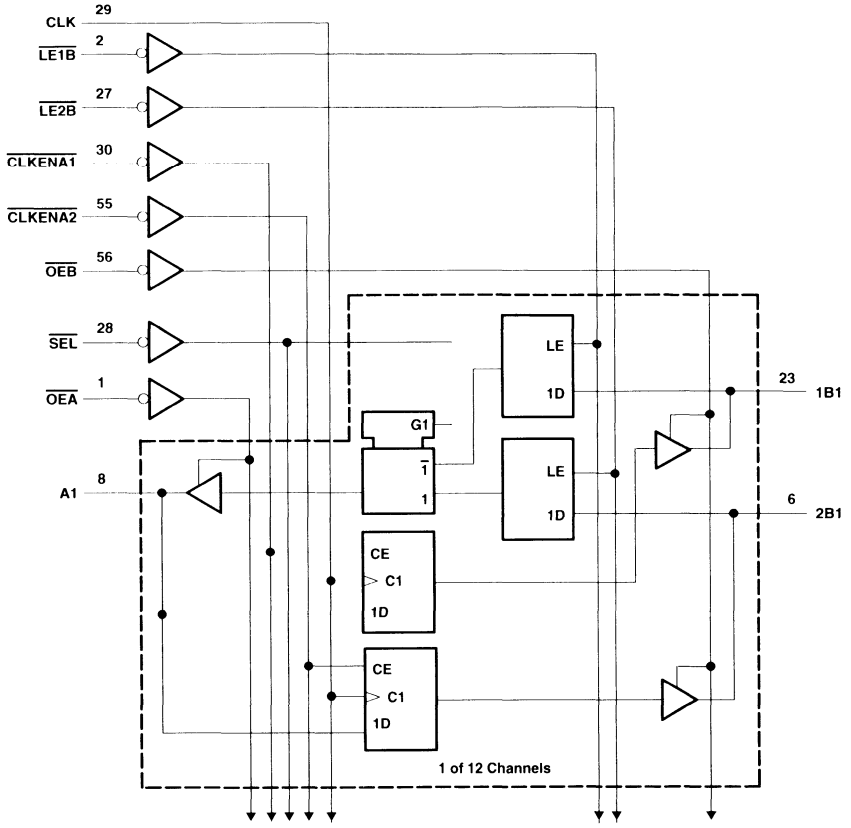
INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
H	H	X	X	$1B_0$†	$2B_0$†
L	X	↑	L	L	X
L	X	↑	H	H	X
X	L	↑	L	X	L
X	L	↑	H	A_0	H

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS				OUTPUT
$\overline{LE}$	$\overline{SEL}$	1B	2B	A
H	X	X	X	A_0†
H	X	X	X	A_0†
L	H	L	X	L
L	H	H	X	H
L	L	X	L	L
L	L	X	H	H

† Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	130	0	130	0	130	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	A before CLK↑	2.6		2.1		1.7		ns
		B before $\overline{LE}$	1.7		1.5		1.3		
		$\overline{CLKEN}$ before CLK↑	1.6		1.3		1		
t_h	Hold time	A after CLK↑	0.6		0.6		0.7		ns
		B after $\overline{LE}$	0.9		0.9		1.1		
		$\overline{CLKEN}$ after CLK↑	1		0.9		0.9		

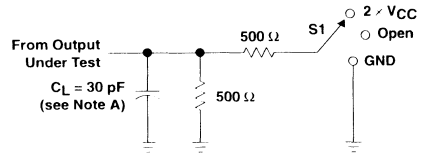
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			130		130		130		MHz
t_{pd}	CLK	B	1	6.2		5	1	4.3	ns
	B	A	1	5.3		4.7	1.4	4	
	$\overline{LE}$		1	6		5.9	1.4	4.8	
	$\overline{SEL}$		1.1	6.4		6.2	1.3	5.2	
t_{en}	$\overline{OEB}$ or $\overline{OEA}$	B or A	1	6		6.1	1	5.1	ns
t_{dis}	$\overline{OEB}$ or $\overline{OEA}$	B or A	1.4	5.4		4.6	1.7	4.2	ns

operating characteristics, T_A = 25°C

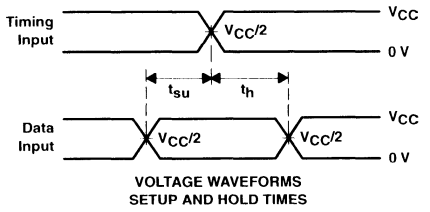
PARAMETER				TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
					TYP	TYP	
C_{pd}	Power dissipation capacitance	A to B	Outputs enabled	C_L = 0, f = 10 MHz	92	105	pF
			Outputs disabled		61	76	
		B to A	Outputs enabled		39	43	
			Outputs disabled		11	13	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

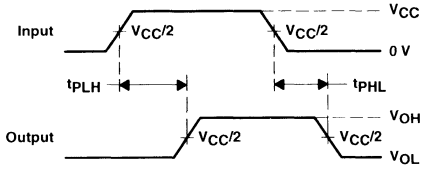


LOAD CIRCUIT

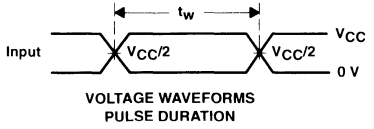
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



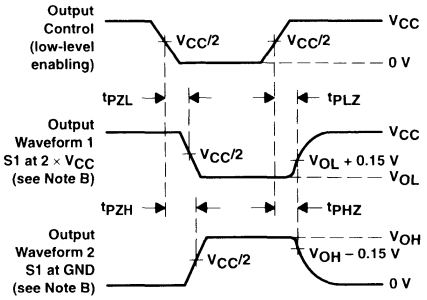
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

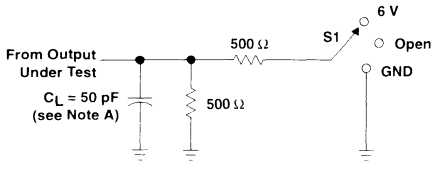


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

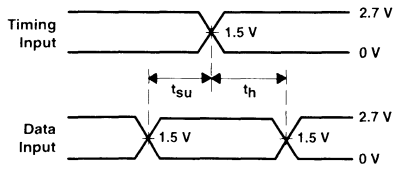
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

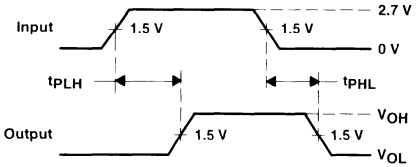


LOAD CIRCUIT

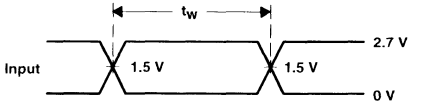
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



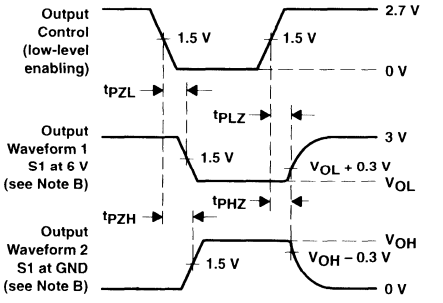
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



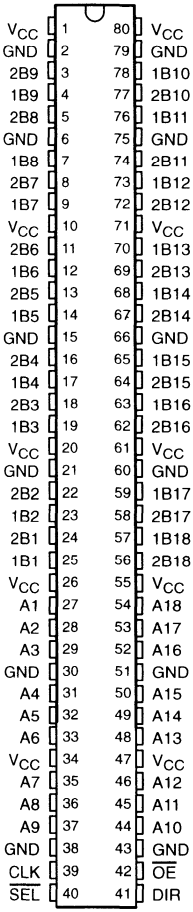
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Thin Very Small-Outline Package**

DBB PACKAGE
(TOP VIEW)



description

The SN74ALVCH16282 is an 18-bit to 36-bit registered bus exchanger designed for 2.3-V to 3.6-V V_{CC} operation.

This part is intended for use in applications in which data must be transferred from a narrow high-speed bus to a wide lower-frequency bus. It is designed specifically for low-voltage (3.3-V) V_{CC} operation.

The device provides synchronous data exchange between the two ports. Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input. For data transfer in the B-to-A direction, the select ($\overline{SEL}$) input selects 1B or 2B data for the A outputs.

For data transfer in the A-to-B direction, a two-stage pipeline is provided in the 1B path, with a single storage register in the 2B path. Data flow is controlled by the active-low output enable ($\overline{OE}$) and the DIR input. The DIR control pin is registered to synchronize the bus direction changes with the clock.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16282 is characterized for operation from –40°C to 85°C.

Function Tables

A-TO-B STORAGE ($\overline{OE}$ = L, DIR = H)

INPUTS			OUTPUTS	
$\overline{SEL}$	CLK	A	1B	2B
H	X	X	$1B_0$†	$2B_0$†
L	↑	L	L‡	X
L	↑	H	H‡	X

† Output level before indicated steady-state input conditions were established

‡ Two CLK edges are needed to propagate the data.

B-TO-A STORAGE ($\overline{OE}$ = L, DIR = L)

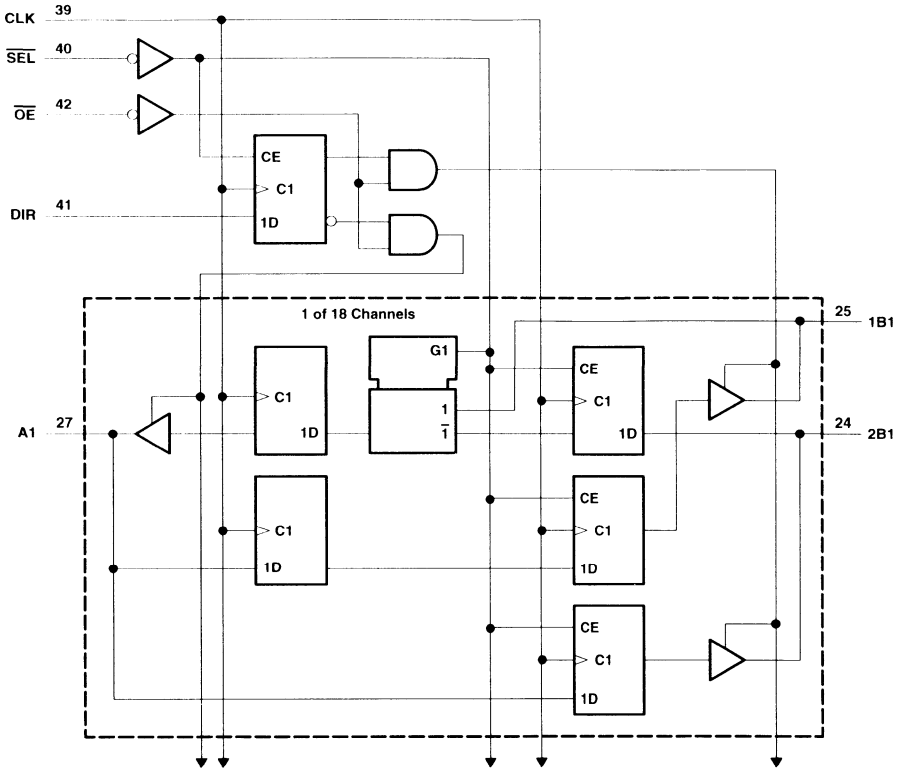
INPUTS				OUTPUT
CLK	$\overline{SEL}$	1B	2B	A
↑	H	X	L	L§
↑	H	X	H	H§
↑	L	L	X	L
↑	L	H	X	H

§ Two CLK edges are needed to propagate the data. The data is loaded in the first register when $\overline{SEL}$ is low and propagates to the second register when $\overline{SEL}$ is high.

OUTPUT ENABLE

INPUTS			OUTPUTS	
CLK	$\overline{OE}$	DIR	A	1B, 2B
↑	H	X	Z	Z
↑	L	L	Z	Active
↑	L	H	Active	Z

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3) ..... 106°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			150		150		150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	A data before CLK↑	2.4		2.3		2		ns
		B data before CLK↑	2.2		2.2		1.8		
		DIR before CLK↑	2.2		2.1		1.7		
		$\overline{SEL}$ before CLK↑	2		2		1.8		
t_h	Hold time	A data after CLK↑	0.5		0.5		0.7		ns
		B data after CLK↑	0.5		0.5		0.6		
		DIR after CLK↑	0.5		0.5		0.5		
		$\overline{SEL}$ after CLK↑	0.7		0.7		0.8		

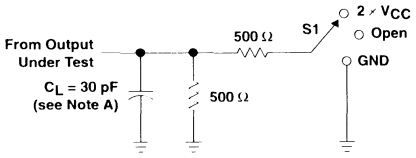
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	A	1	6.1		5.5	1.4	5	ns
		B	1.2	6.3		5.7	1.6	5.3	
t_{en}	$\overline{OE}$	A	1.3	6.9		6.3	1.2	5.7	ns
		B	2.3	8.7		8.1	2.3	7.4	
t_{dis}	$\overline{OE}$	A	1.5	7		5.6	1.8	5.7	ns
		B	2.1	7.9		6.4	2.3	6.4	

operating characteristics, T_A = 25°C

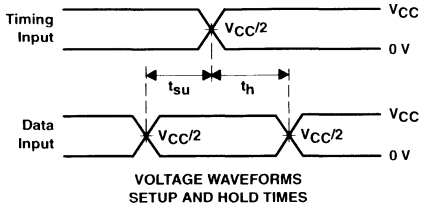
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	282	310	pF
		Outputs disabled		208	228	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

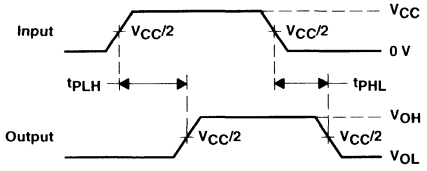


LOAD CIRCUIT

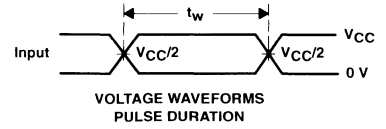
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



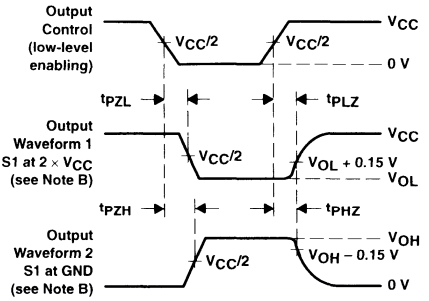
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

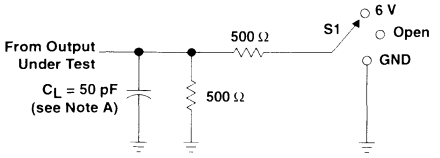


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

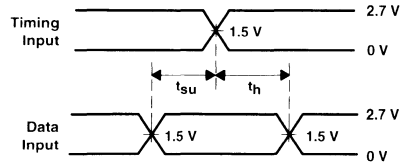
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

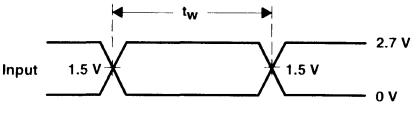


LOAD CIRCUIT

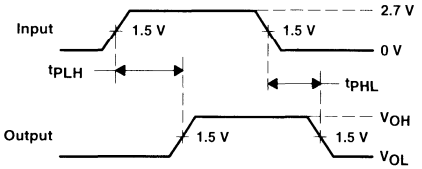
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



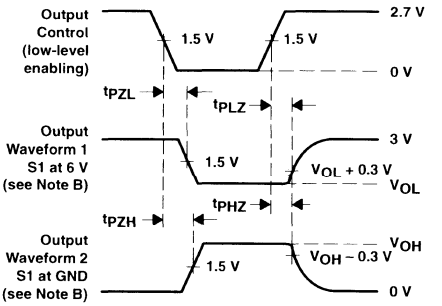
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



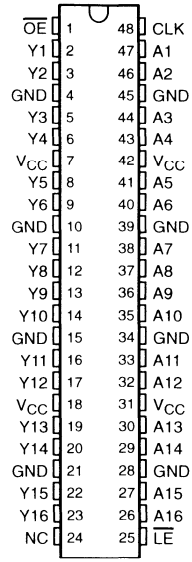
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Designed to Comply With JEDEC 168-Pin and 200-Pin SDRAM Buffered DIMM Specification**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 16-bit universal bus driver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow from A to Y is controlled by the output-enable ($\overline{OE}$) input. The device operates in the transparent mode when the latch-enable ($\overline{LE}$) input is low. When $\overline{LE}$ is high, the A data is latched if the clock (CLK) input is held at a high or low logic level. If $\overline{LE}$ is high, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

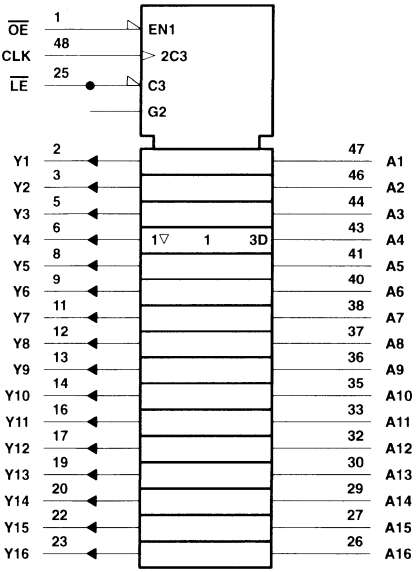
The SN74ALVCH16334 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	$\overline{LE}$	CLK	A	Y
H	X	X	X	Z
L	L	X	L	L
L	L	X	H	H
L	H	↑	L	L
L	H	↑	H	H
L	H	L or H	X	Y_0†

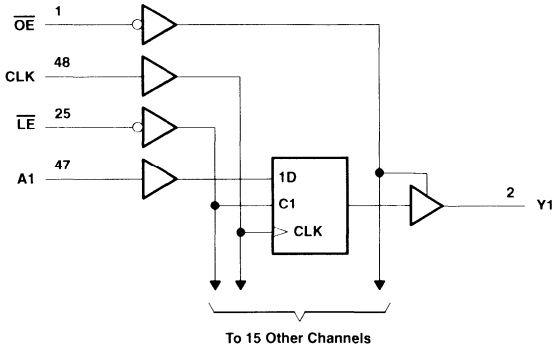
† Output level before the indicated steady-state input conditions were established

logic symbol‡



‡ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DGV package ..... 93°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
I_{hold}		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		8		pF

† All typical values are at V_{CC} = 3.3 V.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency				150		150		150	MHz
t_w	Pulse duration	$\overline{LE}$ low		3.3		3.3		3.3		ns
		CLK high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑		1.4		1.7		1.5		ns
		Data before $\overline{LE}$↑	CLK high	1.2		1.6		1.3		
			CLK low	1.4		1.5		1.2		
t_h	Hold time	Data after CLK↑		0.9		0.8		0.9		ns
		Data after $\overline{LE}$↑	CLK high or low	1.2		1.1		1.1		

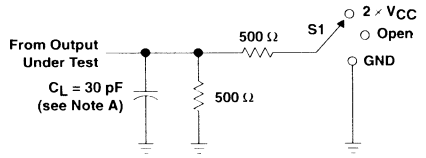
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1	3.7		3.6	1.1	3.3	ns
	$\overline{LE}$		1	4.8		4.4	1.3	4.4	
	CLK		1	4.4		4.1	1	4.1	
t_{en}	$\overline{OE}$	Y	1	5.4		4.6	1.1	4.6	ns
t_{dis}	$\overline{OE}$	Y	1	4.1		4.4	1.7	4.4	ns

operating characteristics, T_A = 25°C

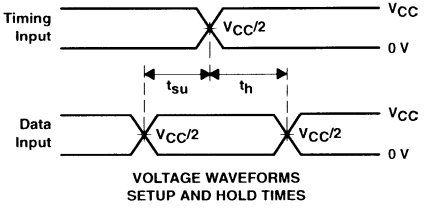
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	32	37	pF
		Outputs disabled		7	11	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

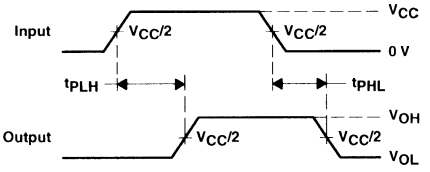


LOAD CIRCUIT

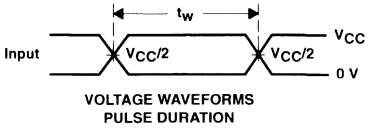
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



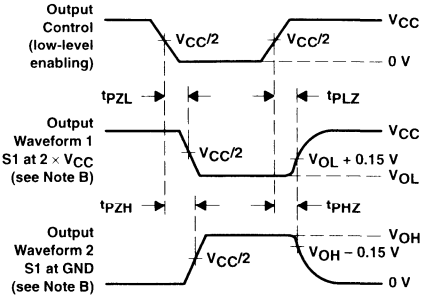
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

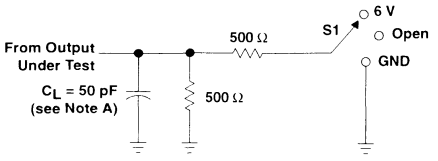


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

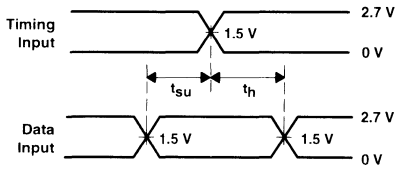
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

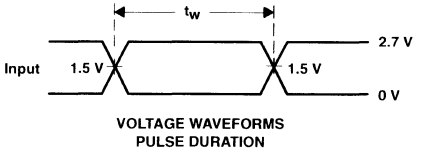


LOAD CIRCUIT

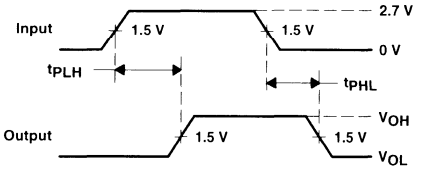
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



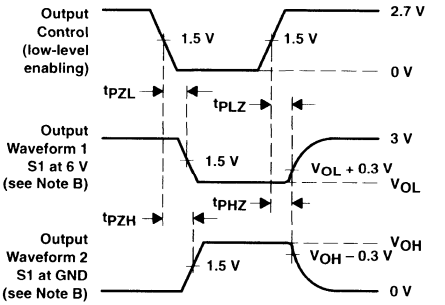
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

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C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
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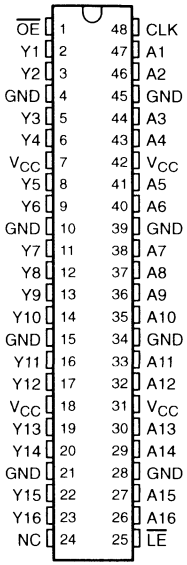
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Port Has Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **Designed to Comply With JEDEC 168-Pin and 200-Pin SDRAM Buffered DIMM Specification**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 16-bit universal bus driver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow from A to Y is controlled by the output-enable ($\overline{OE}$) input. The device operates in the transparent mode when the latch-enable ($\overline{LE}$) input is low. When $\overline{LE}$ is high, the A data is latched if the clock (CLK) input is held at a high or low logic level. If $\overline{LE}$ is high, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

The output port includes equivalent 26-Ω series resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

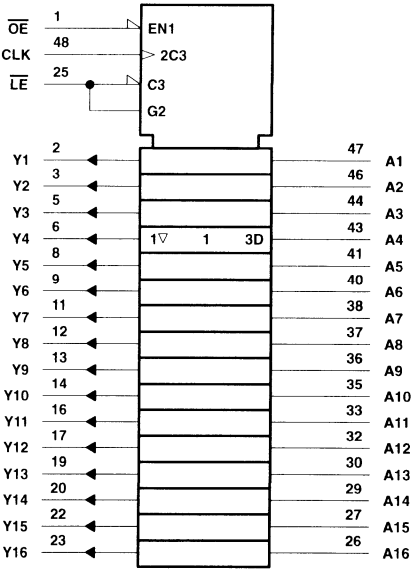
The SN74ALVCH162334 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	$\overline{LE}$	CLK	A	Y
H	X	X	X	Z
L	L	X	L	L
L	L	X	H	H
L	H	↑	L	L
L	H	↑	H	H
L	H	L or H	X	Y_0†

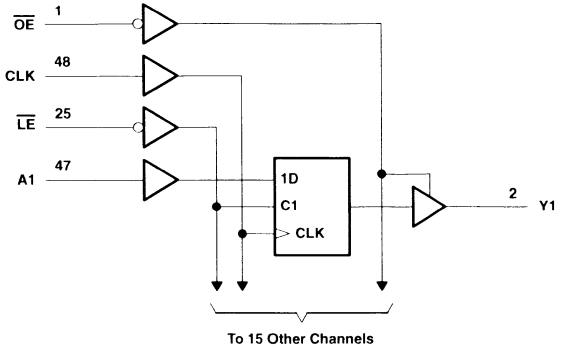
† Output level before the indicated steady-state input conditions were established

logic symbol‡



‡ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 4.6 V
Input voltage range, V_I (see Note 1)	–0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2)	–0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0)	–50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC})	±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC})	±50 mA
Continuous current through each V_{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package	89°C/W
DGV package	93°C/W
DL package	94°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	150	0	150	0	150	MHz
t_w	Pulse duration	$\overline{LE}$ low		3.3		3.3		3.3		ns
		CLK high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑		1.4		1.7		1.5		ns
		Data before $\overline{LE}$↑	CLK high	1.2		1.6		1.3		
			CLK low	1.4		1.5		1.2		
t_h	Hold time	Data after CLK↑		0.9		0.8		0.9		ns
		Data after $\overline{LE}$↑	CLK high or low	1.2		1.1		1.1		

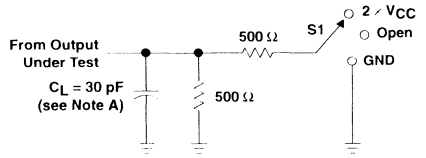
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1	3.9		4.5	1.1	3.9	ns
	$\overline{LE}$		1	5		6	1.3	5	
	CLK		1	4.9		5.4	1	4.9	
t_{en}	$\overline{OE}$	Y	1	5.4		6.4	1.1	5.4	ns
t_{dis}	$\overline{OE}$	Y	1	5		5.1	1.7	5	ns

operating characteristics, T_A = 25°C

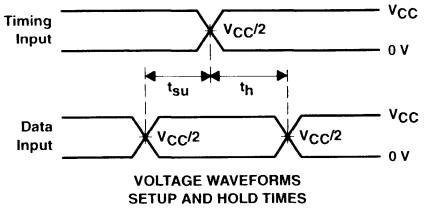
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	32	37	pF
		Outputs disabled		7	11.5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

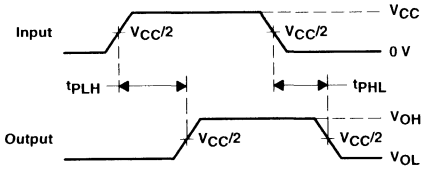


LOAD CIRCUIT

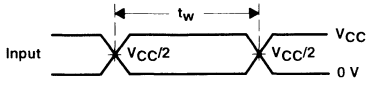
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



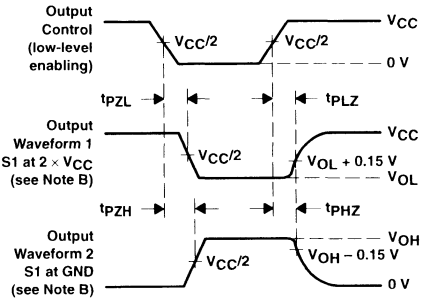
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

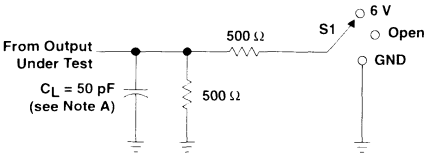


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

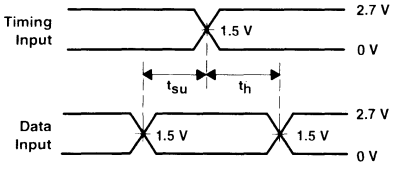
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

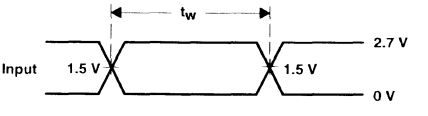


LOAD CIRCUIT

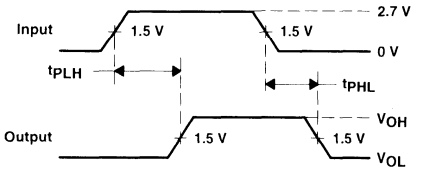
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



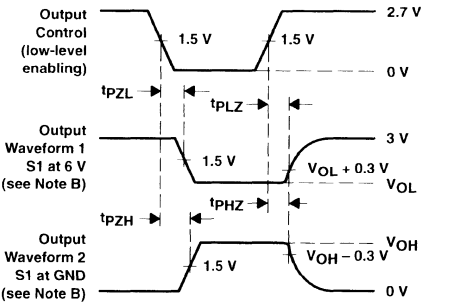
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



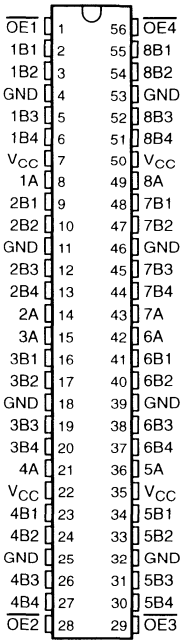
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

The SN74ALVCH16344 is a 1-bit to 4-bit address driver used in applications in which four separate memory locations must be addressed by a single address.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

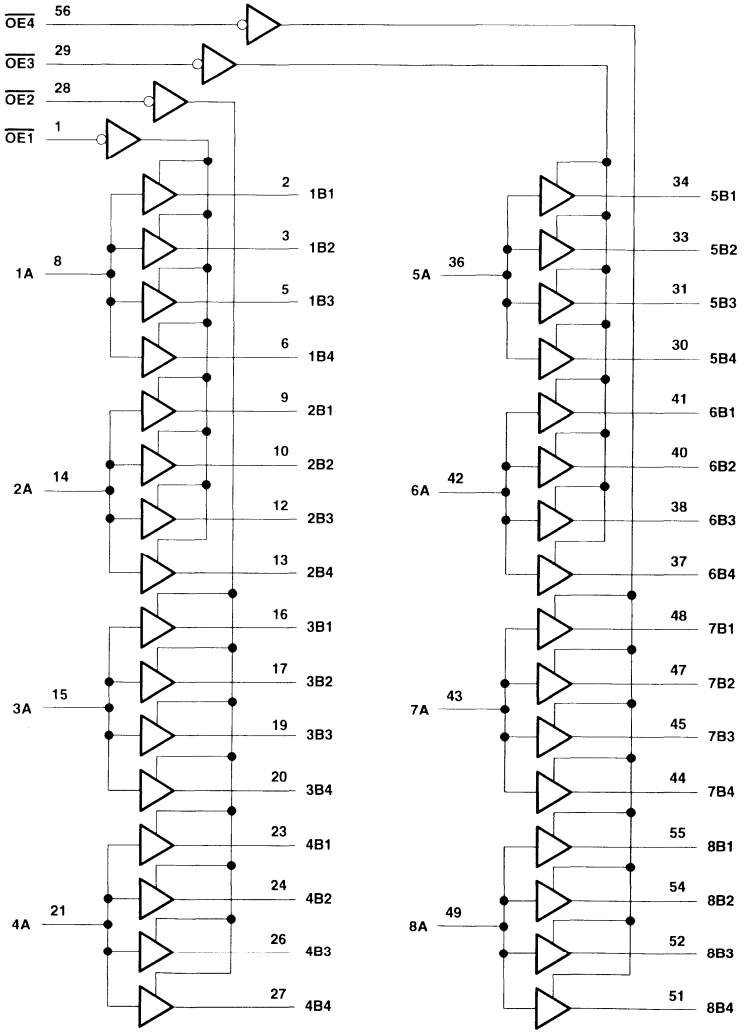
Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The SN74ALVCH16344 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS		OUTPUT
$\overline{OE}$	A	Bn
L	H	H
L	L	L
H	H	Z

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DGV package . . . . . 86°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		2.5		pF
	Data inputs					3.5		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		4		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

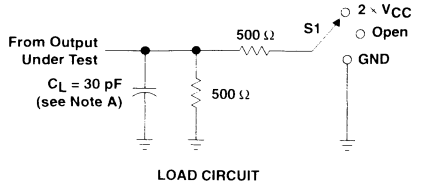
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	B	1	4.6		4.6	1.4	4	ns
t_{en}	$\overline{OE}$	B	1	6.2		6.2	1.2	5.1	ns
t_{dis}	$\overline{OE}$	B	1	5.1		4.4	1.2	4	ns
$t_{sk(o)}$§								0.35	ns
$t_{sk(o)}$¶								0.5	ns

§ Skew between outputs of same bank and same package (same transition). This parameter is warranted but not production tested.
¶ Skew between outputs of all banks and same package (A1 through A8 tied together). This parameter is warranted but not production tested.

operating characteristics, $T_A = 25°C$

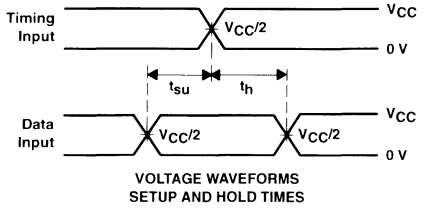
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	68	84	pF
		Outputs disabled		11	14	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

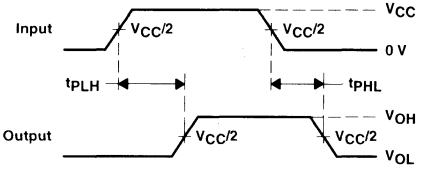


LOAD CIRCUIT

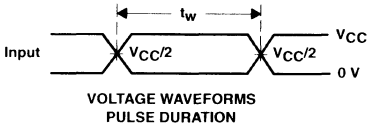
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



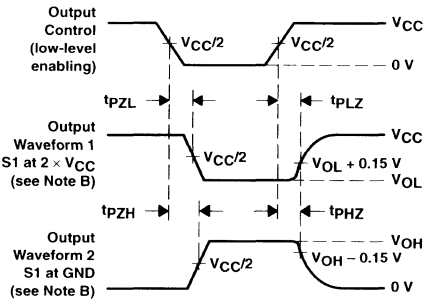
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

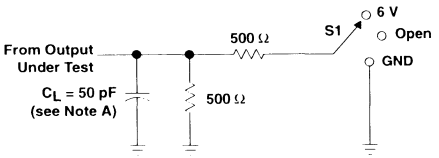


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

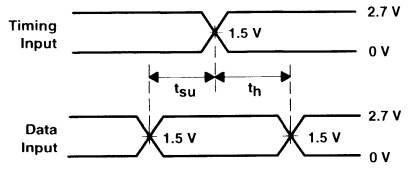
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

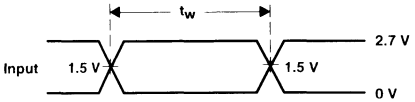


LOAD CIRCUIT

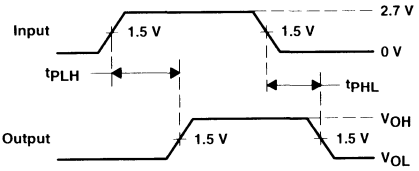
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



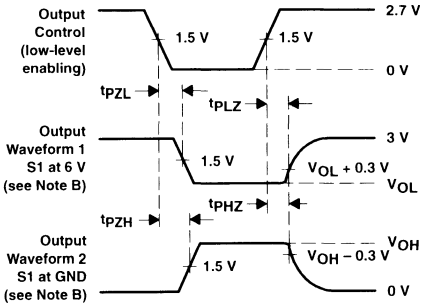
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



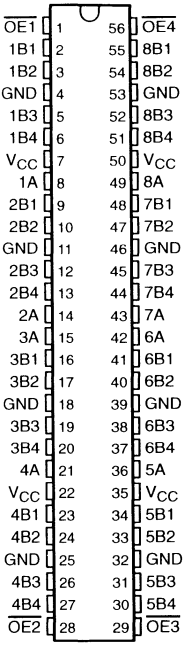
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DGG), Thin Shrink Small-Outline (DL), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

The SN74ALVCH162344 is a 1-bit to 4-bit address driver used in applications in which four separate memory locations must be addressed by a single address.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

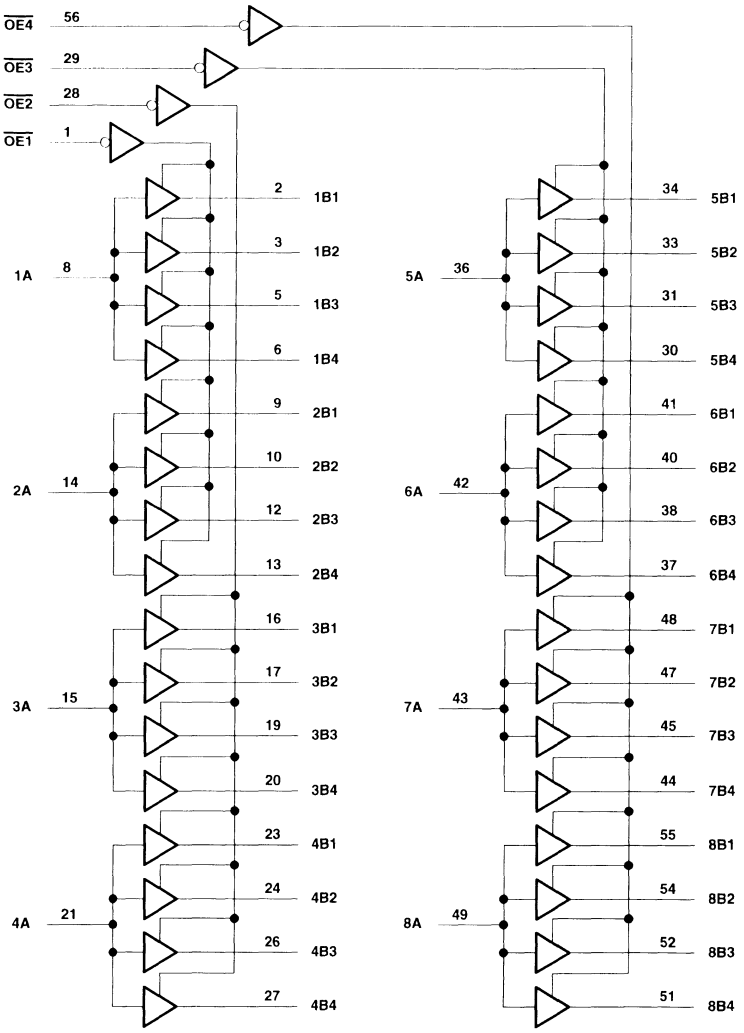
Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The SN74ALVCH162344 is characterized for operation from –40°C to 85°C.

A-TO-B FUNCTION TABLE

INPUTS		OUTPUT
$\overline{OE}$	A	Bn
L	H	H
L	L	L
H	X	Z

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DGV package . . . . . 86°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		2.5		pF
	Data inputs					3.5		
C_o	Outputs	V_O= V_{CC} or GND		3.3 V		4		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

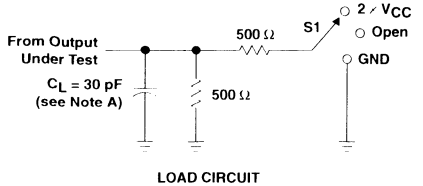
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	B	1	4.9		5.1	1.4	4.4	ns
t_{en}	$\overline{OE}$	B	1	6.4		6.6	1.2	5.7	ns
t_{dis}	$\overline{OE}$	B	1	5.4		4.7	1.2	4.5	ns
$t_{sk(o)}$§								0.35	ns
$t_{sk(o)}$¶								0.5	ns

§ Skew between outputs of the same bank and same package (same transition). This parameter is warranted but not production tested.
¶ Skew between outputs of all banks of same package (A1–A8 tied together). This parameter is warranted but not production tested.

operating characteristics, $T_A = 25°C$

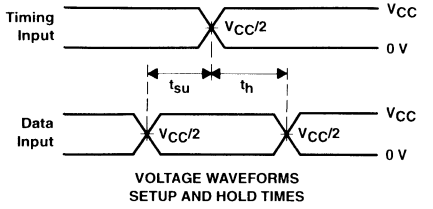
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	68	82	pF
		Outputs disabled		12	14	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

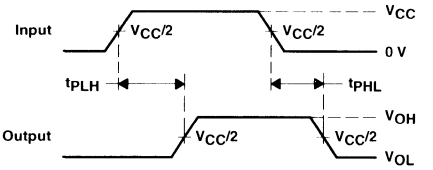


LOAD CIRCUIT

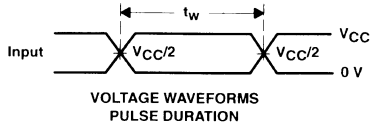
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



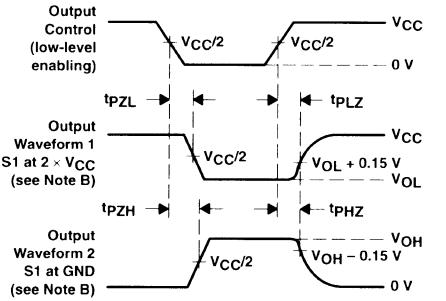
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

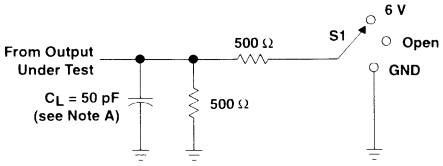


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

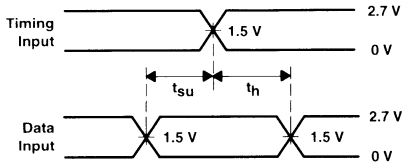
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

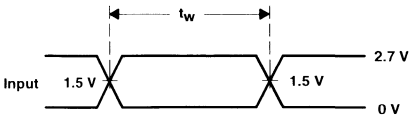


LOAD CIRCUIT

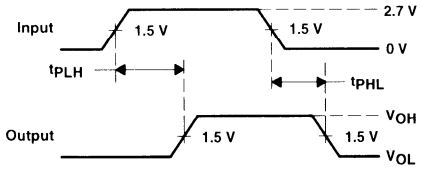
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



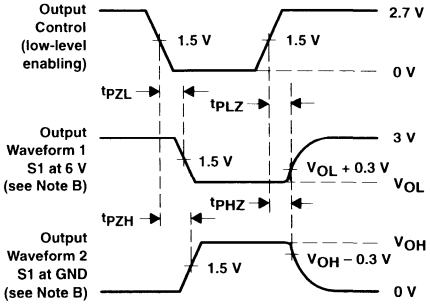
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



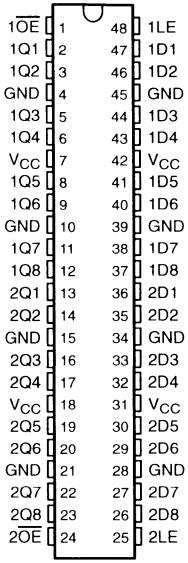
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-833, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit transparent D-type latch is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16373 is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. This device can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components. $\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

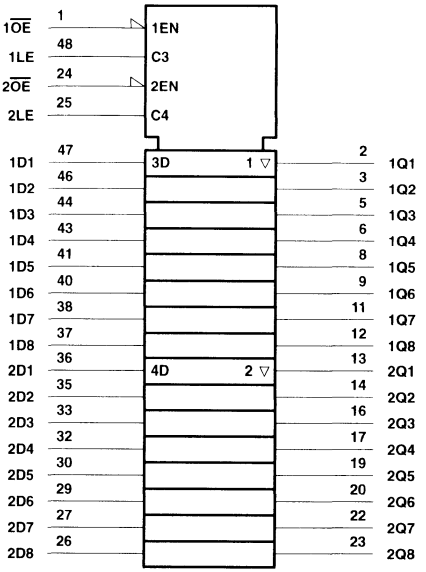
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16373 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

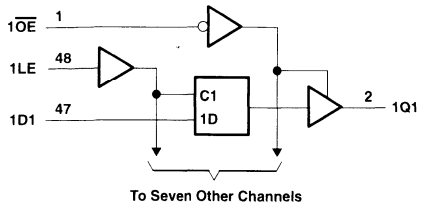
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

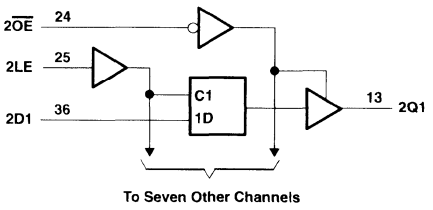
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE↓	1		1		1.1		ns
t_h	Hold time, data after LE↓	1.5		1.7		1.4		ns

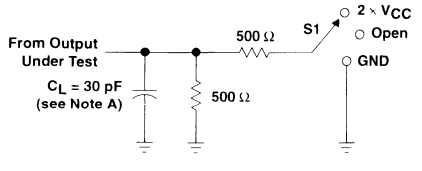
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1	4.5		4.3	1.1	3.6	ns
	LE		1	4.9		4.6	1	3.9	
t_{en}	$\overline{OE}$	Q	1	6		5.7	1	4.7	ns
t_{dis}	$\overline{OE}$	Q	1.2	5.1		4.5	1.4	4.1	ns

operating characteristics, $T_A = 25°C$

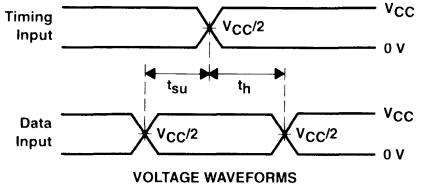
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	19	22	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

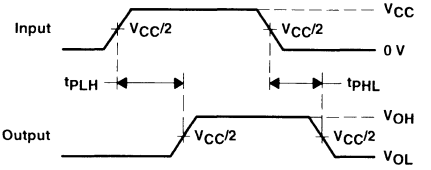


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND

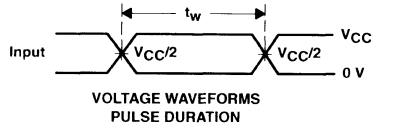
LOAD CIRCUIT



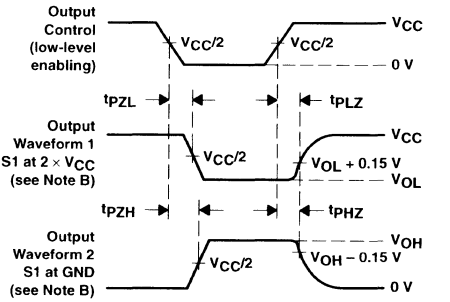
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

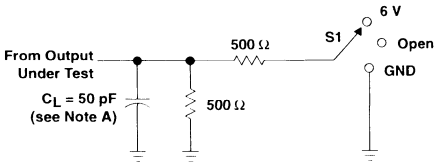


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

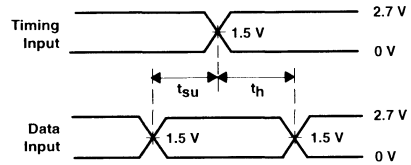
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

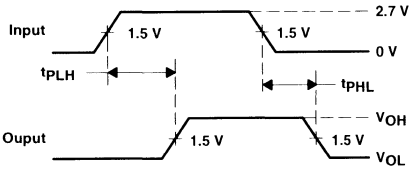


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

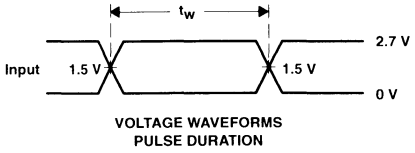
LOAD CIRCUIT



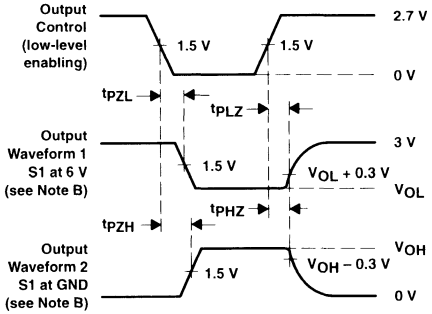
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



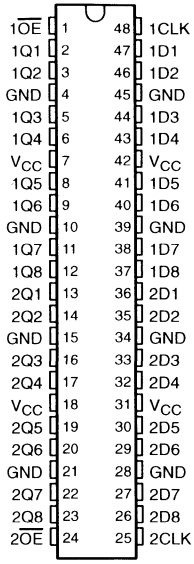
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit edge-triggered D-type flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16374 is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (CLK) input, the Q outputs of the flip-flop take on the logic levels at the data (D) inputs. $\overline{OE}$ can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

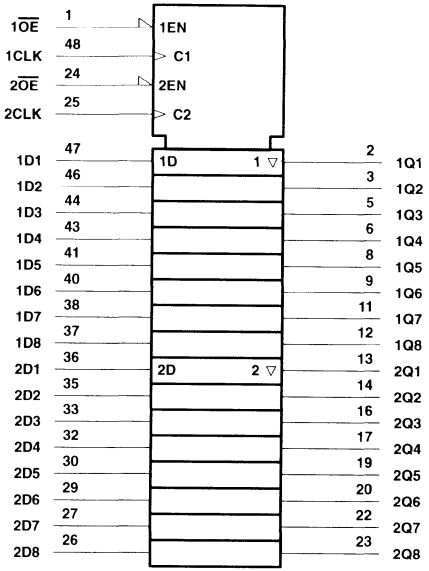
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

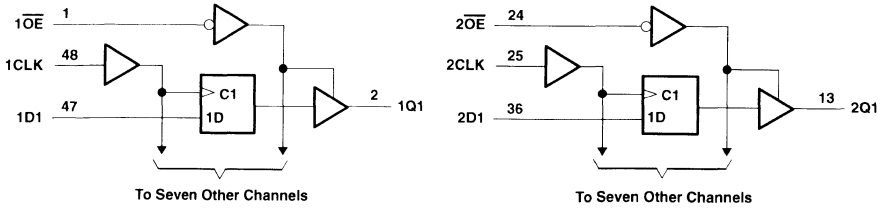
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	2.1		2.2		1.9		ns
t_h	Hold time, data after CLK↑	0.6		0.5		0.5		ns

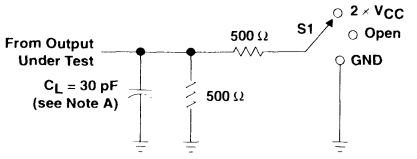
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	5.3		4.9	1	4.2	ns
t_{en}	$\overline{OE}$	Q	1	6.2		5.9	1	4.8	ns
t_{dis}	$\overline{OE}$	Q	1	5.3		4.7	1.2	4.3	ns

operating characteristics, T_A = 25°C

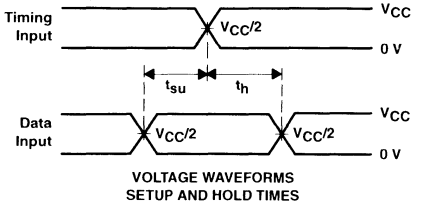
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	31	30	pF
		Outputs disabled		16	18	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

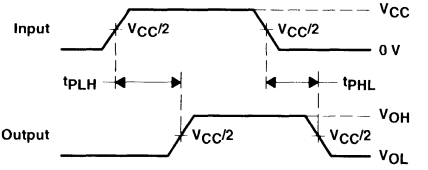


LOAD CIRCUIT

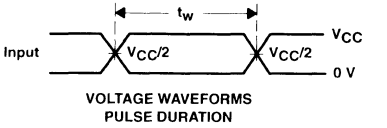
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



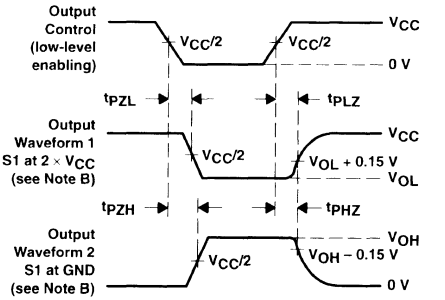
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

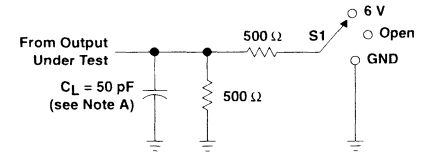


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

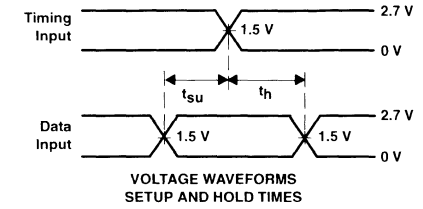
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

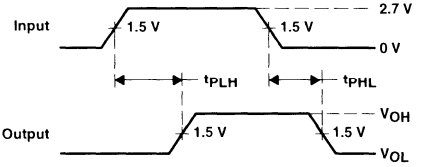


LOAD CIRCUIT

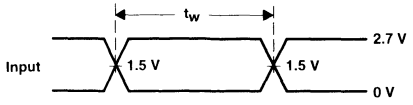
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



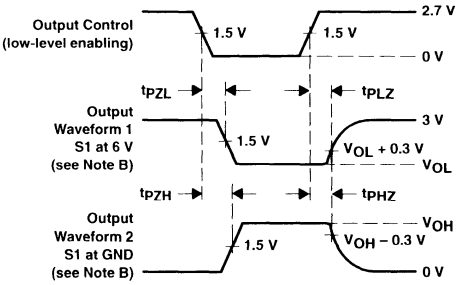
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



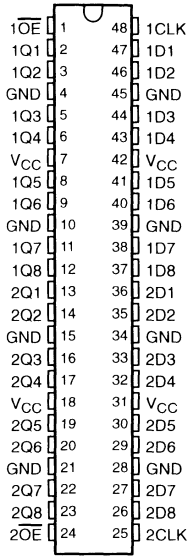
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES:
A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-833, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit edge-triggered D-type flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162374 is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (CLK) input, the Q outputs of the flip-flop take on the logic levels set up at the data (D) inputs.

The output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components. $\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

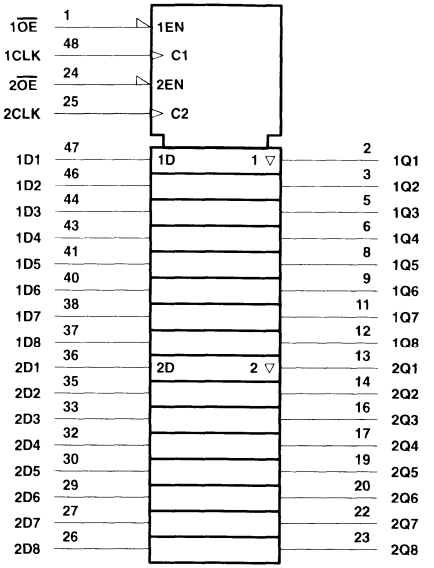
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

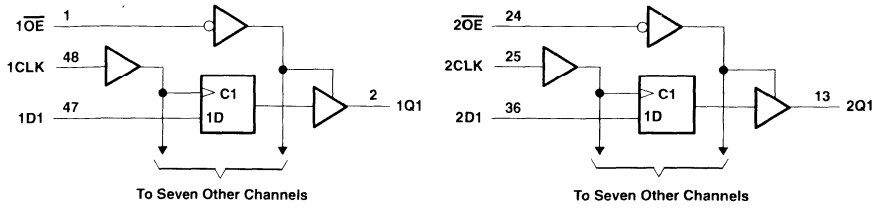
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	2.1		2.2		1.9		ns
t_h	Hold time, data after CLK↑	0.6		0.5		0.5		ns

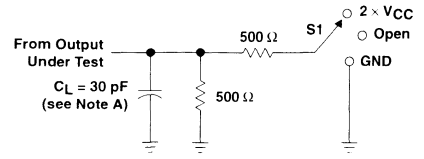
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	5.4		5.4	1	4.6	ns
t_{en}	$\overline{OE}$	Q	1	6.5		6.4	1	5.2	ns
t_{dis}	$\overline{OE}$	Q	1	5.6		5	1.2	4.5	ns

operating characteristics, T_A = 25°C

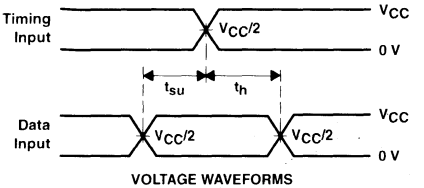
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	28	31	pF
		Outputs disabled		10	11	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

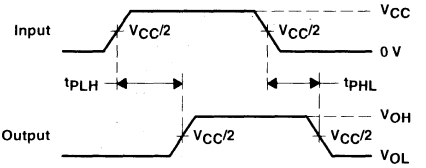


LOAD CIRCUIT

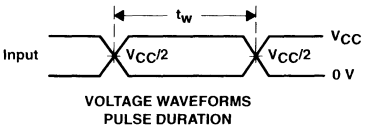
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



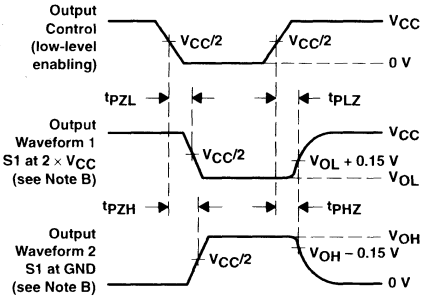
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

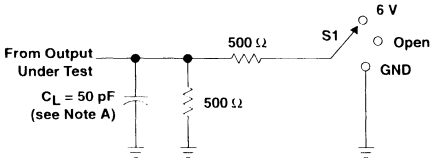


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

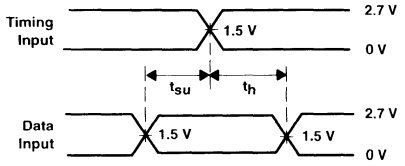
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

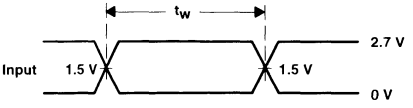


LOAD CIRCUIT

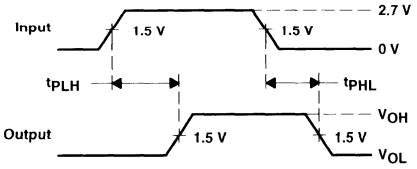
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



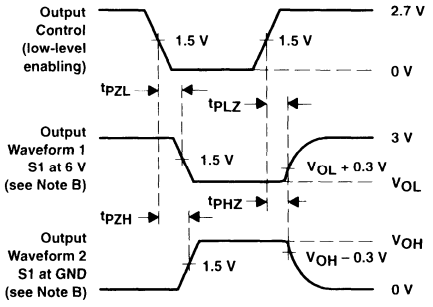
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



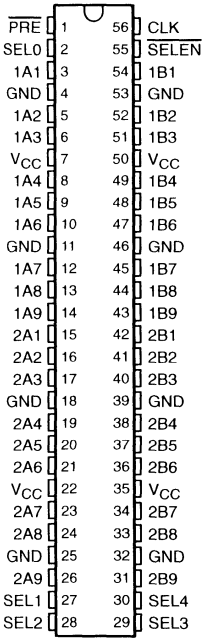
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus+*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBE*™ (Universal Bus Exchanger) Allows Synchronous Data Exchange**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 9-bit, 4-port universal bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16409 allows synchronous data exchange between four different buses. Data flow is controlled by the select (SEL0–SEL4) inputs. A data-flow state is stored on the rising edge of the clock (CLK) input if the select-enable ($\overline{SELEN}$) input is low. Once a data-flow state has been established, data is stored in the flip-flop on the rising edge of CLK if $\overline{SELEN}$ is high.

The data-flow control logic is designed to allow glitch-free data transmission.

When preset ($\overline{PRE}$) transitions high, the outputs are disabled immediately without waiting for a clock pulse. To leave the high-impedance state, both $\overline{PRE}$ and $\overline{SELEN}$ must be low and a clock pulse must be applied.

To ensure the high-impedance state during power up or power down, $\overline{PRE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16409 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

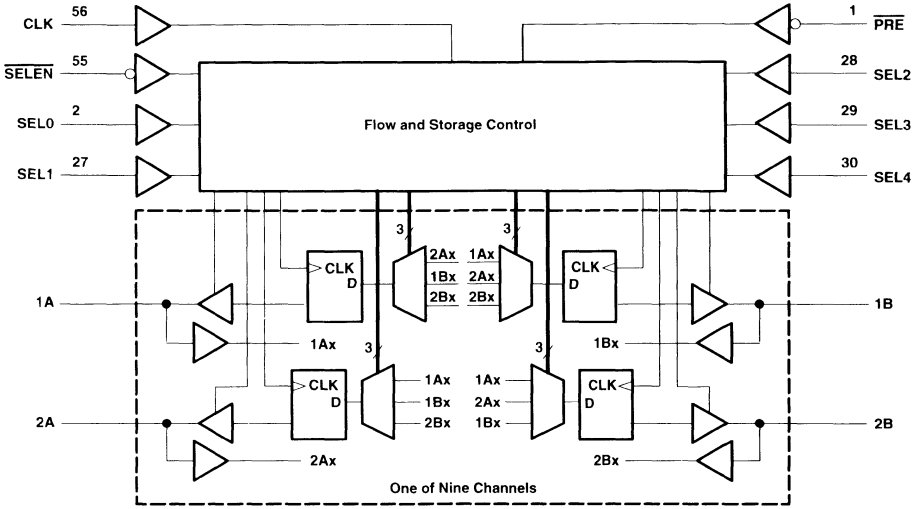
INPUTS		OUTPUT
CLK	SEND PORT	RECEIVE PORT
X	X	B_0†
X	L	L
X	H	H
↑	L	L
↑	H	H
H	X	B_0†
L	X	B_0†

† Output level before the indicated steady-state input conditions were established

DATA-FLOW CONTROL

INPUTS								DATA FLOW
$\overline{PRE}$	$\overline{SELEN}$	CLK	SEL0	SEL1	SEL2	SEL3	SEL4	
H	X	X	X	X	X	X	X	All outputs disabled
L	H	↑	X	X	X	X	X	No change
L	L	↑	0	0	0	0	0	None, all I/Os off
L	L	↑	0	0	0	0	1	Not used
L	L	↑	0	0	0	1	0	Not used
L	L	↑	0	0	0	1	1	Not used
L	L	↑	0	0	1	0	0	Not used
L	L	↑	0	0	1	0	1	Not used
L	L	↑	0	0	1	1	0	Not used
L	L	↑	0	0	1	1	1	Not used
L	L	↑	0	1	0	0	0	2A to 1A and 1B to 2B
L	L	↑	0	1	0	0	1	2A to 1A
L	L	↑	0	1	0	1	0	2B to 1B
L	L	↑	0	1	0	1	1	2A to 1A and 2B to 1B
L	L	↑	0	1	1	0	0	1A to 2A and 1B to 2B
L	L	↑	0	1	1	0	1	1A to 2A
L	L	↑	0	1	1	1	0	1B to 2B
L	L	↑	0	1	1	1	1	1A to 2A and 2B to 1B
L	L	↑	1	0	0	0	0	1A to 1B and 2B to 2A
L	L	↑	1	0	0	0	1	1A to 1B
L	L	↑	1	0	0	1	0	2A to 2B
L	L	↑	1	0	0	1	1	1A to 1B and 2A to 2B
L	L	↑	1	0	1	0	0	1B to 1A and 2A to 2B
L	L	↑	1	0	1	0	1	1B to 1A
L	L	↑	1	0	1	1	0	2B to 2A
L	L	↑	1	0	1	1	1	1B to 1A and 2B to 2A
L	L	↑	1	1	0	0	0	2B to 1A and 2A to 1B
L	L	↑	1	1	0	0	1	1B to 2A
L	L	↑	1	1	0	1	0	2B to 1A
L	L	↑	1	1	0	1	1	2B to 1A and 1B to 2A
L	L	↑	1	1	1	0	0	1A to 2B and 1B to 2A
L	L	↑	1	1	1	0	1	1A to 2B
L	L	↑	1	1	1	1	0	2A to 1B
L	L	↑	1	1	1	1	1	1A to 2B and 2A to 1B

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	120	0	120	MHz
t_w	Pulse duration, CLK high or low		4.2		4.2		3		ns
t_{su}	Setup time	A or B before CLK↑	1.9		1.9		1.4		ns
		SEL before CLK↑	5.1		4.2		3.5		
		$\overline{SELEN}$ before CLK↑	2.5		2.5		1.8		
		$\overline{PRE}$ before CLK↑	1		1		0.7		
t_h	Hold time	A or B after CLK↑	0.8		0.8		1		ns
		SEL after CLK↑	0		0		0		
		$\overline{SELEN}$ after CLK↑	0.5		0.5		0.8		

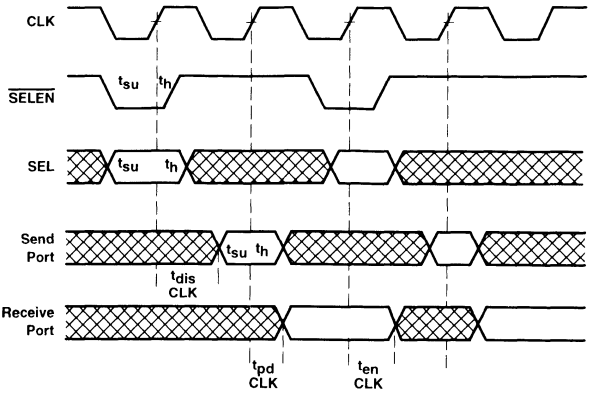
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		120		120		MHz
t_{pd}	CLK	A or B	1.5	6		5.7	1.5	5.1	ns
t_{en}	CLK	A or B	2.4	6.9		6.3	2	5.7	ns
t_{dis}	CLK	A or B	2.3	7.1		6	2	5.7	ns
	$\overline{PRE}$		2.8	7.5		6.5	2.5	6.1	

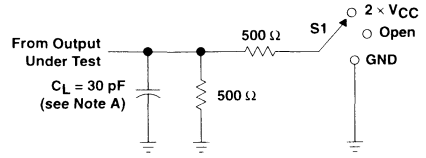
operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	60	60	pF
		Outputs disabled		60	60	

timing diagram

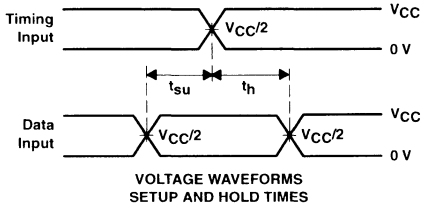


PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

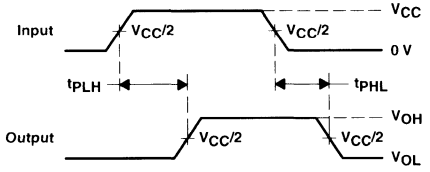


LOAD CIRCUIT

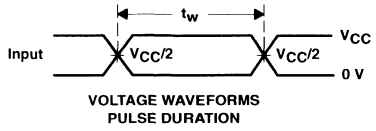
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



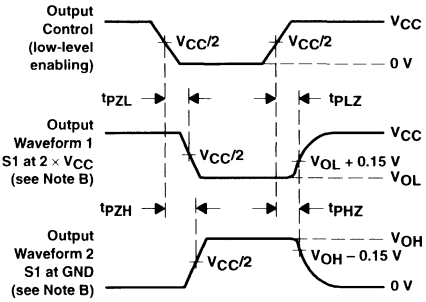
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

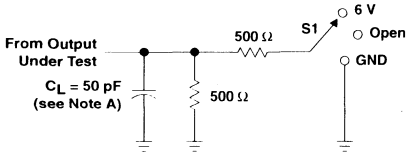


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

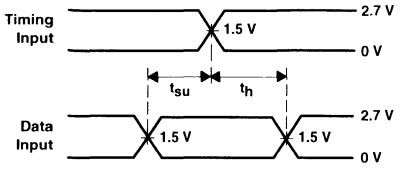
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

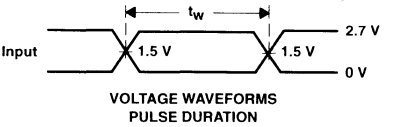


LOAD CIRCUIT

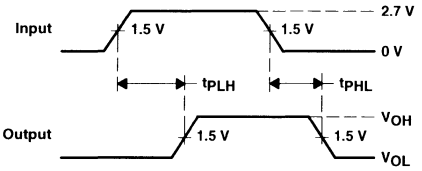
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



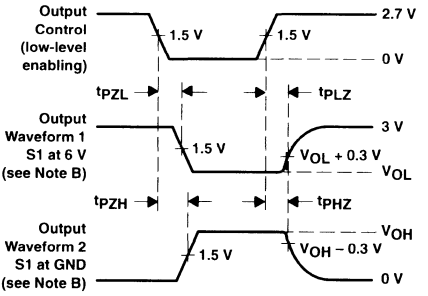
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



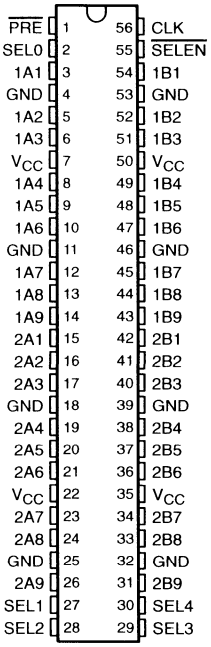
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES:
A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus+*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **B-Port Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- ***UBE*™ (Universal Bus Exchanger) Allows Synchronous Data Exchange**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 9-bit, 4-port universal bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCHR162409 allows synchronous data exchange between four different buses. Data flow is controlled by the select (SEL0–SEL4) inputs. A data-flow state is stored on the rising edge of the clock (CLK) input if the select-enable ($\overline{SELEN}$) input is low. Once a data-flow state has been established, data is stored in the flip-flop on the rising edge of CLK if $\overline{SELEN}$ is high.

The data-flow control logic is designed to allow glitch-free data transmission.

The B outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

When preset ($\overline{PRE}$) transitions high, the outputs are disabled immediately without waiting for a clock pulse. To leave the high-impedance state, both $\overline{PRE}$ and $\overline{SELEN}$ must be low and a clock pulse must be applied.

To ensure the high-impedance state during power up or power down, $\overline{PRE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCHR162409 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

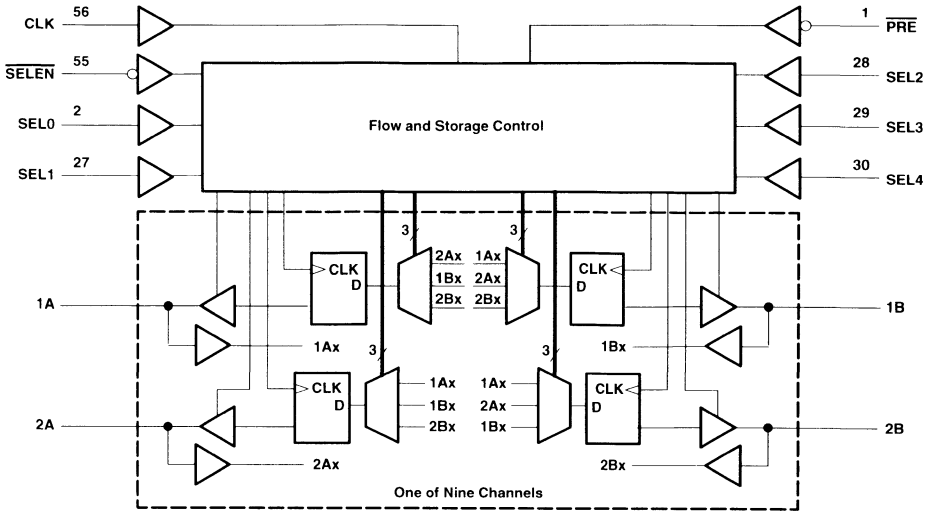
INPUTS		OUTPUT
CLK	SEND PORT	RECEIVE PORT
X	X	B_0†
X	L	L
X	H	H
↑	L	L
↑	H	H
H	X	B_0†
L	X	B_0†

† Output level before the indicated steady-state input conditions were established

DATA-FLOW CONTROL

INPUTS								DATA FLOW
$\overline{PRE}$	$\overline{SELEN}$	CLK	SEL0	SEL1	SEL2	SEL3	SEL4	
H	X	X	X	X	X	X	X	All outputs disabled
L	H	↑	X	X	X	X	X	No change
L	L	↑	0	0	0	0	0	None, all I/Os off
L	L	↑	0	0	0	0	1	Not used
L	L	↑	0	0	0	1	0	Not used
L	L	↑	0	0	0	1	1	Not used
L	L	↑	0	0	1	0	0	Not used
L	L	↑	0	0	1	0	1	Not used
L	L	↑	0	0	1	1	0	Not used
L	L	↑	0	0	1	1	1	Not used
L	L	↑	0	1	0	0	0	2A to 1A and 1B to 2B
L	L	↑	0	1	0	0	1	2A to 1A
L	L	↑	0	1	0	1	0	2B to 1B
L	L	↑	0	1	0	1	1	2A to 1A and 2B to 1B
L	L	↑	0	1	1	0	0	1A to 2A and 1B to 2B
L	L	↑	0	1	1	0	1	1A to 2A
L	L	↑	0	1	1	1	0	1B to 2B
L	L	↑	0	1	1	1	1	1A to 2A and 2B to 1B
L	L	↑	1	0	0	0	0	1A to 1B and 2B to 2A
L	L	↑	1	0	0	0	1	1A to 1B
L	L	↑	1	0	0	1	0	2A to 2B
L	L	↑	1	0	0	1	1	1A to 1B and 2A to 2B
L	L	↑	1	0	1	0	0	1B to 1A and 2A to 2B
L	L	↑	1	0	1	0	1	1B to 1A
L	L	↑	1	0	1	1	0	2B to 2A
L	L	↑	1	0	1	1	1	1B to 1A and 2B to 2A
L	L	↑	1	1	0	0	0	2B to 1A and 2A to 1B
L	L	↑	1	1	0	0	1	1B to 2A
L	L	↑	1	1	0	1	0	2B to 1A
L	L	↑	1	1	0	1	1	2B to 1A and 1B to 2A
L	L	↑	1	1	1	0	0	1A to 2B and 1B to 2A
L	L	↑	1	1	1	0	1	1A to 2B
L	L	↑	1	1	1	1	0	2A to 1B
L	L	↑	1	1	1	1	1	1A to 2B and 2A to 1B

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA,		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	120	0	120	MHz
t_w	Pulse duration, CLK high or low		4.2		4.2		3		ns
t_{su}	Setup time	A or B before CLK↑	1.9		1.9		1.4		ns
		SEL before CLK↑	5.1		4.2		3.5		
		$\overline{SELEN}$ before CLK↑	2.5		2.5		1.8		
		$\overline{PRE}$ before CLK↑	1		1		0.7		
t_h	Hold time	A or B after CLK↑	0.8		0.8		1		ns
		SEL after CLK↑	0		0		0		
		$\overline{SELEN}$ after CLK↑	0.5		0.5		0.8		

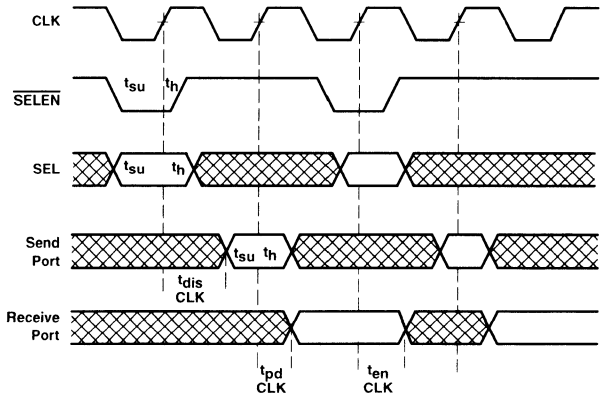
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		120		120		MHz
t_{pd}	CLK	A or B	1.5	6.9		7	1.5	6.2	ns
t_{en}	CLK	A or B	2.4	7.8		7.6	2	6.8	ns
t_{dis}	CLK	A or B	2.3	7.1		6.4	2	6.1	ns
	$\overline{PRE}$		2.8	7.7		7	2.5	6.4	

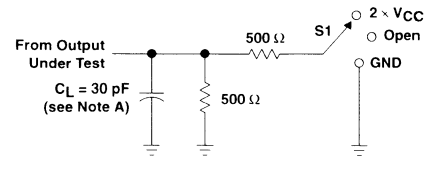
operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	60	60	pF
		Outputs disabled		60	60	

timing diagram

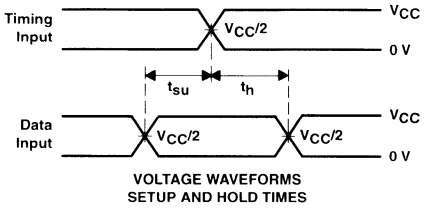


PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

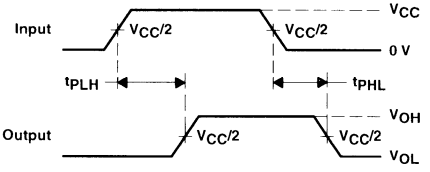


LOAD CIRCUIT

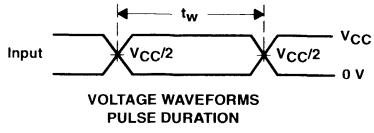
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



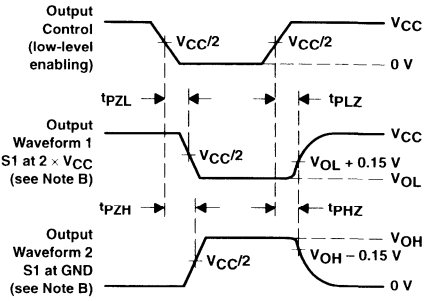
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

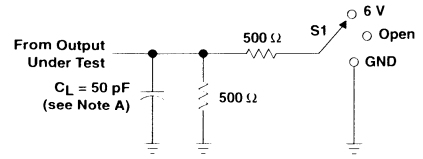


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

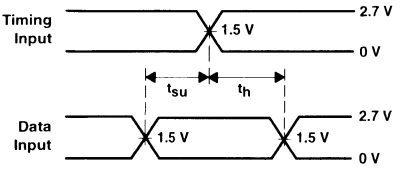
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

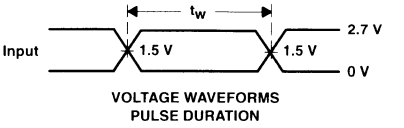


LOAD CIRCUIT

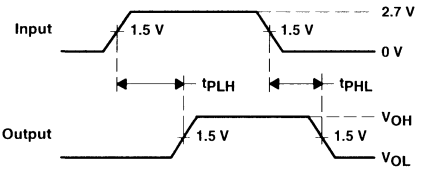
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



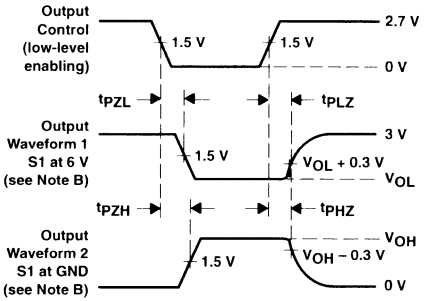
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



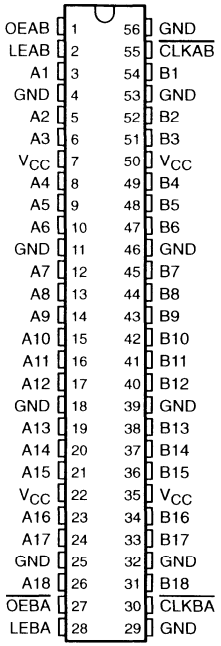
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock ($\overline{CLKAB}$ and $\overline{CLKBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if $\overline{CLKAB}$ is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the high-to-low transition of $\overline{CLKAB}$. Output-enable OEAB is active high. When OEAB is high, the B-port outputs are active. When OEAB is low, the B-port outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, and $\overline{CLKBA}$. The output enables are complementary (OEAB is active high, and $\overline{OEBA}$ is active low).

To ensure the high-impedance state during power up or power down, $\overline{OEBA}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

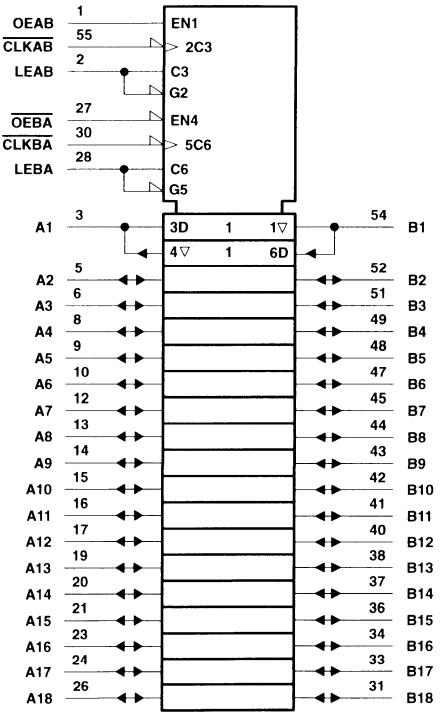
The SN74ALVCH16500 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
OEAB	LEAB	$\overline{CLKAB}$	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	O	L	L
H	L	↓	H	H
H	L	L or H	X	B_0‡

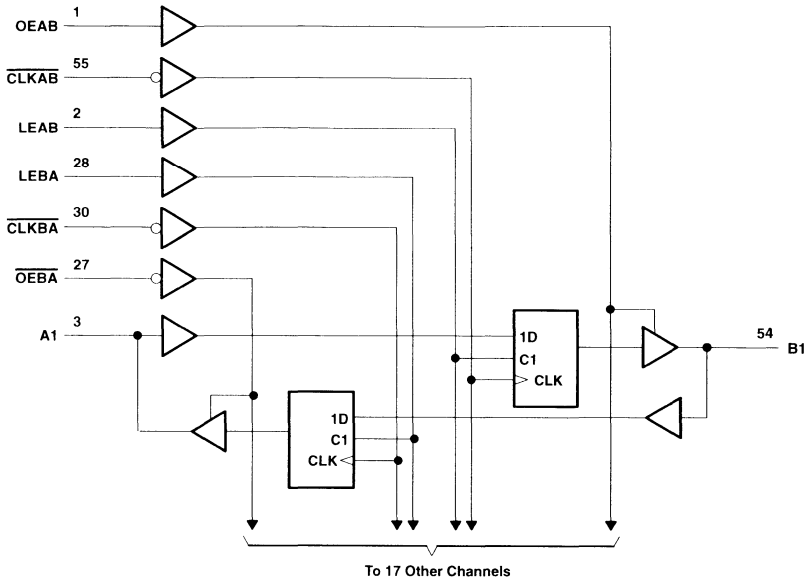
† A-to-B data flow is shown: B-to-A flow is similar but uses OEBA, LEBA, and CLKBA.
‡ Output level before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	150	0	150	0	150	MHz
t_w	Pulse duration	LE high		3.3		3.3		3.3		ns
		$\overline{CLK}$ high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before $\overline{CLK}$↓		1.7		1.4		1.3		ns
		Data before LE↓	$\overline{CLK}$ high	1.1		1		1		
			$\overline{CLK}$ low	1.9		1.6		1.4		
t_h	Hold time	Data after $\overline{CLK}$↓		1.7		1.6		1.3		ns
		Data after LE↓	$\overline{CLK}$ high	2		1.8		1.5		
			$\overline{CLK}$ low	1.6		1.5		1.2		

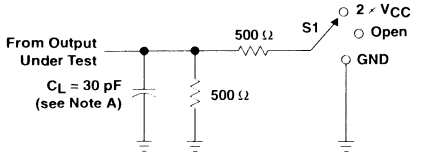
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A or B	B or A	1	5.1		4.7	1	3.9	ns
	LEAB or LEBA	A or B	1	5.9		5.5	1	4.7	
	$\overline{CLKAB}$ or $\overline{CLKBA}$		1	6.6		6.6	1.1	5.5	
t_{en}	OEAB	B	1	5.7		5.4	1	4.6	ns
t_{dis}	OEAB	B	1	6.1		5.7	1.5	5	ns
t_{en}	$\overline{OEBA}$	A	1	6.2		6.2	1	5.2	ns
t_{dis}	$\overline{OEBA}$	A	1	5.4		4.6	1	4.3	ns

operating characteristics, T_A = 25°C

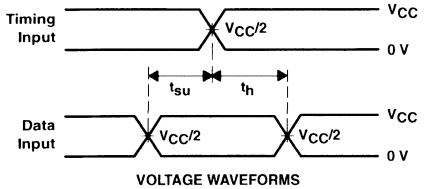
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	40	51	pF
		Outputs disabled		6	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

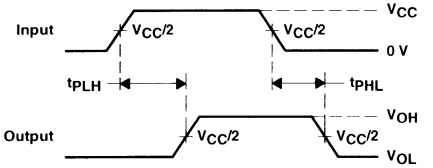


LOAD CIRCUIT

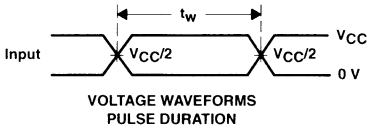
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



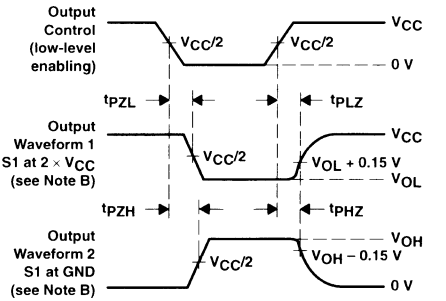
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

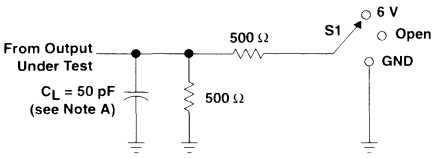


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

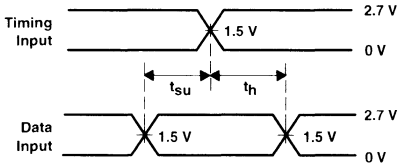
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

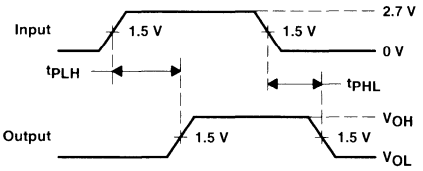


LOAD CIRCUIT

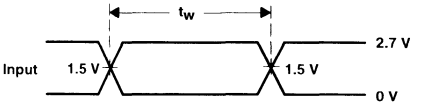
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



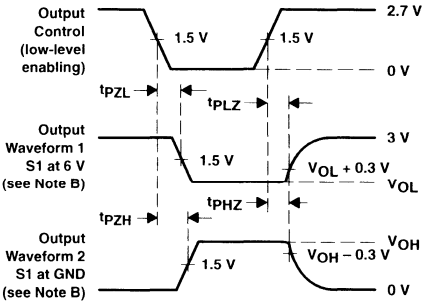
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



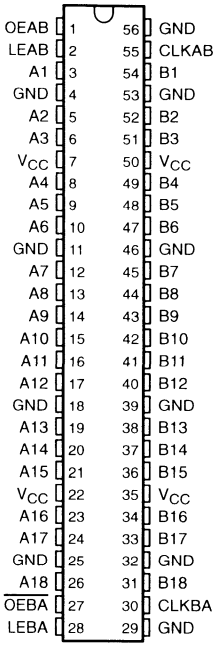
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. When OEAB is high, the outputs are active. When OEAB is low, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, and CLKBA. The output enables are complementary (OEAB is active high and $\overline{OEBA}$ is active low).

To ensure the high-impedance state during power up or power down, $\overline{OEBA}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

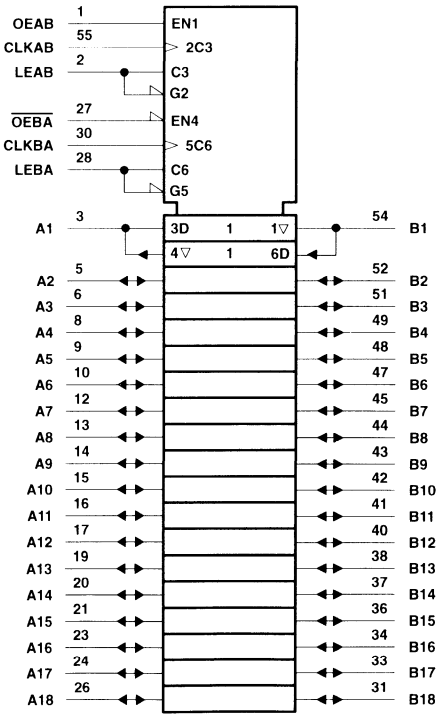
The SN74ALVCH16501 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
OEAB	LEAB	CLKAB	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↑	L	L
H	L	↑	H	H
H	L	L or H	X	B_0‡

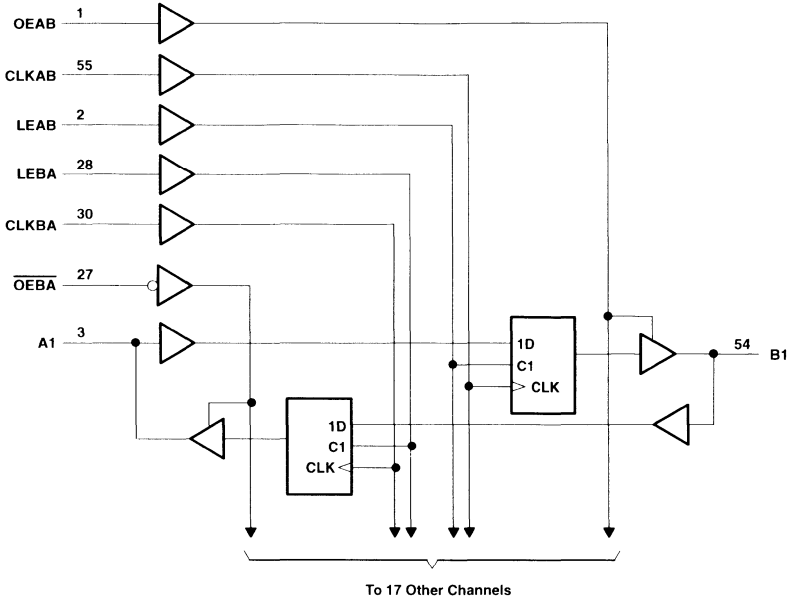
† A-to-B data flow is shown: B-to-A flow is similar but uses OEBA, LEBA, and CLKBA.
‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB is high before LEAB goes low

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	150	0	150	0	150	MHz
t_w	Pulse duration	LE high		3.3		3.3		3.3		ns
		CLK high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑		2.2		2.1		1.7		ns
		Data before LE↓	CLK high	1.9		1.6		1.5		
			CLK low	1.3		1.1		1		
t_h	Hold time	Data after CLK↑		0.6		0.6		0.7		ns
		Data after LE↓	CLK high or low	1.4		1.7		1.4		

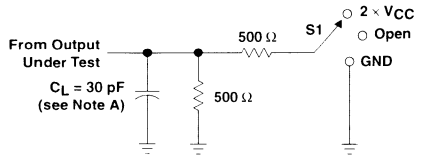
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A or B	B or A	1	4.8		4.5	1	3.9	ns
	LE	A or B	1.1	5.7		5.3	1.3	4.6	
	CLK		1.2	6.1		5.6	1.4	4.9	
t_{en}	OEAB	B	1	5.8		5.3	1	4.6	ns
t_{dis}	OEAB	B	1.5	6.2		5.7	1.4	5	ns
t_{en}	$\overline{OEBA}$	A	1.3	6.3		6	1.1	5	ns
t_{dis}	$\overline{OEBA}$	A	1.3	5.3		4.6	1.3	4.2	ns

operating characteristics, T_A = 25°C

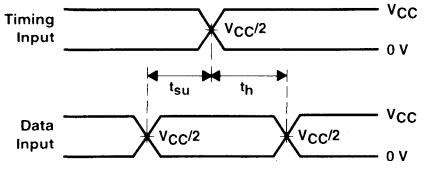
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	44	54	pF
		Outputs disabled		6	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

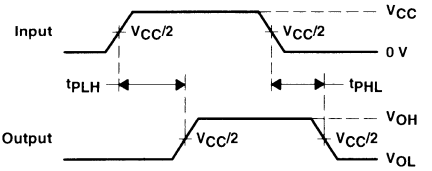


LOAD CIRCUIT

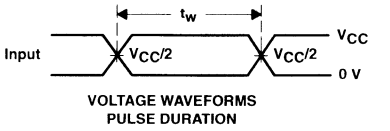
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



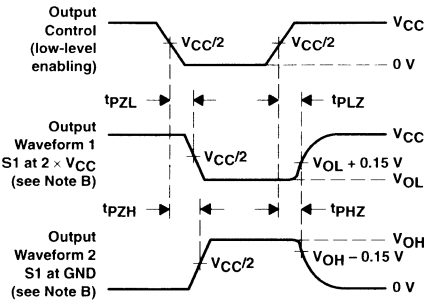
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



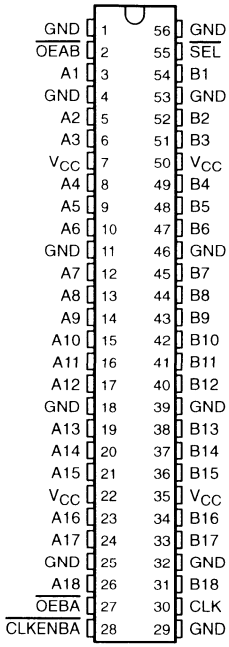
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) and clock-enable ($\overline{CLKENBA}$) inputs. For the A-to-B data flow, the data flows through a single register. The B-to-A data can flow through a four-stage pipeline register path, or through a single register path, depending on the state of the select ($\overline{SEL}$) input.

Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input, provided that the appropriate $\overline{CLKENBA}$ input is low. The B-to-A data transfer is synchronized with CLK.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16524 is characterized for operation from –40°C to 85°C.

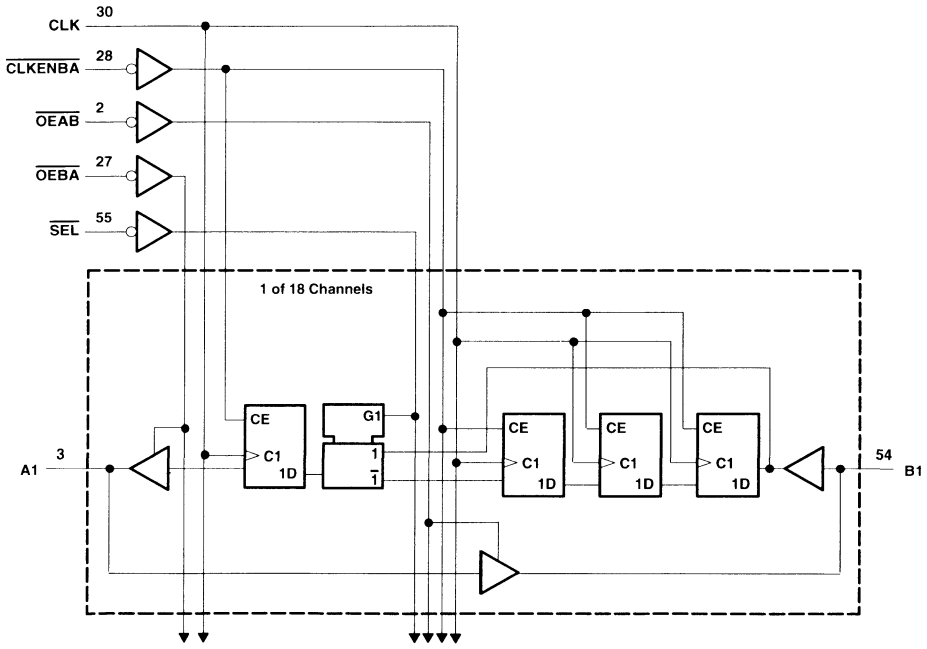
FUNCTION TABLE
B-TO-A STORAGE ($\overline{OEBA}$ = L)

INPUTS				OUTPUT
$\overline{CLKENBA}$	CLK	$\overline{SEL}$	B	A
H	X	X	X	A_0†
L	↑	H	L	L
L	↑	H	H	H
L	↑	L	L	L‡
L	↑	L	H	H‡

† Output level before the indicated steady-state input conditions were established

‡ Four positive CLK edges are needed to propagate data from B to A when $\overline{SEL}$ is low.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
I_{hold}		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	125	0	150	MHz
t_w	Pulse duration, CLK high or low		3.2		3.2		3		ns
t_{su}	Setup time	B data before CLK↑	1.5		1.2		1.1		ns
		$\overline{SEL}$ before CLK↑	2.7		2.4		2.1		
		$\overline{CLKENBA}$ before CLK↑	2.7		2.6		2		
t_h	Hold time	B data after CLK↑	1		0.6		1.2		ns
		$\overline{SEL}$ after CLK↑	0.5		0.2		0.8		
		$\overline{CLKENBA}$ after CLK↑	0.1		0.1		0.3		

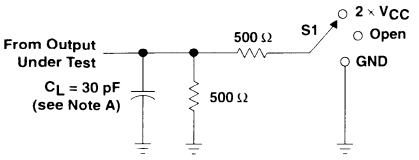
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		125		150		MHz
t_{pd}	A	B	1	3.9		3.8	1	3.2	ns
	CLK	A	1	6.1		6.2	1	5.2	
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	6.1		6.1	1	5.1	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	6.3		5.4	1	4.9	ns

operating characteristics, T_A = 25°C

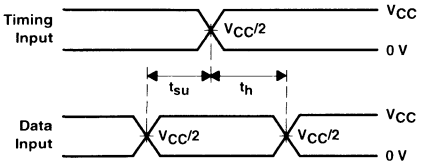
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	160	160	pF
		Outputs disabled		160	160	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

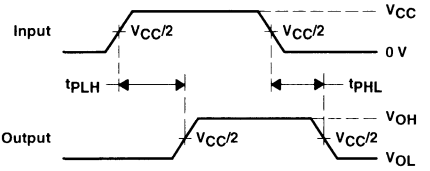


LOAD CIRCUIT

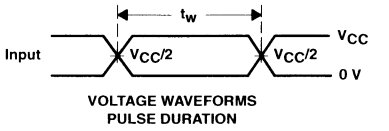
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



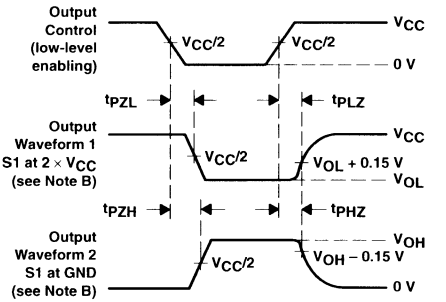
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

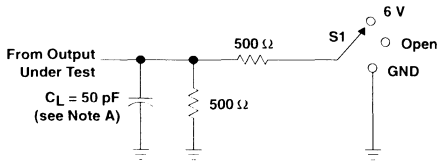


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

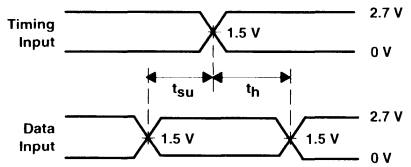
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

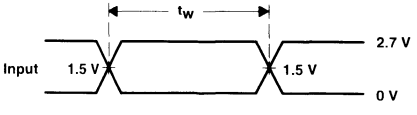


LOAD CIRCUIT

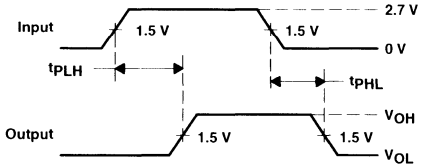
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



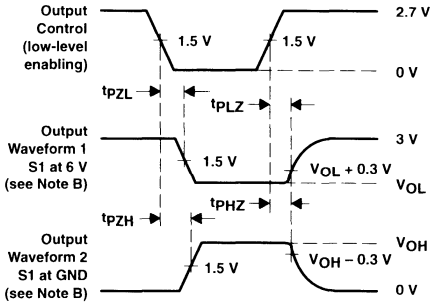
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



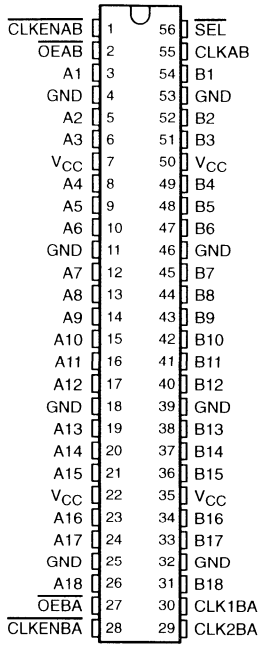
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Option Includes Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) and clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For the A-to-B data flow, the data flows through a single register. The B-to-A data can flow through a four-stage pipeline register path, or through a single register path, depending on the state of the select ($\overline{SEL}$) input.

Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input, provided that the appropriate $\overline{CLKEN}$ inputs are low. The A-to-B data transfer is synchronized to the CLKAB input, and B-to-A data transfer is synchronized with the CLK1BA and CLK2BA inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16525 is characterized for operation from –40°C to 85°C.

Function Tables

A-TO-B STORAGE ($\overline{OEAB}$ = L)

INPUTS			OUTPUT
$\overline{CLKENAB}$	CLKAB	A	B
H	X	X	B_0†
L	↑	L	L
L	↑	H	H

† Output level before the indicated steady-state input conditions were established

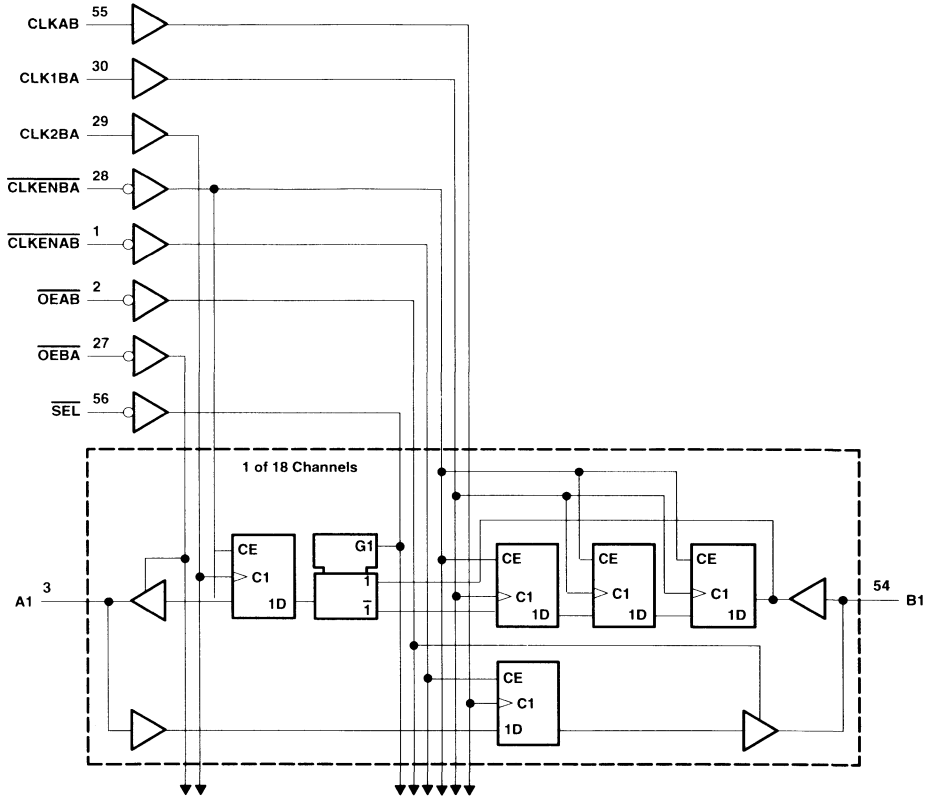
B-TO-A STORAGE ($\overline{OEBA}$ = L)

INPUTS					OUTPUT
$\overline{CLKENBA}$	CLK2BA	CLK1BA	$\overline{SEL}$	B	A
H	X	X	X	X	A_0†
L	↑	X	H	L	L
L	↑	X	H	H	H
L	↑	↑	L	L	L‡
L	↑	↑	L	H	H‡

† Output level before the indicated steady-state input conditions were established

‡ Three CLK1BA edges and one CLK2BA edge are needed to propagate data from B to A when $\overline{SEL}$ is low.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
I_{hold}		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	A or B ports	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input-leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	125	0	150	MHz
t_w	Pulse duration, CLK high or low		3.2		3.2		3		ns
t_{su}	Setup time	A data before CLKAB↑	1.3		1.3		1.3		ns
		B data before CLK2BA↑	2.1		1.8		1.7		
		B data before CLK1BA↑	1.3		1.2		1.1		
		$\overline{SEL}$ before CLK2BA↑	3.3		3.3		3.3		
		$\overline{CLKENAB}$ before CLKAB↑	2.1		1.9		1.6		
		$\overline{CLKENBA}$ before CLK1BA↑	2.7		2.5		2.1		
		$\overline{CLKENBA}$ before CLK2BA↑	2.7		2.5		2.2		
t_h	Hold time	A data after CLKAB↑	0.7		0.4		0.9		ns
		B data after CLK2BA↑	0.4		0		0.6		
		B data after CLK1BA↑	0.8		0.4		1		
		$\overline{SEL}$ after CLK2BA↑	0		0		0.1		
		$\overline{CLKENAB}$ after CLKAB↑	0.1		0.3		0.3		
		$\overline{CLKENBA}$ after CLK1BA↑	0		0		0.1		
		$\overline{CLKENBA}$ after CLK2BA↑	0		0		0		

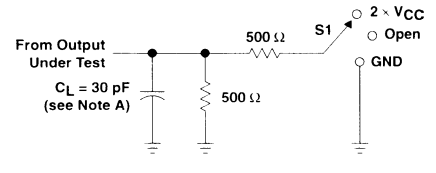
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		125		150		MHz
t_{pd}	CLKAB or CLK2BA	A or B	1	4.5		4.4	1	4.2	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	6.1		6.1	1	5.1	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	6.3		5.4	1	4.9	ns

operating characteristics, T_A = 25°C

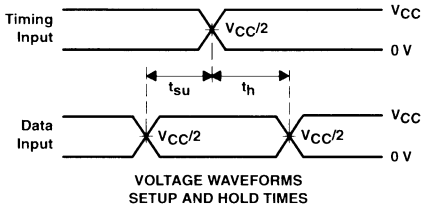
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	160	160	pF
		Outputs disabled				

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

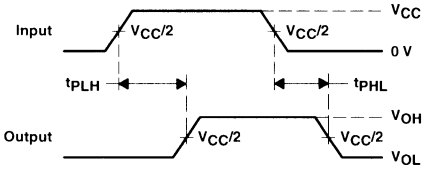


LOAD CIRCUIT

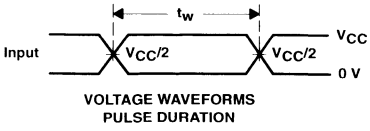
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



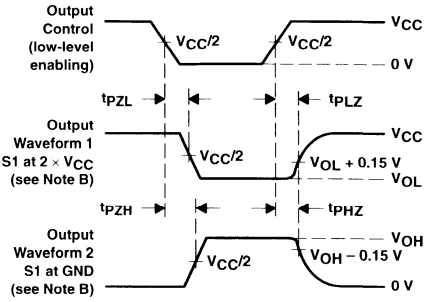
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
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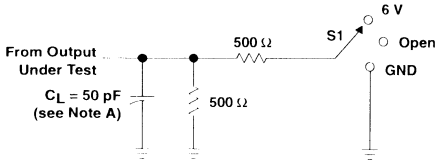
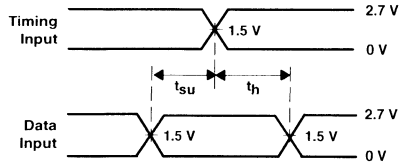
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

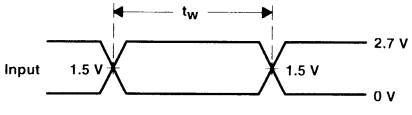


LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



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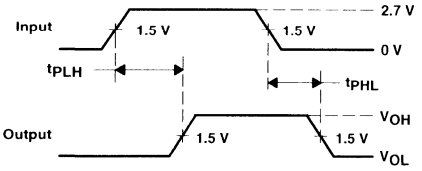
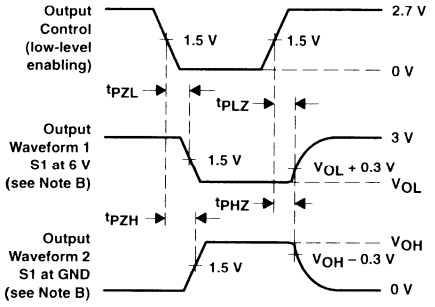


VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



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G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **B-Port Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
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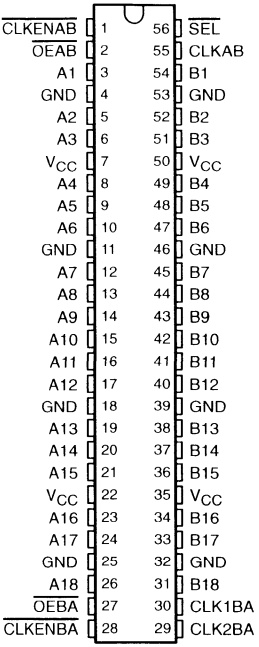
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Option Includes Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) and clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For the A-to-B data flow, the data flows through a single register. The B-to-A data can flow through a four-stage pipeline register path, or through a single register path, depending on the state of the select ($\overline{SEL}$) input.

Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input, provided that the appropriate $\overline{CLKEN}$ inputs are low. The A-to-B data transfer is synchronized to the CLKAB input, and B-to-A data transfer is synchronized with the CLK1BA and CLK2BA inputs.

The B outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162525 is characterized for operation from –40°C to 85°C.

Function Tables

A-TO-B STORAGE ($\overline{OEAB}$ = L)

INPUTS			OUTPUT
$\overline{CLKENAB}$	CLKAB	A	B
H	X	X	B_0†
L	↑	L	L
L	↑	H	H

† Output level before the indicated steady-state input conditions were established

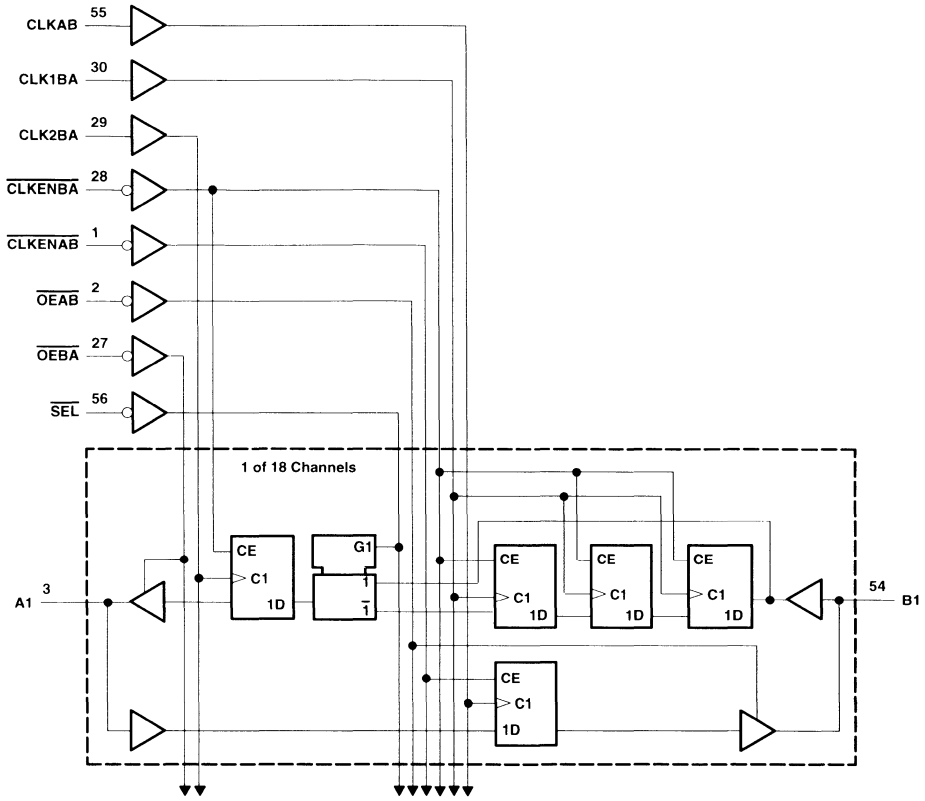
B-TO-A STORAGE ($\overline{OEBA}$ = L)

INPUTS					OUTPUT
$\overline{CLKENBA}$	CLK2BA	CLK1BA	$\overline{SEL}$	B	A
H	X	X	X	X	A_0†
L	↑	X	H	L	L
L	↑	X	H	H	H
L	↑	↑	L	L	L‡
L	↑	↑	L	H	H‡

† Output level before the indicated steady-state input conditions were established

‡ Three CLK1BA edges and one CLK2BA edge are needed to propagate data from B to A when $\overline{SEL}$ is low.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current (A port)	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current (A port)	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
I_{OH}	High-level output current (B port)	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current (B port)	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	A port	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
	B port	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	A port	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
	B port	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	A or B ports	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	125	0	150	MHz
t_w	Pulse duration, CLK high or low		3.2		3.2		3		ns
t_{su}	Setup time	A data before CLKAB↑	1.3		1.3		1.3		ns
		B data before CLK2BA↑	2.1		1.8		1.7		
		B data before CLK1BA↑	1.3		1.2		1.1		
		$\overline{SEL}$ before CLK2BA↑	3.3		3.3		3.3		
		$\overline{CLKENAB}$ before CLKAB↑	2.1		1.9		1.6		
		$\overline{CLKENBA}$ before CLK1BA↑	2.7		2.5		2.1		
		$\overline{CLKENBA}$ before CLK2BA↑	2.7		2.5		2.2		
t_h	Hold time	A data after CLKAB↑	0.7		0.4		0.9		ns
		B data after CLK2BA↑	0.4		0		0.6		
		B data after CLK1BA↑	0.8		0.4		1		
		$\overline{SEL}$ after CLK2BA↑	0		0		0.1		
		$\overline{CLKENAB}$ after CLKAB↑	0.1		0.3		0.3		
		$\overline{CLKENBA}$ after CLK1BA↑	0		0		0.1		
		$\overline{CLKENBA}$ after CLK2BA↑	0		0		0		

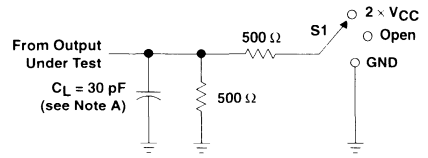
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		125		150		MHz
t_{pd}	CLKAB	B	1	5.5		5.4	1	4.7	ns
	CLK2BA	A	1	4.5		4.4	1	4.2	
t_{en}	$\overline{OEBA}$	A	1	6.1		6.1	1	5.1	ns
	$\overline{OEAB}$	B	1	6.7		6.8	1	5.7	
t_{dis}	$\overline{OEBA}$	A	1	6.3		5.4	1	4.9	ns
	$\overline{OEAB}$	B	1	6.3		5.4	1	4.9	

operating characteristics, T_A = 25°C

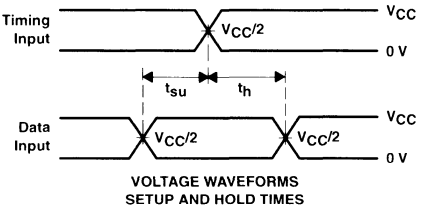
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	160	160	pF
		Outputs disabled		160	160	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

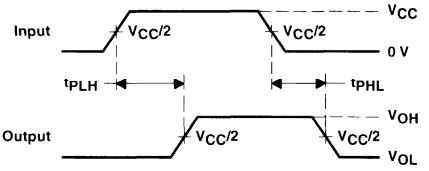


LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



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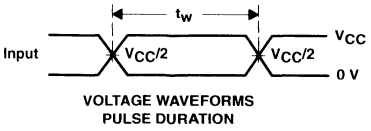
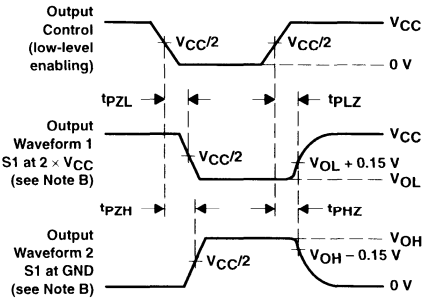


VOLTAGE WAVEFORMS
PULSE DURATION



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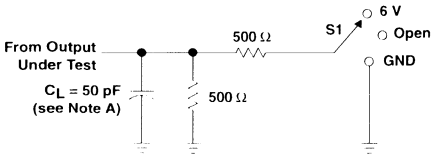

TEST	S1
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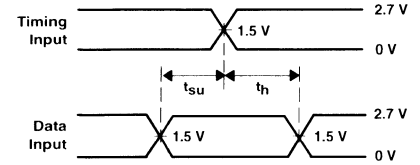
t_{PHZ}/t_{PZH}	GND

LOAD CIRCUIT



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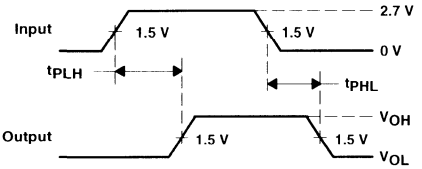

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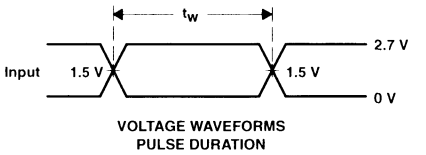

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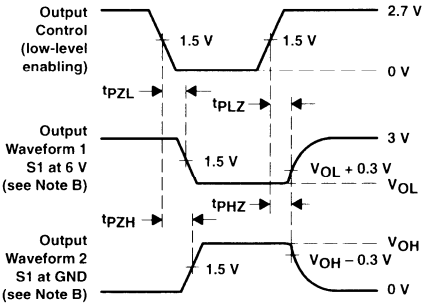

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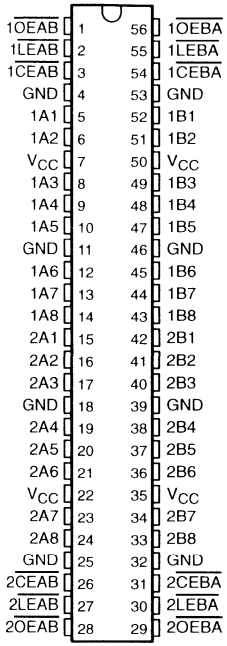
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit registered transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16543 can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

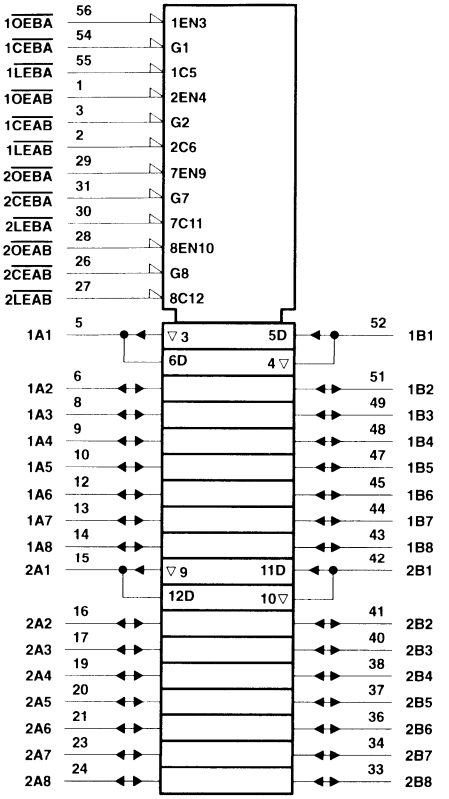
The A-to-B enable ($\overline{CEAB}$) input must be low to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ puts the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar, but requires using $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

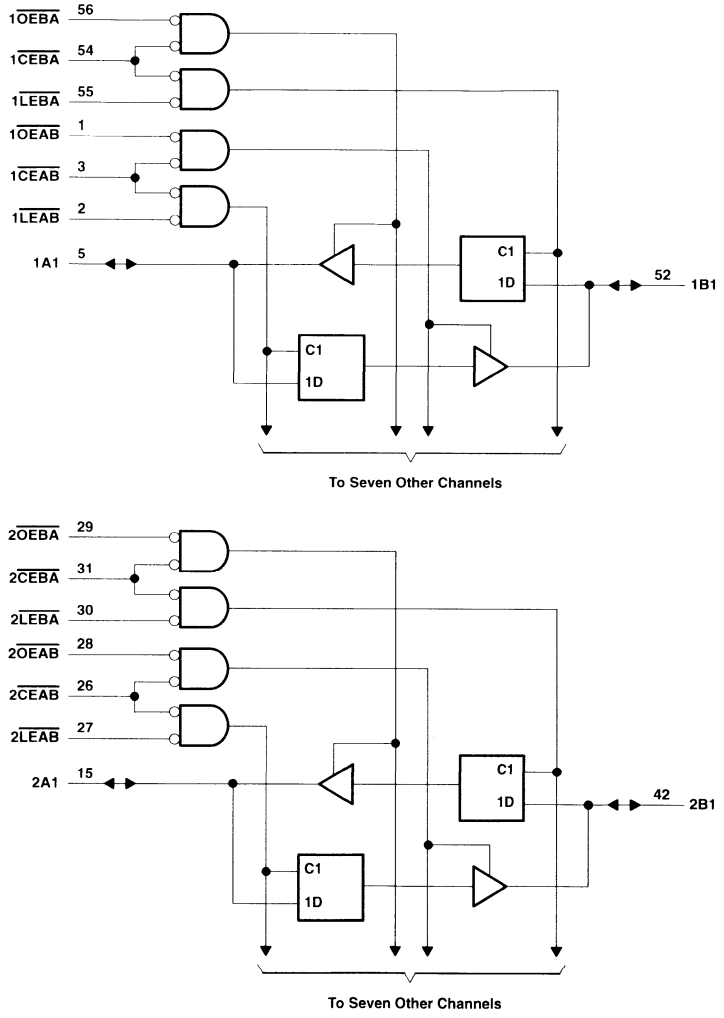
The SN74ALVCH16543 is characterized for operation from –40°C to 85°C.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



FUNCTION TABLE†
(each 8-bit section)

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... 65°C to 150°C

§ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, $\overline{LE}$ or $\overline{CE}$ low		3.3		3.3		3.3		ns
t_{su}	Setup time	Data before $\overline{LE}\uparrow$ or $\overline{CE}\uparrow$	1.2		1.5		1.2		ns
t_h	Hold time	Data after $\overline{LE}\uparrow$ or $\overline{CE}\uparrow$	1.2		0.8		1.3		ns

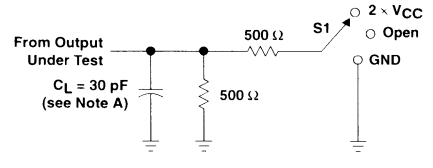
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	5.1		4.8	1	4.3	ns
	$\overline{LE}$	A or B	1	6.5		6.2	1.1	5	
t_{en}	$\overline{CE}$	A or B	1	7.2		6.9	1	5.6	ns
t_{dis}	$\overline{CE}$	A or B	1.3	6.1		6.2	1.5	5.1	ns
t_{en}	$\overline{OE}$	A or B	1	6.8		6.3	1	5.3	ns
t_{dis}	$\overline{OE}$	A or B	1	5.7		4.8	1.1	4.6	ns

operating characteristics, T_A = 25°C

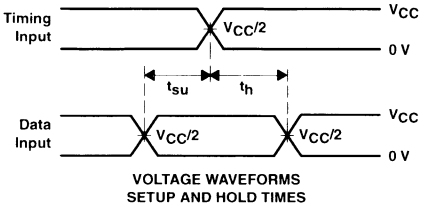
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	54	64	pF
		Outputs disabled		6	7	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

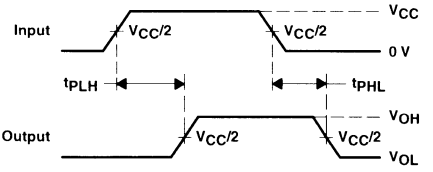


LOAD CIRCUIT

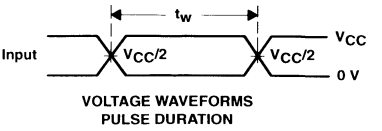
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



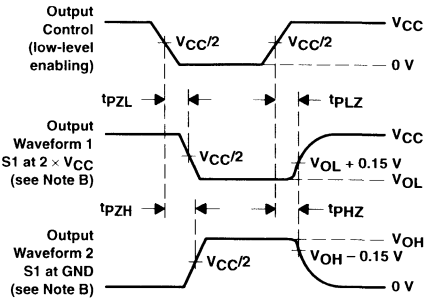
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



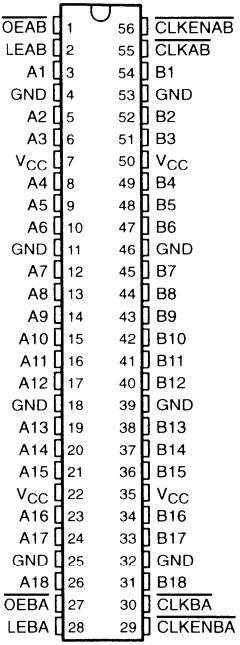
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, Clocked, or Clock-Enabled Mode**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16600 combines D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock ($\overline{CLKAB}$ and $\overline{CLKBA}$) inputs. The clock can be controlled by the clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if $\overline{CLKAB}$ is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the high-to-low transition of $\overline{CLKAB}$. Output enable $\overline{OEAB}$ is active low. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, $\overline{CLKBA}$, and $\overline{CLKENBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

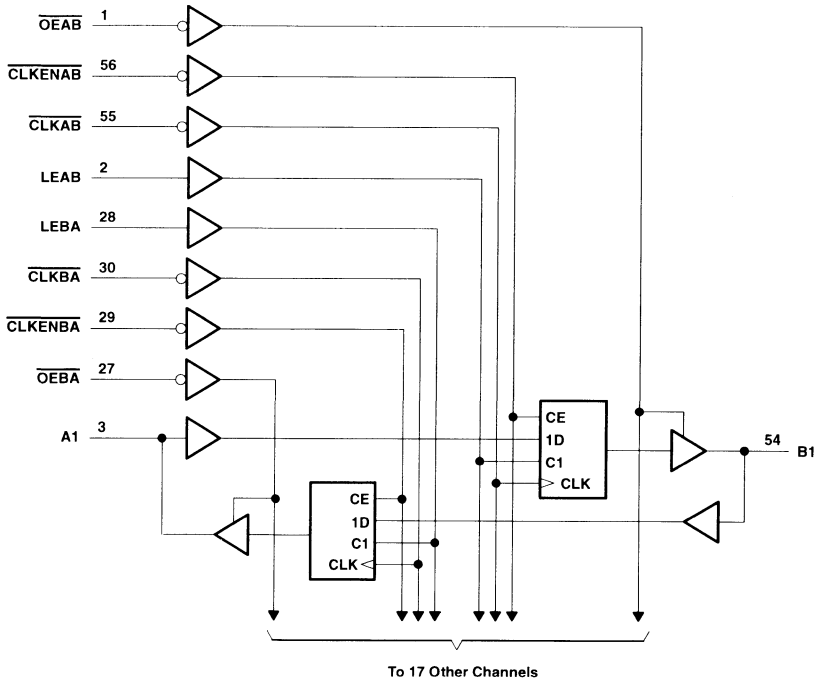
The SN74ALVCH16600 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS					OUTPUT
$\overline{CLKENAB}$	$\overline{OEAB}$	LEAB	$\overline{CLKAB}$	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
H	L	L	X	X	B_0‡
L	L	L	↓	L	L
L	L	L	↓	H	H
L	L	L	L or H	X	B_0‡

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, $\overline{CLKBA}$, and $\overline{CLKENBA}$.
‡ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	150	0	150	0	150	MHz
t_w	Pulse duration	LE high		3.3		3.3		3.3		ns
		$\overline{CLK}$ high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before $\overline{CLK}\uparrow$		1.3		1.3		1.2		ns
		Data before LE↓	$\overline{CLK}$ high	1.2		1.1		1.1		
			$\overline{CLK}$ low	1.8		1.5		1.5		
		$\overline{CLKEN}$ before $\overline{CLK}\uparrow$		0.7		0.7		0.8		
t_h	Hold time	Data after $\overline{CLK}\uparrow$		1.5		1.8		1.5		ns
		Data after LE↓	$\overline{CLK}$ high	1.6		1.9		1.6		
			$\overline{CLK}$ low	1.2		1.6		1.3		
		$\overline{CLKEN}$ after $\overline{CLK}\uparrow$		1.4		1.7		1.4		

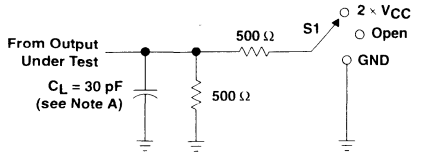
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A or B	B or A	1	5.1		4.7	1	4	ns
	LEAB or LEBA	A or B	1	5.9		5.5	1	4.8	
	$\overline{CLKAB}$ or $\overline{CLKBA}$		1	7.3		6.8	1.3	5.7	
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	6.5		6.3	1.1	5.2	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	5.1		4.7	1.2	4.4	ns

operating characteristics, T_A = 25°C

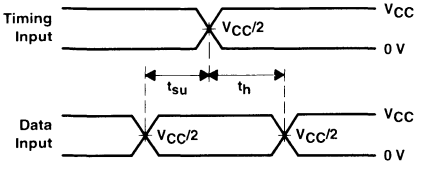
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	43	56	pF
		Outputs disabled		6	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

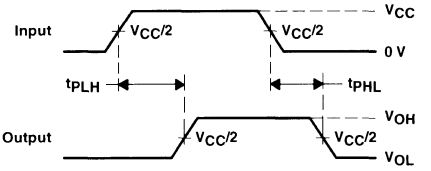


LOAD CIRCUIT

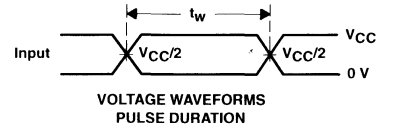
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



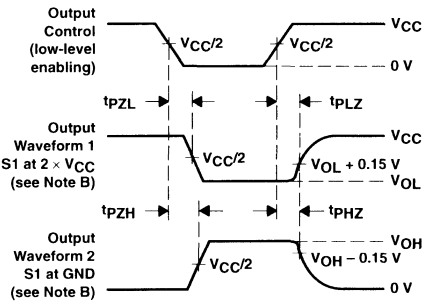
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

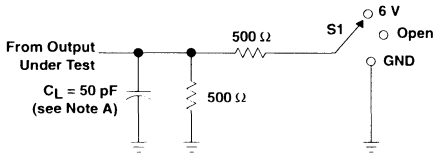


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

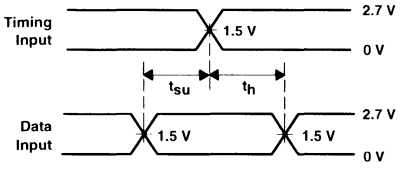
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

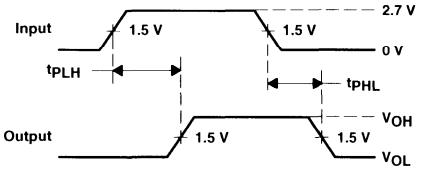


LOAD CIRCUIT

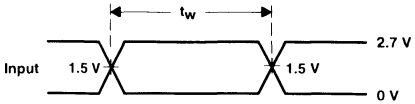
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



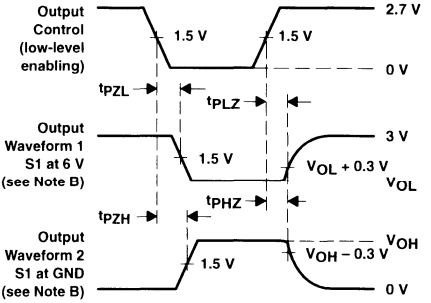
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



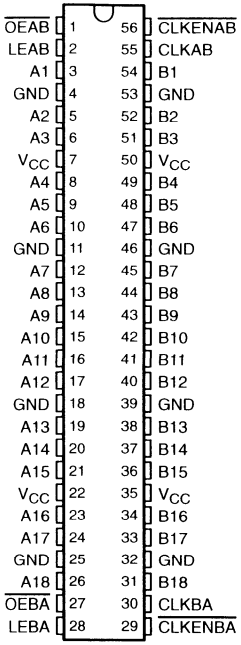
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, Clocked, or Clock-Enabled Mode**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16601 combines D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. The clock can be controlled by the clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. Output enable $\overline{OEAB}$ is active low. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B, but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CLKENBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16601 is characterized for operation from –40°C to 85°C.

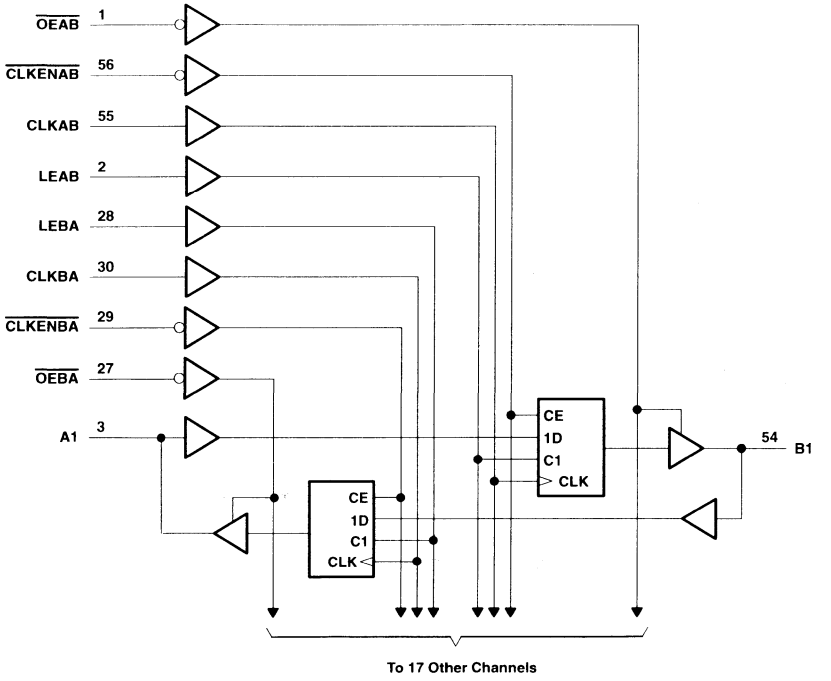
FUNCTION TABLE†

INPUTS					OUTPUT
$\overline{CLKENAB}$	$\overline{OEAB}$	LEAB	CLKAB	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
H	L	L	X	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	L	L or H	X	B_0‡

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CLKENBA}$.

‡ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA			2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V		2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V		2.3 V	1.7			
			V_{IH} = 2 V		2.7 V	2.2			
					3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V		3 V	2			
V_{OL}		I_{OL} = 100 µA			2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V		2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V		2.3 V			0.7	
			V_{IL} = 0.8 V		2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V		3 V			0.55	
I_I		V_I = V_{CC} or GND			3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V			2.3 V	45			µA
		V_I = 1.7 V				–45			
		V_I = 0.8 V			3 V	75			
		V_I = 2 V				–75			
		V_I = 0 to 3.6 V‡			3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND			3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0		3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND		3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND			3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND			3.3 V		8		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	150	0	150	0	150	MHz
t_w	Pulse duration	LE high		3.3		3.3		3.3		ns
		CLK high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑		2.3		2.4		2.1		ns
		Data before LE↓	CLK high	2		1.6		1.6		
			CLK low	1.3		1.2		1.1		
		$\overline{CLKEN}$ before CLK↑		2		2		1.7		
t_h	Hold time	Data after CLK↑		0.7		0.7		0.8		ns
		Data after LE↓	CLK high	1.3		1.6		1.4		
			CLK low	1.7		2		1.7		
		$\overline{CLKEN}$ after CLK↑		0.3		0.5		0.6		

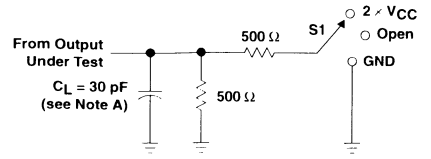
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A or B	B or A	1	4		4.6		4.1	ns
	LEAB or LEBA	A or B	1	4.6		5.3		4.7	
	CLKAB or CLKBA		1.2	5.2		5.8		5	
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1.1	5.3		6.1		5.2	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1.4	4.9		4.8		4.4	ns

operating characteristics, T_A = 25°C

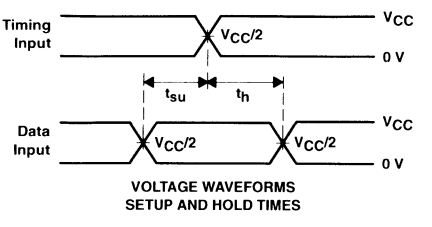
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	41	52	pF
		Outputs disabled		6	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

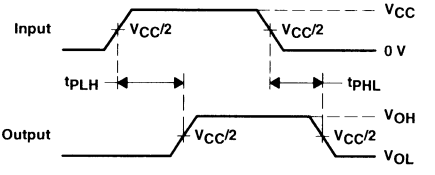


LOAD CIRCUIT

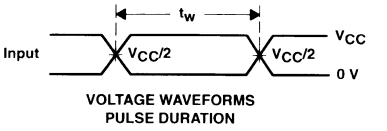
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



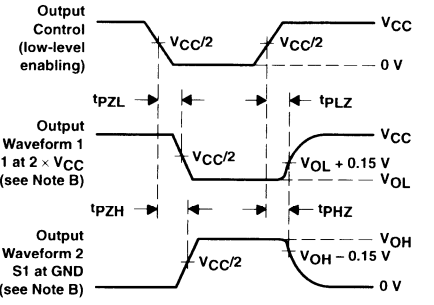
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



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ENABLE AND DISABLE TIMES

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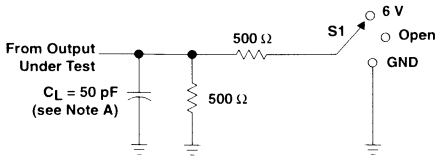
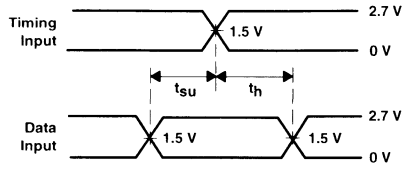
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

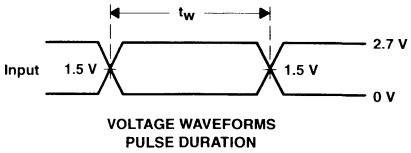


LOAD CIRCUIT

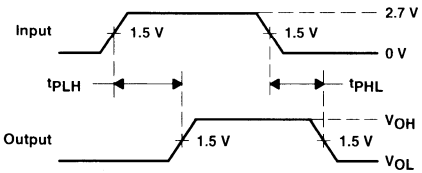
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



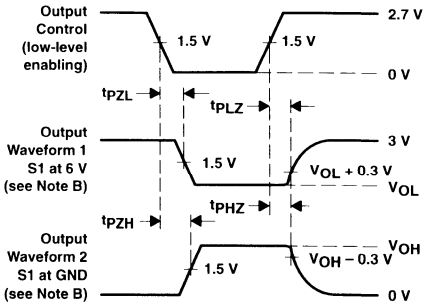
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



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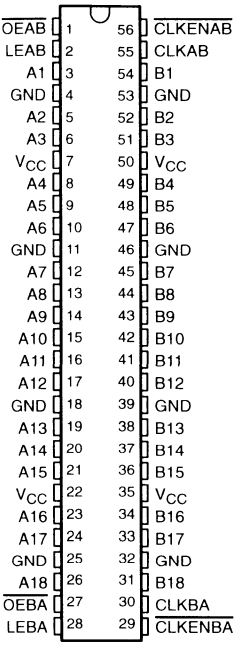
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, Clocked, or Clock-Enabled Mode**
- **B-Port Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162601 combines D-type latches and D-type flip-flops to allow data flow in transparent, latched, clocked, and clock-enabled modes.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. The clock can be controlled by the clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CLKENBA}$.

The B-port outputs include equivalent 26-Ω series resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

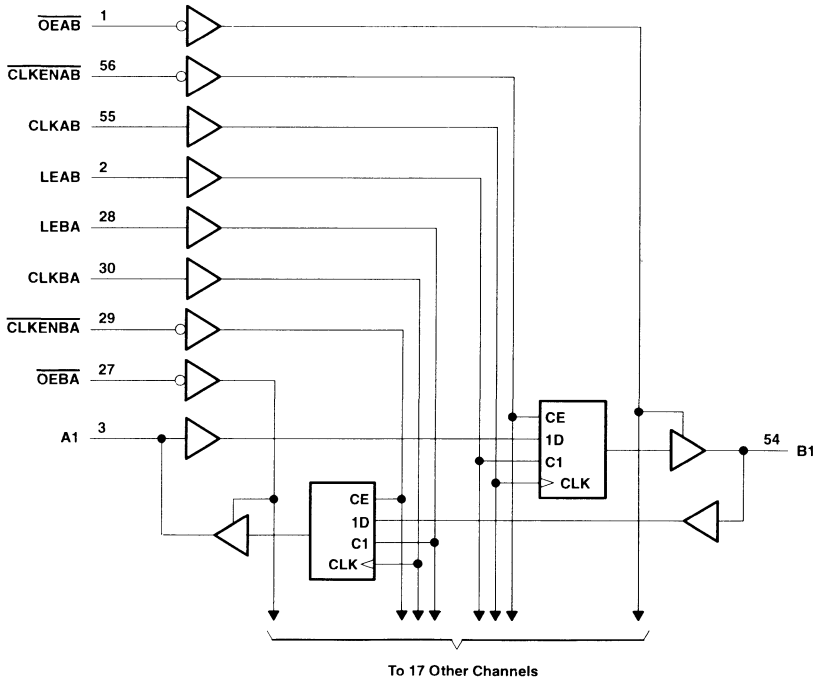
The SN74ALVCH162601 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS					OUTPUT
$\overline{\text{CLKENAB}}$	$\overline{\text{OEAB}}$	LEAB	CLKAB	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
H	L	L	X	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	L	L or H	X	B_0‡

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{\text{OEBA}}$, LEBA, CLKBA, and $\overline{\text{CLKENBA}}$.
‡ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current (B port)	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OH}	High-level output current (A port)	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current (B port)	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
I_{OL}	Low-level output current (A port)	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	B port	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
	A port	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	B port	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
	A port	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	140	0	150	0	150	MHz
t_w	Pulse duration	LE high		3.3		3.3		3.3		ns
		CLK high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑		2.3		2.4		2.1		ns
		Data before LE↓	CLK high	2		1.6		1.6		
			CLK low	1.3		1.2		1.1		
		$\overline{CLKEN}$ before CLK↑		2		2		1.7		
t_h	Hold time	Data after CLK↑		0.7		0.7		0.8		ns
		Data after LE↓	CLK high	1.3		1.6		1.4		
			CLK low	1.7		2		1.7		
		$\overline{CLKEN}$ after CLK↑		0.3		0.5		0.6		

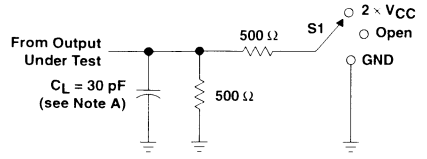
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			140		150		150		MHz
t_{pd}	A	B	1.3	4.8		5.2	1.6	4.5	ns
	B	A	1	4.3		4.6	1	4.1	
	LEAB	B	1	5.5		5.9	1.5	5.1	
	LEBA	A	1	5		5.3	1	4.7	
	CLKAB	B	1.5	6.1		6.3	1.6	5.5	
	CLKBA	A	1.3	5.6		5.8	1.4	5	
t_{en}	$\overline{OEAB}$	B	1.6	6.1		6.7	1.6	5.7	ns
t_{dis}	$\overline{OEAB}$	B	1.8	5.7		5.3	1.8	4.8	ns
t_{en}	$\overline{OEBA}$	A	1.1	5.5		6.1	1.1	5.2	ns
t_{dis}	$\overline{OEBA}$	A	1.3	5.2		4.8	1.6	4.4	ns

operating characteristics, T_A = 25°C

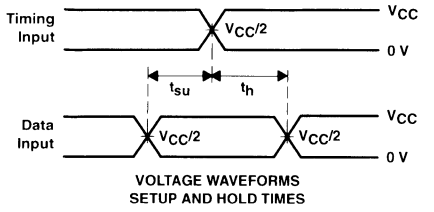
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	41	50	pF
		Outputs disabled		6	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

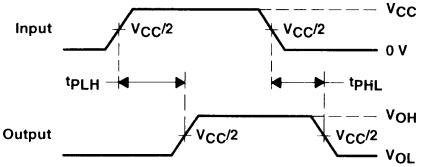


LOAD CIRCUIT

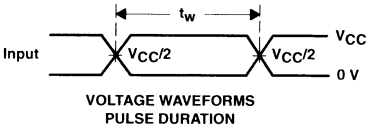
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



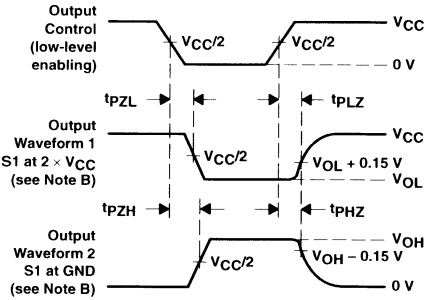
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

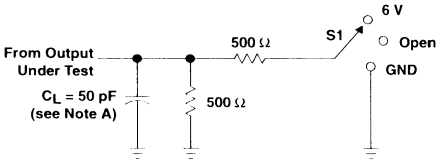


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

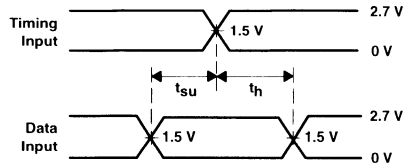
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

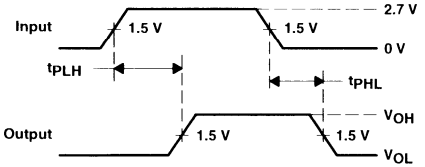


LOAD CIRCUIT

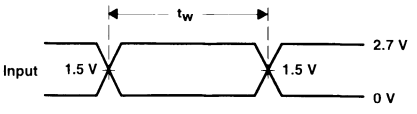
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



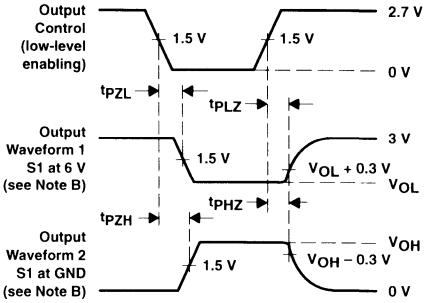
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



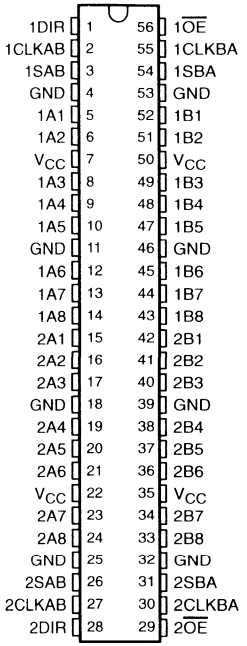
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

This 16-bit bus transceiver and register is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16646 can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74ALVCH16646.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs are provided to control the transceiver functions. In the transceiver mode, data present at the high-impedance port may be stored in either register or in both. The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. DIR determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data may be stored in one register and/or B data may be stored in the other register.

When an output function is disabled, the input function is still enabled and may be used to store and transmit data. Only one of the two buses, A or B, can be driven at a time.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

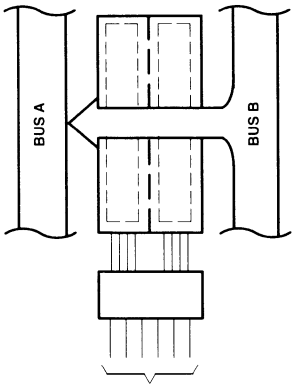
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16646 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

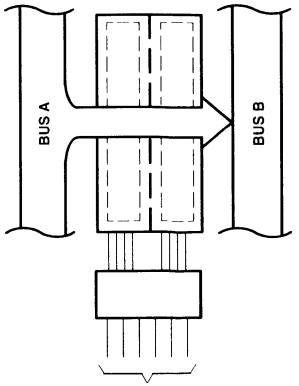
INPUTS						DATA I/Os		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

† The data-output functions may be enabled or disabled by various signals at $\overline{OE}$ and DIR. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.



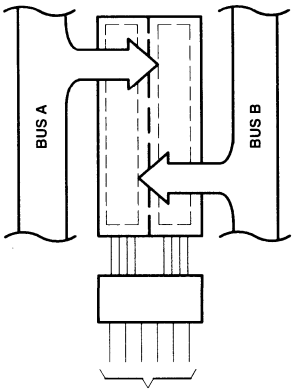
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



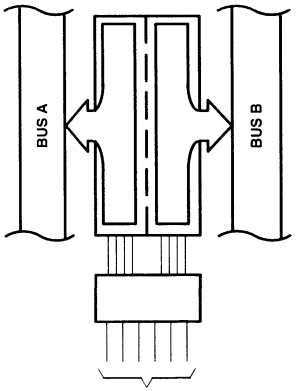
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B

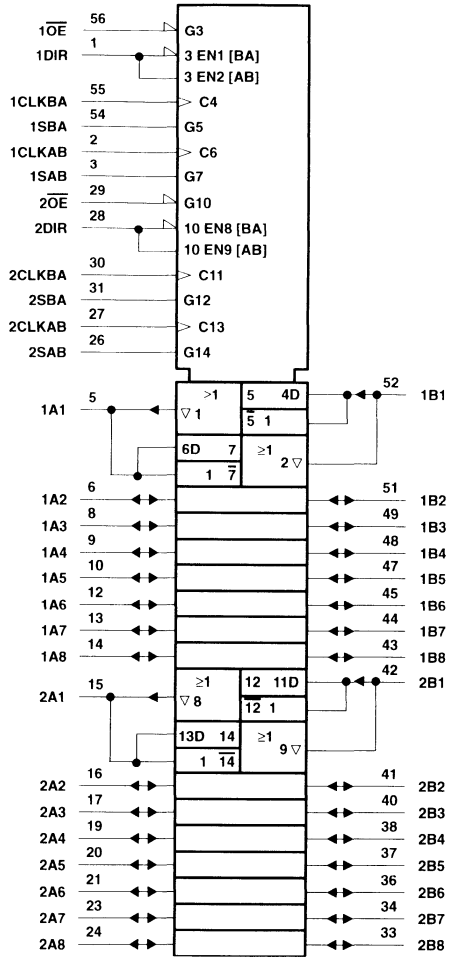


$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA
TO A AND/OR B

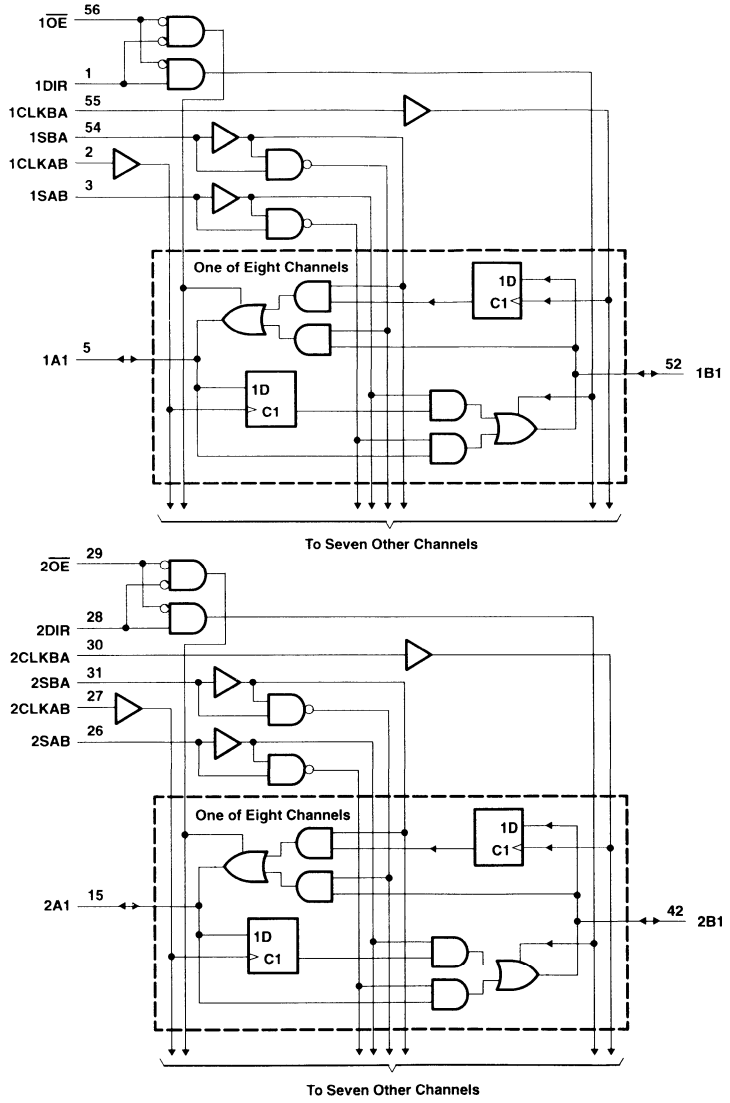
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DGV package ..... 86°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 and 3)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low	3.3		3.3		3.3		ns
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑	1.6		1.7		1.4		ns
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑	0.6		0.4		0.7		ns

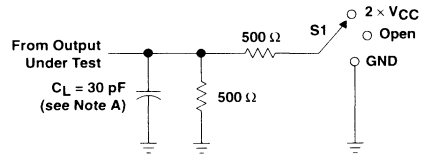
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 and 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A or B	B or A	1	4.8		4.5	1	3.9	ns
	CLKAB or CLKBA	A or B	1	5.6		5.2	1	4.5	
	SAB or SBA		1	6.8		6.4	1	5.3	
t_{en}	$\overline{OE}$	A or B	1	6.5		6.2	1	5.1	ns
t_{dis}	$\overline{OE}$	A or B	1.6	5.7		5	1.4	4.7	ns
t_{en}	DIR	A or B	1	7.8		6.2	1	5.1	ns
t_{dis}	DIR	A or B	1.5	6.5		6	1.1	5.3	ns

operating characteristics, T_A = 25°C

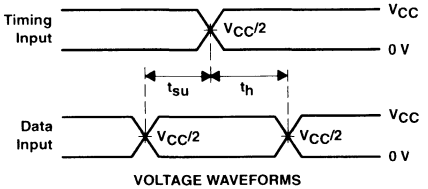
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	39	43	pF
		Outputs disabled		10	12	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

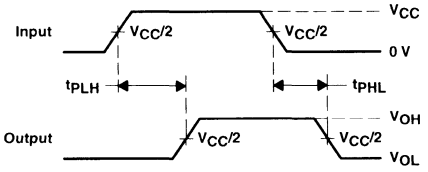


LOAD CIRCUIT

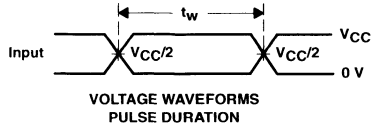
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



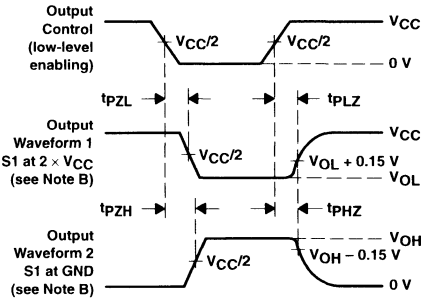
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

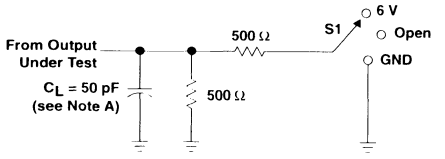


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

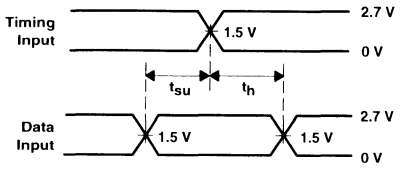
Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

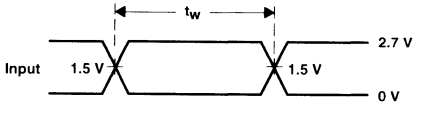


LOAD CIRCUIT

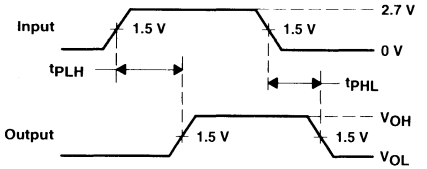
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



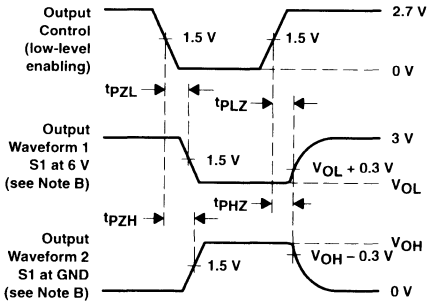
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



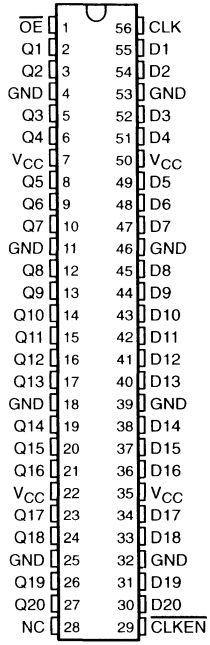
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 20-bit flip-flop is designed specifically for 2.3-V to 3.6-V V_{CC} operation.

The 20 flip-flops of the SN74ALVCH16721 are edge-triggered D-type flip-flops with qualified clock storage. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs if the clock-enable ($\overline{CLKEN}$) input is low. If $\overline{CLKEN}$ is high, no data is stored.

A buffered output-enable ($\overline{OE}$) input places the 20 outputs in either a normal logic state (high or low) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components. $\overline{OE}$ does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

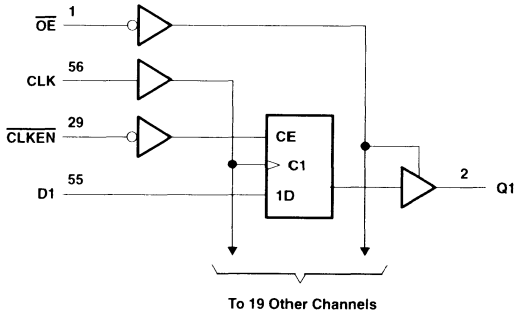
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16721 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS				OUTPUT
$\overline{OE}$	$\overline{CLKEN}$	CLK	D	Q
L	H	X	X	Q_0
L	L	↑	H	H
L	L	↑	L	L
L	L	L or H	X	Q_0
H	X	X	X	Z

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DGV package ..... 86°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	Data before CLK↑	4		3.6		3.1		ns
		$\overline{CLKEN}$ before CLK↑	3.4		3.1		2.7		
t_h	Hold time	Data after CLK↑	0		0		0		ns
		$\overline{CLKEN}$ after CLK↑	0		0		0		

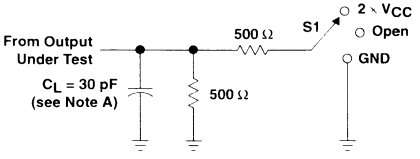
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	5.6	1	5.1	1	4.3	ns
t_{en}	$\overline{OE}$	Q	1	6.1	1	5.8	1	4.8	ns
t_{dis}	$\overline{OE}$	Q	1	5.5	1	4.7	1	4.4	ns

operating characteristics, T_A = 25°C

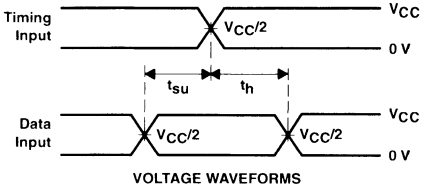
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	55	59	pF
		Outputs disabled		46	49	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

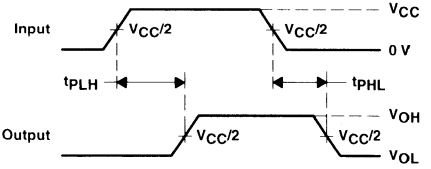


LOAD CIRCUIT

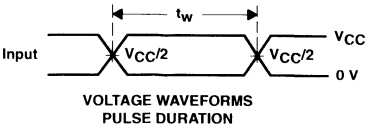
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



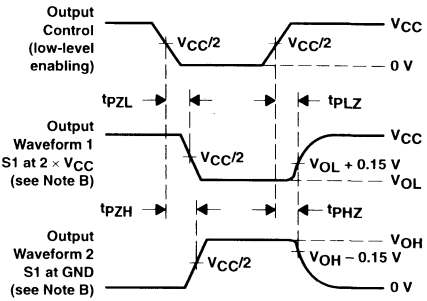
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

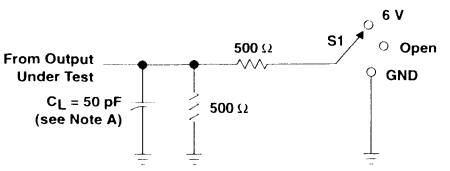


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

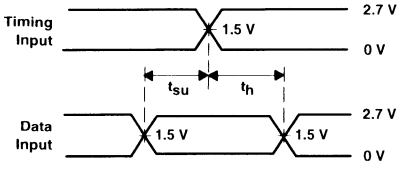
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

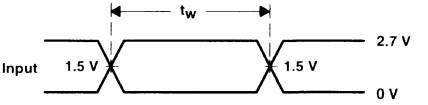


LOAD CIRCUIT

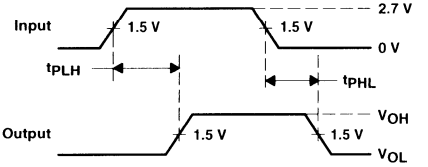
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



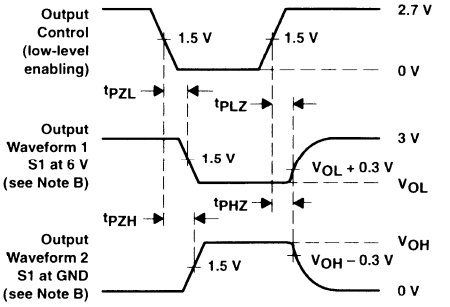
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



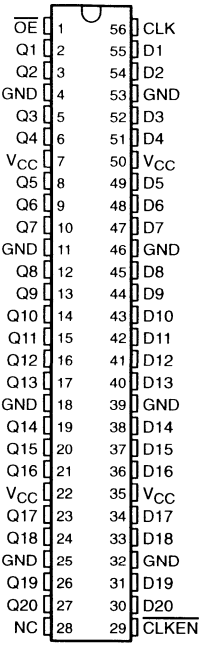
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 20-bit flip-flop is designed for low-voltage 2.3-V to 3.6-V V_{CC} operation.

The 20 flip-flops of the SN74ALVCH162721 are edge-triggered D-type flip-flops with qualified clock storage. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs if the clock-enable ($\overline{CLKEN}$) input is low. If $\overline{CLKEN}$ is high, no data is stored.

A buffered output-enable ($\overline{OE}$) input places the 20 outputs in either a normal logic state (high or low level) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components. $\overline{OE}$ does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

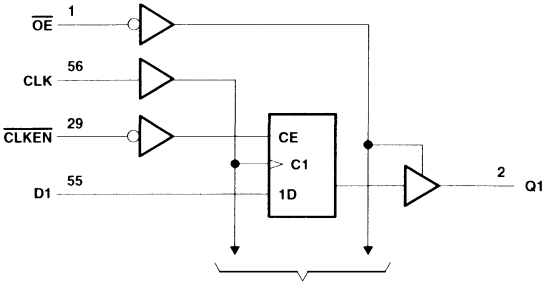
The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

The SN74ALVCH162721 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS				OUTPUT
$\overline{OE}$	$\overline{CLKEN}$	CLK	D	Q
L	H	X	X	Q_0
L	L	↑	H	H
L	L	↑	L	L
L	L	L or H	X	Q_0
H	X	X	X	Z

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
	I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
		V_{IH} = 2 V	3 V	2.4			
	I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
	I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
	I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
	I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
		V_{IL} = 0.8 V	3 V			0.55	
	I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
	I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I	V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.7 V		2.3 V	45			µA
	V_I = 1.7 V		2.3 V	–45			
	V_I = 0.8 V		3 V	75			
	V_I = 2 V		3 V	–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_o	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	Data before CLK↑	4		3.6		3.1		ns
		$\overline{CLKEN}$ before CLK↑	3.4		3.1		2.7		
t_h	Hold time	Data after CLK↑	0		0		0		ns
		$\overline{CLKEN}$ after CLK↑	0		0		0		

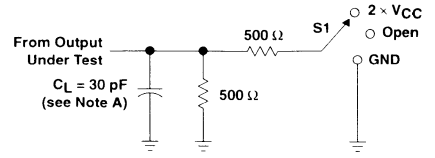
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	6.7		6.2	1	5.3	ns
t_{en}	OE	Q	1	7.2		7	1	5.8	ns
t_{dis}	OE	Q	1	6.3		5.4	1	5	ns

operating characteristics, T_A = 25°C

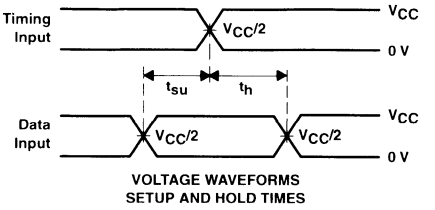
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	55	59	pF
		Outputs disabled		46	49	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

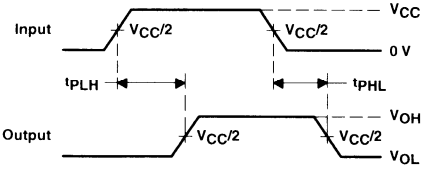


LOAD CIRCUIT

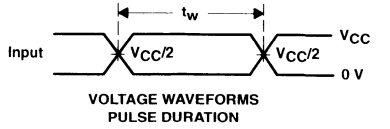
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



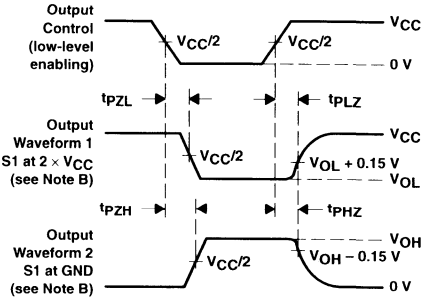
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

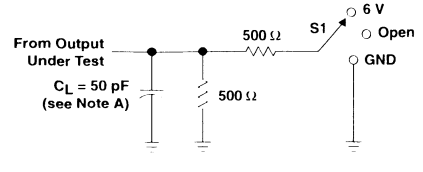


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

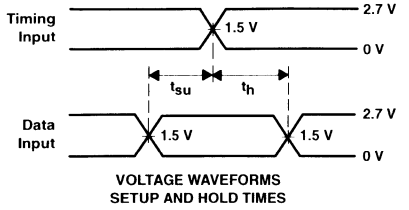
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

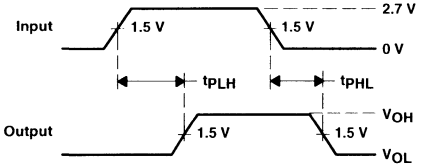


LOAD CIRCUIT

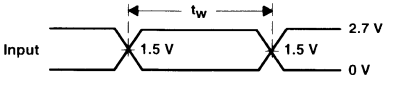
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



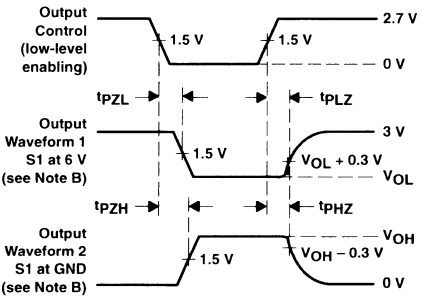
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

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F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

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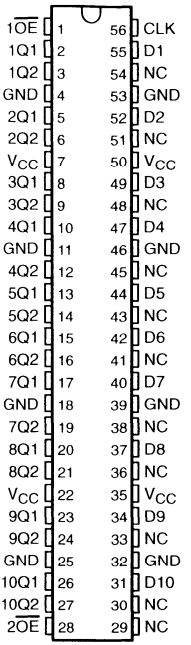
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 10-bit flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The flip-flops of the SN74ALVCH16820 are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the ten outputs in either a normal logic state (high or low logic level) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ input does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

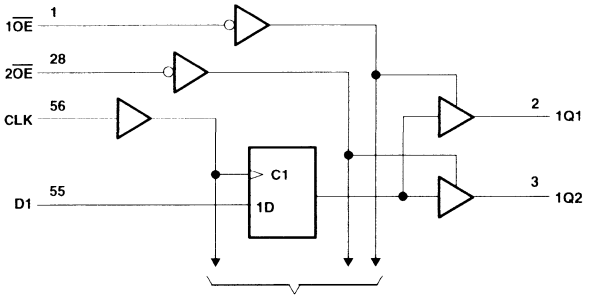
The SN74ALVCH16820 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}_n$†	CLK	D	Q_n†
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

† n = 1, 2

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.7		1.8		1.4		ns
t_h	Hold time, data after CLK↑	1.1		1.1		1		ns

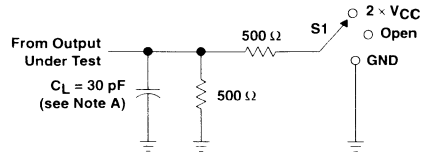
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	5.9		5.5	1	4.8	ns
t_{en}	$\overline{OE}$	Q	1	6.4		6.1	1	5	ns
t_{dis}	$\overline{OE}$	Q	1	5.7		5	1	4.5	ns

operating characteristics, T_A = 25°C

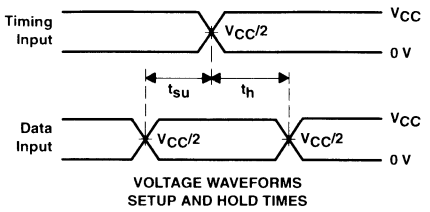
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	60	63	pF
		Outputs disabled		38	46	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

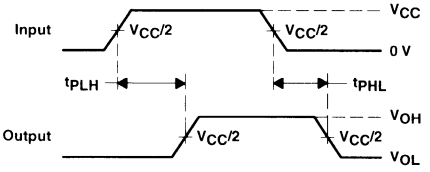


LOAD CIRCUIT

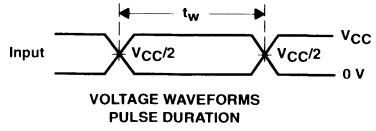
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



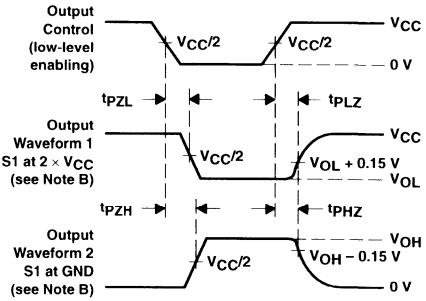
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

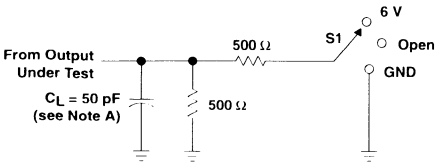


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

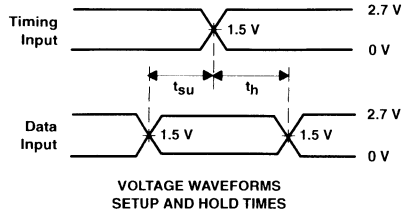
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

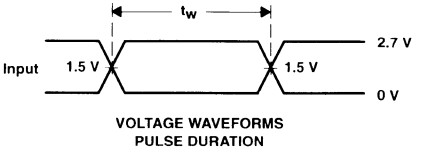


LOAD CIRCUIT

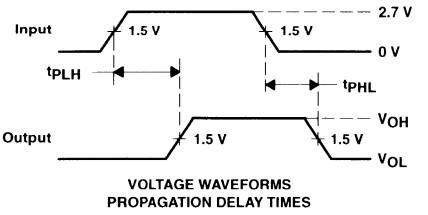
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



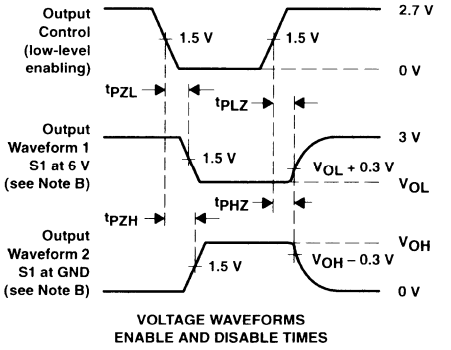
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



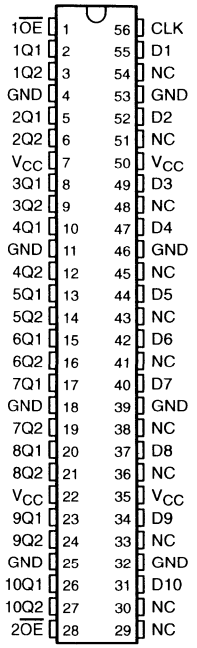
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 10-bit flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162820 flip-flops are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

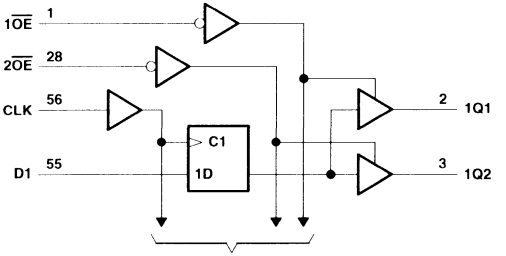
The SN74ALVCH162820 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}_n$†	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

† n = 1, 2

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output-voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.7		1.8		1.4		ns
t_h	Hold time, data after CLK↑	1.1		1.1		1		ns

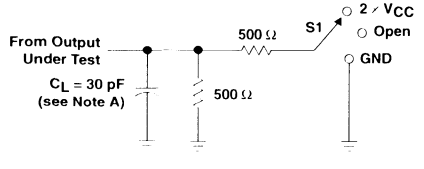
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	6.4		6.2	1	5.4	ns
t_{en}	$\overline{OE}$	Q	1	6.9		6.8	1	5.6	ns
t_{dis}	$\overline{OE}$	Q	1	6.2		5.5	1	5	ns

operating characteristics, T_A = 25°C

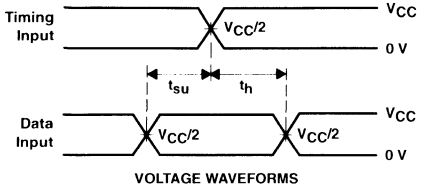
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	68	66	pF
		Outputs disabled		39	47	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

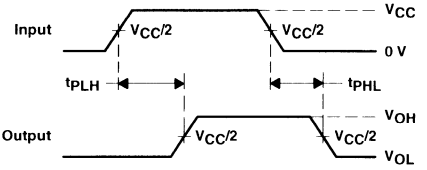


LOAD CIRCUIT

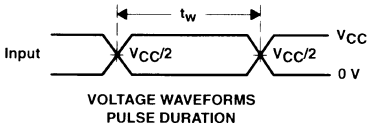
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



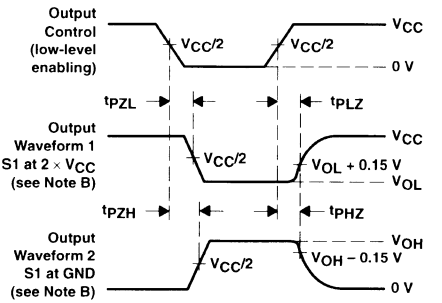
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

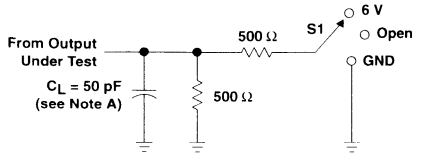


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

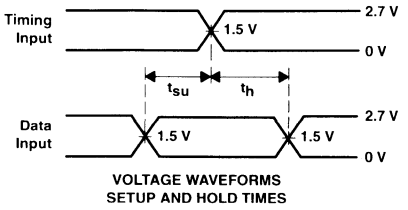
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

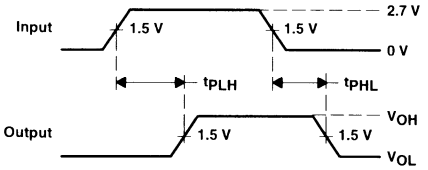


LOAD CIRCUIT

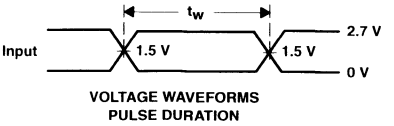
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



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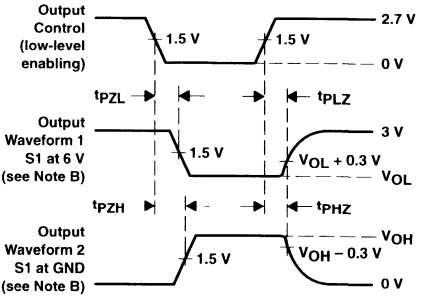
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

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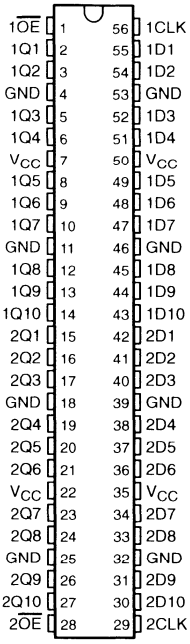
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 20-bit bus-interface flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16821 can be used as two 10-bit flip-flops or one 20-bit flip-flop. The 20 flip-flops are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the ten outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

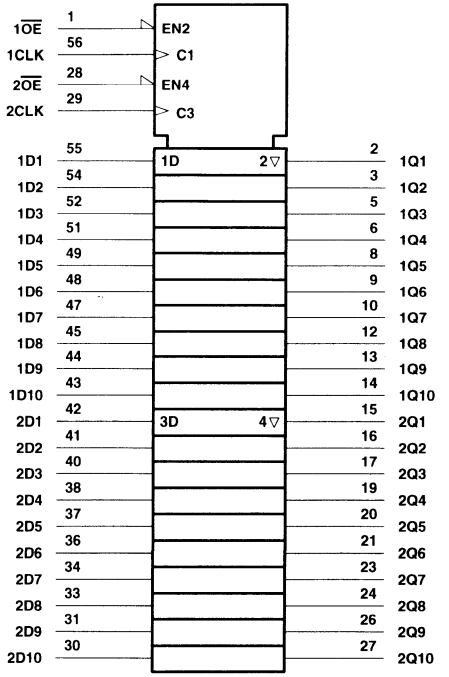
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16821 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 10-bit flip-flop)

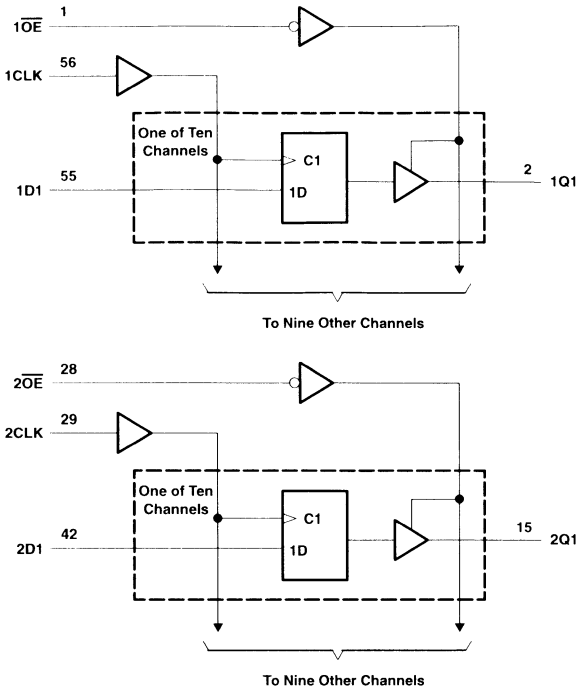
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 4.6 V
Input voltage range, V_I (see Note 1)	–0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2)	–0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0)	–50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC})	±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC})	±50 mA
Continuous current through each V_{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package	81°C/W
DL package	74°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	4.4		3.9		3.4		ns
t_h	Hold time, data after CLK↑	0		0		0		ns

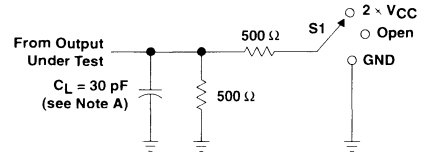
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	5.8		5.3	1	4.5	ns
t_{en}	$\overline{OE}$	Q	1	6.6		6.2	1	5.1	ns
t_{dis}	$\overline{OE}$	Q	1	5.7		5	1	4.6	ns

operating characteristics, T_A = 25°C

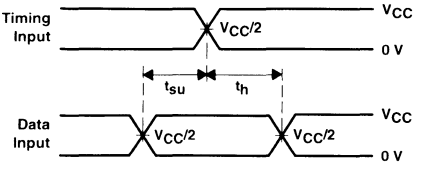
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	36	40	pF
		Outputs disabled		22	24	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

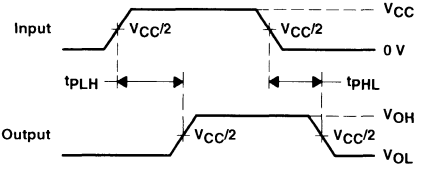


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND

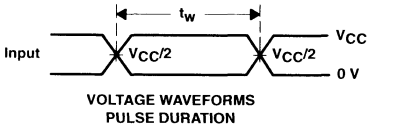
LOAD CIRCUIT



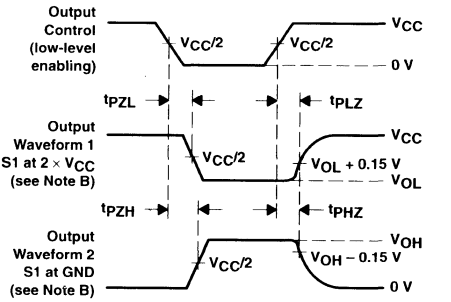
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
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C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
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Figure 1. Load Circuit and Voltage Waveforms

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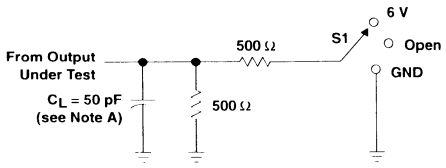
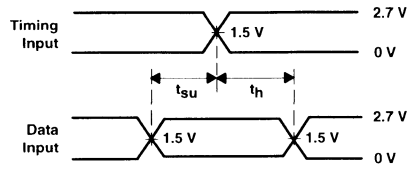
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V



LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



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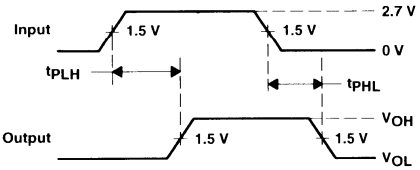
SETUP AND HOLD TIMES



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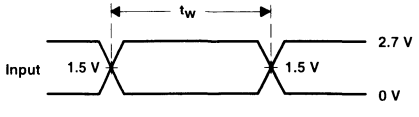

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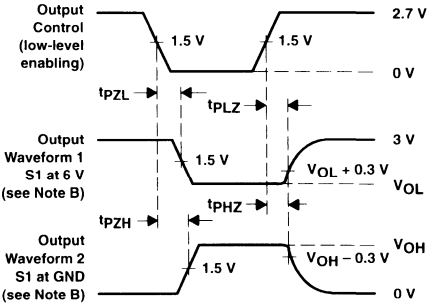

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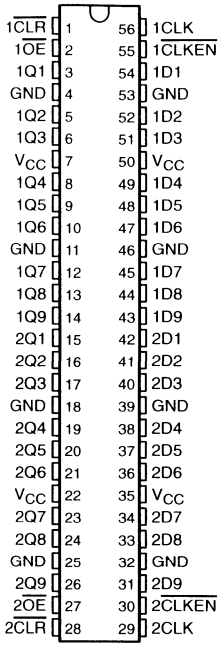


description

This 18-bit bus-interface flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16823 features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing wider buffer registers, I/O ports, bidirectional bus drivers with parity, and working registers.

The SN74ALVCH16823 can be used as two 9-bit flip-flops or one 18-bit flip-flop. With the clock-enable ($\overline{CLKEN}$) input low, the D-type flip-flops enter data on the low-to-high transitions of the clock. Taking $\overline{CLKEN}$ high disables the clock buffer, thus latching the outputs. Taking the clear ($\overline{CLR}$) input low causes the Q outputs to go low independently of the clock.

A buffered output-enable ($\overline{OE}$) input can be used to place the nine outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

The output-enable ($\overline{OE}$) input does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

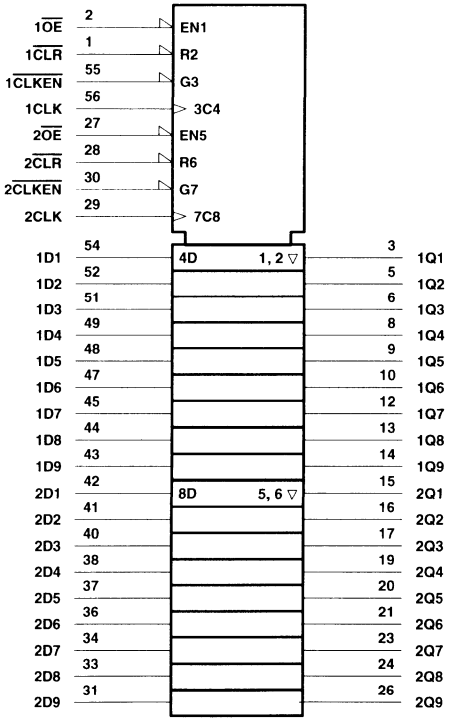
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16823 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 9-bit flip-flop)

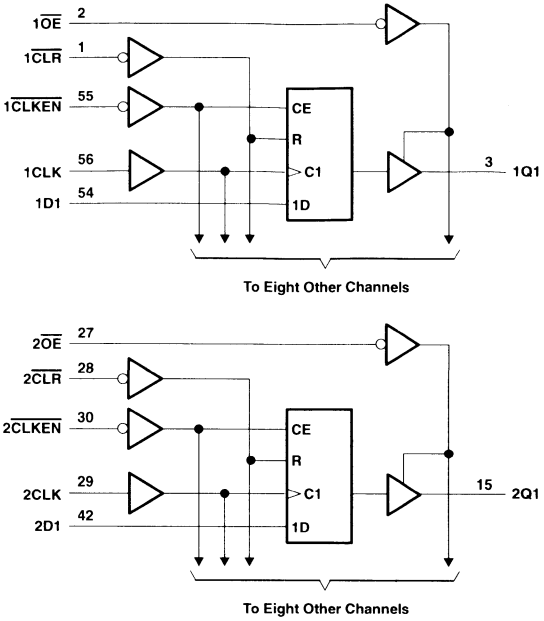
INPUTS					OUTPUT
$\overline{OE}$	$\overline{CLR}$	$\overline{CLKEN}$	CLK	D	Q
L	L	X	X	X	L
L	H	L	↑	H	H
L	H	L	↑	L	L
L	H	L	L	X	Q_0
L	H	H	X	X	Q_0
H	X	X	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 4.6 V
Input voltage range, V_I (see Note 1)	–0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2)	–0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$)	–50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)	±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC})	±50 mA
Continuous current through each V_{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package	81°C/W
DL package	74°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.5		pF
	Data inputs					6.5		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is a bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration	$\overline{CLR}$ low	3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		
t_{su}	Setup time	$\overline{CLR}$ inactive	0.7		0.7		0.8		ns
		Data low before CLK↑	1.4		1.6		1.3		
		Data high before CLK↑	1.1		1.1		1		
		$\overline{CLKEN}$ low before CLK↑	1.8		1.9		1.5		
t_h	Hold time	Data low after CLK↑	0.4		0.5		0.5		ns
		Data high after CLK↑	0.7		0.1		0.8		
		$\overline{CLKEN}$ low after CLK↑	0.2		0.3		0.4		

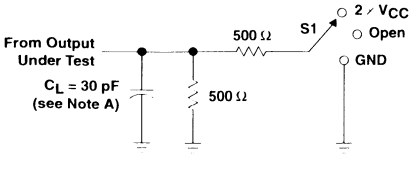
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	5.8		5.2	1	4.5	ns
	$\overline{CLR}$		1	5.4		5.2	1.2	4.6	
t_{en}	$\overline{OE}$	Q	1	6		5.7	1	4.8	ns
t_{dis}	$\overline{OE}$	Q	1.1	5.4		4.7	1.3	4.5	ns

operating characteristics, T_A = 25°C

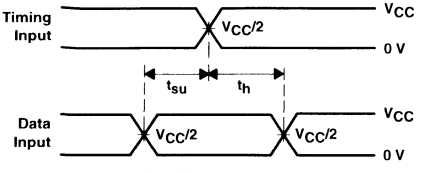
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	27	30	pF
		Outputs disabled		16	18	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

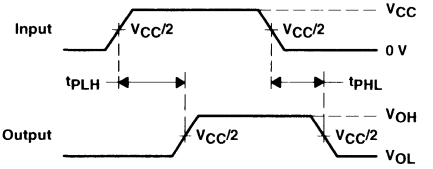


LOAD CIRCUIT

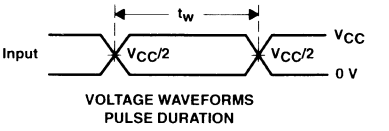
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



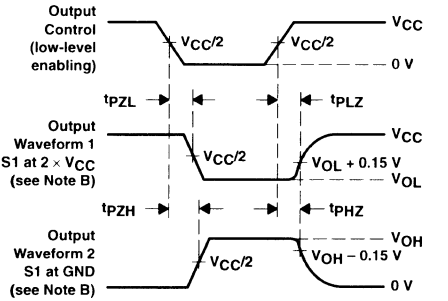
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

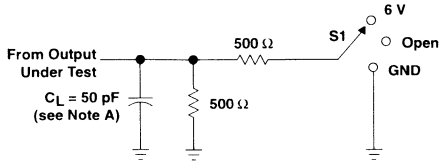


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

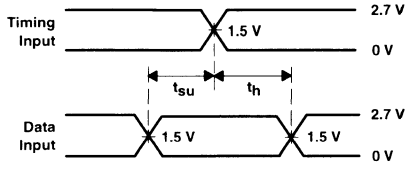
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

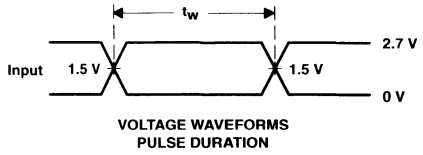


LOAD CIRCUIT

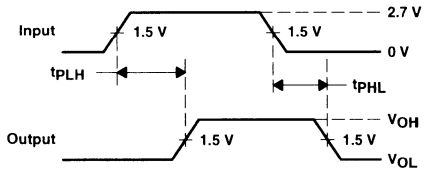
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



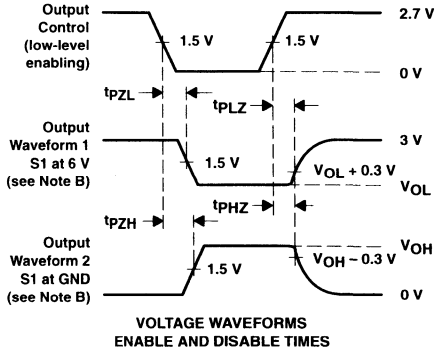
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



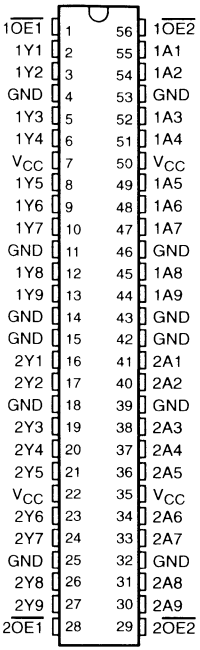
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit buffer and line driver is designed for 2.3-V to 3.6-V V_{CC} operation.

This SN74ALVCH16825 improves the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as two 9-bit buffers or one 18-bit buffer. It provides true data.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all nine affected outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

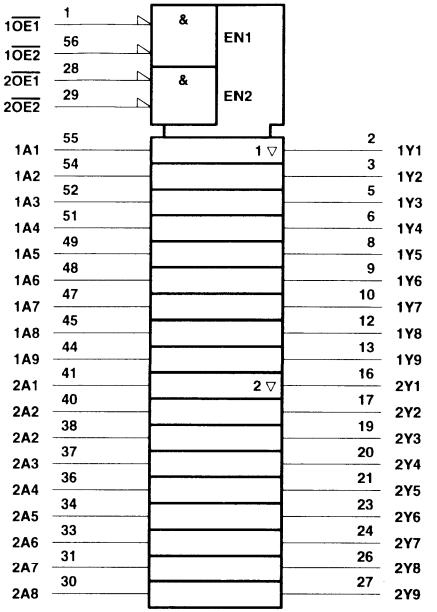
Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The SN74ALVCH16825 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 9-bit section)

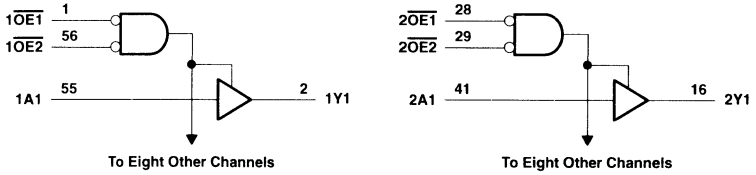
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

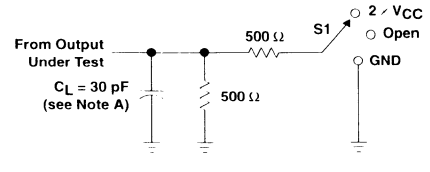
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.1		3.9	1	3.4	ns
t_{en}	$\overline{OE}$	Y	1	6		5.7	1	4.7	ns
t_{dis}	$\overline{OE}$	Y	1.2	5.6		4.9	1.3	4.5	ns

operating characteristics, T_A = 25°C

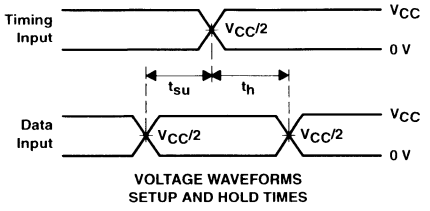
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	18	pF
		Outputs disabled		4	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

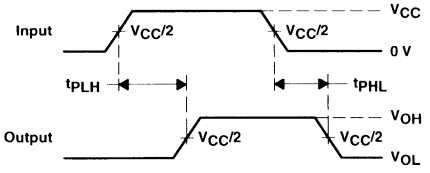


LOAD CIRCUIT

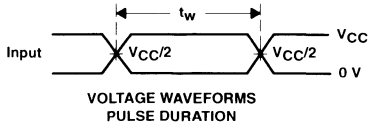
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



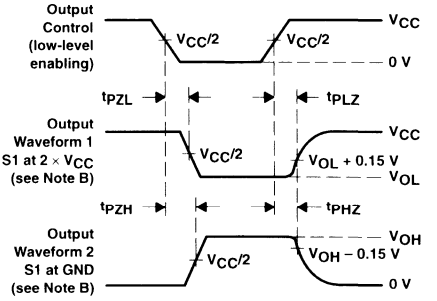
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

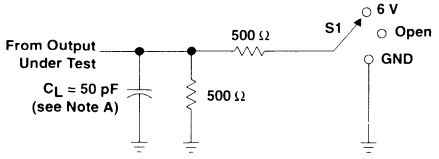


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

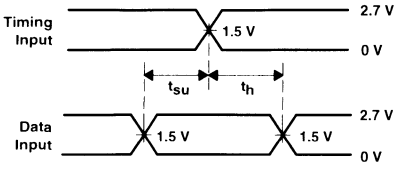
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

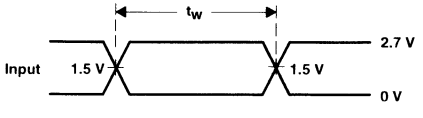


LOAD CIRCUIT

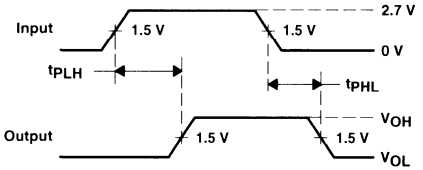
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



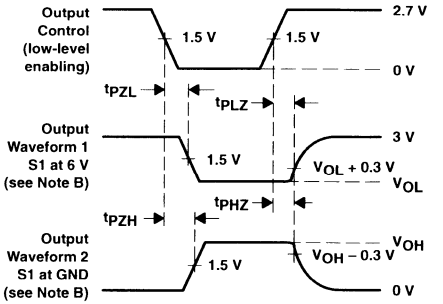
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



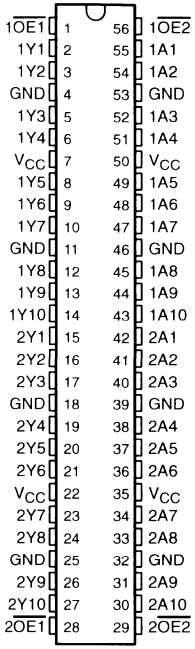
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus* ™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 20-bit noninverting buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16827 is composed of two 10-bit sections with separate output-enable signals. For either 10-bit buffer section, the two output-enable ($1\overline{OE1}$ and $1\overline{OE2}$ or $2\overline{OE1}$ and $2\overline{OE2}$) inputs must both be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 10-bit buffer section are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

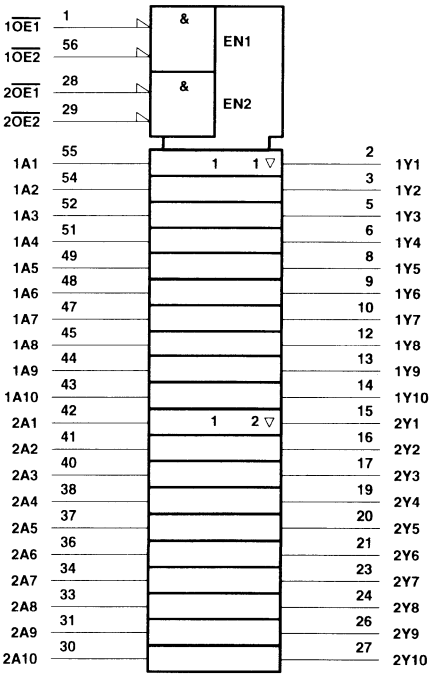
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16827 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 10-bit section)

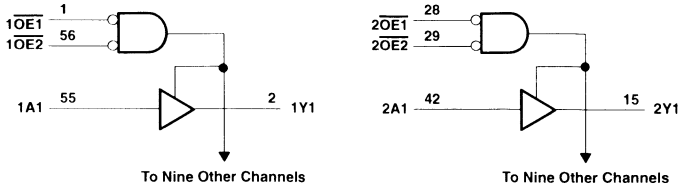
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is a bus-hold maximum dynamic current required to switch the input from one state to another.

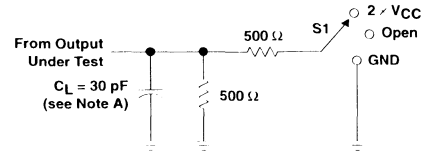
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.1		3.9	1	3.4	ns
t_{en}	$\overline{OE}$	Y	1	6		5.7	1	4.7	ns
t_{dis}	$\overline{OE}$	Y	1.2	5.6		4.9	1.3	4.5	ns

operating characteristics, T_A = 25°C

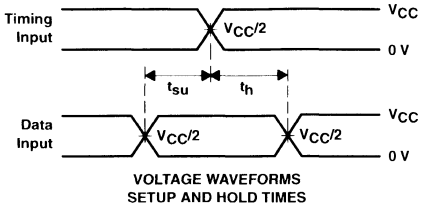
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	18	pF
		Outputs disabled		4	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

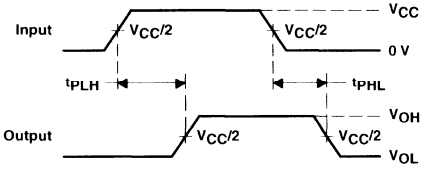


LOAD CIRCUIT

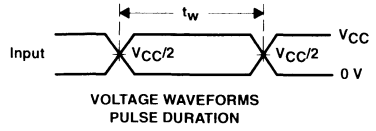
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



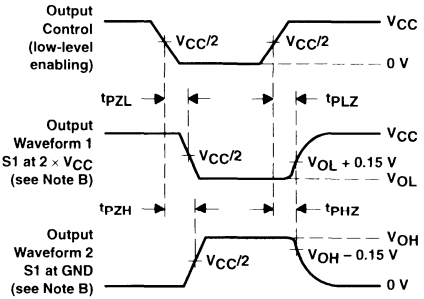
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

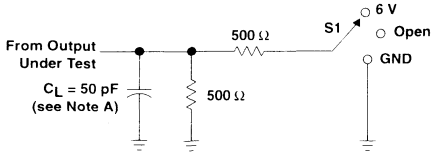


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

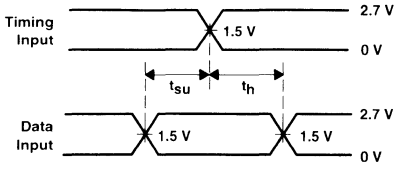
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

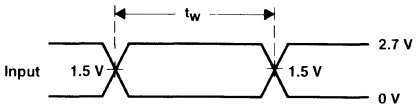


LOAD CIRCUIT

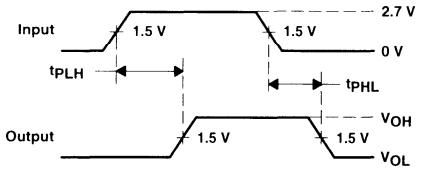
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



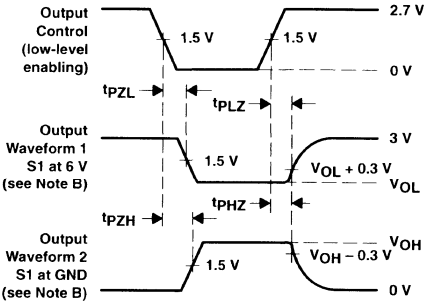
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



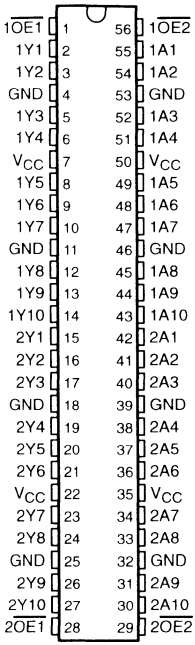
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

This 20-bit noninverting buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162827 is composed of two 10-bit sections with separate output-enable signals. For either 10-bit buffer section, the two output-enable ($1\overline{OE1}$ and $1\overline{OE2}$ or $2\overline{OE1}$ and $2\overline{OE2}$) inputs must both be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 10-bit buffer section are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

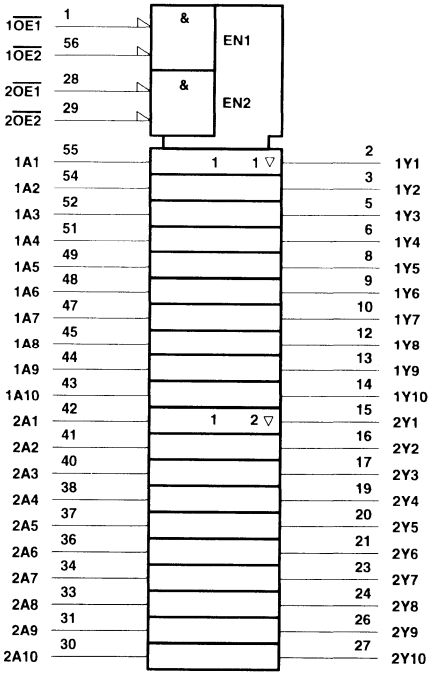
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162827 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 10-bit section)

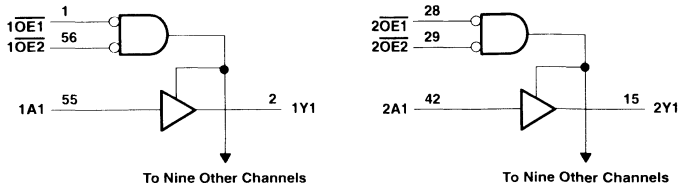
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DGV package . . . . . 86°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_I = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

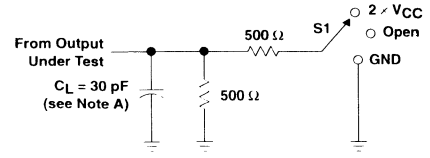
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.4		4.4	1.5	3.8	ns
t_{en}	$\overline{OE}$	Y	1.4	6.3		6.2	1.6	5.1	ns
t_{dis}	$\overline{OE}$	Y	1.7	5.9		5.2	1.8	4.7	ns

operating characteristics, T_A = 25°C

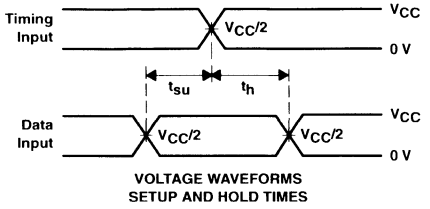
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	18	pF
		Outputs disabled		4	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

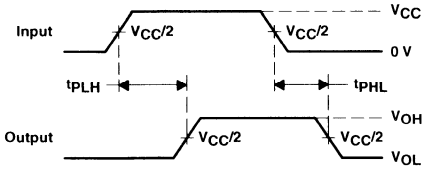


LOAD CIRCUIT

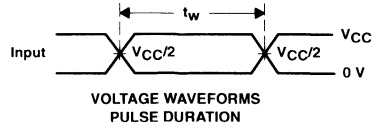
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



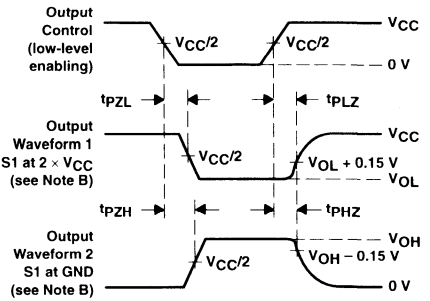
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

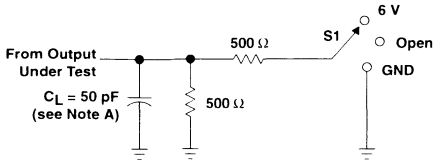


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

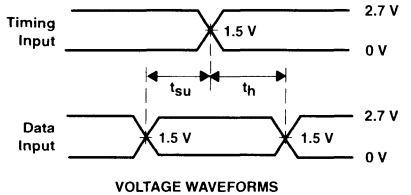
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

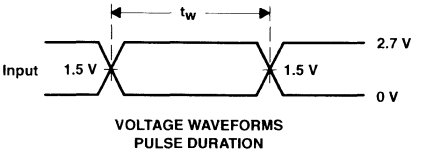


LOAD CIRCUIT

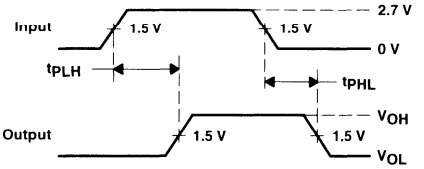
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



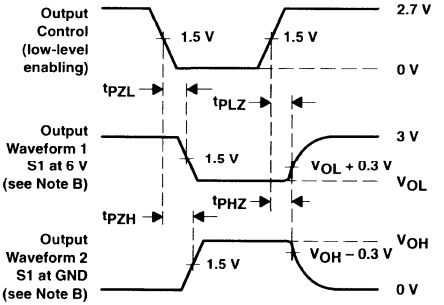
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Plastic 300-mil Thin Shrink Small-Outline Package**

description

This 1-bit to 2-bit address driver is designed for 2.3-V to 3.6-V V_{CC} operation.

Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, the output-enable ($\overline{OE}$) input should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVCH16830 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

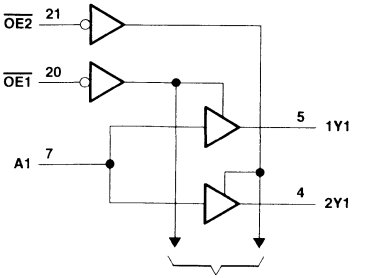
INPUTS			OUTPUTS	
$\overline{OE1}$	$\overline{OE2}$	A	1Yn	2Yn
L	H	H	H	Z
L	H	L	L	Z
H	L	H	Z	H
H	L	L	Z	L
L	L	H	H	H
L	L	L	L	L
H	H	X	Z	Z

DBB PACKAGE
(TOP VIEW)

2Y2	1	80	1Y3
1Y2	2	79	2Y3
GND	3	78	GND
2Y1	4	77	1Y4
1Y1	5	76	2Y4
V_{CC}	6	75	V_{CC}
A1	7	74	1Y5
A2	8	73	2Y5
GND	9	72	GND
A3	10	71	1Y6
A4	11	70	2Y6
GND	12	69	GND
A5	13	68	1Y7
A6	14	67	2Y7
V_{CC}	15	66	V_{CC}
A7	16	65	1Y8
A8	17	64	2Y8
GND	18	63	GND
A9	19	62	1Y9
$\overline{OE1}$	20	61	2Y9
$\overline{OE2}$	21	60	1Y10
A10	22	59	2Y10
GND	23	58	GND
A11	24	57	1Y11
A12	25	56	2Y11
V_{CC}	26	55	V_{CC}
A13	27	54	1Y12
A14	28	53	2Y12
GND	29	52	GND
A15	30	51	1Y13
A16	31	50	2Y13
GND	32	49	GND
A17	33	48	1Y14
A18	34	47	2Y14
V_{CC}	35	46	V_{CC}
2Y18	36	45	1Y15
1Y18	37	44	2Y15
GND	38	43	GND
2Y17	39	42	1Y16
1Y17	40	41	2Y16

PRODUCT PREVIEW

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 4.6 V
Input voltage range, V_I (see Note 1)	–0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2)	–0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0)	–50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC})	±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC})	±50 mA
Continuous current through each V_{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3)	106°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
	Data inputs							
C_o	Outputs	V_O= V_{CC} or GND		3.3 V				pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

PRODUCT PREVIEW

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

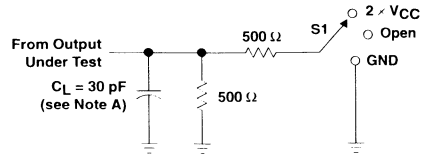
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y							ns
t_{en}	$\overline{OE}$	Y							ns
t_{dis}	$\overline{OE}$	Y							ns

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz			pF
		Outputs disabled				

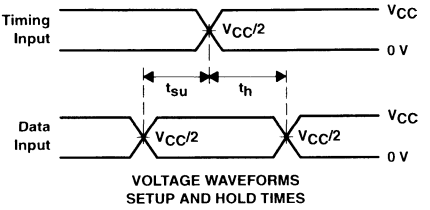
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

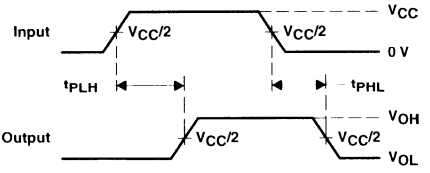


LOAD CIRCUIT

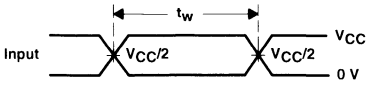
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



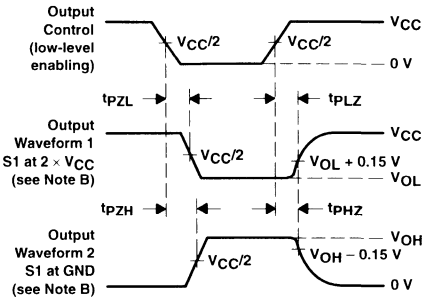
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

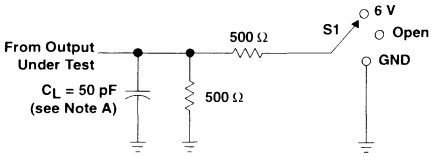


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES:
A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

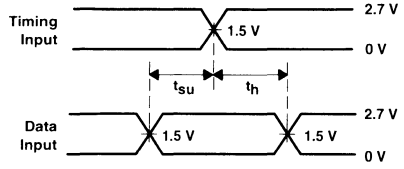
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

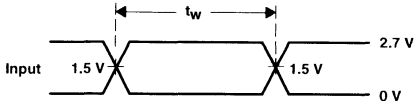


LOAD CIRCUIT

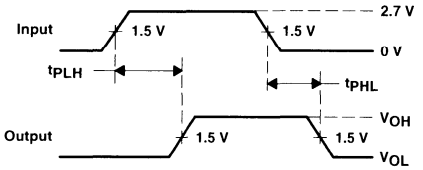
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



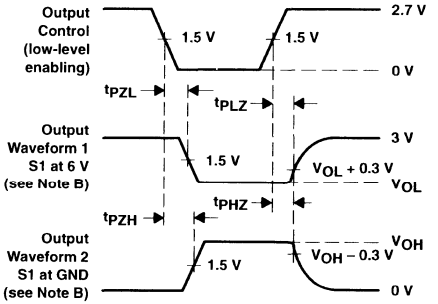
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



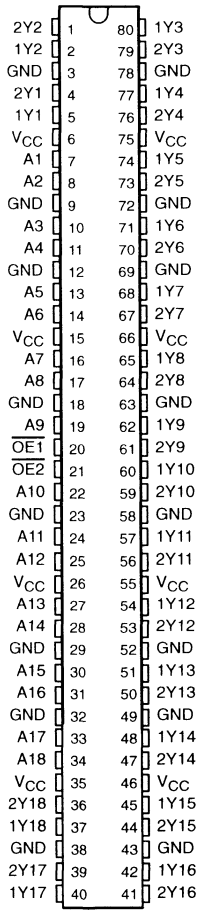
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Thin Very Small-Outline Package**

DBB PACKAGE
(TOP VIEW)



description

This 1-bit to 2-bit address driver is designed for 2.3-V to 3.6-V V_{CC} operation.

Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

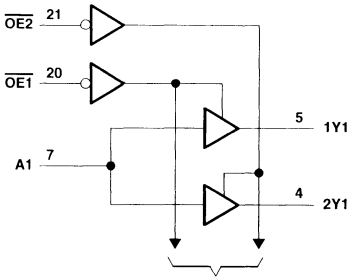
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVCH162830 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS			OUTPUTS	
$\overline{OE1}$	$\overline{OE2}$	A	1Yn	2Yn
L	H	H	H	Z
L	H	L	L	Z
H	L	H	Z	H
H	L	L	Z	L
L	L	H	H	H
L	L	L	L	L
H	H	X	Z	Z

logic diagram (positive logic)



To 17 Other Channels

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3) . . . . . 106°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.5		pF
	Data inputs					5		
C_o	Outputs	V_O= V_{CC} or GND		3.3 V		7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

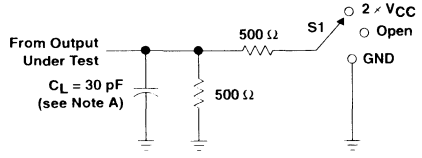
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.2	3.8		4	1.7	3.5	ns
t_{en}	$\overline{OE}$	Y	1	5.7		5.7	1	4.8	ns
t_{dis}	$\overline{OE}$	Y	1.5	6.2		5.4	1.7	5.2	ns

operating characteristics, T_A = 25°C

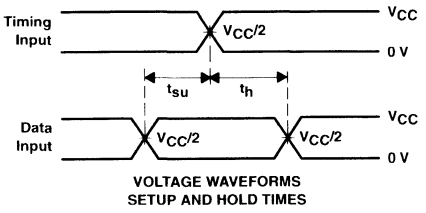
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	50	54	pF
		Outputs disabled		8	8	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

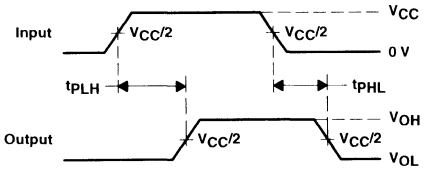


LOAD CIRCUIT

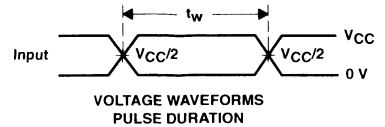
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



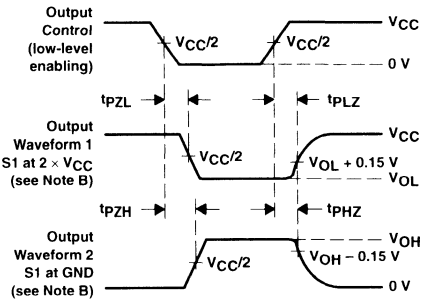
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

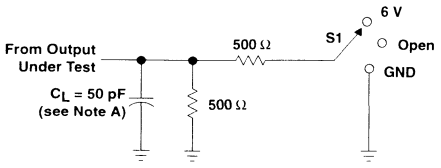


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

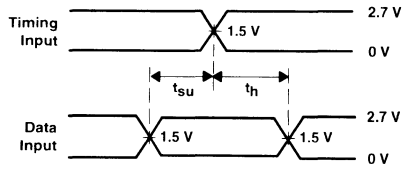
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

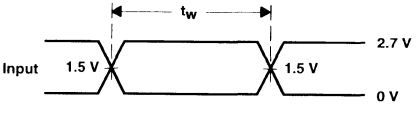


LOAD CIRCUIT

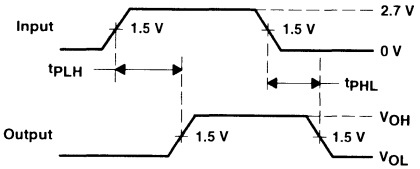
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



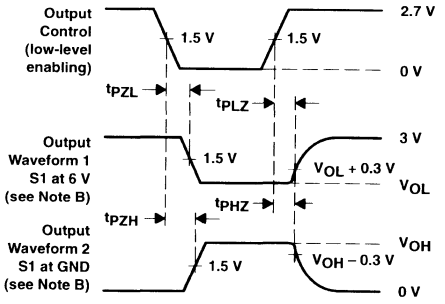
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Thin Very Small-Outline Package**

DBB PACKAGE
(TOP VIEW)

4Y1	1	80	1Y2
3Y1	2	79	2Y2
GND	3	78	GND
2Y1	4	77	3Y2
1Y1	5	76	4Y2
V_{CC}	6	75	V_{CC}
NC	7	74	1Y3
A1	8	73	2Y3
GND	9	72	GND
NC	10	71	3Y3
A2	11	70	4Y3
GND	12	69	GND
NC	13	68	1Y4
A3	14	67	2Y4
V_{CC}	15	66	V_{CC}
NC	16	65	3Y4
A4	17	64	4Y4
GND	18	63	GND
CLK	19	62	1Y5
$\overline{OE1}$	20	61	2Y5
$\overline{OE2}$	21	60	3Y5
$\overline{SEL}$	22	59	4Y5
GND	23	58	GND
A5	24	57	1Y6
A6	25	56	2Y6
V_{CC}	26	55	V_{CC}
A7	27	54	3Y6
NC	28	53	4Y6
GND	29	52	GND
A8	30	51	1Y7
NC	31	50	2Y7
GND	32	49	GND
A9	33	48	3Y7
NC	34	47	4Y7
V_{CC}	35	46	V_{CC}
4Y9	36	45	1Y8
3Y9	37	44	2Y8
GND	38	43	GND
2Y9	39	42	3Y8
1Y9	40	41	4Y8

NC – No internal connection

description

This 1-bit to 4-bit address register/driver is designed for 2.3-V to 3.6-V V_{CC} operation. The device is ideal for use in applications in which a single address bus is driving four separate memory locations. The SN74ALVCH16831 can be used as a buffer or a register, depending on the logic level of the select ($\overline{SEL}$) input.

When $\overline{SEL}$ is logic high, the device is in the buffer mode. The outputs follow the inputs and are controlled by the two output-enable ($\overline{OE}$) controls. Each $\overline{OE}$ controls two groups of nine outputs.

When $\overline{SEL}$ is logic low, the device is in the register mode. The register is an edge-triggered D-type flip-flop. On the positive transition of the clock (CLK) input, data set up at the A inputs is stored in the internal registers. $\overline{OE}$ controls operate the same as in buffer mode.

When $\overline{OE}$ is logic low, the outputs are in a normal logic state (high or low logic level). When $\overline{OE}$ is logic high, the outputs are in the high-impedance state.

$\overline{SEL}$ and $\overline{OE}$ do not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

description (continued)

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

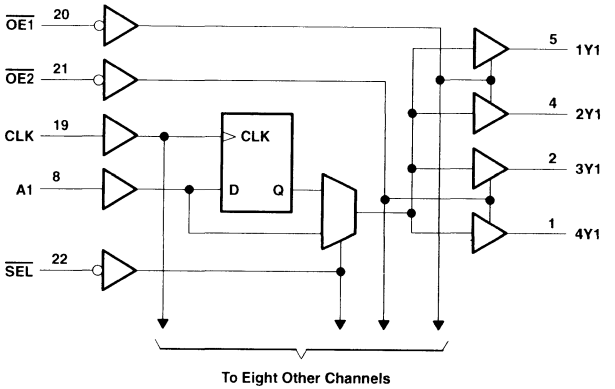
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16831 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	$\overline{SEL}$	CLK	A	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3) . . . . . 106°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.5		pF
	Data inputs					5		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, A data before CLK↑	2		2		1.6		ns
t_h	Hold time, A data after CLK↑	0.7		0.5		1.1		ns

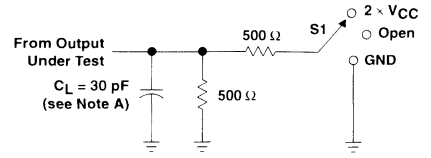
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1.2	4		4.1	1.6	3.6	ns
	CLK		1.1	4.5		4.4	1.5	3.9	
	$\overline{SEL}$		1.3	5.2		5.2	1.7	4.4	
t_{en}	$\overline{OE}$	Y	1.1	5.1		5	1.2	4.3	ns
t_{dis}	$\overline{OE}$	Y	1.4	5.5		4.7	1.6	4.5	ns

operating characteristics, T_A = 25°C

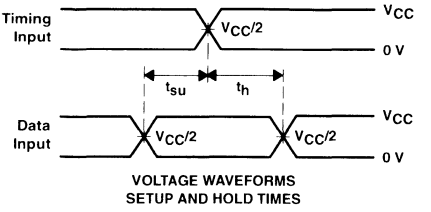
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	119	132	pF
		Outputs disabled		22	25	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

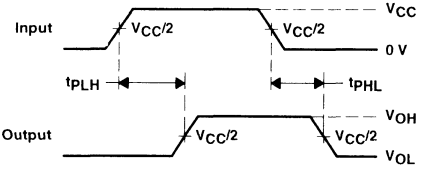


LOAD CIRCUIT

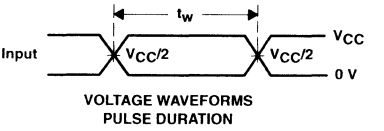
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



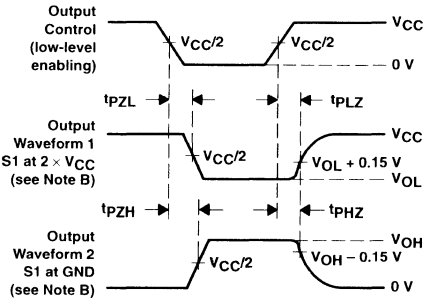
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

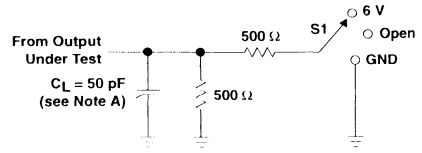


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

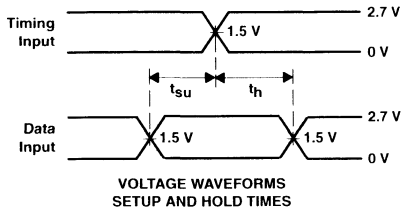
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

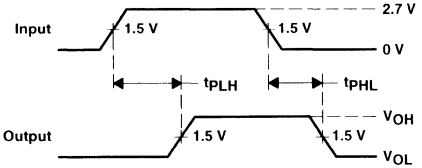


LOAD CIRCUIT

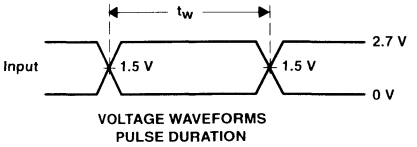
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



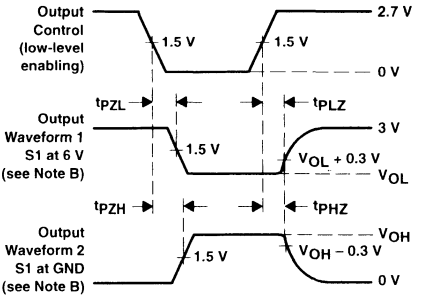
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



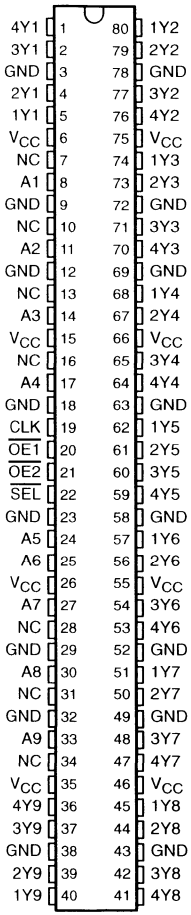
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Thin Very Small-Outline Package**

DBB PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 1-bit to 4-bit address register/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The device is ideal for use in applications in which a single address bus is driving four separate memory locations. The SN74ALVCH162831 can be used as a buffer or a register, depending on the logic level of the select ($\overline{SEL}$) input.

When $\overline{SEL}$ is logic high, the device is in the buffer mode. The outputs follow the inputs and are controlled by the two output-enable ($\overline{OE}$) controls. Each $\overline{OE}$ controls two groups of nine outputs.

When $\overline{SEL}$ is logic low, the device is in the register mode. The register is an edge-triggered D-type flip-flop. On the positive transition of the clock (CLK) input, data set up at the A inputs is stored in the internal registers. $\overline{OE}$ controls operate the same as in buffer mode.

When $\overline{OE}$ is logic low, the outputs are in a normal logic state (high or low logic level). When $\overline{OE}$ is logic high, the outputs are in the high-impedance state.

$\overline{SEL}$ and $\overline{OE}$ do not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

description (continued)

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

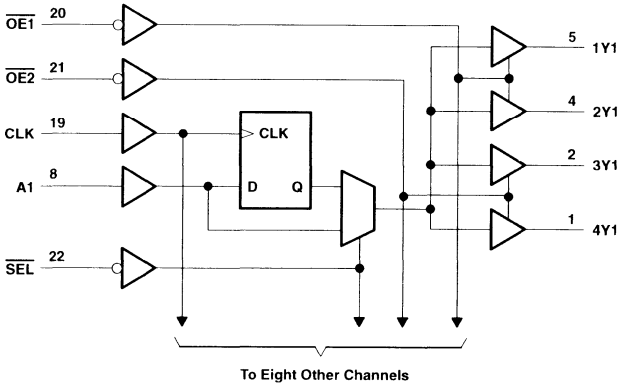
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162831 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	$\overline{SEL}$	CLK	A	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3) . . . . . 106°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.5		pF
	Data inputs					5		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, A data before CLK↑	2		2		1.6		ns
t_h	Hold time, A data after CLK↑	0.7		0.5		1.1		ns

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1.1	4.7		4.8	1.5	4.3	ns
	CLK		1	5.3		5.3	1.4	4.7	
	$\overline{SEL}$		1.1	6		6.2	1.5	4.8	
t_{en}	$\overline{OE}$	Y	1	5.9		5.9	1.1	5.1	ns
t_{dis}	$\overline{OE}$	Y	1.4	6.3		5.4	1.6	5.1	ns

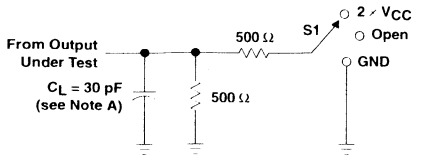
switching characteristics from 0°C to 65°C, C_L = 50 pF

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.15 V		UNIT
			MIN	MAX	
t_{pd}	CLK	Y	1.9	4.5	ns

operating characteristics, T_A = 25°C

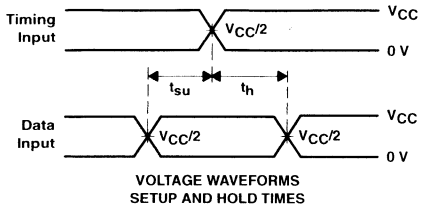
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	119	132	pF
		Outputs disabled		22	25	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

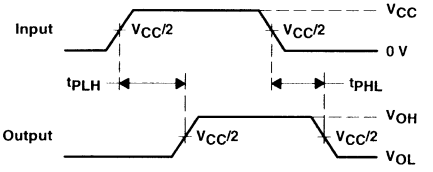


LOAD CIRCUIT

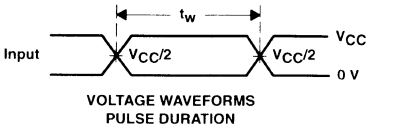
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



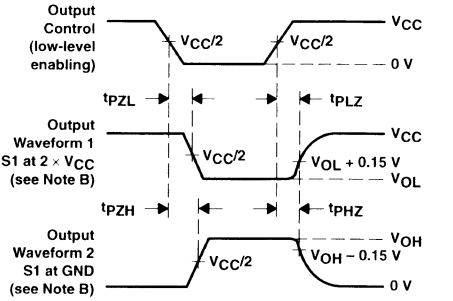
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

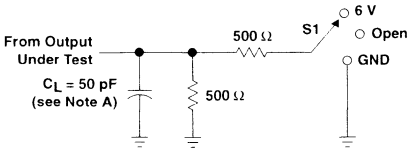


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

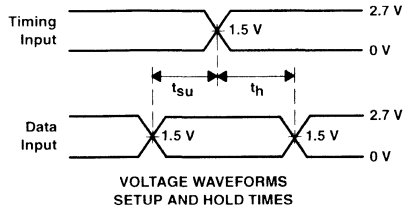
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

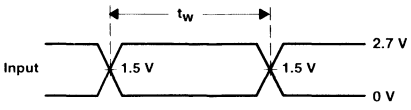


LOAD CIRCUIT

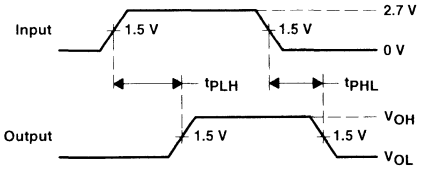
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



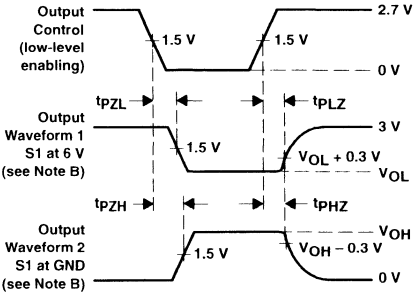
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
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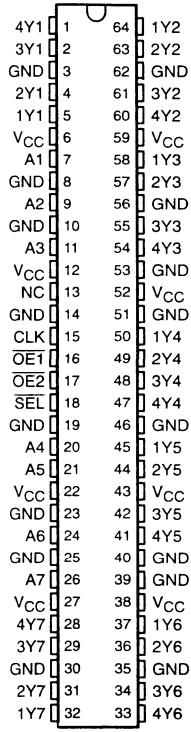
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Thin Shrink Small-Outline Package**

DGG PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 1-bit to 4-bit address register/driver is designed for 2.3-V to 3.6-V V_{CC} operation. This device is ideal for use in applications in which a single address bus is driving four separate memory locations. The SN74ALVCH16832 can be used as a buffer or a register, depending on the logic level of the select ($\overline{SEL}$) input.

When $\overline{SEL}$ is a logic high, the device is in the buffer mode. The outputs follow the inputs and are controlled by the two output-enable ($\overline{OE}$) controls. Each $\overline{OE}$ controls two groups of seven outputs.

When $\overline{SEL}$ is a logic low, the device is in the register mode. The register is an edge-triggered D-type flip-flop. On the positive transition of the clock (CLK) input, data at the A inputs is stored in the internal registers. $\overline{OE}$ controls operate the same as in the buffer mode.

When $\overline{OE}$ is a logic low, the outputs are in a normal logic state (high or low logic level). When $\overline{OE}$ is a logic high, the outputs are in the high-impedance state.

Neither $\overline{SEL}$ nor $\overline{OE}$ affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16832 is characterized for operation from –40°C to 85°C.

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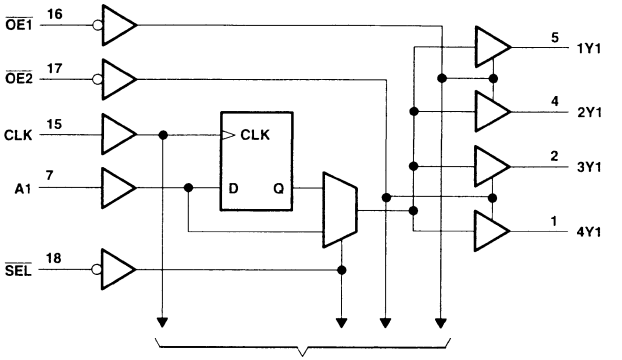
FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	$\overline{SEL}$	CLK	A	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3) ..... 73°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.5		pF
	Data inputs					5		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, A data before CLK↑	2		2		1.6		ns
t_h	Hold time, A data after CLK↑	0.7		0.5		1.1		ns

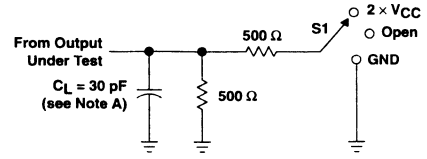
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1.2	4		4.1	1.6	3.6	ns
	CLK		1.1	4.5		4.4	1.5	3.9	
	$\overline{SEL}$		1.3	5.2		5.2	1.7	4.4	
t_{en}	$\overline{OE}$	Y	1.1	5.1		5	1.2	4.3	ns
t_{dis}	$\overline{OE}$	Y	1.4	5.5		4.7	1.6	4.5	ns

operating characteristics, T_A = 25°C

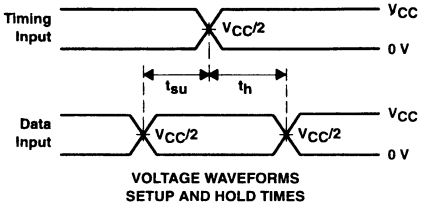
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	119	132	pF
		Outputs disabled		22	25	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

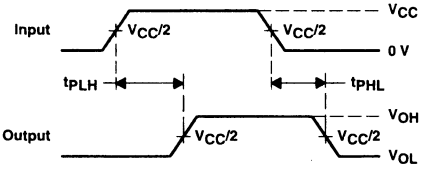


LOAD CIRCUIT

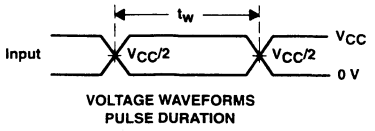
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



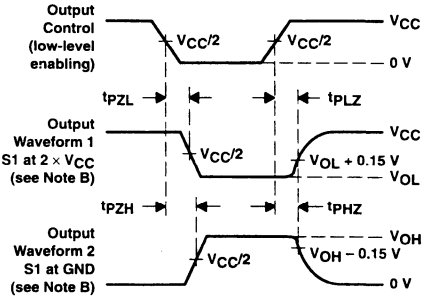
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

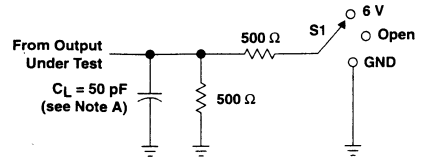


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

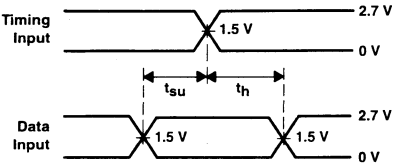
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

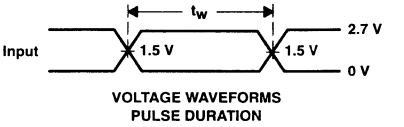


LOAD CIRCUIT

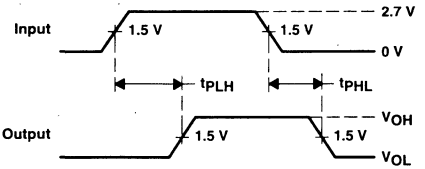
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



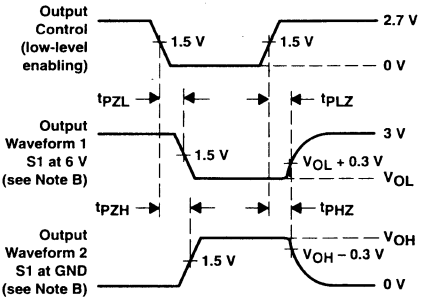
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

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Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
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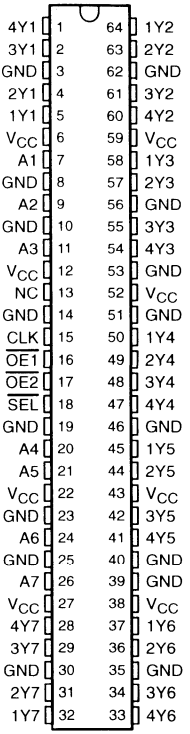
DGG PACKAGE
(TOP VIEW)



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description

This 1-bit to 4-bit address register/driver is designed for 2.3-V to 3.6-V V_{CC} operation. This device is ideal for use in applications in which a single address bus is driving four separate memory locations. The SN74ALVCH162832 can be used as a buffer or a register, depending on the logic level of the select ($\overline{SEL}$) input.

When $\overline{SEL}$ is a logic high, the device is in the buffer mode. The outputs follow the inputs and are controlled by the two output-enable ($\overline{OE}$) controls. Each $\overline{OE}$ controls two groups of seven outputs.

When $\overline{SEL}$ is a logic low, the device is in the register mode. The register is an edge-triggered D-type flip-flop. On the positive transition of the clock (CLK) input, data at the A inputs is stored in the internal registers. $\overline{OE}$ controls operate the same as in the buffer mode.

When $\overline{OE}$ is a logic low, the outputs are in a normal logic state (high or low logic level). When $\overline{OE}$ is a logic high, the outputs are in the high-impedance state.

Neither $\overline{SEL}$ nor $\overline{OE}$ affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

description (continued)

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

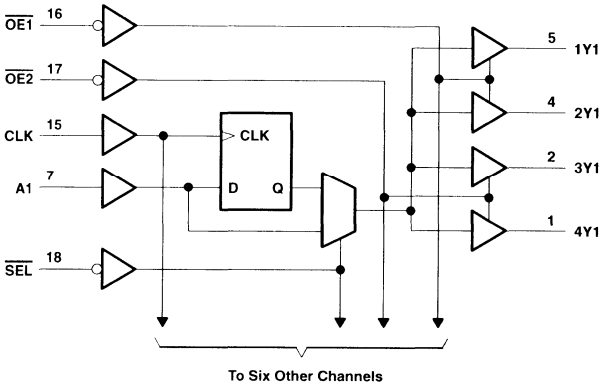
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162832 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	$\overline{SEL}$	CLK	A	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3) . . . . . 73°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA,		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.5		pF
	Data inputs					5		
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, A data before CLK↑	2		2		1.6		ns
t_h	Hold time, A data after CLK↑	0.7		0.5		1.1		ns

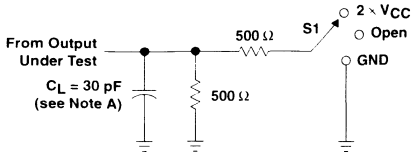
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1.1	4.7		4.8	1.5	4.3	ns
	CLK		1	5.3		5.3	1.4	4.7	
	$\overline{SEL}$		1.1	6		6.2	1.5	4.8	
t_{en}	$\overline{OE}$	Y	1	5.9		5.9	1.1	5.1	ns
t_{dis}	$\overline{OE}$	Y	1.4	6.3		5.4	1.6	5.1	ns

operating characteristics, T_A = 25°C

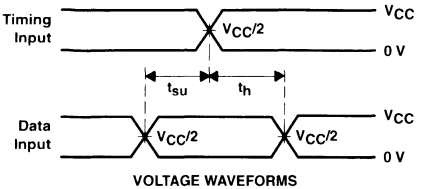
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	119	132	pF
		Outputs disabled		22	25	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

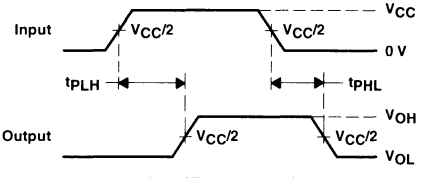


LOAD CIRCUIT

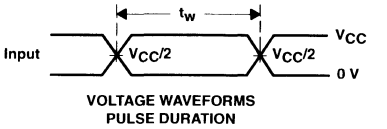
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



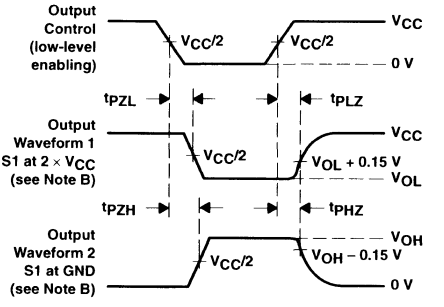
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

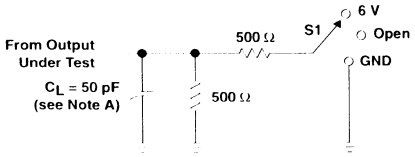


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

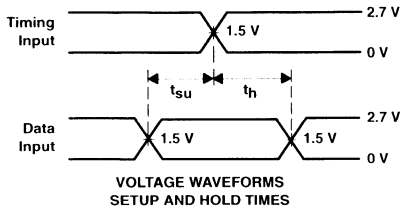
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

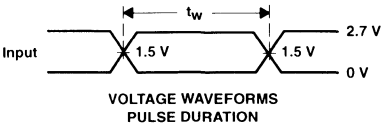


LOAD CIRCUIT

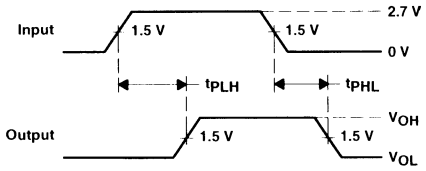
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



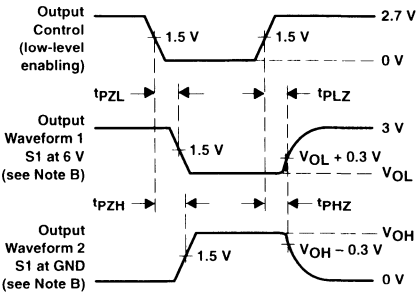
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



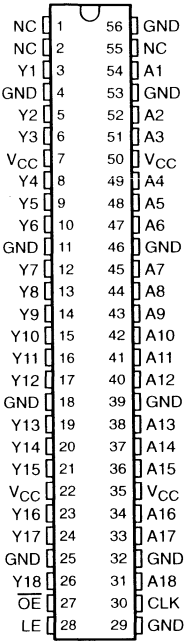
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 18-bit universal bus driver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow from A to Y is controlled by the output-enable ($\overline{OE}$). The device operates in the transparent mode when the latch-enable (LE) input is high. The A data is latched if the clock (CLK) input is held at a high or low logic level. If LE is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

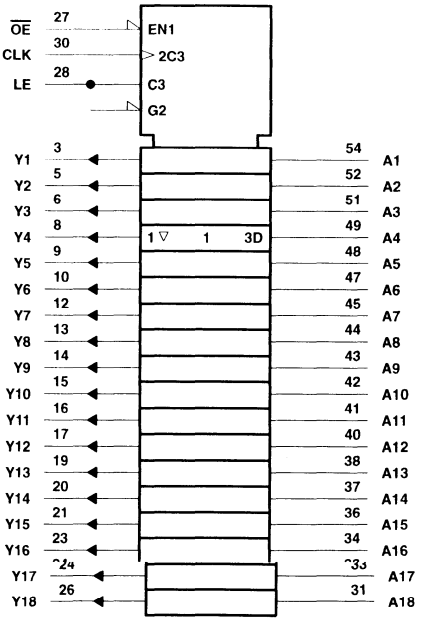
The SN74ALVCH16835 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	LE	CLK	A	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H
L	L	H	X	Y_0†
L	L	L	X	Y_0‡

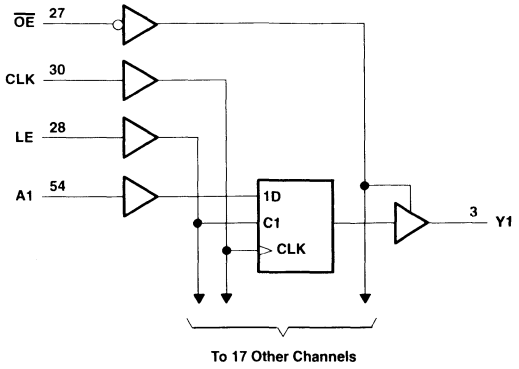
† Output level before the indicated steady-state input conditions were established, provided that CLK is high before LE goes low
‡ Output level before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DGV package ..... 86°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	150	0	150	0	150	MHz
t_w	Pulse duration	LE high		3.3		3.3		3.3		ns
		CLK high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑		2.2		2.1		1.7		ns
		Data before LE↓	CLK high	1.9		1.6		1.5		
			CLK low	1.3		1.1		1		
t_h	Hold time	Data after CLK↑		0.6		0.6		0.7		ns
		Data after LE↓	CLK high or low	1.4		1.7		1.4		

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1	4.2		4.2	1	3.6	ns
	LE		1.3	5		4.9	1.3	4.2	
	CLK		1.4	5.5		5.2	1.4	4.5	
t_{en}	$\overline{OE}$	Y	1.4	5.5		5.6	1.1	4.6	ns
t_{dis}	$\overline{OE}$	Y	1	4.5		4.3	1.3	3.9	ns

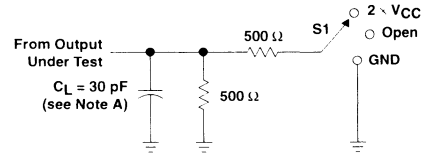
switching characteristics from 0°C to 65°C, C_L = 50 pF

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.15 V		UNIT
			MIN	MAX	
t_{pd}	CLK	Y	1.7	4.5	ns

operating characteristics, T_A = 25°C

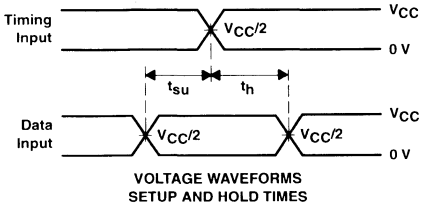
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	26	31	pF
		Outputs disabled		12	14	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

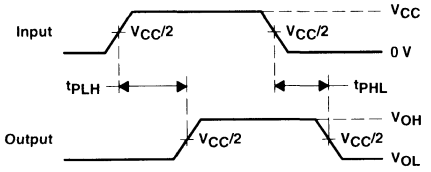


LOAD CIRCUIT

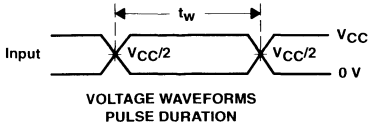
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



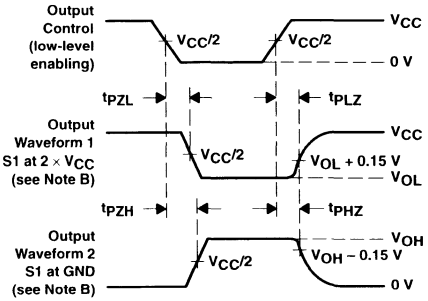
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

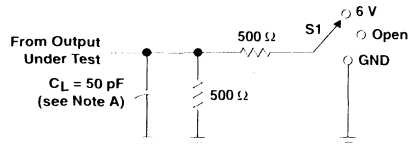


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

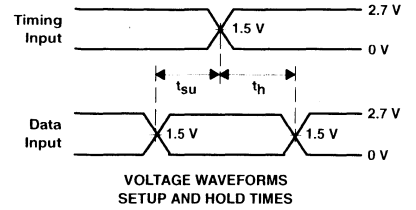
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

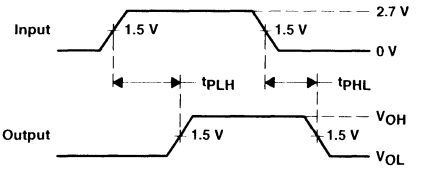


LOAD CIRCUIT

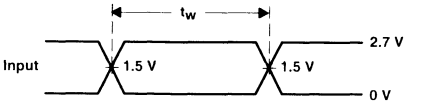
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



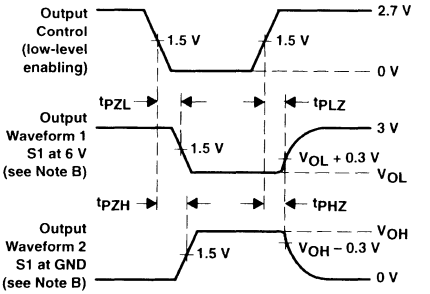
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



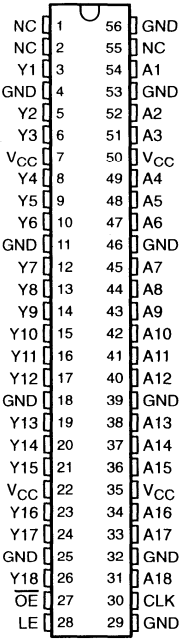
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Port Has Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 18-bit universal bus driver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow from A to Y is controlled by the output-enable ($\overline{OE}$). The device operates in the transparent mode when the latch-enable (LE) input is high. When LE is low, the A data is latched if the clock (CLK) input is held at a high or low logic level. If LE is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The output port includes equivalent 26-Ω series resistors to reduce overshoot and undershoot.

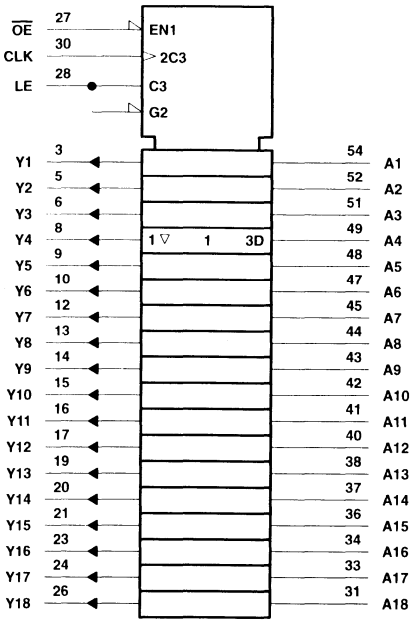
The SN74ALVCH162835 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	LE	CLK	A	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H
L	L	L or H	X	Y_0†

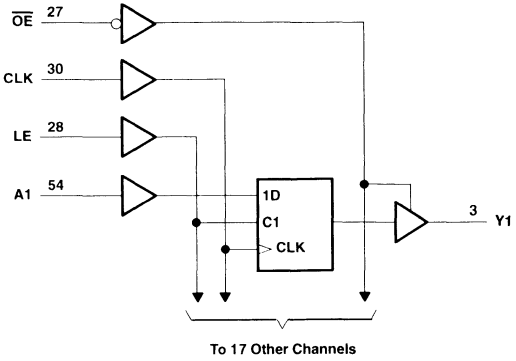
† Output level before the indicated steady-state input conditions were established

logic symbol‡



‡ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DGV package . . . . . 86°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency				150		150		150	MHz
t_w	Pulse duration	LE high		3.3		3.3		3.3		ns
		CLK high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑		2.2		2.1		1.7		ns
		Data before LE↓	CLK high	1.9		1.6		1.5		
			CLK low	1.3		1.1		1		
t_h	Hold time	Data after CLK↑		0.6		0.6		0.7		ns
		Data after LE↓	CLK high or low	1.4		1.7		1.4		

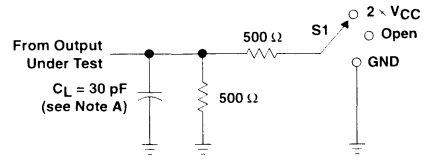
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1	5		5	1	4.2	ns
	LE		1.3	5.9		5.8	1.3	5.1	
	CLK		1.4	6.3		6.1	1.4	5.4	
t_{en}	$\overline{OE}$	Y	1.4	6.3		6.5	1.1	5.5	ns
t_{dis}	$\overline{OE}$	Y	1	4.7		4.9	1.3	4.5	ns

operating characteristics, T_A = 25°C

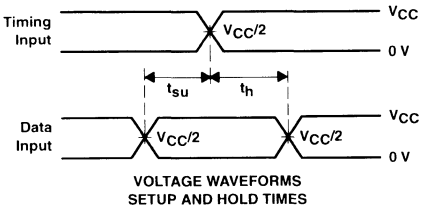
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	36	41	pF
		Outputs disabled		12.5	14	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

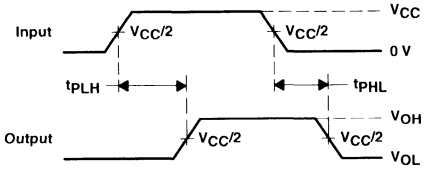


LOAD CIRCUIT

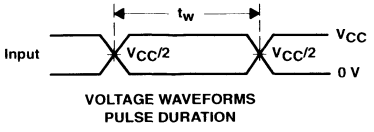
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



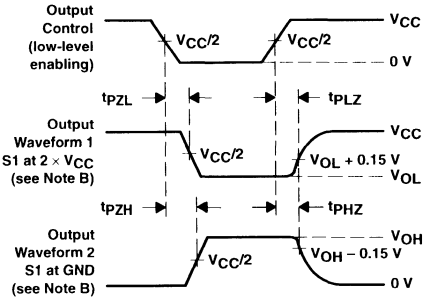
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

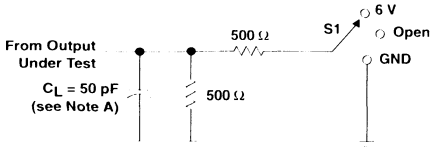


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

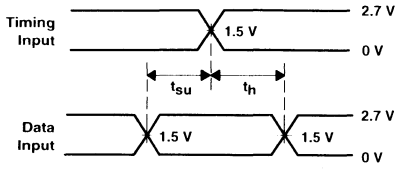
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

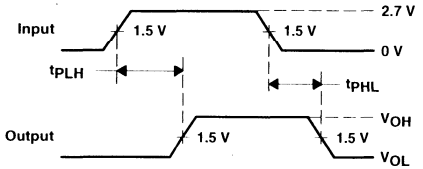


LOAD CIRCUIT

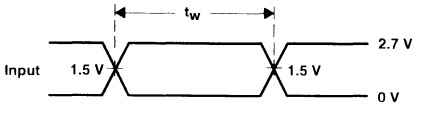
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



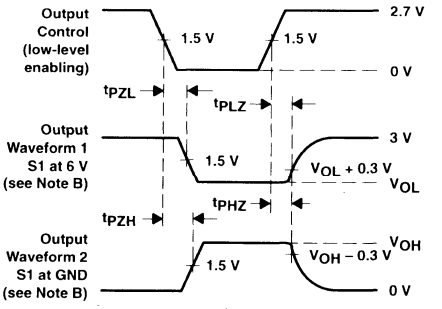
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



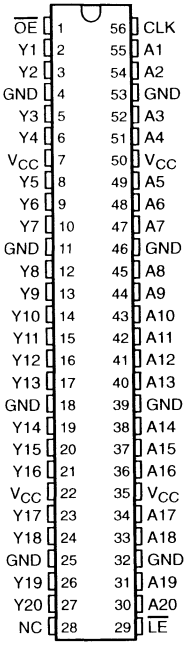
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Designed to Comply With JEDEC 168-Pin and 200-Pin SDRAM Buffered DIMM Specification**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 20-bit universal bus driver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow from A to Y is controlled by the output-enable ($\overline{OE}$) input. The device operates in the transparent mode when the latch-enable ($\overline{LE}$) input is low. The A data is latched if the clock (CLK) input is held at a high or low logic level. If $\overline{LE}$ is high, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16836 is characterized for operation from –40°C to 85°C.

PRODUCT PREVIEW

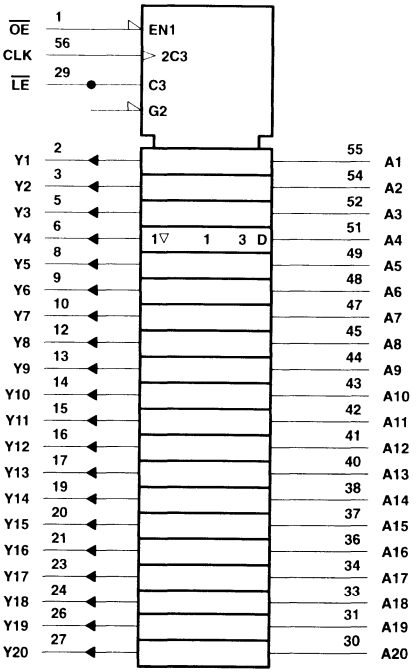
FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	$\overline{LE}$	CLK	A	Y
H	X	X	X	Z
L	L	X	L	L
L	L	X	H	H
L	H	↑	L	L
L	H	↑	H	H
L	H	H	X	Y_0†
L	H	L	X	Y_0‡

† Output level before the indicated steady-state input conditions were established, provided that CLK is high before $\overline{LE}$ goes low

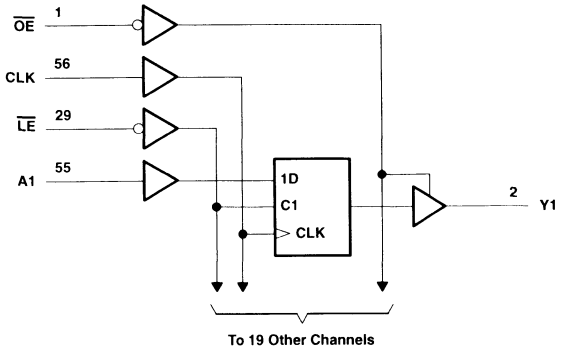
‡ Output level before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
	I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
		V_{IH} = 2 V	2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
	I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
	I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
		V_{IL} = 0.8 V	2.7 V			0.4	
	I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I	V_I = V_{CC} or GND		3.6 V			±5	µA
I_{hold}	V_I = 0.7 V		2.3 V	45			µA
	V_I = 1.7 V			–45			
	V_I = 0.8 V		3 V	75			
	V_I = 2 V			–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND	3.3 V				pF
	Data inputs						
C_o	Outputs	V_O = V_{CC} or GND	3.3 V				pF

† All typical values are at V_{CC} = 3.3 V.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency									MHz
t_w	Pulse duration	$\overline{LE}$ low								ns
		CLK high or low								
t_{su}	Setup time	Data before CLK↑								ns
		Data before $\overline{LE}$↑	CLK high							
			CLK low							
t_h	Hold time	Data after CLK↑								ns
		Data after $\overline{LE}$↑	CLK high or low							

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

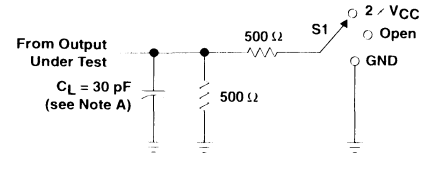
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}									MHz
t_{pd}	A	Y							ns
	$\overline{LE}$								
	CLK								
t_{en}	$\overline{OE}$	Y							ns
t_{dis}	$\overline{OE}$	Y							ns

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz			pF
		Outputs disabled				

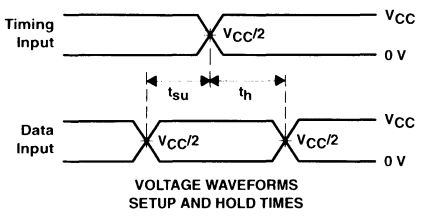
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

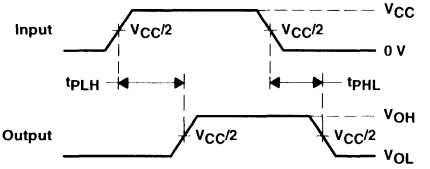


LOAD CIRCUIT

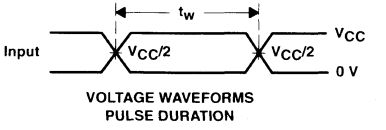
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



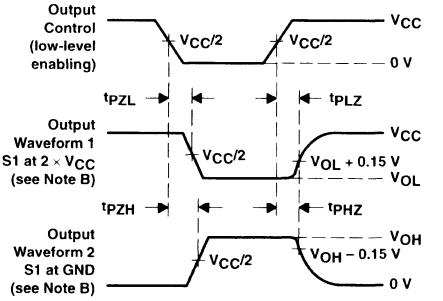
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

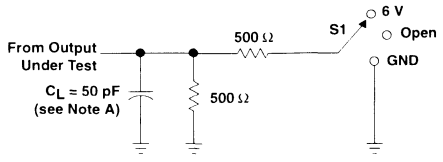


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

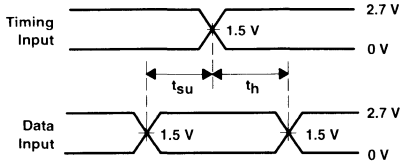
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

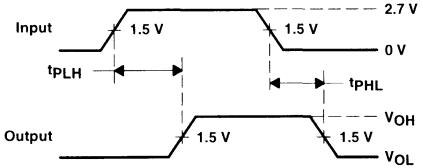


LOAD CIRCUIT

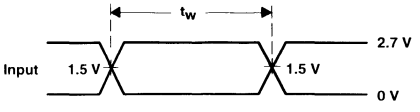
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



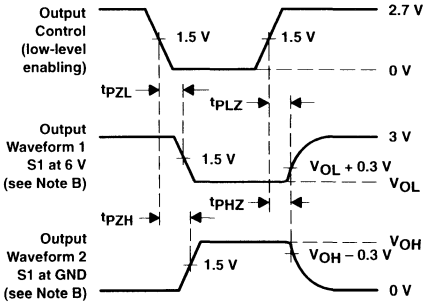
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



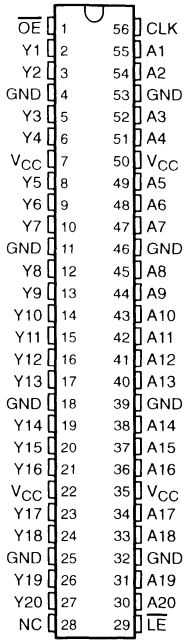
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Port Has Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **Designed to Comply With JEDEC 168-Pin and 200-Pin SDRAM Buffered DIMM Specification**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 20-bit universal bus driver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow from A to Y is controlled by the output-enable ($\overline{OE}$) input. The device operates in the transparent mode when the latch-enable ($\overline{LE}$) input is low. When $\overline{LE}$ is high, the A data is latched if the clock (CLK) input is held at a high or low logic level. If $\overline{LE}$ is high, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The output port includes equivalent 26-Ω series resistors to reduce overshoot and undershoot.

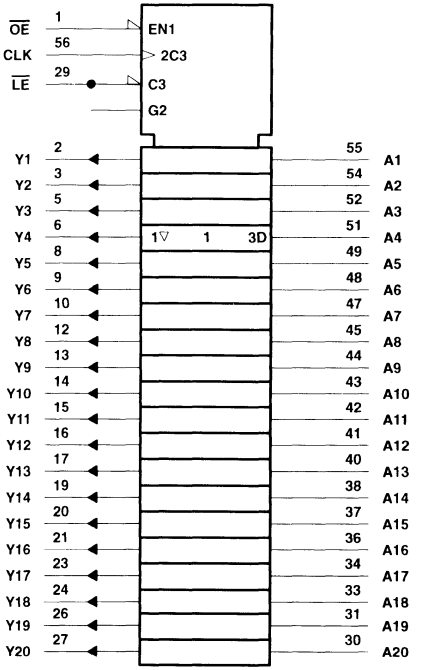
The SN74ALVCH162836 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	$\overline{LE}$	CLK	A	Y
H	X	X	X	Z
L	L	X	L	L
L	L	X	H	H
L	H	↑	L	L
L	H	↑	H	H
L	H	L or H	X	Y_0†

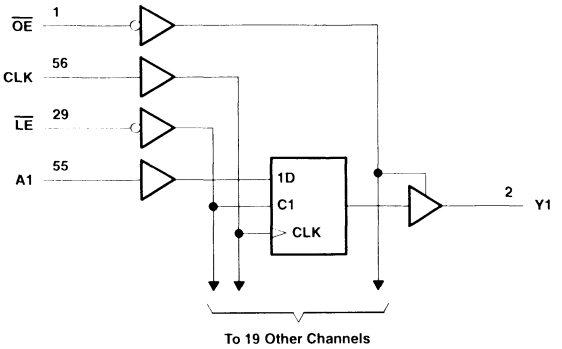
† Output level before the indicated steady-state input conditions were established

logic symbol‡



‡ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DGV package . . . . . 86°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–6	mA
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency				150		150		150	MHz
t_w	Pulse duration	$\overline{LE}$ low		3.3		3.3		3.3		ns
		CLK high or low		3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑		1.4		1.7		1.5		ns
		Data before $\overline{LE}$↑	CLK high	1.2		1.6		1.3		
			CLK low	1.4		1.5		1.2		
t_h	Hold time	Data after CLK↑		0.9		0.9		0.9		ns
		Data after $\overline{LE}$↑	CLK high or low	1.1		1.1		1.1		

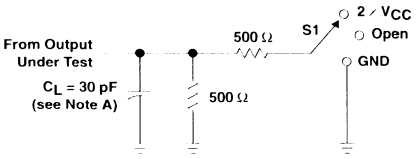
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1	3.8		4.6	1.2	4	ns
	$\overline{LE}$		1.1	4.9		6.1	1.4	5.1	
	CLK		1	4.5		5.5	1.1	5	
t_{en}	$\overline{OE}$	Y	1.1	5.5		6.5	1.2	5.5	ns
t_{dis}	$\overline{OE}$	Y	1	4.2		5.2	1.7	5.1	ns

operating characteristics, T_A = 25°C

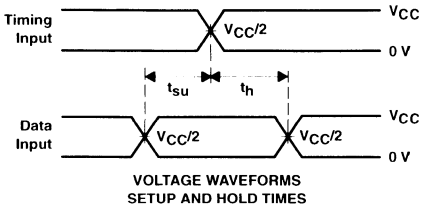
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	31.5	36	pF
		Outputs disabled		8	10.5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

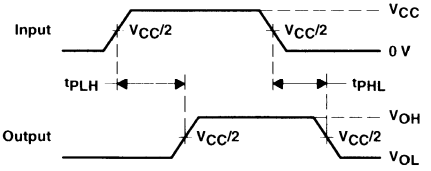


LOAD CIRCUIT

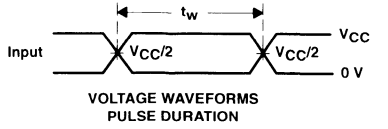
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



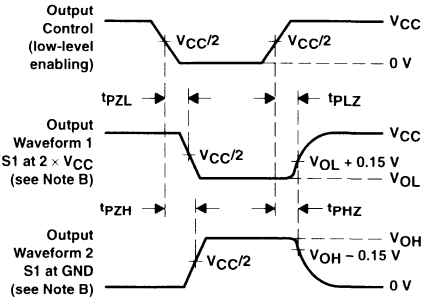
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

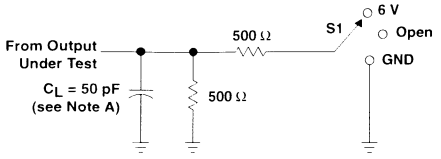


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

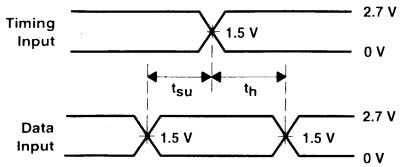
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

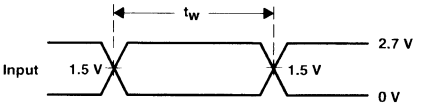


LOAD CIRCUIT

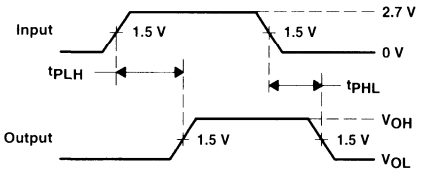
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



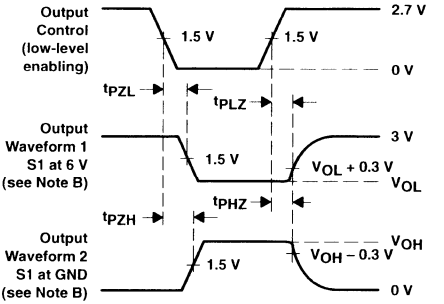
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



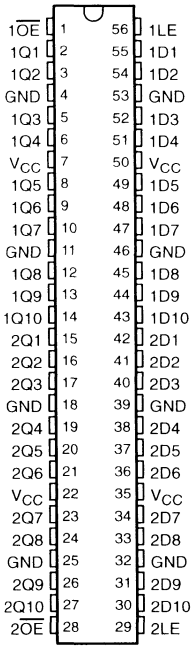
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 20-bit bus-interface D-type latch is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16841 features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, unidirectional bus drivers, and working registers.

The SN74ALVCH16841 can be used as two 10-bit latches or one 20-bit latch. The 20 latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs. While the latch-enable (1LE or 2LE) input is high, the Q outputs of the corresponding 10-bit latch follow the D inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ($1\overline{OE}$ or $2\overline{OE}$) input can be used to place the outputs of the corresponding 10-bit latch in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly.

$\overline{OE}$ does not affect the internal operation of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

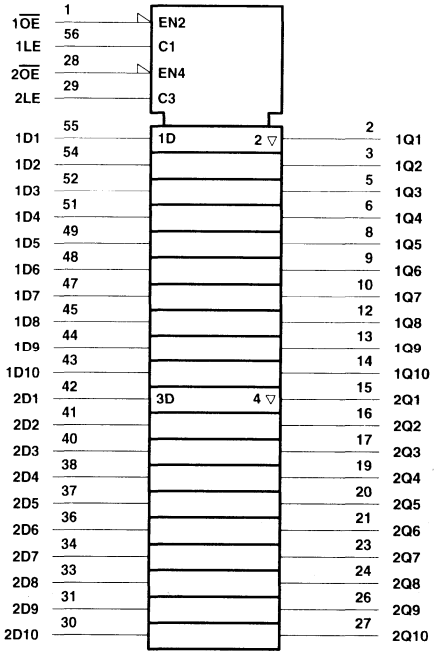
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16841 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 10-bit latch)

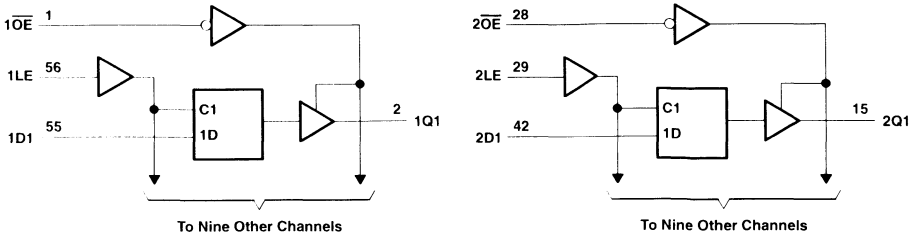
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		2.3 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
	I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
		V_{IH} = 2 V	2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	I_{OL} = 100 μA		2.3 V to 3.6 V			0.2	V
	I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
	I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
		V_{IL} = 0.8 V	2.7 V			0.4	
	I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I	V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$	V_I = 0.7 V		2.3 V	45			μA
	V_I = 1.7 V		2.3 V	–45			
	V_I = 0.8 V		3 V	75			
	V_I = 2 V		3 V	–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i Control inputs	V_I = V_{CC} or GND		3.3 V		4.5		pF
C_i Data inputs					6.5		
C_o Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE↑	0.9		0.7		1.1		ns
t_h	Hold time, data after LE↑	1.2		1.5		1.1		ns

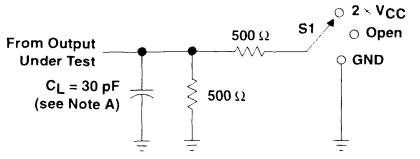
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1	5		4.7	1.2	3.9	ns
	LE		1	5.6		5.1	1	4.3	
t_{en}	$\overline{OE}$	Q	1	6.2		6	1	4.9	ns
t_{dis}	$\overline{OE}$	Q	1.1	5.3		4.3	1.3	4.1	ns

operating characteristics, $T_A = 25°C$

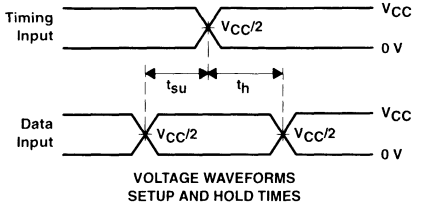
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	12	20	pF
		Outputs disabled		1	3	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

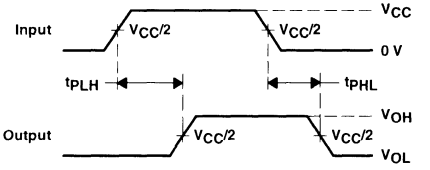


LOAD CIRCUIT

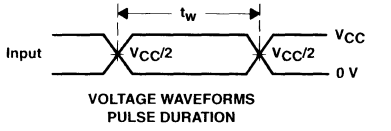
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



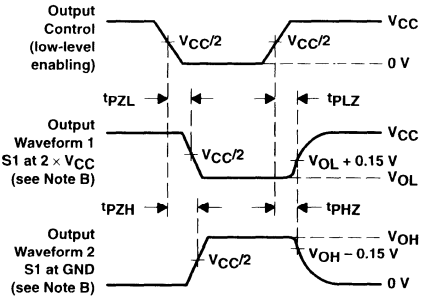
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

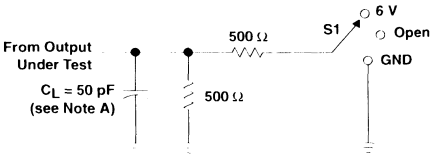


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

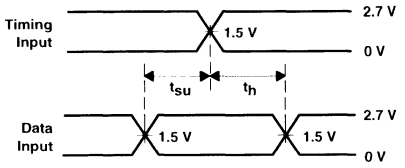
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

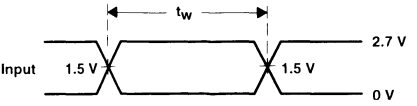


LOAD CIRCUIT

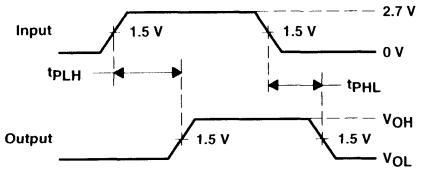
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



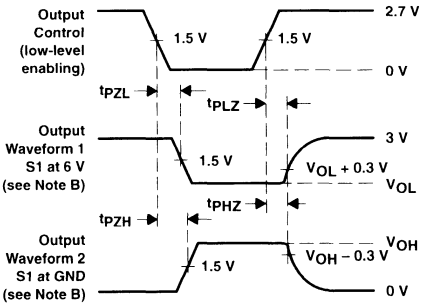
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



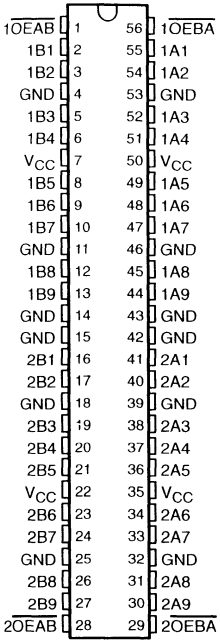
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16863 is an 18-bit noninverting transceiver designed for synchronous communication between data buses. The control-function implementation minimizes external timing requirements.

The SN74ALVCH16863 can be used as two 9-bit transceivers or one 18-bit transceiver. They allow data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16863 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 9-bit section)

INPUTS		OPERATION
$\overline{OEAB}$	$\overline{OEBA}$	
H	L	B data to A bus
L	H	A data to B bus
H	H	Isolation

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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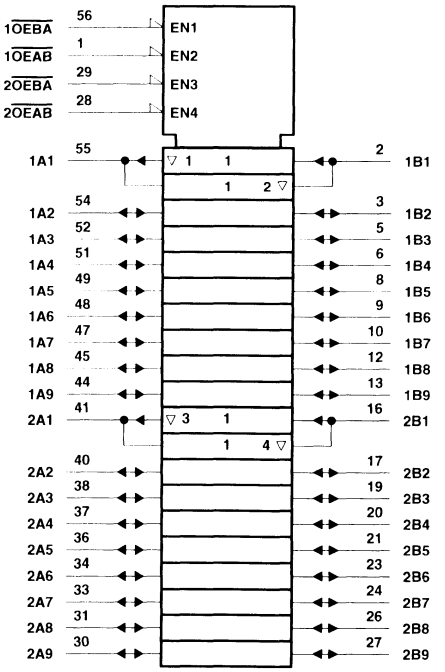
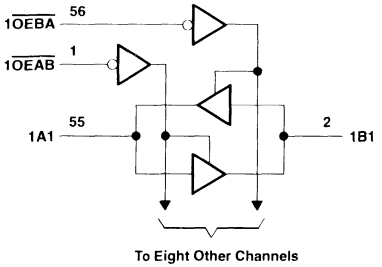
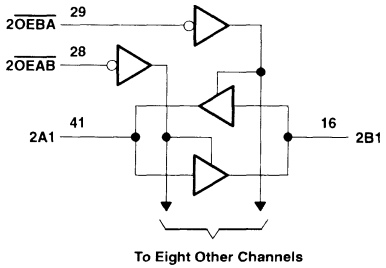
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

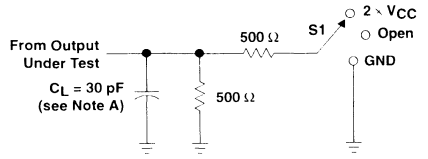
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	4.1		4	1	3.4	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	5.7		5.8	1	4.7	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1.3	5.5		4.7	1.4	4.2	ns

operating characteristics, T_A = 25°C

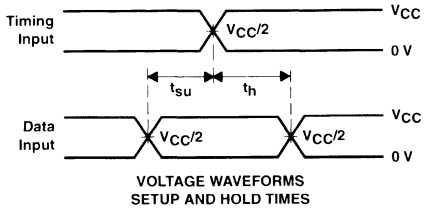
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	21	30	pF
		Outputs disabled		2	3	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

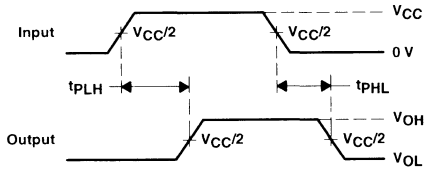


LOAD CIRCUIT

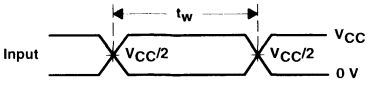
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



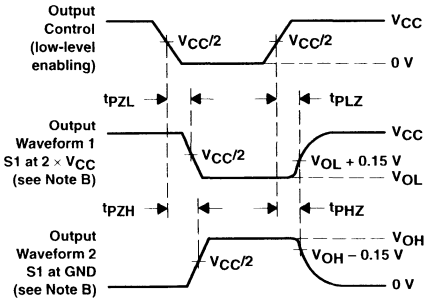
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

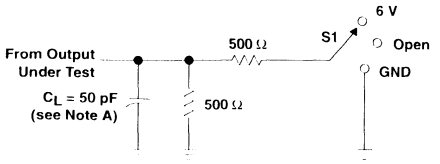


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

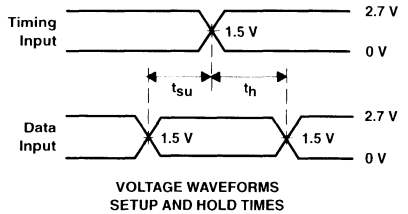
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

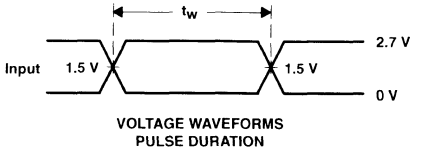


LOAD CIRCUIT

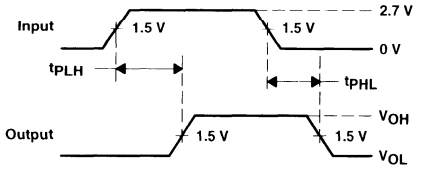
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



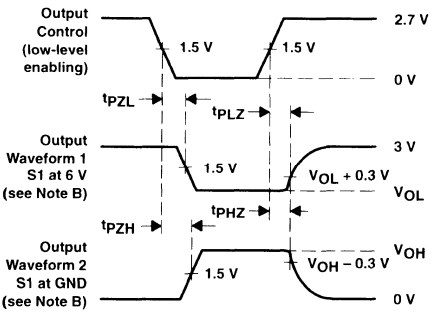
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



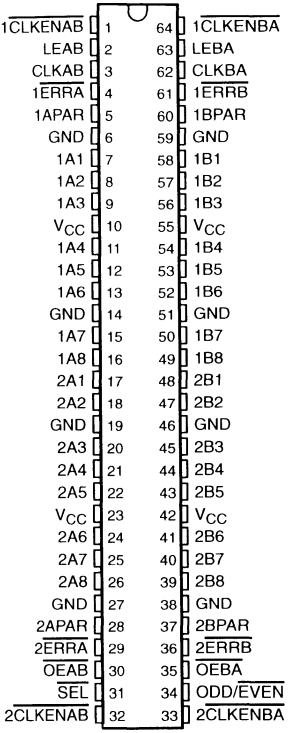
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus+*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **Simultaneously Generates and Checks Parity**
- **Option to Select Generate Parity and Check or Feed-Through Data/Parity in A-to-B or B-to-A Directions**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Thin Shrink Small-Outline Package**

DGG PACKAGE
(TOP VIEW)



description

This 18-bit (dual-octal) noninverting registered transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16901 is a dual 9-bit to dual 9-bit parity transceiver with registers. The device can operate as a feed-through transceiver or it can generate/check parity from the two 8-bit data buses in either direction.

The SN74ALVCH16901 features independent clock (CLKAB or CLKBA), latch-enable (LEAB or LEBA), and dual 9-bit clock-enable ($\overline{\text{CLKENAB}}$ or $\overline{\text{CLKENBA}}$) inputs. It also provides parity-enable ($\overline{\text{SEL}}$) and parity-select (ODD/$\overline{\text{EVEN}}$) inputs and separate error-signal ($\overline{\text{ERRA}}$ or $\overline{\text{ERRB}}$) outputs for checking parity. The direction of data flow is controlled by $\overline{\text{OEAB}}$ and $\overline{\text{OEBA}}$. When $\overline{\text{SEL}}$ is low, the parity functions are enabled. When $\overline{\text{SEL}}$ is high, the parity functions are disabled and the device acts as an 18-bit registered transceiver.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16901 is characterized for operation from –40°C to 85°C.

Function Tables

FUNCTION†

INPUTS					OUTPUT
$\overline{\text{CLKENAB}}$	$\overline{\text{OEAB}}$	LEAB	CLKAB	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	L	L	X	B_0‡
L	L	L	H	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar, but uses $\overline{\text{OEBA}}$, LEBA, and $\overline{\text{CLKENBA}}$.

‡ Output level before the indicated steady-state input conditions were established

§ Output level before the indicated steady-state input conditions were established, provided that CLKAB was low before LEAB went low

PARITY ENABLE

INPUTS			OPERATION OR FUNCTION	
$\overline{\text{SEL}}$	$\overline{\text{OEBA}}$	$\overline{\text{OEAB}}$		
L	H	L	Parity is checked on port A and is generated on port B.	
L	L	H	Parity is checked on port B and is generated on port A.	
L	H	H	Parity is checked on port B and port A.	
L	L	L	Parity is generated on port A and B if device is in FF mode.	
H	L	L	Parity functions are disabled; device acts as a standard 18-bit registered transceiver.	Q_A data to B, Q_B data to A
H	L	H		Q_B data to A
H	H	L		Q_A data to B
H	H	H		Isolation

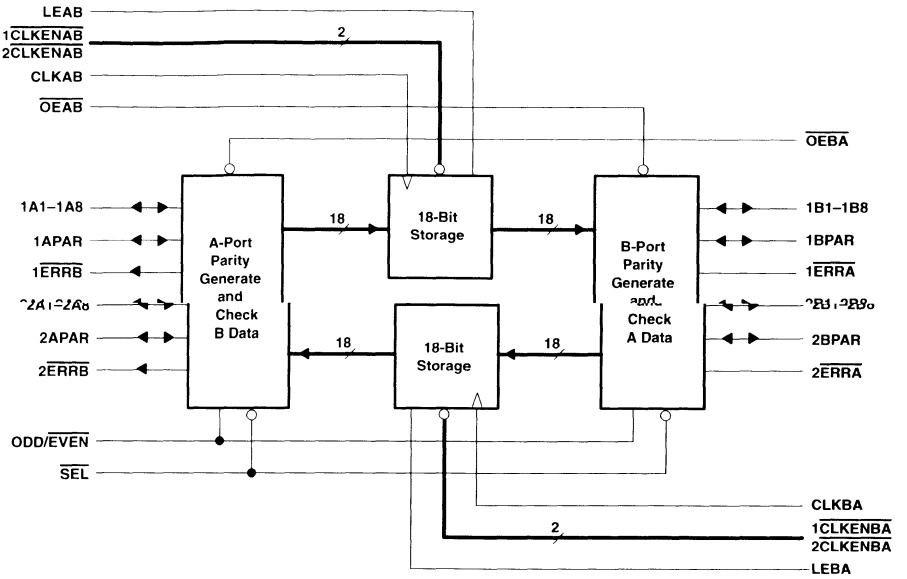
Function Tables (Continued)

PARITY

INPUTS								OUTPUTS			
$\overline{SEL}$	$\overline{OEBA}$	$\overline{OEAB}$	ODD/$\overline{EVEN}$	Σ OF INPUTS A1–A8 = H	Σ OF INPUTS B1–B8 = H	APAR	BPAR	APAR	$\overline{ERRA}$	BPAR	$\overline{ERRB}$
L	H	L	L	0, 2, 4, 6, 8	N/A	L	N/A	N/A	H	L	Z
L	H	L	L	1, 3, 5, 7	N/A	L	N/A	N/A	L	H	Z
L	H	L	L	0, 2, 4, 6, 8	N/A	H	N/A	N/A	L	L	Z
L	H	L	L	1, 3, 5, 7	N/A	H	N/A	N/A	H	H	Z
L	L	H	L	N/A	0, 2, 4, 6, 8	N/A	L	L	Z	N/A	H
L	L	H	L	N/A	1, 3, 5, 7	N/A	L	H	Z	N/A	L
L	L	H	L	N/A	0, 2, 4, 6, 8	N/A	H	L	Z	N/A	L
L	L	H	L	N/A	1, 3, 5, 7	N/A	H	H	Z	N/A	H
L	H	L	H	0, 2, 4, 6, 8	N/A	L	N/A	N/A	L	H	Z
L	H	L	H	1, 3, 5, 7	N/A	L	N/A	N/A	H	L	Z
L	H	L	H	0, 2, 4, 6, 8	N/A	H	N/A	N/A	H	H	Z
L	H	L	H	1, 3, 5, 7	N/A	H	N/A	N/A	L	L	Z
L	L	H	H	N/A	0, 2, 4, 6, 8	N/A	L	H	Z	N/A	L
L	L	H	H	N/A	1, 3, 5, 7	N/A	L	L	Z	N/A	H
L	L	H	H	N/A	0, 2, 4, 6, 8	N/A	H	H	Z	N/A	H
L	L	H	H	N/A	1, 3, 5, 7	N/A	H	L	Z	N/A	L
L	H	H	L	0, 2, 4, 6, 8	0, 2, 4, 6, 8	L	L	Z	H	Z	H
L	H	H	L	1, 3, 5, 7	1, 3, 5, 7	L	L	Z	L	Z	L
L	H	H	L	0, 2, 4, 6, 8	0, 2, 4, 6, 8	H	H	Z	L	Z	L
L	H	H	L	1, 3, 5, 7	1, 3, 5, 7	H	H	Z	H	Z	H
L	H	H	H	0, 2, 4, 6, 8	0, 2, 4, 6, 8	L	L	Z	L	Z	L
L	H	H	H	1, 3, 5, 7	1, 3, 5, 7	L	L	Z	H	Z	H
L	H	H	H	0, 2, 4, 6, 8	0, 2, 4, 6, 8	H	H	Z	H	Z	H
L	H	H	H	1, 3, 5, 7	1, 3, 5, 7	H	H	Z	L	Z	L
L	L	L	L	N/A	N/A	N/A	N/A	PE†	Z	PE†	Z
L	L	L	H	N/A	N/A	N/A	N/A	PO‡	Z	PO‡	Z

† Parity output is set to the level so that the specific bus side is set to even parity.
‡ Parity output is set to the level so that the specific bus side is set to odd parity.

functional block diagram



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2 ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3) ..... 73°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.5		pF
C_o	$\overline{ERR}$ ports	V_O = V_{CC} or GND		3.3 V		6		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	125	0	125	0	125	MHz
t_w	Pulse duration	CLK↑	3		3		3		ns
		LE high	3		3		3		
t_{su}	Setup time	A, APAR or B, BPAR before CLK↑	1.9		2		1.7		ns
		$\overline{CLKEN}$ before CLK↑	2.1		2.1		1.7		
		A, APAR or B, BPAR before LE↓	1.4		1.3		1.2		
t_h	Hold time	A, APAR or B, BPAR after CLK↑	0.4		0.4		0.5		ns
		$\overline{CLKEN}$ after CLK↑	0.5		0.5		0.7		
		A, APAR or B, BPAR after LE↓	0.9		1.1		0.9		

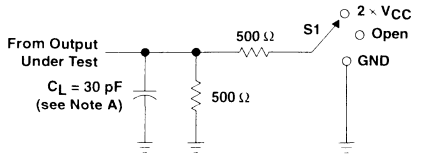
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			125		125		125		MHz
t_{pd}	A or B	B or A	1	5.2		4.8	1	4.4	ns
		BPAR or APAR	2	8.9		7.6	2	6.7	
	APAR or BPAR	BPAR or APAR	1	5.7		5.2	1	4.7	
		$\overline{ERRA}$ or $\overline{ERRB}$	2	9.7		8.7	2	7.5	
	ODD/$\overline{EVEN}$	$\overline{ERRA}$ or $\overline{ERRB}$	1.5	8.7		7.9	1.5	6.8	
		BPAR or APAR	1.5	8.3		7.6	1.5	6.5	
	$\overline{SEL}$	BPAR or APAR	1	6.1		5.9	1	5.1	
	CLKAB or CLKBA	A or B	1	6.4		5.8	1	5.1	
		BPAR or APAR parity feedthrough	1.5	7.1		6.3	1.5	5.6	
		BPAR or APAR parity generated	2.5	10.2		8.7	2	7.7	
		$\overline{ERRA}$ or $\overline{ERRB}$	2.5	10.5		8.9	2	7.9	
	LEAB or LEBA	A or B	1	6		5.5	1	4.8	
		BPAR or APAR parity feedthrough	1.5	6.7		6	1.5	5.3	
		BPAR or APAR parity generated	2.5	9.8		8.3	2	7.4	
		$\overline{ERRA}$ or $\overline{ERRB}$	2.5	9.9		8.5	2	7.5	
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	B, BPAR or A, APAR	1.4	6.3		6.1	1	5.3	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	B, BPAR or A, APAR	1.3	6.1		5.2	1.5	4.9	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	$\overline{ERRA}$ or $\overline{ERRB}$	1.4	6.2		5.5	1	4.9	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	$\overline{ERRA}$ or $\overline{ERRB}$	1.3	7.3		6.5	1	5.7	ns
t_{en}	$\overline{SEL}$	$\overline{ERRA}$ or $\overline{ERRB}$	1.4	6.7		6.5	1	5.5	ns
t_{dis}	$\overline{SEL}$	$\overline{ERRA}$ or $\overline{ERRB}$	1.3	6.4		5.4	1.5	4.9	ns

operating characteristics, T_A = 25°C

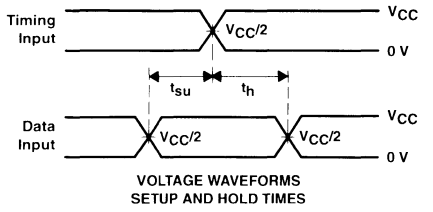
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	22	27	pF
		Outputs disabled		5	8	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

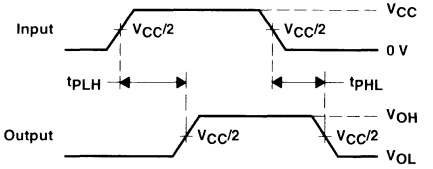


LOAD CIRCUIT

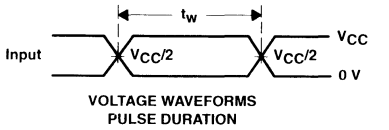
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



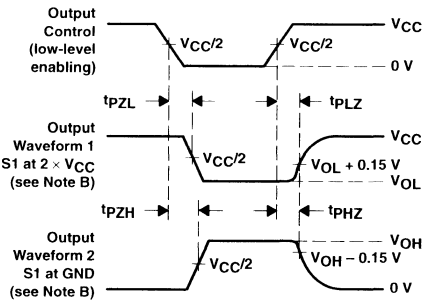
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

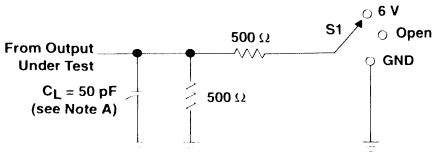


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

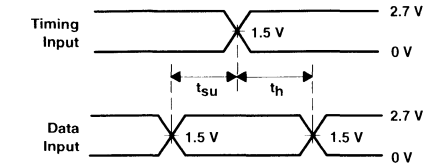
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

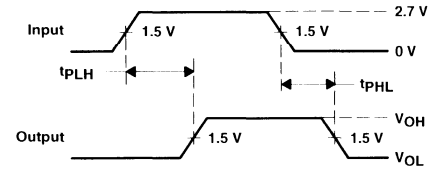


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

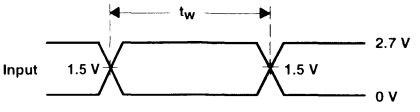
LOAD CIRCUIT



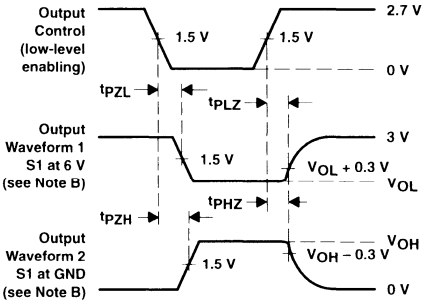
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



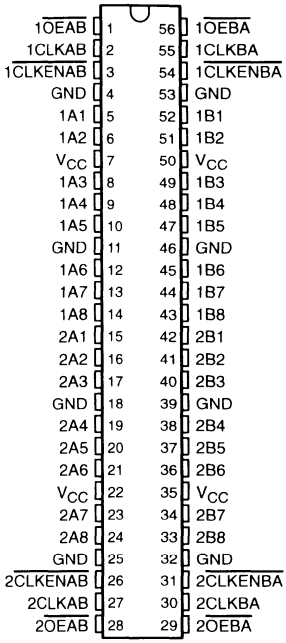
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

This 16-bit registered transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16952 contains two sets of D-type flip-flops for temporary storage of data flowing in either direction. This device can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input provided that the clock-enable ($\overline{\text{CLKENAB}}$ or $\overline{\text{CLKENBA}}$) input is low. Taking the output-enable ($\overline{\text{OEAB}}$ or $\overline{\text{OEBA}}$) input low accesses the data on either port.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16952 is characterized for operation from –40°C to 85°C.

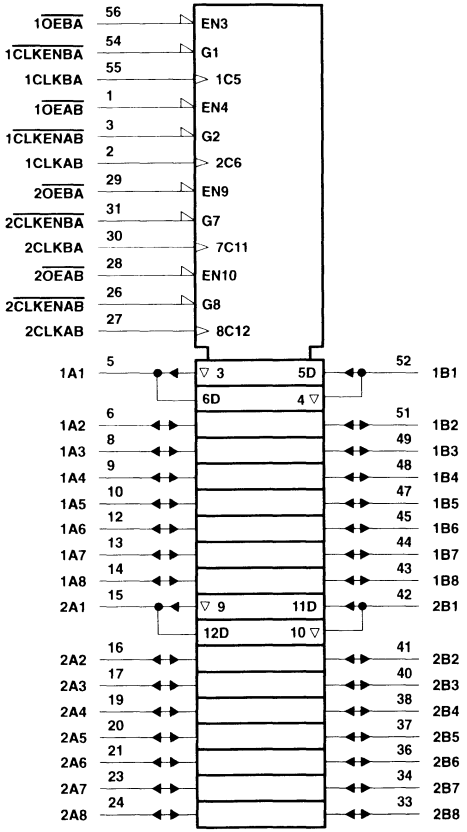
FUNCTION TABLE†

INPUTS				OUTPUT B
$\overline{CLKENAB}$	CLKAB	$\overline{OEAB}$	A	
H	X	L	X	B_0‡
X	L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

† A-to-B data flow is shown; B-to-A data flow is similar, but uses $\overline{CLKENBA}$, CLKBA, and $\overline{OEBA}$.

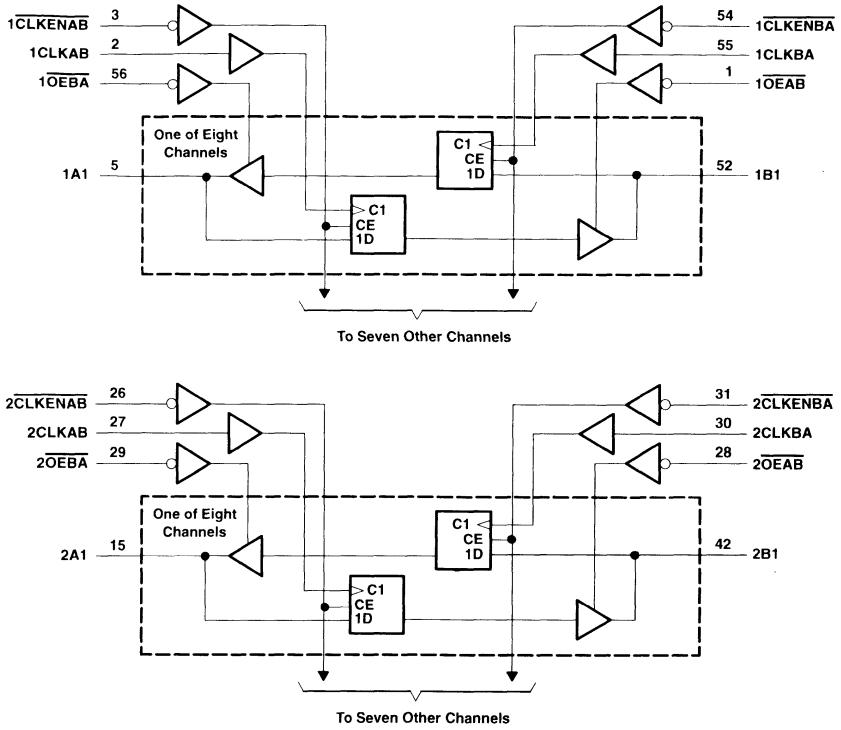
‡ Level of B before the indicated steady-state input conditions were established

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DGV package . . . . . 86°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration	$\overline{CLKEN}$ high	3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK	1.7		1.9		1.5		ns
		$\overline{CLKEN}$ before CLK	1.2		1		1		
t_h	Hold time	Data after CLK	0.6		0.6		0.8		ns
		$\overline{CLKEN}$ after CLK	1.1		0.9		1.1		

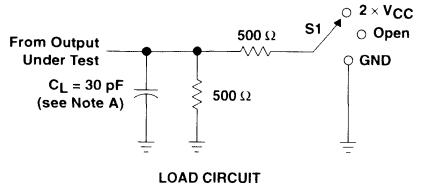
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	A or B	1	4.1		4.6	1	3.9	ns
t_{en}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	1	5.4		5.3	1	4.4	ns
t_{dis}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	1	5.3		4.4	1.1	4	ns

operating characteristics, T_A = 25°C

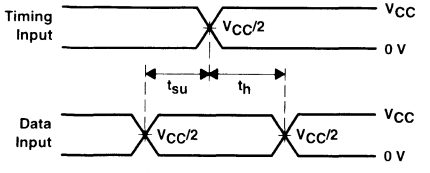
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	53	71	pF
		Outputs disabled		34	40	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

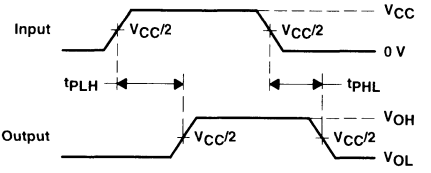


LOAD CIRCUIT

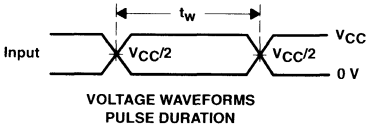
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



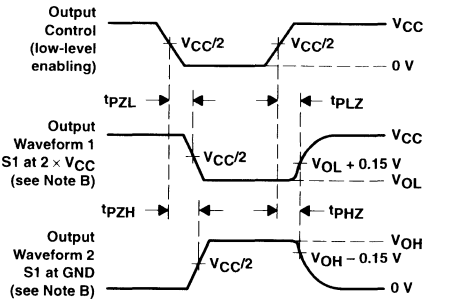
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

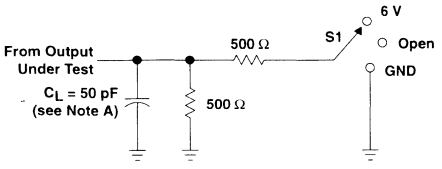


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

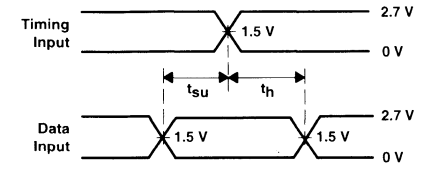
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

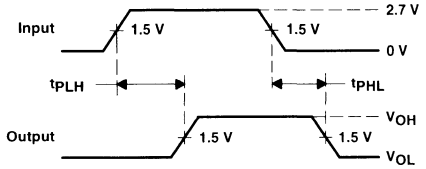


LOAD CIRCUIT

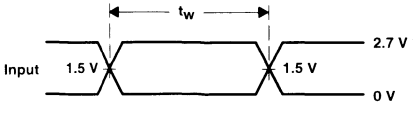
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



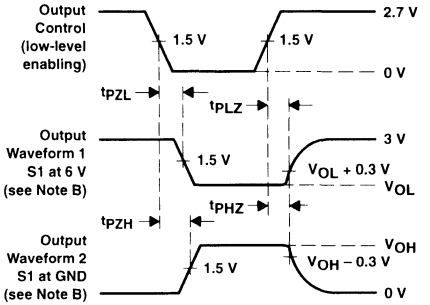
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

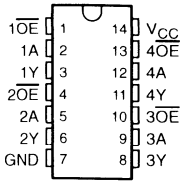
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

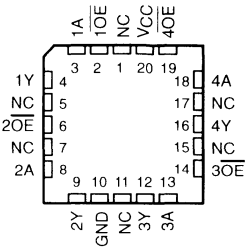
Contents

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Support Live Insertion**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs**

SN54LVT125 . . . J PACKAGE
SN74LVT125 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVT125 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These bus buffers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT125 feature independent line drivers with 3-state outputs. Each output is in the high-impedance state when the associated output-enable ($\overline{OE}$) input is high.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

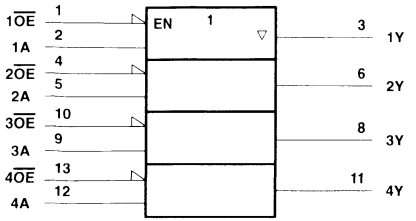
The SN74LVT125 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT125 is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74LVT125 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each buffer)

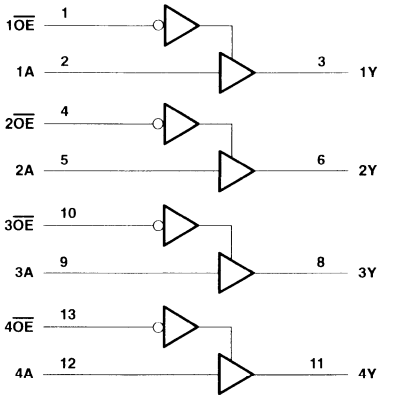
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



Pin numbers shown are for the D, DB, J, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT125 ..... 96 mA
SN74LVT125 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT125 ..... 48 mA
SN74LVT125 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT125		SN74LVT125		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT125			SN74LVT125			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA		V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = − 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = − 24 mA		2						
		I_{OH} = − 32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				−5			−5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	Data inputs	75			75			µA
		V_I = 2 V		−75			−75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				5			5	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				−5			−5	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.12	0.19		0.12	0.19	mA
			Outputs low		4.5	7		4.5	7	
			Outputs disabled		0.12	0.19		0.12	0.19	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} − 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				8			8		pF

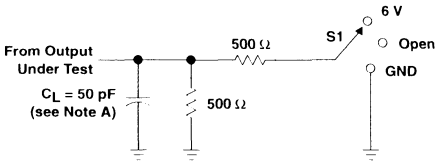
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT125				SN74LVT125				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	4.2		4.7	1	2.7	4	4.5	ns
t_{PHL}			1	4.1		5.1	1	2.9	3.9	4.9	
t_{PZH}	$\overline{OE}$	Y	1	4.9		6.2	1	3.4	4.7	6	ns
t_{PZL}			1.1	4.9		6.7	1.1	3.4	4.7	6.5	
t_{PHZ}	$\overline{OE}$	Y	1.8	5.3		5.9	1.8	3.7	5.1	5.7	ns
t_{PLZ}			1.3	4.7		4.2	1.3	2.6	4.5	4	

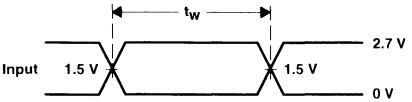
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

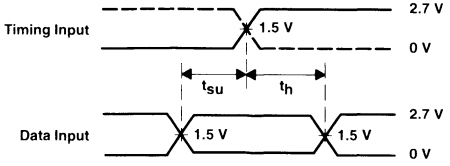


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

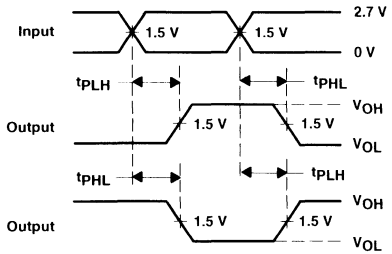
LOAD CIRCUIT FOR OUTPUTS



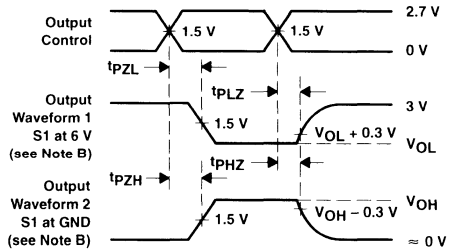
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



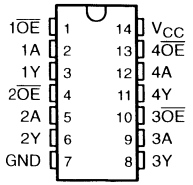
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

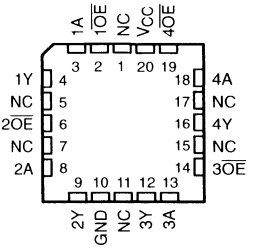
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- High-Impedance State During Power Up and Power Down
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

SN54LVTH125 . . . J PACKAGE
SN74LVTH125 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVTH125 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These bus buffers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH125 feature independent line drivers with 3-state outputs. Each output is in the high-impedance state when the associated output-enable ($\overline{OE}$) input is high.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH125 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH125 is characterized for operation from –40°C to 85°C.

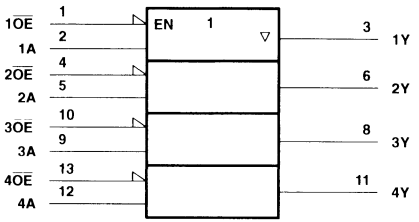
PRODUCT PREVIEW

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

FUNCTION TABLE
(each buffer)

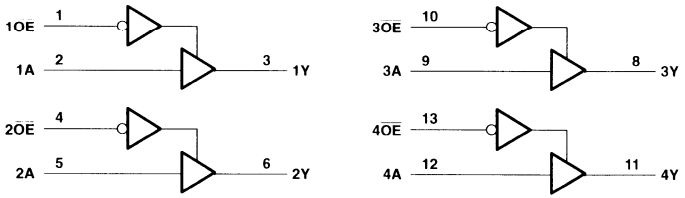
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, and PW packages.

logic diagram (positive logic)



Pin numbers shown are for the D, DB, J, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH125 ..... 96 mA
SN74LVTH125 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH125 ..... 48 mA
SN74LVTH125 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH125		SN74LVTH125		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH125			SN74LVTH125			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±50			±50	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±50			±50	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.12	0.19		0.12	0.19	mA
			Outputs low		4.5	7		4.5	7	
			Outputs disabled		0.12	0.19		0.12	0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.3			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

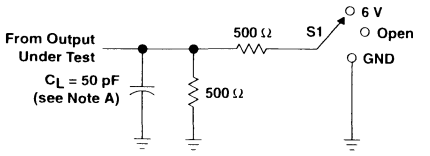
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH125				SN74LVTH125				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	4.2		4.7	1	2.7	4	4.5	ns
t_{PHL}			1	4.1		5.1	1	2.9	3.9	4.9	
t_{PZH}	$\overline{OE}$	Y	1	4.9		6.2	1	3.4	4.7	6	ns
t_{PZL}			1.1	4.9		6.7	1.1	3.4	4.7	6.5	
t_{PHZ}	$\overline{OE}$	Y	1.8	5.3		5.9	1.8	3.7	5.1	5.7	ns
t_{PLZ}			1.3	4.7		4.2	1.3	2.6	4.5	4	

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

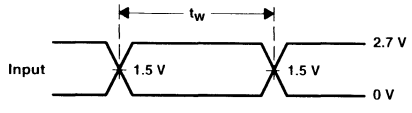
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION

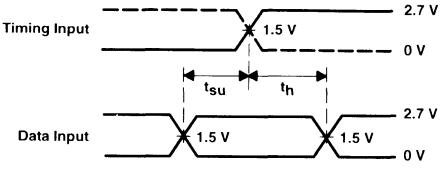


LOAD CIRCUIT

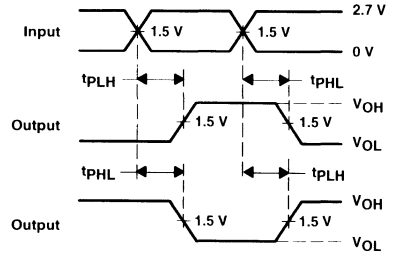
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



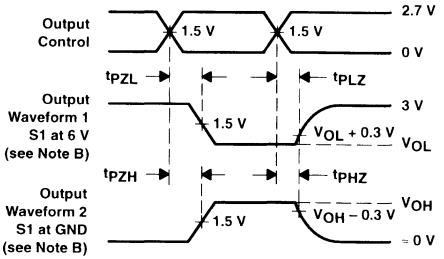
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



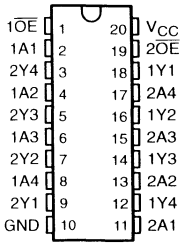
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

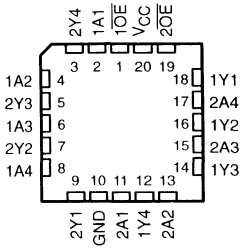
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Latch-Up Performance Exceeds 500 mA JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

SN54LVTH240 . . . J PACKAGE
SN74LVTH240 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH240 . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers and line drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are organized as two 4-bit buffer/line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the devices pass data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

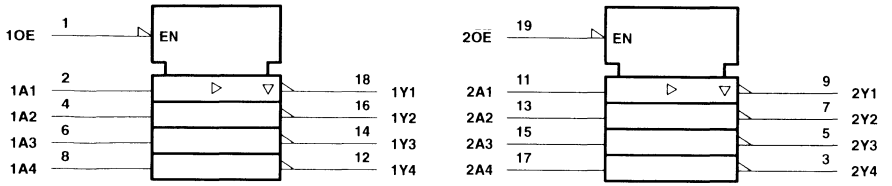
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH240 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

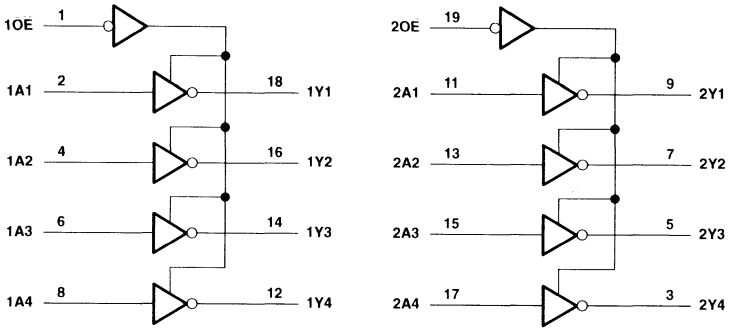
INPUTS		OUTPUT
OE	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH240 . . . . . 96 mA
SN74LVTH240 . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH240 . . . . . 48 mA
SN74LVTH240 . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH240		SN74LVTH240		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH240			SN74LVTH240			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

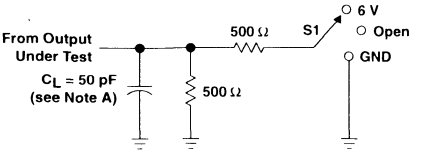
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH240				SN74LVTH240				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	3.9		4.7	1.1	2.2	3.8	4.6	ns
t_{PHL}			1.2	4.2		4.3	1.3	2.6	4	4.2	
t_{PZH}	$\overline{OE}$	Y	1	4.7		5.7	1.1	2.6	4.6	5.6	ns
t_{PZL}			1.3	4.6		5.2	1.4	2.7	4.4	5	
t_{PHZ}	$\overline{OE}$	Y	1.9	4.6		4.8	2	2.9	4.4	4.6	ns
t_{PLZ}			1.7	4.7		4.7	1.8	3	4.3	4.3	

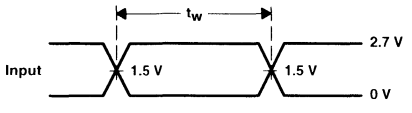
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

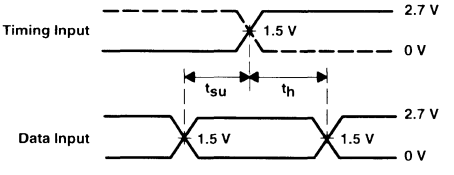


LOAD CIRCUIT

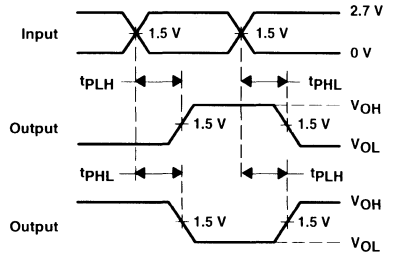
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



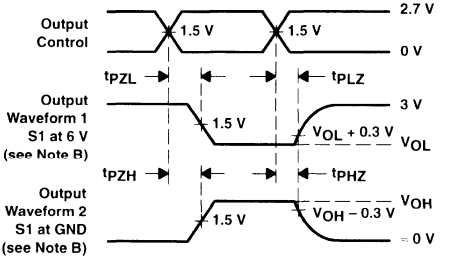
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



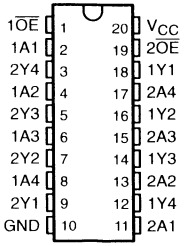
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

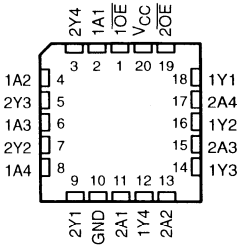
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs**

SN54LVT240A . . . J PACKAGE
SN74LVT240A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT240A . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers and line drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are organized as two 4-bit buffer/line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the devices pass data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

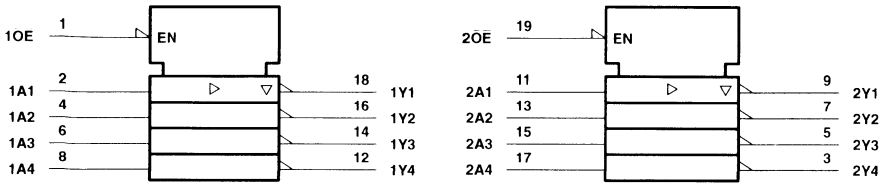
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVT240A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT240A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

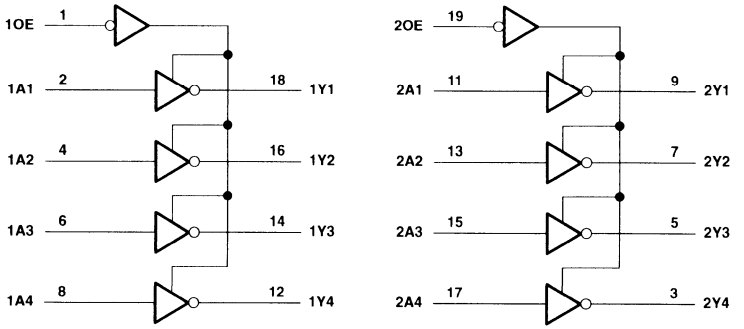
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT240A . . . . . 96 mA
SN74LVT240A . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT240A . . . . . 48 mA
SN74LVT240A . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVT240A		SN74LVT240A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		5		5	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVT240A			SN74LVT240A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			7			7		pF

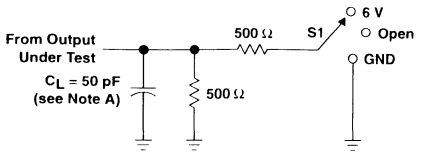
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT240A				SN74LVT240A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	3.9		4.7	1.1	2.2	3.8	4.6	ns
t_{PHL}			1.2	4.2		4.3	1.3	2.6	4	4.2	
t_{PZH}	$\overline{OE}$	Y	1	4.7		5.7	1.1	2.6	4.6	5.6	ns
t_{PZL}			1.3	4.6		5.2	1.4	2.7	4.4	5	
t_{PHZ}	$\overline{OE}$	Y	1.9	4.6		4.8	2	2.9	4.4	4.6	ns
t_{PLZ}			1.7	4.7		4.7	1.8	3	4.3	4.3	

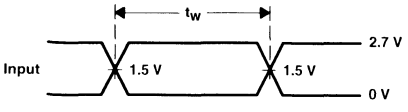
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

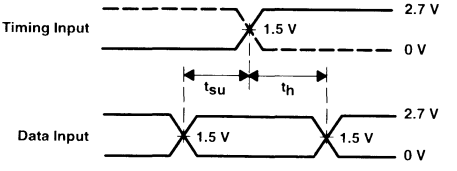


LOAD CIRCUIT

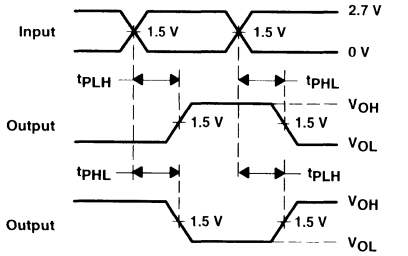
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



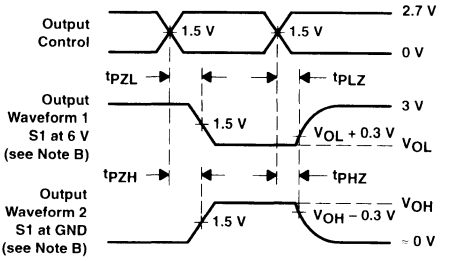
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



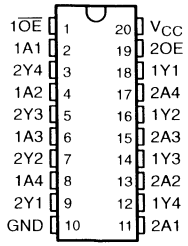
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

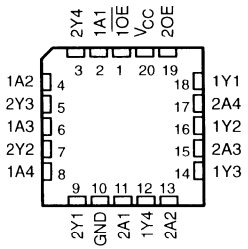
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

SN54LVTH241 . . . J PACKAGE
SN74LVTH241 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH241 . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH241 are organized as two 4-bit line drivers with separate output-enable ($1\overline{OE}$, $2\overline{OE}$) inputs. When $1\overline{OE}$ is low or $2\overline{OE}$ is high, the devices pass data from the A inputs to the Y outputs. When $1\overline{OE}$ is high or $2\overline{OE}$ is low, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

The SN54LVTH241 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH241 is characterized for operation from –40°C to 85°C.

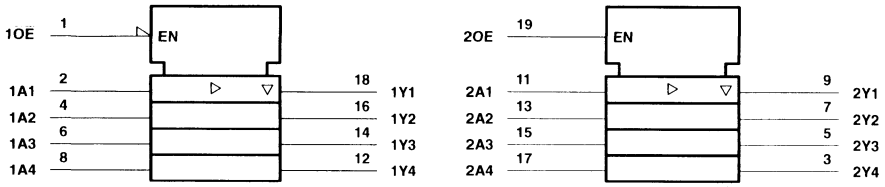
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

FUNCTION TABLES

INPUTS		OUTPUT
$1\overline{OE}$	1A	1Y
L	H	H
L	L	L
H	X	Z

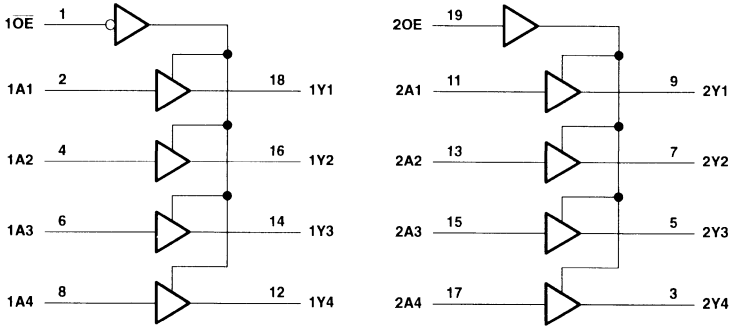
INPUTS		OUTPUT
2OE	2A	2Y
H	H	H
H	L	L
L	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH241 ..... 96 mA
SN74LVTH241 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH241 ..... 48 mA
SN74LVTH241 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DW package ..... 97°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH241		SN74LVTH241		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH241			SN74LVTH241			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$/OE = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$/OE = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

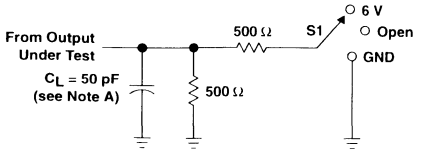
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH241				SN74LVTH241				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	3.7		4	1.1	2.3	3.5	3.9	ns
t_{PHL}			1.2	3.5		3.7	1.3	2.2	3.4	3.6	
t_{PZH}	$\overline{OE}$ or OE	Y	1	4.6		5.5	1.1	2.7	4.5	5.4	ns
t_{PZL}			1.3	4.6		5.1	1.4	2.9	4.4	5	
t_{PHZ}	$\overline{OE}$ or OE	Y	1.5	4.7		5.5	1.6	2.8	4.5	5.3	ns
t_{PLZ}			1.7	5		5.5	1.8	3	4.7	5.2	

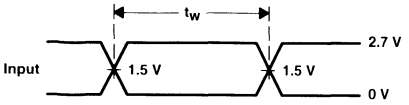
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

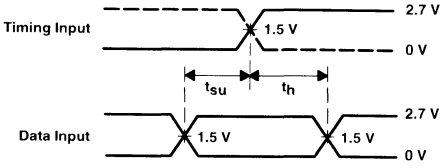


LOAD CIRCUIT

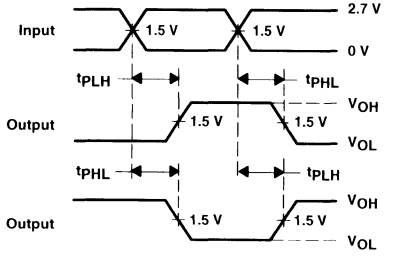
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



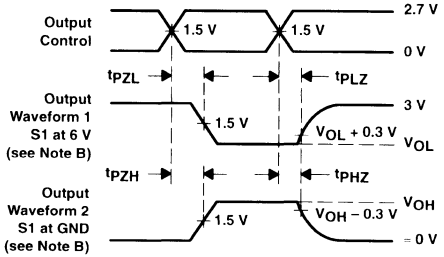
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



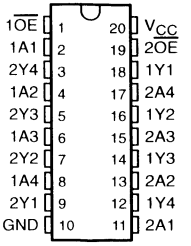
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

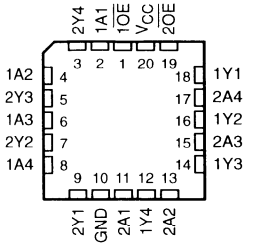
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN54LVTH244A . . . J OR W PACKAGE
SN74LVTH244A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH244A . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers and line drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH244A are organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

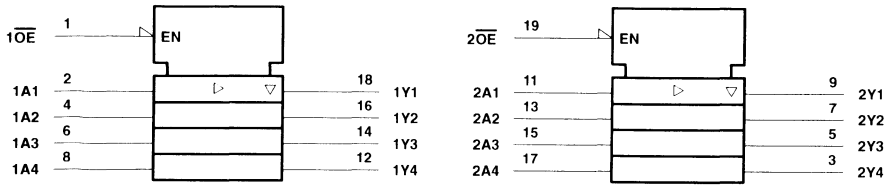
The SN54LVTH244A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH244A is characterized for operation from –40°C to 85°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

FUNCTION TABLE
(each buffer)

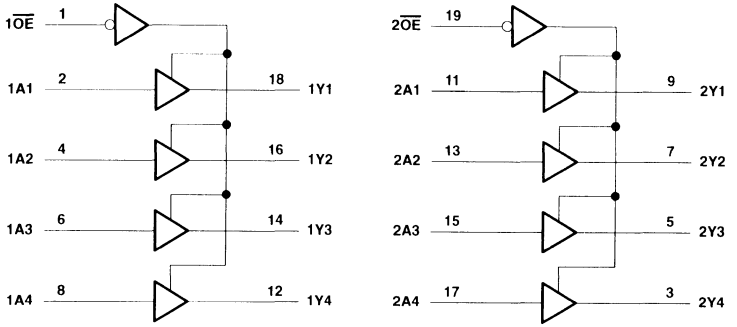
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH244A . . . . . 96 mA
SN74LVTH244A . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH244A . . . . . 48 mA
SN74LVTH244A . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH244A		SN74LVTH244A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH244A			SN74LVTH244A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	A inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

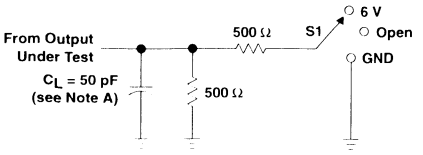
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH244A				SN74LVTH244A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A	Y	1	3.6		3.9	1.1	2.3	3.5		3.8	ns
t_{PHL}			1.2	3.4		3.6	1.3	2.1	3.3		3.6	
t_{PZH}	$\overline{OE}$	Y	1	4.6		5.5	1.1	2.5	4.5		5.3	ns
t_{PZL}			1.3	4.5		5.1	1.4	2.7	4.4		4.9	
t_{PHZ}	$\overline{OE}$	Y	1.8	4.5		4.7	1.9	2.8	4.4		4.5	ns
t_{PLZ}			1.7	4.5		4.6	1.8	2.9	4.4		4.4	

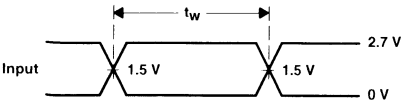
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

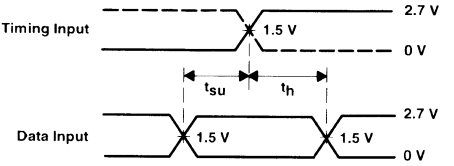


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

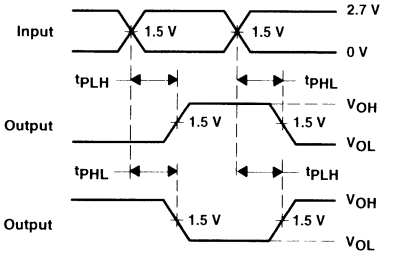
LOAD CIRCUIT



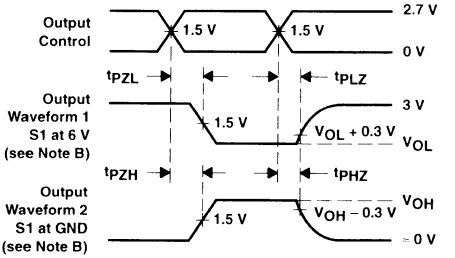
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



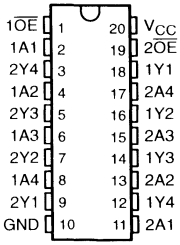
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

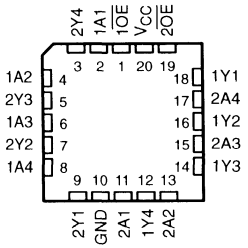
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN54LVT244B . . . J OR W PACKAGE
SN74LVT244B . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT244B . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers and line drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT244B is organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

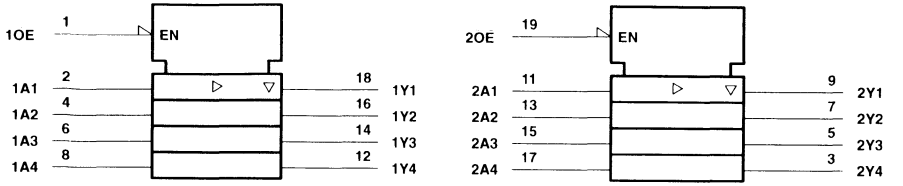
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVT244B is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT244B is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

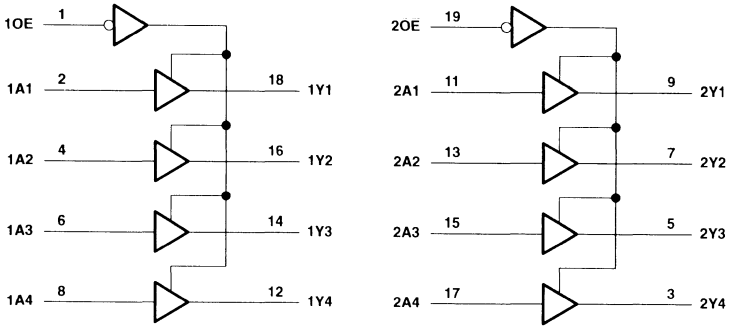
INPUTS		OUTPUT
OE	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT244B . . . . . 96 mA
SN74LVT244B . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT244B . . . . . 48 mA
SN74LVT244B . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVT244B		SN74LVT244B		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVT244B			SN74LVT244B			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.3			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			7			7		pF

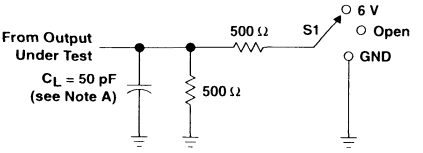
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT244B				SN74LVT244B				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	3.6		3.9	1.1	2.3	3.5	3.8	ns
t_{PHL}			1.2	3.4		3.6	1.3	2.1	3.3	3.6	
t_{PZH}	$\overline{OE}$	Y	1	4.6		5.5	1.1	2.5	4.5	5.3	ns
t_{PZL}			1.3	4.5		5.1	1.4	2.7	4.4	4.9	
t_{PHZ}	$\overline{OE}$	Y	1.8	4.5		4.7	1.9	2.8	4.4	4.5	ns
t_{PLZ}			1.7	4.5		4.6	1.8	2.9	4.4	4.4	

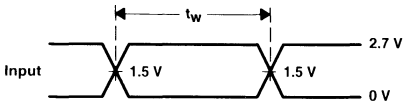
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

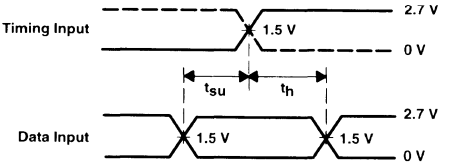


LOAD CIRCUIT

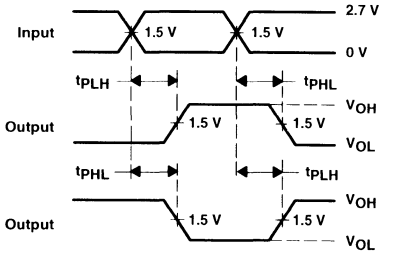
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



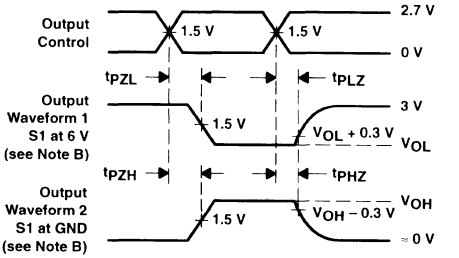
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



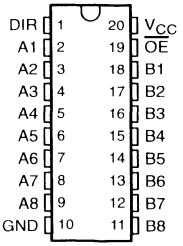
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

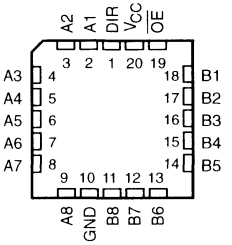
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN54LVTH245A . . . J OR W PACKAGE
SN74LVTH245A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH245A . . . FK PACKAGE
(TOP VIEW)



description

These octal bus transceivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are designed for asynchronous communication between data buses. They transmit data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the devices so the buses are effectively isolated.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

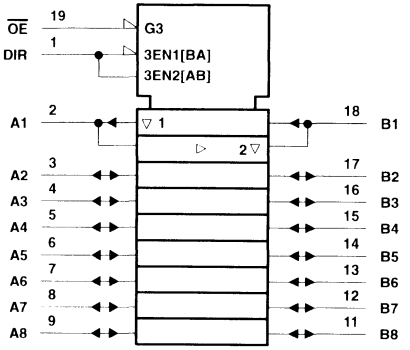
The SN54LVTH245A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH245A is characterized for operation from –40°C to 85°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

FUNCTION TABLE

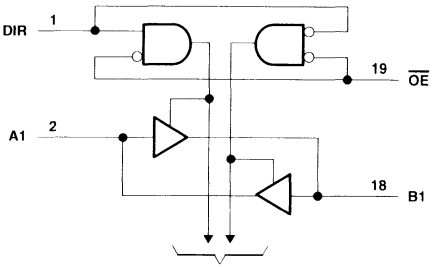
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH245A . . . . . 96 mA
SN74LVTH245A . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH245A . . . . . 48 mA
SN74LVTH245A . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH245A		SN74LVTH245A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		µs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH245A			SN74LVTH245A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			9			9		pF

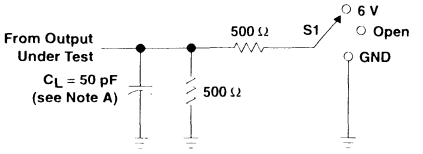
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused terminals are at V_{CC} or GND.
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH245A				SN74LVTH245A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1.1	3.7		4.2	1.2	2.3	3.5		4	ns
t_{PHL}			1.1	3.7		4.2	1.2	2.1	3.5		4	
t_{PZH}	$\overline{OE}$	A or B	1.2	5.7		7.4	1.3	3.2	5.5		7.1	ns
t_{PZL}			1.6	5.7		6.8	1.7	3.4	5.5		6.5	
t_{PHZ}	$\overline{OE}$	A or B	2.1	6.2		6.8	2.2	3.5	5.9		6.5	ns
t_{PLZ}			2.1	5.3		5.5	2.2	3.4	5		5.1	

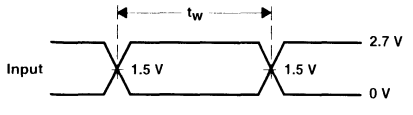
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

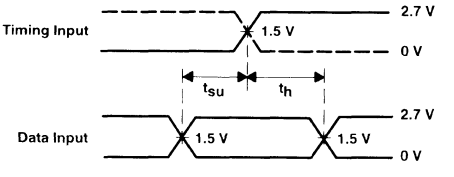


LOAD CIRCUIT

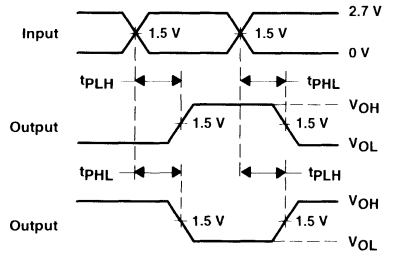
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



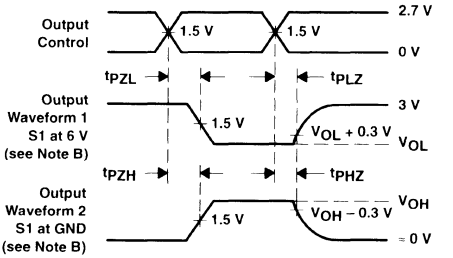
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



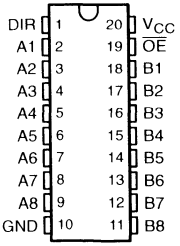
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

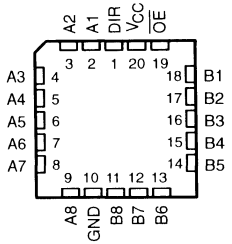
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- B-Port Outputs Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required
- High-Impedance State During Power Up and Power Down
- Power Off Disables Outputs, Permitting Live Insertion
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN54LVTH2245 . . . J OR W PACKAGE
SN74LVTH2245 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH2245 . . . FK PACKAGE
(TOP VIEW)



description

These octal bus transceivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are designed for asynchronous communication between data buses. They transmit data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the devices so the buses are effectively isolated.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The B-port outputs, which are designed to source or sink up to 12 mA, include equivalent 22-Ω series resistors to reduce overshoot and undershoot.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

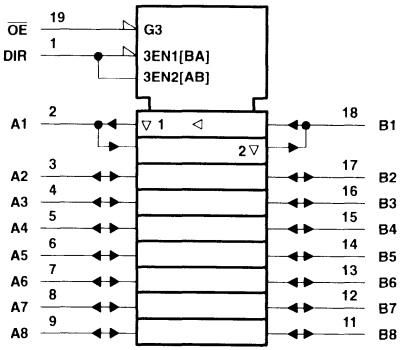
description (continued)

The SN54LVTH2245 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH2245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

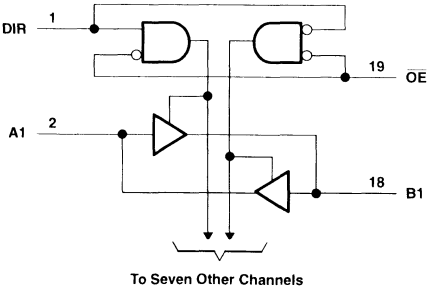
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH2245 (A port) . . . . . 96 mA
SN74LVTH2245 (A port) . . . . . 128 mA
B port . . . . . 30 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH2245 (A port) . . . . . 48 mA
SN74LVTH2245 (A port) . . . . . 64 mA
B port . . . . . 30 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH2245		SN74LVTH2245		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	A port		–24		–32	mA
		B port		–12		–12	
I_{OL}	Low-level output current	A port		48		64	mA
		B port		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH2245			SN74LVTH2245			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}	A port	V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 μA	V_{CC}−0.2			V_{CC}−0.2			V
		V_{CC} = 2.7 V,	I_{OH} = −8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = −24 mA	2						
			I_{OH} = −32 mA				2			
	B port	V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 μA	V_{CC}−0.2			V_{CC}−0.2			V
		V_{CC} = 3 V,	I_{OH} = −12 mA	2			2			
V_{OL}	A port	V_{CC} = 2.7 V	I_{OL} = 100 μA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
	B port	V_{CC} = 2.7 V to 3.6 V,	I_{OL} = 100 μA			0.2			0.2	V
		V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	μA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	μA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	−75			−75			
I_{OZPU}		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100*			±100	μA
I_{OZPD}		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100*			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19		0.1	0.19	mA
			Outputs low			5		3	5	
			Outputs disabled			0.19		0.1	0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			9			9		pF

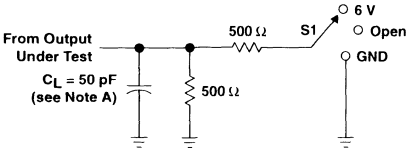
* On products compliant to MIL-PRF-38535, this parameter is not production tested.
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused terminals are at V_{CC} or GND.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH2245				SN74LVTH2245				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	B	1	4.6		5.3	1.1	2.9	4.4	5.1	ns
t_{PHL}			1	4.6		5.3	1.1	2.6	4.4	5.1	
t_{PLH}	B	A	1	3.7		4.2	1.1	2.2	3.5	4	ns
t_{PHL}			1	3.7		4.2	1.1	2	3.5	4	
t_{PZH}	$\overline{OE}$	A	1.2	5.7		7.4	1.3	3.1	5.5	7.1	ns
t_{PZL}			1.6	5.7		6.8	1.7	3.2	5.5	6.5	
t_{PHZ}	$\overline{OE}$	A	2	6.2		6.8	2.2	3.6	5.9	6.5	ns
t_{PLZ}			2	5.3		5.5	2.2	3.4	5	5.1	
t_{PZH}	$\overline{OE}$	B	1.2	6.4		7.6	1.3	3.5	6.2	7.3	ns
t_{PZL}			1.6	6.4		7.5	1.7	3.7	6.2	7.3	
t_{PHZ}	$\overline{OE}$	B	2	6.1		6.8	2.2	3.9	5.9	6.5	ns
t_{PLZ}			2	5.7		5.9	2.2	3.7	5.4	5.7	

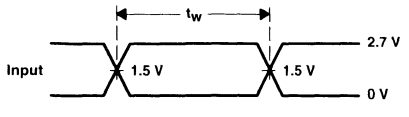
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

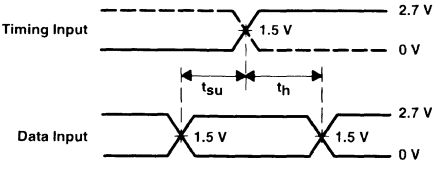


LOAD CIRCUIT

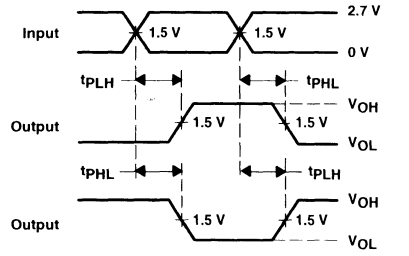
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



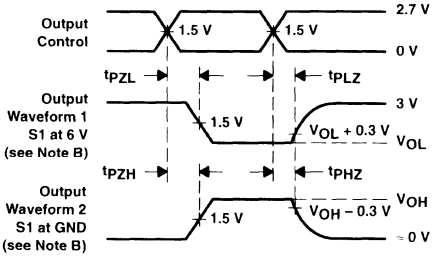
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
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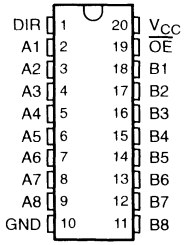
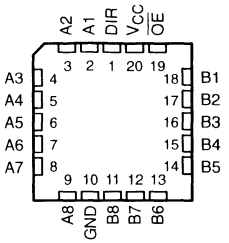
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN54LVT245B . . . J OR W PACKAGE
SN74LVT245B . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT245B . . . FK PACKAGE
(TOP VIEW)



description

These octal bus transceivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are designed for asynchronous communication between data buses. They transmit data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the devices so the buses are effectively isolated.

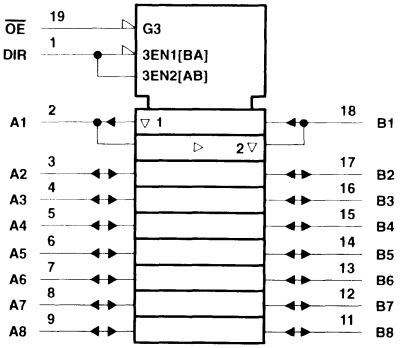
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVT245B is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT245B is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

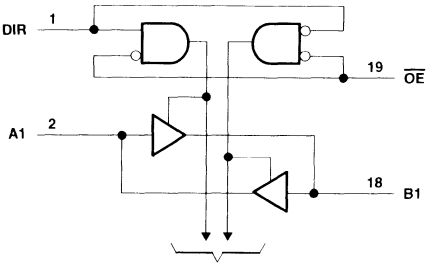
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT245B ..... 96 mA
SN74LVT245B ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT245B ..... 48 mA
SN74LVT245B ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DW package ..... 97°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVT245B		SN74LVT245B		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVT245B			SN74LVT245B			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 µA	V_{CC}−0.2			V_{CC}−0.2			V
		V_{CC} = 2.7 V,	I_{OH} = −8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = −24 mA	2						
			I_{OH} = −32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			9			9		pF

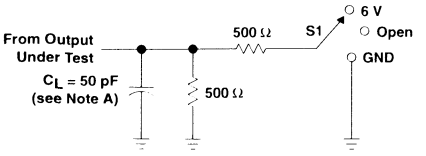
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused terminals are at V_{CC} or GND.
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT245B				SN74LVT245B					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1.1	3.7		4.2	1.2	2.3	3.5		4	ns
t_{PHL}			1.1	3.7		4.2	1.2	2.1	3.5		4	
t_{PZH}	$\overline{OE}$	A or B	1.2	5.7		7.4	1.3	3.2	5.5		7.1	ns
t_{PZL}			1.6	5.7		6.8	1.7	3.4	5.5		6.5	
t_{PHZ}	$\overline{OE}$	A or B	2.1	6.2		6.8	2.2	3.5	5.9		6.5	ns
t_{PLZ}			2.1	5.3		5.5	2.2	3.4	5		5.1	

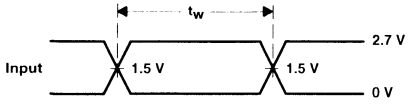
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

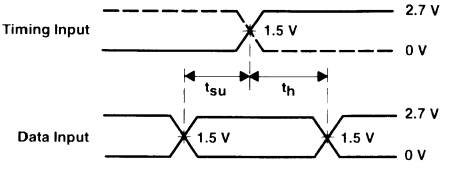


LOAD CIRCUIT

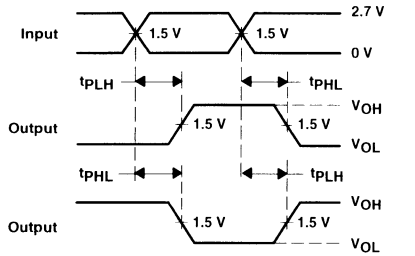
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



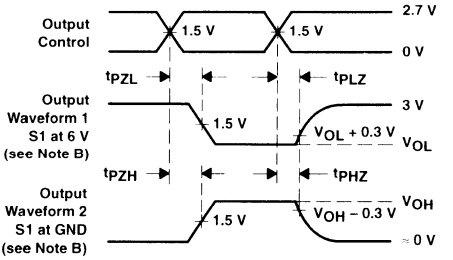
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



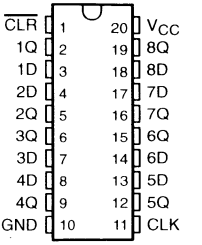
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

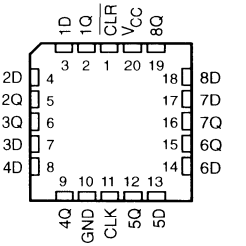
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Buffered Clock and Direct Clear Inputs
- Individual Data Input to Each Flip-Flop
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

SN54LVTH273 . . . J PACKAGE
SN74LVTH273 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH273 . . . FK PACKAGE
(TOP VIEW)



description

These octal D-type flip-flops are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH273 are positive-edge-triggered flip-flops with a direct clear input. Information at the data (D) inputs meeting the setup-time requirements is transferred to the Q outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock (CLK) input is at either the high or low level, the D-input signal has no effect at the output.

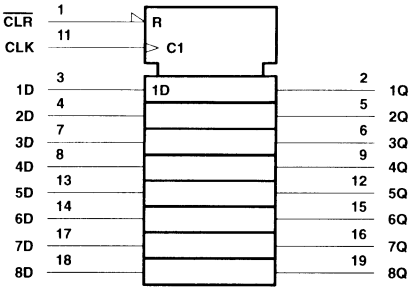
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVTH273 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH273 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

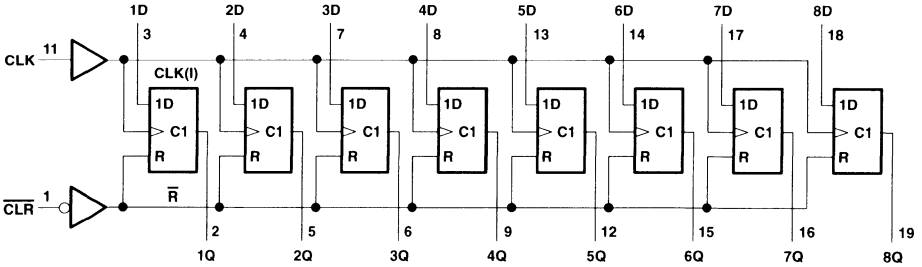
INPUTS			OUTPUT
$\overline{CLR}$	CLK	D	Q
L	X	X	L
H	↑	H	H
H	↑	L	L
H	H or L	X	Q_0

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH273 ..... 96 mA
SN74LVTH273 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH273 ..... 48 mA
SN74LVTH273 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DW package ..... 97°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH273		SN74LVTH273		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH273			SN74LVTH273			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
ΔI_{CC}‡		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

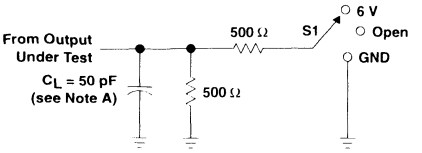
			SN54LVTH273				SN74LVTH273				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150			0	150			MHz
t_w	Pulse duration		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time	Data high or low before CLK↑	2.3		2.7		2.3		2.7		ns
		$\overline{CLR}$ high before CLK↑	2.3		2.7		2.3		2.7		
t_h	Hold time, data high or low after CLK↑		0		0		0		0		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH273				SN74LVTH273				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
f_{max}			150				150				MHz
t_{PLH}	CLK	Any Q	1.6	5		5.6	1.7	3.2	4.9	5.5	ns
t_{PHL}			1.8	4.9		5.2	1.9	3.2	4.8	5.1	
t_{PHL}	$\overline{CLR}$	Any Q	1.5	4.4		4.8	1.6	2.7	4.3	4.7	ns

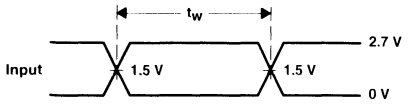
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

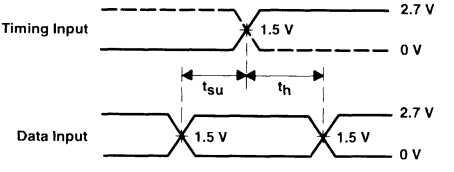


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

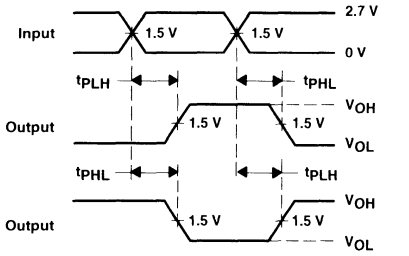
LOAD CIRCUIT



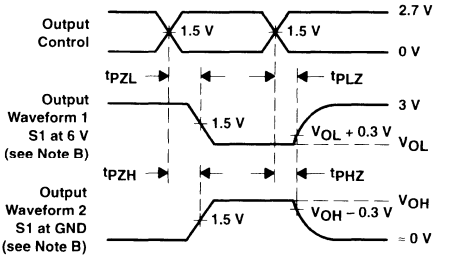
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



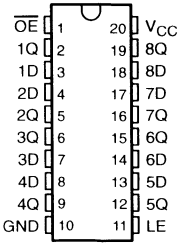
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

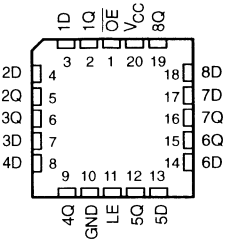
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (J) DIPs**

SN54LVTH373 . . . J OR W PACKAGE
SN74LVTH373 . . . DB, DGV, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH373 . . . FK PACKAGE
(TOP VIEW)



description

These octal latches are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

description (continued)

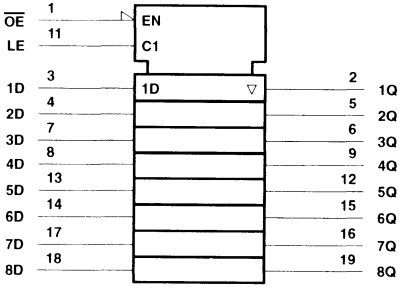
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVTH373 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH373 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each latch)

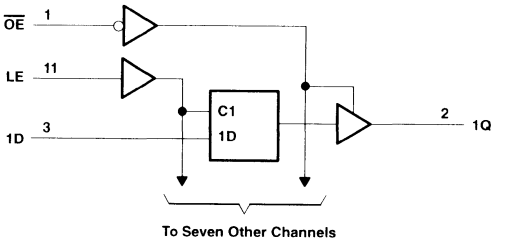
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH373 ..... 96 mA
SN74LVTH373 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH373 ..... 48 mA
SN74LVTH373 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DGV package ..... 146°C/W
DW package ..... 97°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH373		SN74LVTH373		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		µs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH373			SN74LVTH373			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

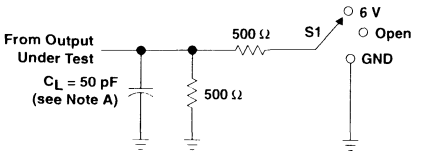
		SN54LVTH373				SN74LVTH373				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3		3		3		3		ns
t_{su}	Setup time, data before LE↓	1.1		0.4		1.1		0.4		ns
t_h	Hold time, data after LE↓	1.7		2		1.4		1.4		ns

switching characteristics over recommended free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH373				SN74LVTH373				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	D	Q	1.4	4.1		4.7	1.5	2.6	3.9		4.5	ns
t_{PHL}			1.4	4.1		4.7	1.5	2.6	3.9		4.5	
t_{PLH}	LE	Q	1.6	4.4		5.1	1.7	2.7	4.2		4.9	ns
t_{PHL}			1.6	4.4		5.1	1.7	2.7	4.2		4.9	
t_{PZH}	$\overline{OE}$	Q	1.2	5		6.1	1.3	3	4.8		5.9	ns
t_{PZL}			1.2	5		5.7	1.3	3	4.8		5.5	
t_{PHZ}	$\overline{OE}$	Q	1.8	4.8		5.1	1.9	3	4.6		4.9	ns
t_{PLZ}			1.8	4.8		4.9	1.9	3	4.5		4.6	

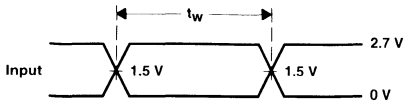
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PAR564.ER MEASUREMENT INFORMATION

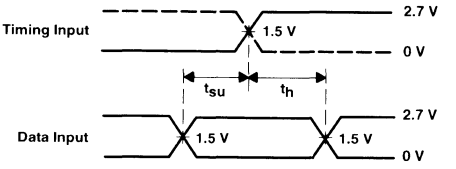


LOAD CIRCUIT

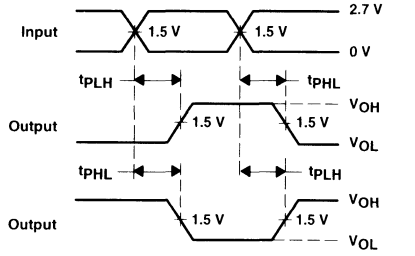
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



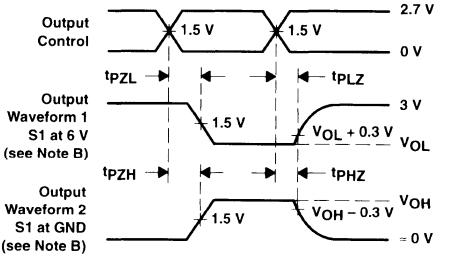
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



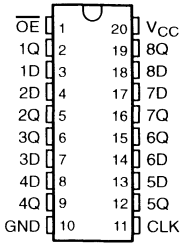
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

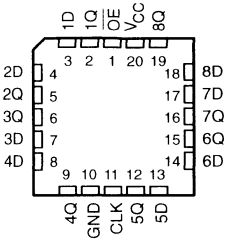
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (J) DIPs**

SN54LVTH374 . . . J OR W PACKAGE
SN74LVTH374 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH374 . . . FK PACKAGE
(TOP VIEW)



description

These octal flip-flops are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The eight flip-flops of the 'LVTH374 devices are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

description (continued)

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

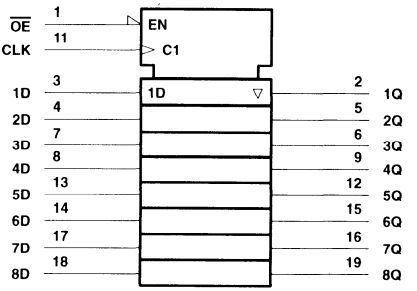
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVTH374 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

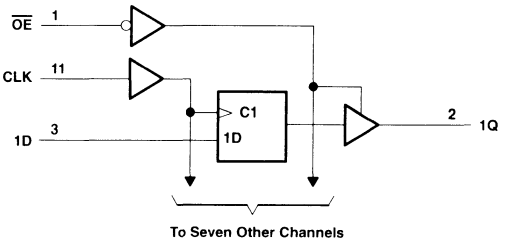
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH374 . . . . . 96 mA
SN74LVTH374 . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH374 . . . . . 48 mA
SN74LVTH374 . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

		SN54LVTH374		SN74LVTH374		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
V_I	Input voltage		5.5		5.5	V
I_{OH}	High-level output current		–24		–32	mA
I_{OL}	Low-level output current		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate	200		200		μs/V
T_A	Operating free-air temperature	–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH374			SN74LVTH374			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 μA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 μA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	μA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	μA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

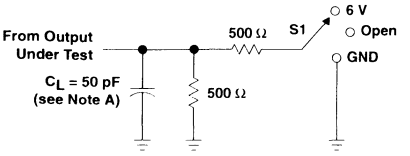
		SN54LVTH374				SN74LVTH374				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		150		150		150		150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.6		2		1.5		2		ns
t_h	Hold time, data after CLK↑	0.8		0.5		0.8		0		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH374				SN74LVTH374					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		150		150			150		MHz
t_{PLH}	CLK	Q	1.7	4.7		5.3	1.8	2.9	4.5		5	ns
t_{PHL}			1.7	4.5		4.6	1.8	2.9	4.2		4.3	
t_{PZH}	$\overline{OE}$	Q	1.2	4.9		5.7	1.3	2.8	4.7		5.6	ns
t_{PZL}			1.5	4.8		5.4	1.6	3	4.7		5.2	
t_{PHZ}	$\overline{OE}$	Q	1.8	4.8		5	1.9	3	4.6		4.9	ns
t_{PLZ}			1.9	4.9		5	2	3.1	4.5		4.6	

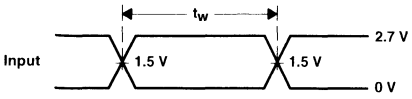
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

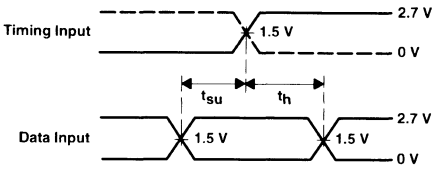


LOAD CIRCUIT

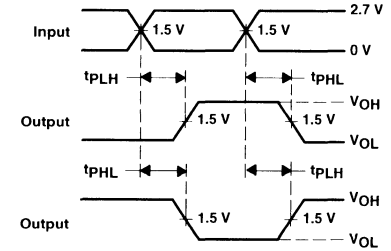
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



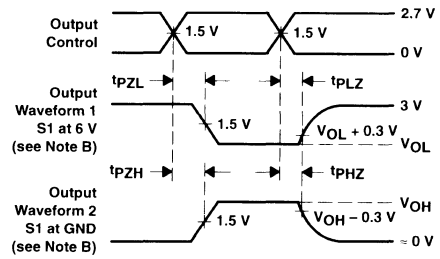
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



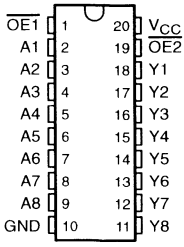
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

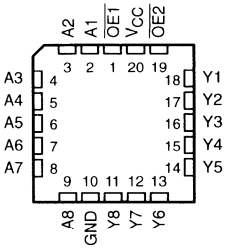
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (J) DIPs**

SN54LVTH540 . . . J OR W PACKAGE
SN74LVTH540 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH540 . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH540 devices are ideal for driving bus lines or buffer memory address registers. These devices feature inputs and outputs on opposite sides of the package that facilitate printed circuit board layout.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

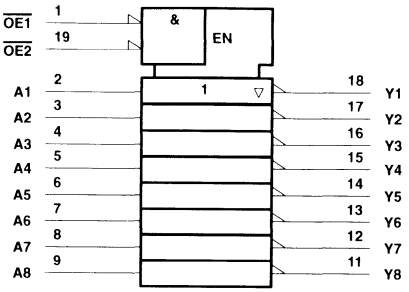
The SN54LVTH540 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH540 is characterized for operation from –40°C to 85°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

FUNCTION TABLE

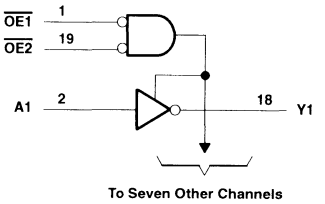
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH540 . . . . . 96 mA
SN74LVTH540 . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH540 . . . . . 48 mA
SN74LVTH540 . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

		SN54LVTH540		SN74LVTH540		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
V_I	Input voltage		5.5		5.5	V
I_{OH}	High-level output current		–24		–32	mA
I_{OL}	Low-level output current		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate	200		200		µs/V
T_A	Operating free-air temperature	–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH540			SN74LVTH540			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

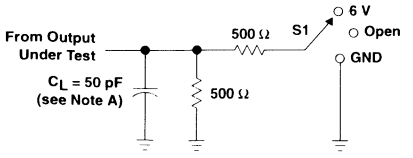
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH540				SN74LVTH540				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	3.9		4.7	1.1	2.4	3.8	4.6	ns
t_{PHL}			1	3.9		4.7	1.1	2.7	3.8	4.6	
t_{PZH}	$\overline{OE1}$ or $\overline{OE2}$	Y	1.4	5.3		6.3	1.5	3.4	5.2	6.2	ns
t_{PZL}			1.4	5.5		6.1	1.5	3.7	5.3	5.9	
t_{PHZ}	$\overline{OE1}$ or $\overline{OE2}$	Y	1.4	5.9		6.2	1.5	3.9	5.6	5.9	ns
t_{PLZ}			1.4	5.5		5.8	1.5	3.5	5	5.3	

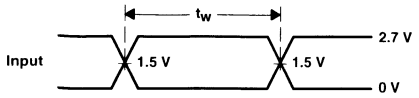
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

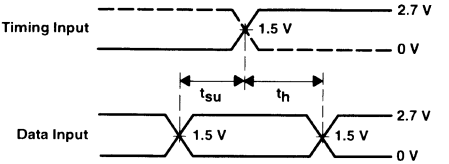


LOAD CIRCUIT

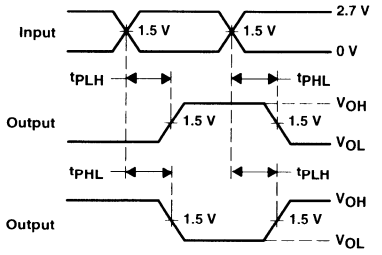
TEST	S1
t_{PHL}/t_{PLH}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



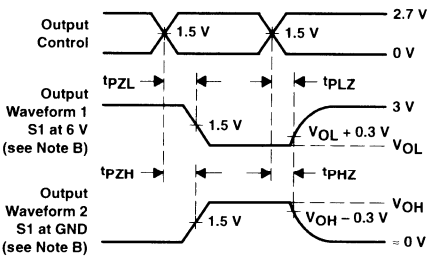
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



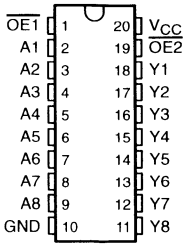
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

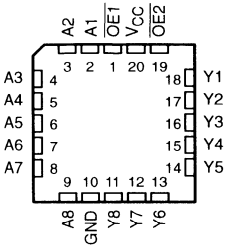
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (J) DIPs

SN54LVTH541 . . . J OR W PACKAGE
SN74LVTH541 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH541 . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH541 devices are ideal for driving bus lines or buffer memory address registers. These devices feature inputs and outputs on opposite sides of the package that facilitate printed circuit board layout.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

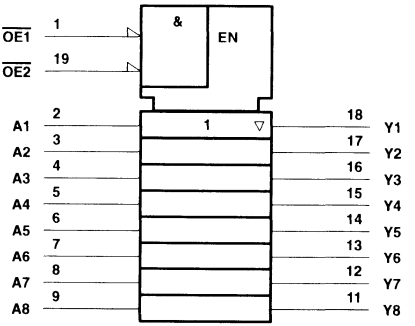
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH541 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH541 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

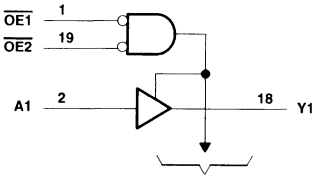
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH541 . . . . . 96 mA
SN74LVTH541 . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH541 . . . . . 48 mA
SN74LVTH541 . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

		SN54LVTH541		SN74LVTH541		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
V_I	Input voltage		5.5		5.5	V
I_{OH}	High-level output current		–24		–32	mA
I_{OL}	Low-level output current		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate	200		200		µs/V
T_A	Operating free-air temperature	–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH541			SN74LVTH541			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

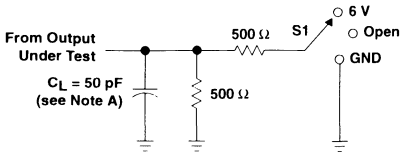
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH541				SN74LVTH541					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A	Y	1	3.7		4	1.1	2.4	3.5		3.9	ns
t_{PHL}			1	3.7		4	1.1	2.4	3.5		3.9	
t_{PZH}	$\overline{OE1}$ or $\overline{OE2}$	Y	1.4	5.3		6.3	1.5	3.5	5.2		6.2	ns
t_{PZL}			1.4	5.4		6	1.5	3.7	5.3		5.9	
t_{PHZ}	$\overline{OE1}$ or $\overline{OE2}$	Y	1.4	5.8		6.1	1.5	3.9	5.6		5.9	ns
t_{PLZ}			1.4	5.4		5.7	1.5	3	5		5.3	

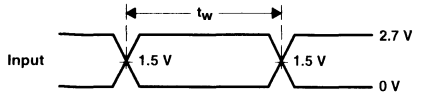
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

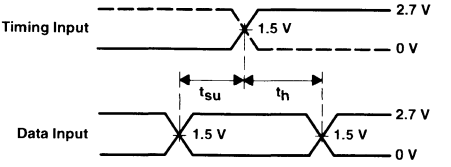


LOAD CIRCUIT

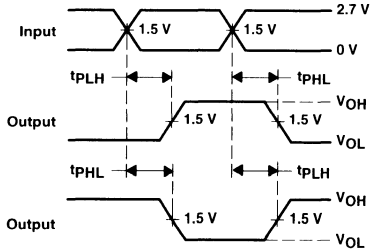
TEST	S1
t_{PHL}/t_{PLH}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



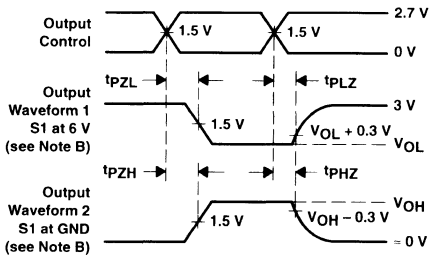
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



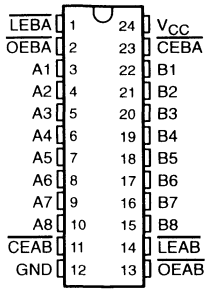
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

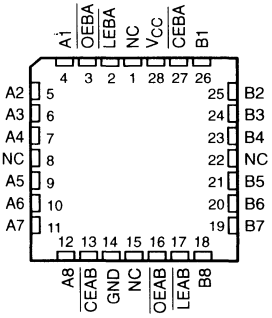
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (JT) DIPs**

SN54LVTH543 . . . JT OR W PACKAGE
SN74LVTH543 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH543 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These octal transceivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH543 contain two sets of D-type latches for temporary storage of data flowing in either direction. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ puts the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar, but requires using the $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$ inputs.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

description (continued)

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

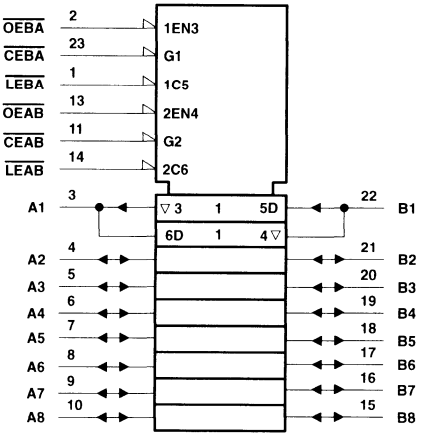
The SN54LVTH543 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH543 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	$B_0^{\ddagger}$
L	L	L	L	L
L	L	L	H	H

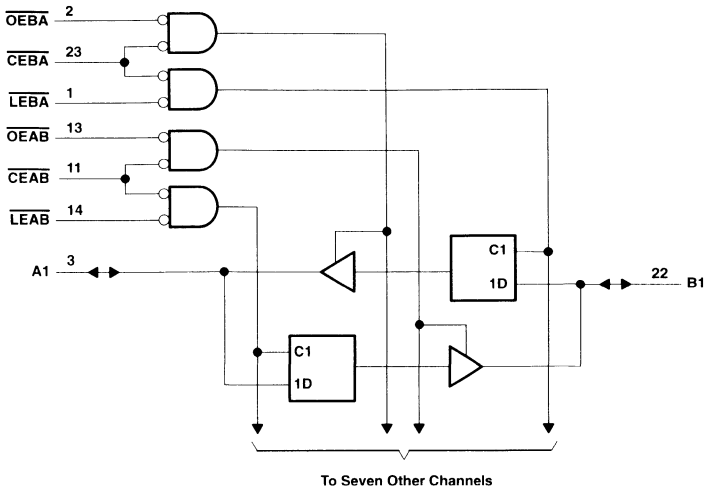
† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, PW, and W packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH543 ..... 96 mA
SN74LVTH543 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH543 ..... 48 mA
SN74LVTH543 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 104°C/W
DW package ..... 81°C/W
PW package ..... 120°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH543		SN74LVTH543		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTH543			SN74LVTH543			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,		I_I = –18 mA			–1.2			–1.2	V
V_{OH}	V_{CC} = 2.7 V to 3.6 V,		I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,		I_{OH} = –8 mA	2.4			2.4			
	V_{CC} = 3 V		I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}	V_{CC} = 2.7 V		I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
	V_{CC} = 3 V		I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZPU}§	V_{CC} = 0 to 1.5 V, V_O = 0.5 to 3 V, $\overline{OE}$ = don't care					±100			±100	µA
I_{OZPD}§	V_{CC} = 1.5 V to 0, V_O = 0.5 to 3 V, $\overline{OE}$ = don't care					±100			±100	µA
I_{CC}	V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND		Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND					0.2			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				9			9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused terminals at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

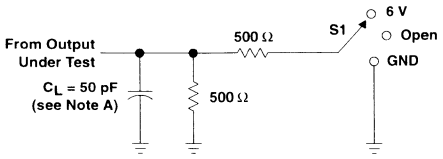
				SN54LVTH543				SN74LVTH543				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration,	$\overline{LEAB}$ or $\overline{LEBA}$ low		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time	A or B before $\overline{LEAB}$ or $\overline{LEBA}\uparrow$	Data high	0.4		0.4		0.4		0.4		ns
			Data low	1		1.5		1		1.5		
		A or B before $\overline{CEAB}$ or $\overline{CEBA}\uparrow$	Data high	0.2		0.2		0.2		0.2		
			Data low	0.7		1.2		0.7		1.2		
t_h	Hold time	A or B after $\overline{LEAB}$ or $\overline{LEBA}\uparrow$	Data high	1.5		0.6		1.5		0.6		ns
			Data low	1.3		1.5		1.3		1.5		
		A or B after $\overline{CEAB}$ or $\overline{CEBA}\uparrow$	Data high	1.6		0.5		1.6		0.5		
			Data low	1.4		1.6		1.4		1.6		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH543				SN74LVTH543				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1.2	3.9	4.5		1.3	2.5	3.7	4.3		ns
t_{PHL}			1.2	3.9	4.5		1.3	2.5	3.7	4.3		
t_{PLH}	$\overline{LE}$	A or B	1.2	5.1	6.1		1.3	2.9	4.7	5.9		ns
t_{PHL}			1.2	5.1	6.1		1.3	2.9	4.7	5.9		
t_{PZH}	$\overline{OE}$	A or B	1	5.1	6.4		1.1	2.9	4.9	6.2		ns
t_{PZL}			1	5.1	6.4		1.1	3.2	4.9	6.2		
t_{PHZ}	$\overline{OE}$	A or B	1.9	5.6	6.2		2	3.4	5.3	5.9		ns
t_{PLZ}			1.9	5.6	6.2		2	3.7	5.3	5.9		
t_{PZH}	$\overline{CE}$	A or B	1.2	5.5	7		1.3	3.2	5.3	6.8		ns
t_{PZL}			1.2	5.5	7		1.3	3.5	5.3	6.8		
t_{PHZ}	$\overline{CE}$	A or B	2.2	5.7	6.2		2.3	3.8	5.4	5.9		ns
t_{PLZ}			2.2	5.7	5.9		2.3	3.9	5.4	5.6		

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION



LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
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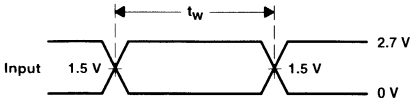
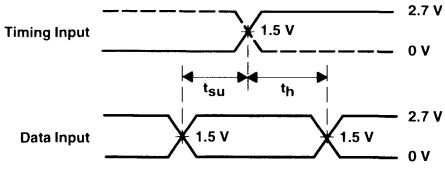
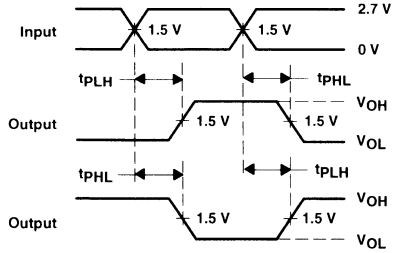


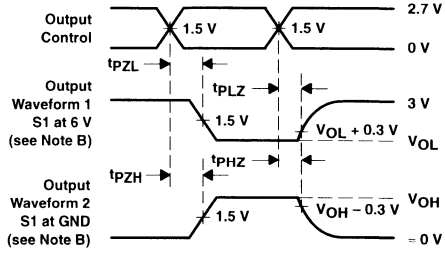
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
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LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 n
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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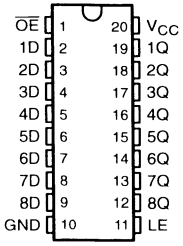
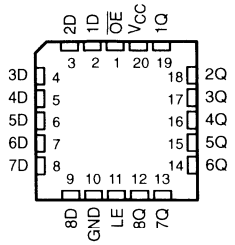
SN54LVTH573 . . . J OR W PACKAGE
SN74LVTH573 . . . DB, DGV, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH573 . . . FK PACKAGE
(TOP VIEW)



description

These octal latches are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The eight latches of the 'LVTH573 are transparent D-type latches. While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

description (continued)

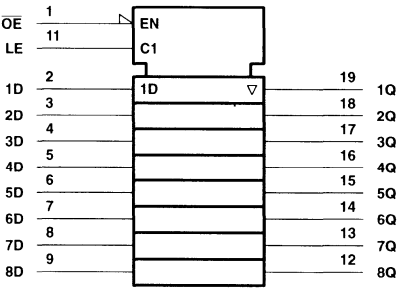
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH573 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH573 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each latch)

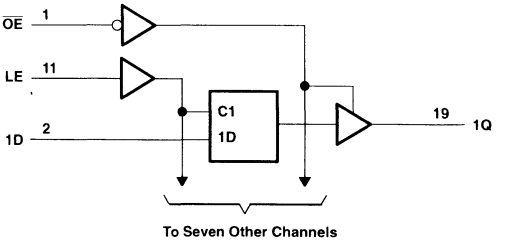
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH573 . . . . . 96 mA
SN74LVTH573 . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH573 . . . . . 48 mA
SN74LVTH573 . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DGV package . . . . . 146°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH573		SN74LVTH573		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH573			SN74LVTH573			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

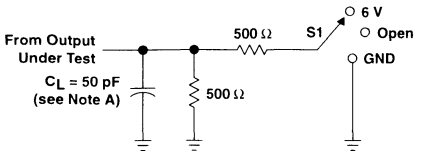
		SN54LVTH573				SN74LVTH573				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3		3		3		3		ns
t_{su}	Setup time, data before LE↓	0.7		0.6		0.7		0.6		ns
t_h	Hold time, data after LE↓	1.5		1.7		1.5		1.7		ns

switching characteristics over recommended free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH573				SN74LVTH573					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	D	Q	1.4	4.1		4.7	1.5	2.6	3.9		4.5	ns
t_{PHL}			1.4	4.1		4.7	1.5	2.9	3.9		4.5	
t_{PLH}	LE	Q	1.8	4.4		5.1	1.9	2.9	4.2		4.9	ns
t_{PHL}			1.8	4.4		5.1	1.9	2.9	4.2		4.9	
t_{PZH}	$\overline{OE}$	Q	1.4	5.2		6	1.5	3.2	5.1		5.9	ns
t_{PZL}			1.4	5.2		6	1.5	3.9	5.1		5.9	
t_{PHZ}	$\overline{OE}$	Q	1.9	5.1		5.7	2	3.5	4.9		5.5	ns
t_{PLZ}			1.9	4.9		5.2	2	3.2	4.6		4.9	

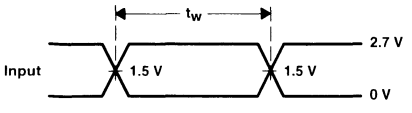
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

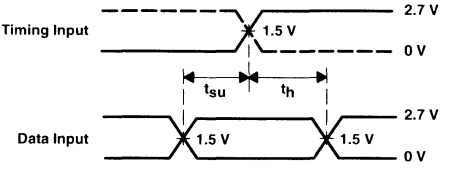


LOAD CIRCUIT

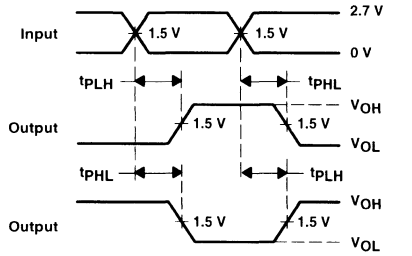
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



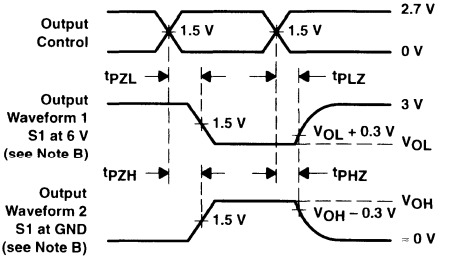
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



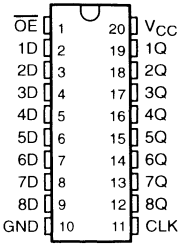
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

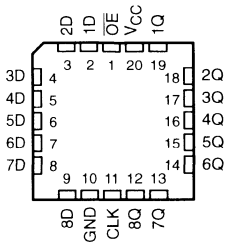
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (J) DIPs**

SN54LVTH574 . . . J OR W PACKAGE
SN74LVTH574 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH574 . . . FK PACKAGE
(TOP VIEW)



description

These octal flip-flops are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The eight flip-flops of the 'LVTH574 are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

description (continued)

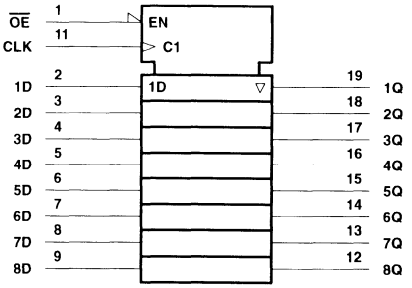
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH574 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH574 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

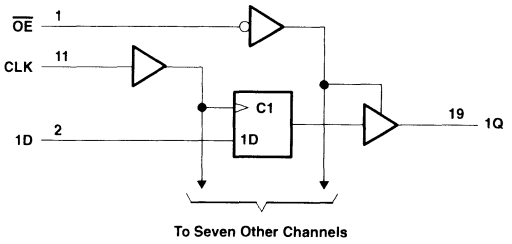
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH574 ..... 96 mA
SN74LVTH574 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH574 ..... 48 mA
SN74LVTH574 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DW package ..... 97°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH574		SN74LVTH574		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH574			SN74LVTH574			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 μA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 μA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	μA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	μA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

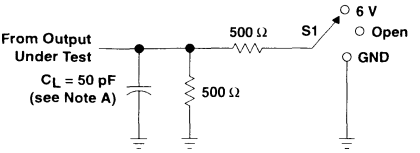
		SN54LVTH574				SN74LVTH574				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	2.1		2.5		2		2.4		ns
t_h	Hold time, data after CLK↑	0.3		0		0.3		0		ns

switching characteristics over recommended free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH574				SN74LVTH574					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		150		150			150		MHz
t_{PLH}	CLK	Q	1.7	4.9		5.5	1.8	3	4.5		5.3	ns
t_{PHL}			1.7	4.9		5.5	1.8	3	4.5		5.3	
t_{PZH}	$\overline{OE}$	Q	1.4	5		6.1	1.5	3.2	4.8		5.9	ns
t_{PZL}			1.4	5		6.1	1.5	3.5	4.8		5.9	
t_{PHZ}	$\overline{OE}$	Q	1.9	5		5.3	2	3.5	4.8		5.1	ns
t_{PLZ}			1.9	4.7		4.7	2	3.2	4.4		4.4	

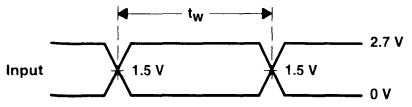
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

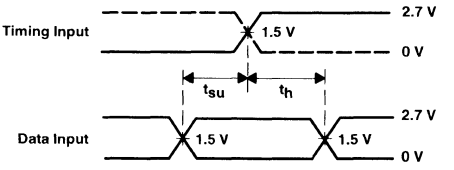


LOAD CIRCUIT

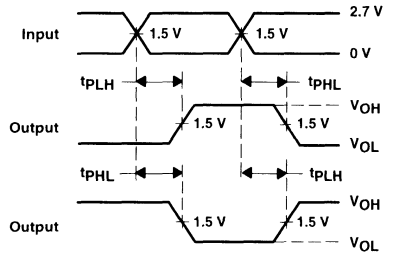
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



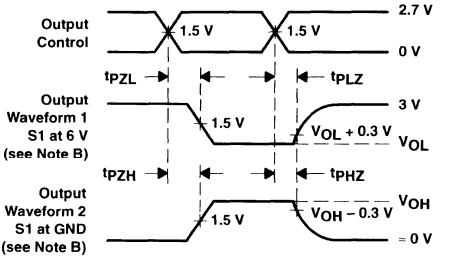
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



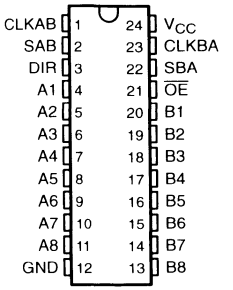
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

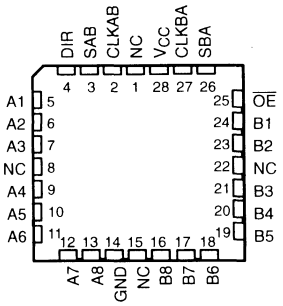
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (JT) DIPs**

SN54LVTH646 . . . JT OR W PACKAGE
SN74LVTH646 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH646 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These bus transceivers and registers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH646 consist of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'LVTH646.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs are provided to control the transceiver functions. In the transceiver mode, data present at the high-impedance port can be stored in either register or in both.

The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The direction control (DIR) determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data can be stored in one register and/or B data can be stored in the other register.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

description (continued)

When an output function is disabled, the input function is still enabled and can be used to store and transmit data. Only one of the two buses, A or B, can be driven at a time.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

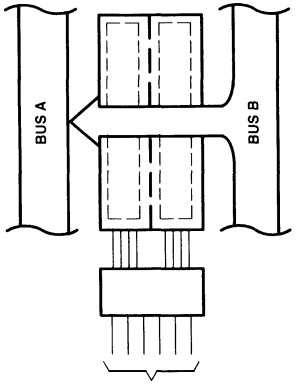
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH646 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH646 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

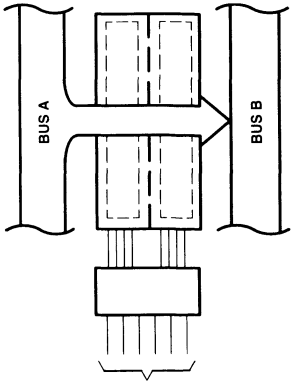
INPUTS						DATA I/Os		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

† The data-output functions can be enabled or disabled by various signals at $\overline{OE}$ and DIR. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.



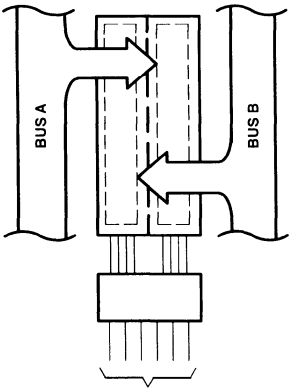
21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER BUS B TO BUS A



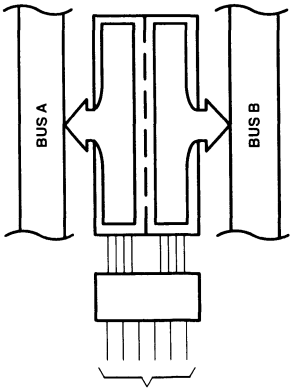
21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER BUS A TO BUS B



21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM A, B, OR A AND B



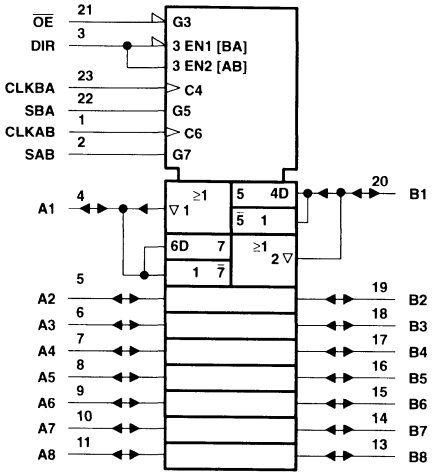
21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA TO A AND/OR B

Pin numbers shown are for the DB, DW, JT, PW, and W packages.

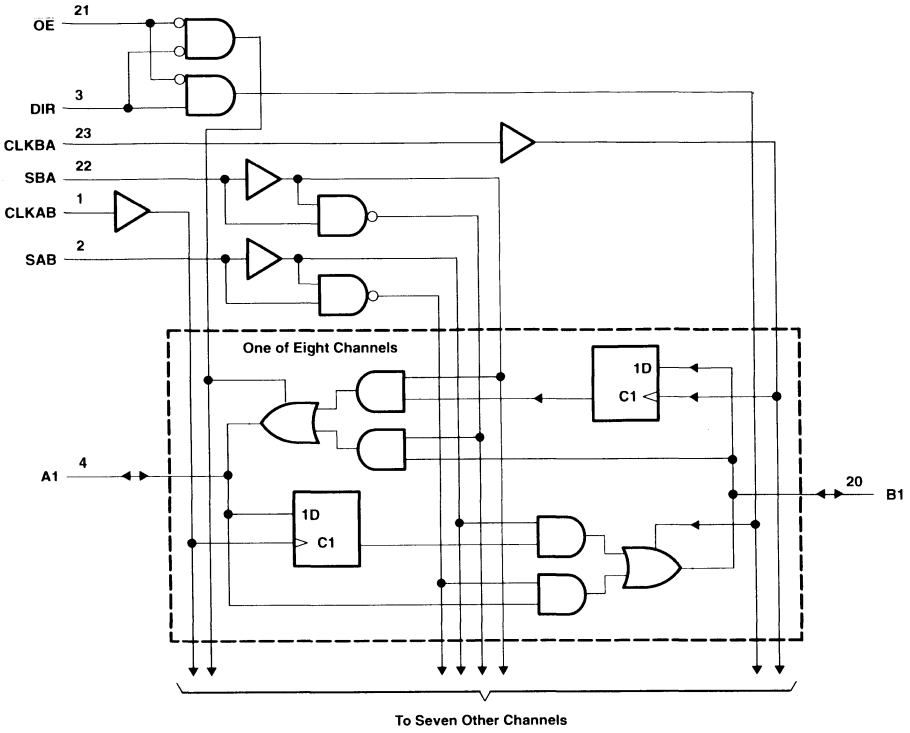
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, PW, and W packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH646 ..... 96 mA
SN74LVTH646 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH646 ..... 48 mA
SN74LVTH646 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 104°C/W
DW package ..... 81°C/W
PW package ..... 120°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH646		SN74LVTH646		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH646			SN74LVTH646			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			9			9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused terminals at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

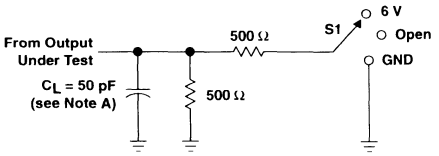
			SN54LVTH646				SN74LVTH646				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high	1.3		1.6		1.2		1.5		ns
		Data low	1.9		2.6		1.6		2.2		
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑		1.2		1.2		0.8		0.8		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH646				SN74LVTH646					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		150		150			150		MHz
t_{PLH}	CLKBA or CLKAB	A or B	1.7	5		5.9	1.8	3.1	4.7		5.6	ns
t_{PHL}			1.7	5		5.9	1.8	3.1	4.7		5.6	
t_{PLH}	A or B	B or A	1.2	3.7		4.3	1.3	2.3	3.5		4.1	ns
t_{PHL}			1.2	3.7		4.3	1.3	2.4	3.5		4.1	
t_{PLH}	SBA or SAB‡	A or B	1.4	5.2		6.3	1.5	3	4.9		6	ns
t_{PHL}			1.4	5.2		6.3	1.5	3.3	4.9		6	
t_{PZH}	$\overline{OE}$	A or B	1	5.4		6.7	1.1	3.1	5.2		6.5	ns
t_{PZL}			1	5.4		6.7	1.1	3.4	5.2		6.5	
t_{PHZ}	$\overline{OE}$	A or B	2.2	5.9		6.5	2.3	3.9	5.5		6.1	ns
t_{PLZ}			2.2	5.9		6.3	2.3	4	5.5		5.9	
t_{PZH}	DIR	A or B	1.2	5.5		6.8	1.3	3.4	5.2		6.6	ns
t_{PZL}			1.2	5.5		6.8	1.3	3.6	5.2		6.6	
t_{PHZ}	DIR	A or B	1.4	5.8		6.9	1.5	3.2	5.6		6.7	ns
t_{PLZ}			1.4	5.9		6.6	1.5	3.8	5.6		6.3	

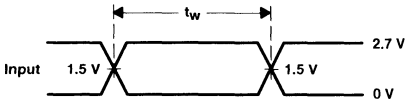
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ These parameters are measured with the internal output state of the storage register opposite that of the bus input.

PARAMETER MEASUREMENT INFORMATION

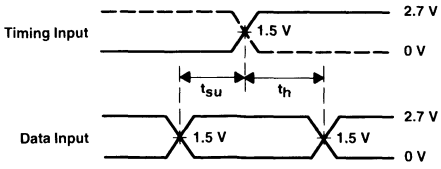


LOAD CIRCUIT

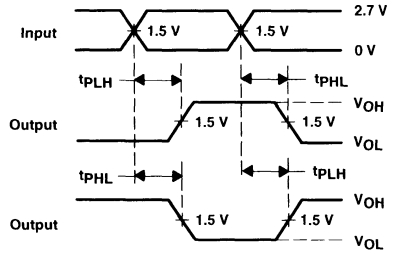
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



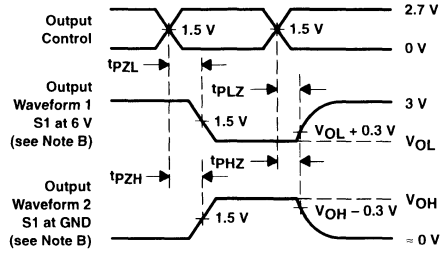
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



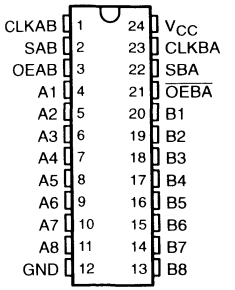
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 r
D. The outputs are measured one at a time with one transition per measurement.

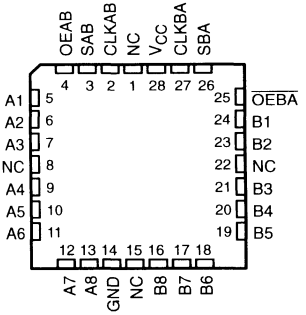
Figure 2. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (JT) DIPs**

SN54LVTH652 . . . JT OR W PACKAGE
SN74LVTH652 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH652 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These bus transceivers and registers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH652 consist of bus-transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers.

Output-enable (OEAB and $\overline{\text{OEBA}}$) inputs are provided to control the transceiver functions. Select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between real-time and stored data. A low input selects real-time data and a high input selects stored data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'LVTH652.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

description (continued)

Data on the A or B data bus, or both, can be stored in the internal D-type flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs, regardless of the select- or enable-control pins. When SAB and SBA are in the real-time transfer mode, it is possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{\text{OEBA}}$. In this configuration, each output reinforces its input; therefore, when all other data sources to the two sets of bus lines are at high impedance, each set of bus lines remains at its last state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

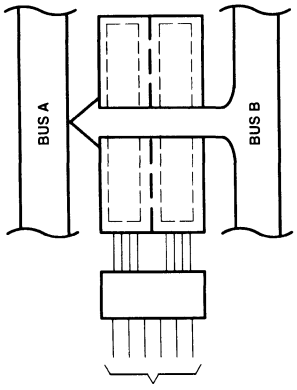
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

The SN54LVTH652 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH652 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

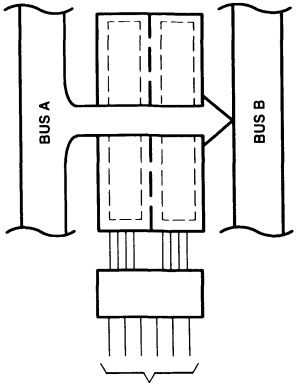
INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

† The data-output functions can be enabled or disabled by a variety of level combinations at OEAB or $\overline{\text{OEBA}}$. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.
‡ Select control = L; clocks can occur simultaneously
Select control = H; clocks must be staggered to load both registers



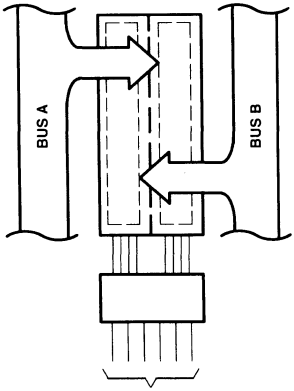
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER BUS B TO BUS A



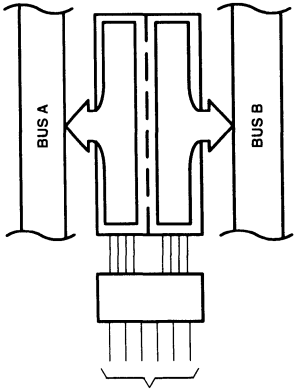
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER BUS A TO BUS B



3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM A, B, OR A AND B



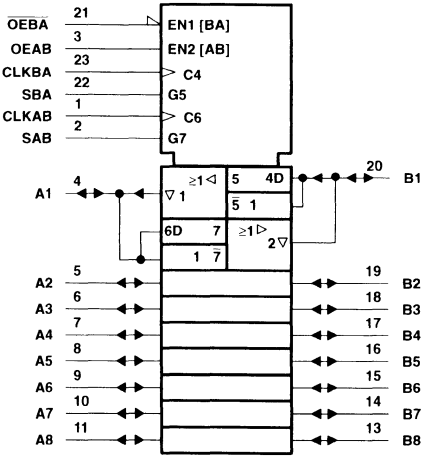
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	L	H or L	H or L	H	H

TRANSFER STORED DATA TO A AND/OR B

Pin numbers shown are for the DB, DW, JT, PW, and W packages.

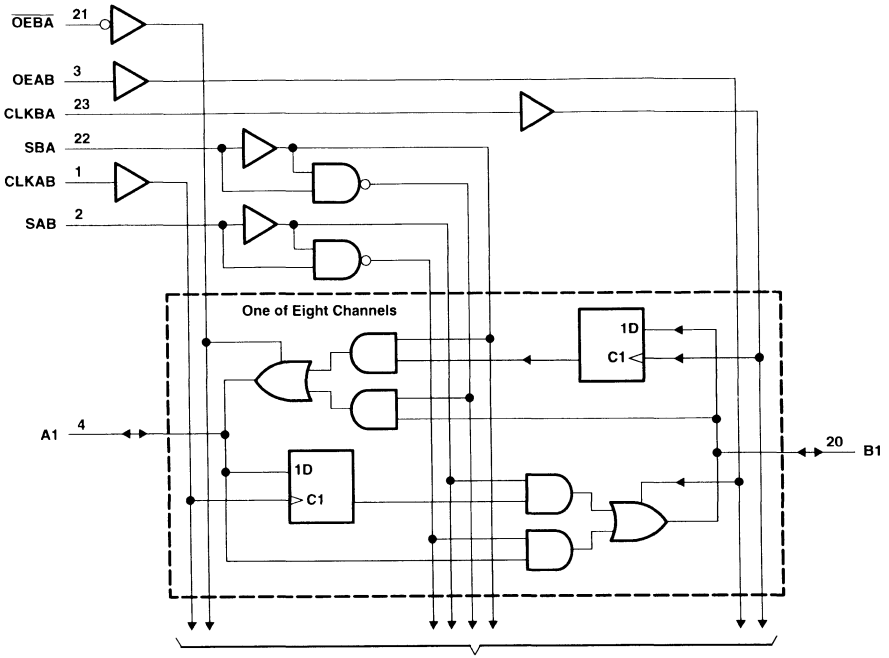
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, PW, and W packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH652 ..... 96 mA
SN74LVTH652 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH652 ..... 48 mA
SN74LVTH652 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 104°C/W
DW package ..... 81°C/W
PW package ..... 120°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH652		SN74LVTH652		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTH652			SN74LVTH652			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,		I_I = –18 mA			–1.2			–1.2	V
V_{OH}	V_{CC} = 2.7 V to 3.6 V,		I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,		I_{OH} = –8 mA	2.4			2.4			
	V_{CC} = 3 V		I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}	V_{CC} = 2.7 V		I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
	V_{CC} = 3 V		I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZPU}§	V_{CC} = 0 to 1.5 V, V_O = 0.5 to 3 V, OE/$\overline{OE}$ = don't care					±100			±100	µA
I_{OZPD}§	V_{CC} = 1.5 V to 0, V_O = 0.5 to 3 V, OE/$\overline{OE}$ = don't care					±100			±100	µA
I_{CC}	V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND		Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND					0.2			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				9			9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused terminals at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

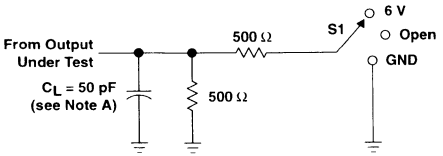
			SN54LVTH652				SN74LVTH652				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high	1.3		1.6		1.2		1.5		ns
		Data low	1.9		2.6		1.6		2.2		
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑		1.2		1.2		0.8		0.8		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH652				SN74LVTH652					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		150		150			150		MHz
t_{PLH}	CLKBA or CLKAB	A or B	1.7	5	5.9		1.8	3.1	4.7	5.6		ns
t_{PHL}			1.7	5	5.9		1.8	3.1	4.7	5.6		
t_{PLH}	A or B	B or A	1.2	3.7	4.3		1.3	2.3	3.5	4.1		ns
t_{PHL}			1.2	3.7	4.3		1.3	2.4	3.5	4.1		
t_{PLH}	SBA or SAB‡	A or B	1.4	5.2	6.3		1.5	3.1	4.9	6		ns
t_{PHL}			1.4	5.2	6.3		1.5	3.4	4.9	6		
t_{PZH}	$\overline{OEBA}$	A	1	5.4	6.7		1.1	2.9	5.2	6.5		ns
t_{PZL}			1	5.4	6.7		1.1	3.1	5.2	6.5		
t_{PHZ}	$\overline{OEBA}$	A	2.2	5.9	6.5		2.3	3.5	5.5	6.1		ns
t_{PLZ}			2.2	5.9	6.3		2.3	3.7	5.5	5.9		
t_{PZH}	OEAB	B	1.2	4.9	5.9		1.3	3	4.7	5.7		ns
t_{PZL}			1.2	4.9	5.9		1.3	3.3	4.7	5.7		
t_{PHZ}	OEAB	B	1.4	5.8	7		1.5	3.6	5.6	6.7		ns
t_{PLZ}			1.4	5.9	6.6		1.5	3.7	5.6	6.3		

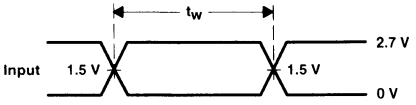
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ These parameters are measured with the internal output state of the storage register opposite that of the bus input.

PARAMETER MEASUREMENT INFORMATION

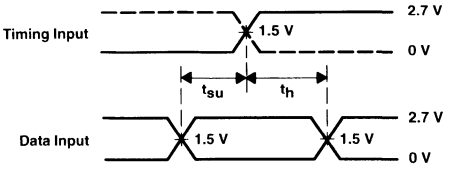


LOAD CIRCUIT

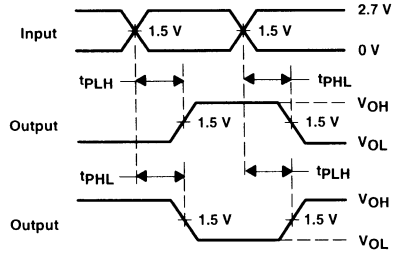
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



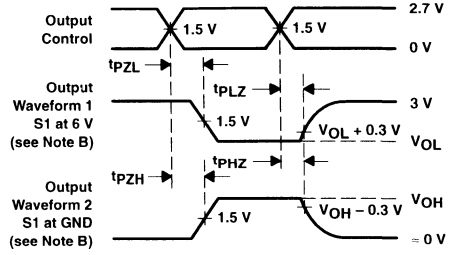
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



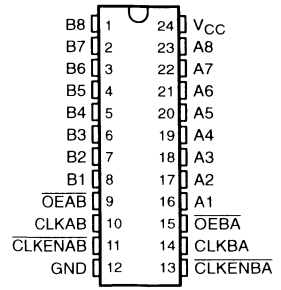
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 r
D. The outputs are measured one at a time with one transition per measurement.

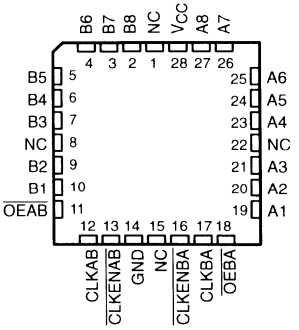
Figure 2. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Bus-Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (JT) DIPs**

SN54LVTH2952 . . . JT PACKAGE
SN74LVTH2952 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH2952 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These octal bus transceivers and registers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH2952 consist of two 8-bit back-to-back registers that store data flowing in both directions between two bidirectional buses. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input, provided that the clock-enable ($\overline{\text{CLKENAB}}$ or $\overline{\text{CLKENBA}}$) input is low. Taking the output-enable ($\overline{\text{OEAB}}$ or $\overline{\text{OEBA}}$) input low accesses the data on either port.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

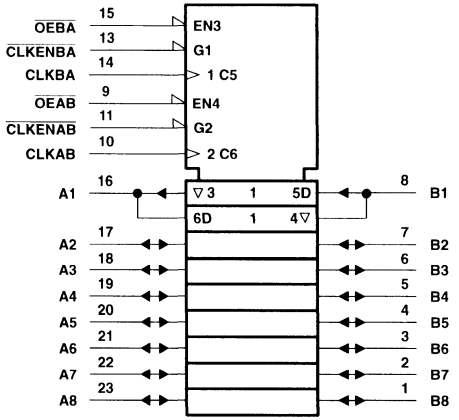
The SN54LVTH2952 is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74LVTH2952 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CLKENAB}$	CLKAB	$\overline{OEAB}$	A	B
H	X	L	X	B_0‡
X	H or L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

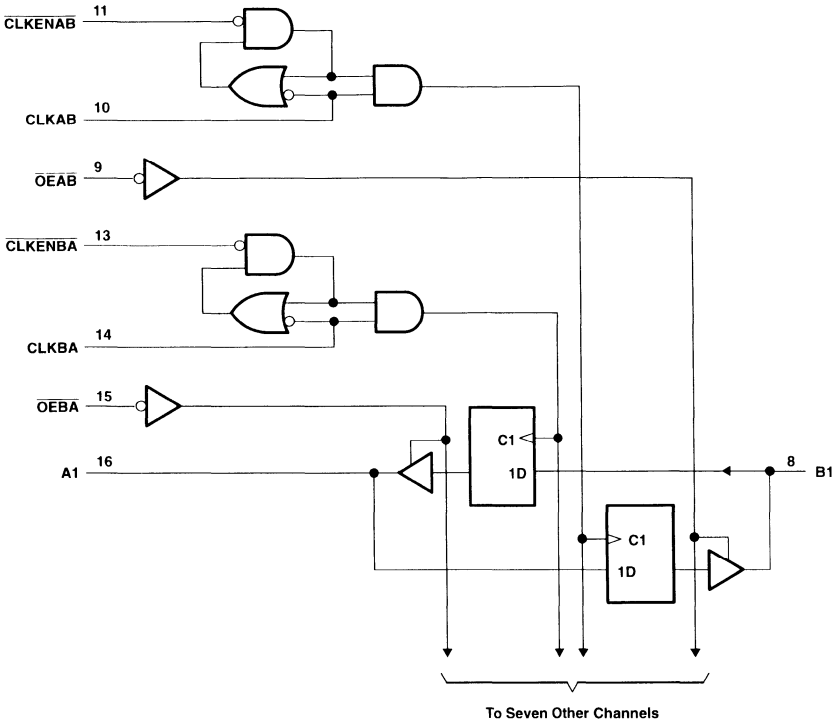
† A-to-B data flow is shown; B-to-A data flow is similar but uses $\overline{CLKENBA}$, CLKBA, and $\overline{OEBA}$.
‡ Level of B before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, and PW packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH2952 ..... 96 mA
SN74LVTH2952 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH2952 ..... 48 mA
SN74LVTH2952 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 104°C/W
DW package ..... 81°C/W
PW package ..... 120°C/W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH2952		SN74LVTH2952		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTH2952			SN74LVTH2952			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 µA		V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = − 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = − 24 mA		2						
		I_{OH} = −32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	−75			−75			
I_{OZPU}	V_{CC} = 0 to 1.5 V, $\overline{OE}$ = don't care	V_O = 0.5 V to 3 V,				±100			±100	µA
I_{OZPD}	V_{CC} = 1.5 V to 0, $\overline{OE}$ = don't care	V_O = 0.5 V to 3 V,				±100			±100	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} − 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				9			9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused terminals at V_{CC} or GND
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirement over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

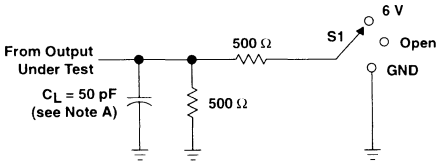
			SN54LVTH2952				SN74LVTH2952				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			150		150		150		150	MHz
t_w	Pulse duration	CLK high	3.3		3.3		3.3		3.3		ns
		CLK low	3.3		3.3		3.3		3.3		
t_{su}	Setup time, A or B before CLK↑	Data high	1.6		2.2		1.5		2.1		ns
		Data low	1.6		2.2		1.5		2.1		
	Setup time, $\overline{CE}$ before CLK↑	Data high	1.6		1.9		1.5		1.8		
		Data low	2		2.6		1.9		2.5		
t_h	Hold time, A or B after CLK↑		1		0.2		1		0.2		ns
	Hold time, $\overline{CE}$ after CLK↑		1.2		0.2		1.2		0.2		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH2952				SN74LVTH2952					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		150		150			150		MHz
t_{PLH}	CLKBA or CLKAB	A or B	1.2	4.8		5.5	1.3	2.9	4.6		5.3	ns
t_{PHL}			1.2	4.8		5.5	1.3	3.1	4.6		5.3	
t_{PZH}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	1	4.8		5.9	1.1	2.6	4.6		5.8	ns
t_{PZL}			1	4.8		5.9	1.1	3	4.6		5.8	
t_{PHZ}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	1.2	5.6		6	1.3	3.6	5.4		5.9	ns
t_{PLZ}			1.5	5.4		5.6	1.6	3.6	5.1		5.3	

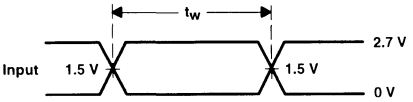
† All typical values are at T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

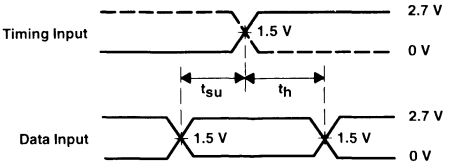


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

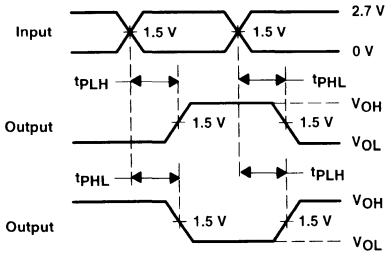
LOAD CIRCUIT FOR OUTPUTS



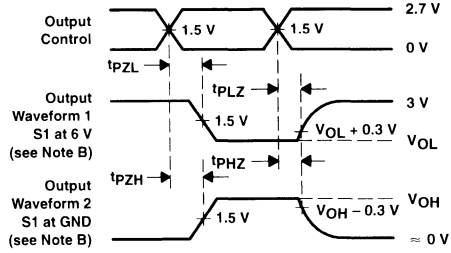
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

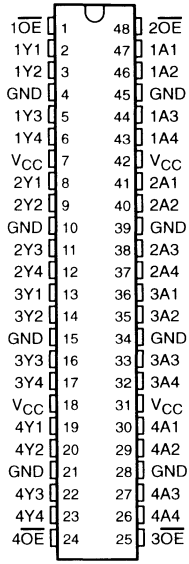
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

Contents

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16240 . . . WD PACKAGE
SN74LVTH16240 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

These 16-bit buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH16240 devices are designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. The devices provide inverting outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

description (continued)

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

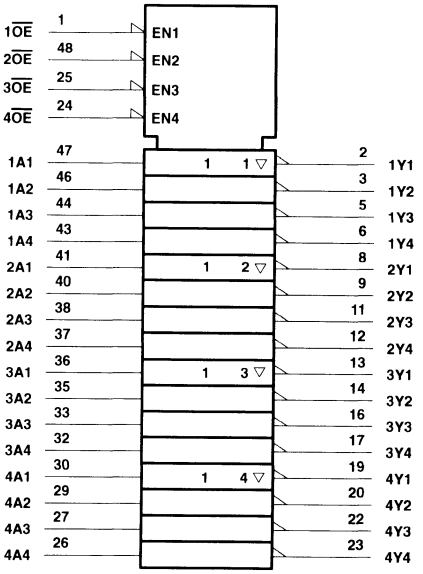
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVTH16240 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

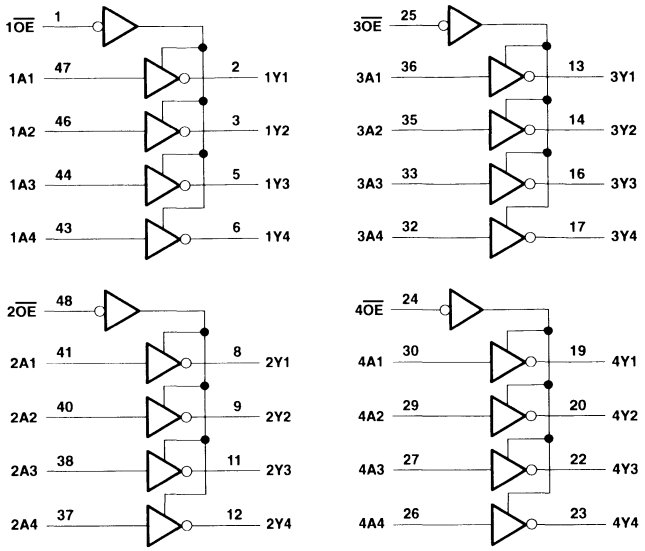
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16240 ..... 96 mA
SN74LVTH16240 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16240 ..... 48 mA
SN74LVTH16240 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16240		SN74LVTH16240		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16240			SN74LVTH16240			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			9			9		pF

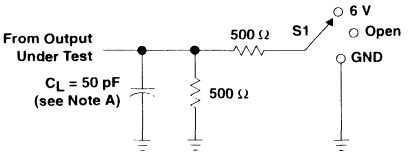
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16240				SN74LVTH16240				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	3.6		4.1	1	2.2	3.5	4	ns
t_{PHL}			1	3.6		4.1	1	2.7	3.5	4	
t_{PZH}	$\overline{OE}$	Y	1	4.2		5.1	1	2.6	4	4.9	ns
t_{PZL}			1.1	4.6		4.8	1.2	2.6	4.4	4.6	
t_{PHZ}	$\overline{OE}$	Y	1.9	4.7		5.2	2	3.4	4.5	5	ns
t_{PLZ}			1.9	4.4		4.5	2	3.2	4.2	4.2	
$t_{sk(o)}$‡									0.5	0.5	ns

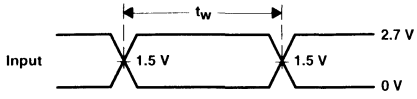
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is not production tested.

PARAMETER MEASUREMENT INFORMATION

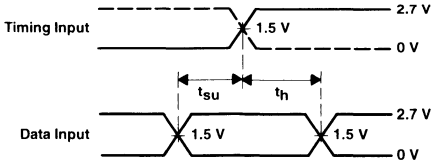


LOAD CIRCUIT

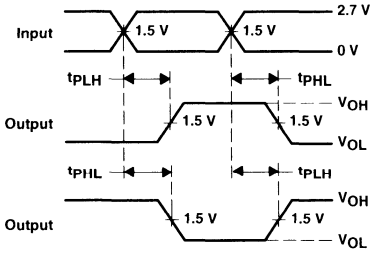
TEST	S1
t_{PHL}/t_{PLH}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



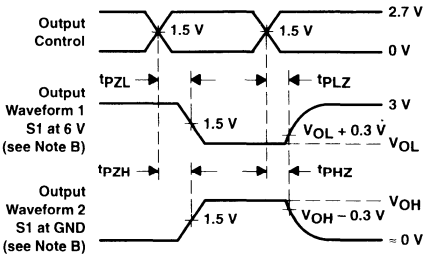
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



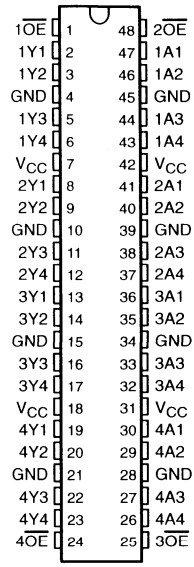
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **Outputs Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH162240 . . . WD PACKAGE
SN74LVTH162240 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH162240 devices are 16-bit buffers/drivers designed specifically for low-voltage (3.3-V) V_{CC} operation and to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. They have the capability to provide a TTL interface to a 5-V system environment.

These devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer and provide inverting outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

The outputs, which are designed to source or sink up to 12 mA, include equivalent 22-Ω series resistors to reduce overshoot and undershoot.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

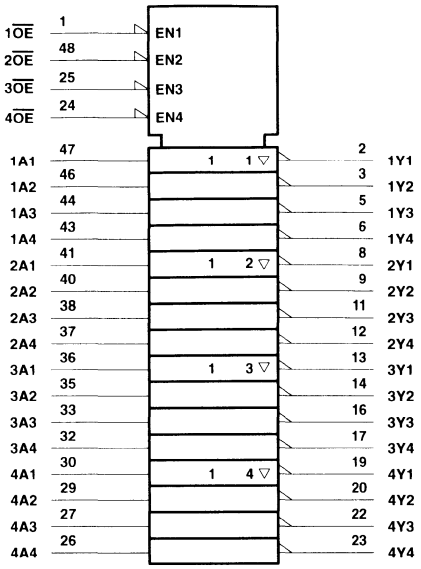
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVTH162240 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH162240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

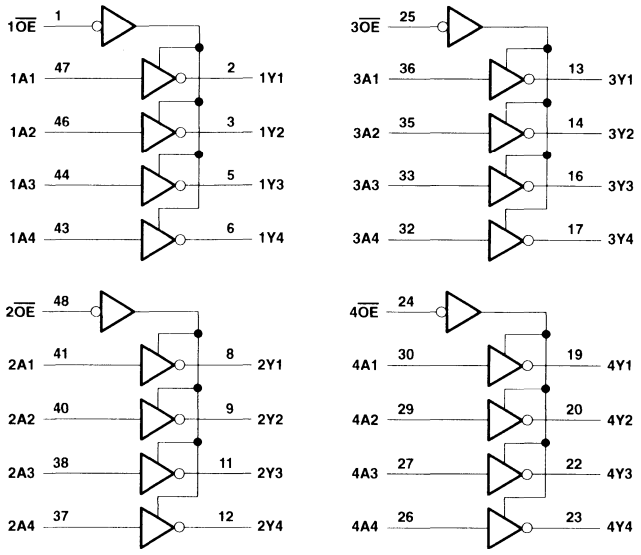
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O ..... 30 mA
Current into any output in the high state, I_O (see Note 2) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH162240		SN74LVTH162240		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–12		–12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH162240			SN74LVTH162240			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 3 V,	I_{OH} = –12 mA	2			2			V
V_{OL}		V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	V
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V			±100			±100	μA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	μA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			9			9		pF

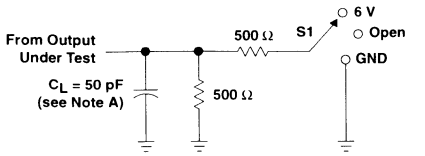
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH162240				SN74LVTH162240				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	4.2		5	1	2.5	4	4.6	ns
t_{PHL}			1	4.2		5	1	2.9	4	4.6	
t_{PZH}	$\overline{OE}$	Y	1	5		5.5	1	2.8	4.8	5.7	ns
t_{PZL}			1	4.9		5.1	1	2.8	4.7	4.9	
t_{PHZ}	$\overline{OE}$	Y	1.9	4.9		5.4	2	3.5	4.7	5.2	ns
t_{PLZ}			1.9	4.7		4.8	2	3.4	4.5	4.5	
$t_{sk(o)}$‡									0.5	0.5	ns

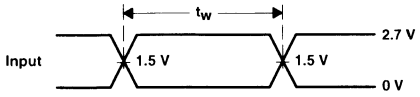
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is not production tested.

PARAMETER MEASUREMENT INFORMATION

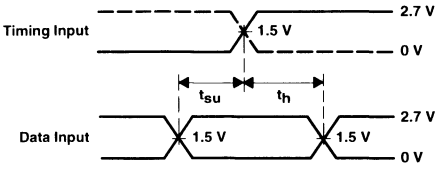


LOAD CIRCUIT

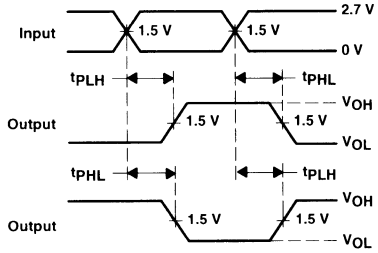
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



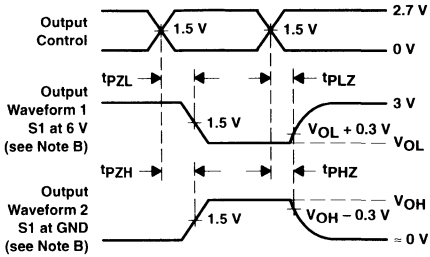
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



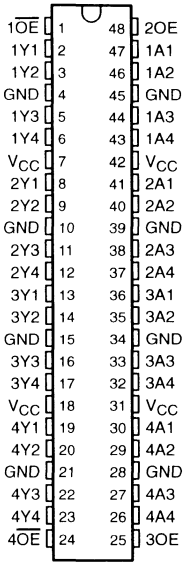
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16241 . . . WD PACKAGE
SN74LVTH16241 . . . DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

These 16-bit buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. The devices provide noninverting outputs and complementary output-enable (OE and $\overline{OE}$) inputs.

description (continued)

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

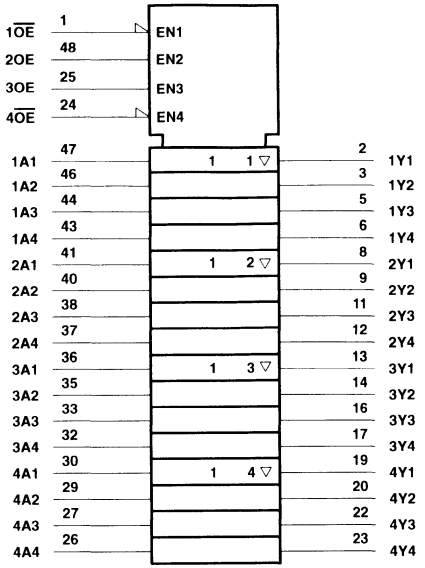
The SN54LVTH16241 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16241 is characterized for operation from –40°C to 85°C.

FUNCTION TABLES

INPUTS		OUTPUTS
$1\overline{OE}$, $4\overline{OE}$	1A, 4A	1Y, 4Y
L	H	H
L	L	L
H	X	Z

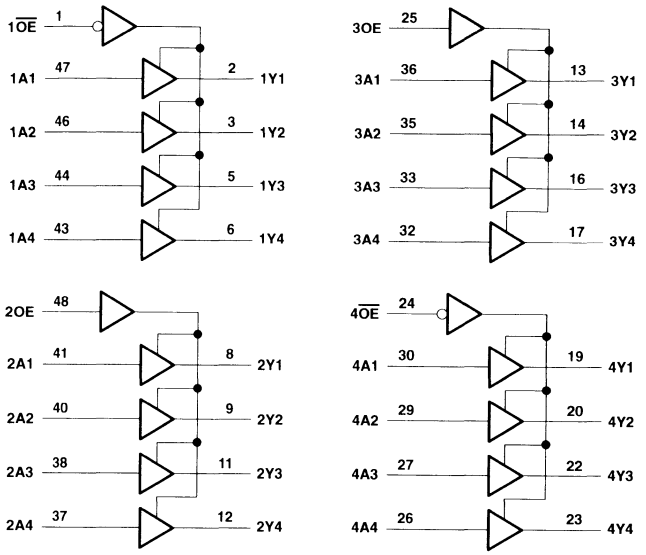
INPUTS		OUTPUTS
2OE, 3OE	2A, 3A	2Y, 3Y
H	H	H
H	L	L
L	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16241 ..... 96 mA
SN74LVTH16241 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16241 ..... 48 mA
SN74LVTH16241 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DGV package ..... 93°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16241		SN74LVTH16241		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16241			SN74LVTH16241			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 μA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 μA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V				±100			±100	μA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	μA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$/OE = don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$/OE = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			9			9		pF

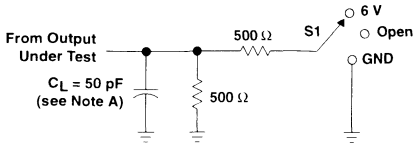
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16241				SN74LVTH16241				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1.1	3.7		4	1.2	2.6	3.5	3.8	ns
t_{PHL}			1.1	3.7		4	1.2	2.2	3.5	3.8	
t_{PZH}	$\overline{OE}$ or OE	Y	1.1	4.7		5.3	1.2	3.2	4.5	5.1	ns
t_{PZL}			1.1	4.7		5.2	1.2	3.2	4.5	4.9	
t_{PHZ}	$\overline{OE}$ or OE	Y	1.9	5.5		6.1	2	3.7	5.3	5.9	ns
t_{PLZ}			1.9	5.2		5.7	2	3.4	4.9	5.4	
$t_{sk(o)}$‡									0.5	0.5	ns

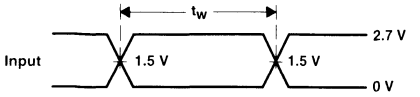
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

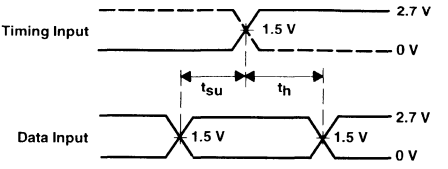


LOAD CIRCUIT

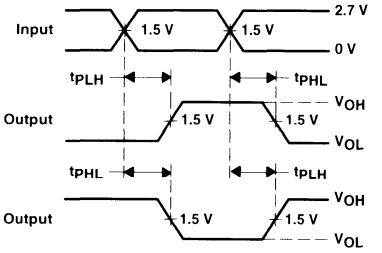
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



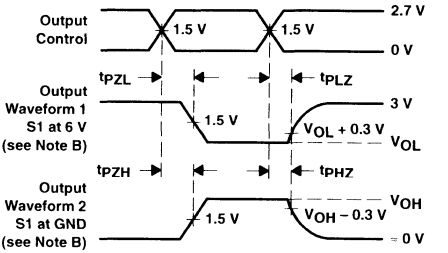
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



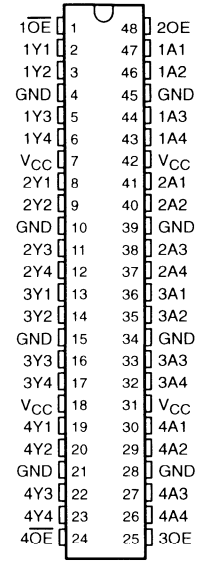
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Members of the Texas Instruments *Widebus*™ Family
- Output Ports Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- High-Impedance State During Power Up and Power Down
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVTH162241 . . . WD PACKAGE
SN74LVTH162241 . . . DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

These 16-bit buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. The devices provide noninverting outputs and complementary output-enable (OE and $\overline{OE}$) inputs.

description (continued)

The A-port outputs, which are designed to source or sink up to 12 mA, include equivalent 22-Ω series resistors to reduce overshoot and undershoot.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

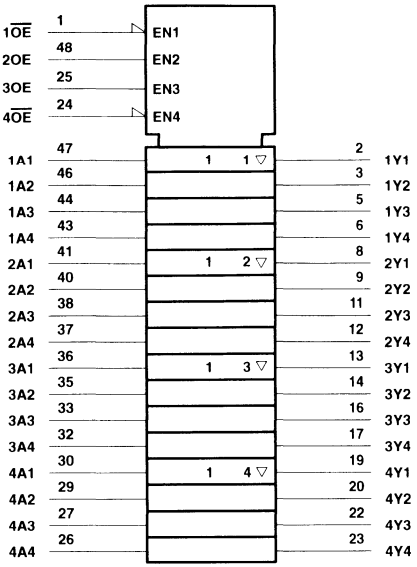
The SN54LVTH162241 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH162241 is characterized for operation from –40°C to 85°C.

FUNCTION TABLES

INPUTS		OUTPUTS
$1\overline{OE}$, $4\overline{OE}$	1A, 4A	1Y, 4Y
L	H	H
L	L	L
H	X	Z

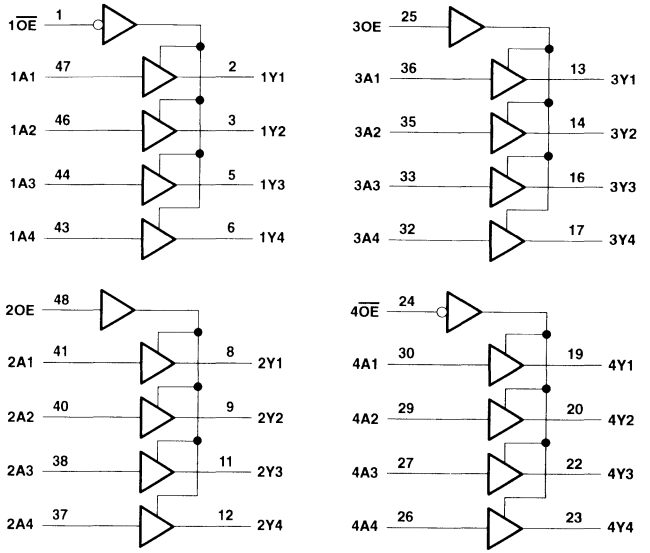
INPUTS		OUTPUTS
2OE, 3OE	2A, 3A	2Y, 3Y
H	H	H
H	L	L
L	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O ..... 30 mA
Current into any output in the high state, I_O (see Note 2) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DGV package ..... 93°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH162241		SN74LVTH162241		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–12		–12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH162241			SN74LVTH162241			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 3 V,	I_{OH} = –12 mA	2			2			V
V_{OL}		V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	V
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V			±100			±100	μA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	μA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$/OE = don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$/OE = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			9			9		pF

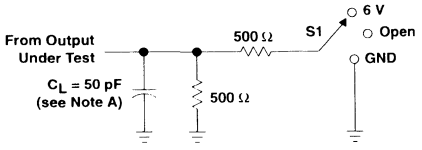
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH162241				SN74LVTH162241				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1.3	4.3		4.9	1.4	3	4.1	4.7	ns
t_{PHL}			1.3	4.3		4.9	1.4	2.4	4.1	4.7	
t_{PZH}	$\overline{OE}$ or OE	Y	1.1	5.2		5.9	1.2	3.5	4.9	5.7	ns
t_{PZL}			1.4	5		5.4	1.5	3.5	4.8	5.2	
t_{PHZ}	$\overline{OE}$ or OE	Y	1.9	5.5		6.2	2	3.7	5.3	5.9	ns
t_{PLZ}			1.9	5.2		5.7	2	3.6	4.9	5.4	
$t_{sk(o)}$‡									0.5	0.5	ns

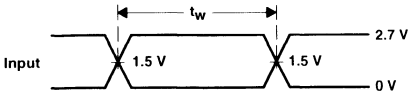
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

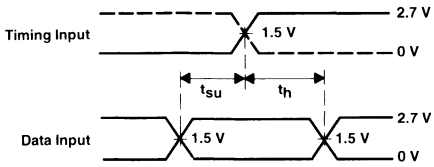


LOAD CIRCUIT

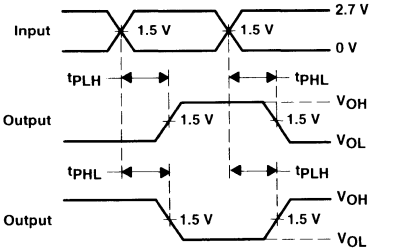
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



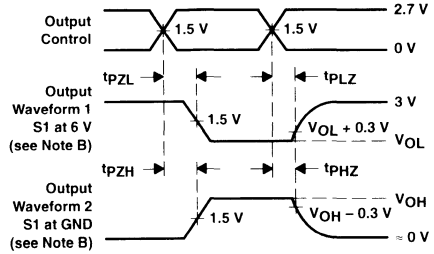
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



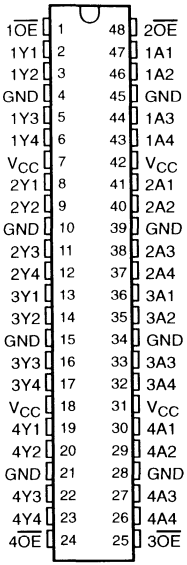
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Members of the Texas Instruments *Widebus*™ Family
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVTH16244A . . . WD PACKAGE
SN74LVTH16244A . . . DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH16244A are 16-bit buffers and line drivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. These devices provide true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

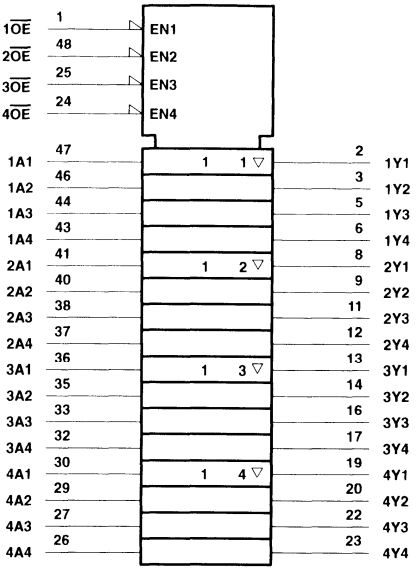
When V_{CC} is between 0 and 1.5-V, the devices are in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5-V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH16244A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

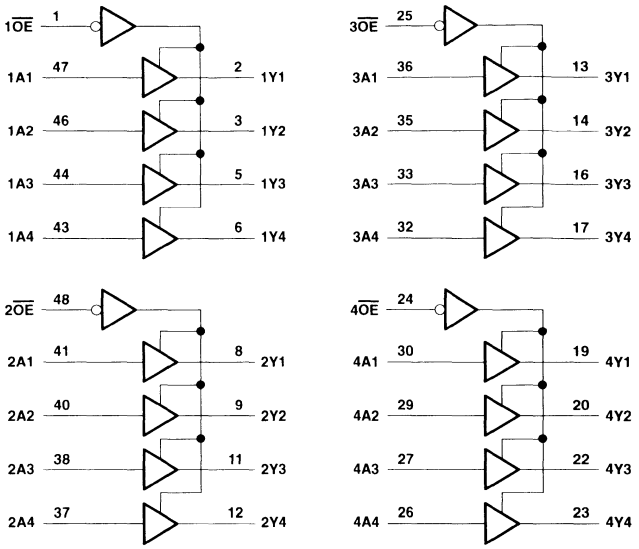
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16244A ..... 96 mA
SN74LVTH16244A ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16244A ..... 48 mA
SN74LVTH16244A ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DGV package ..... 93°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16244A		SN74LVTH16244A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16244A			SN74LVTH16244A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 μA	V_{CC}−0.2			V_{CC}−0.2			V
		V_{CC} = 2.7 V,	I_{OH} = −8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = −24 mA	2						
			I_{OH} = −32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 μA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V							±100	μA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	−75			−75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			−5			−5	μA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			9			9		pF

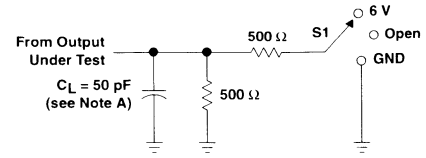
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16244A				SN74LVTH16244A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1.1	3.4		3.9	1.2	2.3	3.2	3.7	ns
t_{PHL}			1.1	3.4		3.9	1.2	2	3.2	3.7	
t_{PZH}	$\overline{OE}$	Y	1.1	4.2		5.2	1.2	2.6	4	5	ns
t_{PZL}			1.1	4.2		5.2	1.2	2.7	4	5	
t_{PHZ}	$\overline{OE}$	Y	2.1	4.7		5.2	2.2	3.3	4.5	5	ns
t_{PLZ}			1.9	4.5		4.7	2	3.1	4.2	4.4	
$t_{sk(o)}$‡									0.5		ns

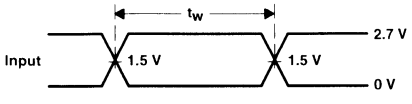
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

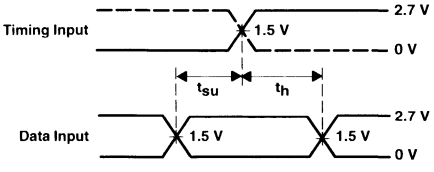


LOAD CIRCUIT

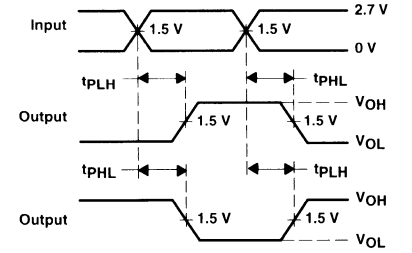
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



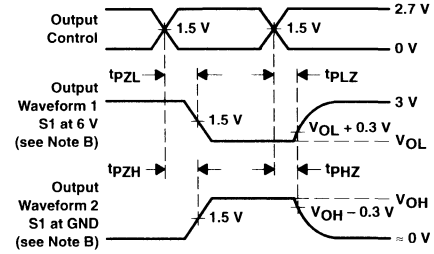
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



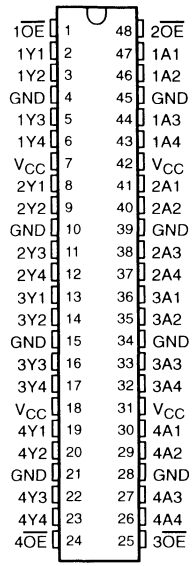
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Members of the Texas Instruments *Widebus*™ Family
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static-Power Dissipation
- Output Ports Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- High-Impedance State During Power Up and Power Down
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVTH162244 . . . WD PACKAGE
SN74LVTH162244 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH162244 are 16-bit buffers and line drivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. These devices provide true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

description (continued)

The outputs, which are designed to source or sink up to 12 mA, include equivalent 22-Ω series resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

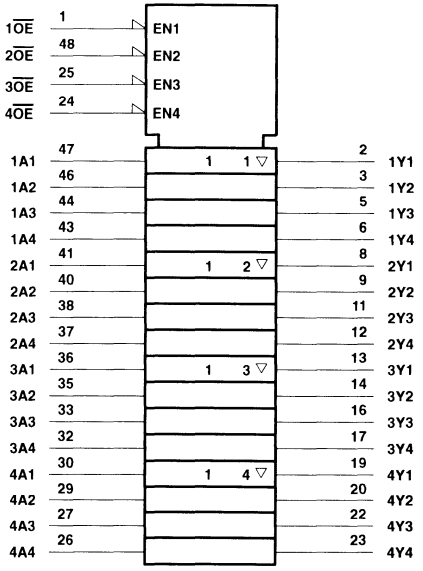
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH162244 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH162244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

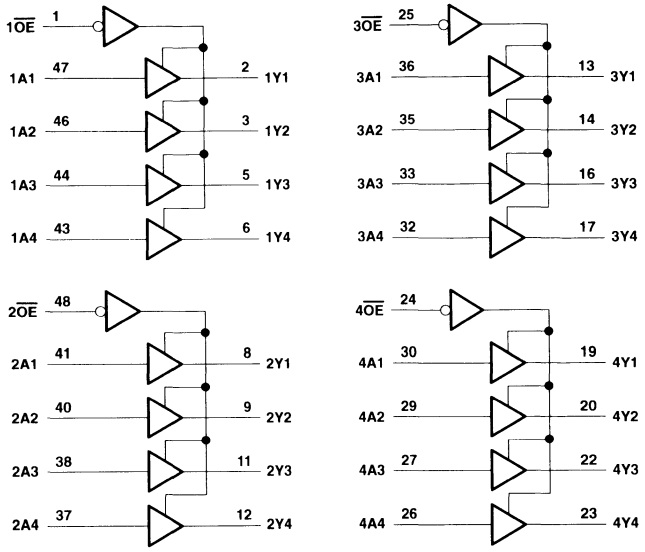
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O ..... 30 mA
Current into any output in the high state, I_O (see Note 2) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH162244		SN74LVTH162244		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–12		–12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH162244			SN74LVTH162244			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 3 V,	I_{OH} = –12 mA	2			2			V
V_{OL}		V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	V
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	μA
$I_{I(hold)}$	A inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	μA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			9			9		pF

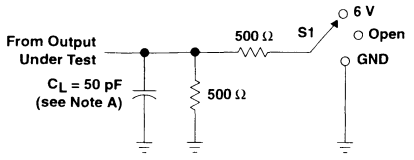
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH162244				SN74LVTH162244				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A	Y	1.3	4.5		5.1	1.4	3.4	4		4.8	ns
t_{PHL}			1.1	3.9		4.5	1.2	2.9	3.6		4.1	
t_{PZH}	$\overline{OE}$	Y	1.1	5.3		6.7	1.2	3.9	5.1		6.5	ns
t_{PZL}			1.3	4.7		6.1	1.4	3.8	4.5		5.8	
t_{PHZ}	$\overline{OE}$	Y	2.1	5.3		5.6	2.2	4.4	5		5.4	ns
t_{PLZ}			1.9	5.5		5.8	2	4.2	5		5.4	
$t_{sk(o)}$‡									0.5			ns

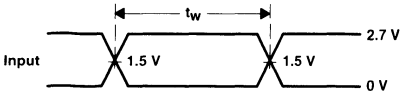
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

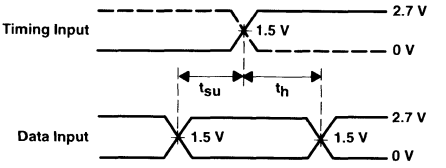


LOAD CIRCUIT

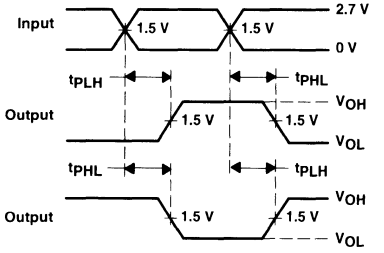
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



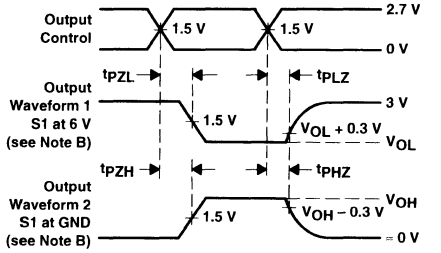
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



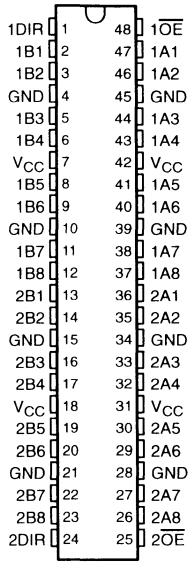
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVTH16245A . . . WD PACKAGE
SN74LVTH16245A . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH16245A devices are 16-bit (dual-octal) noninverting 3-state transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices can be used as two 8-bit transceivers or one 16-bit transceiver. They allow data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the devices so that the buses are effectively isolated.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

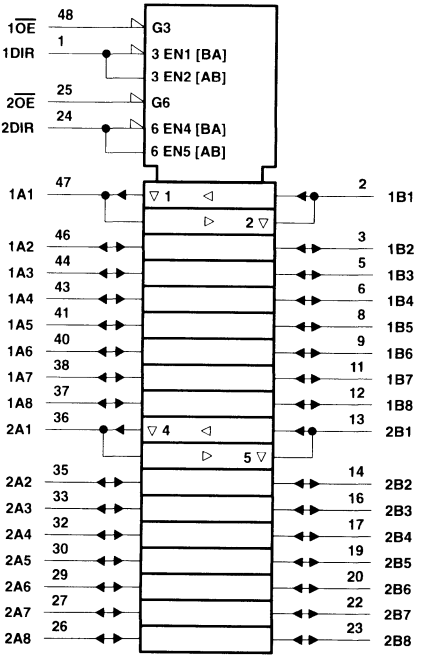
When V_{CC} is between 0 and 1.5 V, the devices are in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH16245A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

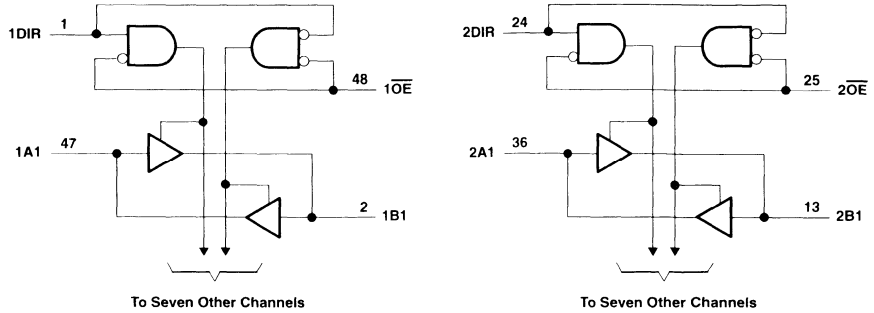
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16245A ..... 96 mA
SN74LVTH16245A ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16245A ..... 48 mA
SN74LVTH16245A ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16245A		SN74LVTH16245A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16245A			SN74LVTH16245A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}¶		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.09			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.09			0.19	
ΔI_{CC}		V_{CC} = 3 V to 3.6, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			10			10		pF

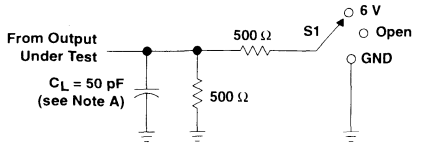
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ This parameter is not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16245A				SN74LVTH16245A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A or B	B or A	0.5	4.4		5.3	1.5	2.3	3.3	3.7	ns
t_{PHL}			0.5	4.7		5.5	1.3	2.1	3.3	3.5	
t_{PZH}	$\overline{OE}$	A or B	0.5	7		7.7	1.5	2.8	4.5	5.3	ns
t_{PZL}			0.5	5.8		7.2	1.6	2.9	4.6	5.2	
t_{PHZ}	$\overline{OE}$	A or B	1	7.2		7.7	2.3	3.7	5.1	5.5	ns
t_{PLZ}			1	6.3		6.5	2.2	3.5	5.1	5.4	
$t_{sk(o)}$‡									0.5	0.5	ns

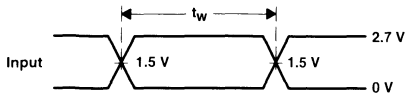
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is not production tested.

PARAMETER MEASUREMENT INFORMATION

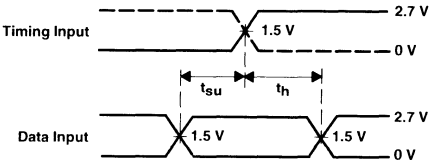


LOAD CIRCUIT

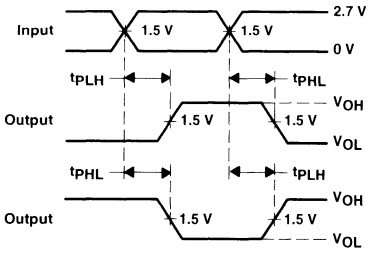
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



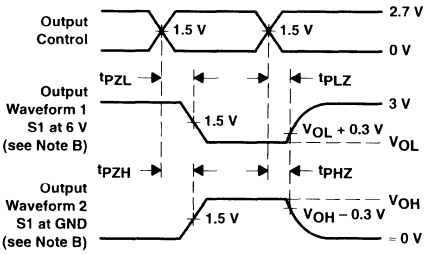
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



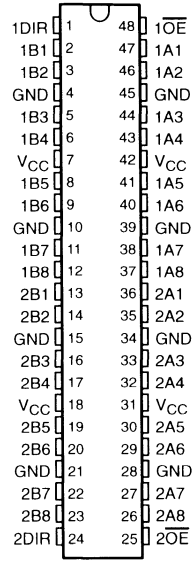
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Members of the Texas Instruments *Widebus*™ Family
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- A-Port Outputs Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVTH162245 . . . WD PACKAGE
SN74LVTH162245 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH162245 are 16-bit (dual-octal) noninverting 3-state transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

description (continued)

These devices can be used as two 8-bit transceivers or one 16-bit transceiver. The devices allow data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

The A-port outputs, which are designed to source or sink up to 12 mA, include equivalent 22-Ω series resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

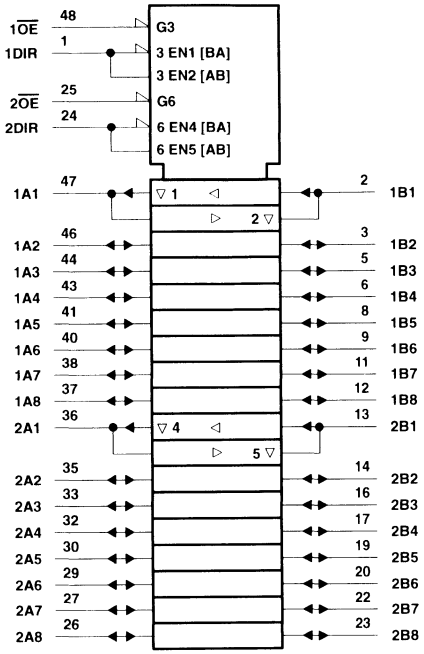
When V_{CC} is between 0 and 1.5 V, the devices are in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH162245 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH162245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

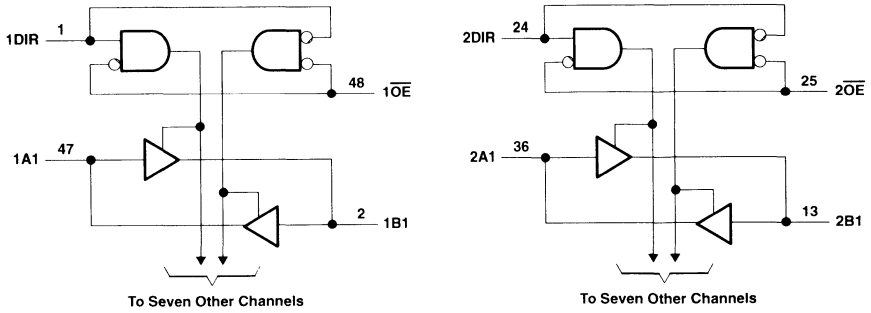
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH162245 (B port) ..... 96 mA
SN74LVTH162245 (B port) ..... 128 mA
A port ..... 30 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH162245 (B port) ..... 48 mA
SN74LVTH162245 (B port) ..... 64 mA
A port ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH162245		SN74LVTH162245		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	A port		–12		–12	mA
		B port		–24		–32	
I_{OL}	Low-level output current	A port		12		12	mA
		B port		48		64	
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH162245			SN74LVTH162245			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}	A port	V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 μA	V_{CC}−0.2			V_{CC}−0.2			V
		V_{CC} = 3 V,	I_{OH} = −12 mA	2			2			
	B port	V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 μA	V_{CC}−0.2			V_{CC}−0.2			
		V_{CC} = 2.7 V,	I_{OH} = −8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = −24 mA	2						
			I_{OH} = −32 mA				2			
V_{OL}	A port	V_{CC} = 2.7 V to 3.6 V,	I_{OL} = 100 μA			0.2			0.2	V
		V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	
	B port	V_{CC} = 2.7 V	I_{OL} = 100 μA			0.2			0.2	
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	μA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			5			5	
			V_I = 0			−10			−10	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	μA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	−75			−75			
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.3			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			10			10		pF

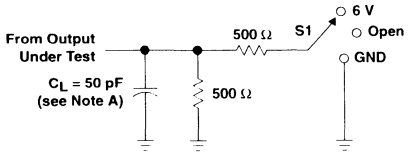
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH162245				SN74LVTH162245				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	B	1	3.5		4	1	2.3	3.3		ns
t_{PHL}			1	3.5		3.9	1	2.2	3.3		
t_{PLH}	B	A	1	4.3		5.3	1	2.8	4		ns
t_{PHL}			1	4.2		4.5	1	2.5	3.4		
t_{PZH}	$\overline{OE}$	B	1	4.8		5.9	1	2.8	4.6		ns
t_{PZL}			1	4.8		5.5	1	3	4.6		
t_{PZH}	$\overline{OE}$	A	1	5.5		7.2	1	3.3	5.3		ns
t_{PZL}			1	5.4		6.4	1	3.3	5.1		
t_{PHZ}	$\overline{OE}$	B	1.5	5.5		5.8	1.5	3.8	5.2		ns
t_{PLZ}			1.5	5.5		5.8	1.5	3.5	5.1		
t_{PHZ}	$\overline{OE}$	A	1.5	5.8		6.5	1.5	4	5.6		ns
t_{PLZ}			1.2	6.3		6.3	1.5	3.8	5.5		
$t_{sk(o)}$‡									0.5		ns

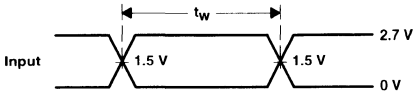
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

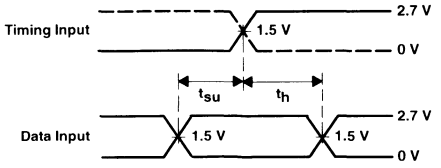


LOAD CIRCUIT

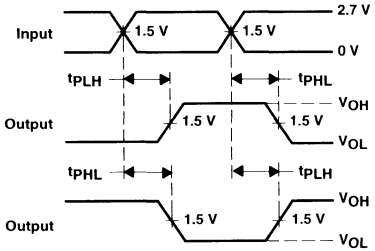
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



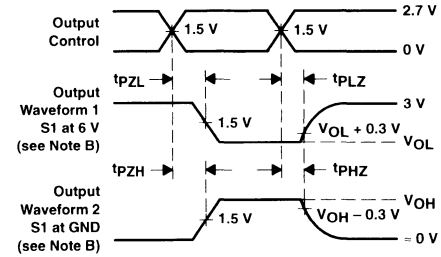
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



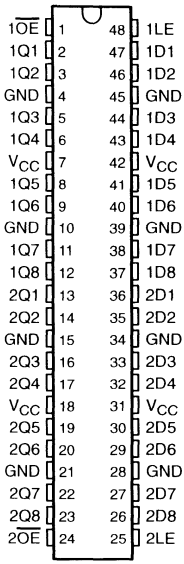
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16373 . . . WD PACKAGE
SN74LVTH16373 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH16373 are 16-bit transparent D-type latches with 3-state outputs designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

These devices can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

description (continued)

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

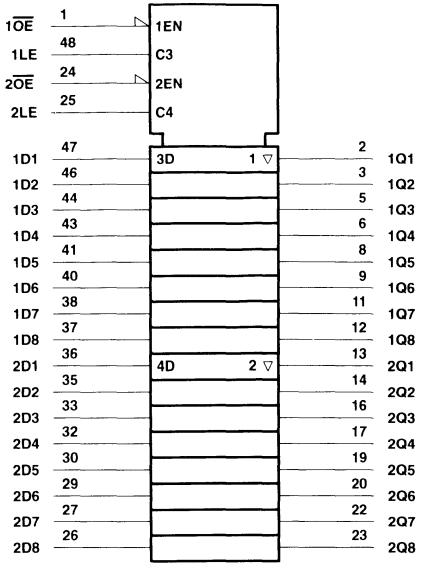
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH16373 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16373 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

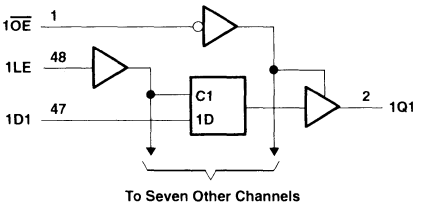
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

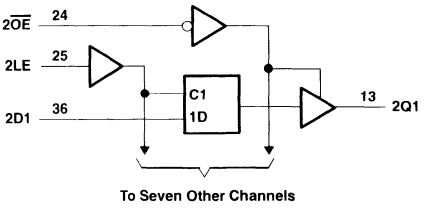
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16373 ..... 96 mA
SN74LVTH16373 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16373 ..... 48 mA
SN74LVTH16373 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16373		SN74LVTH16373		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16373			SN74LVTH16373			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 µA	V_{CC}−0.2			V_{CC}−0.2			V
		V_{CC} = 2.7 V,	I_{OH} = −8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = −24 mA	2						
			I_{OH} = −32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	−75			−75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			−5			−5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			9			9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

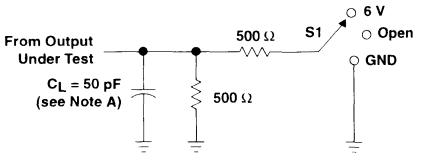
		SN54LVTH16373				SN74LVTH16373				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3		3		3		3		ns
t_{su}	Setup time, data before LE↓	1		0.6		1		0.6		ns
t_h	Hold time, data after LE↓	1		1.1		1		1.1		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16373				SN74LVTH16373					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	D	Q	1.4	4		4.4	1.5	2.7	3.8		4.2	ns
t_{PHL}			1.4	3.8		4.2	1.5	2.5	3.6		4	
t_{PLH}	LE	Q	2	4.5		5	2.1	3	4.3		4.8	ns
t_{PHL}			2	4.2		4.2	2.1	2.9	4		4	
t_{PZH}	$\overline{OE}$	Q	1.4	4.5		5.3	1.5	2.8	4.3		5.1	ns
t_{PZL}			1.4	4.5		5.1	1.5	2.8	4.3		4.7	
t_{PHZ}	$\overline{OE}$	Q	2.3	5.2		5.6	2.4	3.5	5		5.4	ns
t_{PLZ}			1.9	4.9		5.1	2	3.2	4.7		4.8	
$t_{sk(o)}$‡									0.5			ns

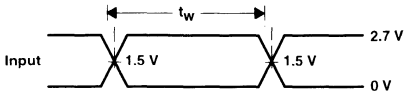
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

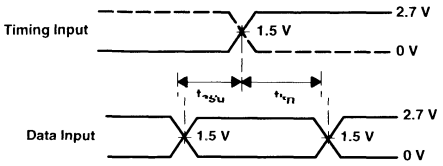


LOAD CIRCUIT

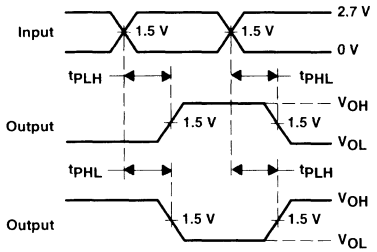
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



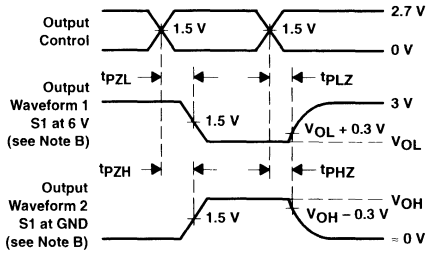
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



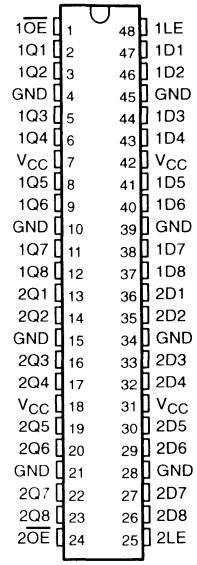
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Members of the Texas Instruments *Widebus*™ Family
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- Output Ports Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- High-Impedance State During Power Up and Power Down
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs, Permitting Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVTH162373 . . . WD PACKAGE
SN74LVTH162373 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH162373 devices are16-bit transparent D-type latches with 3-state outputs designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

description (continued)

The 'LVTH162373 devices can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The outputs, which are designed to source or sink up to 12 mA, include equivalent 22-Ω series resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

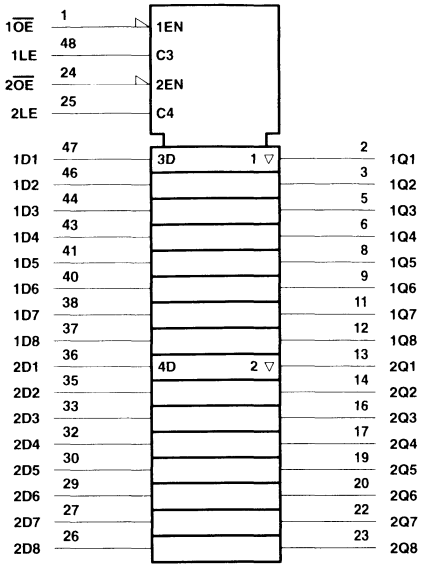
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH162373 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH162373 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

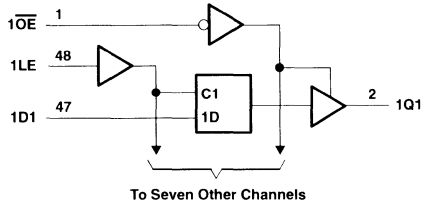
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

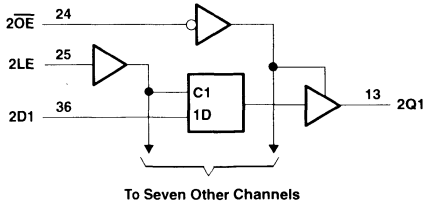
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O ..... 30 mA
Current into any output in the high state, I_O (see Note 2) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH162373		SN74LVTH162373		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–12		–12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: All unused control inputs of the device must be held at VCC or GND to ensure proper device operation.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH162373			SN74LVTH162373			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}		V_{CC} = 3 V,	I_{OH} = −12 mA	2			2			V
V_{OL}		V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	V
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V			±100			±100	μA
$I_{I(hold)}$	A inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	−75			−75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			−5			−5	μA
I_{OZPU}		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{OZPD}		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}‡		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			9			9		pF

* On products compliant to MIL-PRF-38535, this parameter is not production tested.
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

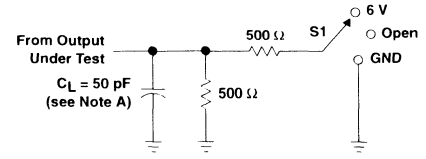
		SN54LVTH162373				SN74LVTH162373				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3		3		3		3		ns
t_{su}	Setup time, data before LE↓	1.3		0.6		1		0.6		ns
t_h	Hold time, data after LE↓	1		1.1		1		1.1		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH162373				SN74LVTH162373				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	D	Q	1.8	5		5.7	1.9	3.1	4.6		5.1	ns
t_{PHL}			1.8	4.4		4.8	1.9	2.8	4		4.3	
t_{PLH}	LE	Q	2.1	5.4		6.2	2.2	3.4	5.1		5.8	ns
t_{PHL}			2.1	4.9		4.7	2.2	3.2	4.6		4.3	
t_{PZH}	$\overline{OE}$	Q	1.7	5.6		7	1.8	3.2	5.4		6.6	ns
t_{PZL}			1.7	5.3		5.9	1.8	3.2	4.9		5.5	
t_{PHZ}	$\overline{OE}$	Q	2.3	6.3		6.6	2.4	3.8	5.4		5.7	ns
t_{PLZ}			1	7.4		6.4	2.2	3.5	5.1		5	
$t_{sk(o)}$‡									0.5			ns

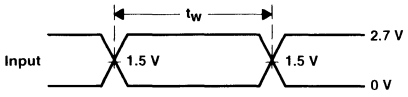
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction.

PARAMETER MEASUREMENT INFORMATION

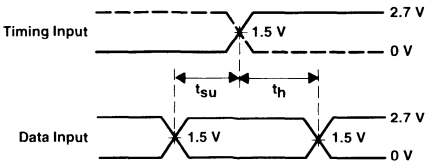


LOAD CIRCUIT

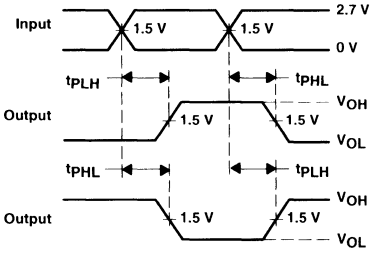
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



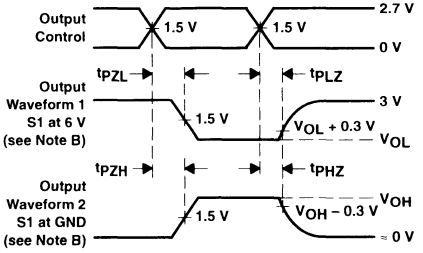
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



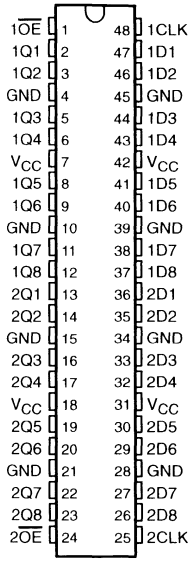
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Members of the Texas Instruments *Widebus*™ Family
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- High-Impedance State During Power Up and Power Down
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVTH16374 . . . WD PACKAGE
SN74LVTH16374 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH16374 are 16-bit edge-triggered D-type flip-flops with 3-state outputs designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

These devices can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (CLK), the Q outputs of the flip-flop take on the logic levels set up at the data (D) inputs.

description (continued)

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

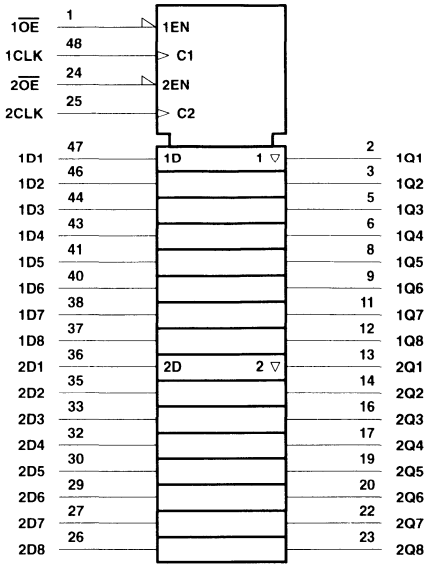
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH16374 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

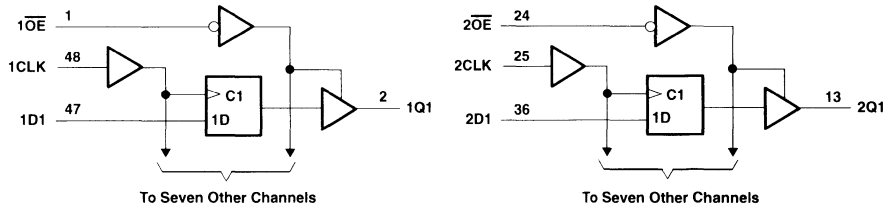
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16374 ..... 96 mA
SN74LVTH16374 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16374 ..... 48 mA
SN74LVTH16374 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16374		SN74LVTH16374		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16374			SN74LVTH16374			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			9			9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

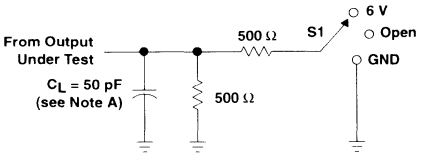
			SN54LVTH16374				SN74LVTH16374				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	160	0	160	0	160	0	160	MHz
t_w	Pulse duration, CLK high or low		3		3		3		3		ns
t_{su}	Setup time, data before CLK↑	High or low	2		2.2		1.8		2		ns
t_h	Hold time, data after CLK↑	High or low	0.8		0.2		0.8		0.1		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16374				SN74LVTH16374					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			160		160		160			160		MHz
t_{PLH}	CLK	Q	1.8	4.7		5.4	1.9	3	4.5		5.2	ns
t_{PHL}			2	4.2		4.4	2.1	2.9	4		4.2	
t_{PZH}	$\overline{OE}$	Q	1.4	4.7		5.6	1.5	2.8	4.5		5.4	ns
t_{PZL}			1.4	4.6		5.2	1.5	2.8	4.4		5	
t_{PHZ}	$\overline{OE}$	Q	2.3	5.2		5.6	2.4	3.5	5		5.4	ns
t_{PLZ}			1.9	4.8		5	2	3.2	4.6		4.8	
$t_{sk(o)}$‡									0.5			ns

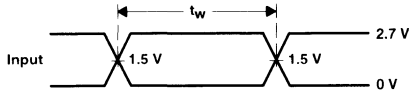
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

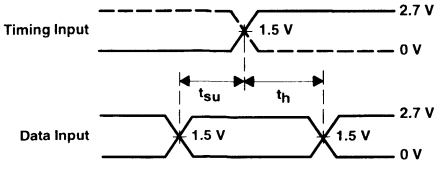


LOAD CIRCUIT

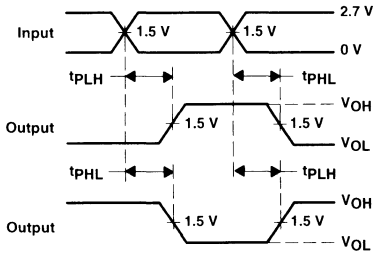
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



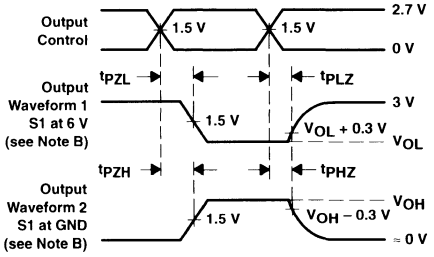
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
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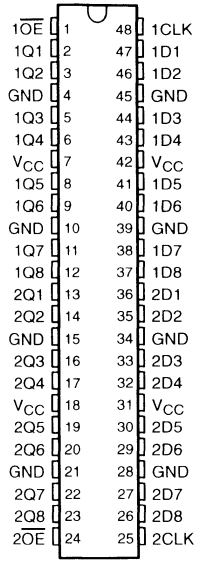
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Output Ports Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH162374 . . . WD PACKAGE
SN74LVTH162374 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH162374 are 16-bit edge-triggered D-type flip-flops with 3-state outputs designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. They are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

description (continued)

The 'LVTH162374 can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (CLK), the Q outputs of the flip-flop take on the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The outputs, which are designed to source or sink up to 12 mA, include equivalent 22-Ω series resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

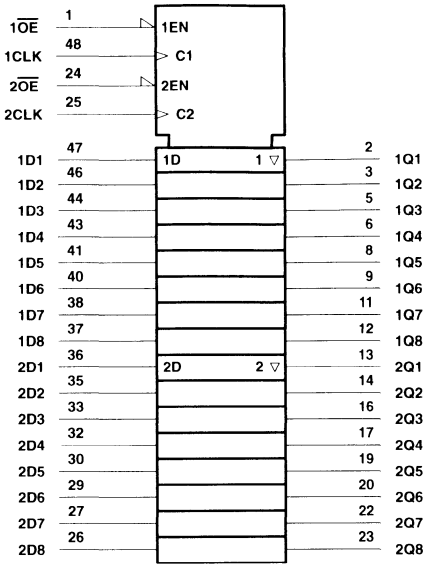
When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH162374 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH162374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

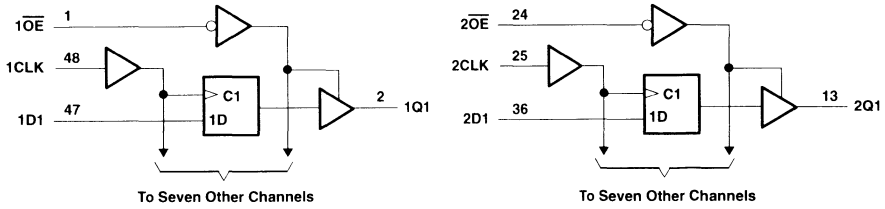
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O ..... 30 mA
Current into any output in the high state, I_O (see Note 2) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH162374		SN74LVTH162374		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–12		–12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH162374			SN74LVTH162374			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 3 V,	I_{OH} = –12 mA	2			2			V
V_{OL}		V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	V
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	μA
$I_{I(hold)}$	A inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	μA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			9			9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

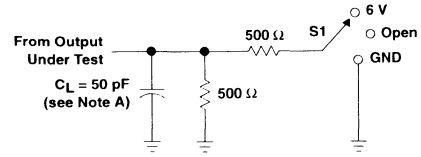
			SN54LVTH162374				SN74LVTH162374				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	160	0	160	0	160	0	160	MHz
t_w	Pulse duration, CLK high or low		3		3		3		3		ns
t_{su}	Setup time, data before CLK↑	High or low	2		2.2		1.8		2		ns
t_h	Hold time, data after CLK↑	High or low	0.8		0.2		0.8		0.1		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH162374				SN74LVTH162374				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
f_{max}			160		160		160			160	MHz
t_{PLH}	CLK	Q	1.9	5.5		6.4	2	3.4	5.3	6.2	ns
t_{PHL}			2.1	5.1		5.3	2.2	3.3	4.9	5.1	
t_{PZH}	$\overline{OE}$	Q	1.7	5.8		7.1	1.8	3.5	5.6	6.9	ns
t_{PZL}			1.7	5.2		6.2	1.8	3.5	4.9	6	
t_{PHZ}	$\overline{OE}$	Q	2.3	5.6		6	2.4	4.2	5.4	5.7	ns
t_{PLZ}			1.9	5.7		5.6	2	3.8	5	5.1	
$t_{sk(o)}$‡									0.5		ns

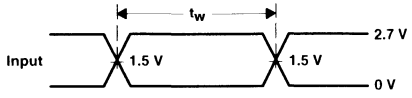
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

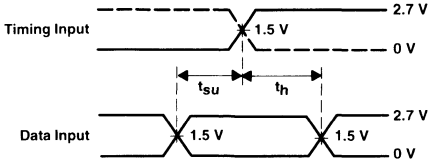


LOAD CIRCUIT

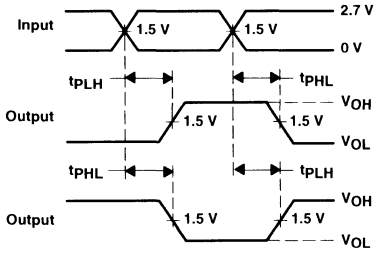
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



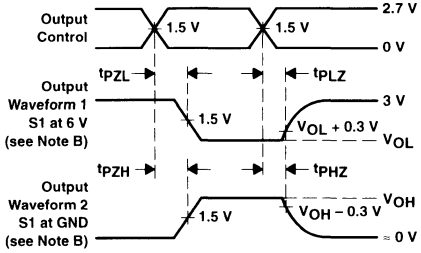
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



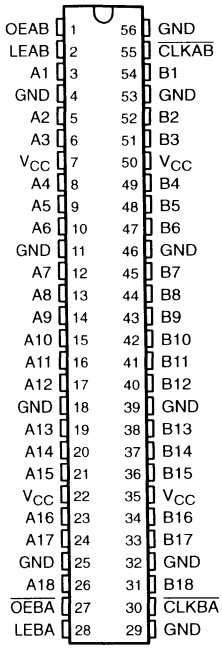
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16500 . . . WD PACKAGE
SN74LVTH16500 . . . DGG OR DL PACKAGE
(TOP VIEW)



PRODUCT PREVIEW

description

The 'LVTH16500 are 18-bit universal bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{\text{OEBA}}$), latch-enable (LEAB and LEBA), and clock ($\overline{\text{CLKAB}}$ and $\overline{\text{CLKBA}}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if $\overline{\text{CLKAB}}$ is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the high-to-low transition of $\overline{\text{CLKAB}}$. Output-enable OEAB is active high. When OEAB is high, the B-port outputs are active. When OEAB is low, the B-port outputs are in the high-impedance state.

description (continued)

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, and $\overline{CLKBA}$. The output enables are complementary (OEAB is active high and $\overline{OEBA}$ is active low).

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

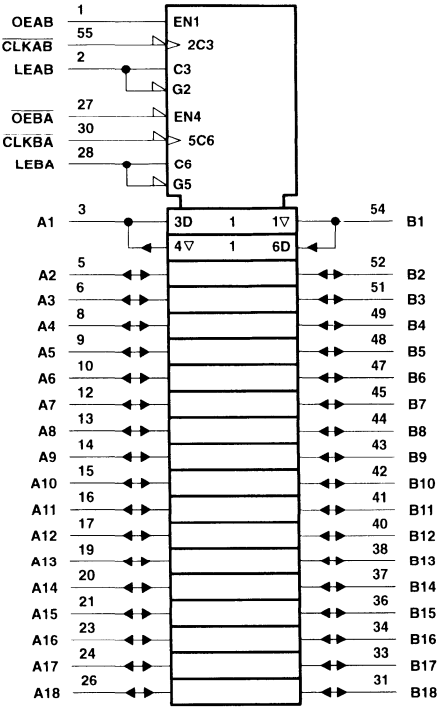
The SN54LVTH16500 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16500 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
OEAB	LEAB	$\overline{CLKAB}$	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↓	L	L
H	L	↓	H	H
H	L	H	X	B_0‡
H	L	L	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, and $\overline{CLKBA}$.
‡ Output level before the indicated steady-state input conditions were established
§ Output level before the indicated steady-state input conditions were established, provided that $\overline{CLKAB}$ was low before LEAB went low

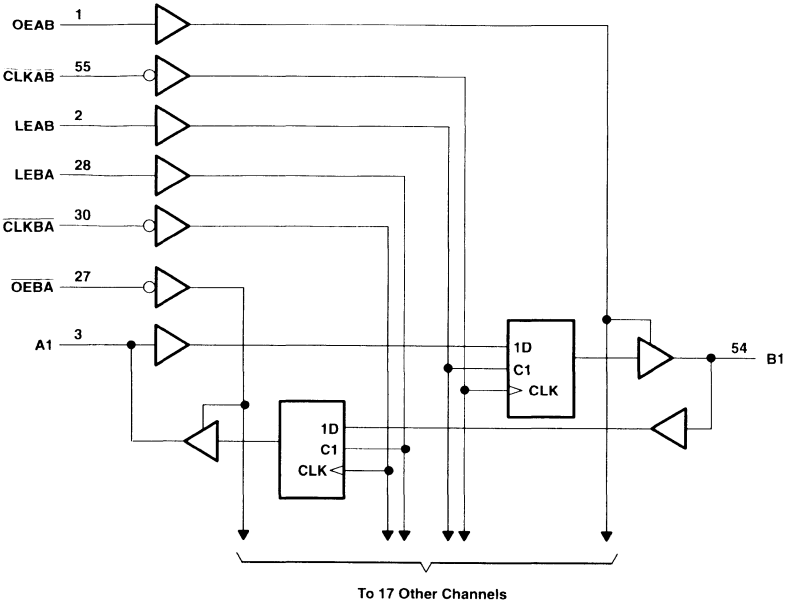
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

PRODUCT PREVIEW

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16500 ..... 96 mA
SN74LVTH16500 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16500 ..... 48 mA
SN74LVTH16500 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16500		SN74LVTH16500		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16500			SN74LVTH16500			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			5			5	
			V_I = 0			–10			–10	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–1			–1	µA
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, OE/$\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, OE/$\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3.5			3.5		pF
C_{io}		V_O = 3 V or 0			12			12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

				SN54LVTH16500				SN74LVTH16500				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	150	0	125	0	150	0	125	MHz
t_w	Pulse duration	LE high		3.3		3.3		3.3		3.3		ns
		$\overline{CLK}$ high or low		3.3		3.3		3.3		3.3		
t_{su}	Setup time	A before $\overline{CLKAB}$↓		1.8		1.1		1.8		1.1		ns
		B before $\overline{CLKBA}$↓		1.9		1.2		1.9		1.2		
		A or B before LE↓	$\overline{CLK}$ high	2.2		1.3		2.2		1.3		
			$\overline{CLK}$ low	2.7		1.9		2.7		1.9		
t_h	Hold time	A or B after $\overline{CLK}$↓		1.2		1.2		1.2		1.2		ns
		A or B after LE↓		0.9		1.1		0.9		1.1		

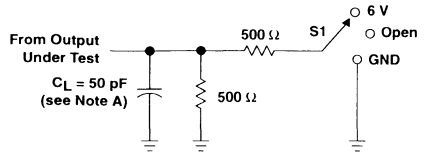
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16500				SN74LVTH16500					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		125		150			125		MHz
t_{PLH}	B or A	A or B	1.7	5.8	7		1.7	3	5.4	6.8		ns
t_{PHL}			1.6	6	7.8		1.6	3.2	5.9	7.7		
t_{PLH}	LEBA or LEAB	A or B	2.3	7.3	8.9		2.3	4	7	8.5		ns
t_{PHL}			2.7	8.2	9.8		2.7	4.3	7.9	9.7		
t_{PLH}	$\overline{CLKBA}$ or $\overline{CLKAB}$	A or B	2	7.4	8.8		2	4.1	7	8.3		ns
t_{PHL}			2.4	8.1	10		2.4	4.4	7.9	9.9		
t_{PZH}	$\overline{OEBA}$ or OEAB	A or B	1.2	5.2	6.1		1.2	3	5	5.9		ns
t_{PZL}			1.5	5.9	7		1.5	3	5.8	6.9		
t_{PHZ}	$\overline{OEBA}$ or OEAB	A or B	2.7	7.7	8.6		2.7	4.6	7.4	8.3		ns
t_{PLZ}			2.8	7.3	7.7		2.8	4.7	6.7	7.2		
$t_{sk(o)}$‡									0.5			ns

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

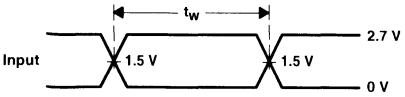
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION

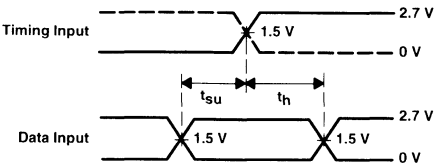


LOAD CIRCUIT

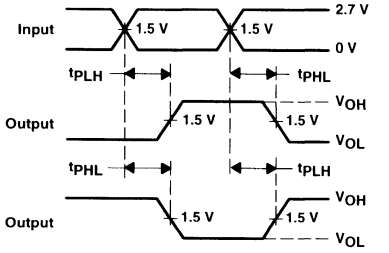
TEST	S1
t_{PHL}/t_{PLH}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



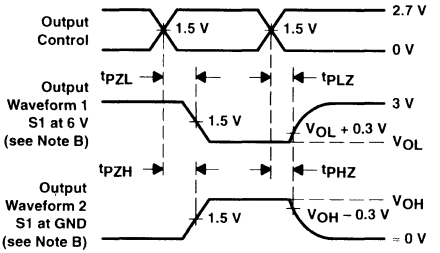
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



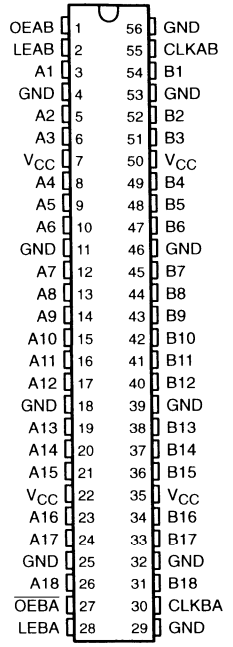
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16501 . . . WD PACKAGE
SN74LVTH16501 . . . DGG OR DL PACKAGE
(TOP VIEW)



PRODUCT PREVIEW

description

The 'LVTH16501 are 18-bit universal bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{\text{OEBA}}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. When OEAB is high, the outputs are active. When OEAB is low, the outputs are in the high-impedance state.

description (continued)

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, and CLKBA. The output enables are complementary (OEAB is active high and $\overline{OEBA}$ is active low).

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

The SN54LVTH16501 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16501 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

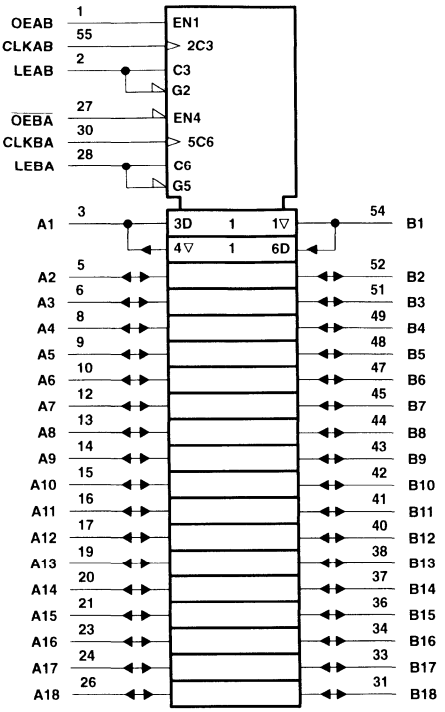
INPUTS				OUTPUT
OEAB	LEAB	CLKAB	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↑	L	L
H	L	↑	H	H
H	L	H	X	B_0‡
H	L	L	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, and CLKBA.

‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

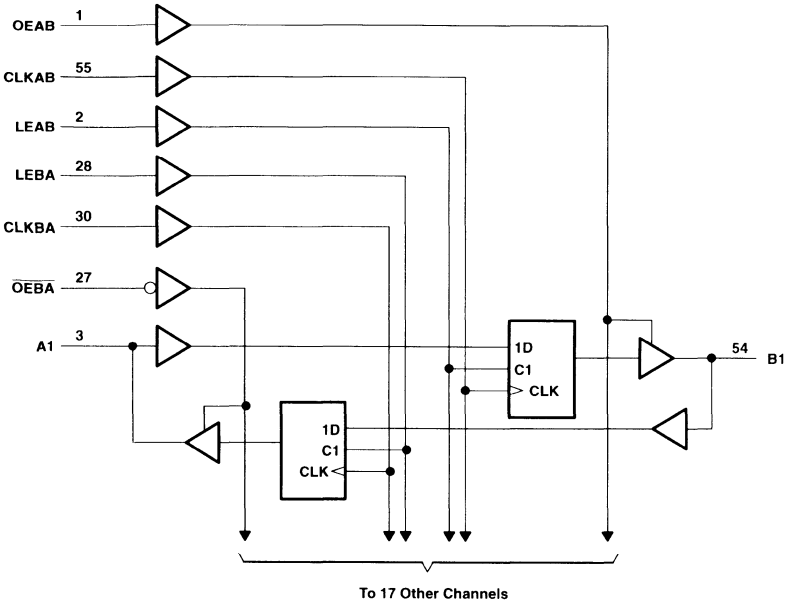
§ Output level before the indicated steady-state input conditions were established

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16501 ..... 96 mA
SN74LVTH16501 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16501 ..... 48 mA
SN74LVTH16501 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16501		SN74LVTH16501		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16501			SN74LVTH16501			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–1			–1	µA
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$/OE = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$/OE = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3.5			3.5		pF
C_{io}		V_O = 3 V or 0			12			12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

				SN54LVTH16501				SN74LVTH16501				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	150	0	125	0	150	0	125	MHz
t_w	Pulse duration	LE high		3.3		3.3		3.3		3.3		ns
		CLK high or low		3.3		3.3		3.3		3.3		
t_{su}	Setup time	A before CLKAB↑		1.6		2.1		1.6		2.1		ns
		B before CLKBA↑		1.6		2.1		1.6		2.1		
		A or B before LE↓	CLK high	3.1		2.7		2.6		1.9		
			CLK low	2.6		2		2		1.3		
t_h	Hold time	A or B after CLK↑		2		2.1		2		2.1		ns
		A or B after LE↓		1.3		1.2		0.9		1.2		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16501				SN74LVTH16501					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		125		150			125		MHz
t_{PLH}	B or A	A or B	1.7	5.4		6.8	1.7	3	5.4		6.8	ns
t_{PHL}			1.6	6		7.8	1.6	3.2	5.9		7.7	
t_{PLH}	LEBA or LEAB	A or B	2.3	7.3		9	2.3	4	7		8.5	ns
t_{PHL}			2.7	8.2		9.8	2.7	4.3	7.9		9.7	
t_{PLH}	CLKBA or CLKAB	A or B	2.5	8.3		9.7	2.5	4.1	7.9		9.2	ns
t_{PHL}			3.5	9.4		10.7	3.5	5.4	8.9		10.4	
t_{PZH}	$\overline{OEBA}$ or OEAB	A or B	1.2	5.1		6.1	1.2	3	5		5.9	ns
t_{PZL}			1.5	5.9		7	1.5	3	5.8		6.9	
t_{PHZ}	$\overline{OEBA}$ or OEAB	A or B	2.7	7.5		8.5	2.7	4.6	7.4		8.3	ns
t_{PLZ}			2.8	6.8		7.5	2.8	4.7	6.7		7.2	
$t_{sk(o)}$‡									0.5			ns

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
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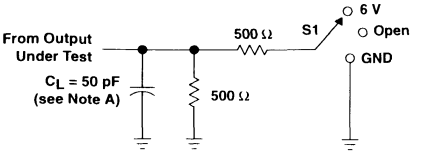
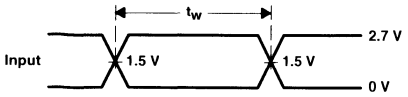
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION

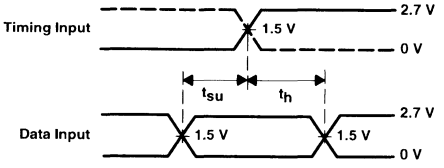


LOAD CIRCUIT

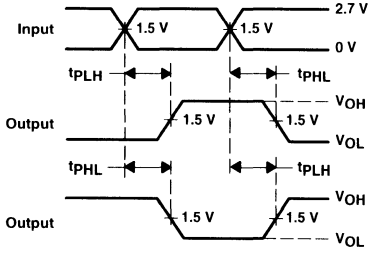
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



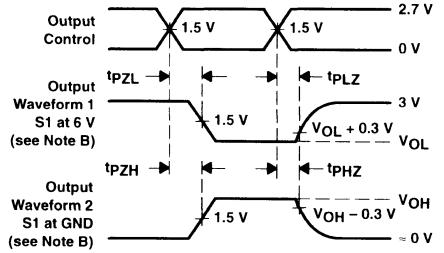
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



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NOTES: A. C_L includes probe and jig capacitance.
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C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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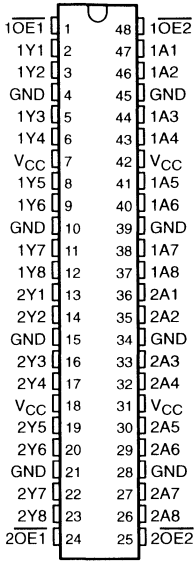
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16541 . . . WD PACKAGE
SN74LVTH16541 . . . DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

These 16-bit buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are noninverting 16-bit buffers composed of two 8-bit sections with separate output-enable signals. For either 8-bit buffer section, the two output-enable ($1\overline{OE1}$ and $1\overline{OE2}$ or $2\overline{OE1}$ and $2\overline{OE2}$) inputs must be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 8-bit buffer section are in the high-impedance state.

description (continued)

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

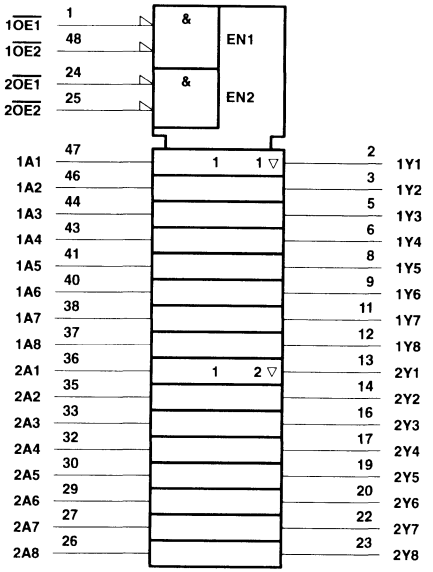
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVTH16541 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16541 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

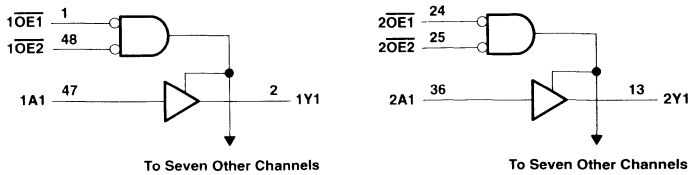
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16541 ..... 96 mA
SN74LVTH16541 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16541 ..... 48 mA
SN74LVTH16541 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DGV package ..... 93°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16541		SN74LVTH16541		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		µs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16541			SN74LVTH16541			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V				±100			±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			9			9		pF

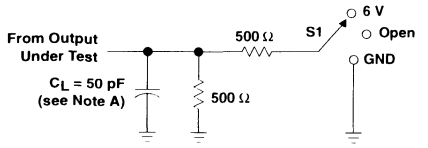
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16541				SN74LVTH16541				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	3.7		4	1	2.4	3.5	3.8	ns
t_{PHL}			1	3.7		4	1	2	3.5	3.8	
t_{PZH}	$\overline{OE}$	Y	1.1	4.8		5.7	1.2	2.7	4.6	5.5	ns
t_{PZL}			1.1	4.8		5.4	1.2	2.8	4.6	5.2	
t_{PHZ}	$\overline{OE}$	Y	2.1	6.2		6.5	2.2	4.1	5.9	6.2	ns
t_{PLZ}			1.9	5.7		6	2.2	3.8	5.4	5.5	
$t_{sk(o)}$‡									0.5	0.5	ns

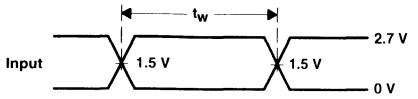
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

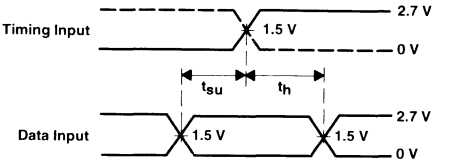


LOAD CIRCUIT

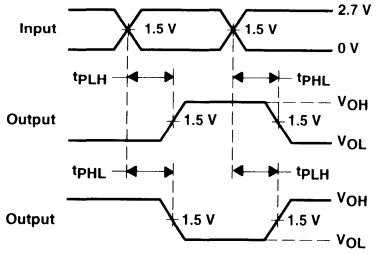
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



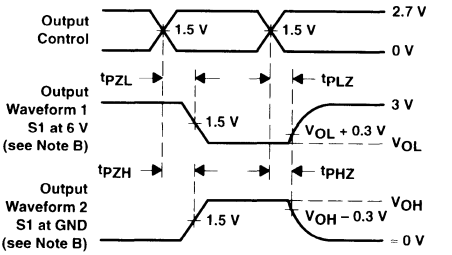
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



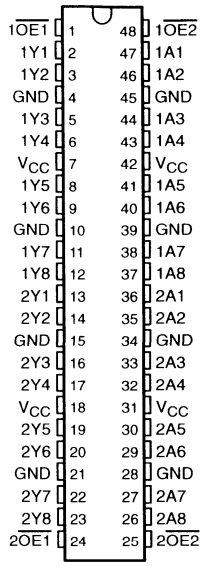
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Members of the Texas Instruments *Widebus*™ Family
- Output Ports Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- High-Impedance State During Power Up and Power Down
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVTH162541 . . . WD PACKAGE
SN74LVTH162541 . . . DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

These 16-bit buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

These devices are noninverting 16-bit buffers composed of two 8-bit sections with separate output-enable signals. For either 8-bit buffer section, the two output-enable ($1\overline{OE1}$ and $1\overline{OE2}$ or $2\overline{OE1}$ and $2\overline{OE2}$) inputs must be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 8-bit buffer section are in the high-impedance state.

The A-port outputs, which are designed to source or sink up to 12 mA, include equivalent 22-Ω series resistors to reduce overshoot and undershoot.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

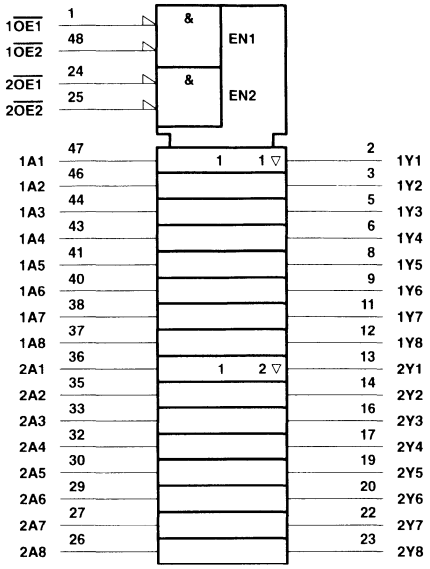
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVTH162541 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH162541 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

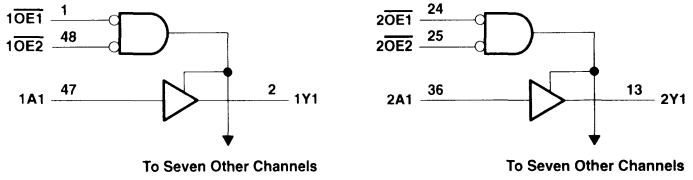
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O ..... 30 mA
Current into any output in the high state, I_O (see Note 2) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DGV package ..... 93°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH162541		SN74LVTH162541		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–12		–12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH162541			SN74LVTH162541			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}		V_{CC} = 3 V,	I_{OH} = −12 mA	2			2			V
V_{OL}		V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	V
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	μA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V			±100			±100	μA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	−75			−75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	μA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			−5			−5	μA
I_{OZPU}‡		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = Don't care				±100			±100	μA
I_{OZPD}‡		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = Don't care				±100			±100	μA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_o		V_O = 3 V or 0			9			9		pF

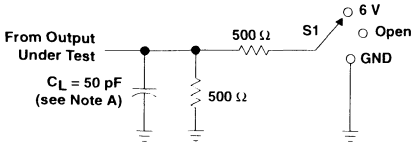
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This parameter is warranted but not production tested.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH162541				SN74LVTH162541				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A	Y	1.1	4.3		4.9	1.2	2.9	4.1		4.7	ns
t_{PHL}			1.1	4.3		4.9	1.2	2.4	4.1		4.7	
t_{PZH}	$\overline{OE}$	Y	1.4	5.3		6.3	1.5	3.2	5		6.1	ns
t_{PZL}			1.4	5.1		5.8	1.5	3.3	4.8		5.5	
t_{PHZ}	$\overline{OE}$	Y	2.1	6.1		6.4	2.2	4.3	5.9		6.2	ns
t_{PLZ}			2.1	5.7		5.9	2.2	4	5.4		5.5	
$t_{sk(o)}$‡									0.5		0.5	ns

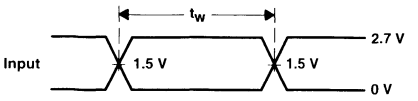
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

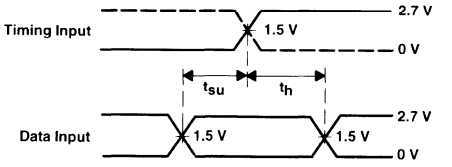


LOAD CIRCUIT

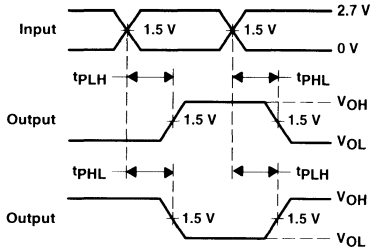
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



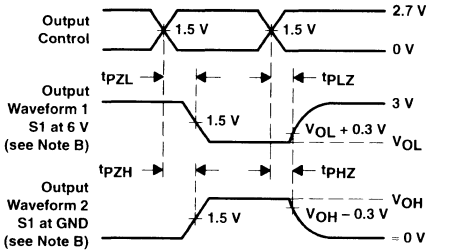
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



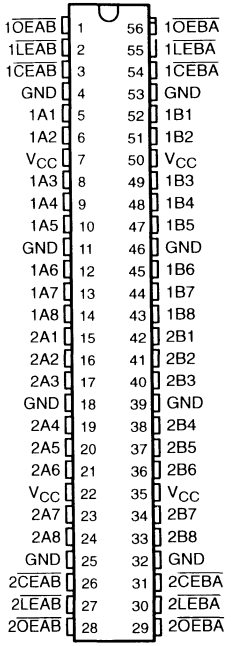
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16543 . . . WD PACKAGE
SN74LVTH16543 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH16543 are 16-bit registered transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ puts the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar but requires using the $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$ inputs.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

PRODUCT PREVIEW

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

The SN54LVTH16543 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16543 is characterized for operation from –40°C to 85°C.

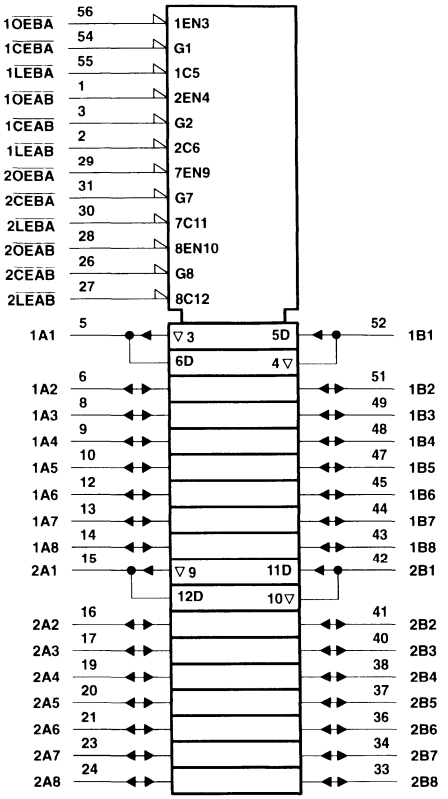
FUNCTION TABLE† (each 8-bit section)

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

PRODUCT PREVIEW

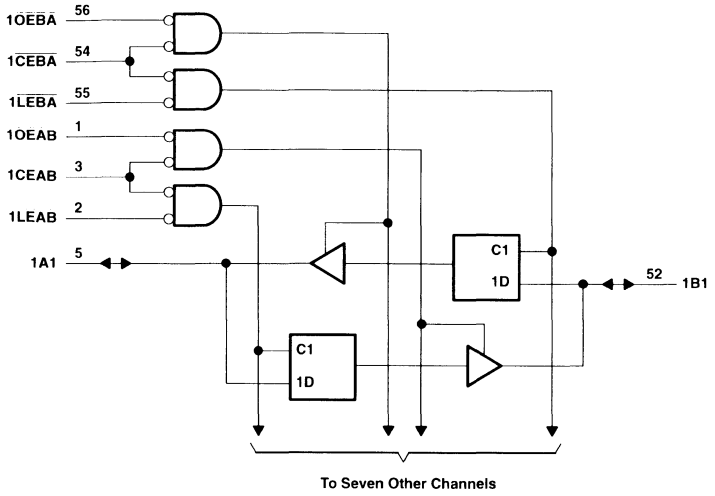
logic symbol†

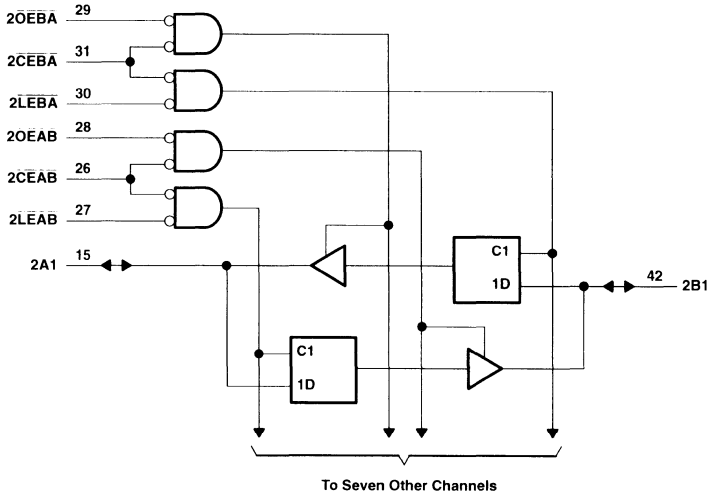


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

PRODUCT PREVIEW

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16543 . . . . . 96 mA
SN74LVTH16543 . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16543 . . . . . 48 mA
SN74LVTH16543 . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16543		SN74LVTH16543		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		µs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16543			SN74LVTH16543			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			5			5	
			V_I = 0			–10			–10	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–1			–1	µA
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, OE = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, OE = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			13			13		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

				SN54LVTH16543				SN74LVTH16543				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, $\overline{LEAB}$ or $\overline{LEBA}$ low			3.3		3.3		3.3		3.3		ns
t_{su}	Setup time	A or B before $\overline{LEAB}$↑ or $\overline{LEBA}$↑	Data high	0.8		0.5		0.8		0.5		ns
			Data low	1.5		1.9		1.5		1.9		
		A or B before $\overline{CEAB}$↑ or $\overline{CEBA}$↑	Data high	0.7		0.4		0.7		0.4		ns
			Data low	1.6		1.9		1.6		1.9		
t_h	Hold time	A or B after $\overline{LEAB}$↑ or $\overline{LEBA}$↑	Data high	0.8		0		0.8		0		ns
			Data low	1.2		1.3		1.2		1.3		
		A or B after $\overline{CEAB}$↑ or $\overline{CEBA}$↑	Data high	0.8		0		0.8		0		ns
			Data low	1.3		1.4		1.3		1.4		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16543				SN74LVTH16543				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1.4	5		5.8	1.4	2.7	4.6		5.5	ns
t_{PHL}			1.3	4.7		5.9	1.3	2.9	4.6		5.8	
t_{PLH}	$\overline{LE}$	A or B	1.3	6.8		8.5	1.7	3.7	6.3		8.1	ns
t_{PHL}			1.5	6.5		8.3	1.9	3.7	6		7.8	
t_{PZH}	$\overline{OE}$	A or B	1.4	6		7.7	1.5	3.3	5.8		7.6	ns
t_{PZL}			1.6	6.3		8.4	1.6	3.3	6.2		8.2	
t_{PHZ}	$\overline{OE}$	A or B	2	6.7		7.3	2	4.1	6.5		7.1	ns
t_{PLZ}			2.7	6		6.2	2.7	3.9	5.8		5.9	
t_{PZH}	$\overline{CE}$	A or B	1.4	6.2		7.7	1.5	3.3	6		7.6	ns
t_{PZL}			1.6	6.6		8.5	1.7	3.3	6.4		8.3	
t_{PHZ}	$\overline{CE}$	A or B	2	6.6		7.2	2	4.1	6.4		7.1	ns
t_{PLZ}			2.6	5.6		5.9	2.6	4	5.4		5.6	
$t_{sk(o)}$‡									0.5			ns

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

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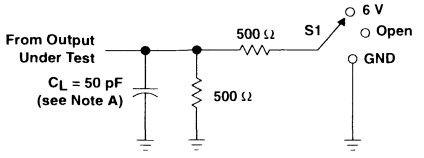
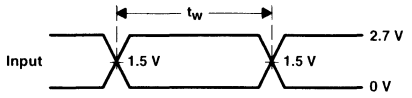
PARAMETER MEASUREMENT INFORMATION

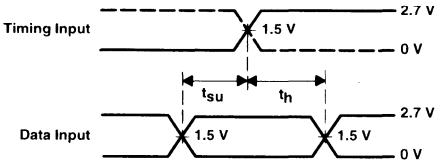


LOAD CIRCUIT

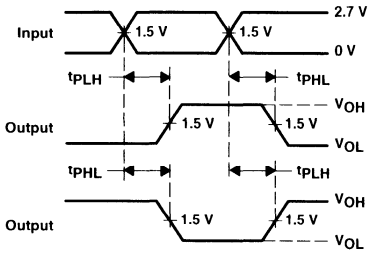
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



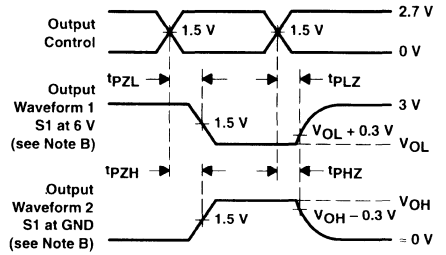
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
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- **High-Impedance State During Power Up and Power Down**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
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- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
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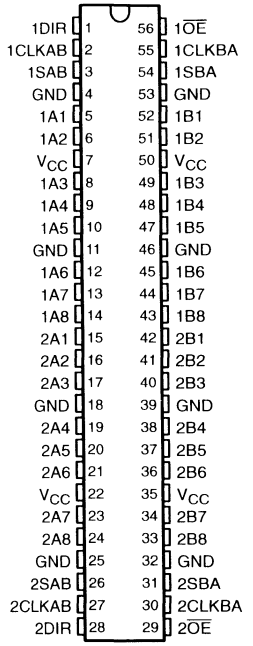
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16646 . . . WD PACKAGE
SN74LVTH16646 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH16646 are 16-bit bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'LVTH16646.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs are provided to control the transceiver functions. In the transceiver mode, data present at the high-impedance port may be stored in either register or in both. The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. DIR determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data can be stored in one register and/or B data can be stored in the other register.

When an output function is disabled, the input function is still enabled and can be used to store and transmit data. Only one of the two buses, A or B, can be driven at a time.

PRODUCT PREVIEW

description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH16646 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16646 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS						DATA I/O		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B Bus
L	H	H or L	X	H	X	Input	Output	Stored A data to bus

† The data-output functions may be enabled or disabled by various signals at $\overline{OE}$ or DIR. Data-input functions are always enabled, i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.

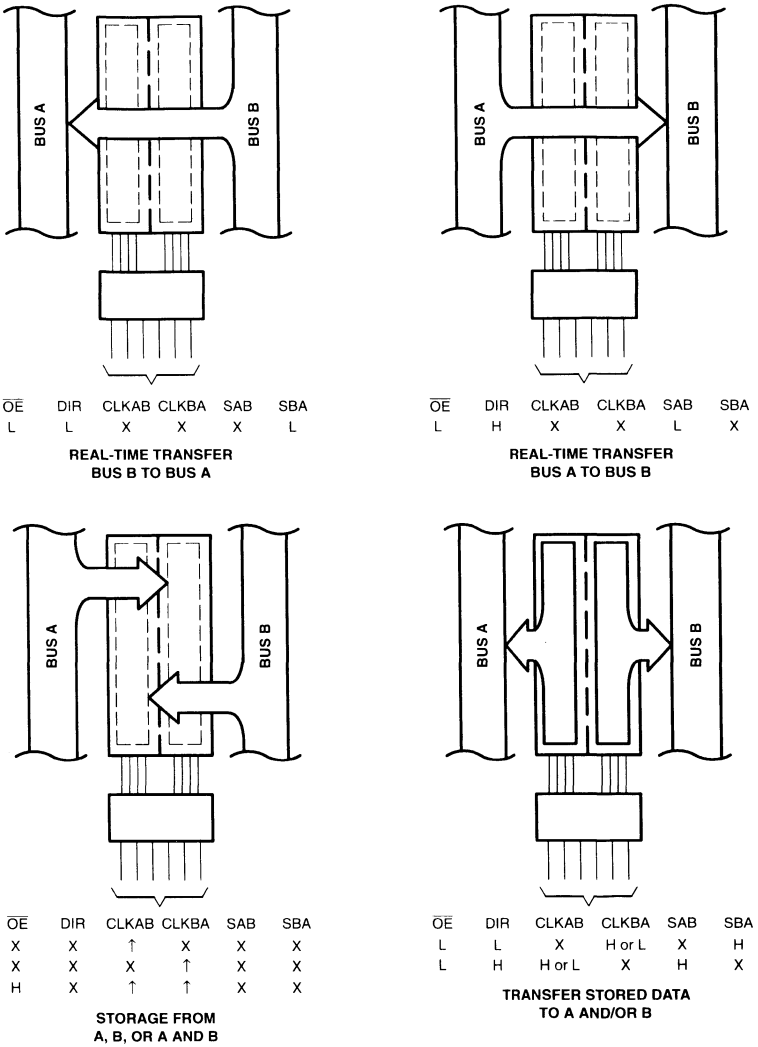
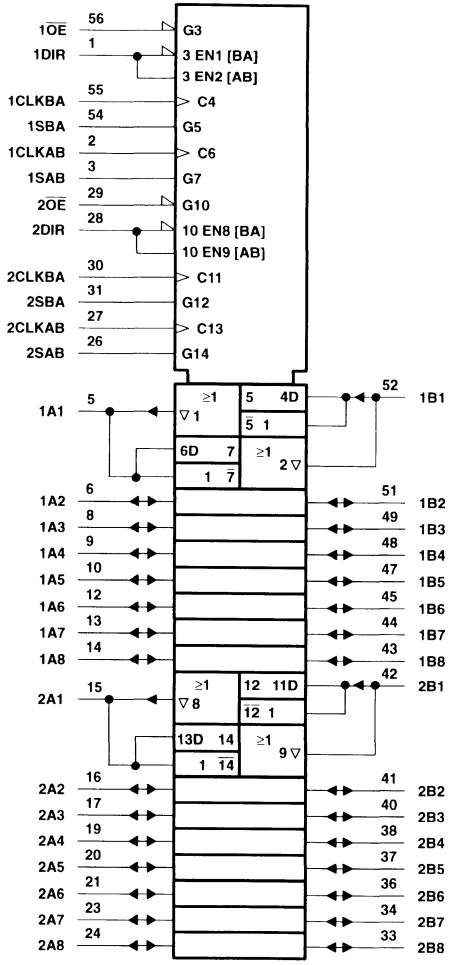


Figure 1. Bus-Management Functions

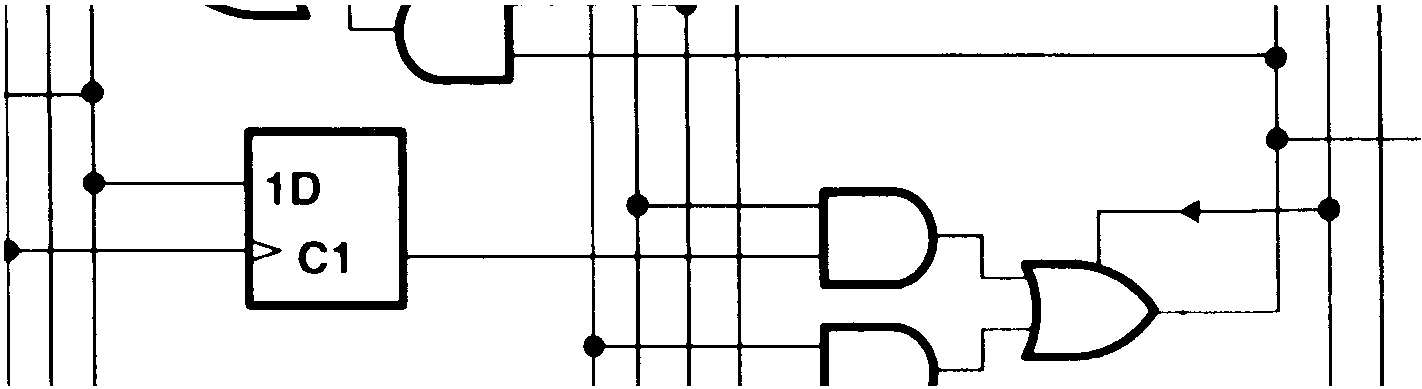
PRODUCT PREVIEW

PRODUCT PREVIEW

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.


1D
C1

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16646 ..... 96 mA
SN74LVTH16646 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16646 ..... 48 mA
SN74LVTH16646 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			SN54LVTH16646		SN74LVTH16646		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16646			SN74LVTH16646			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			5			5	
			V_I = 0			–10			–10	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–1			–1	µA
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3.5			3.5		pF
C_{io}		V_O = 3 V or 0			12			12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

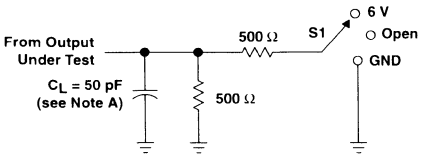
			SN54LVTH16646				SN74LVTH16646				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high	1.3		1.4		1.3		1.4		ns
		Data low	2.4		3		2.4		3		
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑	Data high	0.5		0		0.5		0		ns
		Data low	0.6		0.5		0.5		0.5		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16646				SN74LVTH16646					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		150		150			150		MHz
t_{PLH}	CLKBA or CLKAB	A or B	1.8	6		6.9	1.8	3.8	5.7		6.7	ns
t_{PHL}			2.1	5.9		6.6	2.1	3.9	5.7		6.5	
t_{PLH}	A or B	B or A	1.3	4.9		5.6	1.3	3	4.7		5.4	ns
t_{PHL}			1	4.8		5.8	1	3.1	4.7		5.6	
t_{PLH}	SBA or SAB‡	A or B	1.4	6.4		7.4	1.4	4	6.2		7.2	ns
t_{PHL}			1.4	6.4		7.4	1.4	4.3	6.2		7.2	
t_{PZH}	$\overline{OE}$	A or B	1	5.7		7.4	1	3	5.4		6.4	ns
t_{PZL}			1	6.5		7.5	1	3.1	5.6		6.5	
t_{PHZ}	$\overline{OE}$	A or B	2.3	6.7		7.1	2.3	4.6	6.5		6.9	ns
t_{PLZ}			2.2	6		6.5	2.2	4.5	5.8		5.9	
t_{PZH}	DIR	A or B	1	5.9		7.7	1	3.3	5.7		6.7	ns
t_{PZL}			1.2	5.9		7.3	1.2	3.5	5.8		6.7	
t_{PHZ}	DIR	A or B	1.7	7.3		8.5	1.7	4.7	7.2		8.3	ns
t_{PLZ}			1.5	7.8		7.4	1.5	4.9	6.6		7.2	
$t_{sk(o)}$§									0.5			ns

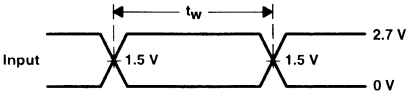
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ These parameters are measured with the internal output state of the storage register opposite that of the bus input.
§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

PARAMETER MEASUREMENT INFORMATION

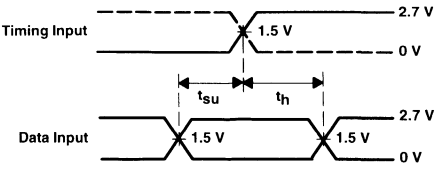


LOAD CIRCUIT

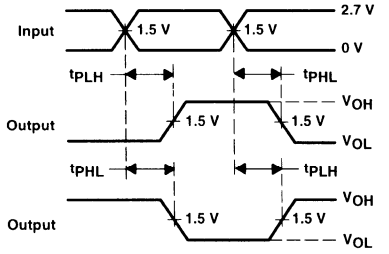
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



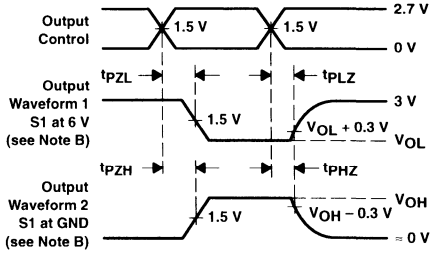
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

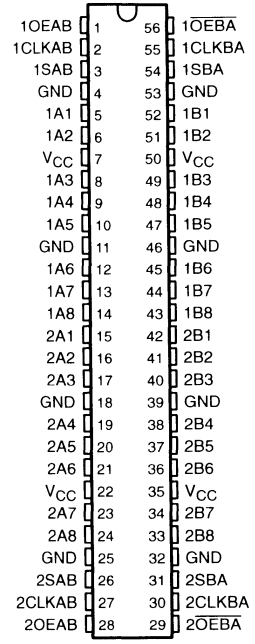
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

PRODUCT PREVIEW

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16652 . . . WD PACKAGE
SN74LVTH16652 . . . DGG OR DL PACKAGE
(TOP VIEW)



PRODUCT PREVIEW

description

The 'LVTH16652 are 16-bit bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as two 8-bit transceivers or one 16-bit transceiver.

Complementary output-enable (OEAB and $\overline{OEBA}$) inputs are provided to control the transceiver functions. Select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. A low input level selects real-time data, and a high input level selects stored data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'LVTH16652.

description (continued)

Data on the A or B bus, or both, can be stored in the internal D flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs, regardless of the levels on the select-control or output-enable inputs. When SAB and SBA are in the real-time transfer mode, it also is possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{\text{OEBA}}$. In this configuration, each output reinforces its input. When all other data sources to the two sets of bus line are at high impedance, each set of bus lines remains at its last level configuration.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVTH16652 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16652 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

† The data-output functions may be enabled or disabled by a variety of level combinations at OEAB or $\overline{\text{OEBA}}$. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.
‡ Select control = L; clocks can occur simultaneously.
Select control = H; clocks must be staggered to load both registers.

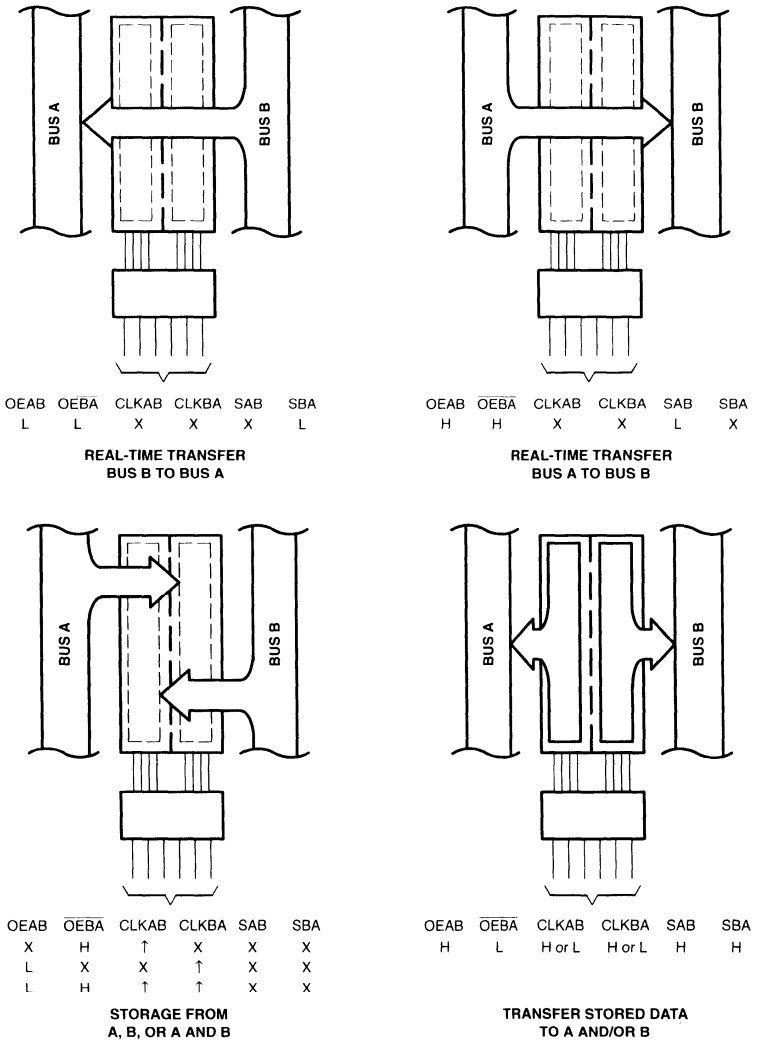
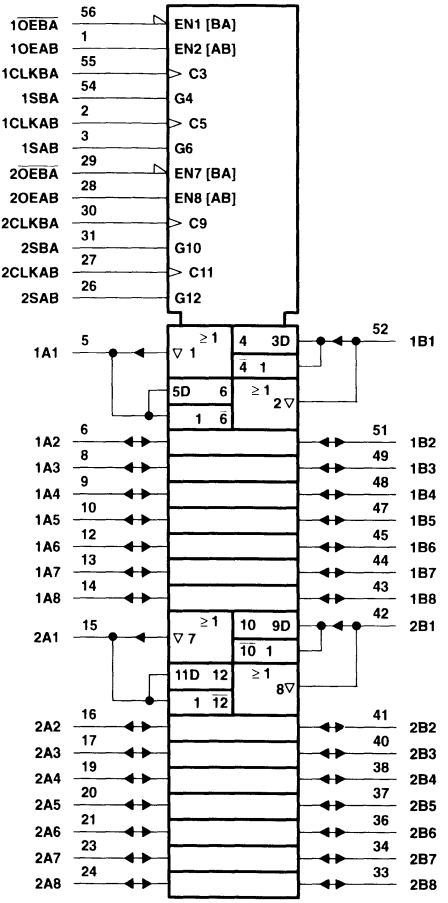


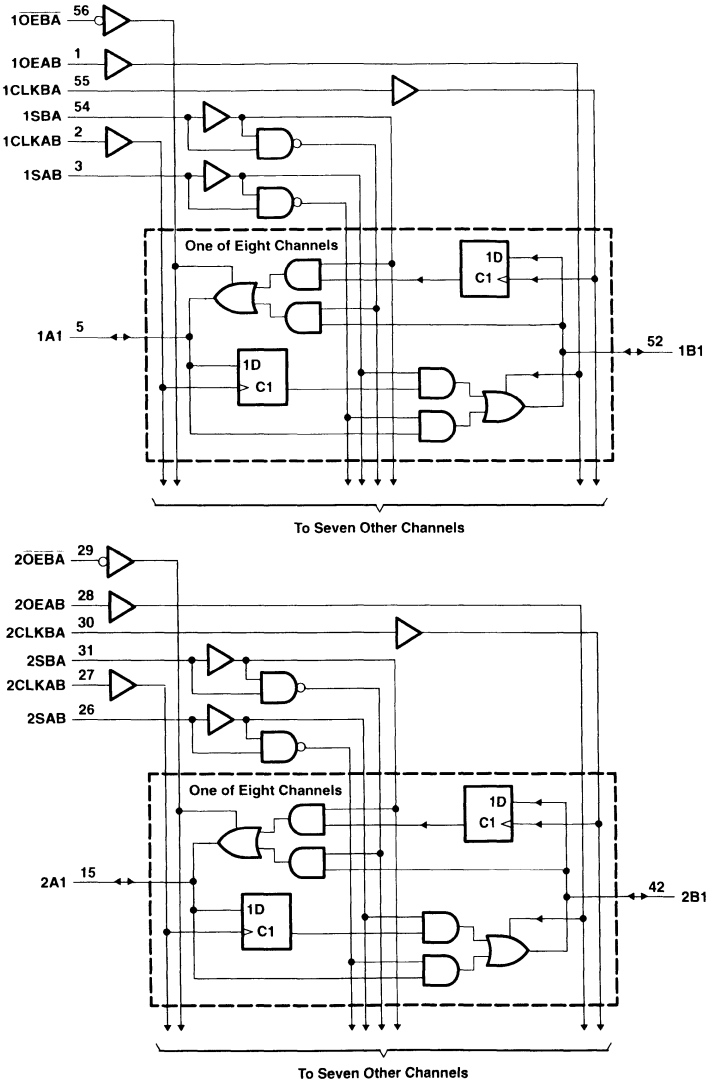
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16652 ..... 96 mA
SN74LVTH16652 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16652 ..... 48 mA
SN74LVTH16652 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			SN54LVTH16652		SN74LVTH16652		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16652			SN74LVTH16652			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
		V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			5			5	
			V_I = 0			–10			–10	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–1			–1	µA
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.1			0.1	mA
			Outputs low			5			5	
			Outputs disabled			0.1			0.1	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0								pF
C_{io}		V_O = 3 V or 0								pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

PRODUCT PREVIEW

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

		SN54LVTH16652				SN74LVTH16652				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency									MHz
t_w	Pulse duration, CLK high or low									ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑									ns
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑									ns

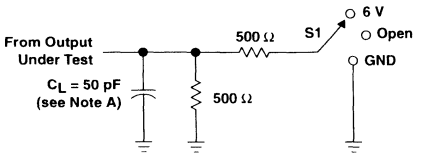
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16652				SN74LVTH16652					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}												MHz
t_{PLH}	CLK	B or A										ns
t_{PHL}												
t_{PLH}	A or B	B or A										ns
t_{PHL}												
t_{PLH}	SAB or SBA	B or A										ns
t_{PHL}												
t_{PZH}	$\overline{OEBA}$	A										ns
t_{PZL}												
t_{PHZ}	$\overline{OEBA}$	A										ns
t_{PLZ}												
t_{PZH}	OEAB	B										ns
t_{PZL}												
t_{PHZ}	OEAB	B										ns
t_{PLZ}												
$t_{sk(o)}$‡												ns

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

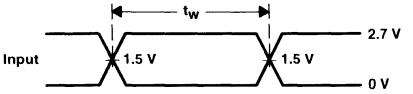
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION

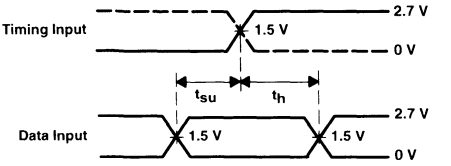


LOAD CIRCUIT

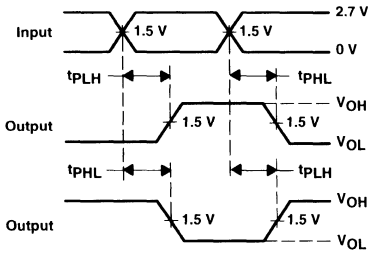
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



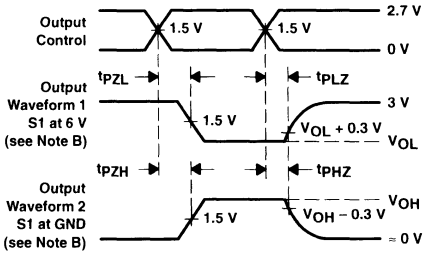
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



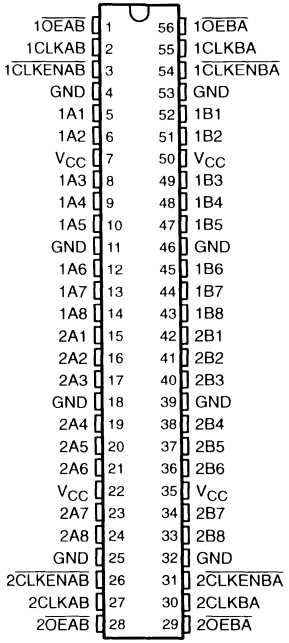
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **High-Impedance State During Power Up and Power Down**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVTH16952 . . . WD PACKAGE
SN74LVTH16952 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVTH16952 are 16-bit registered transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input provided that the clock-enable ($\overline{CLKENAB}$ or $\overline{CLKENBA}$) input is low. Taking the output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) input low accesses the data on either port.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVTH16952 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH16952 is characterized for operation from –40°C to 85°C.

PRODUCT PREVIEW

FUNCTION TABLE†

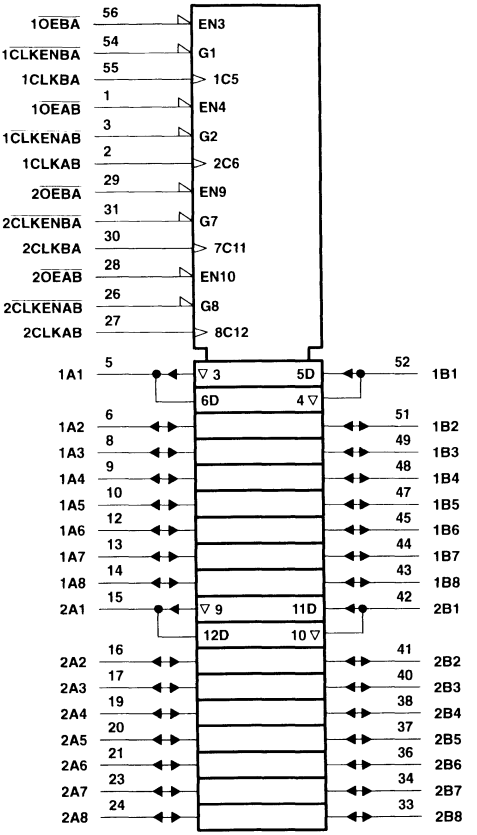
INPUTS				OUTPUT
$\overline{CLKENAB}$	CLKAB	$\overline{OEAB}$	A	B
H	X	L	X	B_0‡
X	L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

† A-to-B data flow is shown; B-to-A data flow is similar, but uses $\overline{CLKENBA}$, CLKBA, and $\overline{OEBA}$.

‡ Level of B before the indicated steady-state input conditions were established

PRODUCT PREVIEW

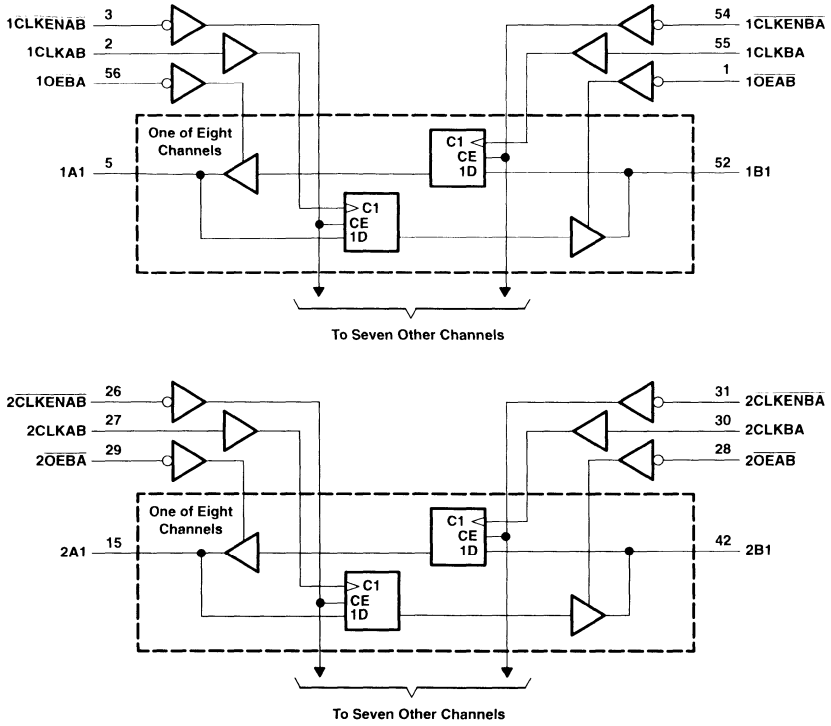
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

PRODUCT PREVIEW

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH16952 ..... 96 mA
SN74LVTH16952 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH16952 ..... 48 mA
SN74LVTH16952 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH16952		SN74LVTH16952		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH16952			SN74LVTH16952			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–1			–1	µA
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			13			13		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

			SN54LVTH16952				SN74LVTH16952				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration	CLKEN high	3.3		3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		3.3		
t_{su}	Setup time	A or B before CLK	2.6		3.3		2.1		2.9		ns
		$\overline{CLKEN}$ before CLK	1.2		1.6		1.2		1.6		
t_h	Hold time	A or B after CLK	0.7		0.7		0.7		0.7		ns
		$\overline{CLKEN}$ after CLK	1.4		1.5		1.4		1.5		

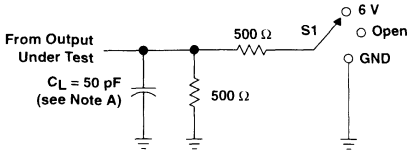
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH16952				SN74LVTH16952					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		150		150			150		MHz
t_{PLH}	CLKBA or CLKAB	A or B	1.6	5.7		7.4	2	3.4	5.8		7.1	ns
t_{PHL}			2	6		7	2	3.4	5.8		6.9	
t_{PZH}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	1	5		7.3	1	2.7	5.6		6.7	ns
t_{PZL}			1.2	5.2		5.9	1.2	2.7	6.5		8	
t_{PHZ}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	1.8	6.7		7.3	2.3	3.9	6.3		6.9	ns
t_{PLZ}			1.2	5.8		6	2.2	3.9	5.1		5.3	
$t_{sk(o)}$‡									0.5			ns

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

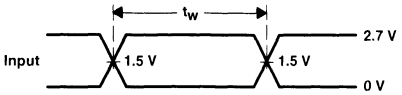
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION

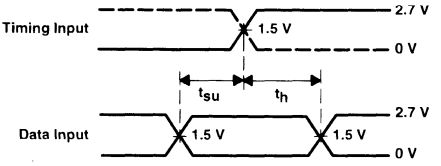


LOAD CIRCUIT

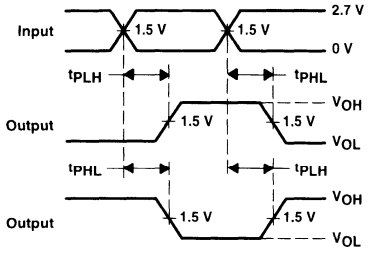
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



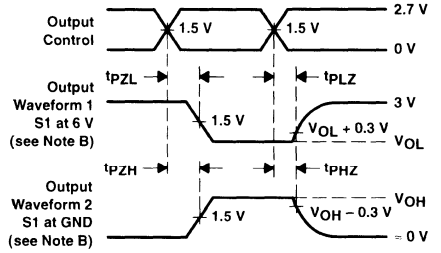
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

Contents

- **Members of the Texas Instruments *SCOPE*™ Family of Testability Products**
- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art 3.3-V ABT Design Supports Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup Resistors**
- **B-Port Outputs of 'LVTH182502A Devices Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required**
- **Compatible With the IEEE Standard 1149.1-1990 (JTAG) Test Access Port and Boundary-Scan Architecture**
- ***SCOPE*™ Instruction Set**
  - **IEEE Standard 1149.1-1990 Required Instructions and Optional CLAMP and HIGHZ**
  - **Parallel-Signature Analysis at Inputs**
  - **Pseudo-Random Pattern Generation From Outputs**
  - **Sample Inputs/Toggle Outputs**
  - **Binary Count From Outputs**
  - **Device Identification**
  - **Even-Parity Opcodes**
- **Packaged in 64-Pin Plastic Thin Quad Flat (PM) Packages Using 0.5-mm Center-to-Center Spacings and 68-Pin Ceramic Quad Flat (HV) Packages Using 25-mil Center-to-Center Spacings**

description

The 'LVTH18502A and 'LVTH182502A scan test devices with 18-bit universal bus transceivers are members of the Texas Instruments SCOPE™ testability integrated-circuit family. This family of devices supports IEEE Standard 1149.1-1990 boundary scan to facilitate testing of complex circuit-board assemblies. Scan access to the test circuitry is accomplished via the 4-wire test access port (TAP) interface.

Additionally, these devices are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

In the normal mode, these devices are 18-bit universal bus transceivers that combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, or clocked modes. They can be used either as two 9-bit transceivers or one 18-bit transceiver. The test circuitry can be activated by the TAP to take snapshot samples of the data appearing at the device pins or to perform a self test on the boundary-test cells. Activating the TAP in the normal mode does not affect the functional operation of the SCOPE™ universal bus transceivers.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A-bus data is latched while CLKAB is held at a static low or high logic level. Otherwise, if LEAB is low, A-bus data is stored on a low-to-high transition of CLKAB. When $\overline{OEAB}$ is low, the B outputs are active. When $\overline{OEAB}$ is high, the B outputs are in the high-impedance state. B-to-A data flow is similar to A-to-B data flow, but uses the $\overline{OEBA}$, LEBA, and CLKBA inputs.

In the test mode, the normal operation of the SCOPE™ universal bus transceivers is inhibited, and the test circuitry is enabled to observe and control the I/O boundary of the device. When enabled, the test circuitry performs boundary-scan test operations according to the protocol described in IEEE Standard 1149.1-1990.

description (continued)

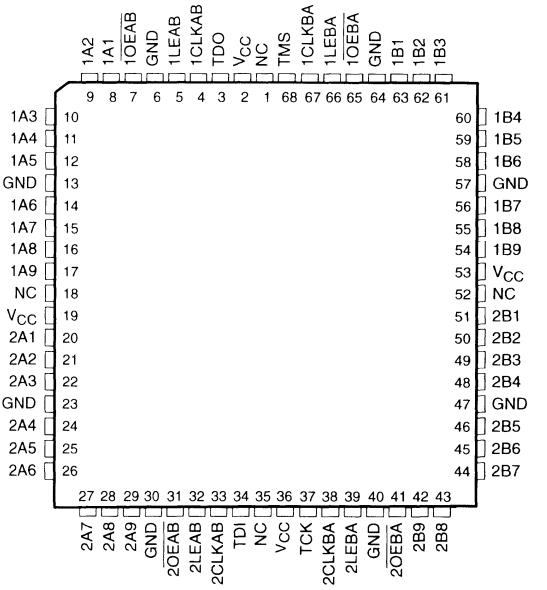
Four dedicated test pins are used to observe and control the operation of the test circuitry: test data input (TDI), test data output (TDO), test mode select (TMS), and test clock (TCK). Additionally, the test circuitry performs other testing functions such as parallel-signature analysis (PSA) on data inputs and pseudo-random pattern generation (PRPG) from data outputs. All testing and scan operations are synchronized to the TAP interface.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The B-port outputs of 'LVTH182502A, which are designed to source or sink up to 12 mA, include 25-Ω series resistors to reduce overshoot and undershoot.

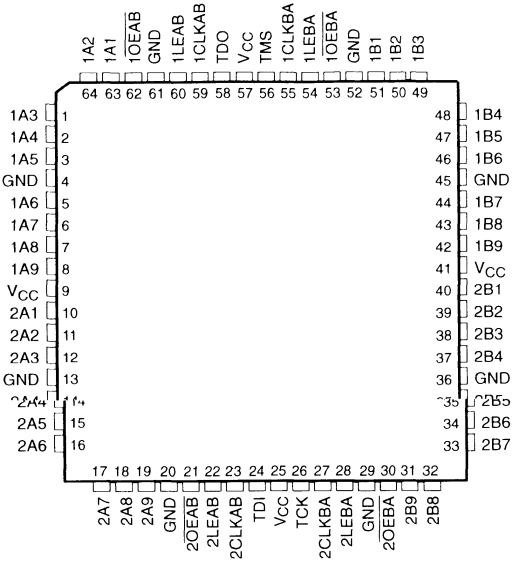
The SN54LVTH18502A and SN54LVTH182502A are characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH18502A and SN74LVTH182502A are characterized for operation from –40°C to 85°C.

SN54LVTH18502A, SN54LVTH182502A . . . HV PACKAGE
(TOP VIEW)



NC – No internal connection

SN74LVTH18502A, SN74LVTH182502A . . . PM PACKAGE
(TOP VIEW)

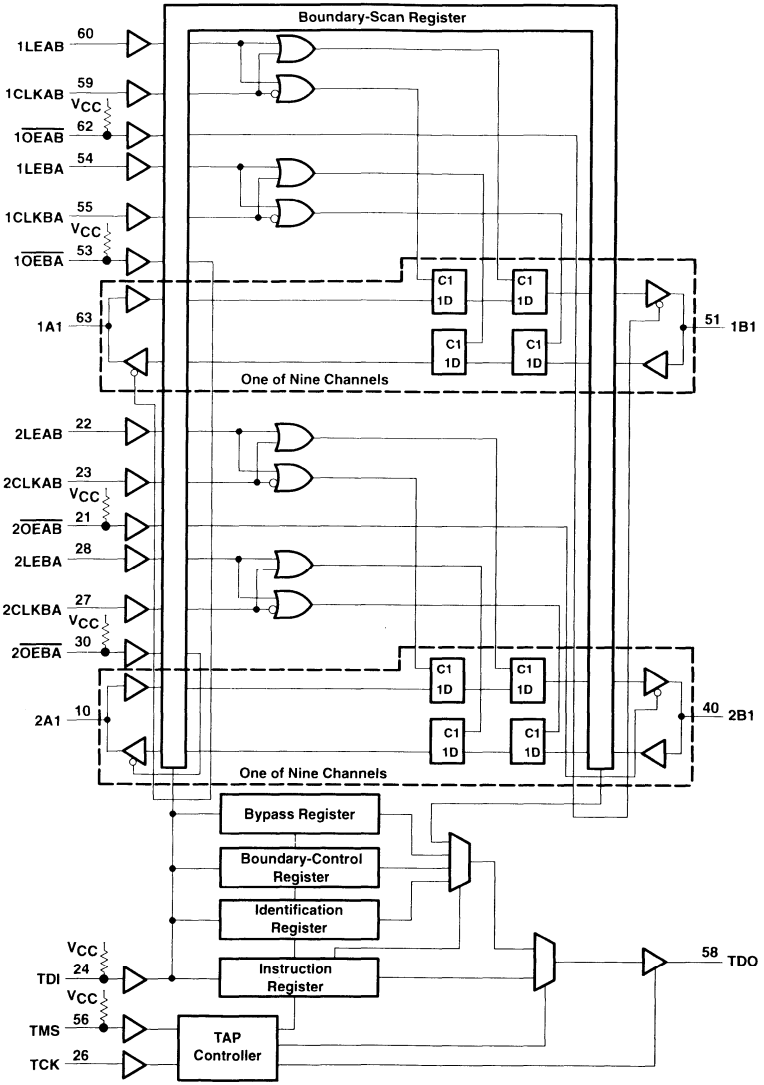


FUNCTION TABLE†
(normal mode, each register)

INPUTS				OUTPUT
$\overline{OEAB}$	LEAB	CLKAB	A	B
L	L	L	X	B_0‡
L	L	↑	L	L
L	L	↑	H	H
L	H	X	L	L
L	H	X	H	H
H	X	X	X	Z

† A-to-B data flow is shown. B-to-A data flow is similar but uses $\overline{OEBA}$, LEBA, and CLKBA.
‡ Output level before the indicated steady-state input conditions are established

functional block diagram



Pin numbers shown are for the PM package.

Terminal Functions

TERMINAL NAME	DESCRIPTION
1A1–1A9, 2A1–2A9	Normal-function A-bus I/O ports. See function table for normal-mode logic.
1B1–1B9, 2B1–2B9	Normal-function B-bus I/O ports. See function table for normal-mode logic.
1CLKAB, 1CLKBA, 2CLKAB, 2CLKBA	Normal-function clock inputs. See function table for normal-mode logic.
GND	Ground
1LEAB, 1LEBA, 2LEAB, 2LEBA	Normal-function latch enables. See function table for normal-mode logic.
$1\overline{OEAB}$, $1\overline{OEBA}$, $2\overline{OEAB}$, $2\overline{OEBA}$	Normal-function output enables. See function table for normal-mode logic. An internal pullup at each terminal forces the terminal to a high level if left unconnected.
TCK	Test clock. One of four terminals required by IEEE Standard 1149.1-1990. Test operations of the device are synchronous to TCK. Data is captured on the rising edge of TCK and outputs change on the falling edge of TCK.
TDI	Test data input. One of four terminals required by IEEE Standard 1149.1-1990. TDI is the serial input for shifting data through the instruction register or selected data register. An internal pullup forces TDI to a high level if left unconnected.
TDO	Test data output. One of four terminals required by IEEE Standard 1149.1-1990. TDO is the serial output for shifting data through the instruction register or selected data register.
TMS	Test mode select. One of four terminals required by IEEE Standard 1149.1-1990. TMS directs the device through its TAP controller states. An internal pullup forces TMS to a high level if left unconnected.
V_{CC}	Supply voltage

test architecture

Serial-test information is conveyed by means of a 4-wire test bus or TAP, that conforms to IEEE Standard 1149.1-1990. Test instructions, test data, and test control signals all are passed along this serial-test bus. The TAP controller monitors two signals from the test bus, TCK and TMS. The TAP controller extracts the synchronization (TCK) and state control (TMS) signals from the test bus and generates the appropriate on-chip control signals for the test structures in the device. Figure 1 shows the TAP-controller state diagram.

The TAP controller is fully synchronous to the TCK signal. Input data is captured on the rising edge of TCK and output data changes on the falling edge of TCK. This scheme ensures data to be captured is valid for fully one-half of the TCK cycle.

The functional block diagram shows the IEEE Standard 1149.1-1990 4-wire test bus and boundary-scan architecture and the relationship among the test bus, the TAP controller, and the test registers. As shown, the device contains an 8-bit instruction register and four test-data registers: a 48-bit boundary-scan register, a 3-bit boundary-control register, a 1-bit bypass register, and a 32-bit device identification register.

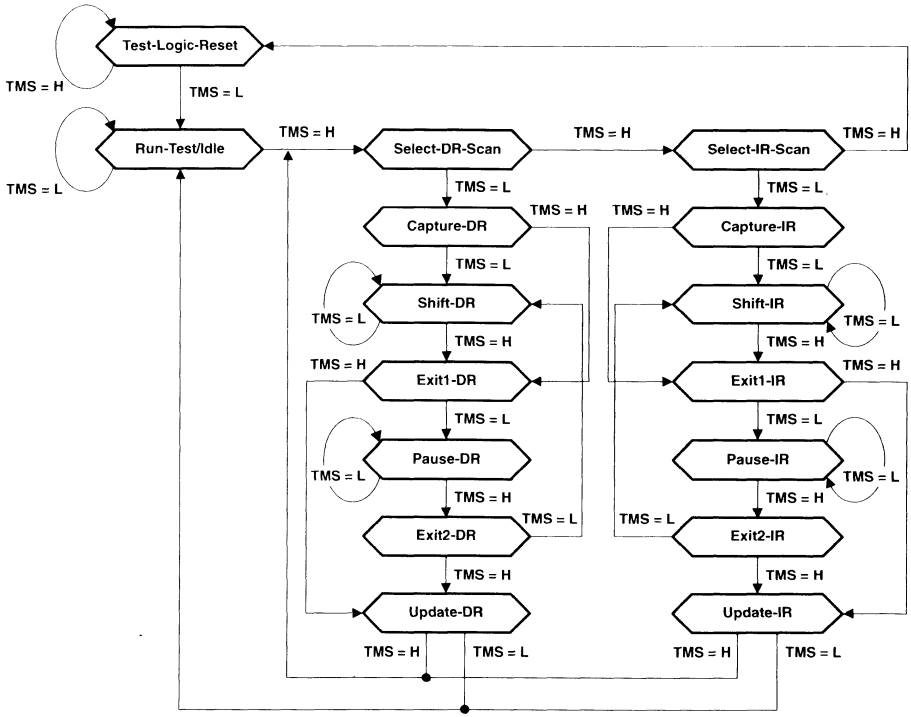


Figure 1. TAP-Controller State Diagram

state diagram description

The TAP controller is a synchronous finite state machine that provides test control signals throughout the device. The state diagram shown in Figure 1 is in accordance with IEEE Standard 1149.1-1990. The TAP controller proceeds through its states based on the level of TMS at the rising edge of TCK.

As shown, the TAP controller consists of 16 states. There are six stable states (indicated by a looping arrow in the state diagram) and ten unstable states. A stable state is a state the TAP controller can retain for consecutive TCK cycles. Any state that does not meet this criterion is an unstable state.

There are two main paths through the state diagram: one to access and control the selected data register and one to access and control the instruction register. Only one register can be accessed at a time.

Test-Logic-Reset

The device powers up in the Test-Logic-Reset state. In the stable Test-Logic-Reset state, the test logic is reset and is disabled so that the normal logic function of the device is performed. The instruction register is reset to an opcode that selects the optional IDCODE instruction, if supported, or the BYPASS instruction. Certain data registers can also be reset to their power-up values.

The state machine is constructed such that the TAP controller returns to the Test-Logic-Reset state in no more than five TCK cycles if TMS is left high. The TMS pin has an internal pullup resistor that forces it high if left unconnected or if a board defect causes it to be open circuited.

For the 'LVTH18502A and 'LVTH182502A, the instruction register is reset to the binary value 10000001, which selects the IDCODE instruction. Bits 47–44 in the boundary-scan register are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., if test mode were invoked the outputs would be at the high-impedance state). Reset-value of other bits in the boundary-scan register should be considered indeterminate. The boundary-control register is reset to the binary value 010, which selects the PSA test operation.

Run-Test/Idle

The TAP controller must pass through the Run-Test/Idle state (from Test-Logic-Reset) before executing any test operations. The Run-Test/Idle state also can be entered following data-register or instruction-register scans. Run-Test/Idle is a stable state in which the test logic can be actively running a test or can be idle. The test operations selected by the boundary-control register are performed while the TAP controller is in the Run-Test/Idle state.

Select-DR-Scan, Select-IR-Scan

No specific function is performed in the Select-DR-Scan and Select-IR-Scan states, and the TAP controller exits either of these states on the next TCK cycle. These states allow the selection of either data-register scan or instruction-register scan.

Capture-DR

When a data-register scan is selected, the TAP controller must pass through the Capture-DR state. In the Capture-DR state, the selected data register can capture a data value as specified by the current instruction. Such capture operations occur on the rising edge of TCK, upon which the TAP controller exits the Capture-DR state.

Shift-DR

Upon entry to the Shift-DR state, the data register is placed in the scan path between TDI and TDO, and on the first falling edge of TCK, TDO goes from the high-impedance state to an active state. TDO enables to the logic level present in the least-significant bit of the selected data register.

While in the stable Shift-DR state, data is serially shifted through the selected data register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-DR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-DR to Shift-DR or from Exit2-DR to Shift-DR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-DR state.

Exit1-DR, Exit2-DR

The Exit1-DR and Exit2-DR states are temporary states that end a data-register scan. It is possible to return to the Shift-DR state from either Exit1-DR or Exit2-DR without recapturing the data register. On the first falling edge of TCK after entry to Exit1-DR, TDO goes from the active state to the high-impedance state.

Pause-DR

No specific function is performed in the stable Pause-DR state, in which the TAP controller can remain indefinitely. The Pause-DR state suspends and resumes data-register scan operations without loss of data.

Update-DR

If the current instruction calls for the selected data register to be updated with current data, such update occurs on the falling edge of TCK, following entry to the Update-DR state.

Capture-IR

When an instruction-register scan is selected, the TAP controller must pass through the Capture-IR state. In the Capture-IR state, the instruction register captures its current status value. This capture operation occurs on the rising edge of TCK, upon which the TAP controller exits the Capture-IR state. For the 'LVTH18502A and 'LVTH182502A, the status value loaded in the Capture-IR state is the fixed binary value 10000001.

Shift-IR

Upon entry to the Shift-IR state, the instruction register is placed in the scan path between TDI and TDO. On the first falling edge of TCK, TDO goes from the high-impedance state to the active state. TDO enables to the logic level present in the least-significant bit of the instruction register.

While in the stable Shift-IR state, instruction data is serially shifted through the instruction register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-IR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-IR to Shift-IR or from Exit2-IR to Shift-IR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-IR state.

Exit1-IR, Exit2-IR

The Exit1-IR and Exit2-IR states are temporary states that end an instruction-register scan. It is possible to return to the Shift-IR state from either Exit1-IR or Exit2-IR without recapturing the instruction register. On the first falling edge of TCK after entry to Exit1-IR, TDO goes from the active state to the high-impedance state.

Pause-IR

No specific function is performed in the stable Pause-IR state, in which the TAP controller can remain indefinitely. The Pause-IR state suspends and resumes instruction-register scan operations without loss of data.

Update-IR

The current instruction is updated and takes effect on the falling edge of TCK, following entry to the Update-IR state.

register overview

With the exception of the bypass and device-identification registers, any test register can be thought of as a serial shift register with a shadow latch on each bit. The bypass and device-identification registers differ in that they contain only a shift register. During the appropriate capture state (Capture-IR for instruction register, Capture-DR for data registers), the shift register can be parallel loaded from a source specified by the current instruction. During the appropriate shift state (Shift-IR or Shift-DR), the contents of the shift register are shifted out from TDO while new contents are shifted in at TDI. During the appropriate update state (Update-IR or Update-DR), the shadow latches are updated from the shift register.

instruction register description

The instruction register (IR) is eight bits long and tells the device what instruction is to be executed. Information contained in the instruction includes the mode of operation (either normal mode, in which the device performs its normal logic function, or test mode, in which the normal logic function is inhibited or altered), the test operation to be performed, which of the four data registers is to be selected for inclusion in the scan path during data-register scans, and the source of data to be captured into the selected data register during Capture-DR.

Table 3 lists the instructions supported by the 'LVTH18502A and 'LVTH182502A. The even-parity feature specified for SCOPE™ devices is supported in this device. Bit 7 of the instruction opcode is the parity bit. Any instructions that are defined for SCOPE™ devices but are not supported by this device default to BYPASS.

During Capture-IR, the IR captures the binary value 10000001. As an instruction is shifted in, this value is shifted out via TDO and can be inspected as verification that the IR is in the scan path. During Update-IR, the value that has been shifted into the IR is loaded into shadow latches. At this time, the current instruction is updated and any specified mode change takes effect. At power up or in the Test-Logic-Reset state, the IR is reset to the binary value 10000001, which selects the IDCODE instruction. The IR order of scan is shown in Figure 2.

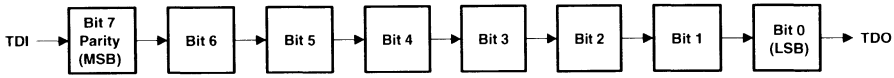


Figure 2. Instruction Register Order of Scan

data register description

boundary-scan register

The boundary-scan register (BSR) is 48 bits long. It contains one boundary-scan cell (BSC) for each normal-function input pin and one BSC for each normal-function I/O pin (one single cell for both input data and output data). The BSR is used 1) to store test data that is to be applied externally to the device output pins, and/or 2) to capture data that appears internally at the outputs of the normal on-chip logic and/or externally at the device input pins.

The source of data to be captured into the BSR during Capture-DR is determined by the current instruction. The contents of the BSR can change during Run-Test/Idle as determined by the current instruction. At power up or in Test-Logic-Reset, BSCs 47–44 are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs are set to benign values (i.e., if test mode were invoked, the outputs would be at the high-impedance state). Reset values of other BSCs should be considered indeterminate.

The BSR order of scan is from TDI through bits 47–0 to TDO. Table 1 shows the BSR bits and their associated device pin signals.

Table 1. Boundary-Scan Register Configuration

BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL
47	$2\overline{OEAB}$	35	2A9-I/O	17	2B9-I/O
46	$1\overline{OEAB}$	34	2A8-I/O	16	2B8-I/O
45	$2\overline{OEBA}$	33	2A7-I/O	15	2B7-I/O
44	$1\overline{OEBA}$	32	2A6-I/O	14	2B6-I/O
43	2CLKAB	31	2A5-I/O	13	2B5-I/O
42	1CLKAB	30	2A4-I/O	12	2B4-I/O
41	2CLKBA	29	2A3-I/O	11	2B3-I/O
40	1CLKBA	28	2A2-I/O	10	2B2-I/O
39	2LEAB	27	2A1-I/O	9	2B1-I/O
38	1LEAB	26	1A9-I/O	8	1B9-I/O
37	2LEBA	25	1A8-I/O	7	1B8-I/O
36	1LEBA	24	1A7-I/O	6	1B7-I/O
—	—	23	1A6-I/O	5	1B6-I/O
—	—	22	1A5-I/O	4	1B5-I/O
—	—	21	1A4-I/O	3	1B4-I/O
—	—	20	1A3-I/O	2	1B3-I/O
—	—	19	1A2-I/O	1	1B2-I/O
—	—	18	1A1-I/O	0	1B1-I/O

boundary-control register

The boundary-control register (BCR) is three bits long. The BCR is used in the context of the boundary-run test (RUNT) instruction to implement additional test operations not included in the basic SCOPE™ instruction set. Such operations include PRPG, PSA, and binary count up (COUNT). Table 4 shows the test operations that are decoded by the BCR.

During Capture-DR, the contents of the BCR are not changed. At power up or in Test-Logic-Reset, the BCR is reset to the binary value 010, which selects the PSA test operation. The BCR order of scan is shown in Figure 3.

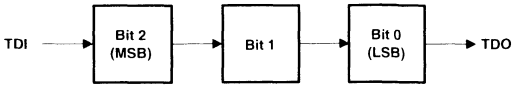


Figure 3. Boundary-Control Register Order of Scan

bypass register

The bypass register is a 1-bit scan path that can be selected to shorten the length of the system scan path, reducing the number of bits per test pattern that must be applied to complete a test operation. During Capture-DR, the bypass register captures a logic 0. The bypass register order of scan is shown in Figure 4.

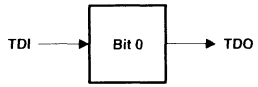


Figure 4. Bypass Register Order of Scan

device-identification register

The device-identification register (IDR) is 32 bits long. It can be selected and read to identify the manufacturer, part number, and version of this device.

For the 'LVTH18502A, the binary value 00110000000000001110000000101111 (3001C02F, hex) is captured (during Capture-DR state) in the IDR to identify this device as Texas Instruments SN54/74LVTH18502A.

For the 'LVTH182502A, the binary value 00110000000000010000100000101111 (3002102F, hex) is captured (during Capture-DR state) in the device-identification register to identify this device as Texas Instruments SN54/74LVTH182502A.

The IDR order of scan is from TDI through bits 31–0 to TDO. Table 2 shows the IDR bits and their significance.

Table 2. Device-Identification Register Configuration

IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE
31	VERSION3	27	PARTNUMBER15	11	MANUFACTURER10†
30	VERSION2	26	PARTNUMBER14	10	MANUFACTURER09†
29	VERSION1	25	PARTNUMBER13	9	MANUFACTURER08†
28	VERSION0	24	PARTNUMBER12	8	MANUFACTURER07†
—	—	23	PARTNUMBER11	7	MANUFACTURER06†
—	—	22	PARTNUMBER10	6	MANUFACTURER05†
—	—	21	PARTNUMBER09	5	MANUFACTURER04†
—	—	20	PARTNUMBER08	4	MANUFACTURER03†
—	—	19	PARTNUMBER07	3	MANUFACTURER02†
—	—	18	PARTNUMBER06	2	MANUFACTURER01†
—	—	17	PARTNUMBER05	1	MANUFACTURER00†
—	—	16	PARTNUMBER04	0	LOGIC1†
—	—	15	PARTNUMBER03	—	—
—	—	14	PARTNUMBER02	—	—
—	—	13	PARTNUMBER01	—	—
—	—	12	PARTNUMBER00	—	—

† Note that for TI products, bits 11–0 of the device-identification register always contain the binary value 000000101111 (02F, hex).

instruction-register opcode description

The instruction-register opcodes are shown in Table 3. The following descriptions detail the operation of each instruction.

Table 3. Instruction-Register Opcodes

BINARY CODE† BIT 7 → BIT 0 MSB → LSB	SCOPE OPCODE	DESCRIPTION	SELECTED DATA REGISTER	MODE
00000000	EXTEST	Boundary scan	Boundary scan	Test
10000001	IDCODE	Identification read	Device identification	Normal
10000010	SAMPLE/PRELOAD	Sample boundary	Boundary scan	Normal
00000011	BYPASS‡	Bypass scan	Bypass	Normal
10000100	BYPASS‡	Bypass scan	Bypass	Normal
00000101	BYPASS‡	Bypass scan	Bypass	Normal
00000110	HIGHZ	Control boundary to high impedance	Bypass	Modified test
10000111	CLAMP	Control boundary to 1/0	Bypass	Test
10001000	BYPASS‡	Bypass scan	Bypass	Normal
00001001	RUNT	Boundary-run test	Bypass	Test
00001010	READBN	Boundary read	Boundary scan	Normal
10001011	READBT	Boundary read	Boundary scan	Test
00001100	CELLTST	Boundary self test	Boundary scan	Normal
10001101	TOPHIP	Boundary toggle outputs	Bypass	Test
10001110	SCANCN	Boundary-control register scan	Boundary control	Normal
00001111	SCANCT	Boundary-control register scan	Boundary control	Test
All others	BYPASS	Bypass scan	Bypass	Normal

† Bit 7 is used to maintain even parity in the 8-bit instruction.
‡ The BYPASS instruction is executed in lieu of a SCOPE™ instruction that is not supported in the 'LVTH18502A or 'LVTH182502A.

boundary scan

This instruction conforms to the IEEE Standard 1149.1-1990 EXTEST instruction. The BSR is selected in the scan path. Data appearing at the device input and I/O pins is captured in the associated BSCs. Data that has been scanned into the I/O BSCs for pins in the output mode is applied to the device I/O pins. Data present at the device pins, except for output enables, is passed through the BSCs to the normal on-chip logic. For I/O pins, the operation of a pin as input or output is determined by the contents of the output-enable BSCs (bits 47–44 of the BSR). When a given output enable is active (logic 0), the associated I/O pins operate in the output mode. Otherwise, the I/O pins operate in the input mode. The device operates in the test mode.

identification read

This instruction conforms to the IEEE Standard 1149.1-1990 IDCODE instruction. The IDR is selected in the scan path. The device operates in the normal mode.

sample boundary

This instruction conforms to the IEEE Standard 1149.1-1990 SAMPLE/PRELOAD instruction. The BSR is selected in the scan path. Data appearing at the device input pins and I/O pins in the input mode is captured in the associated BSCs, while data appearing at the outputs of the normal on-chip logic is captured in the BSCs associated with I/O pins in the output mode. The device operates in the normal mode.

bypass scan

This instruction conforms to the IEEE Standard 1149.1-1990 BYPASS instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the normal mode.

control boundary to high impedance

This instruction conforms to the IEEE Standard 1149.1a-1993 HIGHZ instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in a modified test mode in which all device I/O pins are placed in the high-impedance state, the device input pins remain operational, and the normal on-chip logic function is performed.

control boundary to 1/0

This instruction conforms to the IEEE Standard 1149.1a-1993 CLAMP instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the I/O BSCs for pins in the output mode is applied to the device I/O pins. The device operates in the test mode.

boundary-run test

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the test mode. The test operation specified in the BCR is executed during Run-Test/Idle. The five test operations decoded by the BCR are: sample inputs/toggle outputs (TOPSIP), PRPG, PSA, simultaneous PSA and PRPG (PSA/PRPG), and simultaneous PSA and binary count up (PSA/COUNT).

boundary read

The BSR is selected in the scan path. The value in the BSR remains unchanged during Capture-DR. This instruction is useful for inspecting data after a PSA operation.

boundary self test

The BSR is selected in the scan path. All BSCs capture the inverse of their current values during Capture-DR. In this way, the contents of the shadow latches can be read out to verify the integrity of both shift-register and shadow-latch elements of the BSR. The device operates in the normal mode.

boundary toggle outputs

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK in Run-Test/Idle and is then updated in the shadow latches and applied to the associated device I/O pins on each falling edge of TCK in Run-Test/Idle. Data in the input-mode BSCs remains constant. Data appearing at the device input or I/O pins is not captured in the input-mode BSCs. The device operates in the test mode.

boundary-control-register scan

The BCR is selected in the scan path. The value in the BCR remains unchanged during Capture-DR. This operation must be performed before a boundary-run test operation to specify which test operation is to be executed.

boundary-control-register opcode description

The BCR opcodes are decoded from BCR bits 2–0, as shown in Table 4. The selected test operation is performed while the RUNT instruction is executed in the Run-Test/Idle state. The following descriptions detail the operation of each BCR instruction and illustrate the associated PSA and PRPG algorithms.

Table 4. Boundary-Control Register Opcodes

BINARY CODE BIT 2 → BIT 0 MSB → LSB	DESCRIPTION
X00	Sample inputs/toggle outputs (TOPSIP)
X01	Pseudo-random pattern generation/36-bit mode (PRPG)
X10	Parallel-signature analysis/36-bit mode (PSA)
011	Simultaneous PSA and PRPG/18-bit mode (PSA/PRPG)
111	Simultaneous PSA and binary count up/18-bit mode (PSA/COUNT)

While the control input BSCs (bits 47–36) are not included in the toggle, PSA, PRPG, or COUNT algorithms, the output-enable BSCs (bits 47–44 of the BSR) control the drive state (active or high impedance) of the selected device output pins. These BCR instructions are only valid when both bytes of the device are operating in one direction of data flow (i.e., $1\overline{OEAB} \neq 1\overline{OEBA}$ and $2\overline{OEAB} \neq 2\overline{OEBA}$) and in the same direction of data flow (i.e., $1\overline{OEAB} = 2\overline{OEAB}$ and $1\overline{OEBA} = 2\overline{OEBA}$). Otherwise, the bypass instruction is operated.

sample inputs/toggle outputs (TOPSIP)

Data appearing at the selected device input-mode I/O pins is captured in the shift-register elements of the associated BSCs on each rising edge of TCK. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK.

pseudo-random pattern generation (PRPG)

A pseudo-random pattern is generated in the shift-register elements of the selected BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device output-mode I/O pins on each falling edge of TCK. Figures 5 and 6 show the 36-bit linear-feedback shift-register algorithms through which the patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

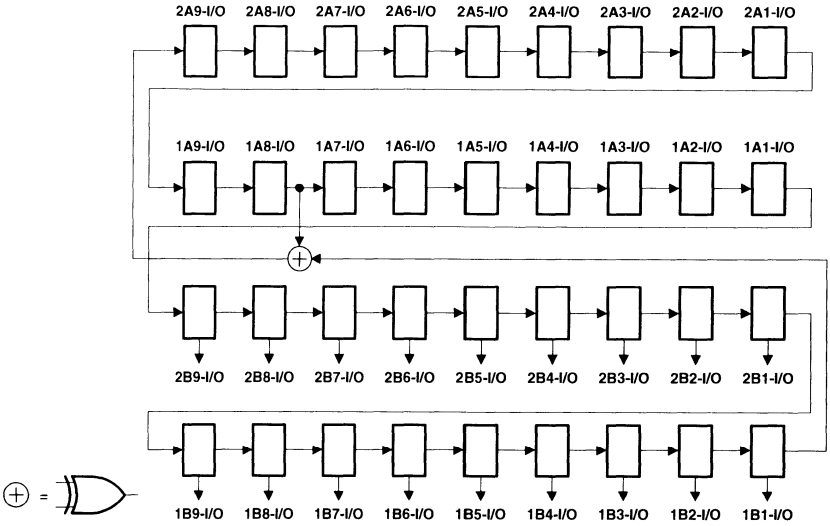


Figure 5. 36-Bit PRPG Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 0, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 1)

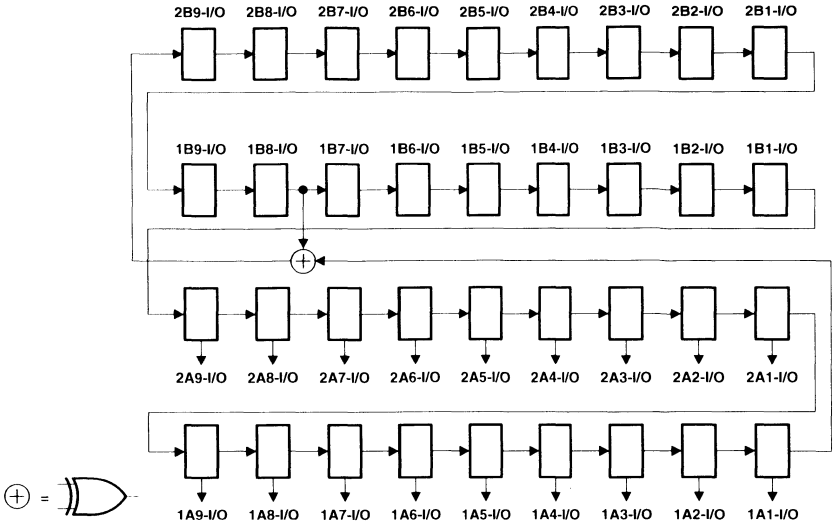


Figure 6. 36-Bit PRPG Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

parallel-signature analysis (PSA)

Data appearing at the selected device input-mode I/O pins is compressed into a 36-bit parallel signature in the shift-register elements of the selected BSCs on each rising edge of TCK. Data in the shadow latches of the selected output-mode BSCs remains constant and is applied to the associated device I/O pins. Figures 7 and 8 show the 36-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

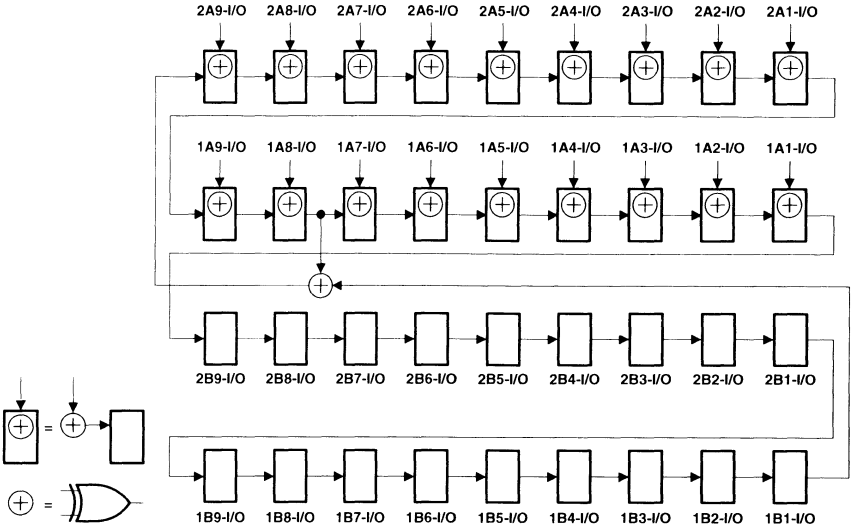


Figure 7. 36-Bit PSA Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 0, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 1)

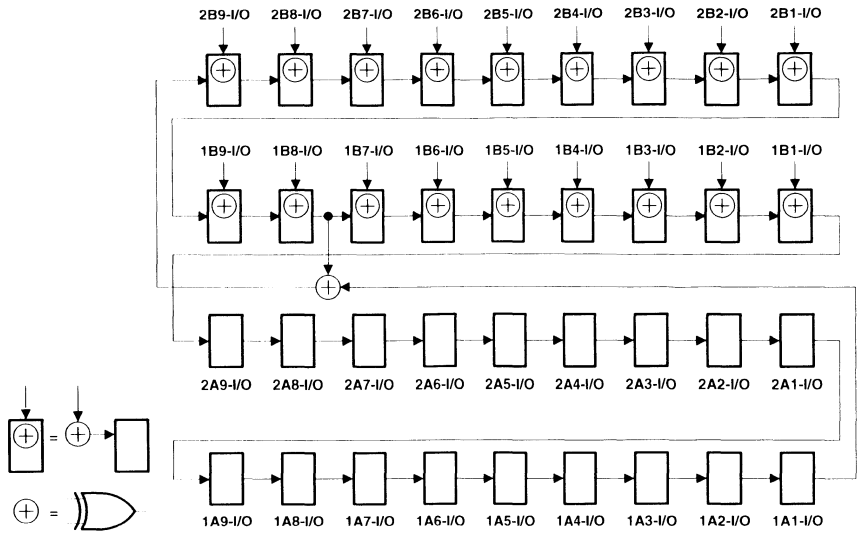


Figure 8. 36-Bit PSA Configuration (1$\overline{OEAB}$ = 2$\overline{OEAB}$ = 1, 1$\overline{OEBA}$ = 2$\overline{OEBA}$ = 0)

simultaneous PSA and PRPG (PSA/PRPG)

Data appearing at the selected device input-mode I/O pins is compressed into an 18-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, an 18-bit pseudo-random pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 9 and 10 show the 18-bit linear-feedback shift-register algorithms through which the signature and patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

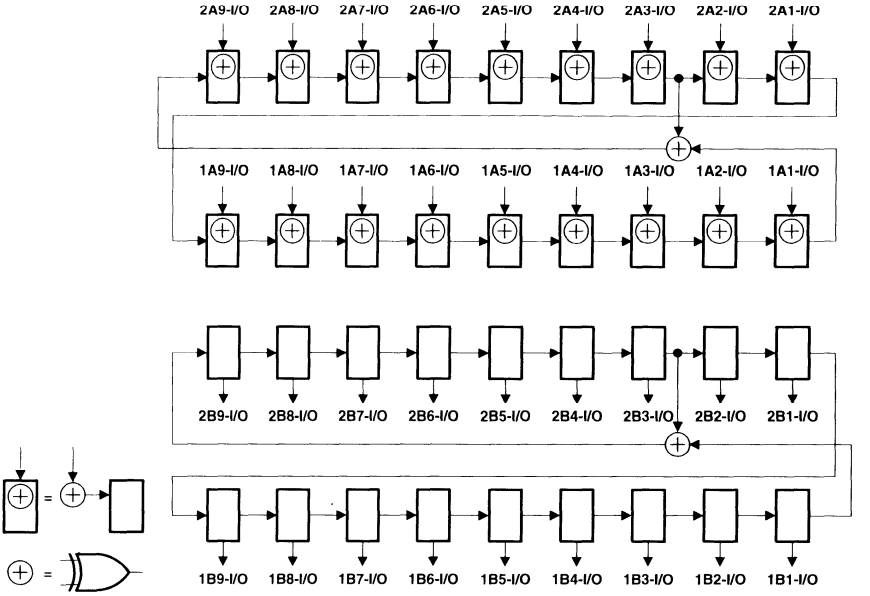


Figure 9. 18-Bit PSA/PRPG Configuration (1$\overline{OEAB}$ = 2$\overline{OEAB}$ = 0, 1$\overline{OEBA}$ = 2$\overline{OEBA}$ = 1)

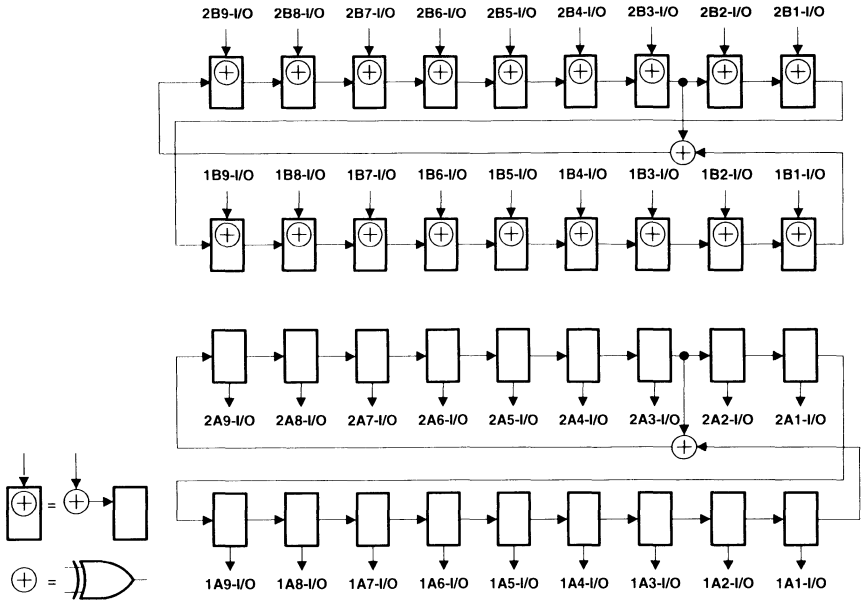


Figure 10. 18-Bit PSA/PRPG Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

simultaneous PSA and binary count up (PSA/COUNT)

Data appearing at the selected device input-mode I/O pins is compressed into an 18-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, an 18-bit binary count-up pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 11 and 12 show the 18-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

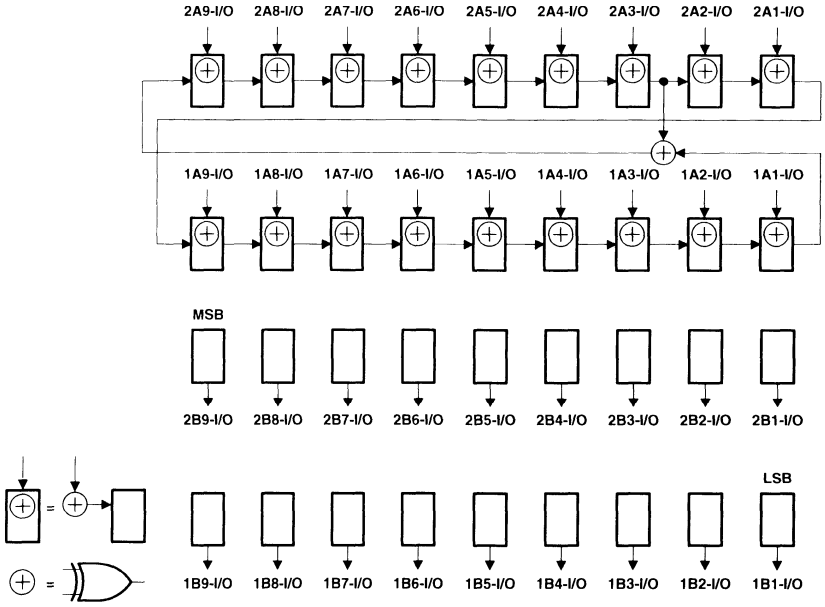


Figure 11. 18-Bit PSA/COUNT Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 0, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 1)

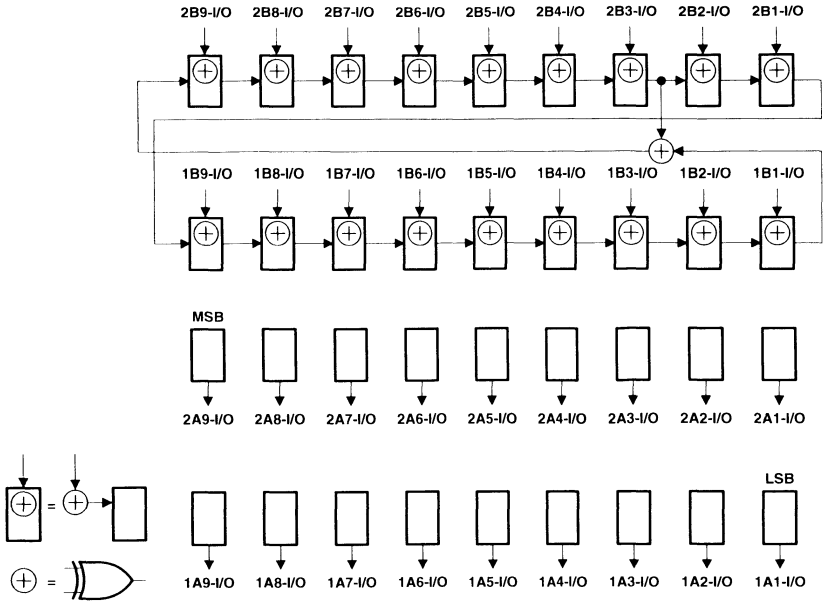


Figure 12. 18-Bit PSA/COUNT Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

timing description

All test operations of the 'LVTH18502A and 'LVTH182502A are synchronous to the TCK signal. Data on the TDI, TMS, and normal-function inputs is captured on the rising edge of TCK. Data appears on the TDO and normal-function output pins on the falling edge of TCK. The TAP controller is advanced through its states (as shown in Figure 1) by changing the value of TMS on the falling edge of TCK and then applying a rising edge to TCK.

A simple timing example is shown in Figure 13. In this example, the TAP controller begins in the Test-Logic-Reset state and is advanced through its states, as necessary, to perform one instruction-register scan and one data-register scan. While in the Shift-IR and Shift-DR states, TDI is used to input serial data, and TDO is used to output serial data. The TAP controller is then returned to the Test-Logic-Reset state. Table 5 details the operation of the test circuitry during each TCK cycle.

Table 5. Explanation of Timing Example

TCK CYCLE(S)	TAP STATE AFTER TCK	DESCRIPTION
1	Test-Logic-Reset	TMS is changed to a logic 0 value on the falling edge of TCK to begin advancing the TAP controller toward the desired state.
2	Run-Test/Idle	
3	Select-DR-Scan	
4	Select-IR-Scan	
5	Capture-IR	The IR captures the 8-bit binary value 10000001 on the rising edge of TCK as the TAP controller exits the Capture-IR state.
6	Shift-IR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
7–13	Shift-IR	One bit is shifted into the IR on each TCK rising edge. With TDI held at a logic 1 value, the 8-bit binary value 11111111 is serially scanned into the IR. At the same time, the 8-bit binary value 10000001 is serially scanned out of the IR via TDO. In TCK cycle 13, TMS is changed to a logic 1 value to end the IR scan on the next TCK cycle. The last bit of the instruction is shifted as the TAP controller advances from Shift-IR to Exit1-IR.
14	Exit1-IR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
15	Update-IR	The IR is updated with the new instruction (BYPASS) on the falling edge of TCK.
16	Select-DR-Scan	
17	Capture-DR	The bypass register captures a logic 0 value on the rising edge of TCK as the TAP controller exits the Capture-DR state.
18	Shift-DR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
19–20	Shift-DR	The binary value 101 is shifted in via TDI, while the binary value 010 is shifted out via TDO.
21	Exit1-DR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
22	Update-DR	The selected data register is updated with the new data on the falling edge of TCK.
23	Select-DR-Scan	
24	Select-IR-Scan	
25	Test-Logic-Reset	Test operation completed

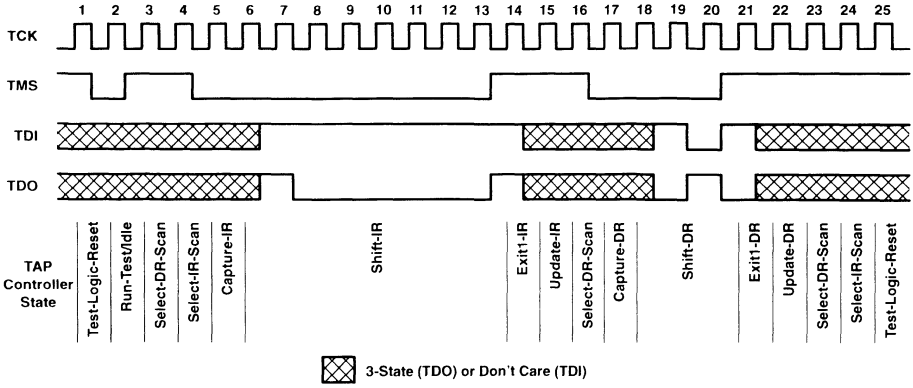


Figure 13. Timing Example

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH18502A ..... 96 mA
SN54LVTH182502A (A port or TDO) ..... 96 mA
SN54LVTH182502A (B port) ..... 30 mA
SN74LVTH18502A ..... 128 mA
SN74LVTH182502A (A port or TDO) ..... 128 mA
SN74LVTH182502A (B port) ..... 30 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH18502A ..... 48 mA
SN54LVTH182502A (A port or TDO) .... 48 mA
SN54LVTH182502A (B port) ..... 30 mA
SN74LVTH18502A ..... 64 mA
SN74LVTH182502A (A port or TDO) .... 64 mA
SN74LVTH182502A (B port) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): PM package ..... 1 W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings can be exceeded if the input and output clamp-current ratings are observed.
2. This current only flows when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 75 mils. For more information, refer to the *Package Thermal Considerations* application note in the *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002.

recommended operating conditions

			SN54LVTH18502A		SN74LVTH18502A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			24		32	mA
I_{OL}†	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH18502A			SN74LVTH18502A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –3 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –8 mA	2.4			2.4			
			I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	CLK, LE, TCK	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or MAX‡,	V_I = 5.5 V			10			10	
	$\overline{OE}$, TDI, TMS	V_{CC} = 3.6 V	V_I = 5.5 V			5			5	
			V_I = V_{CC}			1			1	
			V_I = 0	–25		–100	–25		–100	
	A or B ports§	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$¶	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75		500	75	150	500	µA
			V_I = 2 V	–75		–500	–75	–150	–500	
I_{OZH}	TDO	V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}	TDO	V_{CC} = 3.6 V,	V_O = 0.5 V			–1			–1	µA
I_{OZPU}	TDO	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{OZPD}	TDO	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.6	2		0.6	2	mA
			Outputs low		18	24		18	24	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}#		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.5			0.5	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			10			10		pF
C_o		V_O = 3 V or 0			8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

				SN54LVTH18502A				SN74LVTH18502A				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA		0	100	0	80	0	100	0	80	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low		4.4		5.6		4.4		5.6		ns
		LEAB or LEBA high		3		3		3		3		
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑		2.8		3		2.8		3		ns
		A before LEAB↓ or B before LEBA↓	CLK high	1.5		0.7		1.5		0.7		
			CLK low	1.6		1.6		1.6		1.6		
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑		1.4		1.1		1.4		1.1		ns
		A after LEAB↓ or B after LEBA↓		3.1		3.5		3.1		3.5		

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

			SN54LVTH18502A				SN74LVTH18502A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, LE, or $\overline{OE}$ before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, LE, or $\overline{OE}$ after TCK↑	1.5		1		1.5		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18502A				SN74LVTH18502A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		100		80		100		80		MHz
t_{PLH}	A or B	B or A	1.5	5.1		5.8	1.5	4.9		5.6	ns
t_{PHL}			1.5	5.1		5.8	1.5	4.9		5.6	
t_{PLH}	CLKAB or CLKBA	B or A	1.5	6.3		7.2	1.5	5.8		6.8	ns
t_{PHL}			1.5	6.3		7.2	1.5	5.8		6.8	
t_{PLH}	LEAB or LEBA	B or A	1.5	7.8		9.2	1.5	7.4		8.4	ns
t_{PHL}			1.5	6		6.6	1.5	5.7		6.4	
t_{PZH}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	1.5	7.6		8.5	1.5	7.1		8.3	ns
t_{PZL}			1.5	7.6		8.5	1.5	7.1		8.3	
t_{PHZ}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.5	8.3		8.8	2.5	7.8		8.4	ns
t_{PLZ}			2.5	8.3		8.8	2.5	7.8		8.4	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18502A				SN74LVTH18502A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

recommended operating conditions

			SN54LVTH182502A		SN74LVTH182502A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	A port, TDO		–24		–32	mA
		B port		–12		–12	
I_{OL}	Low-level output current	A port, TDO		24		32	mA
		B port		12		12	
I_{OL}†	Low-level output current	A port, TDO		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH182502A			SN74LVTH182502A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}	A, B, TDO	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA	V_{CC}−0.2			V_{CC}−0.2			V
	A port, TDO	V_{CC} = 2.7 V,	I_{OH} = −3 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = −8 mA	2.4			2.4			
			I_{OH} = −24 mA	2						
			I_{OH} = −32 mA				2			
	B port	V_{CC} = 3 V,	I_{OH} = −12 mA	2			2			
V_{OL}	A, B, TDO	V_{CC} = 2.7 V,	I_{OL} = 100 µA			0.2			0.2	V
	A port, TDO	V_{CC} = 2.7 V,	I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
	B port	V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	
I_I	CLK, LE, TCK	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or MAX‡,	V_I = 5.5 V			10			10	
	$\overline{OE}$, TDI, TMS	V_{CC} = 3.6 V	V_I = 5.5 V			5			5	
			V_I = V_{CC}			1			1	
			V_I = 0	−25		−100	−25		−100	
	A or B ports§	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$¶	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75		500	75	150	500	µA
			V_I = 2 V	−75		−500	−75	−150	−500	
I_{OZH}	TDO	V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}	TDO	V_{CC} = 3.6 V,	V_O = 0.5 V			−1			−1	µA
I_{OZPU}	TDO	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{OZPD}	TDO	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.6	2		0.6	2	mA
			Outputs low		18	24		18	24	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}#		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.5			0.5	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			10			10		pF
C_o		V_O = 3 V or 0			8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

				SN54LVTH182502A				SN74LVTH182502A				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA		0	100	0	80	0	100	0	80	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low		4.4		5.6		4.4		5.6		ns
		LEAB or LEBA high		3		3		3		3		
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑		2.8		3		2.8		3		ns
		A before LEAB↓ or B before LEBA↓	CLK high	1.5		0.7		1.5		0.7		
			CLK low	1.6		1.6		1.6		1.6		
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑		1.4		1.1		1.4		1.1		ns
		A after LEAB↓ or B after LEBA↓		3.1		3.5		3.1		3.5		

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

			SN54LVTH182502A				SN74LVTH182502A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, LE, or $\overline{OE}$ before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, LE, or $\overline{OE}$ after TCK↑	1.5		1		1.5		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

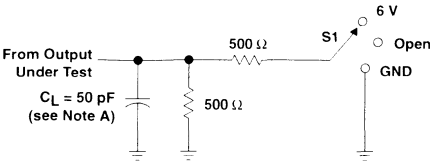
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182502A				SN74LVTH182502A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		100		80		100		80		MHz
t_{PLH}	A	B	1.5	6		6.7	1.5	5.7		6.4	ns
t_{PHL}			1.5	6		6.7	1.5	5.7		6.4	
t_{PLH}	B	A	1.5	5.1		5.8	1.5	4.9		5.6	ns
t_{PHL}			1.5	5.1		5.8	1.5	4.9		5.6	
t_{PLH}	CLKAB	B	1.5	7.1		8.1	1.5	6.7		7.7	ns
t_{PHL}			1.5	7.1		8.1	1.5	6.7		7.7	
t_{PLH}	CLKBA	A	1.5	6.3		7.2	1.5	5.8		6.8	ns
t_{PHL}			1.5	6.3		7.2	1.5	5.8		6.8	
t_{PLH}	LEAB	B	1.5	8.7		9.7	1.5	8.2		9.2	ns
t_{PHL}			1.5	6.5		6.9	1.5	6.2		6.7	
t_{PLH}	LEBA	A	1.5	7.8		9.2	1.5	7.4		8.4	ns
t_{PHL}			1.5	6		6.6	1.5	5.7		6.4	
t_{PZH}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	1.5	8.4		9.6	1.5	7.9		8.7	ns
t_{PZL}			1.5	8.4		9.6	1.5	7.9		8.7	
t_{PHZ}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.5	9.1		9.3	2.5	8.4		8.9	ns
t_{PLZ}			2.5	9.1		9.3	2.5	8.4		8.9	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

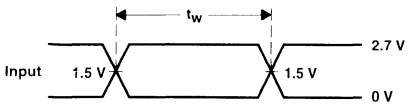
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182502A				SN74LVTH182502A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

PARAMETER MEASUREMENT INFORMATION

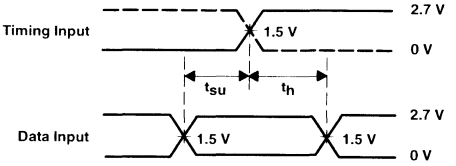


LOAD CIRCUIT

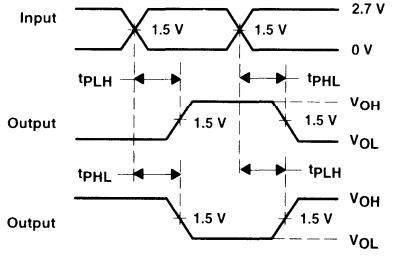
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



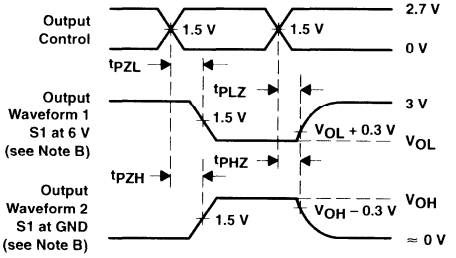
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 14. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *SCOPE*™ Family of Testability Products**
- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art 3.3-V ABT Design Supports Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **B-Port Outputs of 'LVTH182504A Devices Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required**
- **Compatible With the IEEE Std 1149.1-1990 (JTAG) Test Access Port and Boundary-Scan Architecture**
- ***SCOPE* Instruction Set**
  - **IEEE Std 1149.1-1990 Required Instructions and Optional CLAMP and HIGHZ**
  - **Parallel-Signature Analysis at Inputs**
  - **Pseudo-Random Pattern Generation From Outputs**
  - **Sample Inputs/Toggle Outputs**
  - **Binary Count From Outputs**
  - **Device Identification**
  - **Even-Parity Opcodes**
- **Packaged in 64-Pin Plastic Thin Quad Flat (PM) Packages Using 0.5-mm Center-to-Center Spacings and 68-Pin Ceramic Quad Flat (HV) Packages Using 25-mil Center-to-Center Spacings**

description

The 'LVTH18504A and 'LVTH182504A scan test devices with 20-bit universal bus transceivers are members of the Texas Instruments (TI) SCOPE testability integrated-circuit family. This family of devices supports IEEE Std 1149.1-1990 boundary scan to facilitate testing of complex circuit-board assemblies. Scan access to the test circuitry is accomplished via the 4-wire test access port (TAP) interface.

Additionally, these devices are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

In the normal mode, these devices are 20-bit universal bus transceivers that combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, or clocked modes. The test circuitry can be activated by the TAP to take snapshot samples of the data appearing at the device pins or to perform a self-test on the boundary-test cells. Activating the TAP in the normal mode does not affect the functional operation of the SCOPE universal bus transceivers.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A-bus data is latched while $\overline{CLKENAB}$ is high and/or CLKAB is held at a static low or high logic level. Otherwise, if LEAB is low and $\overline{CLKENAB}$ is low, A-bus data is stored on a low-to-high transition of CLKAB. When $\overline{OEAB}$ is low, the B outputs are active. When $\overline{OEAB}$ is high, the B outputs are in the high-impedance state. B-to-A data flow is similar to A-to-B data flow, but uses the $\overline{OEBA}$, LEBA, $\overline{CLKENBA}$, and CLKBA inputs.

In the test mode, the normal operation of the SCOPE universal bus transceivers is inhibited, and the test circuitry is enabled to observe and control the I/O boundary of the device. When enabled, the test circuitry performs boundary-scan test operations according to the protocol described in IEEE Std 1149.1-1990.

description (continued)

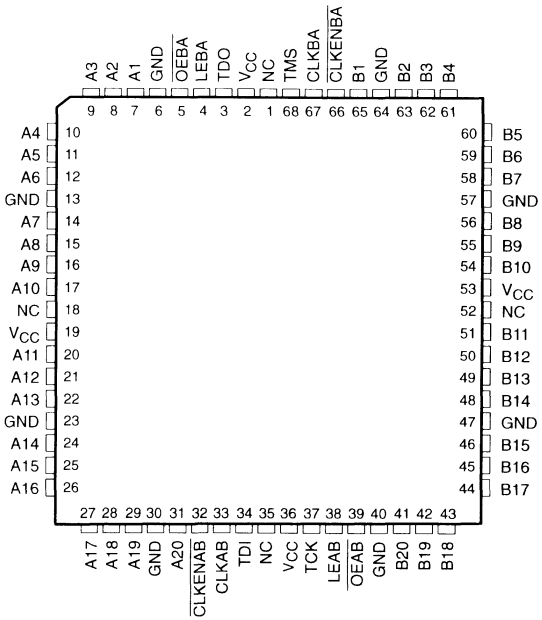
Four dedicated test pins are used to observe and control the operation of the test circuitry: test data input (TDI), test data output (TDO), test mode select (TMS), and test clock (TCK). Additionally, the test circuitry performs other testing functions, such as parallel-signature analysis (PSA) on data inputs and pseudo-random pattern generation (PRPG) from data outputs. All testing and scan operations are synchronized to the TAP interface.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The B-port outputs of 'LVTH182504A, which are designed to source or sink up to 12 mA, include equivalent 25-Ω series resistors to reduce overshoot and undershoot.

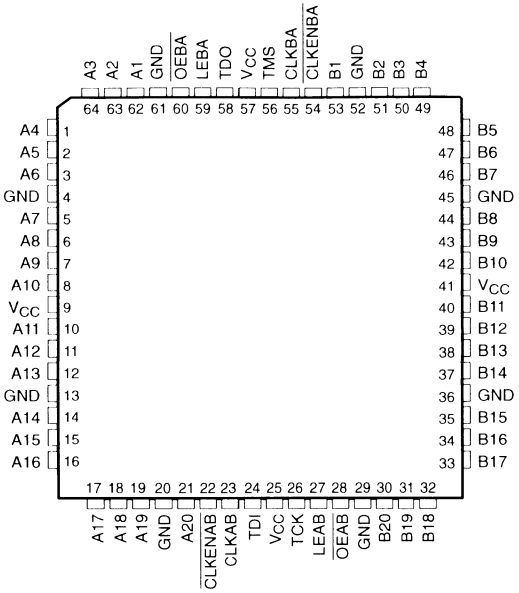
The SN54LVTH18504A and SN54LVTH182504A are characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH18504A and SN74LVTH182504A are characterized for operation from –40°C to 85°C.

SN54LVTH18504A, SN54LVTH182504A . . . HV PACKAGE
(TOP VIEW)



NC – No internal connection

SN74LVTH18504A, SN74LVTH182504A . . . PM PACKAGE
(TOP VIEW)

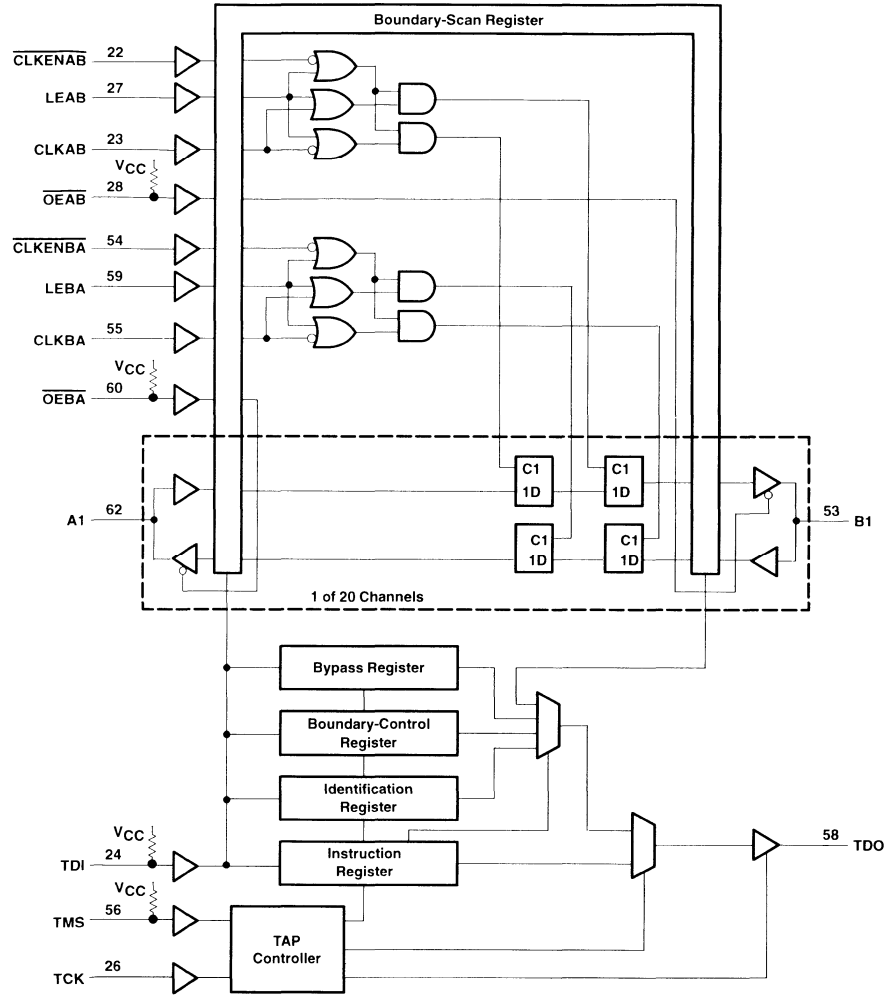


FUNCTION TABLE†
(normal mode, each register)

INPUTS					OUTPUT
$\overline{OEAB}$	LEAB	$\overline{CLKENAB}$	CLKAB	A	B
L	L	L	L	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	H	X	X	B_0‡
L	H	X	X	L	L
L	H	X	X	H	H
H	X	X	X	X	Z

† A-to-B data flow is shown. B-to-A data flow is similar, but uses $\overline{OEBA}$, LEBA, $\overline{CLKENBA}$, and CLKBA.
‡ Output level before the indicated steady-state input conditions were established

functional block diagram



Pin numbers shown are for the PM package.

Terminal Functions

TERMINAL NAME	DESCRIPTION
A1–A20	Normal-function A-bus I/O ports. See function table for normal-mode logic.
B1–B20	Normal-function B-bus I/O ports. See function table for normal-mode logic.
CLKAB, CLKBA	Normal-function clock inputs. See function table for normal-mode logic.
$\overline{\text{CLKENAB}}$, $\overline{\text{CLKENBA}}$	Normal-function clock enables. See function table for normal-mode logic.
GND	Ground
LEAB, LEBA	Normal-function latch enables. See function table for normal-mode logic.
$\overline{\text{OEAB}}$, $\overline{\text{OEBA}}$	Normal-function output enables. See function table for normal-mode logic. An internal pullup at each terminal forces the terminal to a high level if left unconnected.
TCK	Test clock. One of four terminals required by IEEE Std 1149.1-1990. Test operations of the device are synchronous to TCK. Data is captured on the rising edge of TCK and outputs change on the falling edge of TCK.
TDI	Test data input. One of four terminals required by IEEE Std 1149.1-1990. TDI is the serial input for shifting data through the instruction register or selected data register. An internal pullup forces TDI to a high level if left unconnected.
TDO	Test data output. One of four terminals required by IEEE Std 1149.1-1990. TDO is the serial output for shifting data through the instruction register or selected data register.
TMS	Test mode select. One of four terminals required by IEEE Std 1149.1-1990. TMS directs the device through its TAP controller states. An internal pullup forces TMS to a high level if left unconnected.
V_{CC}	Supply voltage

test architecture

Serial-test information is conveyed by means of a 4-wire test bus or TAP that conforms to IEEE Std 1149.1-1990. Test instructions, test data, and test control signals are passed along this serial-test bus. The TAP controller monitors two signals from the test bus: TCK and TMS. The TAP controller extracts the synchronization (TCK) and state control (TMS) signals from the test bus and generates the appropriate on-chip control signals for the test structures in the device. Figure 1 shows the TAP-controller state diagram.

The TAP controller is fully synchronous to the TCK signal. Input data is captured on the rising edge of TCK and output data changes on the falling edge of TCK. This scheme ensures data to be captured is valid for fully one-half of the TCK cycle.

The functional block diagram shows the IEEE Std 1149.1-1990 4-wire test bus and boundary-scan architecture and the relationships of the test bus, the TAP controller, and the test registers. As shown, the device contains an 8-bit instruction register and four test data registers: a 48-bit boundary-scan register, a 3-bit boundary-control register, a 1-bit bypass register, and a 32-bit device-identification register.

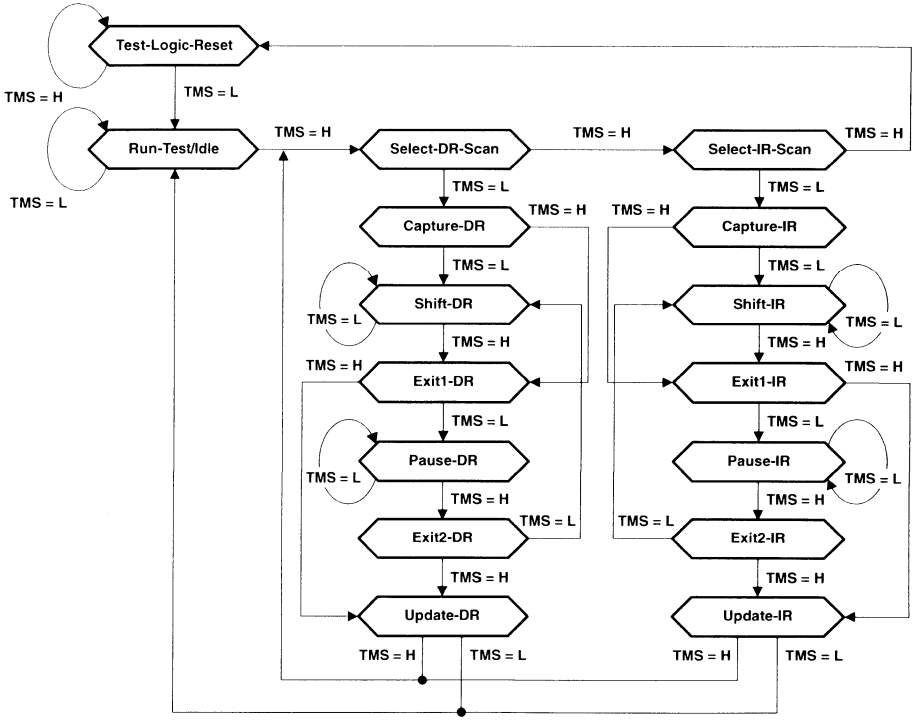


Figure 1. TAP-Controller State Diagram

state diagram description

The TAP controller is a synchronous finite-state machine that provides test control signals throughout the device. The state diagram shown in Figure 1 is in accordance with IEEE Std 1149.1-1990. The TAP controller proceeds through its states, based on the level of TMS at the rising edge of TCK.

As shown, the TAP controller consists of 16 states. There are six stable states (indicated by a looping arrow in the state diagram) and ten unstable states. A stable state is defined as a state the TAP controller can retain for consecutive TCK cycles. Any state that does not meet this criterion is an unstable state.

There are two main paths through the state diagram: one to access and control the selected data register and one to access and control the instruction register. Only one register at a time can be accessed.

Test-Logic-Reset

The device powers up in the Test-Logic-Reset state. In the stable Test-Logic-Reset state, the test logic is reset and is disabled so that the normal logic function of the device is performed. The instruction register is reset to an opcode that selects the optional IDCODE instruction, if supported, or the BYPASS instruction. Certain data registers also can be reset to their power-up values.

The state machine is constructed such that the TAP controller returns to the Test-Logic-Reset state in no more than five TCK cycles if TMS is left high. The TMS pin has an internal pullup resistor that forces it high if left unconnected or if a board defect causes it to be open circuited.

For the 'LVTH18504A and 'LVTH182504A, the instruction register is reset to the binary value 10000001, which selects the IDCODE instruction. Bits 47–46 in the boundary-scan register are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., if test mode were invoked, the outputs would be at high-impedance state). Reset values of other bits in the boundary-scan register should be considered indeterminate. The boundary-control register is reset to the binary value 010, which selects the PSA test operation.

Run-Test/Idle

The TAP controller must pass through the Run-Test/Idle state (from Test-Logic-Reset) before executing any test operations. The Run-Test/Idle state also can be entered following data-register or instruction-register scans. Run-Test/Idle is a stable state in which the test logic can be actively running a test or can be idle. The test operations selected by the boundary-control register are performed while the TAP controller is in the Run-Test/Idle state.

Select-DR-Scan, Select-IR-Scan

No specific function is performed in the Select-DR-Scan and Select-IR-Scan states, and the TAP controller exits either of these states on the next TCK cycle. These states allow the selection of either data-register scan or instruction-register scan.

Capture-DR

When a data-register scan is selected, the TAP controller must pass through the Capture-DR state. In the Capture-DR state, the selected data register can capture a data value as specified by the current instruction. Such capture operations occur on the rising edge of TCK, upon which the TAP controller exits the Capture-DR state.

Shift-DR

Upon entry to the Shift-DR state, the data register is placed in the scan path between TDI and TDO. On the first falling edge of TCK, TDO goes from the high-impedance state to an active state. TDO enables to the logic level present in the least-significant bit of the selected data register.

While in the stable Shift-DR state, data is serially shifted through the selected data register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-DR state (i.e., no shifting occurs during the TCK cycle, in which the TAP controller changes from Capture-DR to Shift-DR or from Exit2-DR to Shift-DR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-DR state.

Exit1-DR, Exit2-DR

The Exit1-DR and Exit2-DR states are temporary states that end a data-register scan. It is possible to return to the Shift-DR state from either Exit1-DR or Exit2-DR without recapturing the data register. On the first falling edge of TCK after entry to Exit1-DR, TDO goes from the active state to the high-impedance state.

Pause-DR

No specific function is performed in the stable Pause-DR state, in which the TAP controller can remain indefinitely. The Pause-DR state suspends and resumes data-register scan operations without loss of data.

Update-DR

If the current instruction calls for the selected data register to be updated with current data, such updates occur on the falling edge of TCK, following entry to the Update-DR state.

Capture-IR

When an instruction-register scan is selected, the TAP controller must pass through the Capture-IR state. In the Capture-IR state, the instruction register captures its current status value. This capture operation occurs on the rising edge of TCK, upon which the TAP controller exits the Capture-IR state. For the 'LVTH18504A and 'LVTH182504A, the status value loaded in the Capture-IR state is the fixed binary value 10000001.

Shift-IR

Upon entry to the Shift-IR state, the instruction register is placed in the scan path between TDI and TDO. On the first falling edge of TCK, TDO goes from the high-impedance state to the active state. TDO enables to the logic level present in the least-significant bit of the instruction register.

While in the stable Shift-IR state, instruction data is serially shifted through the instruction register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-IR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-IR to Shift-IR or from Exit2-IR to Shift-IR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-IR state.

Exit1-IR, Exit2-IR

The Exit1-IR and Exit2-IR states are temporary states that end an instruction-register scan. It is possible to return to the Shift-IR state from either Exit1-IR or Exit2-IR without recapturing the instruction register. On the first falling edge of TCK after entry to Exit1-IR, TDO goes from the active state to the high-impedance state.

Pause-IR

No specific function is performed in the stable Pause-IR state, in which the TAP controller can remain indefinitely. The Pause-IR state suspends and resumes instruction-register scan operations without loss of data.

Update-IR

The current instruction is updated and takes effect on the falling edge of TCK, following entry to the Update-IR state.

register overview

With the exception of the bypass and device-identification registers, any test register can be thought of as a serial-shift register with a shadow latch on each bit. The bypass and device-identification registers differ in that they contain only a shift register. During the appropriate capture state (Capture-IR for instruction register, Capture-DR for data registers), the shift register can be parallel loaded from a source specified by the current instruction. During the appropriate shift state (Shift-IR or Shift-DR), the contents of the shift register are shifted out from TDO while new contents are shifted in at TDI. During the appropriate update state (Update-IR or Update-DR), the shadow latches are updated from the shift register.

instruction register description

The instruction register (IR) is eight bits long and tells the device what instruction is to be executed. Information contained in the instruction includes the mode of operation (either normal mode, in which the device performs its normal logic function, or test mode, in which the normal logic function is inhibited or altered), the test operation to be performed, which of the four data registers is to be selected for inclusion in the scan path during data-register scans, and the source of data to be captured into the selected data register during Capture-DR.

Table 3 lists the instructions supported by the 'LVTH18504A and 'LVTH182504A. The even-parity feature specified for SCOPE devices is supported in this device. Bit 7 of the instruction opcode is the parity bit. Any instructions that are defined for SCOPE devices but are not supported by this device default to BYPASS.

During Capture-IR, the IR captures the binary value 10000001. As an instruction is shifted in, this value is shifted out via TDO and can be inspected as verification that the IR is in the scan path. During Update-IR, the value that has been shifted into the IR is loaded into shadow latches. At this time, the current instruction is updated and any specified mode change takes effect. At power up or in the Test-Logic-Reset state, the IR is reset to the binary value 10000001, which selects the IDCODE instruction. The instruction register order of scan is shown in Figure 2.

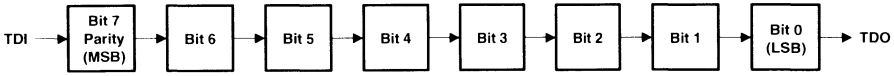


Figure 2. Instruction Register Order of Scan

data register description

boundary-scan register

The boundary-scan register (BSR) is 48 bits long. It contains one boundary-scan cell (BSC) for each normal-function input pin and one BSC for each normal-function I/O pin (one single cell for both input data and output data). The BSR is used to store test data that is to be applied externally to the device output pins, and/or to capture data that appears internally at the outputs of the normal on-chip logic and/or externally at the device input pins.

The source of data to be captured into the BSR during Capture-DR is determined by the current instruction. The contents of the BSR can change during Run-Test/Idle as determined by the current instruction. At power up or in Test-Logic-Reset, BSCs 47–46 are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., if test mode were invoked, the outputs would be at high-impedance state). Reset values of other BSCs should be considered indeterminate.

The BSR order of scan is from TDI through bits 47–0 to TDO. Table 1 shows the BSR bits and their associated device pin signals.

Table 1. Boundary-Scan Register Configuration

BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL
47	$\overline{OEAB}$	39	A20-I/O	19	B20-I/O
46	$\overline{OEBA}$	38	A19-I/O	18	B19-I/O
45	CLKAB	37	A18-I/O	17	B18-I/O
44	CLKBA	36	A17-I/O	16	B17-I/O
43	$\overline{CLKENAB}$	35	A16-I/O	15	B16-I/O
42	$\overline{CLKENBA}$	34	A15-I/O	14	B15-I/O
41	LEAB	33	A14-I/O	13	B14-I/O
40	LEBA	32	A13-I/O	12	B13-I/O
—	—	31	A12-I/O	11	B12-I/O
—	—	30	A11-I/O	10	B11-I/O
—	—	29	A10-I/O	9	B10-I/O
—	—	28	A9-I/O	8	B9-I/O
—	—	27	A8-I/O	7	B8-I/O
—	—	26	A7-I/O	6	B7-I/O
—	—	25	A6-I/O	5	B6-I/O
—	—	24	A5-I/O	4	B5-I/O
—	—	23	A4-I/O	3	B4-I/O
—	—	22	A3-I/O	2	B3-I/O
—	—	21	A2-I/O	1	B2-I/O
—	—	20	A1-I/O	0	B1-I/O

boundary-control register

The boundary-control register (BCR) is three bits long. The BCR is used in the context of the boundary-run (RUNT) instruction to implement additional test operations not included in the basic SCOPE instruction set. Such operations include PRPG, PSA, and binary count up (COUNT). Table 4 shows the test operations that are decoded by the BCR.

During Capture-DR, the contents of the BCR are not changed. At power up or in Test-Logic-Reset, the BCR is reset to the binary value 010, which selects the PSA test operation. The boundary-control register order of scan is shown in Figure 3.

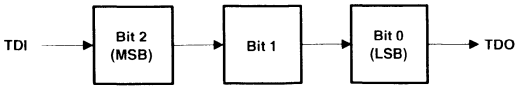


Figure 3. Boundary-Control Register Order of Scan

bypass register

The bypass register is a 1-bit scan path that can be selected to shorten the length of the system scan path, reducing the number of bits per test pattern that must be applied to complete a test operation. During Capture-DR, the bypass register captures a logic 0. The bypass register order of scan is shown in Figure 4.

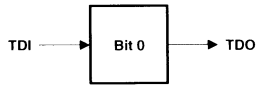


Figure 4. Bypass Register Order of Scan

device-identification register

The device-identification register (IDR) is 32 bits long. It can be selected and read to identify the manufacturer, part number, and version of this device.

For the 'LVTH18504A, either of the binary values 00100000000000001110100000101111 (2001D02F, hex) or 00110000000000011101000000101111 (3001D02F, hex) is captured (during Capture-DR state) in the IDR to identify this device as TI SN54/74LVTH18504A.

For the 'LVTH182504A, either of the binary values 00010000000000010001000000101111 (1002202F, hex) or 00100000000000010001000000101111 (2002202F, hex) is captured (during Capture-DR state) in the IDR to identify this device as TI SN54/74LVTH182504A.

The IDR order of scan is from TDI through bits 31–0 to TDO. Table 2 shows the IDR bits and their significance.

Table 2. Device-Identification Register Configuration

IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE†
31	VERSION3	27	PARTNUMBER15	11	MANUFACTURER10†
30	VERSION2	26	PARTNUMBER14	10	MANUFACTURER09†
29	VERSION1	25	PARTNUMBER13	9	MANUFACTURER08†
28	VERSION0	24	PARTNUMBER12	8	MANUFACTURER07†
—	—	23	PARTNUMBER11	7	MANUFACTURER06†
—	—	22	PARTNUMBER10	6	MANUFACTURER05†
—	—	21	PARTNUMBER09	5	MANUFACTURER04†
—	—	20	PARTNUMBER08	4	MANUFACTURER03†
—	—	19	PARTNUMBER07	3	MANUFACTURER02†
—	—	18	PARTNUMBER06	2	MANUFACTURER01†
—	—	17	PARTNUMBER05	1	MANUFACTURER00†
—	—	16	PARTNUMBER04	0	LOGIC1†
—	—	15	PARTNUMBER03	—	—
—	—	14	PARTNUMBER02	—	—
—	—	13	PARTNUMBER01	—	—
—	—	12	PARTNUMBER00	—	—

† Note that for TI products, bits 11–0 of the device-identification register always contain the binary value 000000101111 (02F, hex).

instruction-register opcode description

The instruction-register opcodes are shown in Table 3. The following descriptions detail the operation of each instruction.

Table 3. Instruction-Register Opcodes

BINARY CODE† BIT 7 → BIT 0 MSB → LSB	SCOPE OPCODE	DESCRIPTION	SELECTED DATA REGISTER	MODE
00000000	EXTEST	Boundary scan	Boundary scan	Test
10000001	IDCODE	Identification read	Device identification	Normal
10000010	SAMPLE/PRELOAD	Sample boundary	Boundary scan	Normal
00000011	BYPASS‡	Bypass scan	Bypass	Normal
10000100	BYPASS‡	Bypass scan	Bypass	Normal
00000101	BYPASS‡	Bypass scan	Bypass	Normal
00000110	HIGHZ	Control boundary to high impedance	Bypass	Modified test
10000111	CLAMP	Control boundary to 1/0	Bypass	Test
10001000	BYPASS‡	Bypass scan	Bypass	Normal
00001001	RUNT	Boundary-run test	Bypass	Test
00001010	READBN	Boundary read	Boundary scan	Normal
10001011	READBT	Boundary read	Boundary scan	Test
00001100	CELLTST	Boundary self test	Boundary scan	Normal
10001101	TOPHIP	Boundary toggle outputs	Bypass	Test
10001110	SCANCN	Boundary-control-register scan	Boundary control	Normal
00001111	SCANCT	Boundary-control-register scan	Boundary control	Test
All others	BYPASS	Bypass scan	Bypass	Normal

† Bit 7 is used to maintain even parity in the 8-bit instruction.
‡ The BYPASS instruction is executed in lieu of a SCOPE instruction that is not supported in the 'LVTH18504A or 'LVTH182504A.

boundary scan

This instruction conforms to the IEEE Std 1149.1-1990 EXTEST instruction. The BSR is selected in the scan path. Data appearing at the device input and I/O pins is captured in the associated BSCs. Data that has been scanned into the I/O BSCs for pins in the output mode is applied to the device I/O pins. Data present at the device pins, except for output-enables, is passed through the BSCs to the normal on-chip logic. For I/O pins, the operation of a pin as input or output is determined by the contents of the output-enable BSCs (bits 47–46 of the BSR). When a given output enable is active (logic 0), the associated I/O pins operate in the output mode. Otherwise, the I/O pins operate in the input mode. The device operates in the test mode.

identification read

This instruction conforms to the IEEE Std 1149.1-1990 IDCODE instruction. The IDR is selected in the scan path. The device operates in the normal mode.

sample boundary

This instruction conforms to the IEEE Std 1149.1-1990 SAMPLE/PRELOAD instruction. The BSR is selected in the scan path. Data appearing at the device input pins and I/O pins in the input mode is captured in the associated BSCs, while data appearing at the outputs of the normal on-chip logic is captured in the BSCs associated with I/O pins in the output mode. The device operates in the normal mode.

bypass scan

This instruction conforms to the IEEE Std 1149.1-1990 BYPASS instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the normal mode.

control boundary to high impedance

This instruction conforms to the IEEE Std 1149.1a-1993 HIGHZ instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in a modified test mode in which all device I/O pins are placed in the high-impedance state, the device input pins remain operational, and the normal on-chip logic function is performed.

control boundary to 1/0

This instruction conforms to the IEEE Std 1149.1a-1993 CLAMP instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the I/O BSCs for pins in the output mode is applied to the device I/O pins. The device operates in the test mode.

boundary-run test

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the test mode. The test operation specified in the BCR is executed during Run-Test/Idle. The five test operations decoded by the BCR are: sample inputs/toggle outputs (TOPSIP), PRPG, PSA, simultaneous PSA and PRPG (PSA/PRPG), and simultaneous PSA and binary count up (PSA/COUNT).

boundary read

The BSR is selected in the scan path. The value in the BSR remains unchanged during Capture-DR. This instruction is useful for inspecting data after a PSA operation.

boundary self test

The BSR is selected in the scan path. All BSCs capture the inverse of their current values during Capture-DR. In this way, the contents of the shadow latches can be read out to verify the integrity of both shift register and shadow latch elements of the BSR. The device operates in the normal mode.

boundary toggle outputs

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK in Run-Test/Idle and is then updated in the shadow latches and applied to the associated device I/O pins on each falling edge of TCK in Run-Test/Idle. Data in the input-mode BSCs remains constant. Data appearing at the device input or I/O pins is not captured in the input-mode BSCs. The device operates in the test mode.

boundary-control-register scan

The BCR is selected in the scan path. The value in the BCR remains unchanged during Capture-DR. This operation must be performed before a boundary-run test operation to specify which test operation is to be executed.

boundary-control-register opcode description

The BCR opcodes are decoded from BCR bits 2–0 as shown in Table 4. The selected test operation is performed while the RUNT instruction is executed in the Run-Test/Idle state. The following descriptions detail the operation of each BCR instruction and illustrate the associated PSA and PRPG algorithms.

Table 4. Boundary-Control Register Opcodes

BINARY CODE BIT 2 → BIT 0 MSB → LSB	DESCRIPTION
X00	Sample inputs/toggle outputs (TOPSIP)
X01	Pseudo-random pattern generation/40-bit mode (PRPG)
X10	Parallel-signature analysis/40-bit mode (PSA)
011	Simultaneous PSA and PRPG/20-bit mode (PSA/PRPG)
111	Simultaneous PSA and binary count up/20-bit mode (PSA/COUNT)

While the control input BSCs (bits 47–36) are not included in the toggle, PSA, PRPG, or COUNT algorithms, the output-enable BSCs (bits 47–46 of the BSR) control the drive state (active or high impedance) of the selected device output pins. These BCR instructions are only valid when the device is operating in one direction of data flow (that is, $\overline{OEAB} \neq \overline{OEBA}$). Otherwise, the bypass instruction is operated.

sample inputs/toggle outputs (TOPSIP)

Data appearing at the selected device input-mode I/O pins is captured in the shift-register elements of the associated BSCs on each rising edge of TCK. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK.

pseudo-random pattern generation (PRPG)

A pseudo-random pattern is generated in the shift-register elements of the selected BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device output-mode I/O pins on each falling edge of TCK. Figures 5 and 6 show the 40-bit linear-feedback shift-register algorithms through which the patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

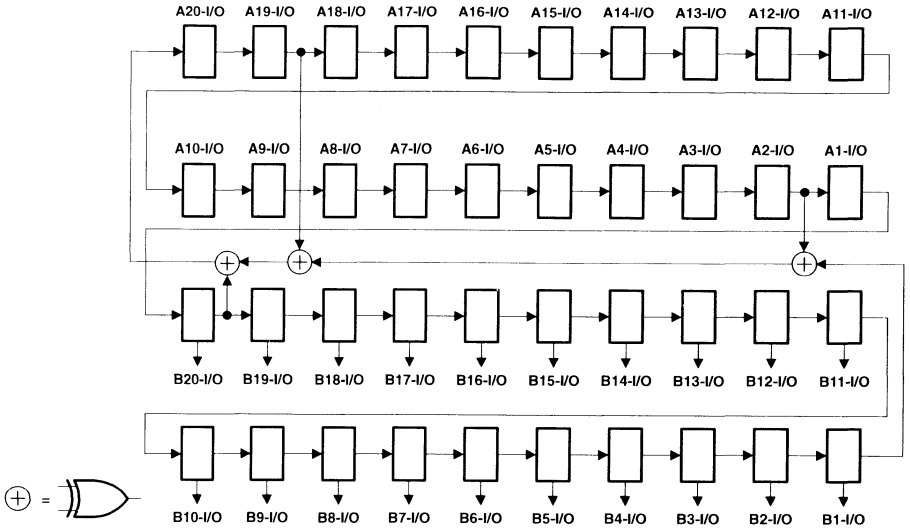


Figure 5. 40-Bit PRPG Configuration ($\overline{OEAB}$ = 0, $\overline{OEBA}$ = 1)

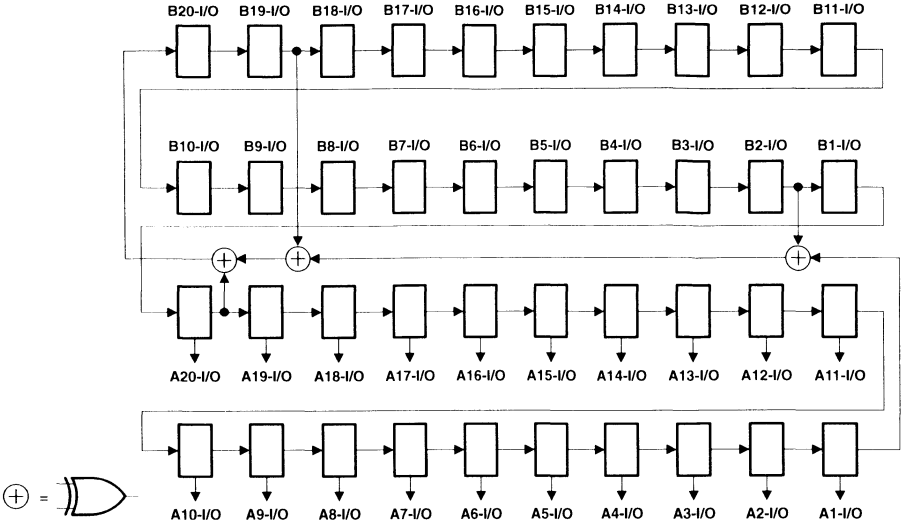


Figure 6. 40-Bit PRPG Configuration ($\overline{OEAB}$ = 1, $\overline{OEBA}$ = 0)

parallel-signature analysis (PSA)

Data appearing at the selected device input-mode I/O pins is compressed into a 40-bit parallel signature in the shift-register elements of the selected BSCs on each rising edge of TCK. Data in the shadow latches of the selected output-mode BSCs remains constant and is applied to the associated device I/O pins. Figures 7 and 8 show the 40-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

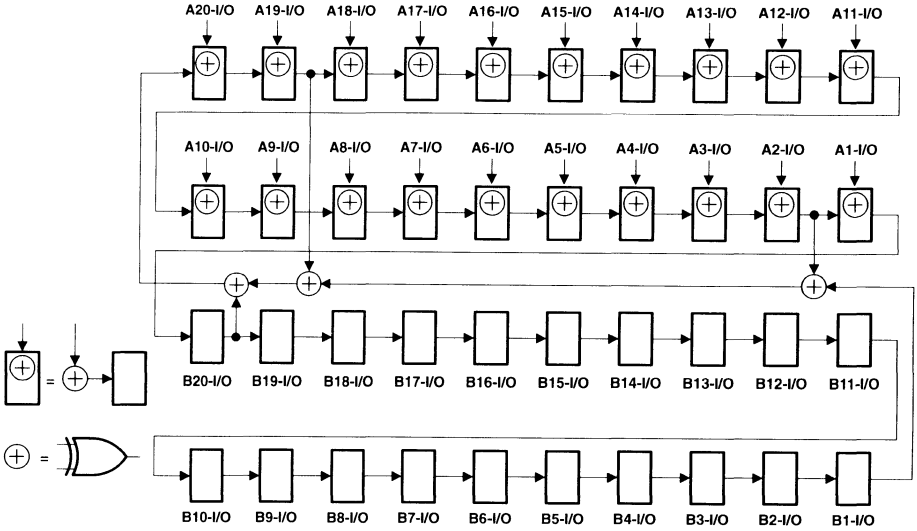


Figure 7. 40-Bit PSA Configuration ($\overline{OEAB}$ = 0, $\overline{OEBA}$ = 1)

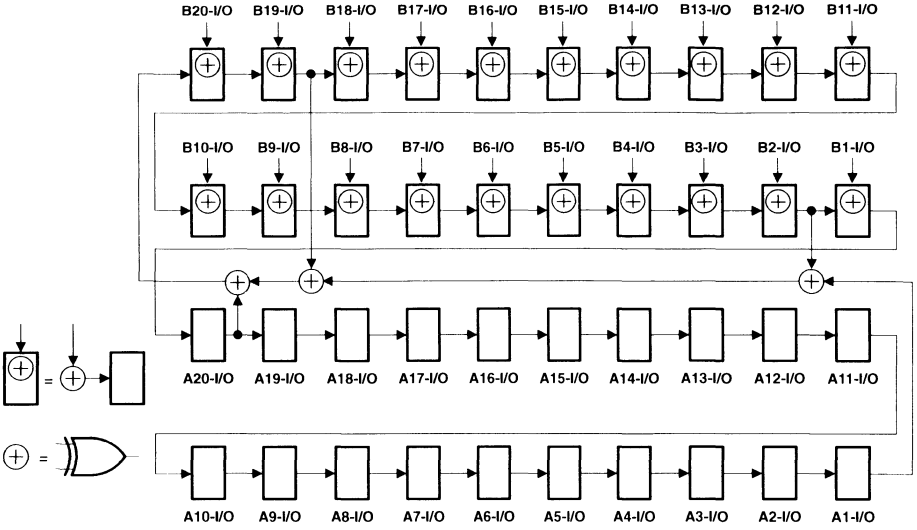


Figure 8. 40-Bit PSA Configuration ($\overline{OEAB}$ = 1, $\overline{OEBA}$ = 0)

simultaneous PSA and PRPG (PSA/PRPG)

Data appearing at the selected device input-mode I/O pins is compressed into a 20-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, a 20-bit pseudo-random pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 9 and 10 show the 20-bit linear-feedback shift-register algorithms through which the signature and patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

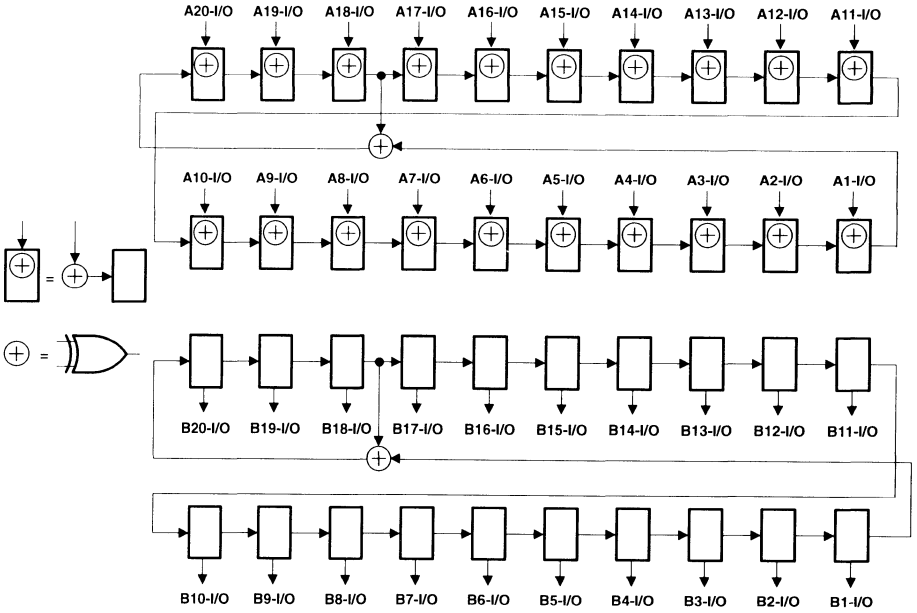


Figure 9. 20-Bit PSA/PRPG Configuration ($\overline{OEAB}$ = 0, $\overline{OEBA}$ = 1)

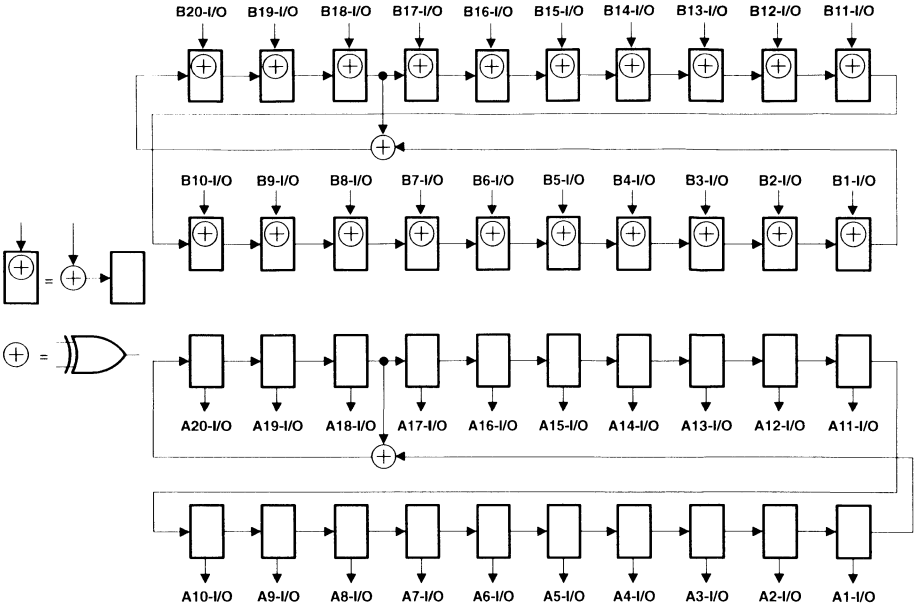


Figure 10. 20-Bit PSA/PRPG Configuration ($\overline{OEAB}$ = 1, $\overline{OEBA}$ = 0)

simultaneous PSA and binary count up (PSA/COUNT)

Data appearing at the selected device input-mode I/O pins is compressed into a 20-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, a 20-bit binary count-up pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 11 and 12 show the 20-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

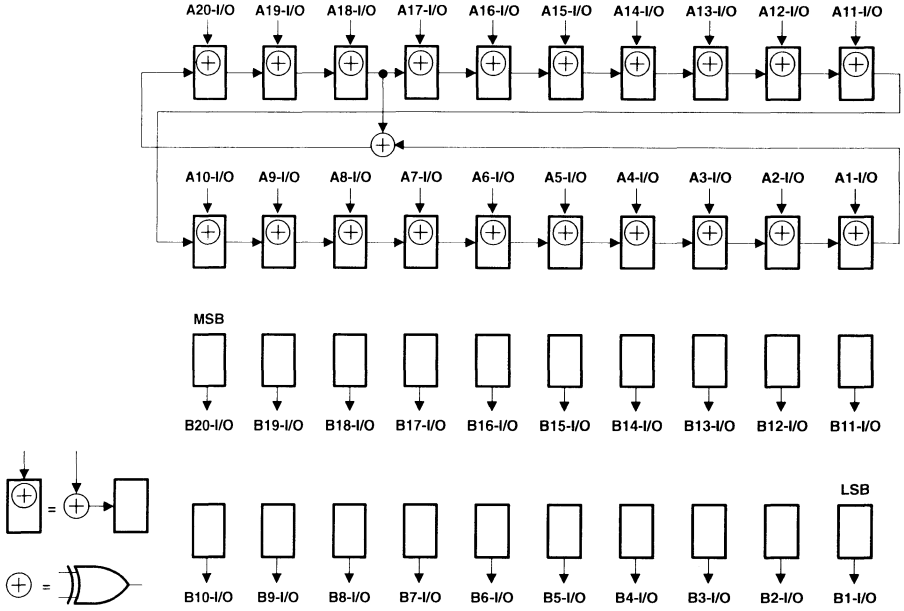


Figure 11. 20-Bit PSA/COUNT Configuration ($\overline{OEAB}$ = 0, $\overline{OEBA}$ = 1)

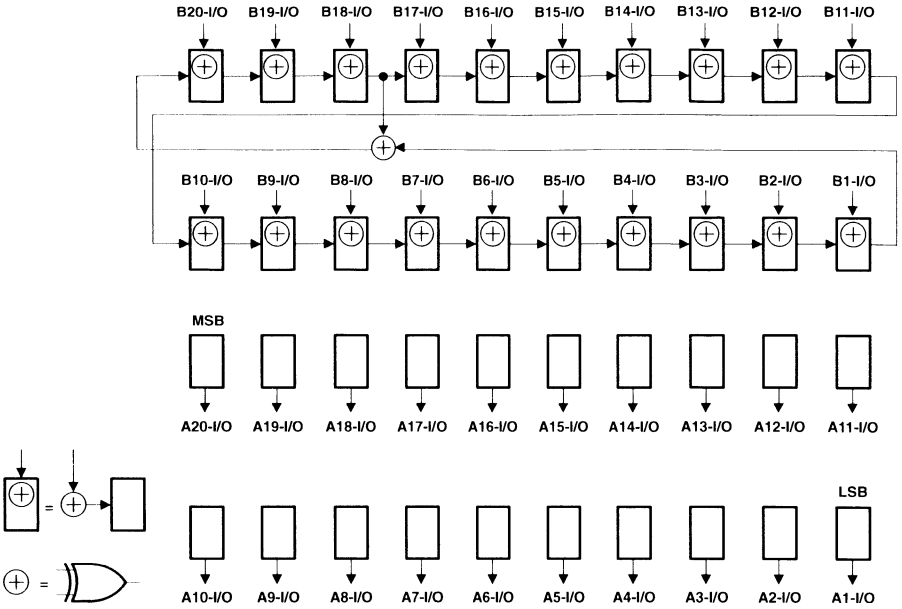


Figure 12. 20-Bit PSA/COUNT Configuration ($\overline{OEAB}$ = 1, $\overline{OEBA}$ = 0)

timing description

All test operations of the 'LVTH18504A and 'LVTH182504A are synchronous to the TCK signal. Data on the TDI, TMS, and normal-function inputs is captured on the rising edge of TCK. Data appears on the TDO and normal-function output pins on the falling edge of TCK. The TAP controller is advanced through its states (as shown in Figure 1) by changing the value of TMS on the falling edge of TCK and then applying a rising edge to TCK.

A simple timing example is shown in Figure 13. In this example, the TAP controller begins in the Test-Logic-Reset state and is advanced through its states to perform one instruction-register scan and one data-register scan. While in the Shift-IR and Shift-DR states, TDI is used to input serial data, and TDO is used to output serial data. The TAP controller is then returned to the Test-Logic-Reset state. Table 5 details the operation of the test circuitry during each TCK cycle.

Table 5. Explanation of Timing Example

TCK CYCLE(S)	TAP STATE AFTER TCK	DESCRIPTION
1	Test-Logic-Reset	TMS is changed to a logic 0 value on the falling edge of TCK to begin advancing the TAP controller toward the desired state.
2	Run-Test/Idle	
3	Select-DR-Scan	
4	Select-IR-Scan	
5	Capture-IR	The IR captures the 8-bit binary value 10000001 on the rising edge of TCK as the TAP controller exits the Capture-IR state.
6	Shift-IR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
7–13	Shift-IR	One bit is shifted into the IR on each TCK rising edge. With TDI held at a logic 1 value, the 8-bit binary value 11111111 is serially scanned into the IR. At the same time, the 8-bit binary value 10000001 is serially scanned out of the IR via TDO. In TCK cycle 13, TMS is changed to a logic 1 value to end the instruction register scan on the next TCK cycle. The last bit of the instruction is shifted as the TAP controller advances from Shift-IR to Exit1-IR.
14	Exit1-IR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
15	Update-IR	The IR is updated with the new instruction (BYPASS) on the falling edge of TCK.
16	Select-DR-Scan	
17	Capture-DR	The bypass register captures a logic 0 value on the rising edge of TCK as the TAP controller exits the Capture-DR state.
18	Shift-DR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
19–20	Shift-DR	The binary value 101 is shifted in via TDI, while the binary value 010 is shifted out via TDO.
21	Exit1-DR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
22	Update-DR	In general, the selected data register is updated with the new data on the falling edge of TCK.
23	Select-DR-Scan	
24	Select-IR-Scan	
25	Test-Logic-Reset	Test operation completed.

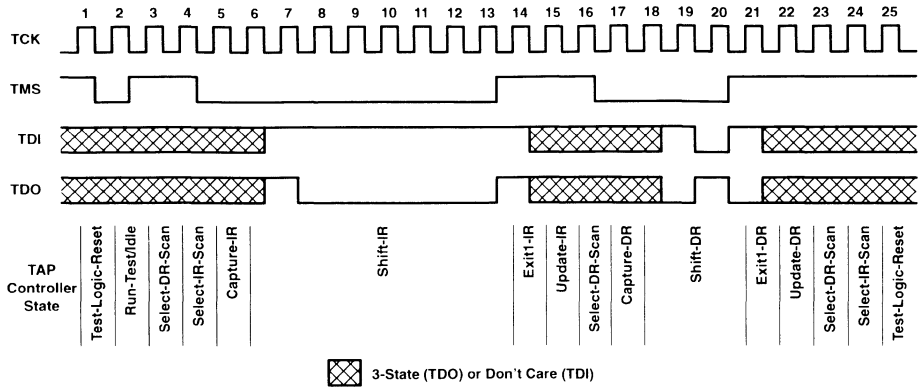


Figure 13. Timing Example

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH18504A . . . . . 96 mA
SN54LVTH182504A (A port or TDO) . . . . . 96 mA
SN54LVTH182504A (B port) . . . . . 30 mA
SN74LVTH18504A . . . . . 128 mA
SN74LVTH182504A (A port or TDO) . . . . . 128 mA
SN74LVTH182504A (B port) . . . . . 30 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH18504A . . . . . 48 mA
SN54LVTH182504A (A port or TDO) . . . . 48 mA
SN54LVTH182504A (B port) . . . . . 30 mA
SN74LVTH18504A . . . . . 64 mA
SN74LVTH182504A (A port or TDO) . . . . 64 mA
SN74LVTH182504A (B port) . . . . . 30 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): PM package . . . . . 67°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings can be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			SN54LVTH18504A		SN74LVTH18504A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			24		32	mA
I_{OL}†	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH18504A			SN74LVTH18504A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –3 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –8 mA	2.4			2.4			
			I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	CLK, $\overline{CLKEN}$, LE, TCK	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or MAX‡,	V_I = 5.5 V			10			10	
	$\overline{OE}$, TDI, TMS	V_{CC} = 3.6 V	V_I = 5.5 V			5			5	
			V_I = V_{CC}			1			1	
			V_I = 0	–25		–100	–25		–100	
	A or B ports§	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$¶	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75		500	75	150	500	µA
			V_I = 2 V	–75		–500	–75	–150	–500	
I_{OZH}	TDO	V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}	TDO	V_{CC} = 3.6 V,	V_O = 0.5 V			–1			–1	µA
I_{OZPU}	TDO	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{OZPD}	TDO	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.6	2		0.6	2	mA
			Outputs low		19.5	27		19.5	27	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}#		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.5			0.5	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			10			10		pF
C_o		V_O = 3 V or 0			8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

				SN54LVTH18504A				SN74LVTH18504A				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA		0	100	0	80	0	100	0	80	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low		4.4		5.6		4.4		5.6		ns
		LEAB or LEBA high		3		3		3		3		
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑		2.4		2.8		2.4		2.8		ns
		A before LEAB↓ or B before LEBA↓	CLK high	1.5		0.7		1.5		0.7		
			CLK low	1.6		1.6		1.6		1.6		
		$\overline{CLKEN}$ before CLK↑		2.8		3.4		2.8		3.4		
t_h	Hold time	A after CLKAB↑		1		0.8		1		0.8		ns
		B after CLKBA↑		1.4		1.1		1.4		1.1		
		A after LEAB↓ or B after LEBA↓		3.1		3.5		3.1		3.5		
		$\overline{CLKEN}$ after CLK↑		0.7		0.2		0.7		0.2		

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

			SN54LVTH18504A				SN74LVTH18504A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, $\overline{CLKEN}$, LE, or $\overline{OE}$ before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, $\overline{CLKEN}$, LE, or $\overline{OE}$ after TCK↑	1.5		1		1.5		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18504A				SN74LVTH18504A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		100		80		100		80		MHz
t_{PLH}	A or B	B or A	1.5	5.4		5.8	1.5	5.1		5.6	ns
t_{PHL}			1.5	5.4		5.8	1.5	5.1		5.6	
t_{PLH}	CLKAB	B	1.5	6.9		7.8	1.5	5.8		6.8	ns
t_{PHL}			1.5	6.9		7.8	1.5	5.8		6.8	
t_{PLH}	CLKBA	A	1.5	6.9		7.8	1.5	6.4		7.4	ns
t_{PHL}			1.5	6.9		7.8	1.5	6.4		7.4	
t_{PLH}	LEAB or LEBA	B or A	2	8.7		9.5	2	8.1		8.8	ns
t_{PHL}			2	7.1		7.4	2	6.7		7.1	
t_{PZH}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2	9.5		10.5	2	9.1		10	ns
t_{PZL}			2	10		10.8	2	9.6		10.4	
t_{PHZ}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.5	12		12.7	2.5	10.4		11.2	ns
t_{PLZ}			2.5	9.6		9.9	2.5	9.1		9.5	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18504A				SN74LVTH18504A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

recommended operating conditions

			SN54LVTH182504A		SN74LVTH182504A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	A port, TDO		–24		–32	mA
		B port		–12		–12	
I_{OL}	Low-level output current	A port, TDO		24		32	mA
		B port		12		12	
I_{OL}†	Low-level output current	A port, TDO		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH182504A			SN74LVTH182504A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}	A, B, TDO	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA	V_{CC}−0.2			V_{CC}−0.2			V
	A port, TDO	V_{CC} = 2.7 V,	I_{OH} = −3 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = −8 mA	2.4			2.4			
			I_{OH} = −24 mA	2						
			I_{OH} = −32 mA				2			
	B port	V_{CC} = 3 V,	I_{OH} = −12 mA	2			2			
V_{OL}	A, B, TDO	V_{CC} = 2.7 V,	I_{OL} = 100 µA			0.2			0.2	V
	A port, TDO	V_{CC} = 2.7 V,	I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
	B port	V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	
I_I	CLK, CLKEN, LE, TCK	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or MAX‡,	V_I = 5.5 V			10			10	
	$\overline{OE}$, TDI, TMS	V_{CC} = 3.6 V	V_I = 5.5 V			5			5	
			V_I = V_{CC}			1			1	
			V_I = 0	−25		−100	−25		−100	
	A or B ports§	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$¶	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75		500	75	150	500	µA
			V_I = 2 V	−75		−500	−75	−150	−500	
I_{OZH}	TDO	V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}	TDO	V_{CC} = 3.6 V,	V_O = 0.5 V			−1			−1	µA
I_{OZPU}	TDO	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{OZPD}	TDO	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.6	2		0.6	2	mA
			Outputs low		19.5	27		19.5	27	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}#		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.5			0.5	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			10			10		pF
C_o		V_O = 3 V or 0			8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

				SN54LVTH182504A				SN74LVTH182504A				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA		0	100	0	80	0	100	0	80	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low		4.4		5.6		4.4		5.6		ns
		LEAB or LEBA high		3		3		3		3		
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑		2.8		3		2.8		3		ns
		A before LEAB↓ or B before LEBA↓	CLK high	1.5		0.7		1.5		0.7		
			CLK low	1.6		1.6		1.6		1.6		
		$\overline{CLKEN}$ before CLK↑		2.8		3.4		2.8		3.4		
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑		1.4		1.1		1.4		1.1		ns
		A after LEAB↓ or B after LEBA↓		3.1		3.5		3.1		3.5		
		$\overline{CLKEN}$ after CLK↑		0.7		0.2		0.7		0.2		

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

			SN54LVTH182504A				SN74LVTH182504A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, $\overline{CLKEN}$, LE, or $\overline{OE}$ before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, $\overline{CLKEN}$, LE, or $\overline{OE}$ after TCK↑	1.5		1		1.5		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

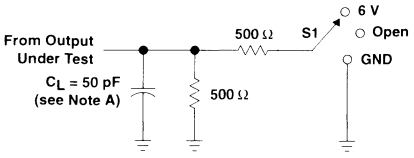
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182504A				SN74LVTH182504A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		100		80		100		80		MHz
t_{PLH}	A	B	1.5	6.4	6.9		1.5	5.9	6.6		ns
t_{PHL}			1.5	6.4	6.9		1.5	5.9	6.6		
t_{PLH}	B	A	1.5	5.4	5.8		1.5	5.1	5.6		ns
t_{PHL}			1.5	5.4	5.8		1.5	5.1	5.6		
t_{PLH}	CLKAB	B	1.5	6.9	7.8		1.5	6.7	7.7		ns
t_{PHL}			1.5	6.9	7.8		1.5	6.7	7.7		
t_{PLH}	CLKBA	A	1.5	6.9	7.8		1.5	6.4	7.4		ns
t_{PHL}			1.5	6.9	7.8		1.5	6.4	7.4		
t_{PLH}	LEAB	B	2	8.7	9.5		2	8.2	9.2		ns
t_{PHL}			2	7.1	7.4		2	6.7	7.1		
t_{PLH}	LEBA	A	2	8.7	9.5		2	8.1	8.8		ns
t_{PHL}			2	7.1	7.4		2	6.7	7.1		
t_{PZH}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2	9.9	11.1		2	9.5	10.6		ns
t_{PZL}			2	10.2	11		2	9.7	10.5		
t_{PHZ}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.5	12	12.7		2.5	11.1	11.8		ns
t_{PLZ}			2.5	11	11.2		2.5	9.8	10		

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

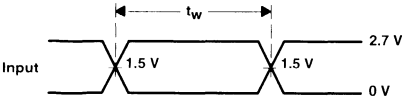
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182504A				SN74LVTH182504A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15	18		2.5	14	17		ns
t_{PHL}			2.5	15	18		2.5	14	17		
t_{PLH}	TCK↓	TDO	1	6	7		1	5.5	6.5		ns
t_{PHL}			1.5	7	8		1.5	6.5	7.5		
t_{PZH}	TCK↓	A or B	4	18	21		4	17	20		ns
t_{PZL}			4	18	21		4	17	20		
t_{PZH}	TCK↓	TDO	1	6	7		1	5.5	6.5		ns
t_{PZL}			1.5	6	7		1.5	5.5	6.5		
t_{PHZ}	TCK↓	A or B	4	19	21		4	18	20		ns
t_{PLZ}			4	18	19.5		4	17	18.5		
t_{PHZ}	TCK↓	TDO	1.5	7.5	9		1.5	7	8.5		ns
t_{PLZ}			1.5	7.5	8.5		1.5	7	8		

PARAMETER MEASUREMENT INFORMATION

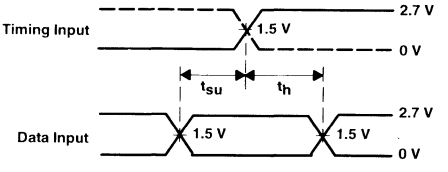


LOAD CIRCUIT

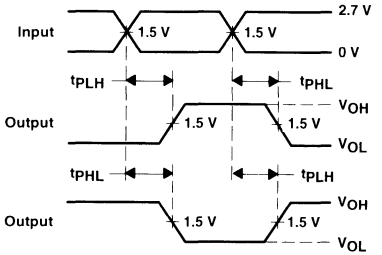
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



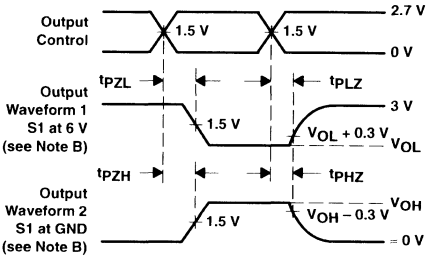
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



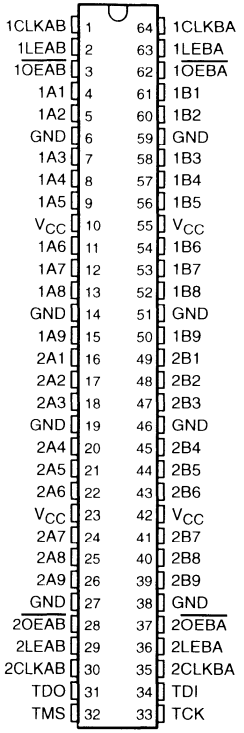
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 14. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *SCOPE*™ Family of Testability Products**
- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art 3.3-V ABT Design Supports Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **B-Port Outputs of 'LVTH182512 Devices Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required**
- **Compatible With the IEEE Std 1149.1-1990 (JTAG) Test Access Port and Boundary-Scan Architecture**
- ***SCOPE*™ Instruction Set**
  - **IEEE Std 1149.1-1990 Required Instructions and Optional CLAMP and HIGHZ**
  - **Parallel-Signature Analysis at Inputs**
  - **Pseudo-Random Pattern Generation From Outputs**
  - **Sample Inputs/Toggle Outputs**
  - **Binary Count From Outputs**
  - **Device Identification**
  - **Even-Parity Opcodes**
- **Package Options Include 64-Pin Plastic Thin Shrink Small Outline (DGG) and 64-Pin Ceramic Dual Flat (HKC) Packages Using 0.5-mm Center-to-Center Spacings**

SN54LVTH18512, SN54LVTH182512 . . . HKC PACKAGE
SN74LVTH18512, SN74LVTH182512 . . . DGG PACKAGE
(TOP VIEW)



description

The 'LVTH18512 and 'LVTH182512 scan test devices with 18-bit universal bus transceivers are members of the Texas Instruments SCOPE™ testability integrated-circuit family. This family of devices supports IEEE Std 1149.1-1990 boundary scan to facilitate testing of complex circuit-board assemblies. Scan access to the test circuitry is accomplished via the 4-wire test access port (TAP) interface.

Additionally, these devices are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

description (continued)

In the normal mode, these devices are 18-bit universal bus transceivers that combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, or clocked modes. They can be used either as two 9-bit transceivers or one 18-bit transceiver. The test circuitry can be activated by the TAP to take snapshot samples of the data appearing at the device pins or to perform a self test on the boundary-test cells. Activating the TAP in the normal mode does not affect the functional operation of the SCOPE™ universal bus transceivers.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB is low, the A data is latched while CLKAB is held at a static low or high logic level. Otherwise, if LEAB is low, A data is stored on a low-to-high transition of CLKAB. When $\overline{OEAB}$ is low, the B outputs are active. When $\overline{OEAB}$ is high, the B outputs are in the high-impedance state. B-to-A data flow is similar to A-to-B data flow but uses the $\overline{OEBA}$, LEBA, and CLKBA inputs.

In the test mode, the normal operation of the SCOPE™ universal bus transceivers is inhibited, and the test circuitry is enabled to observe and control the I/O boundary of the device. When enabled, the test circuitry performs boundary-scan test operations according to the protocol described in IEEE Std 1149.1-1990.

Four dedicated test pins are used to observe and control the operation of the test circuitry: test data input (TDI), test data output (TDO), test mode select (TMS), and test clock (TCK). Additionally, the test circuitry performs other testing functions such as parallel-signature analysis (PSA) on data inputs and pseudo-random pattern generation (PRPG) from data outputs. All testing and scan operations are synchronized to the TAP interface.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The B-port outputs of 'LVTH182512, which are designed to source or sink up to 12 mA, include equivalent 25-Ω series resistors to reduce overshoot and undershoot.

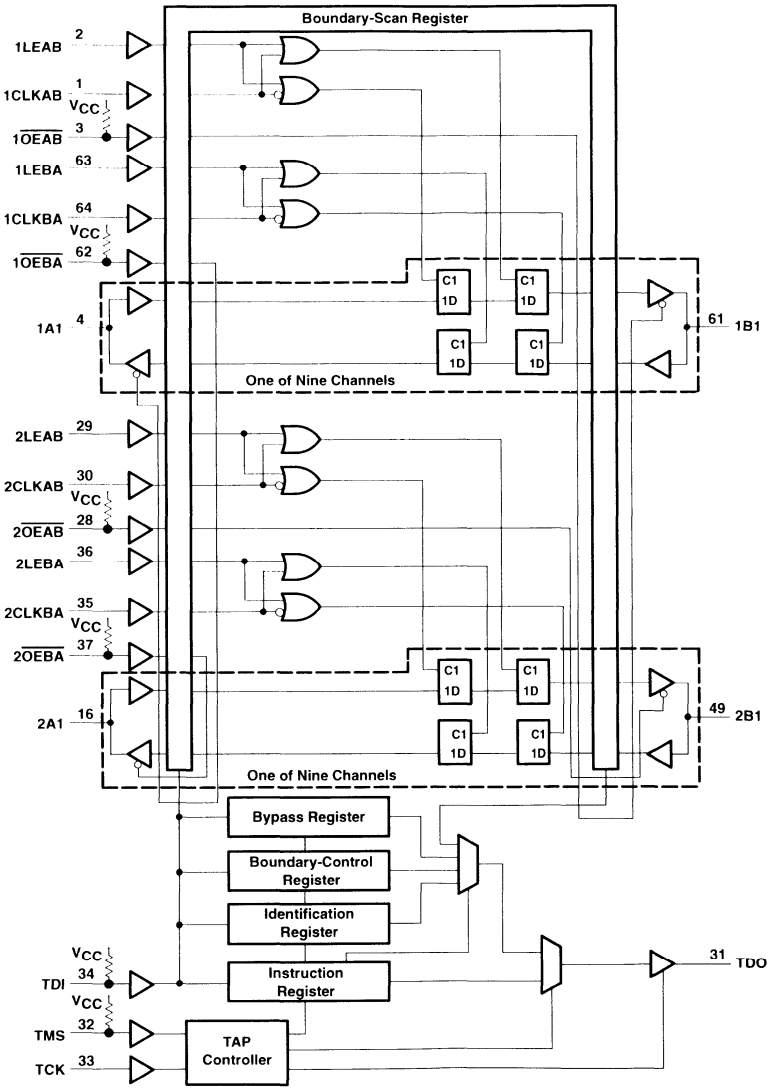
The SN54LVTH18512 and SN54LVTH182512 are characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH18512 and SN74LVTH182512 are characterized for operation from –40°C to 85°C.

FUNCTION TABLE†
(normal mode, each register)

INPUTS				OUTPUT
$\overline{OEAB}$	LEAB	CLKAB	A	B
L	L	L	X	B_0‡
L	L	↑	L	L
L	L	↑	H	H
L	H	X	L	L
L	H	X	H	H
H	X	X	X	Z

† A-to-B data flow is shown. B-to-A data flow is similar but uses $\overline{OEBA}$, LEBA, and CLKBA.
‡ Output level before the indicated steady-state input conditions were established

functional block diagram



Terminal Functions

TERMINAL NAME	DESCRIPTION
1A1–1A9, 2A1–2A9	Normal-function A-bus I/O ports. See function table for normal-mode logic.
1B1–1B9, 2B1–2B9	Normal-function B-bus I/O ports. See function table for normal-mode logic.
1CLKAB, 1CLKBA, 2CLKAB, 2CLKBA	Normal-function clock inputs. See function table for normal-mode logic.
GND	Ground
1LEAB, 1LEBA, 2LEAB, 2LEBA	Normal-function latch enables. See function table for normal-mode logic.
1$\overline{OEAB}$, 1$\overline{OEBA}$, 2$\overline{OEAB}$, 2$\overline{OEBA}$	Normal-function output enables. See function table for normal-mode logic. An internal pullup at each terminal forces the terminal to a high level if left unconnected.
TCK	Test clock. One of four terminals required by IEEE Std 1149.1-1990. Test operations of the device are synchronous to TCK. Data is captured on the rising edge of TCK and outputs change on the falling edge of TCK.
TDI	Test data input. One of four terminals required by IEEE Std 1149.1-1990. TDI is the serial input for shifting data through the instruction register or selected data register. An internal pullup forces TDI to a high level if left unconnected.
TDO	Test data output. One of four terminals required by IEEE Std 1149.1-1990. TDO is the serial output for shifting data through the instruction register or selected data register.
TMS	Test mode select. One of four terminals required by IEEE Std 1149.1-1990. TMS directs the device through its TAP controller states. An internal pullup forces TMS to a high level if left unconnected.
V_{CC}	Supply voltage

test architecture

Serial-test information is conveyed by means of a 4-wire test bus or TAP, that conforms to IEEE Std 1149.1-1990. Test instructions, test data, and test control signals all are passed along this serial-test bus. The TAP controller monitors two signals from the test bus, TCK and TMS. The TAP controller extracts the synchronization (TCK) and state control (TMS) signals from the test bus and generates the appropriate on-chip control signals for the test structures in the device. Figure 1 shows the TAP-controller state diagram.

The TAP controller is fully synchronous to the TCK signal. Input data is captured on the rising edge of TCK and output data changes on the falling edge of TCK. This scheme ensures data to be captured is valid for fully one-half of the TCK cycle.

The functional block diagram shows the IEEE Std 1149.1-1990 4-wire test bus and boundary-scan architecture and the relationship among the test bus, the TAP controller, and the test registers. As shown, the device contains an 8-bit instruction register and four test-data registers: a 48-bit boundary-scan register, a 3-bit boundary-control register, a 1-bit bypass register, and a 32-bit device identification register.

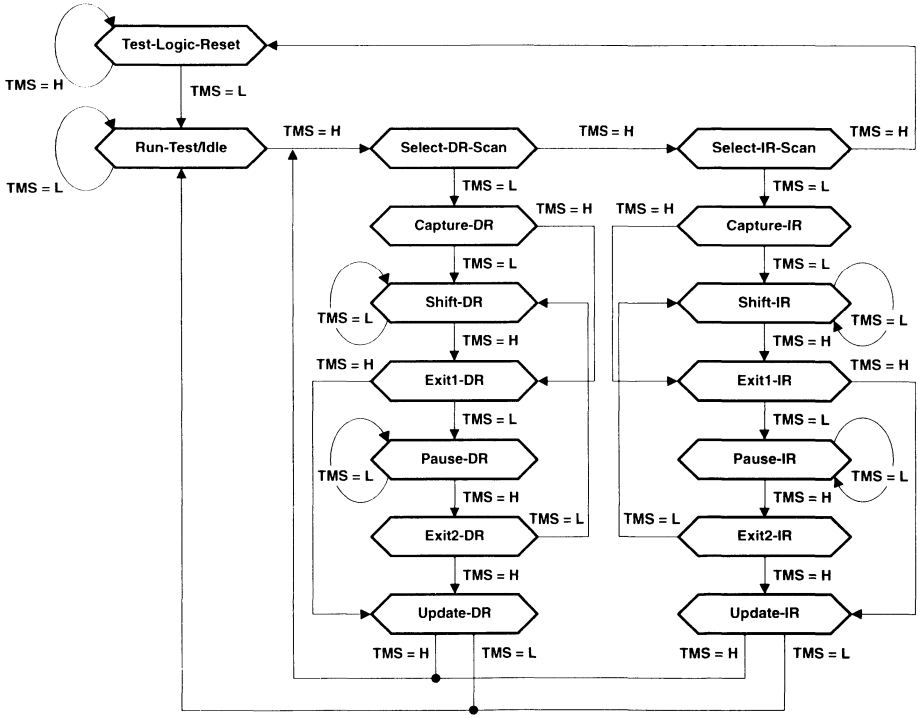


Figure 1. TAP-Controller State Diagram

state diagram description

The TAP controller is a synchronous finite-state machine that provides test control signals throughout the device. The state diagram shown in Figure 1 is in accordance with IEEE Std 1149.1-1990. The TAP controller proceeds through its states based on the level of TMS at the rising edge of TCK.

As shown, the TAP controller consists of 16 states. There are six stable states (indicated by a looping arrow in the state diagram) and ten unstable states. A stable state is a state the TAP controller can retain for consecutive TCK cycles. Any state that does not meet this criterion is an unstable state.

There are two main paths through the state diagram: one to access and control the selected data register and one to access and control the instruction register. Only one register can be accessed at a time.

Test-Logic-Reset

The device powers up in the Test-Logic-Reset state. In the stable Test-Logic-Reset state, the test logic is reset and is disabled so that the normal logic function of the device is performed. The instruction register is reset to an opcode that selects the optional IDCODE instruction, if supported, or the BYPASS instruction. Certain data registers can also be reset to their power-up values.

The state machine is constructed such that the TAP controller returns to the Test-Logic-Reset state in no more than five TCK cycles if TMS is left high. The TMS pin has an internal pullup resistor that forces it high if left unconnected or if a board defect causes it to be open circuited.

For the 'LVTH18512 and 'LVTH182512, the instruction register is reset to the binary value 10000001, which selects the IDCODE instruction. Bits 47–44 in the boundary-scan register are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., if test mode were invoked the outputs would be at the high-impedance state). Reset-value of other bits in the boundary-scan register should be considered indeterminate. The boundary-control register is reset to the binary value 010, which selects the PSA test operation.

Run-Test/Idle

The TAP controller must pass through the Run-Test/Idle state (from Test-Logic-Reset) before executing any test operations. The Run-Test/Idle state also can be entered following data-register or instruction-register scans. Run-Test/Idle is a stable state in which the test logic can be actively running a test or can be idle. The test operations selected by the boundary-control register are performed while the TAP controller is in the Run-Test/Idle state.

Select-DR-Scan, Select-IR-Scan

No specific function is performed in the Select-DR-Scan and Select-IR-Scan states, and the TAP controller exits either of these states on the next TCK cycle. These states allow the selection of either data-register scan or instruction-register scan.

Capture-DR

When a data-register scan is selected, the TAP controller must pass through the Capture-DR state. In the Capture-DR state, the selected data register captures a data value as specified by the current instruction. Such capture operations occur on the rising edge of TCK, upon which the TAP controller exits the Capture-DR state.

Shift-DR

Upon entry to the Shift-DR state, the data register is placed in the scan path between TDI and TDO, and on the first falling edge of TCK, TDO goes from the high-impedance state to an active state. TDO enables to the logic level present in the least-significant bit of the selected data register.

While in the stable Shift-DR state, data is serially shifted through the selected data register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-DR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-DR to Shift-DR or from Exit2-DR to Shift-DR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-DR state.

Exit1-DR, Exit2-DR

The Exit1-DR and Exit2-DR states are temporary states that end a data-register scan. It is possible to return to the Shift-DR state from either Exit1-DR or Exit2-DR without recapturing the data register. On the first falling edge of TCK after entry to Exit1-DR, TDO goes from the active state to the high-impedance state.

Pause-DR

No specific function is performed in the stable Pause-DR state, in which the TAP controller can remain indefinitely. The Pause-DR state suspends and resumes data-register scan operations without loss of data.

Update-DR

If the current instruction calls for the selected data register to be updated with current data, such update occurs on the falling edge of TCK, following entry to the Update-DR state.

Capture-IR

When an instruction-register scan is selected, the TAP controller must pass through the Capture-IR state. In the Capture-IR state, the instruction register captures its current status value. This capture operation occurs on the rising edge of TCK, upon which the TAP controller exits the Capture-IR state. For the 'LVTH18512 and 'LVTH182512, the status value loaded in the Capture-IR state is the fixed binary value 10000001.

Shift-IR

Upon entry to the Shift-IR state, the instruction register is placed in the scan path between TDI and TDO. On the first falling edge of TCK, TDO goes from the high-impedance state to the active state. TDO enables to the logic level present in the least-significant bit of the instruction register.

While in the stable Shift-IR state, instruction data is serially shifted through the instruction register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-IR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-IR to Shift-IR or from Exit2-IR to Shift-IR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-IR state.

Exit1-IR, Exit2-IR

The Exit1-IR and Exit2-IR states are temporary states that end an instruction-register scan. It is possible to return to the Shift-IR state from either Exit1-IR or Exit2-IR without recapturing the instruction register. On the first falling edge of TCK after entry to Exit1-IR, TDO goes from the active state to the high-impedance state.

Pause-IR

No specific function is performed in the stable Pause-IR state, in which the TAP controller can remain indefinitely. The Pause-IR state suspends and resumes instruction-register scan operations without loss of data.

Update-IR

The current instruction is updated and takes effect on the falling edge of TCK, following entry to the Update-IR state.

register overview

With the exception of the bypass and device-identification registers, any test register can be thought of as a serial shift register with a shadow latch on each bit. The bypass and device-identification registers differ in that they contain only a shift register. During the appropriate capture state (Capture-IR for instruction register, Capture-DR for data registers), the shift register can be parallel loaded from a source specified by the current instruction. During the appropriate shift state (Shift-IR or Shift-DR), the contents of the shift register are shifted out from TDO while new contents are shifted in at TDI. During the appropriate update state (Update-IR or Update-DR), the shadow latches are updated from the shift register.

instruction register description

The instruction register (IR) is eight bits long and tells the device what instruction is to be executed. Information contained in the instruction includes the mode of operation (either normal mode, in which the device performs its normal logic function, or test mode, in which the normal logic function is inhibited or altered), the test operation to be performed, which of the four data registers is to be selected for inclusion in the scan path during data-register scans, and the source of data to be captured into the selected data register during Capture-DR.

Table 3 lists the instructions supported by the 'LVTH18512 and 'LVTH182512. The even-parity feature specified for SCOPE™ devices is supported in this device. Bit 7 of the instruction opcode is the parity bit. Any instructions that are defined for SCOPE™ devices but are not supported by this device default to BYPASS.

During Capture-IR, the IR captures the binary value 10000001. As an instruction is shifted in, this value is shifted out via TDO and can be inspected as verification that the IR is in the scan path. During Update-IR, the value that has been shifted into the IR is loaded into shadow latches. At this time, the current instruction is updated and any specified mode change takes effect. At power up or in the Test-Logic-Reset state, the IR is reset to the binary value 10000001, which selects the IDCODE instruction. The IR order of scan is shown in Figure 2.

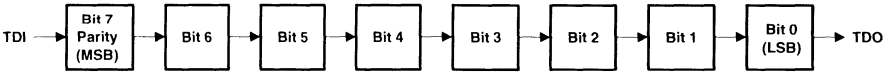


Figure 2. Instruction Register Order of Scan

data register description

boundary-scan register

The boundary-scan register (BSR) is 48 bits long. It contains one boundary-scan cell (BSC) for each normal-function input pin and one BSC for each normal-function I/O pin (one single cell for both input data and output data). The BSR is used to store test data that is to be applied externally to the device output pins, and/or to capture data that appears internally at the outputs of the normal on-chip logic and/or externally at the device input pins.

The source of data to be captured into the BSR during Capture-DR is determined by the current instruction. The contents of the BSR can change during Run-Test/Idle as determined by the current instruction. At power up or in Test-Logic-Reset, BSCs 47–44 are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs are set to benign values (i.e., if test mode were invoked, the outputs would be at the high-impedance state). Reset values of other BSCs should be considered indeterminate.

The BSR order of scan is from TDI through bits 47–0 to TDO. Table 1 shows the BSR bits and their associated device pin signals.

Table 1. Boundary-Scan Register Configuration

BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL
47	$2\overline{OE}AB$	35	2A9-I/O	17	2B9-I/O
46	$1\overline{OE}AB$	34	2A8-I/O	16	2B8-I/O
45	$2\overline{OE}BA$	33	2A7-I/O	15	2B7-I/O
44	$1\overline{OE}BA$	32	2A6-I/O	14	2B6-I/O
43	2CLKAB	31	2A5-I/O	13	2B5-I/O
42	1CLKAB	30	2A4-I/O	12	2B4-I/O
41	2CLKBA	29	2A3-I/O	11	2B3-I/O
40	1CLKBA	28	2A2-I/O	10	2B2-I/O
39	2LEAB	27	2A1-I/O	9	2B1-I/O
38	1LEAB	26	1A9-I/O	8	1B9-I/O
37	2LEBA	25	1A8-I/O	7	1B8-I/O
36	1LEBA	24	1A7-I/O	6	1B7-I/O
—	—	23	1A6-I/O	5	1B6-I/O
—	—	22	1A5-I/O	4	1B5-I/O
—	—	21	1A4-I/O	3	1B4-I/O
—	—	20	1A3-I/O	2	1B3-I/O
—	—	19	1A2-I/O	1	1B2-I/O
—	—	18	1A1-I/O	0	1B1-I/O

boundary-control register

The boundary-control register (BCR) is three bits long. The BCR is used in the context of the boundary-run test (RUNT) instruction to implement additional test operations not included in the basic SCOPE™ instruction set. Such operations include PRPG, PSA, and binary count up (COUNT). Table 4 shows the test operations that are decoded by the BCR.

During Capture-DR, the contents of the BCR are not changed. At power up or in Test-Logic-Reset, the BCR is reset to the binary value 010, which selects the PSA test operation. The BCR order of scan is shown in Figure 3.

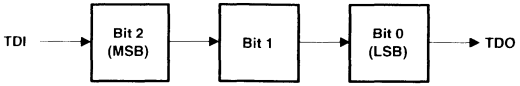


Figure 3. Boundary-Control Register Order of Scan

bypass register

The bypass register is a 1-bit scan path that can be selected to shorten the length of the system scan path, reducing the number of bits per test pattern that must be applied to complete a test operation. During Capture-DR, the bypass register captures a logic 0. The bypass register order of scan is shown in Figure 4.

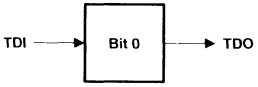


Figure 4. Bypass Register Order of Scan

device-identification register

The device-identification register (IDR) is 32 bits long. It can be selected and read to identify the manufacturer, part number, and version of this device.

For the 'LVTH18512, the binary value 00000000000000011011000000101111 (0003B02F, hex) is captured (during Capture-DR state) in the IDR to identify this device as Texas Instruments SN54/74LVTH18512.

For the 'LVTH182512, the binary value 00000000000000011110000000101111 (0003C02F, hex) is captured (during Capture-DR state) in the device-identification register to identify this device as Texas Instruments SN54/74LVTH182512.

The IDR order of scan is from TDI through bits 31–0 to TDO. Table 2 shows the IDR bits and their significance.

Table 2. Device-Identification Register Configuration

IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE
31	VERSION3	27	PARTNUMBER15	11	MANUFACTURER10†
30	VERSION2	26	PARTNUMBER14	10	MANUFACTURER09†
29	VERSION1	25	PARTNUMBER13	9	MANUFACTURER08†
28	VERSION0	24	PARTNUMBER12	8	MANUFACTURER07†
—	—	23	PARTNUMBER11	7	MANUFACTURER06†
—	—	22	PARTNUMBER10	6	MANUFACTURER05†
—	—	21	PARTNUMBER09	5	MANUFACTURER04†
—	—	20	PARTNUMBER08	4	MANUFACTURER03†
—	—	19	PARTNUMBER07	3	MANUFACTURER02†
—	—	18	PARTNUMBER06	2	MANUFACTURER01†
—	—	17	PARTNUMBER05	1	MANUFACTURER00†
—	—	16	PARTNUMBER04	0	LOGIC1†
—	—	15	PARTNUMBER03	—	—
—	—	14	PARTNUMBER02	—	—
—	—	13	PARTNUMBER01	—	—
—	—	12	PARTNUMBER00	—	—

† Note that for TI products, bits 11–0 of the device-identification register always contain the binary value 000000101111 (02F, hex).

instruction-register opcode description

The instruction-register opcodes are shown in Table 3. The following descriptions detail the operation of each instruction.

Table 3. Instruction-Register Opcodes

BINARY CODE† BIT 7 → BIT 0 MSB → LSB	SCOPE OPCODE	DESCRIPTION	SELECTED DATA REGISTER	MODE
00000000	EXTEST	Boundary scan	Boundary scan	Test
10000001	IDCODE	Identification read	Device identification	Normal
10000010	SAMPLE/PRELOAD	Sample boundary	Boundary scan	Normal
00000011	BYPASS‡	Bypass scan	Bypass	Normal
10000100	BYPASS‡	Bypass scan	Bypass	Normal
00000101	BYPASS‡	Bypass scan	Bypass	Normal
00000110	HIGHZ	Control boundary to high impedance	Bypass	Modified test
10000111	CLAMP	Control boundary to 1/0	Bypass	Test
10001000	BYPASS‡	Bypass scan	Bypass	Normal
00001001	RUNT	Boundary-run test	Bypass	Test
00001010	READBN	Boundary read	Boundary scan	Normal
10001011	READBT	Boundary read	Boundary scan	Test
00001100	CELLTST	Boundary self test	Boundary scan	Normal
10001101	TOPHIP	Boundary toggle outputs	Bypass	Test
10001110	SCANCN	Boundary-control register scan	Boundary control	Normal
00001111	SCANCT	Boundary-control register scan	Boundary control	Test
All others	BYPASS	Bypass scan	Bypass	Normal

† Bit 7 is used to maintain even parity in the 8-bit instruction.
‡ The BYPASS instruction is executed in lieu of a SCOPE™ instruction that is not supported in the 'LVTH18512 or 'LVTH182512.

boundary scan

This instruction conforms to the IEEE Std 1149.1-1990 EXTEST instruction. The BSR is selected in the scan path. Data appearing at the device input and I/O pins is captured in the associated BSCs. Data that has been scanned into the I/O BSCs for pins in the output mode is applied to the device I/O pins. Data present at the device pins, except for output enables, is passed through the BSCs to the normal on-chip logic. For I/O pins, the operation of a pin as input or output is determined by the contents of the output-enable BSCs (bits 47–44 of the BSR). When a given output enable is active (logic 0), the associated I/O pins operate in the output mode. Otherwise, the I/O pins operate in the input mode. The device operates in the test mode.

identification read

This instruction conforms to the IEEE Std 1149.1-1990 IDCODE instruction. The IDR is selected in the scan path. The device operates in the normal mode.

sample boundary

This instruction conforms to the IEEE Std 1149.1-1990 SAMPLE/PRELOAD instruction. The BSR is selected in the scan path. Data appearing at the device input pins and I/O pins in the input mode is captured in the associated BSCs, while data appearing at the outputs of the normal on-chip logic is captured in the BSCs associated with I/O pins in the output mode. The device operates in the normal mode.

bypass scan

This instruction conforms to the IEEE Std 1149.1-1990 BYPASS instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the normal mode.

control boundary to high impedance

This instruction conforms to the IEEE Std 1149.1a-1993 HIGHZ instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in a modified test mode in which all device I/O pins are placed in the high-impedance state, the device input pins remain operational, and the normal on-chip logic function is performed.

control boundary to 1/0

This instruction conforms to the IEEE Std 1149.1a-1993 CLAMP instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the I/O BSCs for pins in the output mode is applied to the device I/O pins. The device operates in the test mode.

boundary-run test

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the test mode. The test operation specified in the BCR is executed during Run-Test/Idle. The five test operations decoded by the BCR are: sample inputs/toggle outputs (TOPSIP), PRPG, PSA, simultaneous PSA and PRPG (PSA/PRPG), and simultaneous PSA and binary count up (PSA/COUNT).

boundary read

The BSR is selected in the scan path. The value in the BSR remains unchanged during Capture-DR. This instruction is useful for inspecting data after a PSA operation.

boundary self test

The BSR is selected in the scan path. All BSCs capture the inverse of their current values during Capture-DR. In this way, the contents of the shadow latches can be read out to verify the integrity of both shift-register and shadow-latch elements of the BSR. The device operates in the normal mode.

boundary toggle outputs

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK in Run-Test/Idle and is then updated in the shadow latches and thereby applied to the associated device I/O pins on each falling edge of TCK in Run-Test/Idle. Data in the input-mode BSCs remains constant. Data appearing at the device input or I/O pins is not captured in the input-mode BSCs. The device operates in the test mode.

boundary-control-register scan

The BCR is selected in the scan path. The value in the BCR remains unchanged during Capture-DR. This operation must be performed before a boundary-run test operation to specify which test operation is to be executed.

boundary-control-register opcode description

The BCR opcodes are decoded from BCR bits 2–0 as shown in Table 4. The selected test operation is performed while the RUNT instruction is executed in the Run-Test/Idle state. The following descriptions detail the operation of each BCR instruction and illustrate the associated PSA and PRPG algorithms.

Table 4. Boundary-Control Register Opcodes

BINARY CODE BIT 2 → BIT 0 MSB → LSB	DESCRIPTION
X00	Sample inputs/toggle outputs (TOPSIP)
X01	Pseudo-random pattern generation/36-bit mode (PRPG)
X10	Parallel-signature analysis/36-bit mode (PSA)
011	Simultaneous PSA and PRPG/18-bit mode (PSA/PRPG)
111	Simultaneous PSA and binary count up/18-bit mode (PSA/COUNT)

While the control input BSCs (bits 47–36) are not included in the toggle, PSA, PRPG, or COUNT algorithms, the output-enable BSCs (bits 47–44 of the BSR) control the drive state (active or high impedance) of the selected device output pins. These BCR instructions are only valid when both bytes of the device are operating in one direction of data flow (i.e., $1\overline{OEAB} \neq 1\overline{OEBA}$ and $2\overline{OEAB} \neq 2\overline{OEBA}$) and in the same direction of data flow (i.e., $1\overline{OEAB} = 2\overline{OEAB}$ and $1\overline{OEBA} = 2\overline{OEBA}$). Otherwise, the bypass instruction is operated.

sample inputs/toggle outputs (TOPSIP)

Data appearing at the selected device input-mode I/O pins is captured in the shift-register elements of the associated BSCs on each rising edge of TCK. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK.

pseudo-random pattern generation (PRPG)

A pseudo-random pattern is generated in the shift-register elements of the selected BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device output-mode I/O pins on each falling edge of TCK. Figures 5 and 6 show the 36-bit linear-feedback shift-register algorithms through which the patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

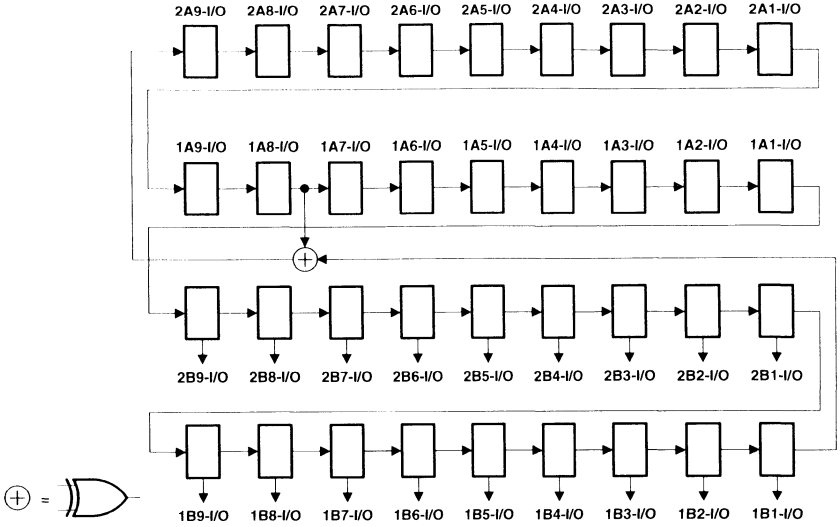


Figure 5. 36-Bit PRPG Configuration (1$\overline{OEAB}$ = 2$\overline{OEAB}$ = 0, 1$\overline{OEBA}$ = 2$\overline{OEBA}$ = 1)

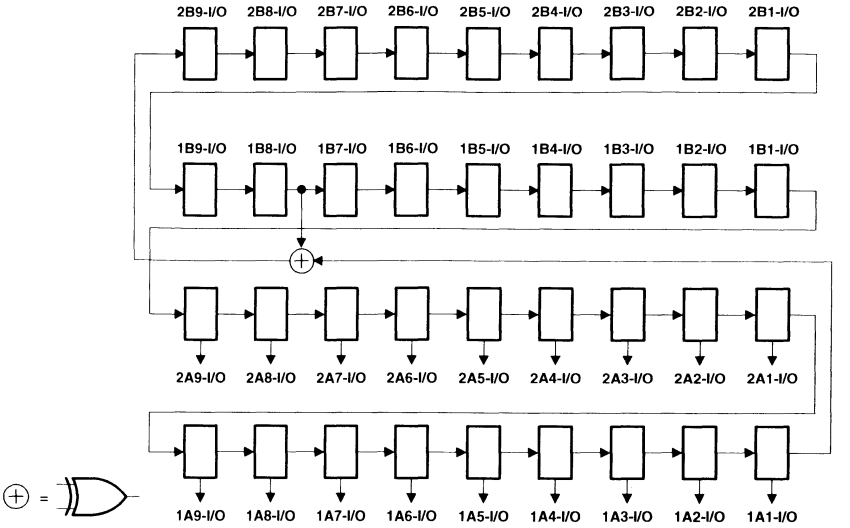


Figure 6. 36-Bit PRPG Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

parallel-signature analysis (PSA)

Data appearing at the selected device input-mode I/O pins is compressed into a 36-bit parallel signature in the shift-register elements of the selected BSCs on each rising edge of TCK. Data in the shadow latches of the selected output-mode BSCs remains constant and is applied to the associated device I/O pins. Figures 7 and 8 show the 36-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

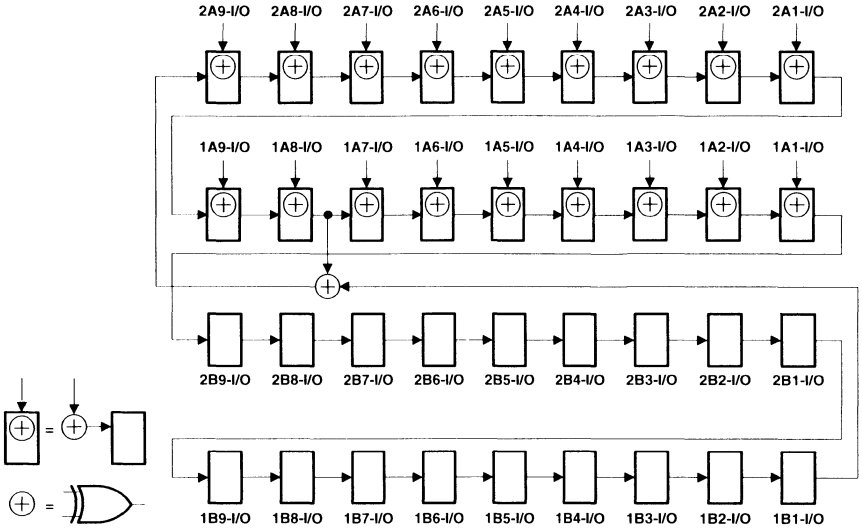


Figure 7. 36-Bit PSA Configuration (1$\overline{OEAB}$ = 2$\overline{OEAB}$ = 0, 1$\overline{OEBA}$ = 2$\overline{OEBA}$ = 1)

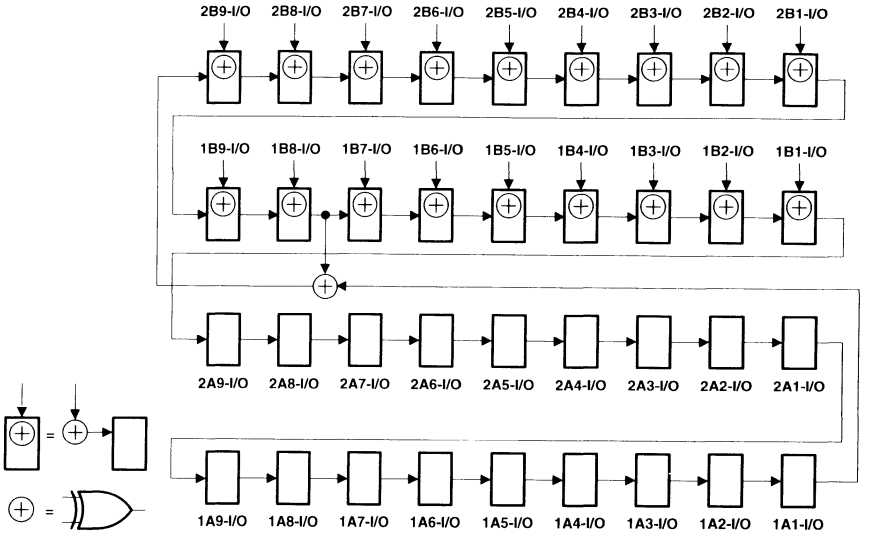


Figure 8. 36-Bit PSA Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

simultaneous PSA and PRPG (PSA/PRPG)

Data appearing at the selected device input-mode I/O pins is compressed into an 18-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, an 18-bit pseudo-random pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 9 and 10 show the 18-bit linear-feedback shift-register algorithms through which the signature and patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

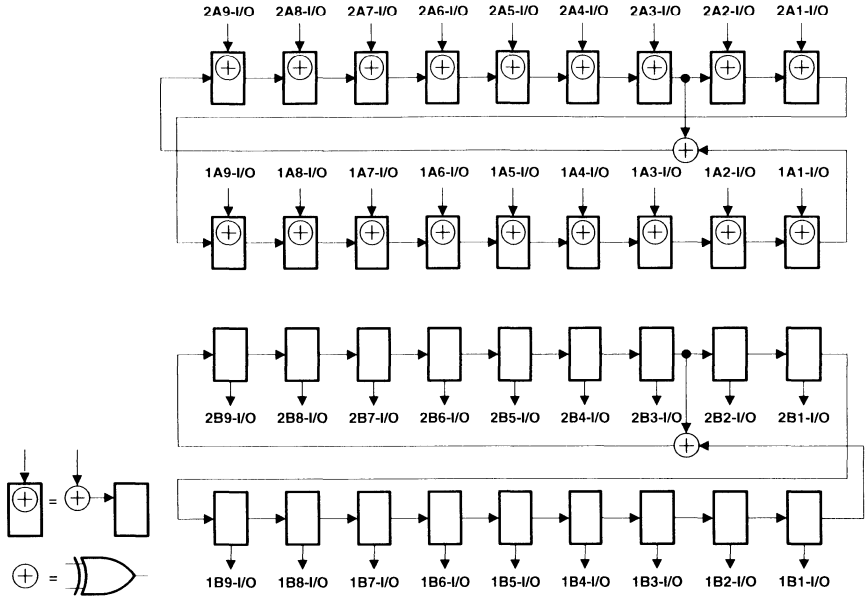


Figure 9. 18-Bit PSA/PRPG Configuration (1$\overline{OEAB}$ = 2$\overline{OEAB}$ = 0, 1$\overline{OEBA}$ = 2$\overline{OEBA}$ = 1)

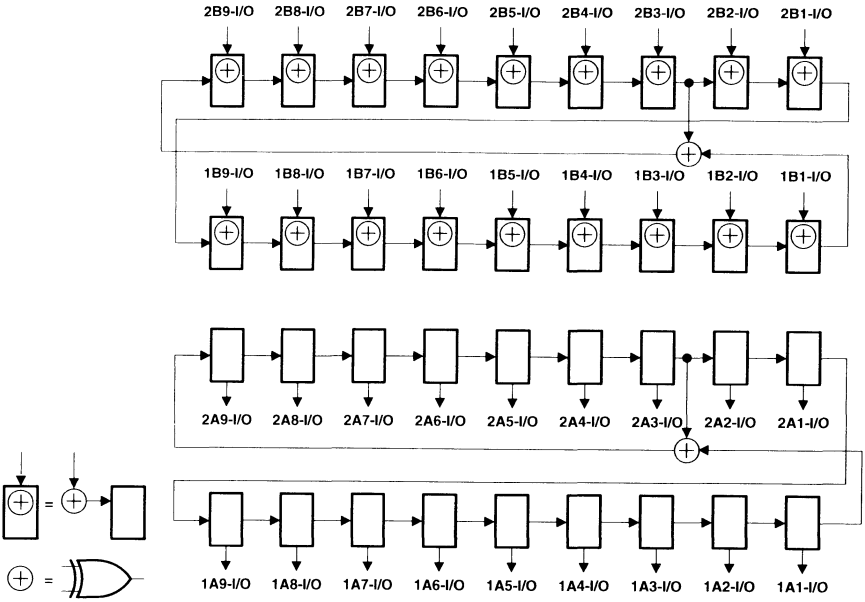


Figure 10. 18-Bit PSA/PRPG Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

simultaneous PSA and binary count up (PSA/COUNT)

Data appearing at the selected device input-mode I/O pins is compressed into an 18-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, an 18-bit binary count-up pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 11 and 12 show the 18-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

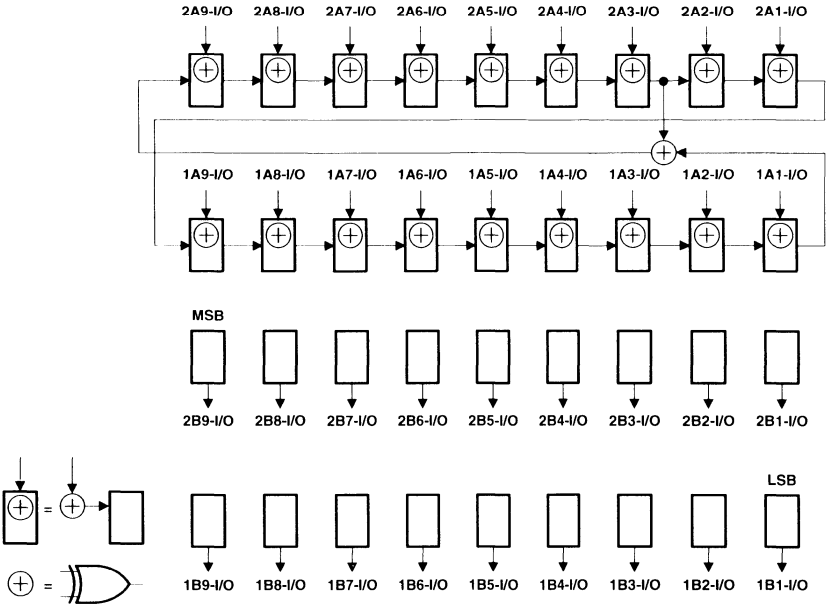


Figure 11. 18-Bit PSA/COUNT Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 0, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 1)

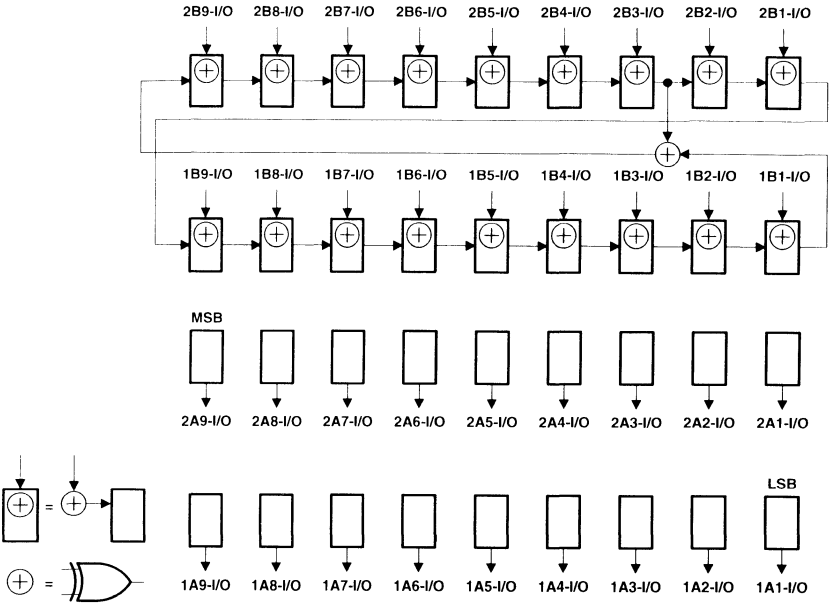


Figure 12. 18-Bit PSA/COUNT Configuration ($1\overline{OEAB}$ = $2\overline{OEAB}$ = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

timing description

All test operations of the 'LVTH18512 and 'LVTH182512 are synchronous to the TCK signal. Data on the TDI, TMS, and normal-function inputs is captured on the rising edge of TCK. Data appears on the TDO and normal-function output pins on the falling edge of TCK. The TAP controller is advanced through its states (as shown in Figure 1) by changing the value of TMS on the falling edge of TCK and then applying a rising edge to TCK.

A simple timing example is shown in Figure 13. In this example, the TAP controller begins in the Test-Logic-Reset state and is advanced through its states, as necessary, to perform one instruction-register scan and one data-register scan. While in the Shift-IR and Shift-DR states, TDI is used to input serial data, and TDO is used to output serial data. The TAP controller is then returned to the Test-Logic-Reset state. Table 5 details the operation of the test circuitry during each TCK cycle.

Table 5. Explanation of Timing Example

TCK CYCLE(S)	TAP STATE AFTER TCK	DESCRIPTION
1	Test-Logic-Reset	TMS is changed to a logic 0 value on the falling edge of TCK to begin advancing the TAP controller toward the desired state.
2	Run-Test/Idle	
3	Select-DR-Scan	
4	Select-IR-Scan	
5	Capture-IR	The IR captures the 8-bit binary value 10000001 on the rising edge of TCK as the TAP controller exits the Capture-IR state.
6	Shift-IR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
7–13	Shift-IR	One bit is shifted into the IR on each TCK rising edge. With TDI held at a logic 1 value, the 8-bit binary value 11111111 is serially scanned into the IR. At the same time, the 8-bit binary value 10000001 is serially scanned out of the IR via TDO. In TCK cycle 13, TMS is changed to a logic 1 value to end the IR scan on the next TCK cycle. The last bit of the instruction is shifted as the TAP controller advances from Shift-IR to Exit1-IR.
14	Exit1-IR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
15	Update-IR	The IR is updated with the new instruction (BYPASS) on the falling edge of TCK.
16	Select-DR-Scan	
17	Capture-DR	The bypass register captures a logic 0 value on the rising edge of TCK as the TAP controller exits the Capture-DR state.
18	Shift-DR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
19–20	Shift-DR	The binary value 101 is shifted in via TDI, while the binary value 010 is shifted out via TDO.
21	Exit1-DR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
22	Update-DR	The selected data register is updated with the new data on the falling edge of TCK.
23	Select-DR-Scan	
24	Select-IR-Scan	
25	Test-Logic-Reset	Test operation completed

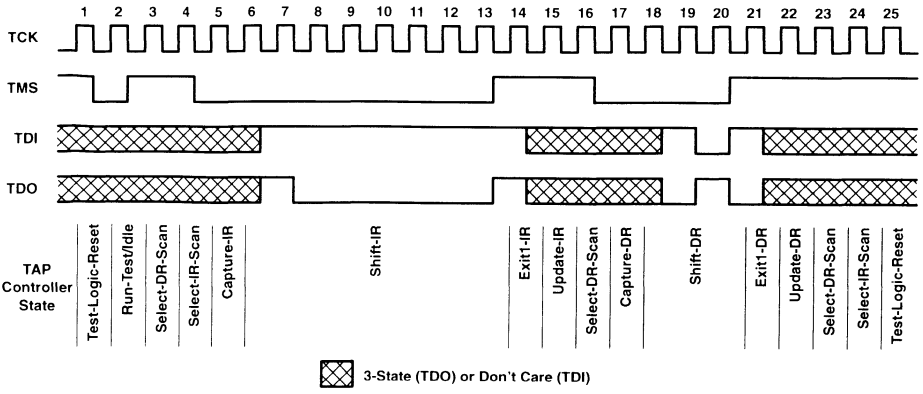


Figure 13. Timing Example

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH18512 ..... 96 mA
SN54LVTH182512 (A port or TDO) ..... 96 mA
SN54LVTH182512 (B port) ..... 30 mA
SN74LVTH18512 ..... 128 mA
SN74LVTH182512 (A port or TDO) ..... 128 mA
SN74LVTH182512 (B port) ..... 30 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH18512 ..... 48 mA
SN54LVTH182512 (A port or TDO) ..... 48 mA
SN54LVTH182512 (B port) ..... 30 mA
SN74LVTH18512 ..... 64 mA
SN74LVTH182512 (A port or TDO) ..... 64 mA
SN74LVTH182512 (B port) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 73°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings can be exceeded if the input and output clamp-current ratings are observed.
2. This current only flows when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH18512		SN74LVTH18512		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			24		32	mA
I_{OL}†	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH18512			SN74LVTH18512			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 µA	V_{CC}−0.2			V_{CC}−0.2			V
		V_{CC} = 2.7 V,	I_{OH} = −3 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = −8 mA	2.4			2.4			
			I_{OH} = −24 mA	2						
			I_{OH} = −32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	CLK, LE, TCK	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	$\overline{OE}$, TDI, TMS	V_{CC} = 3.6 V	V_I = 5.5 V			5			5	
			V_I = V_{CC}			1			1	
			V_I = 0	−25		−100	−25		−100	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$§	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75		500	75	150	500	µA
			V_I = 2 V	−75		−500	−75	−150	−500	
I_{OZH}	TDO	V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}	TDO	V_{CC} = 3.6 V,	V_O = 0.5 V			−1			−1	µA
I_{OZPU}	TDO	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{OZPD}	TDO	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.6	2		0.6	2	mA
			Outputs low		18	24		18	24	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.5			0.5	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			10			10		pF
C_o		V_O = 3 V or 0			8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

				SN54LVTH18512				SN74LVTH18512				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA		0	100	0	80	0	100	0	80	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low		4.4		5.6		4.4		5.6		ns
		LEAB or LEBA high		3		3		3		3		
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑		2.8		3		2.8		3		ns
		A before LEAB↓ or B before LEBA↓	CLK high	1.5		0.7		1.5		0.7		
			CLK low	1.6		1.6		1.6		1.6		
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑		1.4		1.1		1.4		1.1		ns
		A after LEAB↓ or B after LEBA↓		3.1		3.5		3.1		3.5		

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

			SN54LVTH18512				SN74LVTH18512				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, LE, or $\overline{OE}$ before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, LE, or $\overline{OE}$ after TCK↑	1.7		1		1.7		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18512				SN74LVTH18512				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		100		80		100		80		MHz
t_{PLH}	A or B	B or A	1.5	5.1		5.8	1.5	4.9		5.6	ns
t_{PHL}			1.5	5.1		5.8	1.5	4.9		5.6	
t_{PLH}	CLKAB or CLKBA	B or A	1.5	6.3		7.2	1.5	5.8		6.8	ns
t_{PHL}			1.5	6.3		7.2	1.5	5.8		6.8	
t_{PLH}	LEAB or LEBA	B or A	1.5	7.8		9.2	1.5	7.4		8.4	ns
t_{PHL}			1.5	6		6.6	1.5	5.7		6.4	
t_{PZH}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	1.5	7.6		8.5	1.5	7.1		8.3	ns
t_{PZL}			1.5	7.6		8.5	1.5	7.1		8.3	
t_{PHZ}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.5	8.3		8.8	2.5	7.8		8.4	ns
t_{PLZ}			2.5	8.3		8.8	2.5	7.8		8.4	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18512				SN74LVTH18512				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

TEXAS INSTRUMENTS
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recommended operating conditions (see Note 4)

			SN54LVTH182512		SN74LVTH182512		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	A port, TDO		–24		–32	mA
		B port		–12		–12	
I_{OL}	Low-level output current	A port, TDO		24		32	mA
		B port		12		12	
I_{OL}†	Low-level output current	A port, TDO		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH182512			SN74LVTH182512			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}	A, B, TDO	V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 µA	V_{CC}−0.2			V_{CC}−0.2			V
	A port, TDO	V_{CC} = 2.7 V,	I_{OH} = −3 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = −8 mA	2.4			2.4			
			I_{OH} = −24 mA	2						
			I_{OH} = −32 mA				2			
	B port	V_{CC} = 3 V,	I_{OH} = −12 mA	2			2			
V_{OL}	A, B, TDO	V_{CC} = 2.7 V,	I_{OL} = 100 µA			0.2			0.2	V
	A port, TDO	V_{CC} = 2.7 V,	I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
	B port	V_{CC} = 3 V,	I_{OL} = 12 mA			0.8			0.8	
I_I	CLK, LE, TCK	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	$\overline{OE}$, TDI, TMS	V_{CC} = 3.6 V	V_I = 5.5 V			5			5	
			V_I = V_{CC}			1			1	
			V_I = 0	−25		−100	−25		−100	
	A or B ports‡	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$§	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75		500	75	150	500	µA
			V_I = 2 V	−75		−500	−75	−150	−500	
I_{OZH}	TDO	V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}	TDO	V_{CC} = 3.6 V,	V_O = 0.5 V			−1			−1	µA
I_{OZPU}	TDO	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{OZPD}	TDO	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.6	2		0.6	2	mA
			Outputs low		18	24		18	24	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				0.5			0.5	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			10			10		pF
C_o		V_O = 3 V or 0			8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

				SN54LVTH182512				SN74LVTH182512				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA		0	100	0	80	0	100	0	80	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low		4.4		5.6		4.4		5.6		ns
		LEAB or LEBA high		3		3		3		3		
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑		2.8		3		2.8		3		ns
		A before LEAB↓ or B before LEBA↓	CLK high	1.5		0.7		1.5		0.7		
			CLK low	1.6		1.6		1.6		1.6		
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑		1.4		1.1		1.4		1.1		ns
		A after LEAB↓ or B after LEBA↓		3.1		3.5		3.1		3.5		

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

			SN54LVTH182512				SN74LVTH182512				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, LE, or $\overline{OE}$ before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, LE, or $\overline{OE}$ after TCK↑	1.7		1		1.7		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

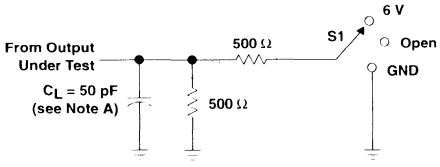
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182512				SN74LVTH182512				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		100		80		100		80		MHz
t_{PLH}	A	B	1.5	6		6.7	1.5	5.7		6.4	ns
t_{PHL}			1.5	6		6.7	1.5	5.7		6.4	
t_{PLH}	B	A	1.5	5.1		5.8	1.5	4.9		5.6	ns
t_{PHL}			1.5	5.1		5.8	1.5	4.9		5.6	
t_{PLH}	CLKAB	B	1.5	7.1		8.1	1.5	6.7		7.7	ns
t_{PHL}			1.5	7.1		8.1	1.5	6.7		7.7	
t_{PLH}	CLKBA	A	1.5	6.3		7.2	1.5	5.8		6.8	ns
t_{PHL}			1.5	6.3		7.2	1.5	5.8		6.8	
t_{PLH}	LEAB	B	1.5	8.7		9.7	1.5	8.2		9.2	ns
t_{PHL}			1.5	6.5		6.9	1.5	6.2		6.7	
t_{PLH}	LEBA	A	1.5	7.8		9.2	1.5	7.4		8.4	ns
t_{PHL}			1.5	6		6.6	1.5	5.7		6.4	
t_{PZH}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	1.5	8.4		9.6	1.5	7.9		8.7	ns
t_{PZL}			1.5	8.4		9.6	1.5	7.9		8.7	
t_{PHZ}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.5	9.1		9.3	2.5	8.4		8.9	ns
t_{PLZ}			2.5	9.1		9.3	2.5	8.4		8.9	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

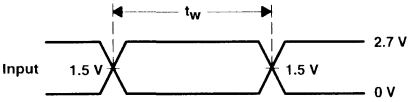
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182512				SN74LVTH182512				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

PARAMETER MEASUREMENT INFORMATION

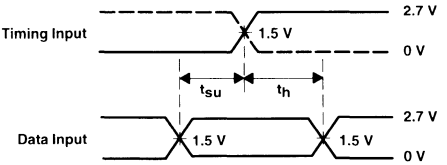


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

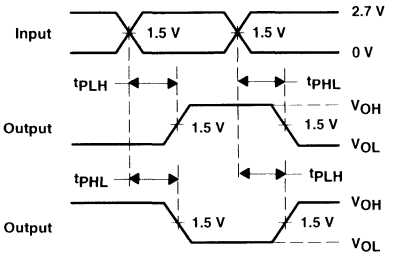
LOAD CIRCUIT



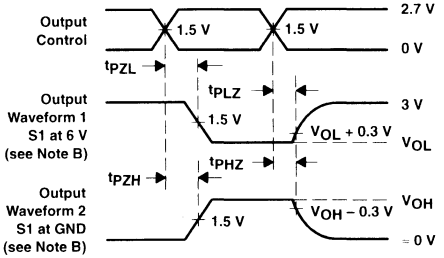
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



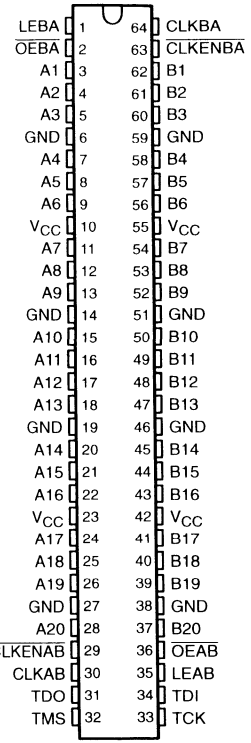
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 14. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *SCOPE*™ Family of Testability Products**
- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art 3.3-V ABT Design Supports Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **B-Port Outputs of 'LVTH182514 Devices Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required**
- **Compatible With the IEEE Std 1149.1-1990 (JTAG) Test Access Port and Boundary-Scan Architecture**
- ***SCOPE*™ Instruction Set**
  - **IEEE Std 1149.1-1990 Required Instructions and Optional CLAMP and HIGHZ**
  - **Parallel-Signature Analysis at Inputs**
  - **Pseudo-Random Pattern Generation From Outputs**
  - **Sample Inputs/Toggle Outputs**
  - **Binary Count From Outputs**
  - **Device Identification**
  - **Even-Parity Opcodes**
- **Package Options Include 64-Pin Plastic Thin Shrink Small-Outline (DGG) and 64-Pin Ceramic Dual Flat (HKC) Packages Using 0.5-mm Center-to-Center Spacings**

SN54LVTH18514, SN54LVTH182514 . . . HKC PACKAGE
SN74LVTH18514, SN74LVTH182514 . . . DGG PACKAGE
(TOP VIEW)



description

The 'LVTH18514 and 'LVTH182514 scan test devices with 20-bit universal bus transceivers are members of the Texas Instruments SCOPE™ testability integrated-circuit family. This family of devices supports IEEE Std 1149.1-1990 boundary scan to facilitate testing of complex circuit-board assemblies. Scan access to the test circuitry is accomplished via the 4-wire test access port (TAP) interface.

Additionally, these devices are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

description (continued)

In the normal mode, these devices are 20-bit universal bus transceivers that combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, or clocked modes. The test circuitry can be activated by the TAP to take snapshot samples of the data appearing at the device pins or to perform a self-test on the boundary-test cells. Activating the TAP in the normal mode does not affect the functional operation of the SCOPE™ universal bus transceivers.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched while $\overline{CLKENAB}$ is high and/or CLKAB is held at a static low or high logic level. Otherwise, if LEAB is low and $\overline{CLKENAB}$ is low, A data is stored on a low-to-high transition of CLKAB. When $\overline{OEAB}$ is low, the B outputs are active. When $\overline{OEAB}$ is high, the B outputs are in the high-impedance state. B-to-A data flow is similar to A-to-B data flow, but uses the $\overline{OEBA}$, LEBA, $\overline{CLKENBA}$, and CLKBA inputs.

In the test mode, the normal operation of the SCOPE™ universal bus transceivers is inhibited, and the test circuitry is enabled to observe and control the I/O boundary of the device. When enabled, the test circuitry performs boundary-scan test operations according to the protocol described in IEEE Std 1149.1-1990.

Four dedicated test pins are used to observe and control the operation of the test circuitry: test data input (TDI), test data output (TDO), test mode select (TMS), and test clock (TCK). Additionally, the test circuitry performs other testing functions, such as parallel-signature analysis (PSA) on data inputs and pseudo-random pattern generation (PRPG) from data outputs. All testing and scan operations are synchronized to the TAP interface.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The B-port outputs of 'LVTH182514, which are designed to source or sink up to 12 mA, include equivalent 25-Ω series resistors to reduce overshoot and undershoot.

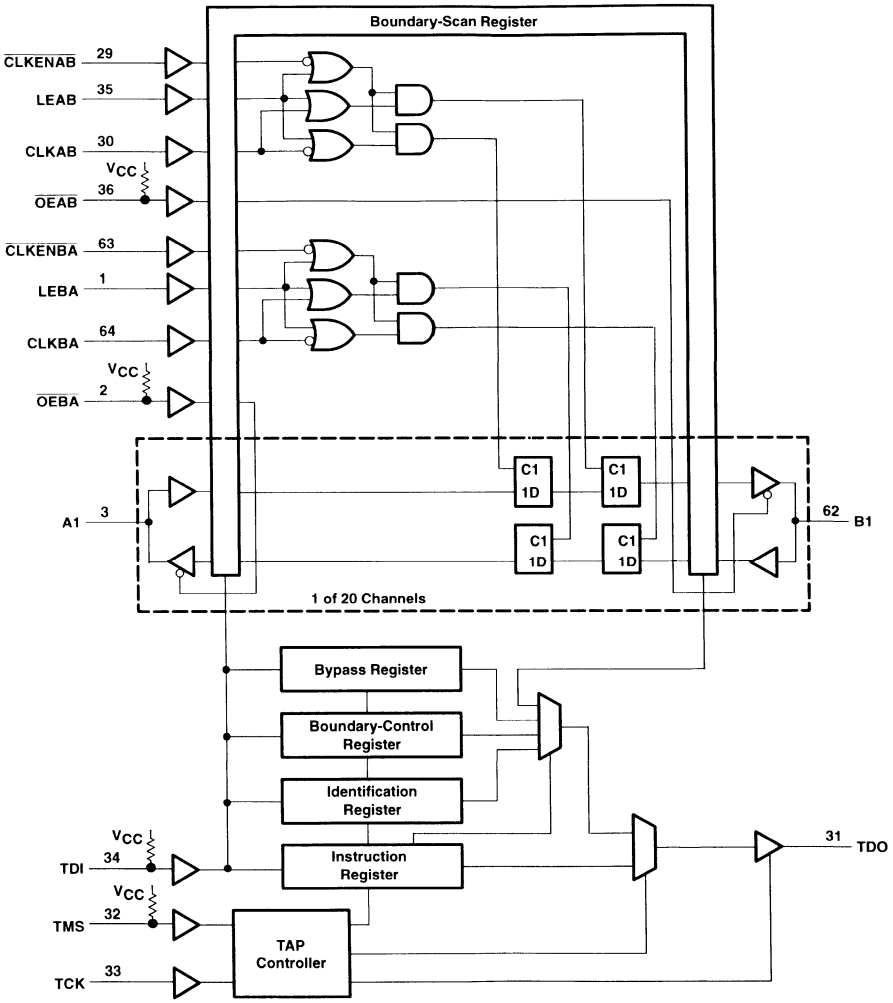
The SN54LVTH18514 and SN54LVTH182514 are characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH18514 and SN74LVTH182514 are characterized for operation from –40°C to 85°C.

FUNCTION TABLE†
(normal mode, each register)

INPUTS					OUTPUT
$\overline{OEAB}$	LEAB	$\overline{CLKENAB}$	CLKAB	A	B
L	L	L	L	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	H	X	X	B_0‡
L	H	X	X	L	L
L	H	X	X	H	H
H	X	X	X	X	Z

† A-to-B data flow is shown. B-to-A data flow is similar, but uses $\overline{OEBA}$, LEBA, $\overline{CLKENBA}$, and CLKBA.
‡ Output level before the indicated steady-state input conditions were established

functional block diagram



Terminal Functions

TERMINAL NAME	DESCRIPTION
A1–A20	Normal-function A-bus I/O ports. See function table for normal-mode logic.
B1–B20	Normal-function B-bus I/O ports. See function table for normal-mode logic.
CLKAB, CLKBA	Normal-function clock inputs. See function table for normal-mode logic.
$\overline{\text{CLKENAB}}$, $\overline{\text{CLKENBA}}$	Normal-function clock enables. See function table for normal-mode logic.
GND	Ground
LEAB, LEBA	Normal-function latch enables. See function table for normal-mode logic.
OEAB, $\overline{\text{OEBA}}$	Normal-function output enables. See function table for normal-mode logic. An internal pullup at each terminal forces the terminal to a high level if left unconnected.
TCK	Test clock. One of four terminals required by IEEE Std 1149.1-1990. Test operations of the device are synchronous to TCK. Data is captured on the rising edge of TCK and outputs change on the falling edge of TCK.
TDI	Test data input. One of four terminals required by IEEE Std 1149.1-1990. TDI is the serial input for shifting data through the instruction register or selected data register. An internal pullup forces TDI to a high level if left unconnected.
TDO	Test data output. One of four terminals required by IEEE Std 1149.1-1990. TDO is the serial output for shifting data through the instruction register or selected data register.
TMS	Test mode select. One of four terminals required by IEEE Std 1149.1-1990. TMS directs the device through its TAP controller states. An internal pullup forces TMS to a high level if left unconnected.
V_{CC}	Supply voltage

test architecture

Serial-test information is conveyed by means of a 4-wire test bus or TAP that conforms to IEEE Std 1149.1-1990. Test instructions, test data, and test control signals are passed along this serial-test bus. The TAP controller monitors two signals from the test bus: TCK and TMS. The TAP controller extracts the synchronization (TCK) and state control (TMS) signals from the test bus and generates the appropriate on-chip control signals for the test structures in the device. Figure 1 shows the TAP-controller state diagram.

The TAP controller is fully synchronous to the TCK signal. Input data is captured on the rising edge of TCK and output data changes on the falling edge of TCK. This scheme ensures data to be captured is valid for fully one-half of the TCK cycle.

The functional block diagram shows the IEEE Std 1149.1-1990 4-wire test bus and boundary-scan architecture and the relationships of the test bus, the TAP controller, and the test registers. As shown, the device contains an 8-bit instruction register and four test data registers: a 48-bit boundary-scan register, a 3-bit boundary-control register, a 1-bit bypass register, and a 32-bit device-identification register.

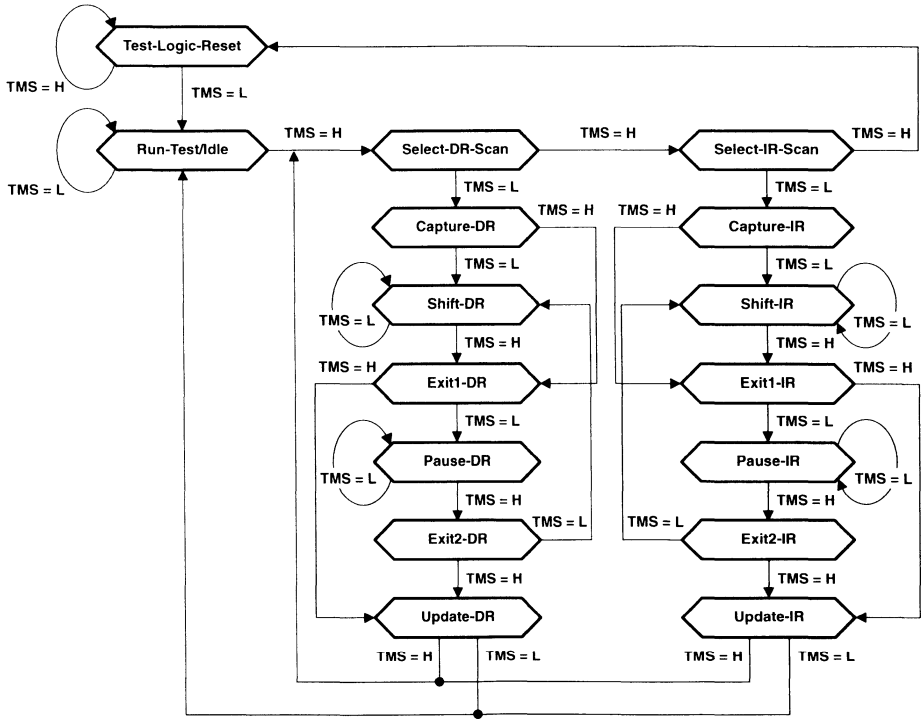


Figure 1. TAP-Controller State Diagram

state diagram description

The TAP controller is a synchronous finite-state machine that provides test control signals throughout the device. The state diagram shown in Figure 1 is in accordance with IEEE Std 1149.1-1990. The TAP controller proceeds through its states, based on the level of TMS at the rising edge of TCK.

As shown, the TAP controller consists of 16 states. There are six stable states (indicated by a looping arrow in the state diagram) and ten unstable states. A stable state is defined as a state the TAP controller can retain for consecutive TCK cycles. Any state that does not meet this criterion is an unstable state.

There are two main paths through the state diagram: one to access and control the selected data register and one to access and control the instruction register. Only one register at a time can be accessed.

Test-Logic-Reset

The device powers up in the Test-Logic-Reset state. In the stable Test-Logic-Reset state, the test logic is reset and is disabled so that the normal logic function of the device is performed. The instruction register is reset to an opcode that selects the optional IDCODE instruction, if supported, or the BYPASS instruction. Certain data registers also can be reset to their power-up values.

The state machine is constructed such that the TAP controller returns to the Test-Logic-Reset state in no more than five TCK cycles if TMS is left high. The TMS pin has an internal pullup resistor that forces it high if left unconnected or if a board defect causes it to be open circuited.

For the 'LVTH18514 and 'LVTH182514, the instruction register is reset to the binary value 10000001, which selects the IDCODE instruction. Bits 47–46 in the boundary-scan register are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., if test mode were invoked, the outputs would be at high-impedance state). Reset values of other bits in the boundary-scan register should be considered indeterminate. The boundary-control register is reset to the binary value 010, which selects the PSA test operation.

Run-Test/Idle

The TAP controller must pass through the Run-Test/Idle state (from Test-Logic-Reset) before executing any test operations. The Run-Test/Idle state also can be entered following data-register or instruction-register scans. Run-Test/Idle is a stable state in which the test logic can be actively running a test or can be idle. The test operations selected by the boundary-control register are performed while the TAP controller is in the Run-Test/Idle state.

Select-DR-Scan, Select-IR-Scan

No specific function is performed in the Select-DR-Scan and Select-IR-Scan states, and the TAP controller exits either of these states on the next TCK cycle. These states allow the selection of either data-register scan or instruction-register scan.

Capture-DR

When a data-register scan is selected, the TAP controller must pass through the Capture-DR state. In the Capture-DR state, the selected data register can capture a data value as specified by the current instruction. Such capture operations occur on the rising edge of TCK, upon which the TAP controller exits the Capture-DR state.

Shift-DR

Upon entry to the Shift-DR state, the data register is placed in the scan path between TDI and TDO. On the first falling edge of TCK, TDO goes from the high-impedance state to an active state. TDO enables to the logic level present in the least-significant bit of the selected data register.

Shift-DR (continued)

While in the stable Shift-DR state, data is serially shifted through the selected data register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-DR state (i.e., no shifting occurs during the TCK cycle, in which the TAP controller changes from Capture-DR to Shift-DR or from Exit2-DR to Shift-DR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-DR state.

Exit1-DR, Exit2-DR

The Exit1-DR and Exit2-DR states are temporary states that end a data-register scan. It is possible to return to the Shift-DR state from either Exit1-DR or Exit2-DR without recapturing the data register. On the first falling edge of TCK after entry to Exit1-DR, TDO goes from the active state to the high-impedance state.

Pause-DR

No specific function is performed in the stable Pause-DR state, in which the TAP controller can remain indefinitely. The Pause-DR state suspends and resumes data-register scan operations without loss of data.

Update-DR

If the current instruction calls for the selected data register to be updated with current data, such updates occur on the falling edge of TCK, following entry to the Update-DR state.

Capture-IR

When an instruction-register scan is selected, the TAP controller must pass through the Capture-IR state. In the Capture-IR state, the instruction register captures its current status value. This capture operation occurs on the rising edge of TCK, upon which the TAP controller exits the Capture-IR state. For the 'LVTH18514 and 'LVTH182514, the status value loaded in the Capture-IR state is the fixed binary value 10000001.

Shift-IR

Upon entry to the Shift-IR state, the instruction register is placed in the scan path between TDI and TDO. On the first falling edge of TCK, TDO goes from the high-impedance state to the active state. TDO enables to the logic level present in the least-significant bit of the instruction register.

While in the stable Shift-IR state, instruction data is serially shifted through the instruction register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-IR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-IR to Shift-IR or from Exit2-IR to Shift-IR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-IR state.

Exit1-IR, Exit2-IR

The Exit1-IR and Exit2-IR states are temporary states that end an instruction-register scan. It is possible to return to the Shift-IR state from either Exit1-IR or Exit2-IR without recapturing the instruction register. On the first falling edge of TCK after entry to Exit1-IR, TDO goes from the active state to the high-impedance state.

Pause-IR

No specific function is performed in the stable Pause-IR state, in which the TAP controller can remain indefinitely. The Pause-IR state suspends and resumes instruction-register scan operations without loss of data.

Update-IR

The current instruction is updated and takes effect on the falling edge of TCK, following entry to the Update-IR state.

register overview

With the exception of the bypass and device-identification registers, any test register can be thought of as a serial-shift register with a shadow latch on each bit. The bypass and device-identification registers differ in that they contain only a shift register. During the appropriate capture state (Capture-IR for instruction register, Capture-DR for data registers), the shift register can be parallel loaded from a source specified by the current instruction. During the appropriate shift state (Shift-IR or Shift-DR), the contents of the shift register are shifted out from TDO while new contents are shifted in at TDI. During the appropriate update state (Update-IR or Update-DR), the shadow latches are updated from the shift register.

instruction register description

The instruction register (IR) is eight bits long and tells the device what instruction is to be executed. Information contained in the instruction includes the mode of operation (either normal mode, in which the device performs its normal logic function, or test mode, in which the normal logic function is inhibited or altered), the test operation to be performed, which of the four data registers is to be selected for inclusion in the scan path during data-register scans, and the source of data to be captured into the selected data register during Capture-DR.

Table 3 lists the instructions supported by the 'LVTH18514 and 'LVTH182514. The even-parity feature specified for SCOPE™ devices is supported in this device. Bit 7 of the instruction opcode is the parity bit. Any instructions that are defined for SCOPE™ devices but are not supported by this device default to BYPASS.

During Capture-IR, the IR captures the binary value 10000001. As an instruction is shifted in, this value is shifted out via TDO and can be inspected as verification that the IR is in the scan path. During Update-IR, the value that has been shifted into the IR is loaded into shadow latches. At this time, the current instruction is updated and any specified mode change takes effect. At power up or in the Test-Logic-Reset state, the IR is reset to the binary value 10000001, which selects the IDCODE instruction. The instruction register order of scan is shown in Figure 2.

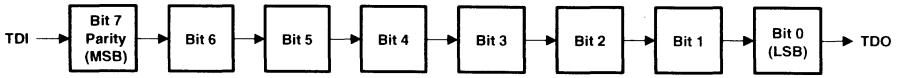


Figure 2. Instruction Register Order of Scan

data register description

boundary-scan register

The boundary-scan register (BSR) is 48 bits long. It contains one boundary-scan cell (BSC) for each normal-function input pin and one BSC for each normal-function I/O pin (one single cell for both input data and output data). The BSR is used to store test data that is to be applied externally to the device output pins, and/or to capture data that appears internally at the outputs of the normal on-chip logic and/or externally at the device input pins.

The source of data to be captured into the BSR during Capture-DR is determined by the current instruction. The contents of the BSR can change during Run-Test/Idle as determined by the current instruction. At power up or in Test-Logic-Reset, BSCs 47–46 are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., if test mode were invoked, the outputs would be at high-impedance state). Reset values of other BSCs should be considered indeterminate.

The BSR order of scan is from TDI through bits 47–0 to TDO. Table 1 shows the BSR bits and their associated device pin signals.

Table 1. Boundary-Scan Register Configuration

BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL
47	$\overline{\text{OEAB}}$	39	A20-I/O	19	B20-I/O
46	$\overline{\text{OEBA}}$	38	A19-I/O	18	B19-I/O
45	CLKAB	37	A18-I/O	17	B18-I/O
44	CLKBA	36	A17-I/O	16	B17-I/O
43	$\overline{\text{CLKENAB}}$	35	A16-I/O	15	B16-I/O
42	$\overline{\text{CLKENBA}}$	34	A15-I/O	14	B15-I/O
41	LEAB	33	A14-I/O	13	B14-I/O
40	LEBA	32	A13-I/O	12	B13-I/O
—	—	31	A12-I/O	11	B12-I/O
—	—	30	A11-I/O	10	B11-I/O
—	—	29	A10-I/O	9	B10-I/O
—	—	28	A9-I/O	8	B9-I/O
—	—	27	A8-I/O	7	B8-I/O
—	—	26	A7-I/O	6	B7-I/O
—	—	25	A6-I/O	5	B6-I/O
—	—	24	A5-I/O	4	B5-I/O
—	—	23	A4-I/O	3	B4-I/O
—	—	22	A3-I/O	2	B3-I/O
—	—	21	A2-I/O	1	B2-I/O
—	—	20	A1-I/O	0	B1-I/O

boundary-control register

The boundary-control register (BCR) is three bits long. The BCR is used in the context of the boundary-run (RUNT) instruction to implement additional test operations not included in the basic SCOPE™ instruction set. Such operations include PRPG, PSA, and binary count up (COUNT). Table 4 shows the test operations that are decoded by the BCR.

During Capture-DR, the contents of the BCR are not changed. At power up or in Test-Logic-Reset, the BCR is reset to the binary value 010, which selects the PSA test operation. The boundary-control register order of scan is shown in Figure 3.

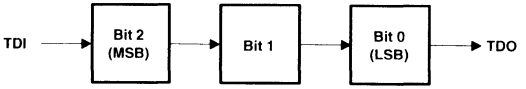


Figure 3. Boundary-Control Register Order of Scan

bypass register

The bypass register is a 1-bit scan path that can be selected to shorten the length of the system scan path, reducing the number of bits per test pattern that must be applied to complete a test operation. During Capture-DR, the bypass register captures a logic 0. The bypass register order of scan is shown in Figure 4.

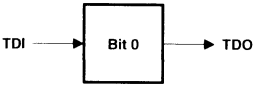


Figure 4. Bypass Register Order of Scan

device-identification register

The device-identification register (IDR) is 32 bits long. It can be selected and read to identify the manufacturer, part number, and version of this device.

For the 'LVTH18514, the binary value 00000000000000011101000000101111 (0003D02F, hex) is captured (during Capture-DR state) in the IDR to identify this device as Texas Instruments SN54/74LVTH18514.

For the 'LVTH182514, the binary value 00000000000000011111000000101111 (0003E02F, hex) is captured (during Capture-DR state) in the IDR to identify this device as Texas Instruments SN54/74LVTH182514.

The IDR order of scan is from TDI through bits 31–0 to TDO. Table 2 shows the IDR bits and their significance.

Table 2. Device-Identification Register Configuration

IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE†
31	VERSION3	27	PARTNUMBER15	11	MANUFACTURER10†
30	VERSION2	26	PARTNUMBER14	10	MANUFACTURER09†
29	VERSION1	25	PARTNUMBER13	9	MANUFACTURER08†
28	VERSION0	24	PARTNUMBER12	8	MANUFACTURER07†
—	—	23	PARTNUMBER11	7	MANUFACTURER06†
—	—	22	PARTNUMBER10	6	MANUFACTURER05†
—	—	21	PARTNUMBER09	5	MANUFACTURER04†
—	—	20	PARTNUMBER08	4	MANUFACTURER03†
—	—	19	PARTNUMBER07	3	MANUFACTURER02†
—	—	18	PARTNUMBER06	2	MANUFACTURER01†
—	—	17	PARTNUMBER05	1	MANUFACTURER00†
—	—	16	PARTNUMBER04	0	LOGIC1†
—	—	15	PARTNUMBER03	—	—
—	—	14	PARTNUMBER02	—	—
—	—	13	PARTNUMBER01	—	—
—	—	12	PARTNUMBER00	—	—

† Note that for TI products, bits 11–0 of the device-identification register always contain the binary value 000000101111 (02F, hex).

instruction-register opcode description

The instruction-register opcodes are shown in Table 3. The following descriptions detail the operation of each instruction.

Table 3. Instruction-Register Opcodes

BINARY CODE† BIT 7 MSB	BIT 0 LSB	SCOPE OPCODE	DESCRIPTION	SELECTED DATA REGISTER	MODE
00000000		EXTEST	Boundary scan	Boundary scan	Test
10000001		IDCODE	Identification read	Device identification	Normal
10000010		SAMPLE/PRELOAD	Sample boundary	Boundary scan	Normal
00000011		BYPASS‡	Bypass scan	Bypass	Normal
10000100		BYPASS‡	Bypass scan	Bypass	Normal
00000101		BYPASS‡	Bypass scan	Bypass	Normal
00000110		HIGHZ	Control boundary to high impedance	Bypass	Modified test
10000111		CLAMP	Control boundary to 1/0	Bypass	Test
10001000		BYPASS‡	Bypass scan	Bypass	Normal
00001001		RUNT	Boundary-run test	Bypass	Test
00001010		READBN	Boundary read	Boundary scan	Normal
10001011		READBT	Boundary read	Boundary scan	Test
00001100		CELLTST	Boundary self test	Boundary scan	Normal
10001101		TOPHIP	Boundary toggle outputs	Bypass	Test
10001110		SCANCN	Boundary-control-register scan	Boundary control	Normal
00001111		SCANCT	Boundary-control-register scan	Boundary control	Test
All others		BYPASS	Bypass scan	Bypass	Normal

† Bit 7 is used to maintain even parity in the 8-bit instruction.
‡ The BYPASS instruction is executed in lieu of a SCOPE™ instruction that is not supported in the 'LVTH18514 or 'LVTH182514.

boundary scan

This instruction conforms to the IEEE Std 1149.1-1990 EXTEST instruction. The BSR is selected in the scan path. Data appearing at the device input and I/O pins is captured in the associated BSCs. Data that has been scanned into the I/O BSCs for pins in the output mode is applied to the device I/O pins. Data present at the device pins, except for output-enables, is passed through the BSCs to the normal on-chip logic. For I/O pins, the operation of a pin as input or output is determined by the contents of the output-enable BSCs (bits 47–46 of the BSR). When a given output enable is active (logic 0), the associated I/O pins operate in the output mode. Otherwise, the I/O pins operate in the input mode. The device operates in the test mode.

identification read

This instruction conforms to the IEEE Std 1149.1-1990 IDCODE instruction. The IDR is selected in the scan path. The device operates in the normal mode.

sample boundary

This instruction conforms to the IEEE Std 1149.1-1990 SAMPLE/PRELOAD instruction. The BSR is selected in the scan path. Data appearing at the device input pins and I/O pins in the input mode is captured in the associated BSCs, while data appearing at the outputs of the normal on-chip logic is captured in the BSCs associated with I/O pins in the output mode. The device operates in the normal mode.

bypass scan

This instruction conforms to the IEEE Std 1149.1-1990 BYPASS instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the normal mode.

control boundary to high impedance

This instruction conforms to the IEEE Std 1149.1a-1993 HIGHZ instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in a modified test mode in which all device I/O pins are placed in the high-impedance state, the device input pins remain operational, and the normal on-chip logic function is performed.

control boundary to 1/0

This instruction conforms to the IEEE Std 1149.1a-1993 CLAMP instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the I/O BSCs for pins in the output mode is applied to the device I/O pins. The device operates in the test mode.

boundary-run test

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the test mode. The test operation specified in the BCR is executed during Run-Test/Idle. The five test operations decoded by the BCR are: sample inputs/toggle outputs (TOPSIP), PRPG, PSA, simultaneous PSA and PRPG (PSA/PRPG), and simultaneous PSA and binary count up (PSA/COUNT).

boundary read

The BSR is selected in the scan path. The value in the BSR remains unchanged during Capture-DR. This instruction is useful for inspecting data after a PSA operation.

boundary self test

The BSR is selected in the scan path. All BSCs capture the inverse of their current values during Capture-DR. In this way, the contents of the shadow latches can be read out to verify the integrity of both shift register and shadow latch elements of the BSR. The device operates in the normal mode.

boundary toggle outputs

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK in Run-Test/Idle and is then updated in the shadow latches and applied to the associated device I/O pins on each falling edge of TCK in Run-Test/Idle. Data in the input-mode BSCs remains constant. Data appearing at the device input or I/O pins is not captured in the input-mode BSCs. The device operates in the test mode.

boundary-control-register scan

The BCR is selected in the scan path. The value in the BCR remains unchanged during Capture-DR. This operation must be performed before a boundary-run test operation to specify which test operation is to be executed.

boundary-control register opcode description

The BCR opcodes are decoded from BCR bits 2–0 as shown in Table 4. The selected test operation is performed while the RUNT instruction is executed in the Run-Test/Idle state. The following descriptions detail the operation of each BCR instruction and illustrate the associated PSA and PRPG algorithms.

Table 4. Boundary-Control Register Opcodes

BINARY CODE BIT 2 MSB	BINARY CODE BIT 0 LSB	DESCRIPTION
X00		Sample inputs/toggle outputs (TOPSIP)
X01		Pseudo-random pattern generation/40-bit mode (PRPG)
X10		Parallel-signature analysis/40-bit mode (PSA)
011		Simultaneous PSA and PRPG/20-bit mode (PSA/PRPG)
111		Simultaneous PSA and binary count up/20-bit mode (PSA/COUNT)

While the control input BSCs (bits 47–36) are not included in the toggle, PSA, PRPG, or COUNT algorithms, the output-enable BSCs (bits 47–46 of the BSR) control the drive state (active or high impedance) of the selected device output pins. These BCR instructions are only valid when the device is operating in one direction of data flow (that is, $\overline{OEAB} \neq \overline{OEBA}$). Otherwise, the bypass instruction is operated.

sample inputs/toggle outputs (TOPSIP)

Data appearing at the selected device input-mode I/O pins is captured in the shift-register elements of the associated BSCs on each rising edge of TCK. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK.

pseudo-random pattern generation (PRPG)

A pseudo-random pattern is generated in the shift-register elements of the selected BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device output-mode I/O pins on each falling edge of TCK. Figures 5 and 6 illustrate the 40-bit linear-feedback shift-register algorithms through which the patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

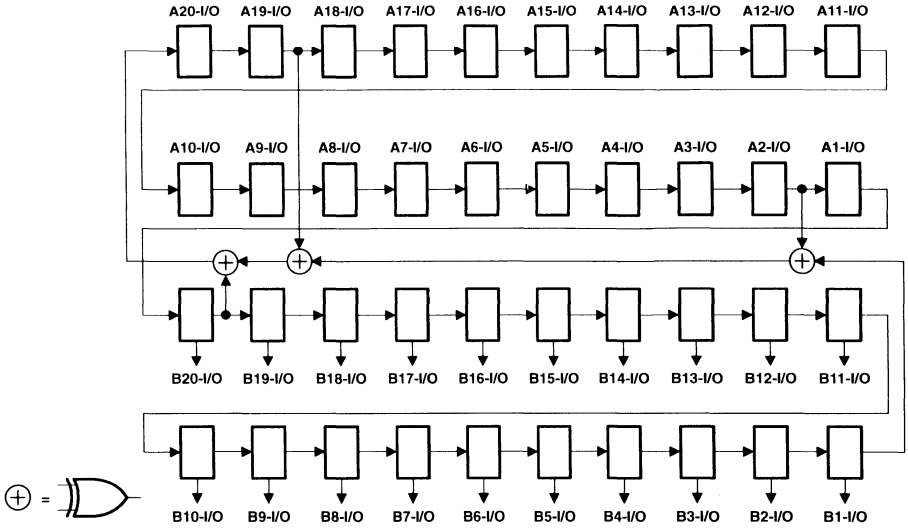


Figure 5. 40-Bit PRPG Configuration ($\overline{OEAB}$ = 0, $\overline{OEBA}$ = 1)

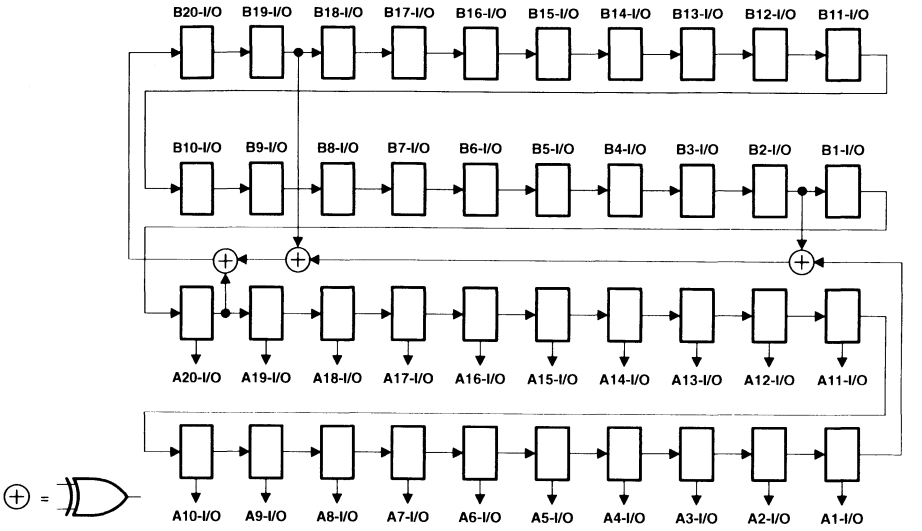


Figure 6. 40-Bit PRPG Configuration ($\overline{OEAB}$ = 1, $\overline{OEBA}$ = 0)

parallel-signature analysis (PSA)

Data appearing at the selected device input-mode I/O pins is compressed into a 40-bit parallel signature in the shift-register elements of the selected BSCs on each rising edge of TCK. Data in the shadow latches of the selected output-mode BSCs remains constant and is applied to the associated device I/O pins. Figures 7 and 8 illustrate the 40-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

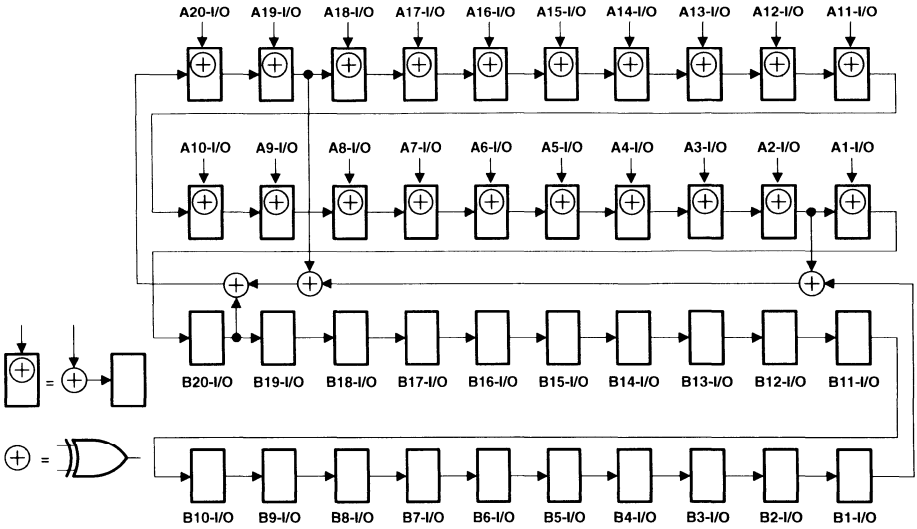


Figure 7. 40-Bit PSA Configuration ($\overline{OEAB}$ = 0, $\overline{OEBA}$ = 1)

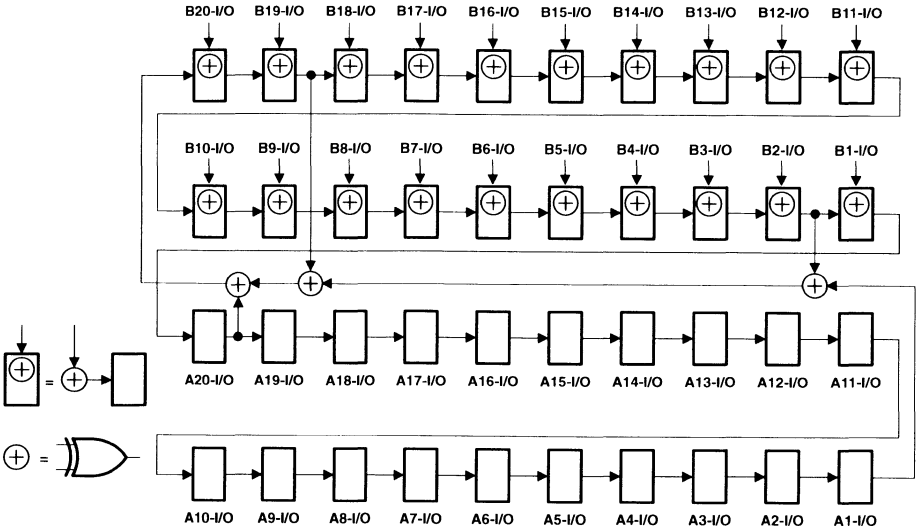


Figure 8. 40-Bit PSA Configuration ($\overline{OEAB}$ = 1, $\overline{OEBA}$ = 0)

simultaneous PSA and PRPG (PSA/PRPG)

Data appearing at the selected device input-mode I/O pins is compressed into a 20-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, a 20-bit pseudo-random pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 9 and 10 illustrate the 20-bit linear-feedback shift-register algorithms through which the signature and patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

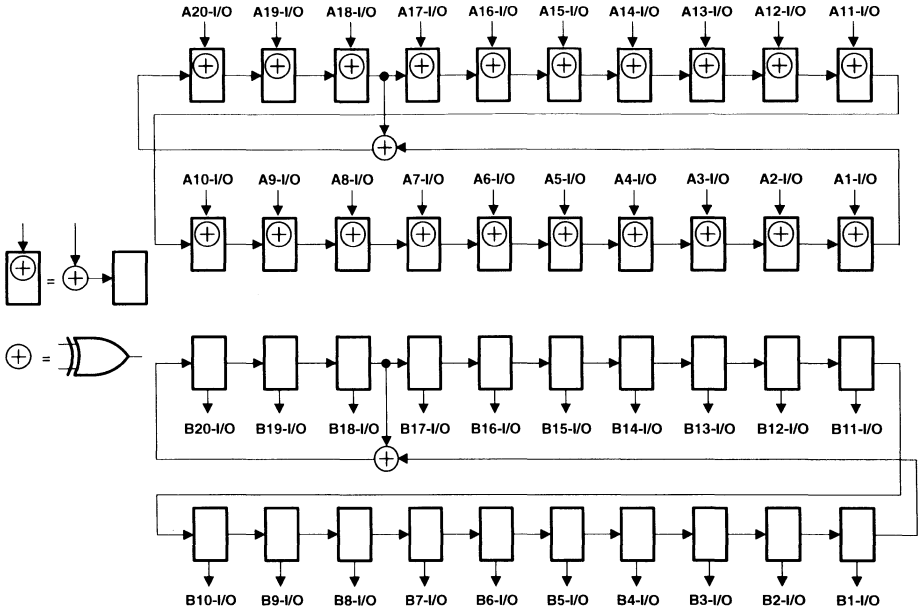


Figure 9. 20-Bit PSA/PRPG Configuration ($\overline{OEAB}$ = 0, $\overline{OEBA}$ = 1)

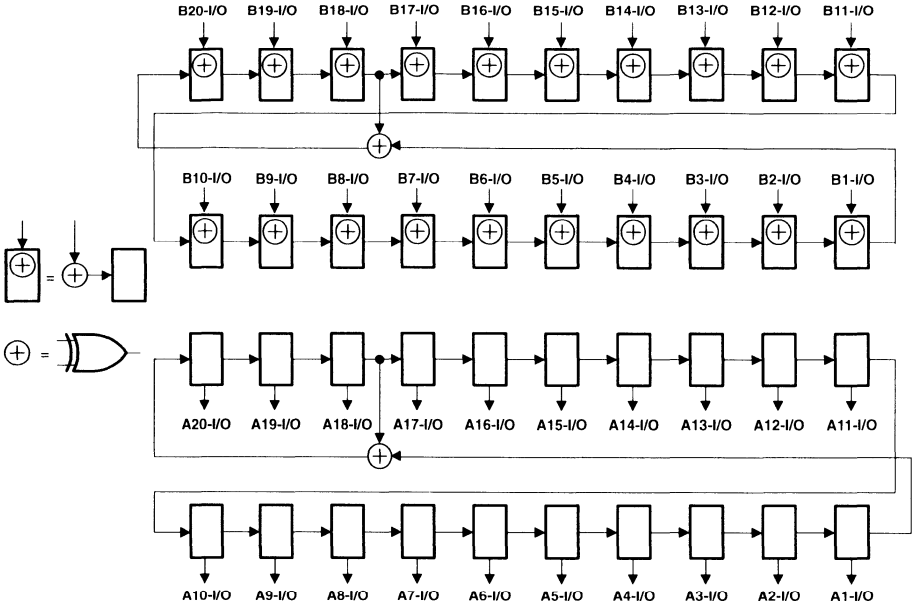


Figure 10. 20-Bit PSA/PRPG Configuration ($\overline{OEAB}$ = 1, $\overline{OEBA}$ = 0)

simultaneous PSA and binary count up (PSA/COUNT)

Data appearing at the selected device input-mode I/O pins is compressed into a 20-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, a 20-bit binary count-up pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 11 and 12 illustrate the 20-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

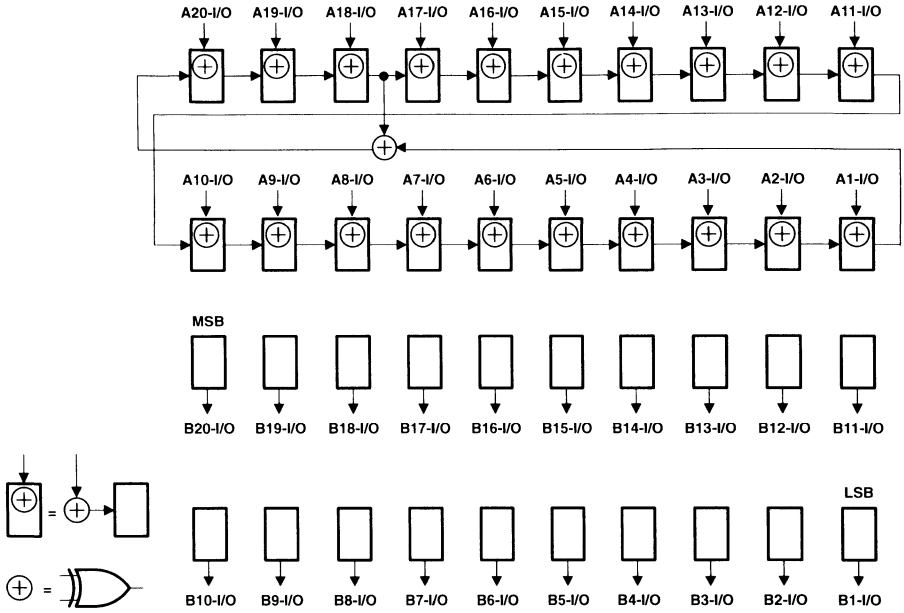


Figure 11. 20-Bit PSA/COUNT Configuration ($\overline{OEAB}$ = 0, $\overline{OEBA}$ = 1)

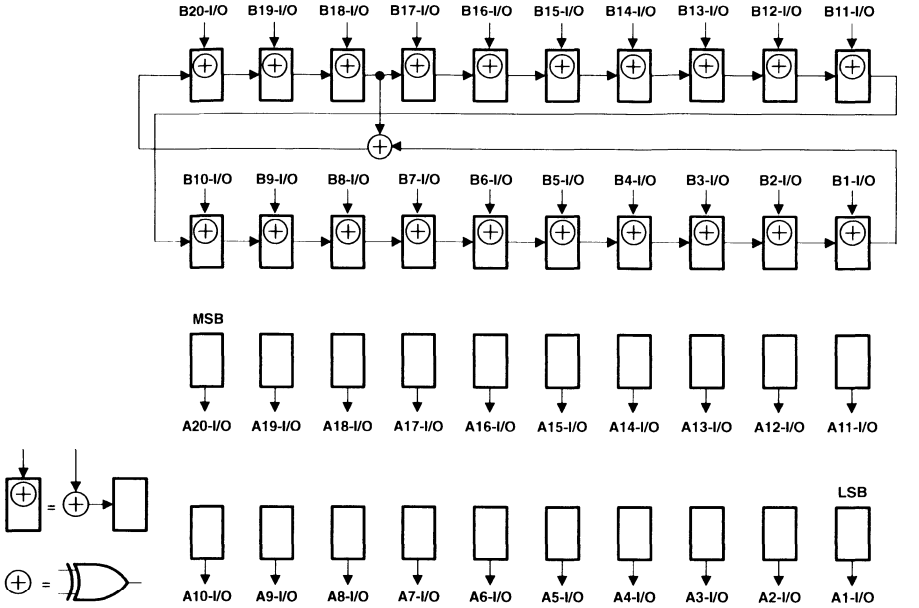


Figure 12. 20-Bit PSA/COUNT Configuration ($\overline{OEAB}$ = 1, $\overline{OEBA}$ = 0)

timing description

All test operations of the 'LVTH18514 and 'LVTH182514 are synchronous to the TCK signal. Data on the TDI, TMS, and normal-function inputs is captured on the rising edge of TCK. Data appears on the TDO and normal-function output pins on the falling edge of TCK. The TAP controller is advanced through its states (as shown in Figure 1) by changing the value of TMS on the falling edge of TCK and then applying a rising edge to TCK.

A simple timing example is shown in Figure 13. In this example, the TAP controller begins in the Test-Logic-Reset state and is advanced through its states, as necessary, to perform one instruction-register scan and one data-register scan. While in the Shift-IR and Shift-DR states, TDI is used to input serial data, and TDO is used to output serial data. The TAP controller is then returned to the Test-Logic-Reset state. Table 5 describes the operation of the test circuitry during each TCK cycle.

Table 5. Explanation of Timing Example

TCK CYCLE(S)	TAP STATE AFTER TCK	DESCRIPTION
1	Test-Logic-Reset	TMS is changed to a logic 0 value on the falling edge of TCK to begin advancing the TAP controller toward the desired state.
2	Run-Test/Idle	
3	Select-DR-Scan	
4	Select-IR-Scan	
5	Capture-IR	The IR captures the 8-bit binary value 10000001 on the rising edge of TCK as the TAP controller exits the Capture-IR state.
6	Shift-IR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
7–13	Shift-IR	One bit is shifted into the IR on each TCK rising edge. With TDI held at a logic 1 value, the 8-bit binary value 11111111 is serially scanned into the IR. At the same time, the 8-bit binary value 10000001 is serially scanned out of the IR via TDO. In TCK cycle 13, TMS is changed to a logic 1 value to end the instruction register scan on the next TCK cycle. The last bit of the instruction is shifted as the TAP controller advances from Shift-IR to Exit1-IR.
14	Exit1-IR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
15	Update-IR	The IR is updated with the new instruction (BYPASS) on the falling edge of TCK.
16	Select-DR-Scan	
17	Capture-DR	The bypass register captures a logic 0 value on the rising edge of TCK as the TAP controller exits the Capture-DR state.
18	Shift-DR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
19–20	Shift-DR	The binary value 101 is shifted in via TDI, while the binary value 010 is shifted out via TDO.
21	Exit1-DR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
22	Update-DR	In general, the selected data register is updated with the new data on the falling edge of TCK.
23	Select-DR-Scan	
24	Select-IR-Scan	
25	Test-Logic-Reset	Test operation completed.

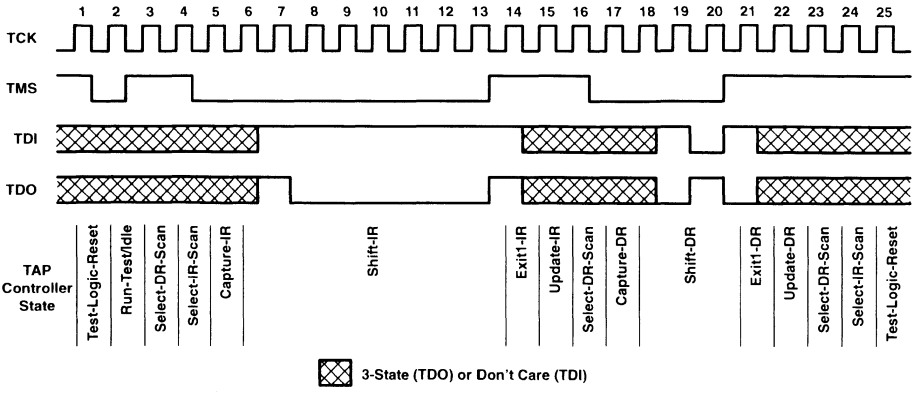


Figure 13. Timing Example

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 4.6 V
Input voltage range, V_I (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1)	–0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH18514	96 mA
SN54LVTH182514 (A port or TDO)	96 mA
SN54LVTH182514 (B port)	30 mA
SN74LVTH18514	128 mA
SN74LVTH182514 (A port or TDO)	128 mA
SN74LVTH182514 (B port)	30 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH18514	48 mA
SN54LVTH182514 (A port or TDO)	48 mA
SN54LVTH182514 (B port)	30 mA
SN74LVTH18514	64 mA
SN74LVTH182514 (A port or TDO)	64 mA
SN74LVTH182514 (B port)	30 mA
Input clamp current, I_{IK} ($V_I < 0$)	–50 mA
Output clamp current, I_{OK} ($V_O < 0$)	–50 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package	73°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings can be exceeded if the input and output clamp-current ratings are observed.
2. This current only flows when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVTH18514		SN74LVTH18514		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			24		32	mA
I_{OL}†	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTH18514			SN74LVTH18514			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = –3 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = –8 mA		2.4			2.4			
		I_{OH} = –24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	CLK, $\overline{CLKEN}$, LE, TCK			±1			±1	µA
	V_{CC} = 0 or 3.6 V,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	$\overline{OE}$, TDI, TMS			5			5	
		V_I = V_{CC}				1			1	
		V_I = 0		–25		–100	–25		–100	
		V_I = 5.5 V	A or B ports‡			20			20	
		V_I = V_{CC}				1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$§	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75		500	75	150	500	µA
		V_I = 2 V		–75		–500	–75	–150	–500	
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V	TDO			1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V	TDO			–1			–1	µA
I_{OZPU}	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{OZPD}	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{CC}	V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND		Outputs high		0.6	2		0.6	2	mA
			Outputs low		19.5	27		19.5	27	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND					0.5			0.5	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				10			10		pF
C_o	V_O = 3 V or 0				8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

				SN54LVTH18514				SN74LVTH18514				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA		0	100	0	80	0	100	0	80	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low		4.4		5.6		4.4		5.6		ns
		LEAB or LEBA high		3		3		3		3		
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑		2.4		2.8		2.4		2.8		ns
		A before LEAB↓ or B before LEBA↓	CLK high	1.5		0.7		1.5		0.7		
			CLK low	1.6		1.6		1.6		1.6		
		$\overline{CLKEN}$ before CLK↑		2.8		3.4		2.8		3.4		
t_h	Hold time	A after CLKAB↑		1		0.8		1		0.8		ns
		B after CLKBA↑		1.4		1.1		1.4		1.1		
		A after LEAB↓ or B after LEBA↓		3.1		3.5		3.1		3.5		
		$\overline{CLKEN}$ after CLK↑		0.7		0.2		0.7		0.2		

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

			SN54LVTH18514				SN74LVTH18514				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, $\overline{CLKEN}$, LE, or $\overline{OE}$ before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, $\overline{CLKEN}$, LE, or $\overline{OE}$ after TCK↑	1.7		1		1.7		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18514				SN74LVTH18514				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		100		80		100		80		MHz
t_{PLH}	A or B	B or A	1.5	5.4		5.8	1.5	5.1		5.6	ns
t_{PHL}			1.5	5.4		5.8	1.5	5.1		5.6	
t_{PLH}	CLKAB	B	1.5	6.9		7.8	1.5	5.8		6.8	ns
t_{PHL}			1.5	6.9		7.8	1.5	5.8		6.8	
t_{PLH}	CLKBA	A	1.5	6.9		7.8	1.5	6.4		7.4	ns
t_{PHL}			1.5	6.9		7.8	1.5	6.4		7.4	
t_{PLH}	LEAB or LEBA	B or A	2	8.7		9.5	2	8.1		8.8	ns
t_{PHL}			2	7.1		7.4	2	6.7		7.1	
t_{PZH}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2	9.5		10.5	2	9.1		10	ns
t_{PZL}			2	10		10.8	2	9.6		10.4	
t_{PHZ}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.5	12		12.7	2.5	10.4		11.2	ns
t_{PLZ}			2.5	9.6		9.9	2.5	9.1		9.5	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18514				SN74LVTH1854				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

recommended operating conditions (see Note 4)

			SN54LVTH182514		SN74LVTH182514		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	A port, TDO		–24		–32	mA
		B port		–12		–12	
I_{OL}	Low-level output current	A port, TDO		24		32	mA
		B port		12		12	
I_{OL}†	Low-level output current	A port, TDO		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTH182514			SN74LVTH182514			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = 2.7 V to 3.6 V,	I_{OH} = −100 µA	A, B, TDO	V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = −3 mA	A port, TDO	2.4			2.4			
	V_{CC} = 3 V	I_{OH} = −8 mA		2.4			2.4			
		I_{OH} = −24 mA		2						
		I_{OH} = −32 mA					2			
		I_{OH} = −12 mA	B port	2			2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA	A, B, TDO			0.2			0.2	V
		I_{OL} = 24 mA	A port, TDO			0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
		I_{OL} = 12 mA	B port			0.8			0.8	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	CLK, $\overline{CLKEN}$, LE, TCK			±1			±1	µA
	V_{CC} = 0 or 3.6 V,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	OE, TDI, TMS			5			5	
		V_I = V_{CC}				1			1	
		V_I = 0		−25		−100	−25		−100	
		V_I = 5.5 V	A or B ports‡			20			20	
		V_I = V_{CC}				1			1	
		V_I = 0				−5			−5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$§	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75		500	75	150	500	µA
		V_I = 2 V		−75		−500	−75	−150	−500	
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V	TDO			1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V	TDO			−1			−1	µA
I_{OZPU}	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{OZPD}	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{CC}	V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND		Outputs high		0.6	2		0.6	2	mA
			Outputs low		19.5	27		19.5	27	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND					0.5			0.5	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				10			10		pF
C_o	V_O = 3 V or 0				8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

				SN54LVTH182514				SN74LVTH182514				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA		0	100	0	80	0	100	0	80	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low		4.4		5.6		4.4		5.6		ns
		LEAB or LEBA high		3		3		3		3		
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑		2.8		3		2.8		3		ns
		A before LEAB↓ or B before LEBA↓	CLK high	1.5		0.7		1.5		0.7		
			CLK low	1.6		1.6		1.6		1.6		
		$\overline{CLKEN}$ before CLK↑		2.8		3.4		2.8		3.4		
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑		1.4		1.1		1.4		1.1		ns
		A after LEAB↓ or B after LEBA↓		3.1		3.5		3.1		3.5		
		$\overline{CLKEN}$ after CLK↑		0.7		0.2		0.7		0.2		

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

			SN54LVTH182514				SN74LVTH182514				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, $\overline{CLKEN}$, LE, or $\overline{OE}$ before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, $\overline{CLKEN}$, LE, or $\overline{OE}$ after TCK↑	1.7		1		1.7		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

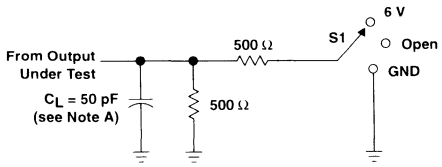
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 14)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182514				SN74LVTH182514				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		100		80		100		80		MHz
t_{PLH}	A	B	1.5	6.4		6.9	1.5	5.9		6.6	ns
t_{PHL}			1.5	6.4		6.9	1.5	5.9		6.6	
t_{PLH}	B	A	1.5	5.4		5.8	1.5	5.1		5.6	ns
t_{PHL}			1.5	5.4		5.8	1.5	5.1		5.6	
t_{PLH}	CLKAB	B	1.5	6.9		7.8	1.5	6.7		7.7	ns
t_{PHL}			1.5	6.9		7.8	1.5	6.7		7.7	
t_{PLH}	CLKBA	A	1.5	6.9		7.8	1.5	6.4		7.4	ns
t_{PHL}			1.5	6.9		7.8	1.5	6.4		7.4	
t_{PLH}	LEAB	B	2	8.7		9.5	2	8.2		9.2	ns
t_{PHL}			2	7.1		7.4	2	6.7		7.1	
t_{PLH}	LEBA	A	2	8.7		9.5	2	8.1		8.8	ns
t_{PHL}			2	7.1		7.4	2	6.7		7.1	
t_{PZH}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2	9.9		11.1	2	9.5		10.6	ns
t_{PZL}			2	10.2		11	2	9.7		10.5	
t_{PHZ}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.5	12		12.7	2.5	11.1		11.8	ns
t_{PLZ}			2.5	11		11.2	2.5	9.8		10	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 14)

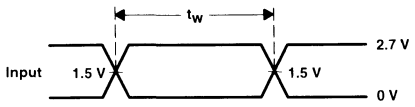
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182514				SN74LVTH182514				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

PARAMETER MEASUREMENT INFORMATION

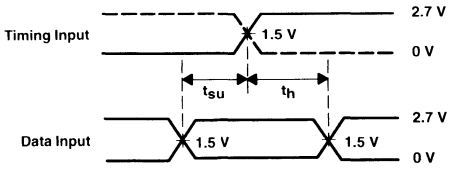


LOAD CIRCUIT

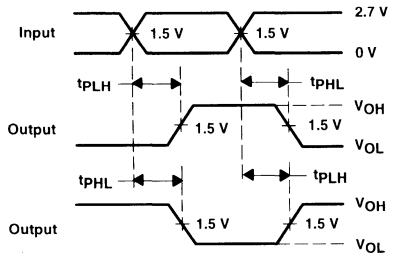
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



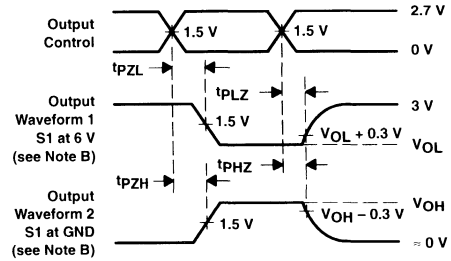
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 14. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *SCOPE*™ Family of Testability Products**
- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art 3.3-V ABT Design Supports Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Include D-Type Flip-Flops and Control Circuitry to Provide Multiplexed Transmission of Stored and Real-Time Data**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **B-Port Outputs of 'LVTH182646A Devices Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required**
- **Compatible With IEEE Std 1149.1-1990 (JTAG) Test Access Port and Boundary-Scan Architecture**
- ***SCOPE* Instruction Set**
  - **IEEE Std 1149.1-1990 Required Instructions and Optional CLAMP and HIGHZ**
  - **Parallel-Signature Analysis at Inputs**
  - **Pseudo-Random Pattern Generation From Outputs**
  - **Sample Inputs/Toggle Outputs**
  - **Binary Count From Outputs**
  - **Device Identification**
  - **Even-Parity Opcodes**
- **Packaged in 64-Pin Plastic Thin Quad Flat (PM) Packages Using 0.5-mm Center-to-Center Spacings and 68-Pin Ceramic Quad Flat (HV) Packages Using 25-mil Center-to-Center Spacings**

description

The 'LVTH18646A and 'LVTH182646A scan test devices with 18-bit bus transceivers and registers are members of the Texas Instruments (TI) SCOPE testability integrated-circuit family. This family of devices supports IEEE Std 1149.1-1990 boundary scan to facilitate testing of complex circuit board assemblies. Scan access to the test circuitry is accomplished via the 4-wire test access port (TAP) interface.

Additionally, these devices are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

In the normal mode, these devices are 18-bit bus transceivers and registers that allow for multiplexed transmission of data directly from the input bus or from the internal registers. They can be used either as two 9-bit transceivers or one 18-bit transceiver. The test circuitry can be activated by the TAP to take snapshot samples of the data appearing at the device pins or to perform a self test on the boundary-test cells. Activating the TAP in the normal mode does not affect the functional operation of the SCOPE bus transceivers and registers.

Transceiver function is controlled by output-enable ($\overline{OE}$) and direction (DIR) inputs. When $\overline{OE}$ is low, the transceiver is active and operates in the A-to-B direction when DIR is high or in the B-to-A direction when DIR is low. When $\overline{OE}$ is high, both the A and B outputs are in the high-impedance state, effectively isolating both buses.

Data flow is controlled by clock (CLKAB and CLKBA) and select (SAB and SBA) inputs. Data on the A bus is clocked into the associated registers on the low-to-high transition of CLKAB. When SAB is low, real-time A data is selected for presentation to the B bus (transparent mode). When SAB is high, stored A data is selected for presentation to the B bus (registered mode). The function of the CLKBA and SBA inputs mirrors that of CLKAB and SAB, respectively. Figure 1 shows the four fundamental bus-management functions that can be performed with the 'LVTH18646A and 'LVTH182646A.

description (continued)

In the test mode, the normal operation of the SCOPE bus transceivers and registers is inhibited, and the test circuitry is enabled to observe and control the I/O boundary of the device. When enabled, the test circuitry performs boundary-scan test operations according to the protocol described in IEEE Std 1149.1-1990.

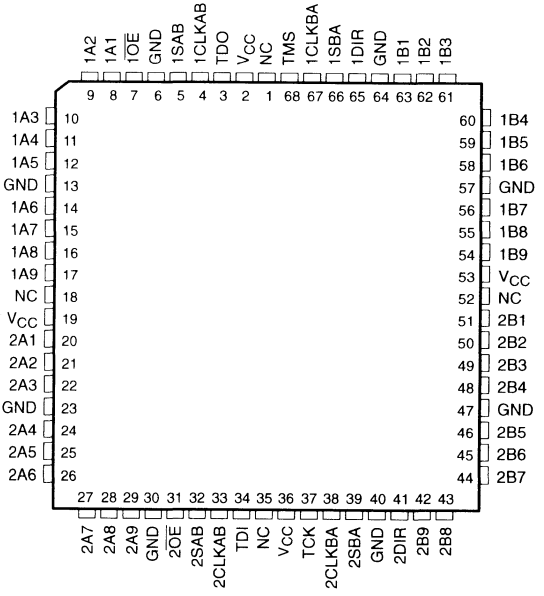
Four dedicated test pins are used to observe and control the operation of the test circuitry: test data input (TDI), test data output (TDO), test mode select (TMS), and test clock (TCK). Additionally, the test circuitry performs other testing functions such as parallel-signature analysis (PSA) on data inputs and pseudo-random pattern generation (PRPG) from data outputs. All testing and scan operations are synchronized to the TAP interface.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The B-port outputs of 'LVTH182646A, which are designed to source or sink up to 12 mA, include equivalent 25-Ω series resistors to reduce overshoot and undershoot.

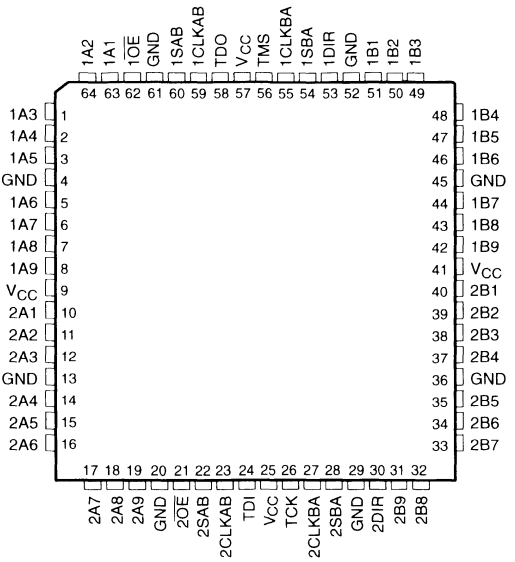
The SN54LVT18646 and SN54LVTH182646A are characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH18646A and SN74LVTH182646A are characterized for operation from –40°C to 85°C.

SN54LVTH18646A, SN54LVTH182646A . . . HV PACKAGE
(TOP VIEW)



NC – No internal connection

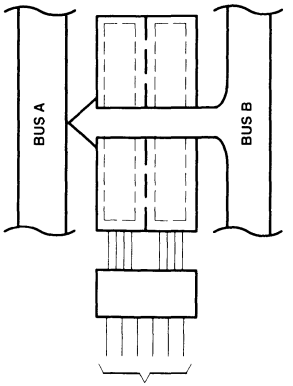
SN74LVTH18646A, SN74LVTH182646A . . . PM PACKAGE
(TOP VIEW)



FUNCTION TABLE
(normal mode, each 9-bit section)

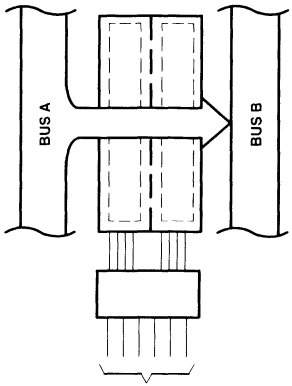
INPUTS						DATA I/O		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1–A9	B1–B9	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	L	L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	X	X	H	Output	Input disabled	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	X	X	H	X	Input disabled	Output	Stored A data to B bus

† The data-output functions can be enabled or disabled by various signals at $\overline{OE}$ and DIR. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.



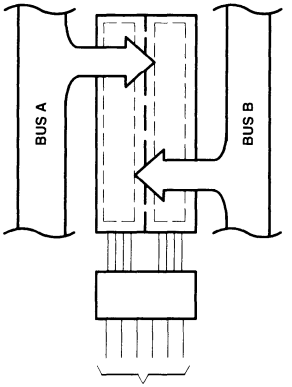
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER BUS B TO BUS A



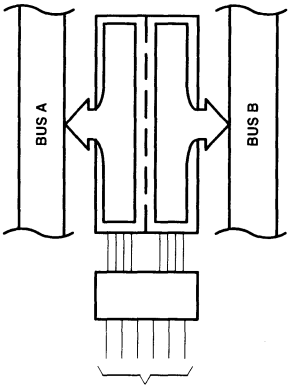
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER BUS A TO BUS B



$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM A, B, OR A AND B

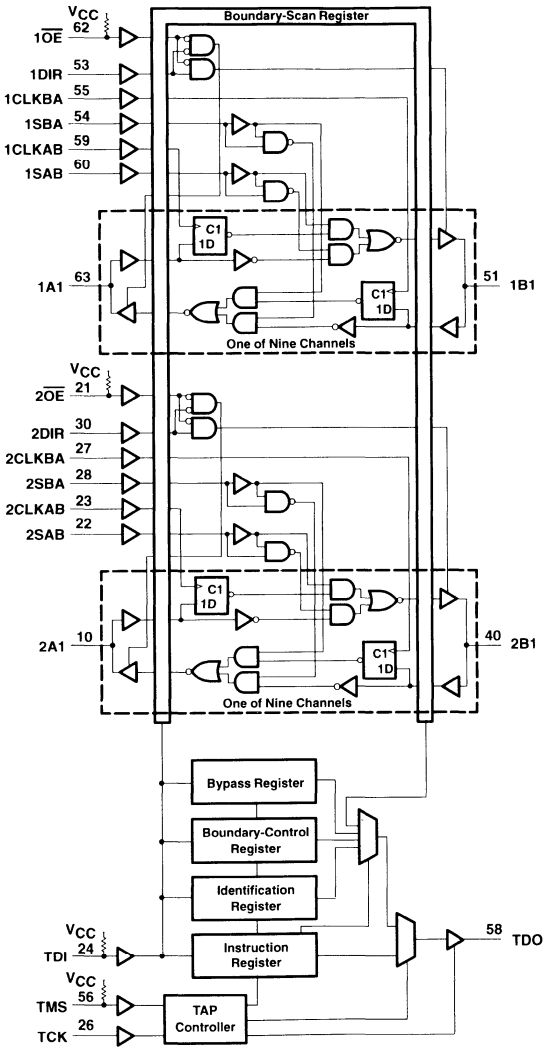


$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	H
L	H	X	X	H	X

TRANSFER STORED DATA TO A AND/OR B

Figure 1. Bus-Management Functions

functional block diagram



Pin numbers shown are for the PM package.

Terminal Functions

TERMINAL NAME	DESCRIPTION
1A1–1A9, 2A1–2A9	Normal-function A-bus I/O ports. See function table for normal-mode logic.
1B1–1B9, 2B1–2B9	Normal-function B-bus I/O ports. See function table for normal-mode logic.
1CLKAB, 1CLKBA, 2CLKAB, 2CLKBA	Normal-function clock inputs. See function table for normal-mode logic.
1DIR, 2DIR	Normal-function direction controls. See function table for normal-mode logic.
GND	Ground
$1\overline{OE}$, $2\overline{OE}$	Normal-function output enables. See function table for normal-mode logic. An internal pullup at each terminal forces the terminal to a high level if left unconnected.
1SAB, 1SBA, 2SAB, 2SBA	Normal-function select controls. See function table for normal-mode logic.
TCK	Test clock. One of four terminals required by IEEE Std 1149.1-1990. Test operations of the device are synchronous to TCK. Data is captured on the rising edge of TCK and outputs change on the falling edge of TCK.
TDI	Test data input. One of four terminals required by IEEE Std 1149.1-1990. TDI is the serial input for shifting data through the instruction register or selected data register. An internal pullup forces TDI to a high level if left unconnected.
TDO	Test data output. One of four terminals required by IEEE Std 1149.1-1990. TDO is the serial output for shifting data through the instruction register or selected data register.
TMS	Test mode select. One of four terminals required by IEEE Std 1149.1-1990. TMS directs the device through its TAP controller states. An internal pullup forces TMS to a high level if left unconnected.
V_{CC}	Supply voltage

test architecture

Serial-test information is conveyed by means of a 4-wire test bus or TAP that conforms to IEEE Std 1149.1-1990. Test instructions, test data, and test control signals all are passed along this serial-test bus. The TAP controller monitors two signals from the test bus, TCK and TMS. The TAP controller extracts the synchronization (TCK) and state control (TMS) signals from the test bus and generates the appropriate on-chip control signals for the test structures in the device. Figure 2 shows the TAP-controller state diagram.

The TAP controller is fully synchronous to the TCK signal. Input data is captured on the rising edge of TCK and output data changes on the falling edge of TCK. This scheme ensures data to be captured is valid for fully one-half of the TCK cycle.

The functional block diagram illustrates the IEEE Std 1149.1-1990 4-wire test bus and boundary-scan architecture and the relationship among the test bus, the TAP controller, and the test registers. As illustrated, the device contains an 8-bit instruction register and four test-data registers: a 52-bit boundary-scan register, a 3-bit boundary-control register, a 1-bit bypass register, and a 32-bit device-identification register.

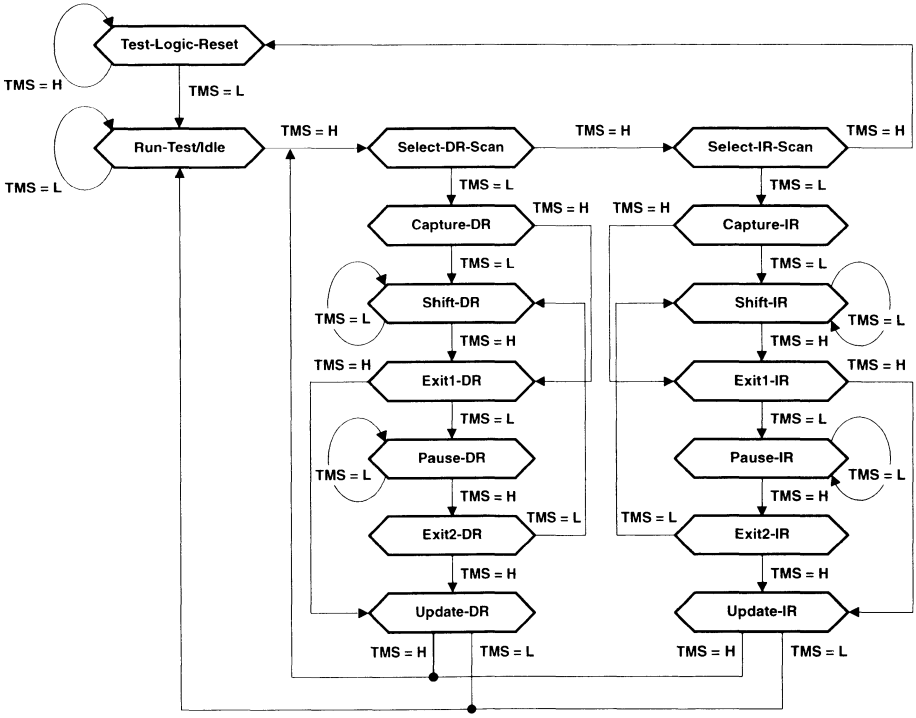


Figure 2. TAP-Controller State Diagram

state diagram description

The TAP controller is a synchronous finite state machine that provides test control signals throughout the device. The state diagram shown in Figure 2 is in accordance with IEEE Std 1149.1-1990. The TAP controller proceeds through its states based on the level of TMS at the rising edge of TCK.

As shown, the TAP controller consists of 16 states. There are six stable states (indicated by a looping arrow in the state diagram) and ten unstable states. A stable state is defined as a state the TAP controller can retain for consecutive TCK cycles. Any state that does not meet this criterion is an unstable state.

There are two main paths through the state diagram: one to access and control the selected data register and one to access and control the instruction register. Only one register can be accessed at a time.

Test-Logic-Reset

The device powers up in the Test-Logic-Reset state. In the stable Test-Logic-Reset state, the test logic is reset and is disabled so that the normal logic function of the device is performed. The instruction register is reset to an opcode that selects the optional IDCODE instruction, if supported, or the BYPASS instruction. Certain data registers can also be reset to their power-up values.

The state machine is constructed such that the TAP controller returns to the Test-Logic-Reset state in no more than five TCK cycles if TMS is left high. The TMS pin has an internal pullup resistor that forces it high if left unconnected or if a board defect causes it to be open circuited.

For the 'LVTH18646A and 'LVTH182646A, the instruction register is reset to the binary value 10000001, which selects the IDCODE instruction. Bits 51–48 in the boundary-scan register are reset to logic 0, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., if test mode were invoked, the outputs would be at high-impedance state). Reset values of other bits in the boundary-scan register should be considered indeterminate. The boundary-control register is reset to the binary value 010, which selects the PSA test operation.

Run-Test/Idle

The TAP controller must pass through the Run-Test/Idle state (from Test-Logic-Reset) before executing any test operations. The Run-Test/Idle state also can be entered following data-register or instruction-register scans. Run-Test/Idle is a stable state in which the test logic can be actively running a test or can be idle. The test operations selected by the boundary-control register are performed while the TAP controller is in the Run-Test/Idle state.

Select-DR-Scan, Select-IR-Scan

No specific function is performed in the Select-DR-Scan and Select-IR-Scan states, and the TAP controller exits either of these states on the next TCK cycle. These states allow the selection of either data-register scan or instruction-register scan.

Capture-DR

When a data-register scan is selected, the TAP controller must pass through the Capture-DR state. In the Capture-DR state, the selected data register can capture a data value as specified by the current instruction. Such capture operations occur on the rising edge of TCK, upon which the TAP controller exits the Capture-DR state.

Shift-DR

Upon entry to the Shift-DR state, the data register is placed in the scan path between TDI and TDO, and on the first falling edge of TCK, TDO goes from the high-impedance state to an active state. TDO enables to the logic level present in the least-significant bit of the selected data register.

While in the stable Shift-DR state, data is serially shifted through the selected data register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-DR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-DR to Shift-DR or from Exit2-DR to Shift-DR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-DR state.

Exit1-DR, Exit2-DR

The Exit1-DR and Exit2-DR states are temporary states that end a data-register scan. It is possible to return to the Shift-DR state from either Exit1-DR or Exit2-DR without recapturing the data register. On the first falling edge of TCK after entry to Exit1-DR, TDO goes from the active state to the high-impedance state.

Pause-DR

No specific function is performed in the stable Pause-DR state, in which the TAP controller can remain indefinitely. The Pause-DR state suspends and resumes data-register scan operations without loss of data.

Update-DR

If the current instruction calls for the selected data register to be updated with current data, such update occurs on the falling edge of TCK, following entry to the Update-DR state.

Capture-IR

When an instruction-register scan is selected, the TAP controller must pass through the Capture-IR state. In the Capture-IR state, the instruction register captures its current status value. This capture operation occurs on the rising edge of TCK, upon which the TAP controller exits the Capture-IR state. For the 'LVTH18646A and 'LVTH182646A, the status value loaded in the Capture-IR state is the fixed binary value 10000001.

Shift-IR

Upon entry to the Shift-IR state, the instruction register is placed in the scan path between TDI and TDO, and on the first falling edge of TCK, TDO goes from the high-impedance state to the active state. TDO enables to the logic level present in the least-significant bit of the instruction register.

While in the stable Shift-IR state, instruction data is serially shifted through the instruction-register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-IR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-IR to Shift-IR or from Exit2-IR to Shift-IR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-IR state.

Exit1-IR, Exit2-IR

The Exit1-IR and Exit2-IR states are temporary states that end an instruction-register scan. It is possible to return to the Shift-IR state from either Exit1-IR or Exit2-IR without recapturing the instruction register. On the first falling edge of TCK after entry to Exit1-IR, TDO goes from the active state to the high-impedance state.

Pause-IR

No specific function is performed in the stable Pause-IR state, in which the TAP controller can remain indefinitely. The Pause-IR state suspends and resumes instruction-register scan operations without loss of data.

Update-IR

The current instruction is updated and takes effect on the falling edge of TCK, following entry to the Update-IR state.

register overview

With the exception of the bypass and device-identification registers, any test register can be thought of as a serial-shift register with a shadow latch on each bit. The bypass and device-identification registers differ in that they contain only a shift register. During the appropriate capture state (Capture-IR for instruction register, Capture-DR for data registers), the shift register can be parallel loaded from a source specified by the current instruction. During the appropriate shift state (Shift-IR or Shift-DR), the contents of the shift register are shifted out from TDO while new contents are shifted in at TDI. During the appropriate update state (Update-IR or Update-DR), the shadow latches are updated from the shift register.

instruction register description

The instruction register (IR) is eight bits long and tells the device what instruction is to be executed. Information contained in the instruction includes the mode of operation (either normal mode, in which the device performs its normal logic function, or test mode, in which the normal logic function is inhibited or altered), the test operation to be performed, which of the four data registers is to be selected for inclusion in the scan path during data-register scans, and the source of data to be captured into the selected data register during Capture-DR.

Table 3 lists the instructions supported by the 'LVTH18646A and 'LVTH182646A. The even-parity feature specified for SCOPE devices is supported in this device. Bit 7 of the instruction opcode is the parity bit. Any instructions that are defined for SCOPE devices but are not supported by this device default to BYPASS.

During Capture-IR, the IR captures the binary value 10000001. As an instruction is shifted in, this value is shifted out via TDO and can be inspected as verification that the IR is in the scan path. During Update-IR, the value that has been shifted into the IR is loaded into shadow latches. At this time, the current instruction is updated and any specified mode change takes effect. At power up or in the Test-Logic-Reset state, the IR is reset to the binary value 10000001, which selects the IDCODE instruction. The IR order of scan is shown in Figure 3.

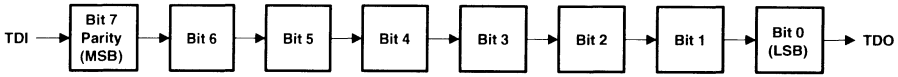


Figure 3. Instruction Register Order of Scan

data register description

boundary-scan register

The boundary-scan register (BSR) is 52 bits long. It contains one boundary-scan cell (BSC) for each normal-function input pin, one BSC for each normal-function I/O pin (one single cell for both input data and output data), and one BSC for each of the internally decoded output-enable signals (1OEA, 2OEA, 1OEB, 2OEB). The BSR is used 1) to store test data that is to be applied externally to the device output pins, and/or 2) to capture data that appears internally at the outputs of the normal on-chip logic and/or externally at the device input pins.

The source of data to be captured into the BSR during Capture-DR is determined by the current instruction. The contents of the BSR can change during Run-Test/Idle, as determined by the current instruction. At power up or in Test-Logic-Reset, BSCs 51–48 are reset to logic 0, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., if test mode were invoked the outputs would be at high-impedance state). Reset values of other BSCs should be considered indeterminate.

When external data is to be captured, the BSCs for signals 1OEA, 2OEA, 1OEB, and 2OEB capture logic values determined by the following positive-logic equations:

$$1OEA = \overline{1\overline{OE}} \bullet \overline{1DIR},\ 2OEA = \overline{2\overline{OE}} \bullet \overline{2DIR},\ 1OEB = \overline{1\overline{OE}} \bullet DIR,\ 2OEB = \overline{2\overline{OE}} \bullet DIR$$

When data is to be applied externally, these BSCs control the drive state (active or high impedance) of their respective outputs.

The BSR order of scan is from TDI through bits 51–0 to TDO. Table 1 shows the BSR bits and their associated device pin signals.

Table 1. Boundary-Scan Register Configuration

BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL
51	2OEB	35	2A9-I/O	17	2B9-I/O
50	1OEB	34	2A8-I/O	16	2B8-I/O
49	2OEA	33	2A7-I/O	15	2B7-I/O
48	1OEA	32	2A6-I/O	14	2B6-I/O
47	2DIR	31	2A5-I/O	13	2B5-I/O
46	1DIR	30	2A4-I/O	12	2B4-I/O
45	$2\overline{OE}$	29	2A3-I/O	11	2B3-I/O
44	$1\overline{OE}$	28	2A2-I/O	10	2B2-I/O
43	2CLKAB	27	2A1-I/O	9	2B1-I/O
42	1CLKAB	26	1A9-I/O	8	1B9-I/O
41	2CLKBA	25	1A8-I/O	7	1B8-I/O
40	1CLKBA	24	1A7-I/O	6	1B7-I/O
39	2SAB	23	1A6-I/O	5	1B6-I/O
38	1SAB	22	1A5-I/O	4	1B5-I/O
37	2SBA	21	1A4-I/O	3	1B4-I/O
36	1SBA	20	1A3-I/O	2	1B3-I/O
—	—	19	1A2-I/O	1	1B2-I/O
—	—	18	1A1-I/O	0	1B1-I/O

boundary-control register

The boundary-control register (BCR) is three bits long. The BCR is used in the context of the RUNT instruction to implement additional test operations not included in the basic SCOPE instruction set. Such operations include PRPG, PSA, and binary count up (COUNT). Table 4 shows the test operations that are decoded by the BCR.

During Capture-DR, the contents of the BCR are not changed. At power up or in Test-Logic-Reset, the BCR is reset to the binary value 010, which selects the PSA test operation. The boundary-control register order of scan is shown in Figure 4.

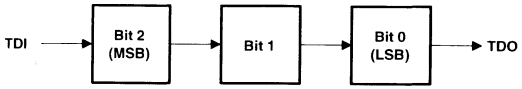


Figure 4. Boundary-Control Register Order of Scan

bypass register

The bypass register is a 1-bit scan path that can be selected to shorten the length of the system scan path, reducing the number of bits per test pattern that must be applied to complete a test operation. During Capture-DR, the bypass register captures a logic 0. The bypass register order of scan is shown in Figure 5.

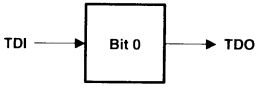


Figure 5. Bypass Register Order of Scan

device-identification register

The device-identification register (IDR) is 32 bits long. It can be selected and read to identify the manufacturer, part number, and version of this device.

For the 'LVTH18646A, the binary value 00100000000000001111000000101111 (2001E02F, hex) is captured (during Capture-DR state) in the device-identification register to identify this device as TI SN54/74LVTH18646A.

For the 'LVTH182646A, the binary value 00100000000000010001100000101111 (2002302F, hex) is captured (during Capture-DR state) in the device-identification register to identify this device as TI SN54/74LVTH182646A.

The device-identification register order of scan is from TDI through bits 31–0 to TDO. Table 2 shows the device identification register bits and their significance.

Table 2. Device-Identification Register Configuration

IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE
31	VERSION3	27	PARTNUMBER15	11	MANUFACTURER10†
30	VERSION2	26	PARTNUMBER14	10	MANUFACTURER09†
29	VERSION1	25	PARTNUMBER13	9	MANUFACTURER08†
28	VERSION0	24	PARTNUMBER12	8	MANUFACTURER07†
—	—	23	PARTNUMBER11	7	MANUFACTURER06†
—	—	22	PARTNUMBER10	6	MANUFACTURER05†
—	—	21	PARTNUMBER09	5	MANUFACTURER04†
—	—	20	PARTNUMBER08	4	MANUFACTURER03†
—	—	19	PARTNUMBER07	3	MANUFACTURER02†
—	—	18	PARTNUMBER06	2	MANUFACTURER01†
—	—	17	PARTNUMBER05	1	MANUFACTURER00†
—	—	16	PARTNUMBER04	0	LOGIC1†
—	—	15	PARTNUMBER03	—	—
—	—	14	PARTNUMBER02	—	—
—	—	13	PARTNUMBER01	—	—
—	—	12	PARTNUMBER00	—	—

† Note that for TI products, bits 11–0 of the device-identification register always contain the binary value 000000101111 (02F, hex).

instruction-register opcode description

The instruction-register opcodes are shown in Table 3. The following descriptions detail the operation of each instruction.

Table 3. Instruction-Register Opcodes

BINARY CODE† BIT 7 → BIT 0 MSB → LSB	SCOPE OPCODE	DESCRIPTION	SELECTED DATA REGISTER	MODE
00000000	EXTEST	Boundary scan	Boundary scan	Test
10000001	IDCODE	Identification read	Device identification	Normal
10000010	SAMPLE/PRELOAD	Sample boundary	Boundary scan	Normal
00000011	BYPASS‡	Bypass scan	Bypass	Normal
10000100	BYPASS‡	Bypass scan	Bypass	Normal
00000101	BYPASS‡	Bypass scan	Bypass	Normal
00000110	HIGHZ	Control boundary to high impedance	Bypass	Modified test
10000111	CLAMP	Control boundary to 1/0	Bypass	Test
10001000	BYPASS‡	Bypass scan	Bypass	Normal
00001001	RUNT	Boundary run test	Bypass	Test
00001010	READBN	Boundary read	Boundary scan	Normal
10001011	READBT	Boundary read	Boundary scan	Test
00001100	CELLTST	Boundary self test	Boundary scan	Normal
10001101	TOPHIP	Boundary toggle outputs	Bypass	Test
10001110	SCANCN	Boundary-control register scan	Boundary control	Normal
00001111	SCANCT	Boundary-control register scan	Boundary control	Test
All others	BYPASS	Bypass scan	Bypass	Normal

† Bit 7 is used to maintain even parity in the 8-bit instruction.
‡ The BYPASS instruction is executed in lieu of a SCOPE instruction that is not supported in the 'LVTH18646 or 'LVTH182646.

boundary scan

This instruction conforms to the IEEE Std 1149.1-1990 EXTEST instruction. The BSR is selected in the scan path. Data appearing at the device input and I/O pins is captured in the associated BSCs. Data that has been scanned into the I/O BSCs for pins in the output mode is applied to the device I/O pins. Data present at the device pins is passed through the BSCs to the normal on-chip logic. For I/O pins, the operation of a pin as input or output is determined by the contents of the output-enable BSCs (bits 51–48 of the BSR). When a given output enable is active (logic 1), the associated I/O pins operate in the output mode. Otherwise, the I/O pins operate in the input mode. The device operates in the test mode.

identification read

This instruction conforms to the IEEE Std 1149.1-1990 IDCODE instruction. The device identification register is selected in the scan path. The device operates in the normal mode.

sample boundary

This instruction conforms to the IEEE Std 1149.1-1990 SAMPLE/PRELOAD instruction. The BSR is selected in the scan path. Data appearing at the device input pins and I/O pins in the input mode is captured in the associated BSCs, while data appearing at the outputs of the normal on-chip logic is captured in the BSCs associated with I/O pins in the output mode. The device operates in the normal mode.

bypass scan

This instruction conforms to the IEEE Std 1149.1-1990 BYPASS instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the normal mode.

control boundary to high impedance

This instruction conforms to the IEEE Std 1149.1a-1993 HIGHZ instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in a modified test mode in which all device I/O pins are placed in the high-impedance state, the device input pins remain operational, and the normal on-chip logic function is performed.

control boundary to 1/0

This instruction conforms to the IEEE Std 1149.1a-1993 CLAMP instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the I/O BSCs for pins in the output mode is applied to the device I/O pins. The device operates in the test mode.

boundary-run test

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the test mode. The test operation specified in the BCR is executed during Run-Test/Idle. The five test operations decoded by the BCR are: sample inputs/toggle outputs (TOPSIP), PRPG, PSA, simultaneous PSA and PRPG (PSA/PRPG), and simultaneous PSA and binary count up (PSA/COUNT).

boundary read

The BSR is selected in the scan path. The value in the BSR remains unchanged during Capture-DR. This instruction is useful for inspecting data after a PSA operation.

boundary self test

The BSR is selected in the scan path. All BSCs capture the inverse of their current values during Capture-DR. In this way, the contents of the shadow latches can be read out to verify the integrity of both shift-register and shadow-latch elements of the BSR. The device operates in the normal mode.

boundary toggle outputs

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK in Run-Test/Idle and is then updated in the shadow latches and thereby applied to the associated device I/O pins on each falling edge of TCK in Run-Test/Idle. Data in the input-mode BSCs remains constant. Data appearing at the device input or I/O pins is not captured in the input-mode BSCs. The device operates in the test mode.

boundary-control-register scan

The BCR is selected in the scan path. The value in the BCR remains unchanged during Capture-DR. This operation must be performed before a boundary-run test operation to specify which test operation is to be executed.

boundary-control-register opcode description

The BCR opcodes are decoded from BCR bits 2–0 as shown in Table 4. The selected test operation is performed while the RUNT instruction is executed in the Run-Test/Idle state. The following descriptions detail the operation of each BCR instruction and illustrate the associated PSA and PRPG algorithms.

Table 4. Boundary-Control Register Opcodes

BINARY CODE BIT 2 → BIT 0 MSB → LSB	DESCRIPTION
X00	Sample inputs/toggle outputs (TOPSIP)
X01	Pseudo-random pattern generation/36-bit mode (PRPG)
X10	Parallel-signature analysis/36-bit mode (PSA)
011	Simultaneous PSA and PRPG/18-bit mode (PSA/PRPG)
111	Simultaneous PSA and binary count up/18-bit mode (PSA/COUNT)

While the control input BSCs (bits 51–36) are not included in the toggle, PSA, PRPG, or COUNT algorithms, the output-enable BSCs (bits 51–48 of the BSR) control the drive state (active or high impedance) of the selected device output pins. These BCR instructions are only valid when both bytes of the device are operating in one direction of data flow (that is, 1OEA ≠ 1OEB and 2OEA ≠ 2OEB) and in the same direction of data flow (that is, 1OEA = 2OEA and 1OEB = 2OEB). Otherwise, the bypass instruction is operated.

sample inputs/toggle outputs (TOPSIP)

Data appearing at the selected device input-mode I/O pins is captured in the shift-register elements of the associated BSCs on each rising edge of TCK. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK.

pseudo-random pattern generation (PRPG)

A pseudo-random pattern is generated in the shift-register elements of the selected BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device output-mode I/O pins on each falling edge of TCK. Figures 6 and 7 illustrate the 36-bit linear-feedback shift-register algorithms through which the patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

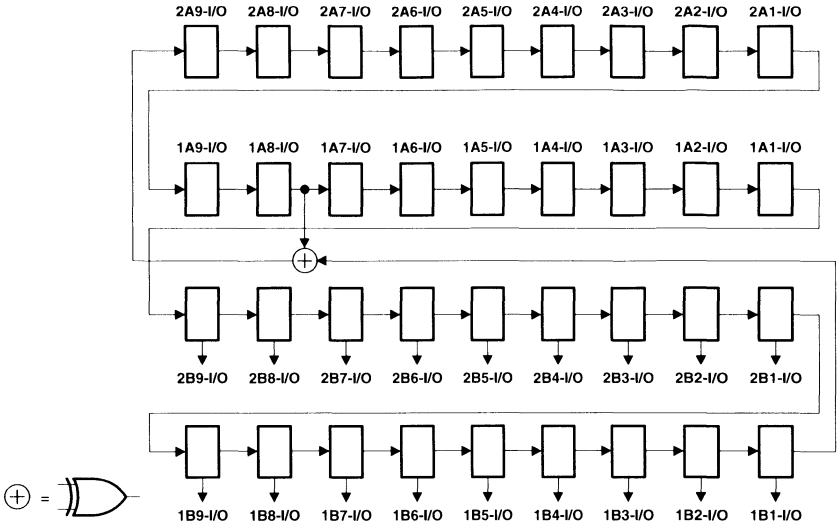


Figure 6. 36-Bit PRPG Configuration (1OEA = 2OEA = 0, 1OEB = 2OEB = 1)

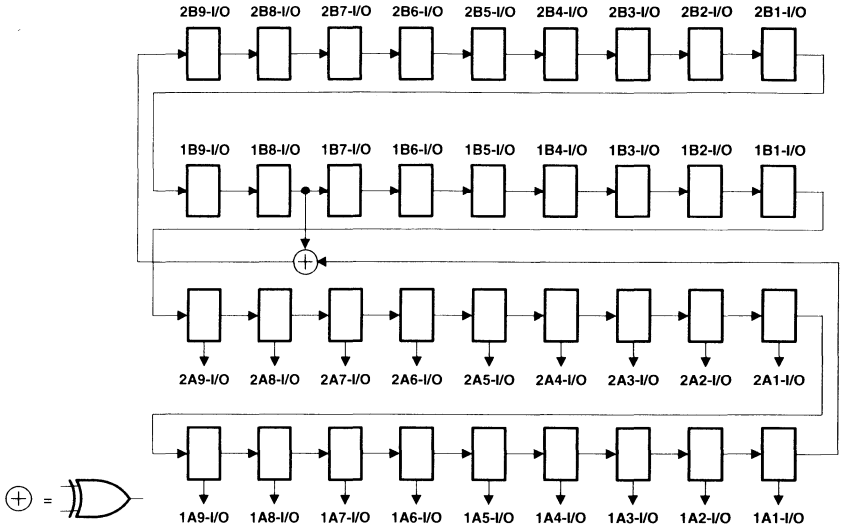


Figure 7. 36-Bit PRPG Configuration (1OEA = 2OEA = 1, 1OEB = 2OEB = 0)

parallel-signature analysis (PSA)

Data appearing at the selected device input-mode I/O pins is compressed into a 36-bit parallel signature in the shift-register elements of the selected BSCs on each rising edge of TCK. Data in the shadow latches of the selected output-mode BSCs remains constant and is applied to the associated device I/O pins. Figures 8 and 9 illustrate the 36-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

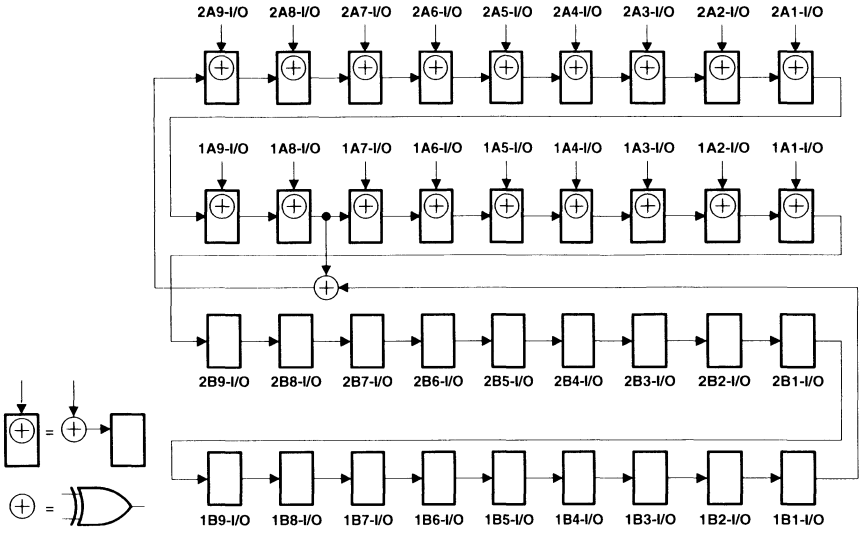


Figure 8. 36-Bit PSA Configuration (1OEA = 2OEA = 0, 1OEB = 2OEB = 1)

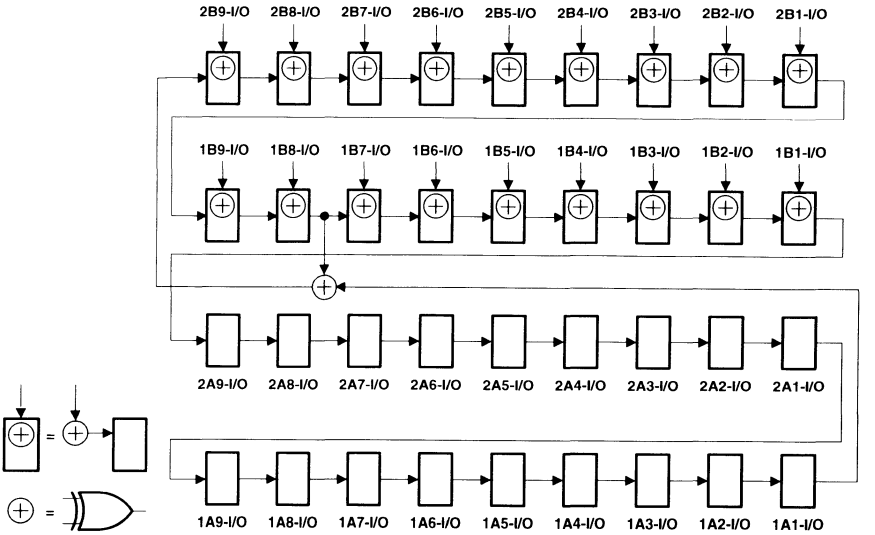


Figure 9. 36-Bit PSA Configuration (1OEA = 2OEA = 1, 1OEB = 2OEB = 0)

simultaneous PSA and PRPG (PSA/PRPG)

Data appearing at the selected device input-mode I/O pins is compressed into an 18-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, an 18-bit pseudo-random pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 10 and 11 illustrate the 18-bit linear-feedback shift-register algorithms through which the signature and patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

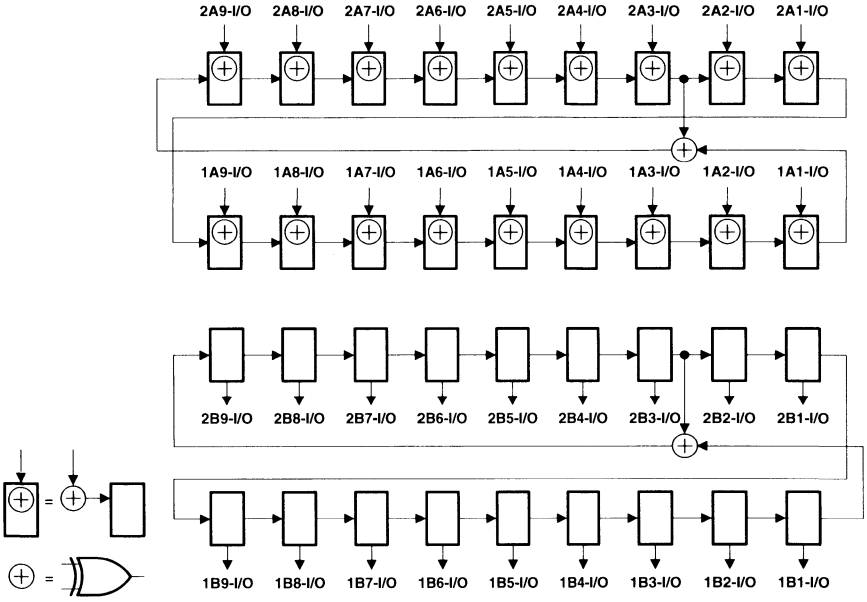


Figure 10. 18-Bit PSA/PRPG Configuration (1OEA = 2OEA = 0, 1OEB = 2OEB = 1)

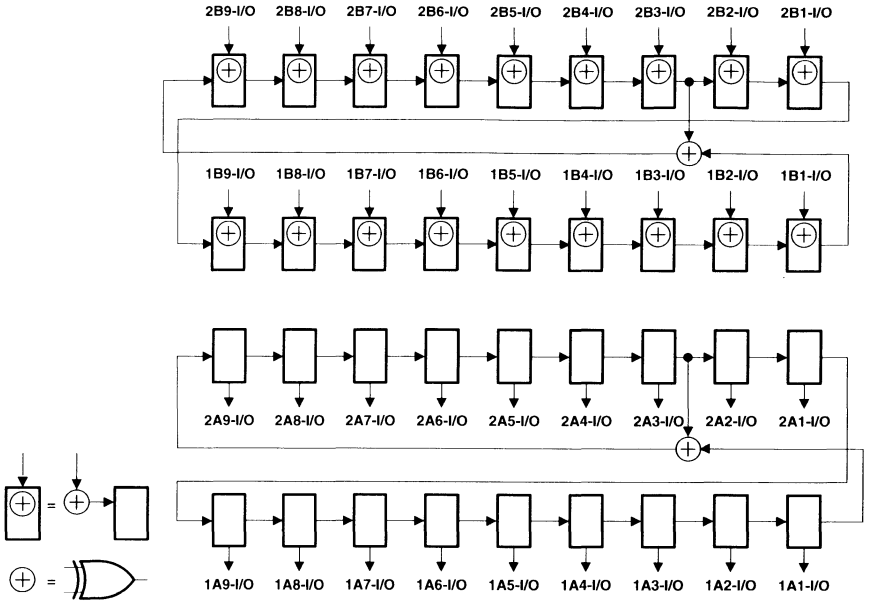


Figure 11. 18-Bit PSA/PRPG Configuration (1OEA = 2OEA = 1, 1OEB = 2OEB = 0)

simultaneous PSA and binary count up (PSA/COUNT)

Data appearing at the selected device input-mode I/O pins is compressed into an 18-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, an 18-bit binary count-up pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 12 and 13 illustrate the 18-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

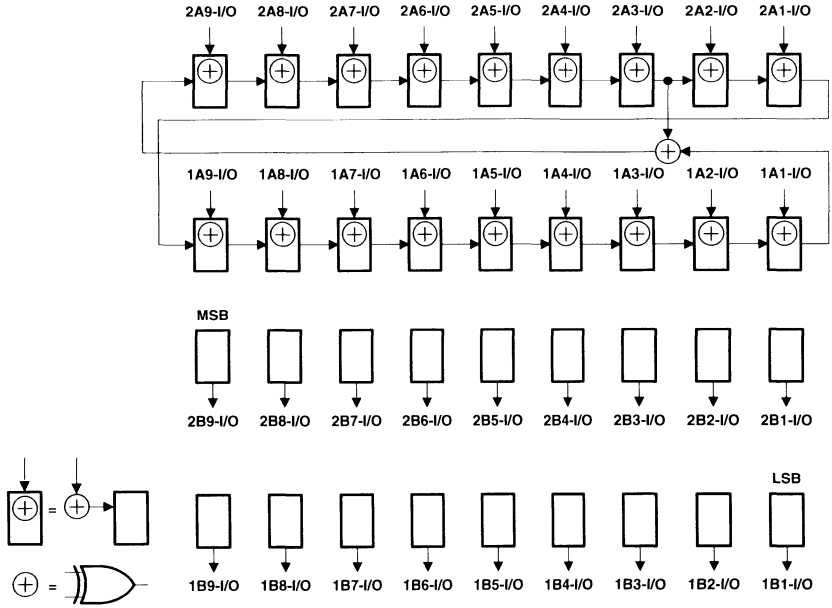


Figure 12. 18-Bit PSA/COUNT Configuration (1OEA = 2OEA = 0, 1OEB = 2OEB = 1)

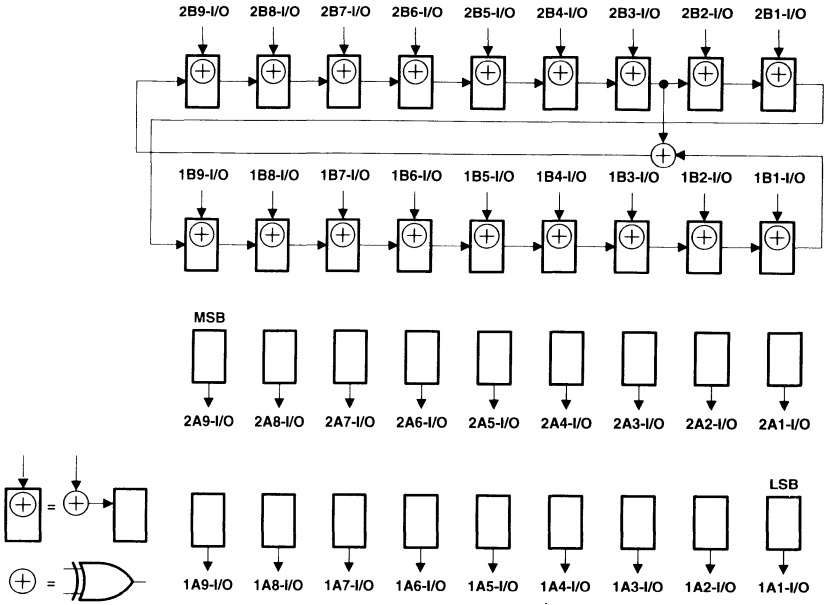


Figure 13. 18-Bit PSA/COUNT Configuration (1OEA = 2OEA = 1, 1OEB = 2OEB = 0)

timing description

All test operations of the 'LVTH18646A and 'LVTH182646A are synchronous to the TCK signal. Data on the TDI, TMS, and normal-function inputs is captured on the rising edge of TCK. Data appears on the TDO and normal-function output pins on the falling edge of TCK. The TAP controller is advanced through its states (as shown in Figure 2) by changing the value of TMS on the falling edge of TCK and then applying a rising edge to TCK.

A simple timing example is shown in Figure 14. In this example, the TAP controller begins in the Test-Logic-Reset state and is advanced through its states as necessary to perform one instruction-register scan and one data-register scan. While in the Shift-IR and Shift-DR states, TDI is used to input serial data, and TDO is used to output serial data. The TAP controller is then returned to the Test-Logic-Reset state. Table 5 explains the operation of the test circuitry during each TCK cycle.

Table 5. Explanation of Timing Example

TCK CYCLE(S)	TAP STATE AFTER TCK	DESCRIPTION
1	Test-Logic-Reset	TMS is changed to a logic 0 value on the falling edge of TCK to begin advancing the TAP controller toward the desired state.
2	Run-Test/Idle	
3	Select-DR-Scan	
4	Select-IR-Scan	
5	Capture-IR	The IR captures the 8-bit binary value 10000001 on the rising edge of TCK as the TAP controller exits the Capture-IR state.
6	Shift-IR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
7–13	Shift-IR	One bit is shifted into the IR on each TCK rising edge. With TDI held at a logic 1 value, the 8-bit binary value 11111111 is serially scanned into the IR. At the same time, the 8-bit binary value 10000001 is serially scanned out of the IR via TDO. In TCK cycle 13, TMS is changed to a logic 1 value to end the IR scan on the next TCK cycle. The last bit of the instruction is shifted as the TAP controller advances from Shift-IR to Exit1-IR.
14	Exit1-IR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
15	Update-IR	The IR is updated with the new instruction (BYPASS) on the falling edge of TCK.
16	Select-DR-Scan	
17	Capture-DR	The bypass register captures a logic 0 value on the rising edge of TCK as the TAP controller exits the Capture-DR state.
18	Shift-DR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
19–20	Shift-DR	The binary value 101 is shifted in via TDI, while the binary value 010 is shifted out via TDO.
21	Exit1-DR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
22	Update-DR	In general, the selected data register is updated with the new data on the falling edge of TCK.
23	Select-DR-Scan	
24	Select-IR-Scan	
25	Test-Logic-Reset	Test operation completed

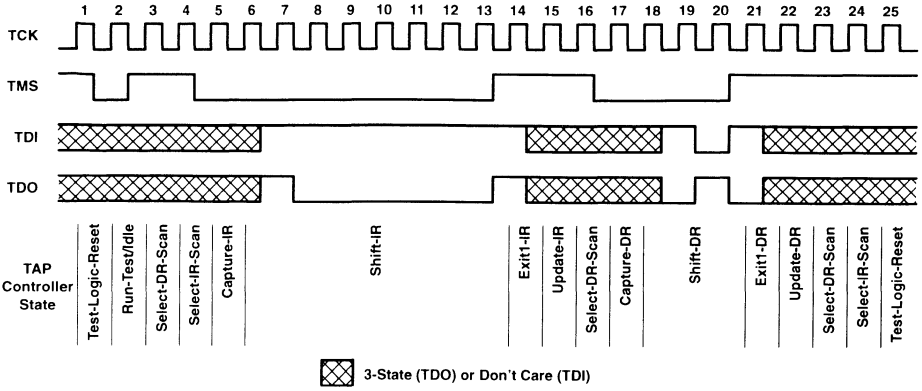


Figure 14. Timing Example

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH18646A ..... 96 mA
SN54LVTH182646A (A port or TDO) ..... 96 mA
SN54LVTH182646A (B port) ..... 30 mA
SN74LVTH18646A ..... 128 mA
SN74LVTH182646A (A port or TDO) ..... 128 mA
SN74LVTH182646A (B port) ..... 30 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH18646A ..... 48 mA
SN54LVTH182646A (A port or TDO) .... 48 mA
SN54LVTH182646A (B port) ..... 30 mA
SN74LVTH18646A ..... 64 mA
SN74LVTH182646A (A port or TDO) .... 64 mA
SN74LVTH182646A (B port) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Package thermal impedance, θ_{JA} (see Note 3): PM package ..... 67°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings can be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			SN54LVTH18646A		SN74LVTH18646A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage					0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			24		32	mA
I_{OL}†	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH18646A			SN74LVTH18646A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –3 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –8 mA	2.4			2.4			
			I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	CLK, DIR, S, TCK	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or MAX‡,	V_I = 5.5 V			10			10	
	$\overline{OE}$, TDI, TMS	V_{CC} = 3.6 V	V_I = 5.5 V			50			50	
			V_I = V_{CC}			1			1	
			V_I = 0	–25		–100	–25		–100	
	A or B ports§	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$¶	A or B ports	V_{CC} = 3 V	V_I = 0.8 V	75	150	500	75	150	500	µA
			V_I = 2 V	–75	–150	–500	–75	–150	–500	
I_{OZH}	TDO	V_{CC} = 3.6 V,	V_O = 3 V			1			1	µA
I_{OZL}	TDO	V_{CC} = 3.6 V,	V_O = 0.5 V			–1			–1	µA
I_{OZPU}	TDO	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{OZPD}	TDO	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V			±50			±50	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.6	2		0.6	2	mA
			Outputs low		20	24		20	24	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}#		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.5			0.5	mA
C_i		V_I = 3 V or 0			4			4		pF
C_{io}		V_O = 3 V or 0			10			10		pF
C_o		V_O = 3 V or 0			8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 15)

			SN54LVTH18646A				SN74LVTH18646A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA	0	120	0	100	0	120	0	100	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low	3.8		5		3.8		5		ns
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑	2.9		3.1		2.9		3.1		ns
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑	0.8		0.2		0.8		0.2		ns

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 15)

			SN54LVTH18646A				SN74LVTH18646A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, DIR, $\overline{OE}$ or S before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, DIR, $\overline{OE}$ or S after TCK↑	1.5		1		1.5		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 15)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18646A				SN74LVTH18646A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		120		100		120		100		MHz
t_{PLH}	A or B	B or A	1.5	5		5.4	1.5	4.7		5.2	ns
t_{PHL}			1.5	5		5.4	1.5	4.7		5.2	
t_{PLH}	CLKAB or CLKBA	B or A	1.5	6.9		7.5	1.5	6.5		7.1	ns
t_{PHL}			1.5	6.9		7.5	1.5	6.5		7.1	
t_{PLH}	SAB or SBA	B or A	1.5	7.9		8.7	1.5	7.5		8.4	ns
t_{PHL}			1.5	7.9		8.7	1.5	7.5		8.4	
t_{PZH}	DIR	B or A	1.5	8.2		9.2	1.5	7.8		8.6	ns
t_{PZL}			1.5	8.2		9.2	1.5	7.8		8.6	
t_{PZH}	$\overline{OE}$	B or A	1.5	8.6		9.5	1.5	8.1		9	ns
t_{PZL}			1.5	8.6		9.5	1.5	8.1		9	
t_{PHZ}	DIR	B or A	2.5	10.5		11.3	2.5	9.7		10.6	ns
t_{PLZ}			2.5	9		10.1	2.5	8.6		9.3	
t_{PHZ}	$\overline{OE}$	B or A	3	11.1		11.9	3	10.4		11.1	ns
t_{PLZ}			3	9.8		10.5	3	9.1		9.7	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 15)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18646A				SN74LVTH18646A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

recommended operating conditions

			SN54LVTH182646A		SN74LVTH182646A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	A port, TDO		–24		–32	mA
		B port		–12		–12	
I_{OL}	Low-level output current	A port, TDO		24		32	mA
		B port		12		12	
I_{OL}†	Low-level output current	A port, TDO		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTH182646A			SN74LVTH182646A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA	A port, TDO	V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = −3 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = −8 mA		2.4			2.4			
		I_{OH} = −24 mA		2						
		I_{OH} = −32 mA					2			
		I_{OH} = −12 mA	B port	2			2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA	A port, TDO			0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
		I_{OL} = 12 mA	B port			0.8			0.8	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	CLK, DIR, S, TCK			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	$\overline{OE}$, TDI, TMS			50			50	
		V_I = V_{CC}				1			1	
		V_I = 0		−25		−100	−25		−100	
		V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				1			1	
		V_I = 0				−5			−5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$¶	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75	150	500	75	150	500	µA
		V_I = 2 V		−75	−150	−500	−75	−150	−500	
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V	TDO			1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V	TDO			−1			−1	µA
I_{OZPU}	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{OZPD}	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{CC}	V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.6	2		0.6	2	mA
		Outputs low			20	24		20	24	
		Outputs disabled			0.6	2		0.6	2	
ΔI_{CC}#	V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND					0.5			0.5	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				10			10		pF
C_o	V_O = 3 V or 0				8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ The parameter $I_{I(hold)}$ includes the off-state ouput leakage current.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 15)

			SN54LVTH182646A				SN74LVTH182646A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA	0	120	0	100	0	120	0	100	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low	3.8		5		3.8		5		ns
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑	2.9		3.1		2.9		3.1		ns
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑	0.8		0.2		0.8		0.2		ns

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 15)

			SN54LVTH182646A				SN74LVTH182646A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, DIR, $\overline{OE}$ or S before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, DIR, $\overline{OE}$ or S after TCK↑	1.5		1		1.5		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

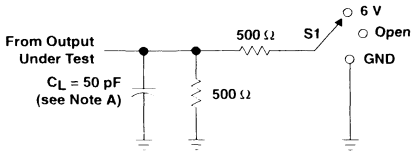
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 15)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182646A				SN74LVTH182646A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		120		100		120		100		MHz
t_{PLH}	B	A	1.5	5		5.4	1.5	4.7		5.2	ns
t_{PHL}			1.5	5		5.4	1.5	4.7		5.2	
t_{PLH}	A	B	1.5	5.9		6.5	1.5	5.6		6.2	ns
t_{PHL}			1.5	5.9		6.5	1.5	5.6		6.2	
t_{PLH}	CLKBA	A	1.5	6.9		7.5	1.5	6.5		7.1	ns
t_{PHL}			1.5	6.9		7.5	1.5	6.5		7.1	
t_{PLH}	CLKAB	B	1.5	7.8		8.7	1.5	7.3		8.2	ns
t_{PHL}			1.5	7.8		8.7	1.5	7.3		8.2	
t_{PLH}	SBA	A	1.5	7.9		8.7	1.5	7.5		8.4	ns
t_{PHL}			1.5	7.9		8.7	1.5	7.5		8.4	
t_{PLH}	SAB	B	1.5	8.5		9.2	1.5	8		8.8	ns
t_{PHL}			1.5	8.5		9.2	1.5	8		8.8	
t_{PZH}	DIR	B or A	1.5	8.7		9.4	1.5	8.1		8.8	ns
t_{PZL}			1.5	8.7		9.4	1.5	8.1		8.8	
t_{PZH}	$\overline{OE}$	B or A	1.5	9.1		10.1	1.5	8.6		9.4	ns
t_{PZL}			1.5	9.1		10.1	1.5	8.6		9.4	
t_{PHZ}	DIR	B or A	2.5	10.5		11.3	2.5	9.7		10.6	ns
t_{PLZ}			2.5	9		10.1	2.5	8.6		9.3	
t_{PHZ}	$\overline{OE}$	B or A	3	11.1		11.9	3	10.4		11.1	ns
t_{PLZ}			3	9.8		10.5	3	9.1		9.7	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 15)

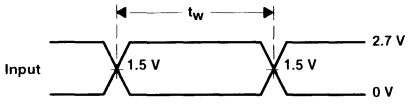
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182646A				SN74LVTH182646A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

PARAMETER MEASUREMENT INFORMATION

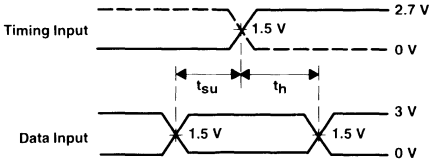


LOAD CIRCUIT

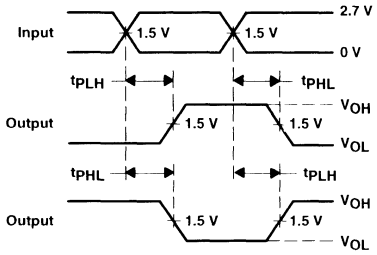
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



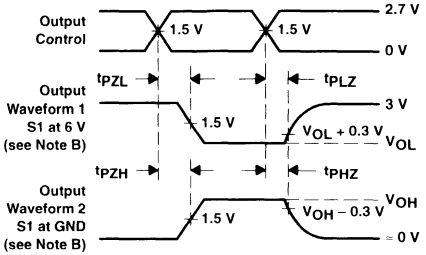
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 15. Load Circuit and Voltage Waveforms

- **Members of the Texas Instruments *SCOPE*™ Family of Testability Products**
- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art 3.3-V ABT Design Supports Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Include D-Type Flip-Flops and Control Circuitry to Provide Multiplexed Transmission of Stored and Real-Time Data**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **B-Port Outputs of 'LVTH182652A Devices Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required**
- **Compatible With the IEEE Std 1149.1-1990 (JTAG) Test Access Port and Boundary-Scan Architecture**
- ***SCOPE* Instruction Set**
  - **IEEE Std 1149.1-1990 Required Instructions and Optional CLAMP and HIGHZ**
  - **Parallel-Signature Analysis at Inputs**
  - **Pseudo-Random Pattern Generation From Outputs**
  - **Sample Inputs/Toggle Outputs**
  - **Binary Count From Outputs**
  - **Device Identification**
  - **Even-Parity Opcodes**
- **Packaged in 64-Pin Plastic Thin Quad Flat (PM) Packages Using 0.5-mm Center-to-Center Spacings and 68-Pin Ceramic Quad Flat (HV) Packages Using 25-mil Center-to-Center Spacings**

description

The 'LVTH18652A and 'LVTH182652A scan test devices with 18-bit bus transceivers and registers are members of the Texas Instruments (TI) SCOPE testability integrated-circuit family. This family of devices supports IEEE Std 1149.1-1990 boundary scan to facilitate testing of complex circuit board assemblies. Scan access to the test circuitry is accomplished via the 4-wire test access port (TAP) interface.

Additionally, these devices are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

In the normal mode, these devices are 18-bit bus transceivers and registers that allow for multiplexed transmission of data directly from the input bus or from the internal registers. They can be used either as two 9-bit transceivers or one 18-bit transceiver. The test circuitry can be activated by the TAP to take snapshot samples of the data appearing at the device pins or to perform a self test on the boundary-test cells. Activating the TAP in the normal mode does not affect the functional operation of the SCOPE bus transceivers and registers.

Data flow in each direction is controlled by clock (CLKAB and CLKBA), select (SAB and SBA), and output-enable (OEAB and $\overline{\text{OEBA}}$) inputs. For A-to-B data flow, data on the A bus is clocked into the associated registers on the low-to-high transition of CLKAB. When SAB is low, real-time A data is selected for presentation to the B bus (transparent mode). When SAB is high, stored A data is selected for presentation to the B bus (registered mode). When OEAB is high, the B outputs are active. When OEAB is low, the B outputs are in the high-impedance state.

Control for B-to-A data flow is similar to that for A-to-B data flow but uses CLKBA, SBA, and $\overline{\text{OEBA}}$ inputs. Since the $\overline{\text{OEBA}}$ input is active-low, the A outputs are active when $\overline{\text{OEBA}}$ is low and are in the high-impedance state when $\overline{\text{OEBA}}$ is high. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'LVTH18652A and 'LVTH182652A.

description (continued)

In the test mode, the normal operation of the SCOPE bus transceivers and registers is inhibited, and the test circuitry is enabled to observe and control the I/O boundary of the device. When enabled, the test circuitry performs boundary-scan test operations according to the protocol described in IEEE Std 1149.1-1990.

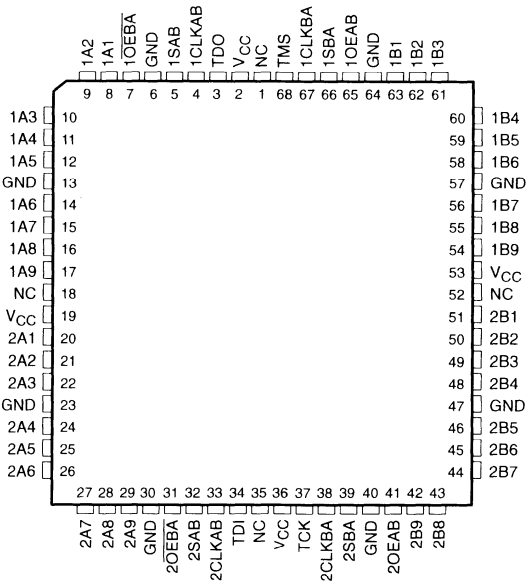
Four dedicated test pins are used to observe and control the operation of the test circuitry: test data input (TDI), test data output (TDO), test mode select (TMS), and test clock (TCK). Additionally, the test circuitry performs other testing functions such as parallel-signature analysis (PSA) on data inputs and pseudo-random pattern generation (PRPG) from data outputs. All testing and scan operations are synchronized to the TAP interface.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The B-port outputs of 'LVTH182652A, which are designed to source or sink up to 12 mA, include equivalent 25-Ω series resistors to reduce overshoot and undershoot.

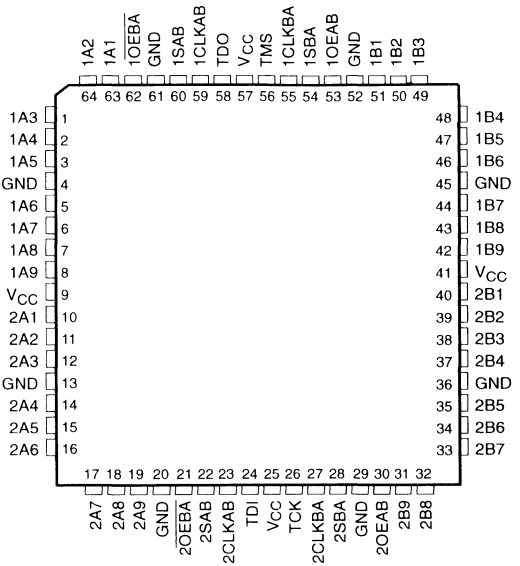
The SN54LVTH18652A and SN54LVTH182652A are characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH18652A and SN74LVTH182652A are characterized for operation from –40°C to 85°C.

SN54LVTH18652A, SN54LVTH182652A . . . HV PACKAGE
(TOP VIEW)



NC – No internal connection

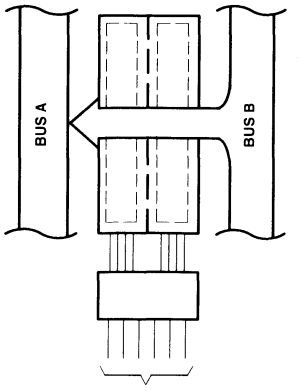
SN74LVTH18652A, SN74LVTH182652A . . . PM PACKAGE
(TOP VIEW)



FUNCTION TABLE
(normal mode, each 9-bit section)

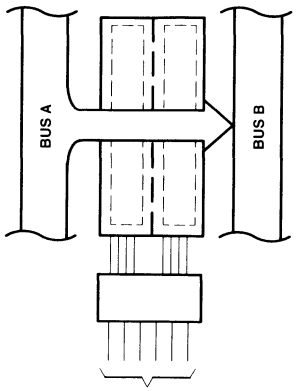
INPUTS						DATA I/O		OPERATION OR FUNCTION
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA	A1–A9	B1–B9	
L	H	L	L	X	X	Input disabled	Input disabled	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	L	X	X	Input	Unspecified†	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	L	↑	X	X	Unspecified†	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	X	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	X	X	H	X	Input	Output	Stored A data to B bus
H	L	X	X	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

† The data-output functions can be enabled or disabled by a variety of level combinations at OEAB or $\overline{OEBA}$. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.
‡ Select control = L: clocks can occur simultaneously.
Select control = H: clocks must be staggered to load both registers.



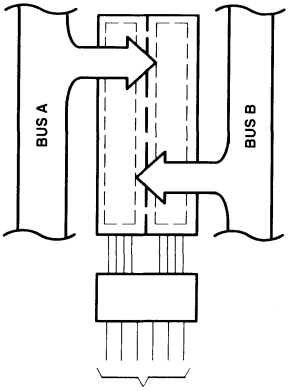
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER BUS B TO BUS A



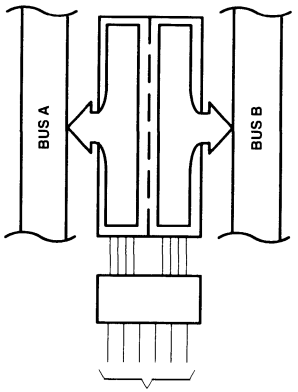
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER BUS A TO BUS B



OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM A, B, OR A AND B

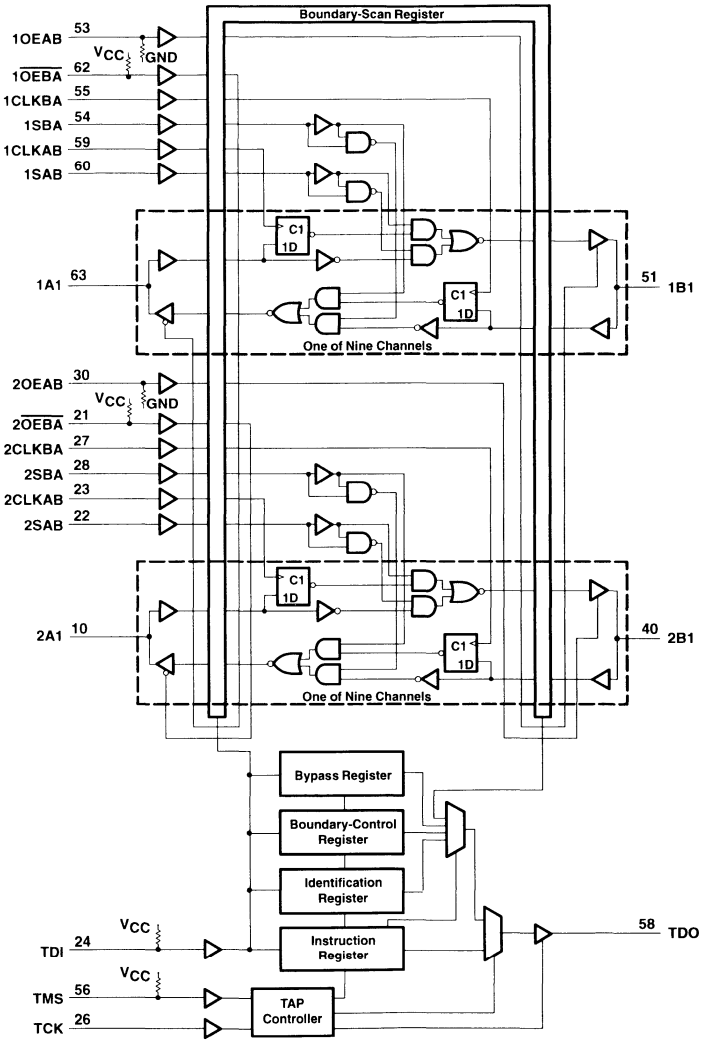


OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	L	X	X	H	H

TRANSFER STORED DATA TO A AND/OR B

Figure 1. Bus-Management Functions

functional block diagram



Pin numbers shown are for the PM package.

Terminal Functions

TERMINAL NAME	DESCRIPTION
1A1–1A9, 2A1–2A9	Normal-function A-bus I/O ports. See function table for normal-mode logic.
1B1–1B9, 2B1–2B9	Normal-function B-bus I/O ports. See function table for normal-mode logic.
1CLKAB, 1CLKBA, 2CLKAB, 2CLKBA	Normal-function clock inputs. See function table for normal-mode logic.
GND	Ground
1OEAB, 2OEAB	Normal-function active-high output enables. See function table for normal-mode logic. An internal pulldown at each terminal forces the terminal to a low level if left unconnected.
$\overline{1OEBA}$, $\overline{2OEBA}$	Normal-function active-low output enables. See function table for normal-mode logic. An internal pullup at each terminal forces the terminal to a high level if left unconnected.
1SAB, 1SBA, 2SAB, 2SBA	Normal-function select controls. See function table for normal-mode logic.
TCK	Test clock. One of four terminals required by IEEE Std 1149.1-1990. Test operations of the device are synchronous TCK. Data is captured on the rising edge of TCK and outputs change on the falling edge of TCK.
TDI	Test data input. One of four terminals required by IEEE Std 1149.1-1990. TDI is the serial input for shifting data through the instruction register or selected data register. An internal pullup forces TDI to a high level if left unconnected.
TDO	Test data output. One of four terminals required by IEEE Std 1149.1-1990. TDO is the serial output for shifting data through the instruction register or selected data register.
TMS	Test mode select. One of four terminals required by IEEE Std 1149.1-1990. TMS directs the device through its TAP controller states. An internal pullup forces TMS to a high level if left unconnected.
V_{CC}	Supply voltage

test architecture

Serial-test information is conveyed by means of a 4-wire test bus or TAP that conforms to IEEE Std 1149.1-1990. Test instructions, test data, and test control signals all are passed along this serial-test bus. The TAP controller monitors two signals from the test bus, TCK and TMS. The TAP controller extracts the synchronization (TCK) and state control (TMS) signals from the test bus and generates the appropriate on-chip control signals for the test structures in the device. Figure 2 shows the TAP-controller state diagram.

The TAP controller is fully synchronous to the TCK signal. Input data is captured on the rising edge of TCK and output data changes on the falling edge of TCK. This scheme ensures data to be captured is valid for fully one-half of the TCK cycle.

The functional block diagram shows the IEEE Std 1149.1-1990 4-wire test bus and boundary-scan architecture and the relationship among the test bus, the TAP controller, and the test registers. As shown, the device contains an 8-bit instruction register and four test-data registers: a 48-bit boundary-scan register, a 3-bit boundary-control register, a 1-bit bypass register, and a 32-bit device-identification register.

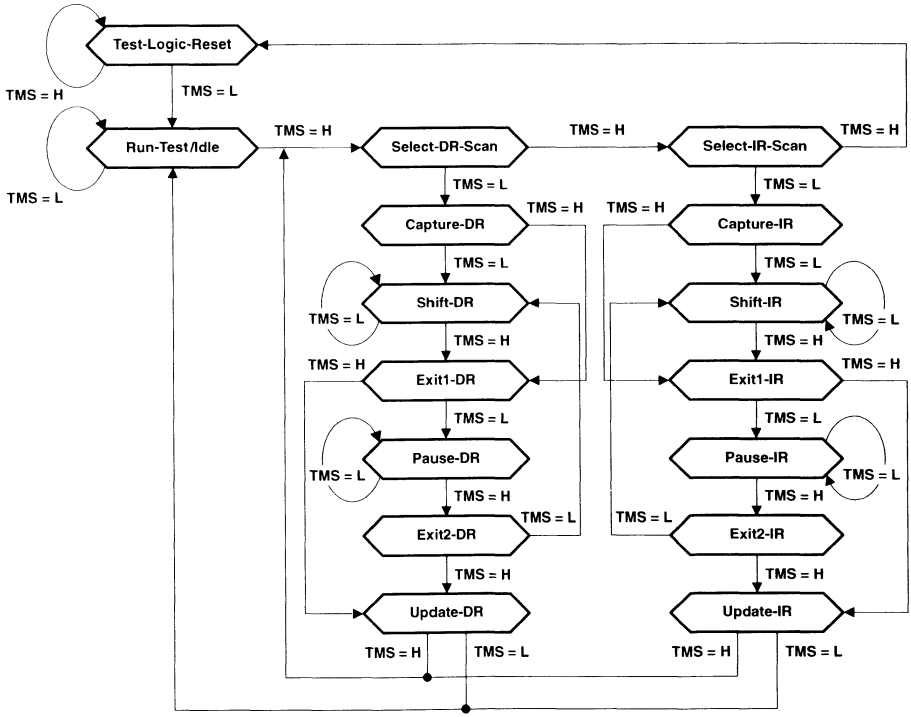


Figure 2. TAP-Controller State Diagram

state diagram description

The TAP controller is a synchronous finite state machine that provides test control signals throughout the device. The state diagram shown in Figure 2 is in accordance with IEEE Std 1149.1-1990. The TAP controller proceeds through its states based on the level of TMS at the rising edge of TCK.

As shown, the TAP controller consists of 16 states. There are six stable states (indicated by a looping arrow in the state diagram) and ten unstable states. A stable state is defined as a state the TAP controller can retain for consecutive TCK cycles. Any state that does not meet this criterion is an unstable state.

There are two main paths through the state diagram: one to access and control the selected data register and one to access and control the instruction register. Only one register can be accessed at a time.

Test-Logic-Reset

The device powers up in the Test-Logic-Reset state. In the stable Test-Logic-Reset state, the test logic is reset and is disabled so that the normal logic function of the device is performed. The instruction register is reset to an opcode that selects the optional IDCODE instruction, if supported, or the BYPASS instruction. Certain data registers can also be reset to their power-up values.

The state machine is constructed such that the TAP controller returns to the Test-Logic-Reset state in no more than five TCK cycles if TMS is left high. The TMS pin has an internal pullup resistor that forces it high if left unconnected or if a board defect causes it to be open circuited.

For the 'LVTH18652A and 'LVTH182652A, the instruction register is reset to the binary value 10000001, which selects the IDCODE instruction. Bits 47–46 in the boundary-scan register are reset to logic 0 while bits 45–44 are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., such that if test mode were invoked the outputs would be at high-impedance state). Reset values of other bits in the boundary-scan register should be considered indeterminate. The boundary-control register is reset to the binary value 010, which selects the PSA test operation.

Run-Test/Idle

The TAP controller must pass through the Run-Test/Idle state (from Test-Logic-Reset) before executing any test operations. The Run-Test/Idle state also can be entered following data-register or instruction-register scans. Run-Test/Idle is a stable state in which the test logic can be actively running a test or can be idle. The test operations selected by the boundary-control register are performed while the TAP controller is in the Run-Test/Idle state.

Select-DR-Scan, Select-IR-Scan

No specific function is performed in the Select-DR-Scan and Select-IR-Scan states, and the TAP controller exits either of these states on the next TCK cycle. These states allow the selection of either data-register scan or instruction-register scan.

Capture-DR

When a data-register scan is selected, the TAP controller must pass through the Capture-DR state. In the Capture-DR state, the selected data register can capture a data value as specified by the current instruction. Such capture operations occur on the rising edge of TCK, upon which the TAP controller exits the Capture-DR state.

Shift-DR

Upon entry to the Shift-DR state, the data register is placed in the scan path between TDI and TDO, and on the first falling edge of TCK, TDO goes from the high-impedance state to an active state. TDO enables to the logic level present in the least-significant bit of the selected data register.

While in the stable Shift-DR state, data is serially shifted through the selected data register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-DR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-DR to Shift-DR or from Exit2-DR to Shift-DR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-DR state.

Exit1-DR, Exit2-DR

The Exit1-DR and Exit2-DR states are temporary states that end a data-register scan. It is possible to return to the Shift-DR state from either Exit1-DR or Exit2-DR without recapturing the data register. On the first falling edge of TCK after entry to Exit1-DR, TDO goes from the active state to the high-impedance state.

Pause-DR

No specific function is performed in the stable Pause-DR state, in which the TAP controller can remain indefinitely. The Pause-DR state suspends and resumes data-register scan operations without loss of data.

Update-DR

If the current instruction calls for the selected data register to be updated with current data, such update occurs on the falling edge of TCK, following entry to the Update-DR state.

Capture-IR

When an instruction-register scan is selected, the TAP controller must pass through the Capture-IR state. In the Capture-IR state, the instruction register captures its current status value. This capture operation occurs on the rising edge of TCK, upon which the TAP controller exits the Capture-IR state. For the 'LVTH18652A and 'LVTH182652A, the status value loaded in the Capture-IR state is the fixed binary value 10000001.

Shift-IR

Upon entry to the Shift-IR state, the instruction register is placed in the scan path between TDI and TDO, and on the first falling edge of TCK, TDO goes from the high-impedance state to the active state. TDO enables to the logic level present in the least-significant bit of the instruction register.

While in the stable Shift-IR state, instruction data is serially shifted through the instruction register on each TCK cycle. The first shift occurs on the first rising edge of TCK after entry to the Shift-IR state (i.e., no shifting occurs during the TCK cycle in which the TAP controller changes from Capture-IR to Shift-IR or from Exit2-IR to Shift-IR). The last shift occurs on the rising edge of TCK, upon which the TAP controller exits the Shift-IR state.

Exit1-IR, Exit2-IR

The Exit1-IR and Exit2-IR states are temporary states that end an instruction-register scan. It is possible to return to the Shift-IR state from either Exit1-IR or Exit2-IR without recapturing the instruction register. On the first falling edge of TCK after entry to Exit1-IR, TDO goes from the active state to the high-impedance state.

Pause-IR

No specific function is performed in the stable Pause-IR state, in which the TAP controller can remain indefinitely. The Pause-IR state suspends and resumes instruction-register scan operations without loss of data.

Update-IR

The current instruction is updated and takes effect on the falling edge of TCK, following entry to the Update-IR state.

register overview

With the exception of the bypass and device-identification registers, any test register can be thought of as a serial-shift register with a shadow latch on each bit. The bypass and device identification registers differ in that they contain only a shift register. During the appropriate capture state (Capture-IR for instruction register, Capture-DR for data registers), the shift register can be parallel loaded from a source specified by the current instruction. During the appropriate shift state (Shift-IR or Shift-DR), the contents of the shift register are shifted out from TDO while new contents are shifted in at TDI. During the appropriate update state (Update-IR or Update-DR), the shadow latches are updated from the shift register.

instruction register description

The instruction register (IR) is eight bits long and tells the device what instruction is to be executed. Information contained in the instruction includes the mode of operation (either normal mode, in which the device performs its normal logic function, or test mode, in which the normal logic function is inhibited or altered), the test operation to be performed, which of the four data registers is to be selected for inclusion in the scan path during data-register scans, and the source of data to be captured into the selected data register during Capture-DR.

Table 3 lists the instructions supported by the 'LVTH18652A and 'LVTH182652A. The even-parity feature specified for SCOPE devices is supported in this device. Bit 7 of the instruction opcode is the parity bit. Any instructions that are defined for SCOPE devices but are not supported by this device default to BYPASS.

During Capture-IR, the IR captures the binary value 10000001. As an instruction is shifted in, this value is shifted out via TDO and can be inspected as verification that the IR is in the scan path. During Update-IR, the value that has been shifted into the IR is loaded into shadow latches. At this time, the current instruction is updated and any specified mode change takes effect. At power up or in the Test-Logic-Reset state, the IR is reset to the binary value 10000001, which selects the IDCODE instruction. The IR order of scan is shown in Figure 3.

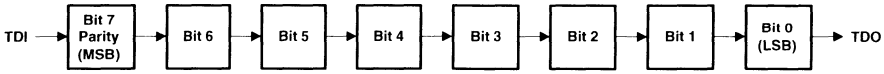


Figure 3. Instruction Register Order of Scan

data register description

boundary-scan register

The boundary-scan register (BSR) is 48 bits long. It contains one boundary-scan cell (BSC) for each normal-function input pin and one BSC for each normal-function I/O pin (one single cell for both input data and output data). The BSR is used 1) to store test data that is to be applied externally to the device output pins, and/or 2) to capture data that appears internally at the outputs of the normal on-chip logic and/or externally at the device input pins.

The source of data to be captured into the BSR during Capture-DR is determined by the current instruction. The contents of the BSR can change during Run-Test/Idle, as determined by the current instruction. At power up or in Test-Logic-Reset, BSCs 47–46 are reset to logic 0 while BSCs 45–44 are reset to logic 1, ensuring that these cells, which control A-port and B-port outputs, are set to benign values (i.e., if test mode were invoked the outputs would be at high-impedance state). Reset values of other BSCs should be considered indeterminate.

The BSR order of scan is from TDI through bits 47–0 to TDO. Table 1 shows the BSR bits and their associated device pin signals.

Table 1. Boundary-Scan Register Configuration

BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL	BSR BIT NUMBER	DEVICE SIGNAL
47	2OEAB	35	2A9-I/O	17	2B9-I/O
46	1OEAB	34	2A8-I/O	16	2B8-I/O
45	$2\overline{OEBA}$	33	2A7-I/O	15	2B7-I/O
44	$1\overline{OEBA}$	32	2A6-I/O	14	2B6-I/O
43	2CLKAB	31	2A5-I/O	13	2B5-I/O
42	1CLKAB	30	2A4-I/O	12	2B4-I/O
41	2CLKBA	29	2A3-I/O	11	2B3-I/O
40	1CLKBA	28	2A2-I/O	10	2B2-I/O
39	2SAB	27	2A1-I/O	9	2B1-I/O
38	1SAB	26	1A9-I/O	8	1B9-I/O
37	2SBA	25	1A8-I/O	7	1B8-I/O
36	1SBA	24	1A7-I/O	6	1B7-I/O
—	—	23	1A6-I/O	5	1B6-I/O
—	—	22	1A5-I/O	4	1B5-I/O
—	—	21	1A4-I/O	3	1B4-I/O
—	—	20	1A3-I/O	2	1B3-I/O
—	—	19	1A2-I/O	1	1B2-I/O
—	—	18	1A1-I/O	0	1B1-I/O

boundary-control register

The boundary-control register (BCR) is three bits long. The BCR is used in the context of the RUNT instruction to implement additional test operations not included in the basic SCOPE instruction set. Such operations include PRPG, PSA, and binary count up (COUNT). Table 4 shows the test operations that are decoded by the BCR.

During Capture-DR, the contents of the BCR are not changed. At power up or in Test-Logic-Reset, the BCR is reset to the binary value 010, which selects the PSA test operation. The BCR order of scan is shown in Figure 4.

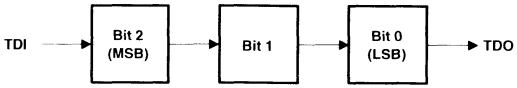


Figure 4. Boundary-Control Register Order of Scan

bypass register

The bypass register is a 1-bit scan path that can be selected to shorten the length of the system scan path, reducing the number of bits per test pattern that must be applied to complete a test operation. During Capture-DR, the bypass register captures a logic 0. The bypass register order of scan is shown in Figure 5.

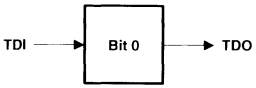


Figure 5. Bypass Register Order of Scan

device-identification register

The device-identification register (IDR) is 32 bits long. It can be selected and read to identify the manufacturer, part number, and version of this device.

For the 'LVTH18652A, the binary value 00100000000000001111000000101111 (2001F02F, hex) is captured (during Capture-DR state) in the device-identification register to identify this device as TI SN54/74LVTH18652A.

For the 'LVTH182652A, the binary value 00100000000000010010000000101111 (2002402F, hex) is captured (during Capture-DR state) in the device-identification register to identify this device as TI SN54/74LVTH182652A.

The device-identification register order of scan is from TDI through bits 31–0 to TDO. Table 2 shows the device-identification register bits and their significance.

Table 2. Device-Identification Register Configuration

IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE	IDR BIT NUMBER	IDENTIFICATION SIGNIFICANCE
31	VERSION3	27	PARTNUMBER15	11	MANUFACTURER10†
30	VERSION2	26	PARTNUMBER14	10	MANUFACTURER09†
29	VERSION1	25	PARTNUMBER13	9	MANUFACTURER08†
28	VERSION0	24	PARTNUMBER12	8	MANUFACTURER07†
—	—	23	PARTNUMBER11	7	MANUFACTURER06†
—	—	22	PARTNUMBER10	6	MANUFACTURER05†
—	—	21	PARTNUMBER09	5	MANUFACTURER04†
—	—	20	PARTNUMBER08	4	MANUFACTURER03†
—	—	19	PARTNUMBER07	3	MANUFACTURER02†
—	—	18	PARTNUMBER06	2	MANUFACTURER01†
—	—	17	PARTNUMBER05	1	MANUFACTURER00†
—	—	16	PARTNUMBER04	0	LOGIC1†
—	—	15	PARTNUMBER03	—	—
—	—	14	PARTNUMBER02	—	—
—	—	13	PARTNUMBER01	—	—
—	—	12	PARTNUMBER00	—	—

† Note that for TI products, bits 11–0 of the device-identification register always contain the binary value 000000101111 (02F, hex).

instruction-register opcode description

The instruction-register opcodes are shown in Table 3. The following descriptions detail the operation of each instruction.

Table 3. Instruction-Register Opcodes

BINARY CODE† BIT 7 → BIT 0 MSB → LSB	SCOPE OPCODE	DESCRIPTION	SELECTED DATA REGISTER	MODE
00000000	EXTEST	Boundary scan	Boundary scan	Test
10000001	IDCODE	Identification read	Device identification	Normal
10000010	SAMPLE/PRELOAD	Sample boundary	Boundary scan	Normal
00000011	BYPASS‡	Bypass scan	Bypass	Normal
10000100	BYPASS‡	Bypass scan	Bypass	Normal
00000101	BYPASS‡	Bypass scan	Bypass	Normal
00000110	HIGHZ	Control boundary to high impedance	Bypass	Modified test
10000111	CLAMP	Control boundary to 1/0	Bypass	Test
10001000	BYPASS‡	Bypass scan	Bypass	Normal
00001001	RUNT	Boundary run test	Bypass	Test
00001010	READBN	Boundary read	Boundary scan	Normal
10001011	READBT	Boundary read	Boundary scan	Test
00001100	CELLTST	Boundary self test	Boundary scan	Normal
10001101	TOPHIP	Boundary toggle outputs	Bypass	Test
10001110	SCANCN	Boundary-control register scan	Boundary control	Normal
00001111	SCANCT	Boundary-control register scan	Boundary control	Test
All others	BYPASS	Bypass scan	Bypass	Normal

† Bit 7 is used to maintain even parity in the 8-bit instruction.
‡ The BYPASS instruction is executed in lieu of a SCOPE instruction that is not supported in the 'LVTH18652 or 'LVTH182652.

boundary scan

This instruction conforms to the IEEE Std 1149.1-1990 EXTEST instruction. The BSR is selected in the scan path. Data appearing at the device input and I/O pins is captured in the associated BSCs. Data that has been scanned into the I/O BSCs for pins in the output mode is applied to the device I/O pins. Data present at the device pins, except for output enables, is passed through the BSCs to the normal on-chip logic. For I/O pins, the operation of a pin as input or output is determined by the contents of the output-enable BSCs (bits 47–44 of the BSR). When a given output enable is active (logic 0 for $\overline{\text{OEBA}}$, logic 1 for OEAB), the associated I/O pins operate in the output mode. Otherwise, the I/O pins operate in the input mode. The device operates in the test mode.

identification read

This instruction conforms to the IEEE Std 1149.1-1990 IDCODE instruction. The device identification register is selected in the scan path. The device operates in the normal mode.

sample boundary

This instruction conforms to the IEEE Std 1149.1-1990 SAMPLE/PRELOAD instruction. The BSR is selected in the scan path. Data appearing at the device input pins and I/O pins in the input mode is captured in the associated BSCs, while data appearing at the outputs of the normal on-chip logic is captured in the BSCs associated with I/O pins in the output mode. The device operates in the normal mode.

bypass scan

This instruction conforms to the IEEE Std 1149.1-1990 BYPASS instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the normal mode.

control boundary to high impedance

This instruction conforms to the IEEE Std 1149.1a-1993 HIGHZ instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in a modified test mode in which all device I/O pins are placed in the high-impedance state, the device input pins remain operational, and the normal on-chip logic function is performed.

control boundary to 1/0

This instruction conforms to the IEEE Std 1149.1a-1993 CLAMP instruction. The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the I/O BSCs for pins in the output mode is applied to the device I/O pins. The device operates in the test mode.

boundary-run test

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. The device operates in the test mode. The test operation specified in the BCR is executed during Run-Test/Idle. The five test operations decoded by the BCR are: sample inputs/toggle outputs (TOPSIP), PRPG, PSA, simultaneous PSA and PRPG (PSA/PRPG), and simultaneous PSA and binary count up (PSA/COUNT).

boundary read

The BSR is selected in the scan path. The value in the BSR remains unchanged during Capture-DR. This instruction is useful for inspecting data after a PSA operation.

boundary self test

The BSR is selected in the scan path. All BSCs capture the inverse of their current values during Capture-DR. In this way, the contents of the shadow latches can be read out to verify the integrity of both shift-register and shadow-latch elements of the BSR. The device operates in the normal mode.

boundary toggle outputs

The bypass register is selected in the scan path. A logic 0 value is captured in the bypass register during Capture-DR. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK in Run-Test/Idle and is then updated in the shadow latches and applied to the associated device I/O pins on each falling edge of TCK in Run-Test/Idle. Data in the input-mode BSCs remains constant. Data appearing at the device input or I/O pins is not captured in the input-mode BSCs. The device operates in the test mode.

boundary-control-register scan

The BCR is selected in the scan path. The value in the BCR remains unchanged during Capture-DR. This operation must be performed before a boundary-run test operation to specify which test operation is to be executed.

boundary-control-register opcode description

The BCR opcodes are decoded from BCR bits 2–0 as shown in Table 4. The selected test operation is performed while the RUNT instruction is executed in the Run-Test/Idle state. The following descriptions detail the operation of each BCR instruction and illustrate the associated PSA and PRPG algorithms.

Table 4. Boundary-Control Register Opcodes

BINARY CODE BIT 2 → BIT 0 MSB → LSB	DESCRIPTION
X00	Sample inputs/toggle outputs (TOPSIP)
X01	Pseudo-random pattern generation/36-bit mode (PRPG)
X10	Parallel-signature analysis/36-bit mode (PSA)
011	Simultaneous PSA and PRPG/18-bit mode (PSA/PRPG)
111	Simultaneous PSA and binary count up/18-bit mode (PSA/COUNT)

While the control input BSCs (bits 47–36) are not included in the toggle, PSA, PRPG, or COUNT algorithms, the output-enable BSCs (bits 47–44 of the BSR) control the drive state (active or high impedance) of the selected device output pins. These BCR instructions are only valid when both bytes of the device are operating in one direction of data flow (that is, 1OEAB = $1\overline{OEBA}$ and 2OEAB = $2\overline{OEBA}$) and in the same direction of data flow (that is, 1OEAB = 2OEAB and $1\overline{OEBA} = 2\overline{OEBA}$). Otherwise, the bypass instruction is operated.

sample inputs/toggle outputs (TOPSIP)

Data appearing at the selected device input-mode I/O pins is captured in the shift-register elements of the associated BSCs on each rising edge of TCK. Data in the shift-register elements of the selected output-mode BSCs is toggled on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK.

pseudo-random pattern generation (PRPG)

A pseudo-random pattern is generated in the shift-register elements of the selected BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device output-mode I/O pins on each falling edge of TCK. Figures 6 and 7 illustrate the 36-bit linear-feedback shift-register algorithms through which the patterns are generated. An initial seed value should be scanned into the BSR prior to performing this operation. A seed value of all zeroes does not produce additional patterns.

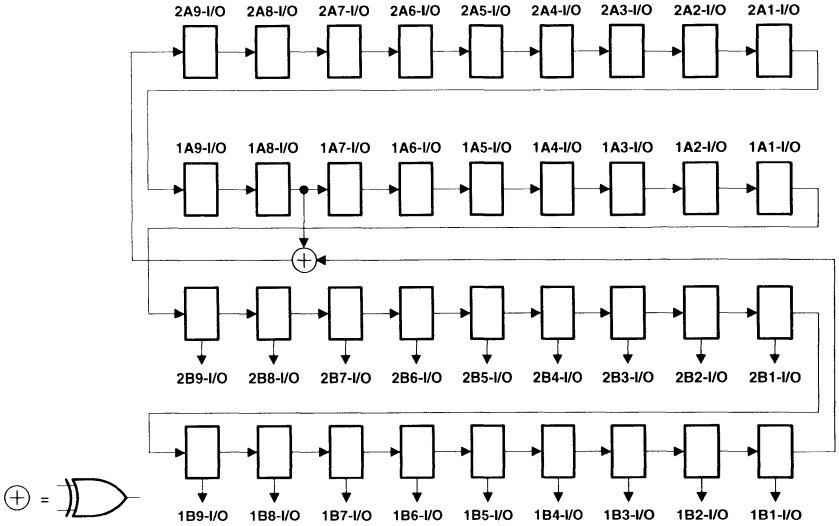


Figure 6. 36-Bit PRPG Configuration (1OEAB = 2OEAB = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 1)

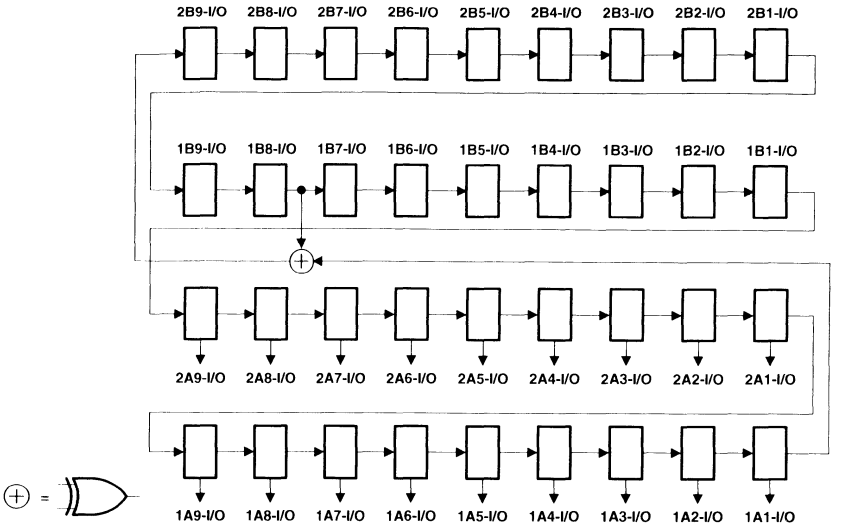


Figure 7. 36-Bit PRPG Configuration (1OEAB = 2OEAB = 0, 1$\overline{\text{OEBA}}$ = 2$\overline{\text{OEBA}}$ = 0)

parallel-signature analysis (PSA)

Data appearing at the selected device input-mode I/O pins is compressed into a 36-bit parallel signature in the shift-register elements of the selected BSCs on each rising edge of TCK. Data in the shadow latches of the selected output-mode BSCs remains constant and is applied to the associated device I/O pins. Figures 8 and 9 illustrate the 36-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

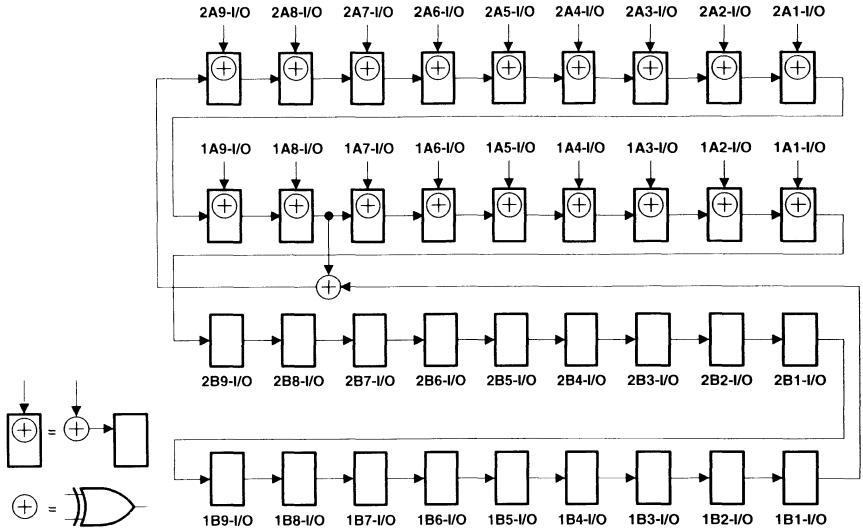


Figure 8. 36-Bit PSA Configuration (1OEAB = 2OEAB = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 1)

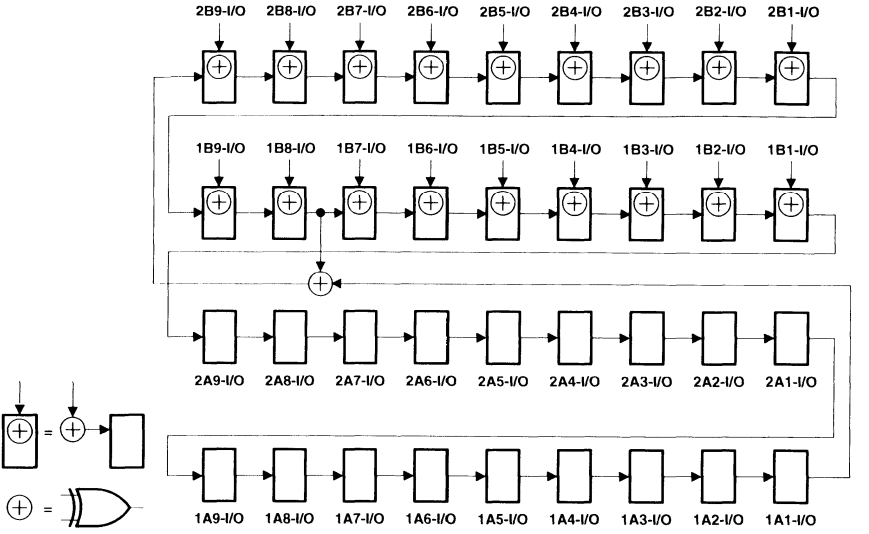


Figure 9. 36-Bit PSA Configuration (1OEAB = 2OEAB = 0, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

simultaneous PSA and PRPG (PSA/PRPG)

Data appearing at the selected device input-mode I/O pins is compressed into an 18-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, an 18-bit pseudo-random pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 10 and 11 illustrate the 18-bit linear-feedback shift-register algorithms through which the signature and patterns are generated. An initial seed value should be scanned into the BSR before performing this operation. A seed value of all zeroes does not produce additional patterns.

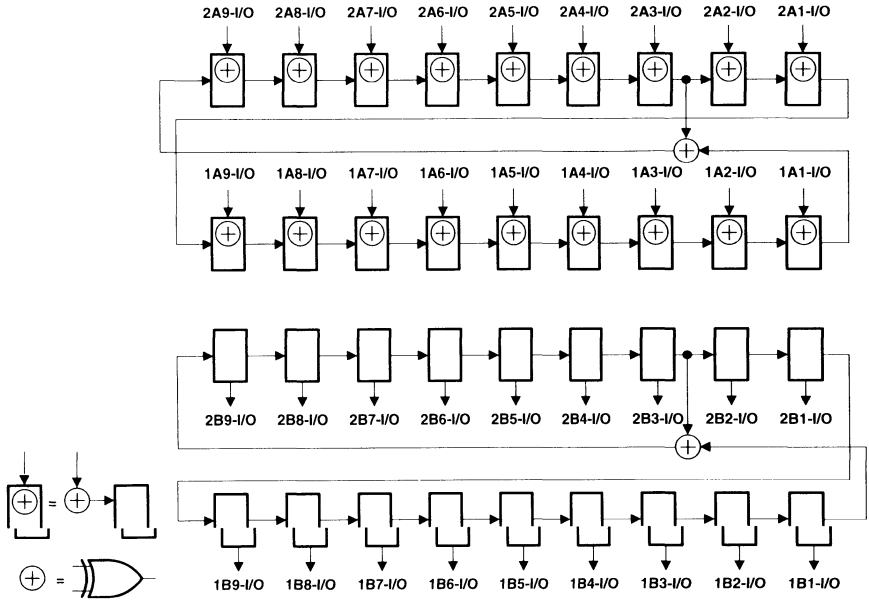


Figure 10. 18-Bit PSA/PRPG Configuration (1OEAB = 2OEAB = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 1)

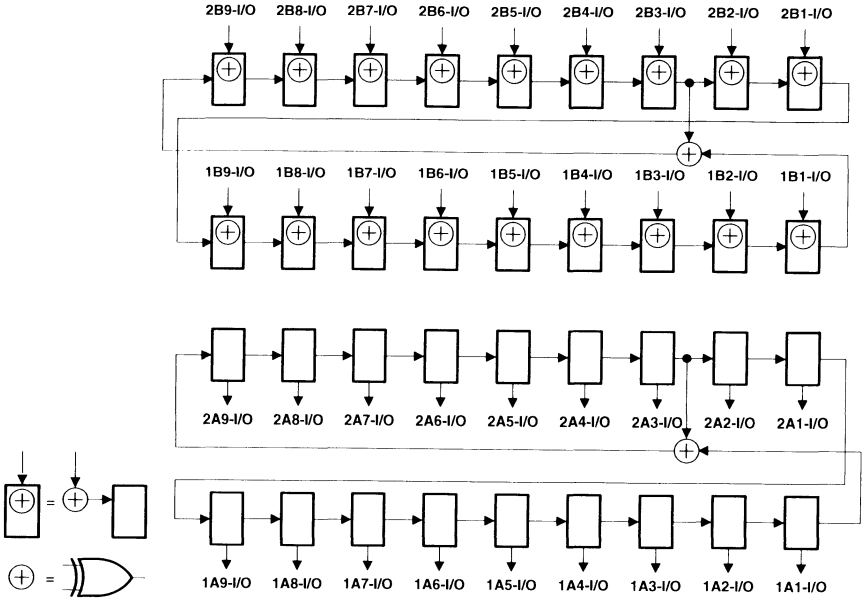


Figure 11. 18-Bit PSA/PRPG Configuration (1OEAB = 2OEAB = 0, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

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simultaneous PSA and binary count up (PSA/COUNT)

Data appearing at the selected device input-mode I/O pins is compressed into an 18-bit parallel signature in the shift-register elements of the selected input-mode BSCs on each rising edge of TCK. At the same time, an 18-bit binary count-up pattern is generated in the shift-register elements of the selected output-mode BSCs on each rising edge of TCK, updated in the shadow latches, and applied to the associated device I/O pins on each falling edge of TCK. Figures 12 and 13 illustrate the 18-bit linear-feedback shift-register algorithms through which the signature is generated. An initial seed value should be scanned into the BSR before performing this operation.

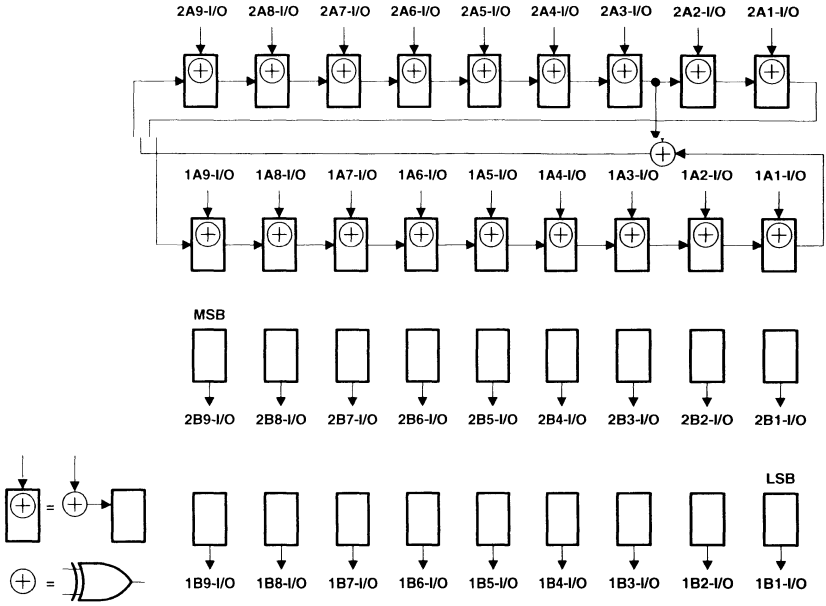


Figure 12. 18-Bit PSA/COUNT Configuration (1OEAB = 2OEAB = 1, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 1)

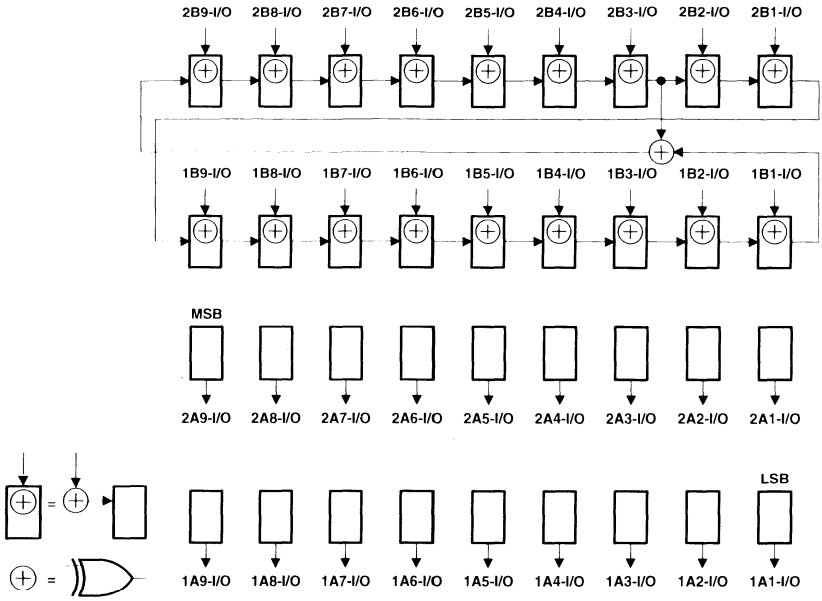


Figure 13. 18-Bit PSA/COUNT Configuration (1OEAB = 2OEAB = 0, $1\overline{OEBA}$ = $2\overline{OEBA}$ = 0)

timing description

All test operations of the 'LVTH18652A and 'LVTH182652A are synchronous to the TCK signal. Data on the TDI, TMS, and normal-function inputs is captured on the rising edge of TCK. Data appears on the TDO and normal-function output pins on the falling edge of TCK. The TAP controller is advanced through its states (as shown in Figure 2) by changing the value of TMS on the falling edge of TCK and then applying a rising edge to TCK.

A simple timing example is shown in Figure 14. In this example, the TAP controller begins in the Test-Logic-Reset state and is advanced through its states as necessary to perform one instruction-register scan and one data-register scan. While in the Shift-IR and Shift-DR states, TDI is used to input serial data, and TDO is used to output serial data. The TAP controller is then returned to the Test-Logic-Reset state. Table 5 explains the operation of the test circuitry during each TCK cycle.

Table 5. Explanation of Timing Example

TCK CYCLE(S)	TAP STATE AFTER TCK	DESCRIPTION
1	Test-Logic-Reset	TMS is changed to a logic 0 value on the falling edge of TCK to begin advancing the TAP controller toward the desired state.
2	Run-Test/Idle	
3	Select-DR-Scan	
4	Select-IR-Scan	
5	Capture-IR	The IR captures the 8-bit binary value 10000001 on the rising edge of TCK as the TAP controller exits the Capture-IR state.
6	Shift-IR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
7–13	Shift-IR	One bit is shifted into the IR on each TCK rising edge. With TDI held at a logic 1 value, the 8-bit binary value 11111111 is serially scanned into the IR. At the same time, the 8-bit binary value 10000001 is serially scanned out of the IR via TDO. In TCK cycle 13, TMS is changed to a logic 1 value to end the IR scan on the next TCK cycle. The last bit of the instruction is shifted as the TAP controller advances from Shift-IR to Exit1-IR.
14	Exit1-IR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
15	Update-IR	The IR is updated with the new instruction (BYPASS) on the falling edge of TCK.
16	Select-DR-Scan	
17	Capture-DR	The bypass register captures a logic 0 value on the rising edge of TCK as the TAP controller exits the Capture-DR state.
18	Shift-DR	TDO becomes active and TDI is made valid on the falling edge of TCK. The first bit is shifted into the TAP on the rising edge of TCK as the TAP controller advances to the next state.
19–20	Shift-DR	The binary value 101 is shifted in via TDI, while the binary value 010 is shifted out via TDO.
21	Exit1-DR	TDO becomes inactive (goes to the high-impedance state) on the falling edge of TCK.
22	Update-DR	In general, the selected data register is updated with the new data on the falling edge of TCK.
23	Select-DR-Scan	
24	Select-IR-Scan	
25	Test-Logic-Reset	Test operation completed

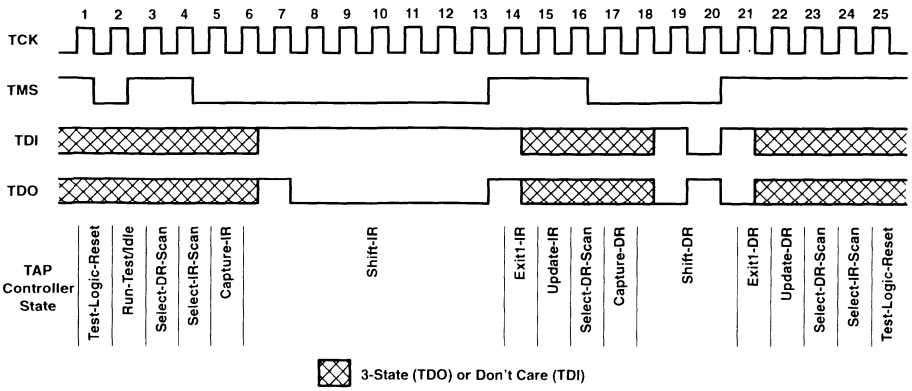


Figure 14. Timing Example

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 4.6 V
Input voltage range, V_I (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1)	–0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH18652A	96 mA
SN54LVTH182652A (A port or TDO)	96 mA
SN54LVTH182652A (B port)	30 mA
SN74LVTH18652A	128 mA
SN74LVTH182652A (A port or TDO)	128 mA
SN74LVTH182652A (B port)	30 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH18652A	48 mA
SN54LVTH182652A (A port or TDO)	48 mA
SN54LVTH182652A (B port)	30 mA
SN74LVTH18652A	64 mA
SN74LVTH182652A (A port or TDO)	64 mA
SN74LVTH182652A (B port)	30 mA
Input clamp current, I_{IK} ($V_I < 0$)	–50 mA
Output clamp current, I_{OK} ($V_O < 0$)	–50 mA
Package thermal impedance, θ_{JA} (see Note 3): PM package	67°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings can be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			SN54LVTH18652A		SN74LVTH18652A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			24		32	mA
I_{OL}†	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTH18652A			SN74LVTH18652A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = –3 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = –8 mA		2.4			2.4			
		I_{OH} = –24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V, V_I = V_{CC} or GND		CLK, S, TCK			±1			±1	µA
	V_{CC} = 0 or MAX‡, V_I = 5.5 V					10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	$\overline{OEBA}$, TDI, TMS			50			50	
		V_I = V_{CC}				1			1	
		V_I = 0		–25		–100	–25		–100	
		V_I = 5.5 V	OEAB	25		150	25		150	
		V_I = V_{CC}		25		100	25		100	
		V_I = 0				–5			–5	
		V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$¶	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75	150	500	75	150	500	µA
		V_I = 2 V		–75	–150	–500	–75	–150	–500	
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V	TDO			1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V	TDO			–1			–1	µA
I_{OZPU}	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{OZPD}	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{CC}	V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND		Outputs high		0.6	2		0.6	2	mA
			Outputs low		18.5	24		18.5	24	
			Outputs disabled		0.6	2		0.6	2	
ΔI_{CC}#	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND					0.5			0.5	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				10			10		pF
C_o	V_O = 3 V or 0				8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ The parameter $I_{I(hold)}$ includes the off-state output leakage current.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 15)

			SN54LVTH18652A				SN74LVTH18652A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA	0	120	0	100	0	120	0	100	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low	3.8		5		3.8		5		ns
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑	2.9		3.1		2.9		3.1		ns
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑	0.8		0.2		0.8		0.2		ns

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 15)

			SN54LVTH18652A				SN74LVTH18652A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, OEAB, $\overline{OEBA}$ or S before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, OEAB, $\overline{OEBA}$ or S after TCK↑	1.5		1		1.5		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 15)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18652A				SN74LVTH18652A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		100		120		100		120		MHz
t_{PLH}	A or B	B or A	1.5	5		5.4	1.5	4.7		5.2	ns
t_{PHL}			1.5	5		5.4	1.5	4.7		5.2	
t_{PLH}	CLKAB or CLKBA	B or A	1.5	6.9		7.5	1.5	6.5		7.1	ns
t_{PHL}			1.5	6.9		7.5	1.5	6.5		7.1	
t_{PLH}	SAB or SBA	B or A	1.5	7.9		8.7	1.5	7.5		8.4	ns
t_{PHL}			1.5	7.9		8.7	1.5	7.5		8.4	
t_{PZH}	OEAB or $\overline{OEBA}$	B or A	1.5	7.5		8	1.5	7.1		7.5	ns
t_{PZL}			1.5	7.5		8	1.5	7.1		7.5	
t_{PHZ}	OEAB or $\overline{OEBA}$	B or A	2	8.8		9.5	2	8.3		9	ns
t_{PLZ}			2	7.6		8.4	2	7		7.7	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 15)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH18652A				SN74LVTH18652A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

recommended operating conditions

			SN54LVTH182652A		SN74LVTH182652A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	A port, TDO		–24		–32	mA
		B port		–12		–12	
I_{OL}	Low-level output current	A port, TDO		24		32	mA
		B port		12		12	
I_{OL}†	Low-level output current	A port, TDO		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

† Current duty cycle ≤ 50%, f ≥ 1 kHz

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTH182652A			SN74LVTH182652A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA	A port, TDO	V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = −3 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = −8 mA		2.4			2.4			
		I_{OH} = −24 mA		2						
		I_{OH} = −32 mA					2			
		I_{OH} = −12 mA	B port	2			2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA	A port, TDO			0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
		I_{OL} = 12 mA	B port			0.8			0.8	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	CLK, S, TCK			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	$\overline{OEAB}$, TDI, TMS			50			50	
		V_I = V_{CC}				1			1	
		V_I = 0		−25		−100	−25		−100	
		V_I = 5.5 V	OEAB	25		150	25		150	
		V_I = V_{CC}		25		100	25		100	
		V_I = 0				−5	−25		−5	
		V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				1			1	
		V_I = 0				−5			−5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$¶	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75	150	500	75	150	500	µA
		V_I = 2 V		−75	−150	−500	−75	−150	−500	
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V	TDO			1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V	TDO			−1			−1	µA
I_{OZPU}	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{OZPD}	V_{CC} = 1.5 V to 0,	V_O = 0.5 V or 3 V	TDO			±50			±50	µA
I_{CC}	V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.6	2		0.6	2	mA
		Outputs low			18.5	24		18.5	24	
		Outputs disabled			0.6	2		0.6	2	
ΔI_{CC}#	V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND					0.5			0.5	mA

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ The parameter $I_{I(hold)}$ includes the off-state ouput leakage current.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	SN54LVTH182652A			SN74LVTH182652A			UNIT
		MIN	TYP†	MAX	MIN	TYP†	MAX	
C_i	V_I = 3 V or 0		4			4		pF
C_{io}	V_O = 3 V or 0		10			10		pF
C_o	V_O = 3 V or 0		8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 15)

			SN54LVTH182652A				SN74LVTH182652A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	CLKAB or CLKBA	0	120	0	100	0	120	0	100	MHz
t_w	Pulse duration	CLKAB or CLKBA high or low	3.8		5		3.8		5		ns
t_{su}	Setup time	A before CLKAB↑ or B before CLKBA↑	2.9		3.1		2.9		3.1		ns
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑	0.8		0.2		0.8		0.2		ns

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 15)

			SN54LVTH182652A				SN74LVTH182652A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	TCK	0	50	0	40	0	50	0	40	MHz
t_w	Pulse duration	TCK high or low	9.5		10.5		9.5		10.5		ns
t_{su}	Setup time	A, B, CLK, OEAB, $\overline{OEBA}$ or S before TCK↑	6.5		7		6.5		7		ns
		TDI before TCK↑	2.5		3.5		2.5		3.5		
		TMS before TCK↑	2.5		3.5		2.5		3.5		
t_h	Hold time	A, B, CLK, OEAB, $\overline{OEBA}$ or S after TCK↑	1.5		1		1.5		1		ns
		TDI after TCK↑	1.5		1		1.5		1		
		TMS after TCK↑	1.5		1		1.5		1		
t_d	Delay time	Power up to TCK↑	50		50		50		50		ns
t_r	Rise time	V_{CC} power up	1		1		1		1		µs

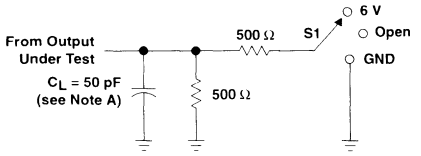
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (normal mode) (see Figure 15)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182652A				SN74LVTH182652A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	CLKAB or CLKBA		120		100		120		100		MHz
t_{PLH}	B	A	1.5	5		5.4	1.5	4.7		5.2	ns
t_{PHL}			1.5	5		5.4	1.5	4.7		5.2	
t_{PLH}	A	B	1.5	5.9		6.5	1.5	5.6		6.2	ns
t_{PHL}			1.5	5.9		6.5	1.5	5.6		6.2	
t_{PLH}	CLKBA	A	1.5	6.9		7.5	1.5	6.5		7.1	ns
t_{PHL}			1.5	6.9		7.5	1.5	6.5		7.1	
t_{PLH}	CLKAB	B	1.5	7.8		8.7	1.5	7.3		8.2	ns
t_{PHL}			1.5	7.8		8.7	1.5	7.3		8.2	
t_{PLH}	SBA	A	1.5	7.9		8.7	1.5	7.5		8.4	ns
t_{PHL}			1.5	7.9		8.7	1.5	7.5		8.4	
t_{PLH}	SAB	B	1.5	8.5		9.2	1.5	8		8.8	ns
t_{PHL}			1.5	8.5		9.2	1.5	8		8.8	
t_{PZH}	OEAB or $\overline{OEBA}$	B or A	1.5	7.9		8.6	1.5	7.4		8.1	ns
t_{PZL}			1.5	7.9		8.6	1.5	7.4		8.1	
t_{PHZ}	OEAB or $\overline{OEBA}$	B or A	2	8.8		9.5	2	8.3		9	ns
t_{PLZ}			2	7.6		8.4	2	7		7.7	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (test mode) (see Figure 15)

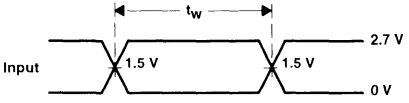
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH182652A				SN74LVTH182652A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	TCK		50		40		50		40		MHz
t_{PLH}	TCK↓	A or B	2.5	15		18	2.5	14		17	ns
t_{PHL}			2.5	15		18	2.5	14		17	
t_{PLH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PHL}			1.5	7		8	1.5	6.5		7.5	
t_{PZH}	TCK↓	A or B	4	18		21	4	17		20	ns
t_{PZL}			4	18		21	4	17		20	
t_{PZH}	TCK↓	TDO	1	6		7	1	5.5		6.5	ns
t_{PZL}			1.5	6		7	1.5	5.5		6.5	
t_{PHZ}	TCK↓	A or B	4	19		21	4	18		20	ns
t_{PLZ}			4	18		19.5	4	17		18.5	
t_{PHZ}	TCK↓	TDO	1.5	7.5		9	1.5	7		8.5	ns
t_{PLZ}			1.5	7.5		8.5	1.5	7		8	

PARAMETER MEASUREMENT INFORMATION

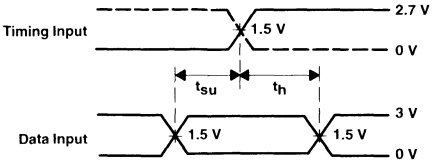


LOAD CIRCUIT

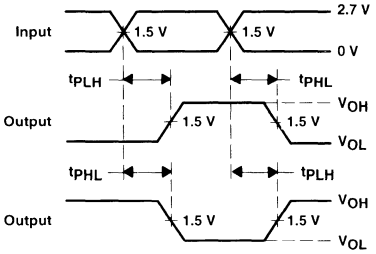
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



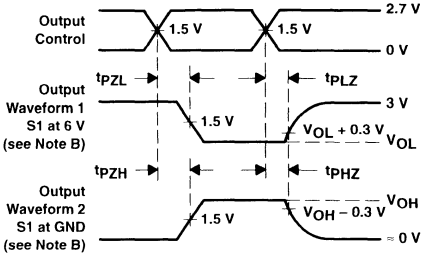
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



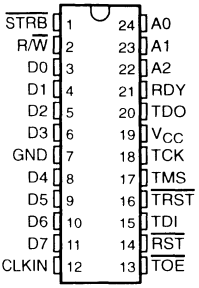
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

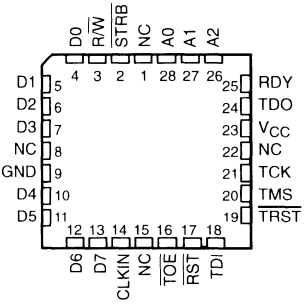
Figure 15. Load Circuit and Voltage Waveforms

- **Members of Texas Instruments (TI) Broad Family of Testability Products Supporting IEEE Std 1149.1-1990 (JTAG) Test Access Port (TAP) and Boundary-Scan Architecture**
- **Provide Built-In Access to IEEE Std 1149.1 Scan-Accessible Test/Maintenance Facilities at Board and System Levels**
- **While Powered at 3.3 V, the TAP Interface is Fully 5-V Tolerant for Mastering Both 5-V and/or 3.3-V IEEE Std 1149.1 Targets**
- **Simple Interface to Low-Cost 3.3-V Microprocessors/Microcontrollers Via 8-Bit Asynchronous Read/Write Data Bus**
- **Easy Programming Via Scan-Level Command Set and Smart TAP Control**
- **Transparently Generate Protocols to Support Multidrop TAP Configurations Using TI's Addressable Scan Port**
- **Flexible TCK Generator Provides Programmable Division, Gated-TCK, and Free-Running-TCK Modes**
- **Discrete TAP Control Mode Supports Arbitrary TMS/TDI Sequences for Non-Compliant Targets**
- **Programmable 32-Bit Test Cycle Counter Allows Virtually Unlimited Scan/Test Length**
- **Accommodate Target Retiming (Pipeline) Delays of Up to 15 TCK Cycles**
- **Test Output Enable ($\overline{TOE}$) Allows for External Control of TAP Signals**
- **High-Drive Outputs (–32-mA I_{OH}, 64-mA I_{OL}) at TAP Support Backplane Interface and/or High Fanout**
- **Package Options Include Plastic Small-Outline (DW) Package, Ceramic Chip Carriers (FK), and Ceramic 300-mil DIPs (JT)**

SN54LVT8980 . . . JT PACKAGE
SN74LVT8980 . . . DW PACKAGE
(TOP VIEW)



SN54LVT8980 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

The 'LVT8980 embedded test-bus controllers (eTBC) are members of the TI broad family of testability integrated circuits. This family of devices supports IEEE Std 1149.1-1990 boundary scan to facilitate testing of complex circuit assemblies. Unlike most other devices of this family, the eTBC is not a boundary-scannable device; rather, its function is to master an IEEE Std 1149.1 (JTAG) test access port (TAP) under the command of an embedded host microprocessor/microcontroller. Thus, the eTBC enables the practical and effective use of the IEEE Std 1149.1 test-access infrastructure to support embedded/built-in test, emulation, and configuration/maintenance facilities at board and system levels.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

description (continued)

The eTBC masters all TAP signals required to support one 4- or 5-wire IEEE Std 1149.1 serial test bus – test clock (TCK), test mode select (TMS), test data input (TDI), test data output (TDO), and test reset ($\overline{TRST}$). All such signals can be connected directly to the associated target IEEE Std 1149.1 devices without need for additional logic or buffering. However, as well as being directly connected, the TMS, TDI, and TDO signals can be connected to distant target IEEE Std 1149.1 devices via a pipeline, with a retiming delay of up to 15 TCK cycles; the eTBC automatically handles all associated serial-data justification.

Conceptually, the eTBC operates as a simple 8-bit memory- or I/O- mapped peripheral to a microprocessor/microcontroller (host). High-level commands and parallel data are passed to/from the eTBC via its generic host interface, which includes an 8-bit data bus (D7–D0) and a 3-bit address bus (A2–A0). Read/write select (R/$\overline{W}$) and strobe ($\overline{STRB}$) signals are implemented so that the critical host-interface timing is independent of the CLKIN period. An asynchronous ready (RDY) indicator is provided to hold off, or insert wait states into, a host read/write cycle when the eTBC cannot respond immediately to the requested read/write operation.

High-level commands are issued by the host to cause the eTBC to generate the TMS sequences necessary to move the test bus from any stable TAP-controller state to any other such stable state, to scan instruction or data through test registers in target devices, and/or to execute instructions in the Run-Test/Idle TAP state. A 32-bit counter can be programmed to allow a predetermined number of scan or execute cycles.

During scan operations, serial data that appears at the TDI input is transferred into a serial-to-4 × 8-bit-parallel first-in/first-out (FIFO) read buffer, which can then be read by the host to obtain the return serial-data stream up to eight bits at a time. Serial data that is to be transmitted from the TDO output is written by the host, up to eight bits at a time, to a 4 × 8-bit-parallel-to-serial FIFO write buffer.

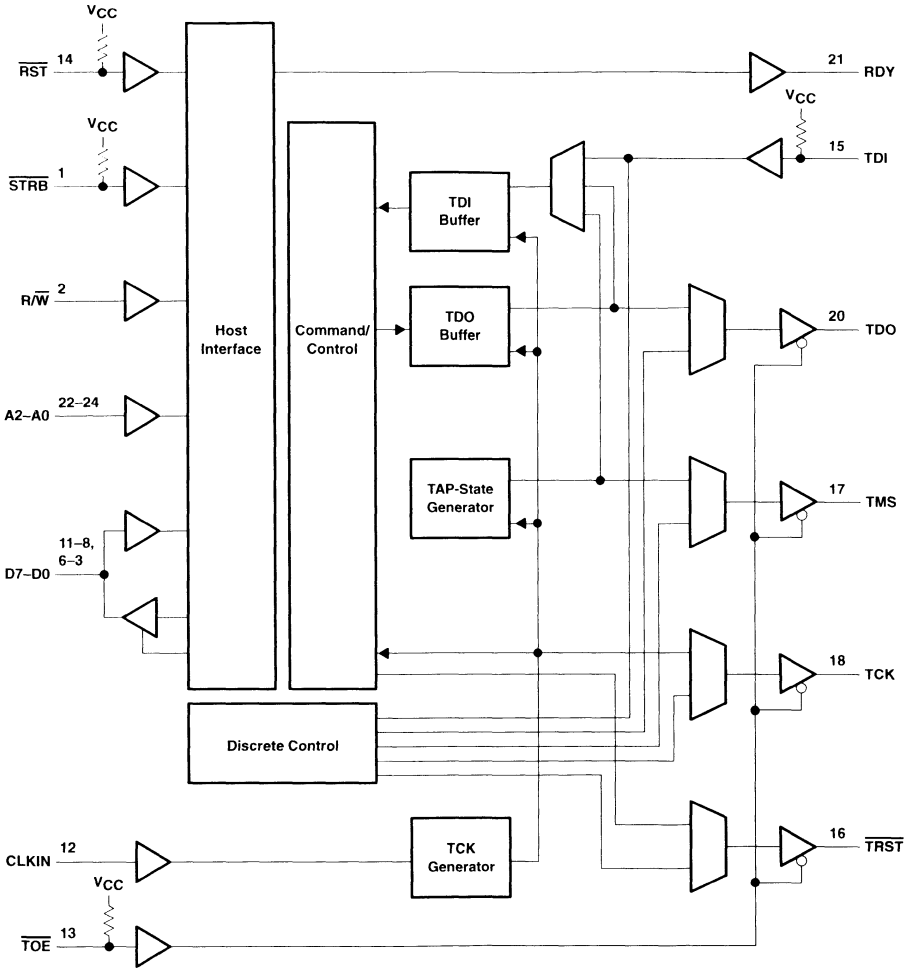
In addition to such simple state-movement, scan, and run-test operations, the eTBC supports several additional commands that provide for input-only scans, output-only scans, recirculate scans (in which TDI is mirrored back to TDO), and a scan mode that generates the protocols used to support multidrop TAP configurations using TI's addressable scan port. Two loopback modes also are supported that allow the microprocessor/microcontroller host to monitor the TDO or TMS data streams output by the eTBC.

The eTBC's flexible clocking architecture allows the user to choose between free-running (in which the TCK always follows CLKIN) and gated modes (in which the TCK output is held static except during state-move, run-test, or scan cycles) as well as to divide down TCK from CLKIN. A discrete mode is also available in which the TAP is driven strictly by read/write cycles under full control of the microprocessor/microcontroller host. These features ensure that virtually any IEEE Std 1149.1 target device or device chain – even where such may not fully comply to IEEE Std 1149.1 – can be serviced by the eTBC.

While most operations of the eTBC are synchronous to CLKIN, a test-output enable ($\overline{TOE}$) is provided for output control of the TAP outputs, and a reset ($\overline{RST}$) input is provided for hardware reset of the eTBC. The former can be used to disable the eTBC so that an external controller can master the associated IEEE Std 1149.1 test bus.

The SN54LVT8980 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT8980 is characterized for operation from –40°C to 85°C.

functional block diagram



Pin numbers shown are for the DW and JT packages.

Terminal Functions

TERMINAL NAME	DESCRIPTION
A2–A0	Address inputs. A2–A0 form the 3-bit address bus that interfaces the eTBC to its microprocessor/microcontroller host. These inputs directly index the eTBC register to be accessed (read from or written to).
CLKIN	Clock input. CLKIN is the system clock input for the eTBC. Most operations of the eTBC are synchronous to CLKIN. Internally, the CLKIN signal is divided by a programmable divisor to generate TCK.
D7–D0	Data inputs/outputs. D7–D0 form the 8-bit bidirectional data bus that interfaces the eTBC to its microprocessor/microcontroller host. Data in the eTBC registers is accessed (read or written) using this data bus. D7 is considered the most-significant bit, while D0 is considered the least-significant bit.
GND	Ground
RDY	Ready output. RDY is used to indicate to the microprocessor/microcontroller host whether or not the eTBC is ready to service the access (read or write) operation that is currently being requested. If RDY remains high following the initiation of an access cycle ($\overline{STRB}$ negative edge) then the eTBC is ready. Otherwise, if RDY goes low following the initiation of an access cycle ($\overline{STRB}$ negative edge) then the eTBC is not ready. In cases where the eTBC is not ready, subsequent processing in the eTBC may clear the not-ready state, which allows RDY to return high before the end of the access cycle. In any event, the RDY output returns high upon the termination of any access cycle ($\overline{STRB}$ positive edge).
$\overline{RST}$	Reset input. $\overline{RST}$ is used to initiate asynchronous reset of the eTBC. Assertion (low) of $\overline{RST}$ places the eTBC in a reset state from which it does not exit until $\overline{RST}$ is released (high). While $\overline{RST}$ is low, the eTBC ignores host writes, the RDY, TDO, TMS, and $\overline{TRST}$ outputs are high, while TCK outputs CLKIN/16. An internal pullup forces $\overline{RST}$ to a high level if it has no external connection.
R/$\overline{W}$	Read/write select. R/$\overline{W}$ is used by the microprocessor/microcontroller host to instruct the eTBC as to whether it is to perform read access (R/$\overline{W}$ high) or write access (R/$\overline{W}$ low). While R/$\overline{W}$ is high and $\overline{STRB}$ is low, the D7-D0 outputs are enabled to drive low and/or high logic levels onto the host data bus. Otherwise, while R/$\overline{W}$ is low, the D7–D0 outputs are disabled to a high-impedance state so that the host data bus can drive to the eTBC.
$\overline{STRB}$	Read/write strobe. $\overline{STRB}$ is used by the microprocessor/microcontroller host to instruct the eTBC to initiate ($\overline{STRB}$ negative edge) or terminate/conclude ($\overline{STRB}$ positive edge) an access (read or write) operation. An internal pullup forces $\overline{STRB}$ to a high level if it has no external connection.
TCK	Test clock. TCK transmits the TCK signal required by the eTBC's IEEE Std 1149.1 target(s). All operations of the TAP are synchronous to TCK. Generally, the TCK signal is generated internally by the eTBC by division of CLKIN by a programmable divisor. Alternatively, when the eTBC is in its discrete-control mode, a rising edge of TCK is generated on a read to the discrete-control register, while a falling edge is generated on a write to the discrete-control register.
TDI	Test data input. TDI receives the TDI signal output by the eTBC's IEEE Std 1149.1 target(s). It is the serial input for shifting test data from the target(s); it is sampled on the rising edge of TCK and is expected to be transferred from the target(s) on the falling edge of TCK. An internal pullup forces TDI to a high level if it has no external connection.
TDO	Test data output. TDO transmits the TDO signal required by the eTBC's IEEE Std 1149.1 target(s). It is the serial output for shifting test data to the target(s); it is transferred on the falling edge of TCK and is sampled in the target on the rising edge of TCK.
TMS	Test mode select. TMS transmits the TMS signal required by the eTBC's IEEE Std 1149.1 target(s). It is the one control signal that directs the next TAP-controller state of the target(s). It is transferred from the eTBC on the falling edge of TCK and is sampled in the target(s) on the rising edge of TCK.
$\overline{TOE}$	Test-output enable. $\overline{TOE}$ is the active-low output enable for the eTBC TAP outputs (TCK, TDO, TMS, $\overline{TRST}$). When $\overline{TOE}$ is inactive (high) the TAP outputs are disabled to a high-impedance state. Otherwise, when $\overline{TOE}$ is active (low), the TAP outputs are enabled to drive low and/or high logic levels according to other eTBC functions. An internal pullup forces $\overline{TOE}$ to a high level if it has no external connection.
$\overline{TRST}$	Test reset. $\overline{TRST}$ transmits the $\overline{TRST}$ signal that may be required by some of the eTBC's IEEE Std 1149.1 target(s). A low signal at $\overline{TRST}$ is intended to initiate asynchronous test reset of the connected target(s). Such a low signal at $\overline{TRST}$ is generated only when the microprocessor/microcontroller host writes an appropriate value into the eTBC command register or, while the eTBC is in discrete-control mode, into the discrete-control register.
V_{CC}	Supply voltage

application information

In application, the eTBC is used to master a single IEEE Std 1149.1 TAP under the control of a microprocessor/microcontroller host. A typical implementation is shown in Figure 1.

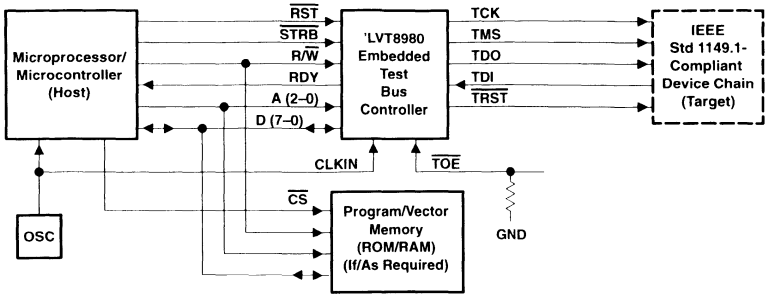


Figure 1. eTBC Application

All signals required to master IEEE Std 1149.1-compliant devices – TCK, TMS, TDO, TDI – are sourced/received by the eTBC. The eTBC can also source the optional $\overline{\text{TRST}}$ signal. Additionally, the eTBC implements high-drive output buffers, allowing it to interface directly to on- or off-board targets without need for buffering or other additional logic.

The eTBC's generic host interface allows it to act as a simple 8-bit memory- or I/O-mapped peripheral. As shown in Figure 1, for many choices of host microprocessor/microcontroller, this interface can be accomplished without additional logic. While the eTBC requires a clock input (CLKIN), in many cases it can be driven from the same source that provides a clock signal to the host.

Thus, in combination with the host microprocessor/microcontroller, the eTBC can be used to implement a two-chip embedded test-control function supporting board- and system-level built-in test based on structured IEEE Std 1149.1 test access. In some cases, for additional program and/or test vector storage, an external ROM/RAM may be required.

By use of the eTBC in such an embedded test control function, the host microprocessor/microcontroller is freed from the burden of generating the TAP-state sequences, serializing the outgoing bit stream, and deserializing the incoming bit stream. All such tasks are implemented in the eTBC, allowing the host to operate at full 8-bit parallel efficiency, host software to operate at the level of discrete scan operations versus the level of TAP manipulation, and test throughput to be maximized. The eTBC's full suite of data-scan and instruction-scan commands ensure that the host software operates efficiently.

Host efficiency and flexibility is also maximized through the eTBC's fully visible status and implementation of the ready output (RDY). RDY goes inactive during a read or write access if the host-requested access cannot be performed immediately. Thus, it can be used to insert hold or wait states back to the host. When the condition blocking the access clears, the requested access completes. Additionally, all conditions that can cause such a blocking condition are continuously updated in the eTBC status and command registers. Thus, the host software can poll the eTBC status rather than implement RDY in hardware.

application information (continued)

The eTBC also provides several capabilities that support special target application requirements. The eTBC's test-output enable allows its master function to be disabled so that another device (an external tester, for example) can control the target TAP. Where required, due to target non-compliance or sensitivity to state sequencing, discrete-control mode provides the host software with arbitrary control of TMS and TDO sequences. Also, where targets may be sensitive to leaving Shift-DR state during scan operation, gated-TCK mode allows the TCK output to be stopped, rather than cycling the target TAP state to Pause-DR state, when service to TDI buffer or TDO buffer is required.

Where target devices are extremely distant (due to cabling, etc.), pipelining may be implemented at intervals along the incoming or outgoing paths to retime (deskew) the TDI, TDO, and TMS signals. An example is shown in Figure 2. In such applications, the eTBC can automatically adjust the incoming test-data bit stream to account for cycle delays introduced by the pipeline.

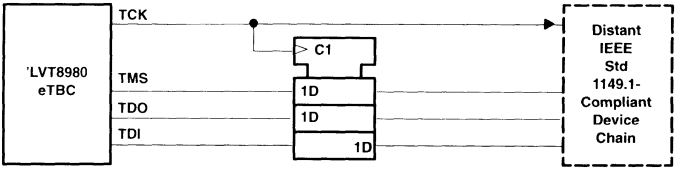


Figure 2. Retimed Interface to Target

Also, in gated-TCK mode, special scan commands provide transparent support for addressable shadow protocols. Thus, in conjunction with its high-drive outputs, the eTBC can fully support multidrop backplane TAP configurations implemented with TI's addressable scan ports (ASP). Figure 3 shows a multidrop TAP configuration in a passive-backplane application implemented with a centralized (one eTBC per chassis/rack) test-control architecture, while Figure 4 shows a passive-backplane application implemented with a distributed (eTBC per module) test-control architecture. Figure 5 shows a multidrop TAP configuration in an active-backplane (motherboard) application.

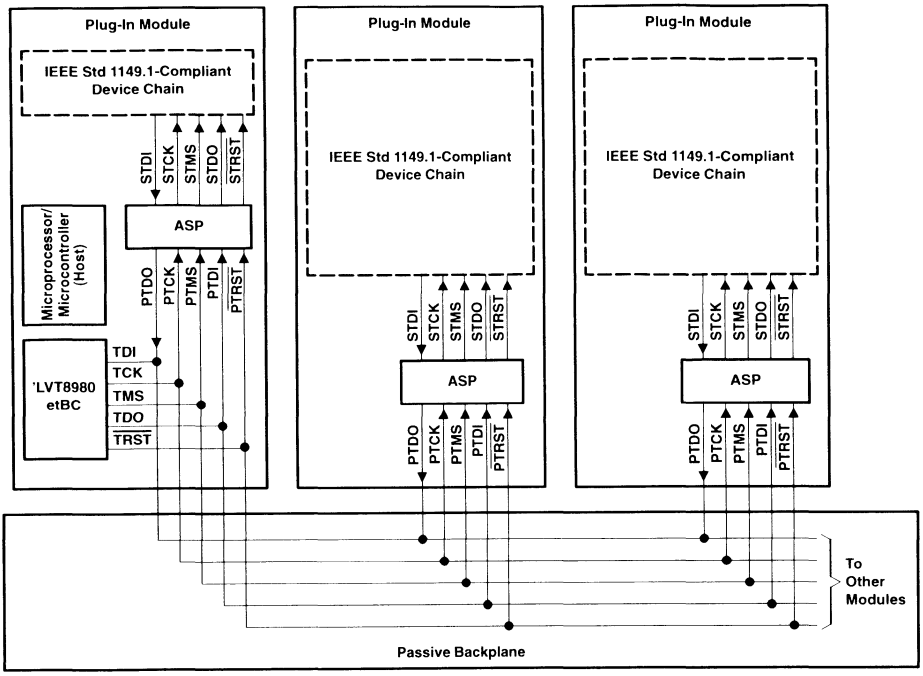


Figure 3. Passive-Backplane Application With Centralized (eTBC Per Chassis) Test-Control Architecture

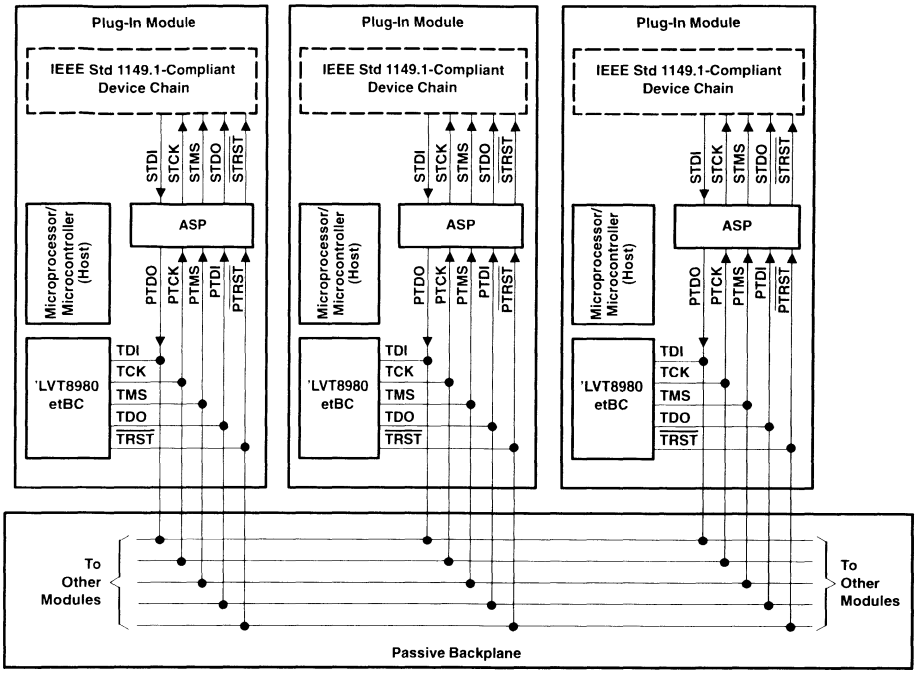


Figure 4. Passive-Backplane Application With Distributed Test-Control (eTBC Per Card) Architecture

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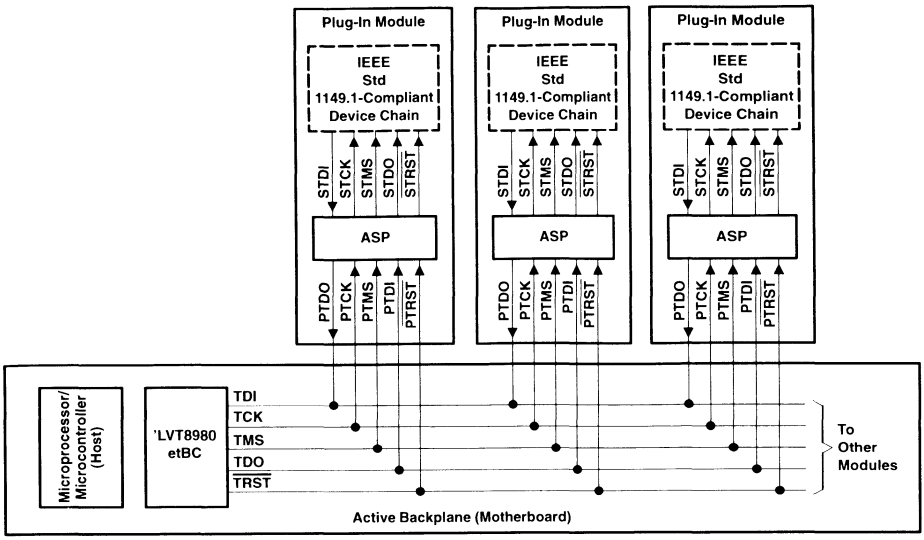


Figure 5. Active-Backplane (Motherboard) Application

architecture

Conceptually, the eTBC can be viewed as an IEEE Std 1149.1 coprocessor/accelerator that operates in conjunction with (and under the control of) a host microprocessor/microcontroller. The eTBC implements this function using an 8-bit generic host interface and a scan-test-based command/control architecture. As shown in the functional block diagram, beyond these fundamental elements and another central block supporting discrete-control mode, the eTBC functions are accomplished in four additional blocks – one for each of the required TAP signals – a TCK generator, a TAP-state (TMS) generator, a TDO buffer, and a TDI buffer.

host interface

The eTBC host interface is implemented generically on an 8-bit read/write data bus (D7–D0). Three address pins (A2–A0) directly index the eTBC's eight read/write registers: configurationA, configurationB, status, command, TDO buffer, TDI buffer, counter, and discrete control. The register address map is given in Table 1.

host access timing

Host access timing is asynchronous to the clock input (CLKIN) and is fully controlled by the read/write strobe ($\overline{\text{STRB}}$). The read/write select (R/$\overline{\text{W}}$) serves to control the direction of data flow on the bidirectional data bus. Figure 6 shows the read access timing while Figure 7 shows the write access timing. As shown, for either read or write access, R/$\overline{\text{W}}$ and address signals should be held while $\overline{\text{STRB}}$ is low.

For read access (R/$\overline{\text{W}}$ high) the eTBC data bus outputs are made active, on the falling edge of $\overline{\text{STRB}}$, to drive the data contained in the selected eTBC register. Otherwise, when $\overline{\text{STRB}}$ is high, the eTBC data outputs are at high impedance. Therefore, in many applications, the R/$\overline{\text{W}}$ signal can be shared in common with other host peripherals (ROM or RAM, for example) while the $\overline{\text{STRB}}$ signal is generated separately (by discrete chip-select signals available from the host or a decode logic) for each required peripheral.

host access timing (continued)

For write access (R/$\overline{W}$ low), the eTBC data outputs remain at high impedance independent of $\overline{STRB}$. The address of the register to be written is latched from the address pins on the falling edge of $\overline{STRB}$, while the data to be written is latched from the data bus on the rising edge of $\overline{STRB}$.

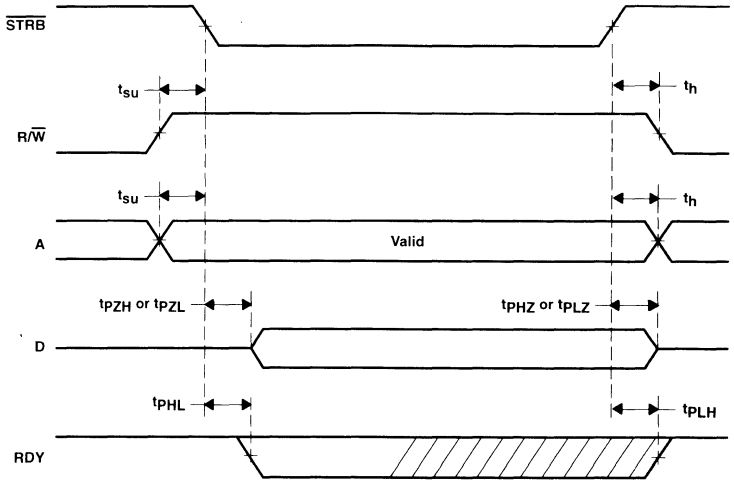


Figure 6. Read Access Timing

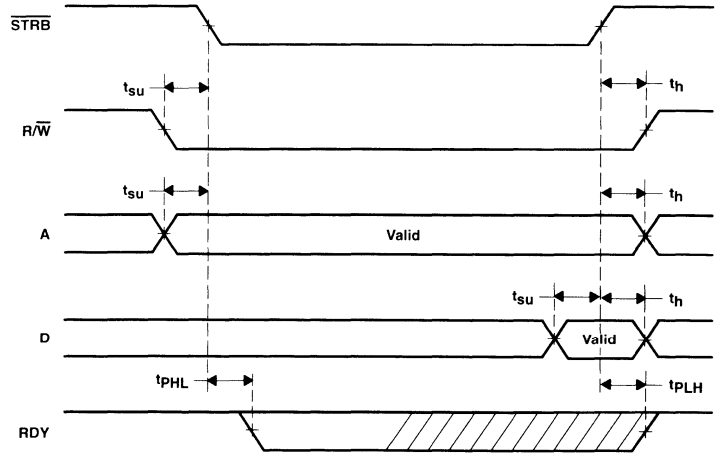


Figure 7. Write Access Timing

ready output

The ready output (RDY) from the host interface can be used, where the selected microprocessor/microcontroller supports it, to insert wait or hold states back to the host. If a host-requested access cannot be performed immediately, RDY goes inactive (low) during that given access. When the condition blocking the access clears, RDY goes active (high) and the eTBC grants the requested access. Alternatively, where such hardware-generated hold or wait states are not supported in the selected microprocessor/microcontroller host, the eTBC status and/or command registers can be polled to determine its readiness to grant a given read or write access.

Conditions that cause a host access to be blocked (and RDY to become inactive) are limited to the following:

- While the TDI buffer is empty, as indicated in status register (bit 7, TDIS), a requested read to TDI-buffer register generates RDY inactive; this condition clears, RDY goes active, and the requested access completes, when the TDI buffer is no longer empty.
- While the TDO buffer is full or is being reset upon initiation of a scan command, as indicated in status register (bit 6, TDOS), a requested write to TDO-buffer register generates RDY inactive; this condition clears, RDY goes active, and the requested access completes, when the TDO buffer is no longer full or the TDO-buffer reset completes, as applicable.
- While a command is in progress, as indicated by a non-zero value in the opcode field (bits 3–0, OPCOD) of the command register, a requested write to command, configurationA, configurationB, or counter registers generates RDY inactive. This condition clears, RDY goes active, and the requested access is complete, when the previously specified command finishes. The sole exception is the writing of a logic 1 into the software reset (bit 7, SWRST) bit of the command register, which is never blocked.
- While a full-duplex scan command is in progress, and the number of retiming-delay bits is other than zero, the number of writes to TDO-buffer register may not exceed, by more than 5, the number of reads to TDI-buffer register. A write to TDO-buffer register that does exceed this limit is blocked, and generates RDY inactive, indefinitely; the TDI-buffer register must be read before another write to TDO-buffer register.

register descriptions

A summary of the eTBC registers, their address mappings, bit assignments, reset values, and host accessibility (read/write or read-only) is provided in Table 1. All registers are fully readable by the host. All registers are fully writeable by the host with the exception of the status and TDI-buffer registers. Also, with the exception of TDO-buffer and command registers, writes to any register while a command is in progress are held off (RDY inactive) or ignored. Bits designated as reserved should be written to logic 0; read-only bits designated as reserved always read logic 0.

Table 1. Register Summary

ADDRESS A2–A0	REGISTER	REGISTER DETAIL (BIT ASSIGNMENTS)								RESET VALUE	HOST ACCESS
		BIT 7 (MSB)	BIT 6	BIT 5	BIT 4	BIT 3	BIT 2	BIT 1	BIT 0 (LSB)		
000	ConfigurationA	Reserved		NTOE	LPBK		MODE			0x00	R/W
001	ConfigurationB	CDIV			Reserved	RDLY				0x80	R/W
010	Status	TDIS	TDOS	CTRS	Reserved	TAPST				0x00	R
011	Command	SWRST	NTRST	ENDST		OPCOD				0x00	R/W
100	TDO buffer									0x00	R/W
101	TDI buffer									0x00	R
110	Counter									0x00	R/W
111	Discrete control	Reserved				DNTR	DTMS	DTDI	DTDO	0x00	R/W

configuration registers

All eTBC test commands operate under the influence of the configurationA and configurationB registers. The decodes of the various bit groups assigned to these registers are given in Table 2 and Table 3, respectively. These registers are fully readable at all times and are fully writeable except when an eTBC command is in progress. Bit group values designated as reserved should not be written.

Table 2. ConfigurationA Register Decode

CONFIGURATIONA		VALUE	RESULT
BIT GROUP	BIT NO.		
NTOE	5	0	TAP outputs (TCK, TDO, TMS, $\overline{TRST}$) are enabled.
		1	TAP outputs (TCK, TDO, TMS, $\overline{TRST}$) are disabled (high impedance).
LPBK	4–3	00	No loopback – TDI pin inputs to TDI buffer.
		01	TMS loopback – TAP-state generator inputs to TDI buffer. TMS and TDO pins are fixed high.
		10	TDO loopback – TDO buffer inputs to TDI buffer. TMS and TDO pins are fixed high.
		11	Reserved
MODE	2–0	000	Automatic/free-running-TCK mode – all TAP outputs are generated autonomously in the eTBC according to the active command. The TCK output runs continuously; while operating a scan command, if the TDI buffer becomes full and/or the TDO buffer becomes empty, the TAP state is cycled to Pause-DR or Pause-IR, as appropriate, until the host performs the required buffer service.
		001	Automatic/gated-TCK mode – all TAP outputs are generated autonomously in the eTBC according to the active command. The TCK output is run only when required to move TAP state or to progress run-test or scan operations, otherwise, it is gated off (low); while operating a scan command, if the TDI buffer becomes full and/or the TDO buffer becomes empty, the TAP state remains in Shift-IR or Shift-DR, as appropriate, but the TCK output is gated off until the host performs the required buffer service.
		010	Discrete-control mode – all TAP outputs are determined by contents of the discrete-control register under control of host software.
		011–111	Reserved

Table 3. ConfigurationB Register Decode

CONFIGURATIONB		VALUE	RESULT
BIT GROUP	BIT NO.		
CDIV	7–5	000–111	TCK = (CLKIN)/(2^{CDIV}); reset value TCK = (CLKIN)/(2^4) = CLKIN/16
RDLY	3–0	0000–11 11	Number of retiming delays to accommodate = RDLY; while operating a scan command, TDI sampling is delayed by a number of TCK cycles, equal to RDLY, following the generation of Shift-DR or Shift-IR state, as appropriate.

The negated test-output-enable ($\overline{TOE}$) bit allows the host to disable the TAP outputs via software in a manner analogous to the hardware $\overline{TOE}$. The loopback (LPBK) bit group allows the selection of the source of data to be input to the TDI buffer – from the TDI pin for normal eTBC operations or, for eTBC verification purpose, from TAP-state (TMS) generator or TDO buffer. The test mode (MODE) bit group provides a choice of automatic/free-running-TCK, automatic/gated-TCK, or discrete-control modes.

The clock-divisor (CDIV) bit group allows software control of the TCK output frequency based on a division of the CLKIN input. Divisors from 2^0 (1) to 2^7 (128) are provided. The clock divisor defaults to 2^4 (16) on eTBC reset (power-up, hardware-initiated, or software-initiated). The retiming-delay (RDLY) bit group provides for the automatic accommodation of retiming (pipeline) delays, which can be used to deskew the TAP signals to target scan chains that are electrically distant (due to cabling delays, etc).

status register

The status of the eTBC is fully reported and continuously updated in the status register. The decode of the various bit groups assigned to the status register is given in Table 4.

Table 4. Status Register Decode

STATUS		VALUE	RESULT
BIT GROUP	BIT NO.		
TDIS	7	0	The TDI buffer is empty – no TDI data is available for host read.
		1	The TDI buffer is not empty – at least one byte of TDI data is available for host read.
TDOS	6	0	The TDO buffer is not full – at least one byte in TDO buffer is available for host write.
		1	The TDO buffer is full – no bytes in TDO buffer are available for host write.
CTRS	5	0	The counter is not loaded with a complete 32-bit value – command operation cannot begin until counter load completes.
		1	The counter is loaded with a complete 32-bit value – command operation can begin.
TAPST	3–0	0000	The current target TAP state (as sent by eTBC) is Test-Logic-Reset.
		0001	The current target TAP state (as sent by eTBC) is Select-DR-Scan.
		0010	The current target TAP state (as sent by eTBC) is Capture-DR.
		0011	The current target TAP state (as sent by eTBC) is Shift-DR.
		0100	The current target TAP state (as sent by eTBC) is Exit1-DR.
		0101	The current target TAP state (as sent by eTBC) is Pause-DR.
		0110	The current target TAP state (as sent by eTBC) is Exit2-DR.
		0111	The current target TAP state (as sent by eTBC) is Update-DR.
		1000	The current target TAP state (as sent by eTBC) is Run-Test/Idle.
		1001	The current target TAP state (as sent by eTBC) is Select-IR-Scan.
		1010	The current target TAP state (as sent by eTBC) is Capture-IR.
		1011	The current target TAP state (as sent by eTBC) is Shift-IR
		1100	The current target TAP state (as sent by eTBC) is Exit1-IR.
		1101	The current target TAP state (as sent by eTBC) is Pause-IR.
		1110	The current target TAP state (as sent by eTBC) is Exit2-IR.
		1111	The current target TAP state (as sent by eTBC) is Update-IR.

The TDI-buffer-status (TDIS) bit reports the readiness of the TDI buffer to respond to a host read. The TDO-buffer-status (TDOS) bit reports the readiness of the TDO buffer to respond to a host write. The counter-status (CTRS) bit reports the readiness of the counter to support a command that uses the counter. The current-TAP-state (TAPST) bit group continuously reports the target TAP state as monitored by the eTBC.

command register

The command register is used to perform software reset of the eTBC, to discretely control the state of the TRST output when not in discrete-control mode, and to initiate test operations in the target(s).The decode of the various bits assigned to the command register is given in Table 5.

Any read to the command register while a command is in progress returns the value written to the command register upon initiation of the command. Once a command finishes, the operation-code (OPCOD) bit group in the command register is reset to null. In this way, the status of a requested command can be monitored/polled by the host.

With the exception of the software-reset (SWRST) bit, which can be written at any time, writes to the command register while a command is in progress causes RDY inactive and is ignored if the write cycle is terminated before the previously requested command finishes.

Table 5. Command Register Decode

COMMAND		VALUE	RESULT	TEST OPERATION COMMENTS			
BIT GROUP	BIT NO.			WORKING TAP STATE	USES COUNTER	USES TDI BUFFER	USES TDO BUFFER
SWRST	7	0	Normal operation				
		1	Full reset				
TRST	6	0	If not in discrete-control mode, output high to $\overline{\text{TRST}}$ pin				
		1	If not in discrete-control mode, output low to $\overline{\text{TRST}}$ pin				
ENDST	5–4	00	Finish command in TAP state Test-Logic-Reset				
		01	Finish command in TAP state Run-Test/Idle				
		10	Finish command in TAP state Pause-DR				
		11	Finish command in TAP state Pause-IR				
OPCOD	3–0	0000	Null				
		0001	Reserved				
		0010	Execute run test	Run-Test/Idle	Yes	No	No
		0011	Execute input-only ASP scan	N/A	Yes	Yes	No
		0100	Execute ASP scan	N/A	Yes	Yes	Yes
		0101	Execute output-only ASP scan	N/A	Yes	No	Yes
		0110	Execute state move	N/A	No	No	No
		0111	Execute state jump	N/A	No	No	No
		1000	Execute instruction-register scan	Shift-IR	Yes	Yes	Yes
		1001	Execute data-register scan	Shift-DR	Yes	Yes	Yes
		1010	Execute input-only instruction-register scan	Shift-IR	Yes	Yes	No
		1011	Execute input-only data-register scan	Shift-DR	Yes	Yes	No
		1100	Execute output-only instruction-register scan	Shift-IR	Yes	No	Yes
		1101	Execute output-only data-register scan	Shift-DR	Yes	No	Yes
		1110	Execute recirculate instruction-register scan	Shift-IR	Yes	Yes	No
		1111	Execute recirculate data-register scan	Shift-DR	Yes	Yes	No

The software-reset (SWRST) bit is provided to allow software initiation of full eTBC reset. This bit of the command register can be written at any time, regardless of the configuration or command in progress. The test-reset (TRST) bit allows direct software control of the state of $\overline{\text{TRST}}$ output in modes other than discrete control.

The end-TAP-state (ENDST) bit group determines the TAP state in which the target scan chain is left when the requested command finishes. The operation-code (OPCOD) bit group determines the test operation to be executed in the target.

counter register

The counter register, while only 8 bits wide like any other eTBC register, provides read/write access to the full 32-bit eTBC counter. Writes to the counter register are accomplished by four complete host access cycles, otherwise the counter is considered unloaded (CTRS = 0). Reads to the counter register likewise are accomplished by four complete host access cycles. However, reads do not affect the counter-loaded status (CTRS). The counter access (both read and write) is in least-significant-byte-first order. Any writes to the counter register while a command is in progress are ignored. The 32-bit value present in the counter at initiation of a command is used to determine the number of TCK cycles or scan bits for which the command is operated.

TDO-buffer register

The TDO-buffer register, while only 8 bits wide like any other eTBC register, provides write access to the full 4×8 (32-bit) FIFO that comprises the TDO buffer. The TDO-buffer register can be written as long as the TDO buffer does not become full. When the TDO buffer becomes full, further writes to the TDO-buffer register cause RDY inactive (and consequent hold or wait states to be sent back to the host, if supported) and cause the write to be ignored if the write cycle is terminated before the TDO-buffer-full status is cleared.

TDI-buffer register

The TDI-buffer register, while only 8 bits wide like any other eTBC register, provides read access to the full 4×8 (32-bit) FIFO that comprises the TDI buffer. The TDI-buffer register can be read as long as the TDI buffer does not become empty. When the TDI buffer becomes empty, further reads to the TDI-buffer register cause RDY inactive (and consequent hold or wait states to be sent back to the host, if supported) and cause the read data to be invalid if the read cycle is terminated before the TDI-buffer-empty status is cleared.

discrete-control register

The discrete-control register is used to program the state of the TAP outputs (TCK, TDO, TMS, $\overline{\text{TRST}}$) and to poll the state of the TAP input (TDI) when the eTBC is in its discrete-control mode. The contents of the discrete-control register determine values output to TDO, TMS, and $\overline{\text{TRST}}$ according to the decode in Table 6. The TCK output is generated on each read and write to the discrete-control register; writes generate TCK falling edge, while reads generate TCK rising edge. In modes other than the discrete-control mode, this register is fully writeable and readable, but writes and reads have no effect on eTBC or target operation.

Table 6. Discrete-Control Register Decode

DISCRETE CONTROL		VALUE	RESULT
BIT GROUP	BIT NO.		
DNTR	3	0	If in discrete-control mode, output low to $\overline{\text{TRST}}$ pin, otherwise nothing
		1	If in discrete-control mode, output high to $\overline{\text{TRST}}$ pin, otherwise nothing
DTMS	2	0	If in discrete-control mode, output low to TMS pin, otherwise nothing
		1	If in discrete-control mode, output high to TMS pin, otherwise nothing
DTDI	1	0	The TDI data received is a logic 0.
		1	The TDI data received is a logic 1.
DTDO	0	0	If in discrete-control mode, output low to TDO pin, otherwise nothing
		1	If in discrete-control mode, output high to TDO pin, otherwise nothing

command/control

The eTBC's command-based architecture is structured around a set of comprehensive IEEE Std 1149.1 (JTAG) test objectives, which include TAP state movement, scan operations, and run test (operation of test logic in Run-Test/Idle state). The set of test operations, as decoded from the command register (bits 3–0, OPCOD) is given in Table 5. Commands are initiated by writing the eTBC command register; upon command initiation, the test-control logic is initialized and the TDO and TDI buffers are cleared. Command completion is indicated when the operation code (OPCOD) field of the command register returns to the value of the null command.

The eTBC command operation is modified by the configurationA, and configurationB registers, which should be written prior to writing the command register, as the values in these registers cannot be modified while a command is in progress. Also, commands are only operated in automatic test modes, as specified in the configurationA register (bits 2–0, MODE) – while in the discrete-control mode, commands are ignored.

All eTBC commands operate similarly to accomplish IEEE Std 1149.1 test objectives. First, the eTBC generates a TMS sequence to move the target scan chain from its current TAP state to a working state that depends on the test objective. Second, the command is operated (test run, bits scanned) in the working state for a number of TCK cycles (or scan bits) determined by the value of the counter upon command initiation. Third, the eTBC generates a TMS sequence to move the target scan chain from the working state to the end state specified in the command register (bits 5–4, ENDST). For some commands, one or more of these steps are omitted.

TAP-state-movement commands

Two eTBC commands are provided to accomplish TAP state movement. The state-move command operates to generate a TMS sequence to move the target scan chain directly from its current TAP state to the end state specified in the command register. The state-jump command moves the eTBC's stored value of the target TAP state without generating any changes to the TMS output. The state-jump command can therefore be used to switch between targets that share the same test bus, such as those in a multidrop backplane configuration implemented with TI addressable scan ports, but that may be left in different TAP states.

run-test command

The run-test command allows the test logic of the target scan chain to execute autonomously in the Run-Test/Idle TAP state. Such test logic is commonly used to implement chip- or board-level built-in self test. The run-test command generates TMS sequences to move the target scan chain from its current TAP state to the Run-Test/Idle TAP state where it remains for a number of TCK cycles determined by the value of the counter upon command initiation. Upon the countdown of the counter to zero, the eTBC generates TMS sequences to move the target scan chain to the end state specified in the command register.

scan commands

Eleven eTBC commands are provided to perform scan operations to target scan chains. These can be classified by the destination of scan data in the target – addressable scan port (ASP), IEEE Std 1149.1 instruction register, or IEEE Std 1149.1 data register – and by the nature/direction of the data transfer – full-duplex (default), input-only, output-only, or recirculate. The only combination of these two factors that is not implemented is recirculate ASP scan.

addressable scan port (ASP) scan commands

The ASP scan commands scan data to and/or from an addressable scan port target. Since ASP devices require that TMS remain fixed throughout their select and acknowledge protocols, the eTBC does not generate TMS sequences or change its stored value of the target's TAP state. Also, for the same reason, ASP scan commands that target ASP devices should be operated in gated-TCK mode. The ASP scan commands do allow data written to the TDO buffer to be driven serially onto the TDO pin and bits received serially at the TDI pin to be stored into the TDI buffer for reading by the host. However, the ASP scan commands do not perform any bit-pair encoding of ASP select protocols or decoding of ASP acknowledge protocols. Such encoding/decoding must be performed in the host. The number of data bits transferred in and/or out is determined by the value of the counter upon command initiation.

instruction-register scan commands

The instruction-register scan commands scan bits to and/or from the concatenation of instruction registers in a target scan chain. The eTBC generates a TMS sequence to move the target scan chain from its current TAP state to the Shift-IR TAP state. Data written to the TDO buffer can be driven serially onto the TDO pin and bits received serially at the TDI pin can be stored into the TDI buffer for reading by the host. The number of data bits transferred in and/or out is determined by the value of the counter upon command initiation. If, during the operation of an instruction register scan command, the TDO buffer becomes empty, or the TDI buffer becomes full, the TAP state is sequenced to Pause-IR (if in free-running-TCK mode) or the TCK output is gated off (if in gated-TCK mode) until the required buffer service is performed. Upon the countdown of the counter to zero, the eTBC generates TMS sequences to move the target scan chain to the end state specified in the command register.

data-register scan commands

The data-register scan commands operate to scan bits to and/or from the concatenation of data registers in a target scan chain. The eTBC generates a TMS sequence to move the target scan chain from its current TAP state to the Shift-DR TAP state. Data written to the TDO buffer may be driven serially onto the TDO pin and bits received serially at the TDI pin may be stored into the TDI buffer for reading by the host. The number of data bits transferred in and/or out is determined by the value of the counter upon command initiation. If, during the operation of a data-register scan command, the TDO buffer becomes empty, or the TDI buffer becomes full, the TAP state is sequenced to Pause-DR (if in free-running-TCK mode) or the TCK output is gated off (if in gated-TCK mode) until the required buffer service is performed. Upon the countdown of the counter to zero, the eTBC generates TMS sequences to move the target scan chain to the end state specified in the command register.

other scan-command variations

As noted before, the nature/direction of the data transfer for any scan command can vary along with the destination of scan data in the target, as follows:

- For scan commands of the full-duplex (default) class, both TDO buffer and TDI buffer are used to scan data to and from the target scan chain, respectively.
- For scan commands of the input-only class, only the TDI buffer is used to scan data from the target scan chain; outgoing TDO data is fixed at a high level throughout the scan operation.
- For scan commands of the output-only class, only the TDO buffer is used to scan data to the target scan chain; incoming TDI data is simply ignored.
- For scan commands of the recirculate class, only the TDI buffer is used to scan data from the target scan chain; outgoing TDO data is generated by recirculating the incoming TDI data back into the target scan chain.

counter

As described above, the value loaded in the eTBC's 32-bit counter at initiation of a command is used to specify the number of TCK cycles or scan bits to remain in the command's working state. As each TCK cycle or scan bit is processed for a run-test or scan command, respectively, the counter value is decremented. When the counter value reaches zero, the command leaves its working state to finish in the end state specified in the command register.

Before a command that uses the counter can be initiated, a full 32-bit value should be loaded by four consecutive writes to the counter register. As well, the full 32-bit current value of the counter can be observed by four consecutive reads to the counter register. The counter status (unloaded/loaded) is maintained and observable in the status register (bit 5, CTRS).

Upon eTBC reset (power-up, hardware-initiated, or software-initiated), the counter is cleared and assumes its unloaded state.

TCK generator

The TCK generator sources the test clock (TCK) signal required by the IEEE Std 1149.1 target(s) and the eTBC-internal test-control logic. The fundamental TCK frequency is produced by division of CLKIN. The divisor is programmable within a range of 1 to 128 in the configurationB register (bits 7–5, CDIV). The TCK output to the target(s) operate in free-running or gated modes. The free-running mode toggles TCK continuously, based on CLKIN, while the gated mode operates the TCK only when required to move the target TAP state or to perform a run-test or scan operation.

While the eTBC is in discrete-control mode, the TCK generator is not used; instead, the state of TCK is toggled on each alternating read and write to the discrete-control register. A falling edge of TCK is produced by write, while a rising edge of TCK is produced by read.

Upon eTBC reset (power-up, hardware-initiated, or software-initiated), the TCK generator assumes its free-running mode with a clock divisor of 16 (TCK = CLKIN/16).

TAP-state generator

The TAP-state generator sources the TMS signal, which sequences the TAP controllers of connected IEEE Std 1149.1-compliant target devices. The TAP controller specified by IEEE Std 1149.1 is a synchronous finite-state machine that provides test control signals throughout each target device; its state diagram is shown in Figure 8. This diagram and the TAP-controller states are discussed subsequently.

The TAP-state generator operates under the control of an executing command to generate the TMS sequences required to move connected target devices from one stable state to another, to capture and scan test data into/out of target devices, and to operate built-in test modes of target devices in the Run-Test/Idle state.

The TAP state currently being generated is always maintained by the TAP-state generator and is constantly available in the eTBC status register (bits 3–0, TAPST) for host read. Based on the TAP state that is current upon command initiation, the TAP-state generator will source a defined sequence of TMS values to reach the TAP state in which the command is progressed (e.g., Shift-IR, Shift-DR, Run-Test/Idle), and ultimately to reach the specified end TAP state. These sequences are detailed in Tables 7–12.

While the eTBC is in free-running-TCK mode, if a currently operating scan command empties or fills a required test data buffer, then the TAP-state generator sources the TMS sequences required to move the connected target devices to their Pause-IR or Pause-DR states. In such case, the TAP-state generator maintains target devices in their Pause-IR or Pause-DR states until the required test data buffer is serviced appropriately. However, if such a buffer condition occurs while the eTBC is in gated-TCK mode, the TAP-state generator maintains the target devices in their Shift-IR or Shift-DR states while the TCK is gated off.

While the eTBC is in discrete-control mode, the TAP-state generator is not used; instead, the state of the TMS pin is determined by the contents of the discrete-control register. Thus, TMS sequences that cannot be generated automatically still can be applied through the eTBC to targets that require such (e.g., near-compliant devices).

The TAP-state generator also is not used during the operation of the special addressable shadow protocol (ASP) scan commands. Since, by definition, ASPs operate only while the TAP is idling (maintaining one of the TAP states Test-Logic-Reset, Run-Test/Idle, Pause-IR, or Pause-DR), the TMS pin must be maintained at the value it held upon initiation of the ASP scan command.

For eTBC verification/debugging, in addition to continuous update of the current target TAP state in the eTBC status register, the output of the TAP-state (TMS) generator can be selected for loopback into the TDI buffer. When this TMS-loopback mode is selected, although a host-requested command executes in the eTBC, the target is not affected, as both TMS and TDI are fixed at a high level.

Upon eTBC reset (power up, hardware initiated, or software initiated), the TAP-state generator assumes the Test-Logic-Reset TAP state.

Table 7. TMS Sequencing From TAP State Test-Logic-Reset

FROM TEST-LOGIC-RESET (TMS = H) TO:											
TEST-LOGIC-RESET		RUN-TEST-IDLE		SHIFT-DR		PAUSE-DR		SHIFT-IR		PAUSE-IR	
NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE
H	T-L-R	L	R-T/I	L	R-T/I	L	R-T/I	L	R-T/I	L	R-T/I
				H	S-DR-S	H	S-DR-S	H	S-DR-S	H	S-DR-S
				L	Capture-DR	L	Capture-DR	H	S-IR-S	H	S-IR-S
				L	Shift-DR	H	Exit1-DR	L	Capture-IR	L	Capture-IR
						L	Pause-DR	L	Shift-IR	H	Exit1-IR
										L	Pause-IR

Table 8. TMS Sequencing From TAP State Run-Test/Idle

FROM RUN-TEST/IDLE (TMS = L) TO:											
TEST-LOGIC-RESET		RUN-TEST-IDLE		SHIFT-DR		PAUSE-DR		SHIFT-IR		PAUSE-IR	
NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE
H	S-DR-S	L	R-T/I	H	S-DR-S	H	S-DR-S	H	S-DR-S	H	S-DR-S
H	S-IR-S			L	Capture-DR	L	Capture-DR	H	S-IR-S	H	S-IR-S
H	T-L-R			L	Shift-DR	H	Exit1-DR	L	Capture-IR	L	Capture-IR
						L	Pause-DR	L	Shift-IR	H	Exit1-IR
										L	Pause-IR

Table 9. TMS Sequencing From TAP State Pause-DR

FROM PAUSE-DR (TMS = L) TO:											
TEST-LOGIC-RESET		RUN-TEST-IDLE		SHIFT-DR		PAUSE-DR		SHIFT-IR		PAUSE-IR	
NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE
H	Exit2-DR	H	Exit2-DR	H	Exit2-DR	H	Exit2-DR	H	Exit2-DR	H	Exit2-DR
H	Update-DR	H	Update-DR	L	Shift-DR	H	Update-DR	H	Update-DR	H	Update-DR
H	S-DR-S	L	R-T/I			H	S-DR-S	H	S-DR-S	H	S-DR-S
H	S-IR-S					L	Capture-DR	H	S-IR-S	H	S-IR-S
H	T-L-R					H	Exit1-DR	L	Capture-IR	L	Capture-IR
						L	Pause-DR	L	Shift-IR	H	Exit1-IR
										L	Pause-IR

Table 10. TMS Sequencing From TAP State Pause-IR

FROM PAUSE-IR (TMS = L) TO:											
TEST-LOGIC-RESET		RUN-TEST-IDLE		SHIFT-DR		PAUSE-DR		SHIFT-IR		PAUSE-IR	
NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE
H	Exit2-IR	H	Exit2-IR	H	Exit2-IR	H	Exit2-IR	H	Exit2-IR	H	Exit2-IR
H	Update-IR	H	Update-IR	H	Update-IR	H	Update-IR	L	Shift-IR	H	Update-IR
H	S-DR-S	L	R-T/I	H	S-DR-S	H	S-DR-S			H	S-DR-S
H	S-IR-S			L	Capture-DR	L	Capture-DR			H	S-IR-S
H	T-L-R			L	Shift-DR	H	Exit1-DR			L	Capture-IR
						L	Pause-DR			H	Exit1-IR
										L	Pause-IR

Table 11. TMS Sequencing From TAP State Shift-DR

FROM SHIFT-DR (TMS = L) TO:							
TEST-LOGIC-RESET		RUN-TEST-IDLE		PAUSE-DR		PAUSE-IR	
NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE
H	Exit1-DR	H	Exit1-DR	H	Exit1-DR	H	Exit1-DR
H	Update-DR	H	Update-DR	L	Pause-DR	H	Update-DR
H	S-DR-S	L	R-T/I			H	S-DR-S
H	S-IR-S					H	S-IR-S
H	T-L-R					L	Capture-IR
						H	Exit1-IR
						L	Pause-IR

Table 12. TMS Sequencing From TAP State Shift-IR

FROM SHIFT-IR (TMS = L) TO:							
TEST-LOGIC-RESET		RUN-TEST-IDLE		PAUSE-DR		PAUSE-IR	
NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE	NEXT TMS	NEXT TAP STATE
H	Exit1-IR	H	Exit1-IR	H	Exit1-IR	H	Exit1-IR
H	Update-IR	H	Update-IR	H	Update-IR	L	Pause-IR
H	S-DR-S	L	R-T/I	H	S-DR-S		
H	S-IR-S			L	Capture-DR		
H	T-L-R			H	Exit1-DR		
				L	Pause-DR		

state diagram description

The state diagram shown in Figure 8 is in accordance with IEEE Std 1149.1-1990. The TAP controller proceeds through its states based on the level of TMS at the rising edge of TCK.

As shown, the TAP controller consists of 16 states. There are six stable states (indicated by a looping arrow in the state diagram) and ten unstable states. A stable state is a state the TAP controller can retain for consecutive TCK cycles. Any state that does not meet this criterion is an unstable state.

There are two main paths though the state diagram: one to access and control the selected data register and one to access and control the instruction register. Only one register can be accessed at any given time.

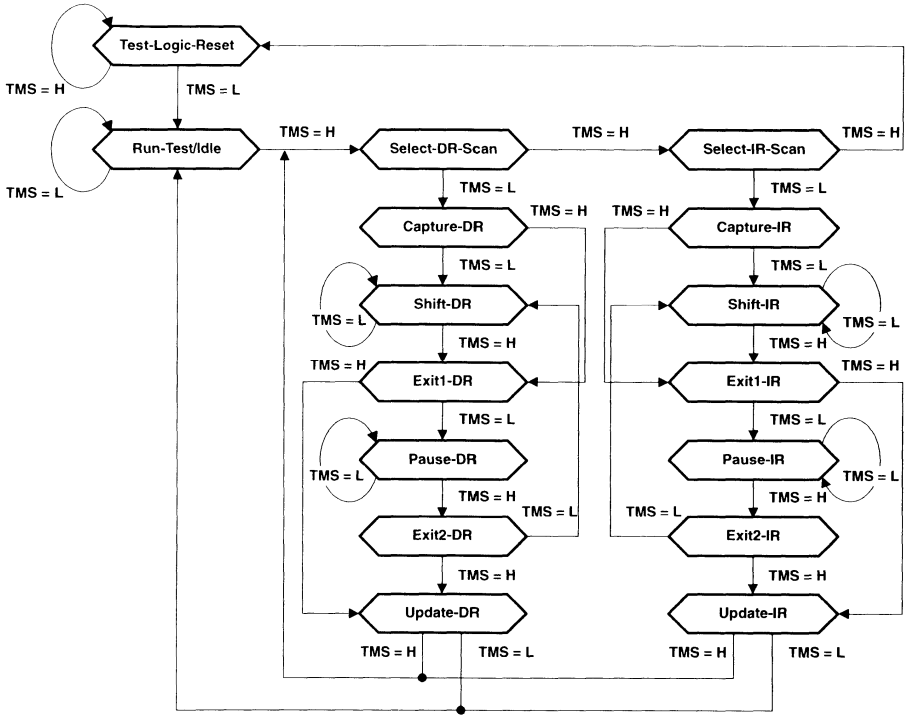


Figure 8. TAP-Controller State Diagram

Test-Logic-Reset

The eTBC TAP-state generator powers up in the Test-Logic-Reset state. Alternatively, the eTBC can be forced to this state asynchronously by assertion of its $\overline{RST}$ input or synchronously by writing the eTBC command register (bit 7-SWRST).

For a target device in the stable Test-Logic-Reset state, the test logic is reset and is disabled so that the normal logic function of the device is performed. The instruction register is reset to an opcode that selects the optional IDCODE instruction, if supported, or the BYPASS instruction. Certain data registers also can be reset to their power-up values.

Run-Test/Idle

For a target device, Run-Test/Idle is a stable state in which the test logic can be actively running a test or can be idle.

Select-DR-Scan, Select-IR-Scan

For a target device, no specific function is performed in the Select-DR-Scan and Select-IR-Scan states, and the TAP controller exits either of these states on the next TCK cycle. These states allow the selection of either data-register scan or instruction-register scan.

Capture-DR

For a target device in the Capture-DR state, the selected data register can capture a data value as specified by the current instruction. Such capture operations occur on the rising edge of TCK, upon which the Capture-DR state is exited.

Shift-DR

For a target device, upon entry to the Shift-DR state, the selected data register is placed in the scan path between TDI and TDO, and on the first falling edge of TCK, TDO goes from the high-impedance state to an active state. TDO outputs the logic level present in the least-significant bit of the selected data register. While in the stable Shift-DR state, data is serially shifted through the selected data register on each TCK cycle.

Exit1-DR, Exit2-DR

For a target device, the Exit1-DR and Exit2-DR states are temporary states that end a data-register scan. It is possible to return to the Shift-DR state from either Exit1-DR or Exit2-DR without recapturing the data register. On the first falling edge of TCK after entry to Exit1-DR, TDO goes from the active state to the high-impedance state.

Pause-DR

For target devices, no specific function is performed in the stable Pause-DR state. The Pause-DR state suspends and resumes data-register scan operations without loss of data.

Update-DR

For a target device, if the current instruction calls for the selected data register to be updated with current data, such update occurs on the falling edge of TCK, following entry to the Update-DR state.

Capture-IR

For a target device in the Capture-IR state, the instruction register captures its current status value. This capture operation occurs on the rising edge of TCK, upon which the Capture-IR state is exited.

Shift-IR

For a target device, upon entry to the Shift-IR state, the instruction register is placed in the scan path between TDI and TDO, and on the first falling edge of TCK, TDO goes from the high-impedance state to an active state. TDO outputs the logic level present in the least-significant bit of the instruction register. While in the stable Shift-IR state, instruction data is serially shifted through the instruction register on each TCK cycle.

Exit1-IR, Exit2-IR

For target devices, the Exit1-IR and Exit2-IR states are temporary states that end an instruction-register scan. It is possible to return to the Shift-IR state from either Exit1-IR or Exit2-IR without recapturing the instruction register. On the first falling edge of TCK after entry to Exit1-IR, TDO goes from the active state to the high-impedance state.

Pause-IR

For target devices, no specific function is performed in the stable Pause-IR state, in which the TAP controller can remain indefinitely. The Pause-IR state suspends and resumes instruction-register scan operations without loss of data.

Update-IR

For target devices, the current instruction is updated and takes effect on the falling edge of TCK, following entry to the Update-IR state.

TDO buffer

The TDO buffer is the 4 × 8-bit-parallel-to-serial FIFO that accepts scan data from the host in 8-bit-parallel format and serializes it onto the TDO pin during scan operations. Scan data is expected to be transferred from the host in least-significant-byte-first order to meet IEEE Std 1149.1 requirements for least-significant-bit-first scan order. Any partial byte to be written should be justified to D0. The TDO buffer is cleared upon command initiation, so no scan data should be written to the TDO buffer before writing a scan command to the command register.

The TDO-buffer status (not full/full) is maintained in the status register (bit 6, TDOS). When the TDO-buffer status is full, writes to the TDO buffer is held off by RDY inactive and if the write cycle is aborted prior to RDY active, the write data is ignored.

For the convenience and efficiency of operating scans to the target for which outgoing data is not required, the eTBC supports special classes of input-only and recirculate scan commands that do not require nor operate the TDO buffer and so the host need not perform any write access to it. While the input-only scan commands are operating, the TDO pin outputs a fixed high level. While the recirculate scan commands are operating, the TDO pin recirculates to the target the data that is received at TDI.

While the eTBC is in discrete-control mode, the TDO buffer is not used; instead, the state of the TDO pin is determined by the contents of the discrete-control register. Thus, TMS/TDO sequences that cannot be automatically generated still can be applied through the eTBC to targets that require such (e.g., near-compliant devices).

For eTBC verification/debugging, the TDO-buffer output can be selected for loopback into the TDI buffer. When this TDO-loopback mode is selected, although a host-requested command executes in the eTBC, the target is not affected, as both TMS and TDI are fixed at a high level.

Upon eTBC reset (power up, hardware initiated, or software initiated), the TDO buffer is cleared and assumes its not-full state.

TDI buffer

The TDI buffer is the serial-to-4 × 8-bit-parallel FIFO that serially receives data at the TDI pin and makes it available in 8-bit-parallel format for reading by the host. Scan data is expected to be transferred from the IEEE Std 1149.1 targets in least-significant-bit-first order and is made available for host read in least-significant-byte-first order. The last data available for host read during a scan command may be a partial byte, in which case it is justified to D0.

The TDI-buffer status (empty/not empty) is maintained in the status register (bit 7, TDIS). When the TDI-buffer status is empty, reads to the TDI buffer is held off by RDY inactive and, if the read cycle is aborted prior to RDY active, the read data is invalid.

The TDI buffer is able to automatically accommodate retiming (pipeline) delays to the target. While operating a scan command, TDI sampling is delayed by a number of TCK cycles, equal to a value given in the configurationB register (bits 3–0, RDLY), following the generation of Shift-DR or Shift-IR state, as appropriate.

For the convenience and efficiency of operating scans to the target for which incoming data is not required, the eTBC supports a special class of output-only scan commands that neither require nor operate the TDI buffer. While the output-only scan commands are operating, the data received at TDI is ignored and the host need not perform any read access to the TDI buffer.

While the eTBC is in discrete-control mode, the TDI buffer is not used; instead, the state of the TDO pin is observed in the discrete-control register. Thus, TMS/TDO sequences that cannot be automatically generated can still be applied through the eTBC to targets that require such (e.g., near-compliant devices).

For eTBC verification/debugging, the input to the TDI buffer can be selected for loopback from either TDO buffer or TAP-state (TMS) generator. When either of these loopback modes is selected, although a host-requested command executes in the eTBC, the target is not affected, as both TMS and TDI are fixed at a high level.

Upon eTBC reset (power up, hardware initiated, or software initiated), the TDI buffer is cleared and assumes its empty state.

discrete control

The discrete-control block provides the multiplexing and control logic required to support the eTBC's discrete-control mode in addition to its automatic modes. While the eTBC is in discrete-control mode, the TAP signals are fully controllable/accessible to the host via reads/writes to the discrete-control register. No commands can be initiated/operated while the eTBC is in the discrete-control mode.

Upon eTBC reset (power up, hardware initiated, or software initiated), the discrete-control mode is inactive.

reset

The eTBC provides three mechanisms for comprehensive and equivalent reset – power-up reset, hardware-initiated reset ($\overline{RST}$), and software-initiated reset (SWRST, bit 7 of command register) to the following effect:

- All eTBC registers are reset to default values as given in Table 1.
- The command/control logic is fully reset.
- The counter is cleared/unloaded. The TDO buffer and TDI buffer are cleared/emptied.
- The TAP-state generator is reset to the Test-Logic-Reset TAP state.
- TDO, TMS, and $\overline{TRST}$ output high levels; TCK outputs CLKIN/16.

As a consequence, the IEEE Std 1149.1 targets can be expected to be driven synchronously to the Test-Logic-Reset state no later than the fifth rising edge of TCK (72 CLKIN cycles).

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O
(see Note 1): D, RDY ..... –0.5 V to V_{CC} + 0.5 V
TCK, TDO, TMS, $\overline{TRST}$ ..... –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT8980 (D, RDY) ..... 12 mA
SN54LVT8980 (TCK, TDO, TMS, $\overline{TRST}$) ..... 96 mA
SN74LVT8980 (D, RDY) ..... 12 mA
SN74LVT8980 (TCK, TDO, TMS, $\overline{TRST}$) ..... 128 mA
Current into any output in the high state, I_O
(see Note 2): SN54LVT8980 (D, RDY) ..... 16 mA
SN54LVT8980 (TCK, TDO, TMS, $\overline{TRST}$) ..... 48 mA
SN74LVT8980 (D, RDY) ..... 16 mA
SN74LVT8980 (TCK, TDO, TMS, $\overline{TRST}$) ..... 64 mA
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O > V_{CC}): D, RDY ..... 50 mA
Package thermal impedance, θ_{JA} (see Note 3): DW package ..... 81°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This current flows only when the output is in the high state and V_O > V_{CC}.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVT8980		SN74LVT8980		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	D, RDY		–8		–8	mA
		TCK, TDO, TMS, $\overline{TRST}$		–24		–32	
I_{OL}	Low-level output current	D, RDY		6		6	mA
		TCK, TDO, TMS, $\overline{TRST}$		48		64	
$\Delta t/\Delta v$	Input transition rise or fall rate			10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs (A, CLKIN, R/$\overline{W}$) must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVT8980			SN74LVT8980			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}	D, RDY	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –4 mA	2.3			2.3			
		V_{CC} = 3 V	I_{OH} = –4 mA	2.6			2.6			
			I_{OH} = – 8 mA	2.4			2.4			
	TCK, TDO, TMS, TRST	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}	D, RDY	V_{CC} = MIN to MAX‡,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 2.7 V	I_{OL} = 4 mA			0.55			0.55	
			I_{OL} = 6 mA			0.8			0.8	
		V_{CC} = 3 V	I_{OL} = 4 mA			0.55			0.55	
			I_{OL} = 6 mA			0.8			0.8	
	TCK, TDO, TMS, TRST	V_{CC} = MIN to MAX‡,	I_{OL} = 100 µA			0.2			0.2	
		V_{CC} = 2.7 V	I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	A, CLKIN, RST, R/W, STRB, TDI, TOE	V_{CC} = 0 or MAX‡,	V_I = 5.5 V			10			10	µA
	A, CLKIN, R/W	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	RST, STRB, TDI, TOE	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0	–40		–100	–40		–100	
I_{off}	TCK, TDO, TMS, TRST	V_{CC} = 0, V_I or V_O = 0 to 4.5 V				±100			±100	µA
I_{OZH}	D, TCK, TDO, TMS, TRST	V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}	D, TCK, TDO, TMS, TRST	V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}§	TCK, TDO, TMS, TRST	V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = 0				±100			±100	µA
I_{OZPD}§	TCK, TDO, TMS, TRST	V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = 0				±100			±100	µA

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This parameter is characterized but not tested.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS	SN54LVT8980			SN74LVT8980			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
I_{CC}	Outputs high	V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND			0.5			0.5	mA
	Outputs low				7			7	
	Outputs disabled				0.5			0.5	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND			0.2			0.2	mA
C_i		V_I = 3 V or 0		4			4		pF
C_{io}		V_O = 3 V or 0		5			5		pF
C_o		V_O = 3 V or 0		7			7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 9 and 10)

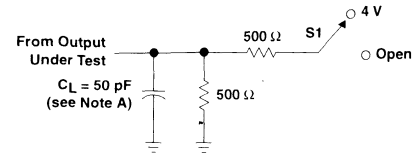
				SN54LVT8980				SN74LVT8980				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency, CLKIN		TCK = CLKIN (CDIV = 0)	0	20	0	16	0	20	0	16	MHz
			TCK = CLKIN/2 (CDIV = 1)	0	40	0	32	0	40	0	32	
			TCK ≤ CLKIN/4 (CDIV ≥ 2)	0	70	0	64	0	70	0	64	
t_w	Pulse duration	CLKIN high or low	TCK = CLKIN (CDIV = 0)	25		31		25		31		ns
			TCK = CLKIN/2 (CDIV = 1)	12.5		15.5		12.5		15.6		
			TCK ≤ CLKIN/4 (CDIV ≥ 2)	7.1		7.8		7.1		7.8		
		$\overline{RST}$ low		10		10		10		10		
		$\overline{STRB}$ low		8		8		8		8		
t_{su}	Setup time	A before $\overline{STRB}$↓	Read or write (R/$\overline{W}$ high or low)	10		10		10		10		ns
		D before $\overline{STRB}$↑	Write (R/$\overline{W}$ low)	5		5		5		5		
		R/$\overline{W}$ before $\overline{STRB}$↓		5		5		5		5		
		TDI before CLKIN↑		5		5		5		5		
t_h	Hold time	A after $\overline{STRB}$↑	Read or write (R/$\overline{W}$ high or low)	5		5		5		5		ns
		D after $\overline{STRB}$↑	Write (R/$\overline{W}$ low)	15		15		15		15		
		R/$\overline{W}$ after $\overline{STRB}$↑		6		6		6		6		
		TDI after CLKIN↑		10		10		10		10		

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 9 and 10)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT8980				SN74LVT8980				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	CLKIN	TCK	6	20		25	6	10	17	20	ns
t_{PHL}			6	20		25	6	10	17	20	
t_{PLH}	CLKIN	TDO, TMS	8	35		40	8	18	30	35	ns
t_{PHL}			8	35		40	8	18	30	35	
t_{PLH}	$\overline{RST}\downarrow$	D	3	35		40	3	17	30	35	ns
t_{PHL}			3	35		40	3	17	30	35	
t_{PLH}	$\overline{RST}\downarrow$	RDY	3	35		40	3	17	30	35	ns
t_{PHL}			3	35		40	3	17	30	35	
t_{PLH}	$\overline{RST}\downarrow$	TDO, TMS, $\overline{TRST}$	5	30		35	5	15	25	30	ns
t_{PHL}		TCK	5	30		35	5	15	25	30	
t_{PLH}	$\overline{STRB}\uparrow$	RDY	3	22		28	3	10	18	22	ns
t_{PHL}	$\overline{STRB}\downarrow$		3	22		28	3	10	18	22	
t_{PLH}	$\overline{STRB}\uparrow$	TCK, TDO, TMS, $\overline{TRST}$ discrete mode	3	28		35	3	14	22	28	ns
t_{PHL}			3	28		35	3	14	22	28	
t_{PLH}	$\overline{STRB}\uparrow$	TCK, TDO, TMS, $\overline{TRST}$ other modes	6	40		45	6	20	35	40	ns
t_{PHL}			6	40		45	6	20	35	40	
t_{PZH}	$\overline{STRB}\downarrow$	D	3	20		25	3	8	15	18	ns
t_{PZL}			3	20		25	3	8	15	18	
t_{PZH}	$\overline{STRB}\uparrow$	TCK, TDO, TMS, $\overline{TRST}$	5	30		35	5	15	25	30	ns
t_{PZL}			5	30		35	5	15	25	30	
t_{PZH}	$\overline{TOE}\downarrow$	TCK, TDO, TMS, $\overline{TRST}$	2	15		18	2	6	12	15	ns
t_{PZL}			2	15		18	2	6	12	15	
t_{PHZ}	$\overline{STRB}\uparrow$	D	3	20		25	3	8	15	18	ns
t_{PLZ}			3	20		25	3	8	15	18	
t_{PHZ}	$\overline{STRB}\uparrow$	TCK, TDO, TMS, $\overline{TRST}$	5	30		35	5	15	25	30	ns
t_{PLZ}			5	30		35	5	15	25	30	
t_{PHZ}	$\overline{TOE}\uparrow$	TCK, TDO, TMS, $\overline{TRST}$	2	15		18	2	6	12	15	ns
t_{PLZ}			2	15		18	2	6	12	15	

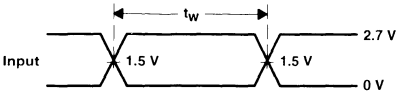
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

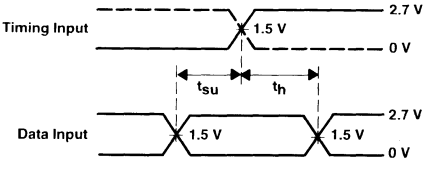


LOAD CIRCUIT

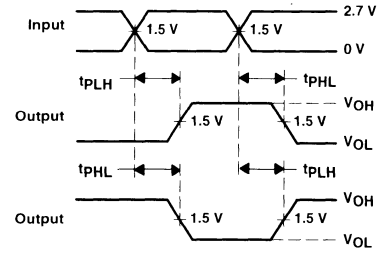
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	4 V
t_{PHZ}/t_{PZH}	GND



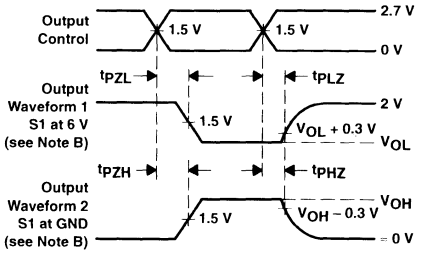
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS

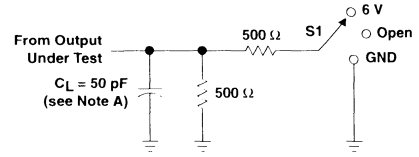


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

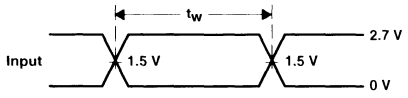
Figure 9. Load Circuit and Voltage Waveforms (D and RDY Outputs)

PARAMETER MEASUREMENT INFORMATION

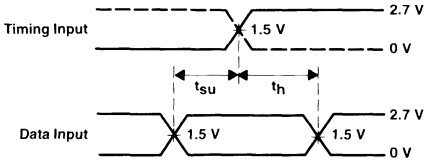


LOAD CIRCUIT

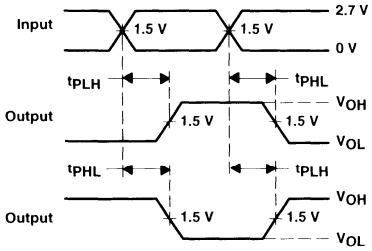
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



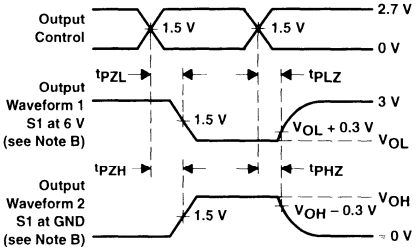
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: E. C_L includes probe and jig capacitance.
F. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
G. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
H. The outputs are measured one at a time with one transition per measurement.

Figure 10. Load Circuit and Voltage Waveforms (TCK, TDO, TMS, $\overline{TRST}$ Outputs)

silicon errata

The descriptions and specifications included in this data sheet represent the intended performance of the 'LVT8990 device. In most cases, these descriptions and specifications also represent the actual performance of silicon of a given revision. Specific exceptions are noted here.

item 1 – operation of host interface ($\overline{STRB}$) asynchronous to CLKIN

The host interface, which is timed by $\overline{STRB}$, is intended to be, and properly should be, fully asynchronous relative to CLKIN. In short, the device should function as described in this data sheet regardless of the timing relationship between applied $\overline{STRB}$ and CLKIN.

The 'LVT8990 "X" die, however, fails to function properly when $\overline{STRB}$ is not synchronous to CLKIN. Specifically, $\overline{STRB}$ must be applied considering adequate setup time requirements as follows:

		SN74LVT8980				UNIT
		V_{CC} = 3.3 ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	
t_{su}	$\overline{STRB}$ high before CLKIN↑	25		25		ns

A fix is proposed for device revision 'LVT8980A.

workaround

For an 'LVT8980 "X" die design, always operate the host interface (specifically, $\overline{STRB}$) synchronously to CLKIN, maintaining setup time requirements as given above. In most applications, this would mean that the eTBDC CLKIN is driven from the same original clock source as the host CPU.

item 1 – read of TDI buffer while it is empty (not ready)

When a read is made to TDI buffer while it is empty (not ready), the RDY pin signal is specified to go low, indicating that the eTBC is not presently ready to service the requested access. If, while $\overline{STRB}$ is held low, subsequent processing of a scan command fills a byte in the TDI buffer, the RDY pin signal is specified to return high, indicating that the eTBC is ready to complete the access. Correspondingly, the available byte of data from TDI buffer should be latched onto the data bus such that the host can access this data.

The 'LVT8990 "X" die, however, does not function properly with respect to the actual data latched to the data bus. That is, if a read is made to TDI buffer while it is empty (not ready), the RDY pin signal goes low as specified; as well, if the $\overline{STRB}$ pin signal is held low, and further processing of a scan command fills a byte in the TDI buffer, the RDY pin signal returns high as specified. However, at the same time that RDY returns high, the TDI data byte should be latched onto the data bus. If this does not occur, the data that does appear on the data bus is not valid.

A fix is proposed for device revision 'LVT8980A.

workaround

For an LVT8990 "X" design, always poll the TDI buffer (read status register, bit 7, TDIS) to ensure that it is ready prior to a desired read to TDI buffer. Of course, such a software-polled mode versus the hardware-inserted wait-states (RDY) mode (as originally specified, and as proposed to be fixed in 'LVT8980A device revision) places more overhead on the CPU and likely reduces throughput as well.

considerations for migrating 'LVT8990 "X" die designs to 'LVT8980A

As noted above, device revision 'LVT8980A proposes to fix the two known silicon errata of 'LVT8980. It is recommended that designs based on the 'LVT8980 "X" die consider and plan for migration to 'LVT8980A.

In the case of all known silicon errata items, the 'LVT8980A device function will be a super set of the actual function of 'LVT8980 "X" die and will comply with the device descriptions and specifications of this data sheet. So, with respect to the proposed fixes, 'LVT8980JA can directly replace 'LVT8980 "X" die in existing designs.

However, the 'LVT8980A device revision proposes to make an additional change that does not comply with the device descriptions and specifications of this data sheet. This additional change is noted here.

item 1 – make $\overline{\text{TOE}}$ pin signal high enabling and rename to $\overline{\text{TOFF}}$

The 'LVT8980A device revision proposes to modify the polarity of the $\overline{\text{TOE}}$ (active-low test output enable) pin signal (pin 13 for DW, JT packages) to high enabling and consequently to rename the pin signal to active-low test off ($\overline{\text{TOFF}}$).

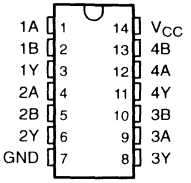
workaround

For an 'LVT8980 "X" die design, it is recommended that the $\overline{\text{TOE}}$ pin be tied off to ground via a discrete resistor. Then, to migrate to use of 'LVT8980A device, the design need only be modified to omit the resistor – the internal resistor at the 'LVT8980A $\overline{\text{TOFF}}$ pin will ensure that it is driven by default to the state required to enable the device TAP outputs.

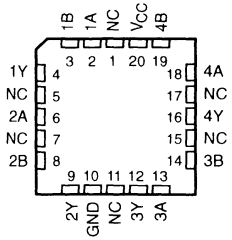
Contents

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK) and Flat (W) Packages, and DIPs (J)

SN54LVC00A . . . J OR W PACKAGE
SN74LVC00A . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVC00A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These quadruple 2-input positive-NAND gates are designed for 2.7-V to 3.6-V V_{CC} operation. The 'LVC00A perform the Boolean function $Y = \overline{A \bullet B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN54LVC00A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC00A is characterized for operation from –40°C to 85°C.

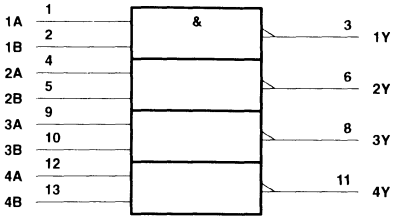
FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

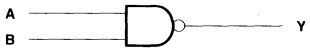
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, PW, and W packages.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			SN54LVC00A		SN74LVC00A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC00A			SN74LVC00A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			2.2			
		3 V	2.4			2.4			
	I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA	2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

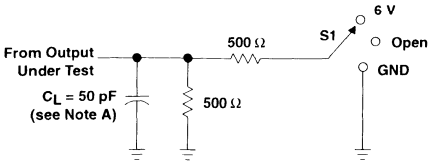
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC00A				SN74LVC00A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	4.3		5.1	1	4.3		5.1	ns
$t_{sk(o)}$‡*				1				1			ns

* On products compliant to MIL-PRF-38535, this parameter does not apply.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

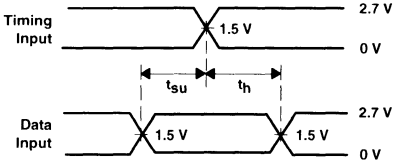
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	9.5	pF

PARAMETER MEASUREMENT INFORMATION

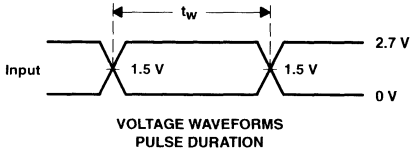


LOAD CIRCUIT

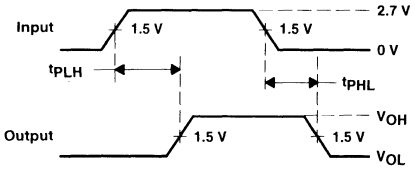
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



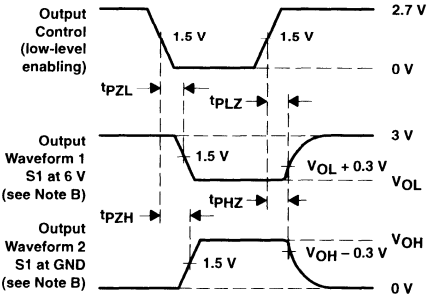
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



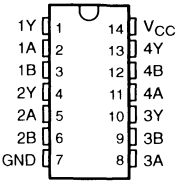
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

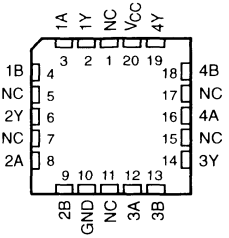
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Inputs Accept Voltages to 5.5 V**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW) Packages, Ceramic Flat (W), Chip Carriers (FK), and Ceramic 300-mil DIPs (J)**

SN54LVC02A . . . J OR W PACKAGE
SN74AHC02A . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVC02A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These quadruple 2-input positive-NOR gates are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC02A perform the Boolean function $Y = \overline{A + B}$ or $Y = \overline{A} \bullet \overline{B}$ in positive logic.

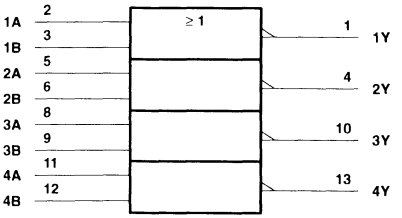
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN54LVC02A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC02A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

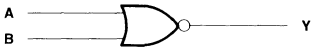
INPUTS		OUTPUT
A	B	Y
H	X	L
X	H	L
L	L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, PW, and W packages.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply-voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input-voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output-voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC02A		SN74LVC02A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LVC02A			SN74LVC02A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			2.2			
		3 V	2.4			2.4			
	I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA	2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

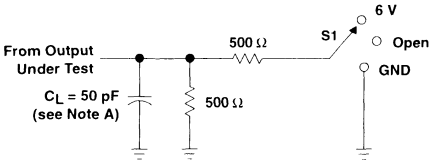
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC02A				SN74LVC02A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	4.4		5.4	1	4.4		5.4	ns
$t_{sk(o)}$‡*				1				1			ns

‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.
* On products compliant to MIL-PRF-38535, this parameter does not apply.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

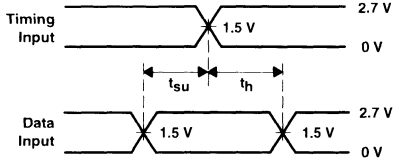
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	9.5	pF

PARAMETER MEASUREMENT INFORMATION

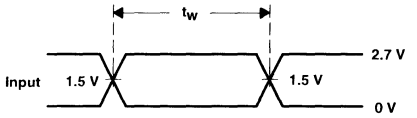


LOAD CIRCUIT

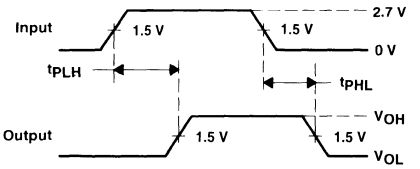
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



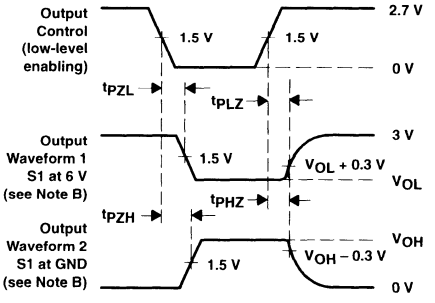
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

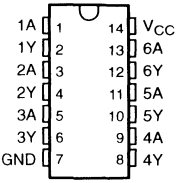
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

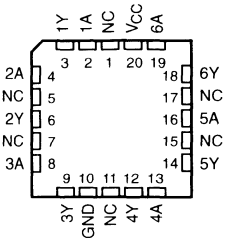
SCAS281F – JANUARY 1993 – REVISED SEPTEMBER 1997

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Ceramic Chip Carriers (FK), and Thin Shrink Small-Outline (PW) Packages

SN54LVC04A . . . J OR W PACKAGE
SN74LVC04A . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVC04A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These hex inverters contain six independent inverters designed for 2.7-V to 3.6-V V_{CC} operation. The 'LVC04A perform the Boolean function $Y = \overline{A}$.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN54LVC04A is characterized for operation over the full military temperature range from –55°C to 125°C. The SN74LVC04A is characterized for operation from –40°C to 85°C.

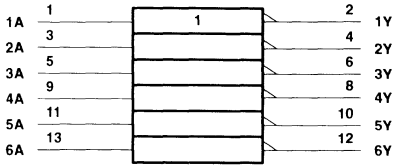
FUNCTION TABLE
(each inverter)

INPUT A	OUTPUT Y
H	L
L	H

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, PW, and W packages.

logic diagram, each inverter (positive logic)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC04A		SN74LVC04A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LVC04A			SN74LVC04A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			2.2			
		3 V	2.4			2.4			
	I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA	2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC04A				SN74LVC04A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	0.5	4.5		5.5	1	4.5		5.5	ns
$t_{sk(o)}$*‡								1			ns

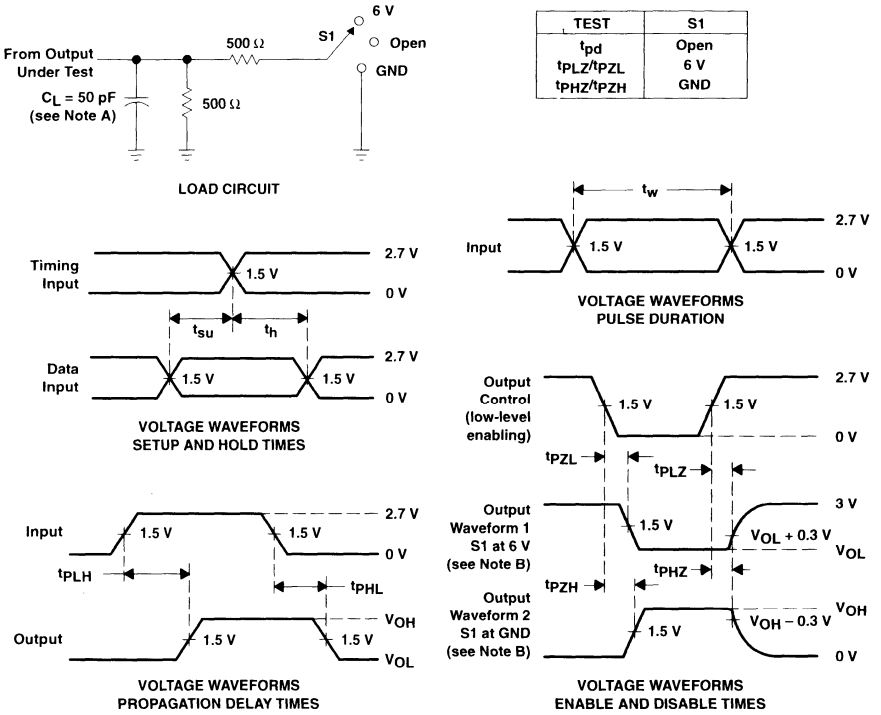
* On products compliant to MIL-PRF-38535, this parameter does not apply.

‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF, f = 10 MHz	8	pF

PARAMETER MEASUREMENT INFORMATION



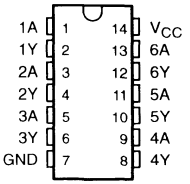
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

SCAS282D – JANUARY 1993 – REVISED JANUARY 1997

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This hex inverter is designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVCU04A contains six independent inverters with unbuffered outputs, and performs the Boolean function $Y = \overline{A}$.

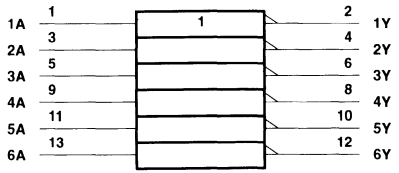
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVCU04A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

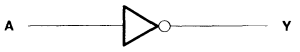
INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each inverter (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V	2.16		V
		V_{CC} = 3 V	2.4		
		V_{CC} = 3.6 V	2.88		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.65	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA	V_{IH} = 2.16 V	2.7 V			0.2	V
		V_{IH} = 2.88 V	3.6 V			0.2	
	I_{OL} = 12 mA,	V_{IH} = 2.16 V	2.7 V			0.4	
	I_{OL} = 24 mA,	V_{IH} = 2.4 V	3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

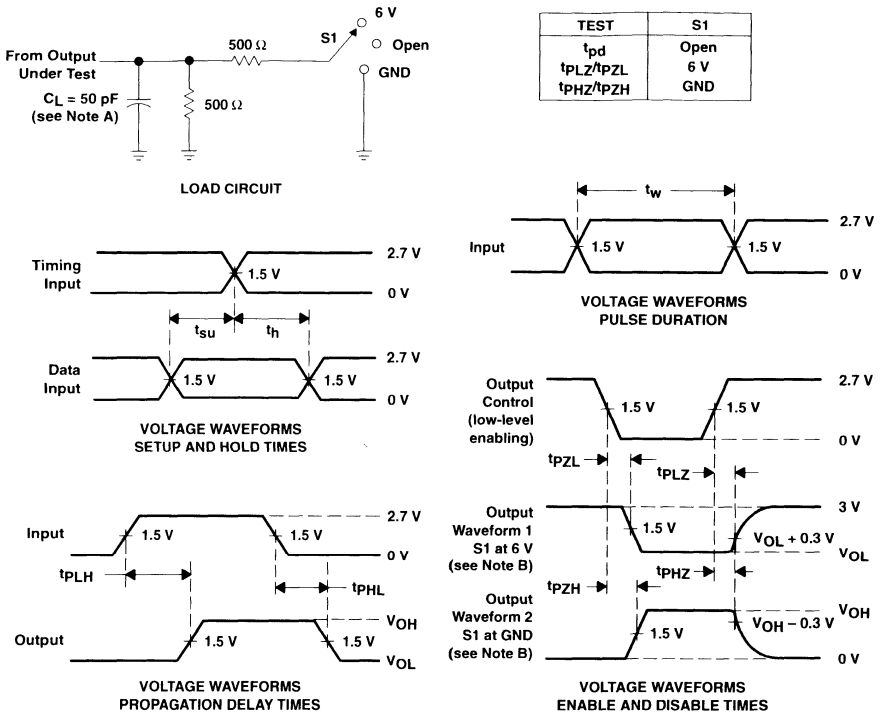
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	3.8		4.7	ns
$t_{sk(o)}$‡				1			ns

‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF, f = 10 MHz	5	pF

PARAMETER MEASUREMENT INFORMATION

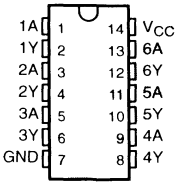


NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, $Z_O = 50\ \Omega$, $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

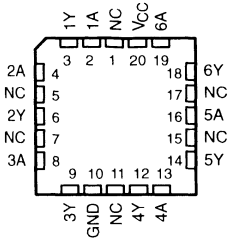
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Inputs and Open-Drain Outputs Accept Voltages up to 5.5 V**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs**

SN54LVC06A . . . J OR W PACKAGE
SN74LVC06A . . . D, DGV, OR PW PACKAGE
(TOP VIEW)



SN54LVC06A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These hex inverter buffers/drivers are designed for 2.3-V to 3.6-V V_{CC} operation.

The outputs of the 'LVC06A devices are open drain and can be connected to other open-drain outputs to implement active-low wired-OR or active-high wired-AND functions. The maximum sink current is 24 mA.

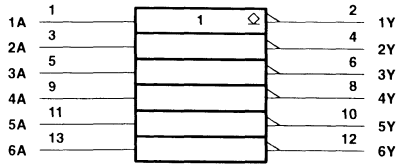
Inputs can be driven from 2.5-V, 3.3-V, or 5-V devices. This feature allows the use of these devices as translators in a mixed system environment.

The SN54LVC06A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC06A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DGV, and PW packages.

logic diagram, each inverter (positive logic)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O ..... –0.5 V to 6.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, Θ_{JA} (see Note 3): D package ..... 127°C/W
DGV package ..... 182°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC06A		SN74LVC06A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.3	3.6	2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8		0.8	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	5.5	0	5.5	V
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12		12	mA
		V_{CC} = 2.7 V		12		12	
		V_{CC} = 3 V		24		24	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent the device from malfunctioning.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	SN54LVC06A			SN74LVC06A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OL}	I_{OL} = 100 µA		2.3 V to 3.6 V			0.2			0.2	V
	I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4			0.4	
	I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7			0.7	
		V_{IL} = 0.8 V	2.7 V			0.4			0.4	
	I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC06A						UNIT
			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	3.1		3.9	1	3.7	ns

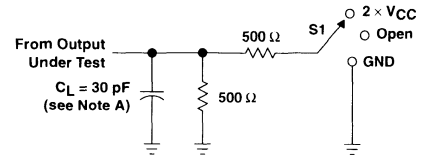
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LVC06A						UNIT
			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	3.1		3.9	1	3.7	ns

operating characteristics, T_A = 25°C

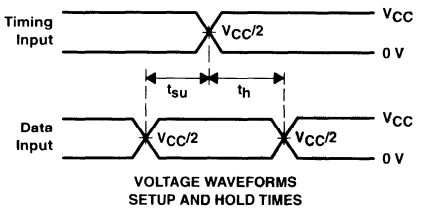
PARAMETER		TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
			TYP	TYP	
C_{pd}	Power dissipation capacitance per inverter	C_L = 0, f = 10 MHz	2	2.5	pF

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

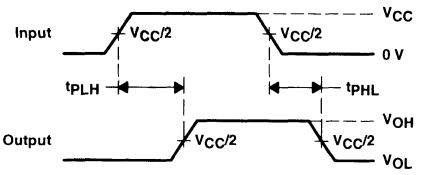


LOAD CIRCUIT

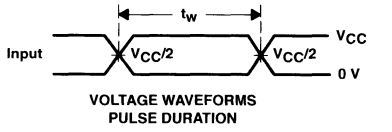
TEST	S1
t_{PZL} (see Note F)	2 × V_{CC}
t_{PLZ} (see Note G)	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



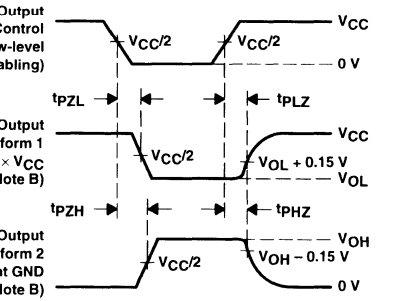
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

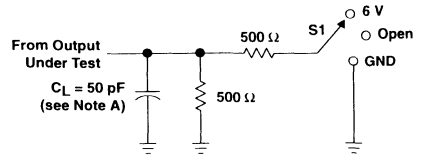


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. Since this device has open-drain outputs, t_{PLZ} and t_{PZL} are the same as t_{pd}.
F. t_{PZL} is measured at $V_{CC}/2$.
G. t_{PLZ} is measured at V_{OL} + 0.15 V.

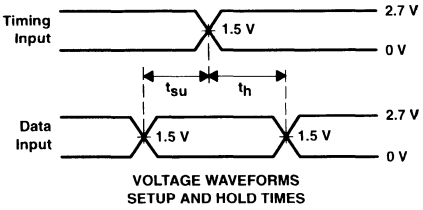
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 AND 3.3 V ± 0.3 V

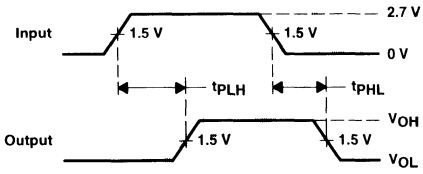


LOAD CIRCUIT

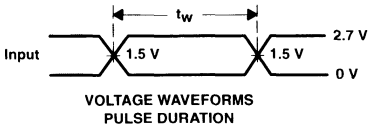
TEST	S1
t_{PZL} (see Note F)	6 V
t_{PLZ} (see Note G)	6 V
t_{PHZ}/t_{PZH}	GND



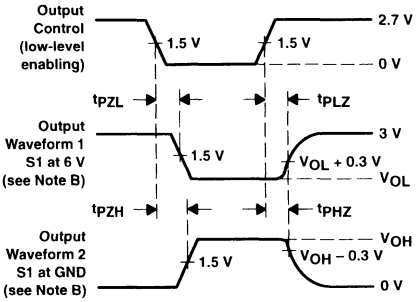
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



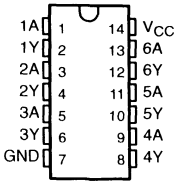
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. Since this device has open-drain outputs, t_{PLZ} and t_{PZL} are the same as t_{pd}.
F. t_{PZL} is measured at 1.5 V.
G. t_{PLZ} is measured at V_{OL} + 0.3 V.

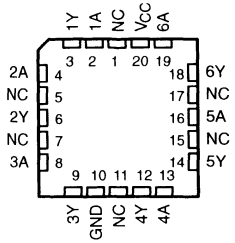
Figure 2. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Inputs and Open-Drain Outputs Accept Voltages Up to 5.5 V**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs**

SN54LVC07A . . . J OR W PACKAGE
SN74LVC07A . . . D, DGV, OR PW PACKAGE
(TOP VIEW)



SN54LVC07A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These hex buffers/drivers are designed for 2.3-V to 3.6-V V_{CC} operation.

The outputs of the 'LVC07A devices are open drain and can be connected to other open-drain outputs to implement active-low wired-OR or active-high wired-AND functions. The maximum sink current is 24 mA.

Inputs can be driven from 2.5-V, 3.3-V, or 5-V devices. This feature allows the use of these devices as translators in a mixed system environment.

The SN54LVC07A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC07A is characterized for operation from –40°C to 85°C.

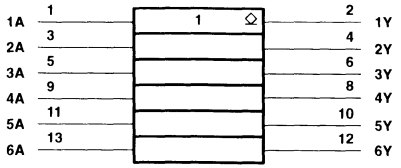
FUNCTION TABLE
(each buffer/driver)

INPUT A	OUTPUT Y
H	H
L	L

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DGV, J, PW, and W packages.

logic diagram, each buffer/driver (positive logic)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O ..... –0.5 V to 6.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DGV package ..... 182°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC07A		SN74LVC07A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.3	3.6	2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8		0.8	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	5.5	0	5.5	V
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12		12	mA
		V_{CC} = 2.7 V		12		12	
		V_{CC} = 3 V		24		24	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent the device from malfunctioning.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC07A			SN74LVC07A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OL}	I_{OL} = 100 µA	2.3 V to 3.6 V			0.2			0.2	V
	I_{OL} = 6 mA	2.3 V			0.4			0.4	
	I_{OL} = 12 mA	2.3 V			0.7			0.7	
		2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC07A						UNIT
			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	2.8		3	1	2.9	ns

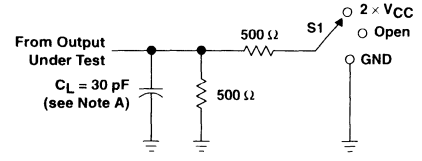
switching characteristics over recommended operating free-air temperature range, (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LVC07A						UNIT
			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	2.8		3	1	2.9	ns

operating characteristics, T_A = 25°C

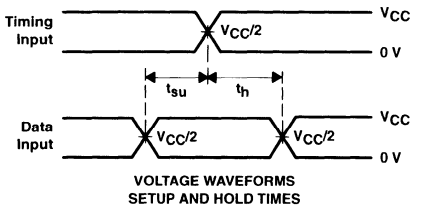
PARAMETER		TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
			TYP	TYP	
C_{pd}	Power dissipation capacitance per buffer/driver	C_L = 0, f = 10 MHz	1.9	2.5	pF

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

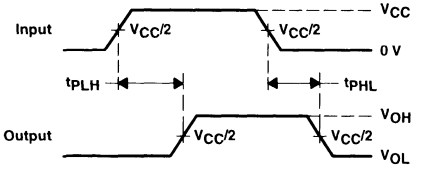


LOAD CIRCUIT

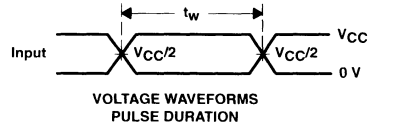
TEST	S1
t_{PZL} (see Note F)	2 × V_{CC}
t_{PLZ} (see Note G)	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



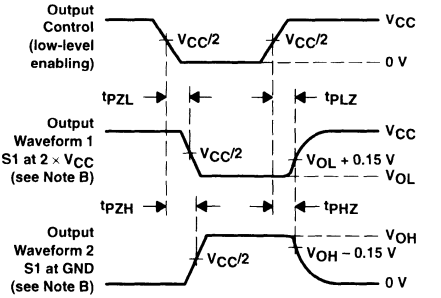
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

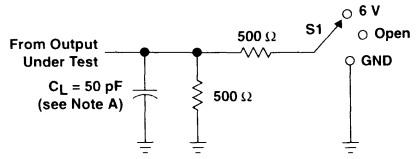


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. Since this device has open-drain outputs, t_{PLZ} and t_{PZL} are the same as t_{pd}.
F. t_{PZL} is measured at $V_{CC}/2$.
G. t_{PLZ} is measured at V_{OL} + 0.15 V.

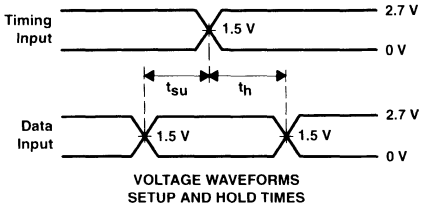
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 AND 3.3 V ± 0.3 V

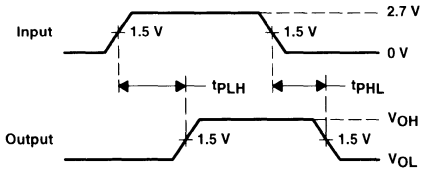


LOAD CIRCUIT

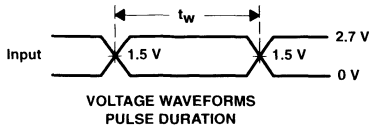
TEST	S1
t_{PZL} (see Note F)	6 V
t_{PLZ} (see Note G)	6 V
t_{PHZ}/t_{PZH}	GND



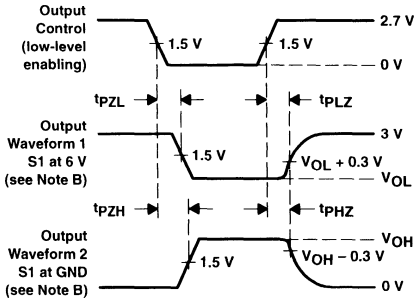
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



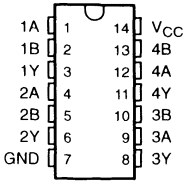
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. Since this device has open-drain outputs, t_{PLZ} and t_{PZL} are the same as t_{pd}.
F. t_{PZL} is measured at 1.5 V.
G. t_{PLZ} is measured at V_{OL} + 0.3 V.

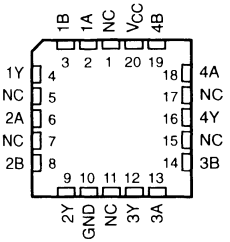
Figure 2. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Inputs Accept Voltages to 5.5 V**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK) and Flat (W) Packages, and DIPs (J)**

SN54LVC08A . . . J OR W PACKAGE
SN74LVC08A . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVC08A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These quadruple 2-input positive-AND gates are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC08A perform the Boolean function $Y = A \bullet B$ or $Y = \overline{\overline{A} + \overline{B}}$ in positive logic.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-/5-V system environment.

The SN54LVC08A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC08A is characterized for operation from –40°C to 85°C.

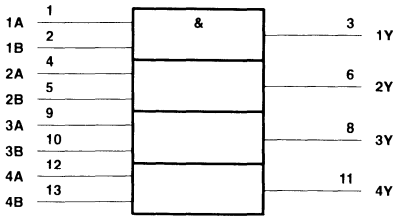
FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	H	H
L	X	L
X	L	L

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

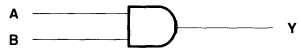
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, PW, and W packages.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			SN54LVC08A		SN74LVC08A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	8	0	8	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC08A			SN74LVC08A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 μA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			2.2			
		3 V	2.4			2.4			
	I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 μA	2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	μA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	μA
C_i	V_I = V_{CC} or GND	3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

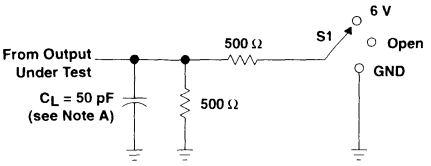
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC08A				SN74LVC08A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	4.1		4.8	1	4.1		4.8	ns
$t_{sk(o)}$‡*				1				1			ns

* On products compliant to MIL-PRF-38535, this parameter does not apply.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

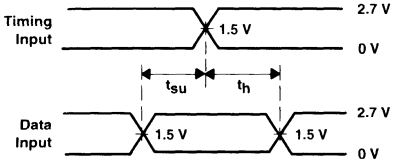
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	10	pF

PARAMETER MEASUREMENT INFORMATION

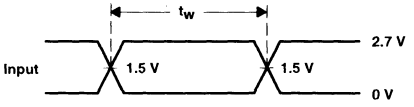


LOAD CIRCUIT

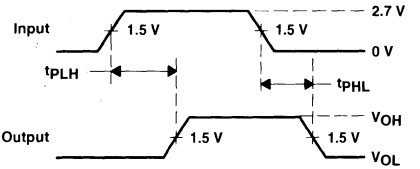
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



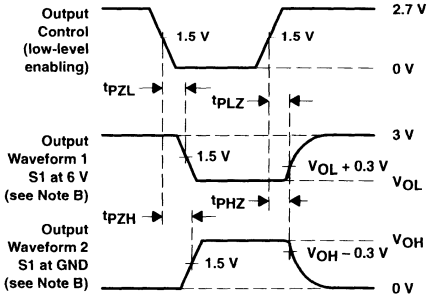
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



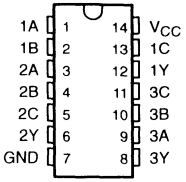
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This triple 3-input positive-NAND gate is designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVC10A performs the Boolean function $Y = \overline{A \bullet B \bullet C}$ or $Y = \overline{A} + \overline{B} + \overline{C}$ in positive logic.

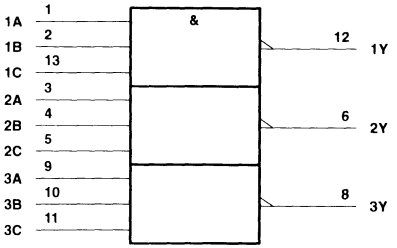
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC10A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

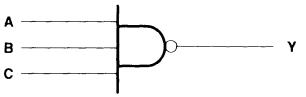
INPUTS			OUTPUT
A	B	C	Y
H	H	H	L
L	X	X	H
X	L	X	H
X	X	L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

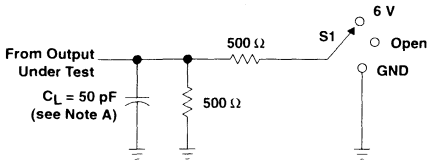
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.9		5.8	ns
$t_{sk(o)}$‡				1			ns

‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

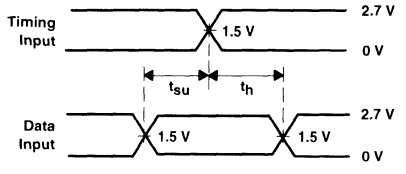
PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF,	f = 10 MHz	11	pF

PARAMETER MEASUREMENT INFORMATION

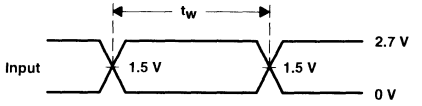


LOAD CIRCUIT

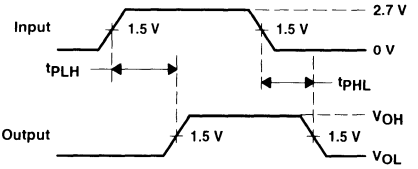
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



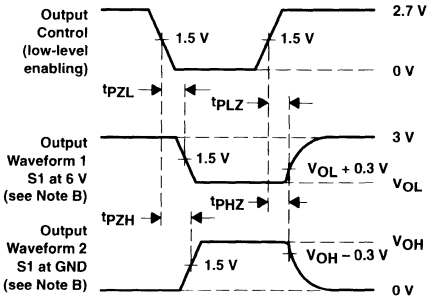
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



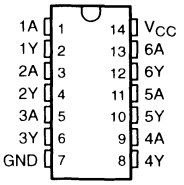
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

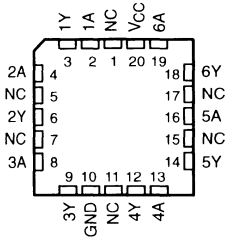
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Inputs Accept Voltages to 5.5 V**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs**

SN54LVC14A . . . J OR W PACKAGE
SN74LVC14A . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVC14 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

This hex Schmitt-trigger inverter is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC14A contains six independent inverters, and performs the Boolean function $Y = \overline{A}$.

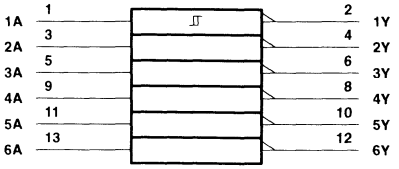
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN54LVC14A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC14A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

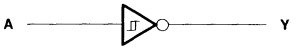
INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, N, PW, and W packages.

logic diagram, each inverter (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply-voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input-voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output-voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC14A		SN74LVC14A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC14A			SN74LVC14A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{T+} Positive-going threshold		2.7 V	0.8		2	0.8		2	V
		3 V	0.8		2	0.8		2	
		3.6 V	0.8		2	0.8		2	
V_{T-} Negative-going threshold		2.7 V	0.4		1.4	0.4		1.4	V
		3 V	0.6		1.5	0.6		1.5	
		3.6 V	0.8		1.8	0.8		1.8	
ΔV_T Hysteresis ($V_{T+} - V_{T-}$)		2.7 V	0.3		1.1	0.3		1.1	V
		3 V	0.3		1.2	0.3		1.2	
		3.6 V	0.3		1.2	0.3		1.2	
V_{OH}	I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			2.2			
		3 V	2.4			2.4			
	I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA	2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	µA
I_{CC}	$V_I = V_{CC}$ or GND, I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	$V_I = V_{CC}$ or GND	3.3 V		5			5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

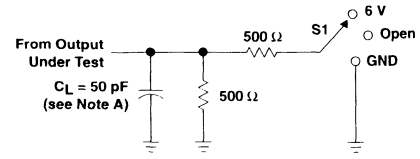
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC14A				SN74LVC14A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	6.4		7.5	1	6.4		7.5	ns
$t_{sk(o)}$†								1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

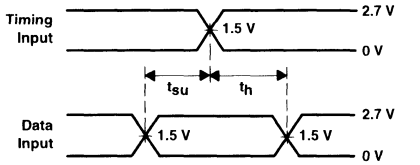
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF, f = 10 MHz	7	pF

PARAMETER MEASUREMENT INFORMATION

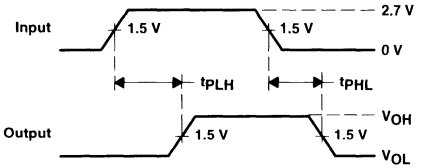


LOAD CIRCUIT

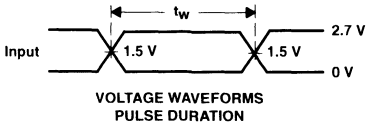
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



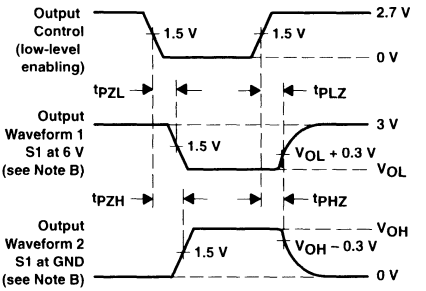
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



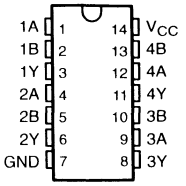
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

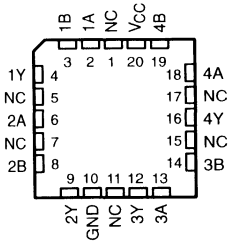
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs

SN54LVC32A . . . J OR W PACKAGE
SN74LVC32A . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVC32A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These quadruple 2-input positive-OR gates are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC32A devices perform the Boolean function $Y = A + B$ or $Y = \overline{\overline{A} \bullet \overline{B}}$ in positive logic.

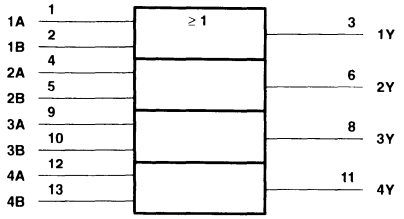
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN54LVC32A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC32A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	X	H
X	H	H
L	L	L

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, PW, and W packages.

logic diagram, each gate (positive logic)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0) ..... –50 mA
Continuous output current, I_O ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC32A		SN74LVC32A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	7	0	7	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC32A			SN74LVC32A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			2.2			
		3 V	2.4			2.4			
	I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA	2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	µA
I_{CC}	$V_I = V_{CC}$ or GND, I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	$V_I = V_{CC}$ or GND	3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

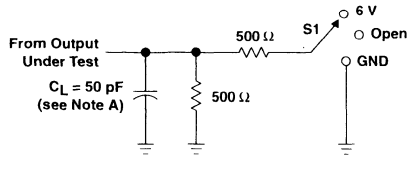
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC32A				SN74LVC32A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	3.8		4.4	1.5	3.8		4.4	ns
$t_{sk(o)}$‡								1			ns

‡ Skew between any two outputs of the same package switching in the same direction.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

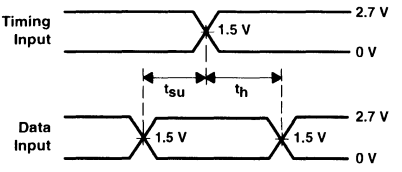
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	12.5	pF

PARAMETER MEASUREMENT INFORMATION

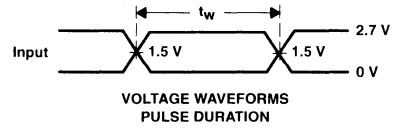


LOAD CIRCUIT

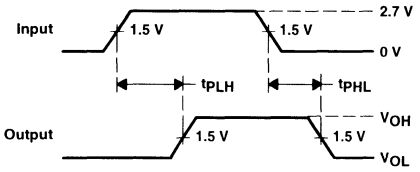
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



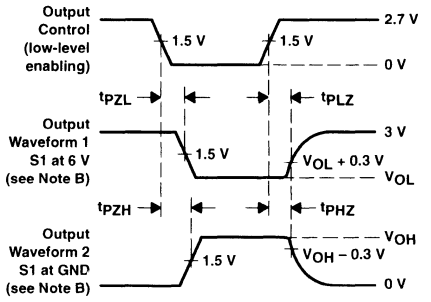
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



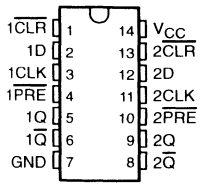
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

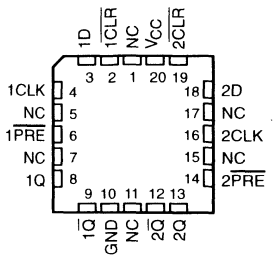
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Inputs Accept Voltages to 5.5 V**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and 300-mil DIPs (J)**

SN54LVC74A . . . J OR W PACKAGE
SN74LVC74A . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVC74A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These dual positive-edge-triggered D-type flip-flops are designed for 2.7-V to 3.6-V V_{CC} operation.

A low level at the preset ($\overline{PRE}$) or clear ($\overline{CLR}$) inputs sets or resets the outputs, regardless of the levels of the other inputs. When $\overline{PRE}$ and $\overline{CLR}$ are inactive (high), data at the data (D) input meeting the setup time requirements is transferred to the outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the D input can be changed without affecting the levels at the outputs.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

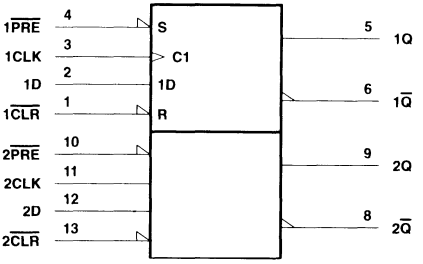
The SN54LVC74A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC74A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUTS	
$\overline{PRE}$	$\overline{CLR}$	CLK	D	Q	$\overline{Q}$
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H†	H†
H	H	↑	H	H	L
H	H	↑	L	L	H
H	H	L	X	Q_0	$\overline{Q}_0$

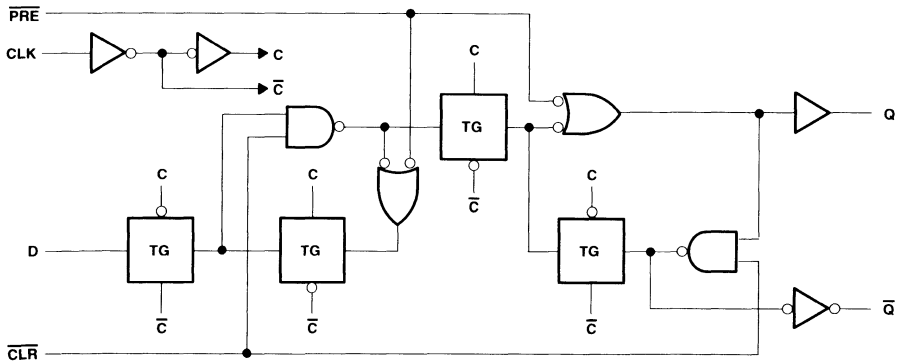
† This configuration is unstable; that is, it does not persist when $\overline{PRE}$ or $\overline{CLR}$ returns to its inactive (high) level.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, PW, and W packages.

logic diagram, each flip-flop (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply-voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input-voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output-voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC74A		SN74LVC74A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	0	10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC74A			SN74LVC74A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			2.2			
		3 V	2.4			2.4			
	I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA	2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN54LVC74A				SN74LVC74A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	100	0	83	0	100	0	83	MHz
t_w	Pulse duration	$\overline{PRE}$ or $\overline{CLR}$ low	3.3		3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		3.3		
t_{su}	Setup time before CLK↑	Data	3		3.4		3		3.4		ns
		$\overline{PRE}$ or $\overline{CLR}$ inactive	2		2.2		2		2.2		
t_h	Hold time, data after CLK↑		1		1		0		1		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

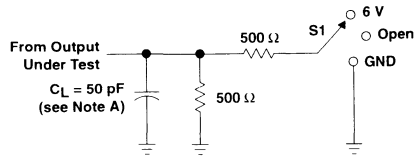
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC74A				SN74LVC74A				UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			100		83		100		83		MHz
t_{pd}	CLK	Q or $\overline{Q}$	1	5.2		6	1	5.2		6	ns
	$\overline{PRE}$ or $\overline{CLR}$		1	5.4		6.4	1	5.4		6.4	
$t_{sk(o)}$*‡								1			ns

* For products compliant to MIL-PRF-38535, this parameter does not apply.
‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

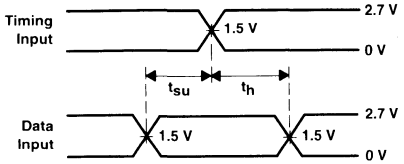
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	C_L = 50 pF, f = 10 MHz	27	pF

PARAMETER MEASUREMENT INFORMATION

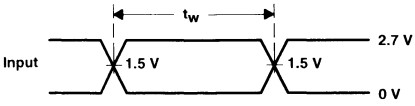


LOAD CIRCUIT

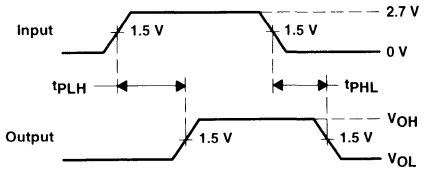
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



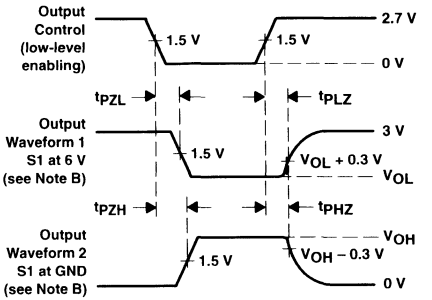
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



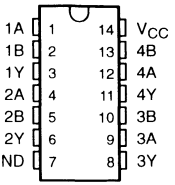
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

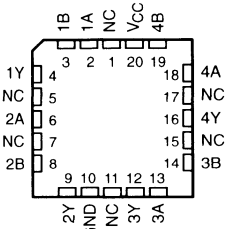
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages, Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs

SN54LVC86A . . . J OR W PACKAGE
SN74LVC86A . . . D, DB, DGV, OR PW PACKAGE
(TOP VIEW)



SN54LVC86A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These quadruple 2-input exclusive-OR gates are designed for 2.7-V to 3.6-V V_{CC} operation. The 'LVC86A devices perform the Boolean function $Y = A \oplus B$ or $Y = A\overline{B} + \overline{A}B$ in positive logic.

A common application is as a true/complement element. If one of the inputs is low, the other input is reproduced in true form at the output. If one of the inputs is high, the signal on the other input is reproduced inverted at the output.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN54LVC86A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC86A is characterized for operation from –40°C to 85°C.

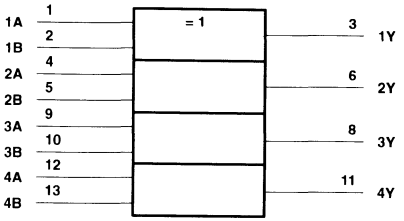
FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC is a trademark of Texas Instruments Incorporated.

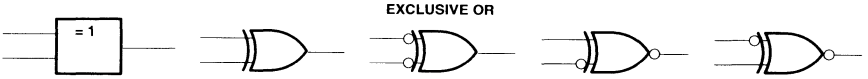
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, DGV, J, PW, and W packages.

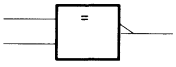
exclusive-OR logic

An exclusive-OR gate has many applications, some of which can be represented better by alternative logic symbols.



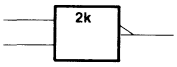
These five equivalent exclusive-OR symbols are valid for an SN74LVC86A gate in positive logic; negation may be shown at any two ports.

LOGIC-IDENTITY ELEMENT



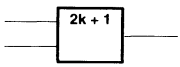
The output is active (low) if all inputs stand at the same logic level (i.e., A = B).

EVEN-PARITY ELEMENT



The output is active (low) if an even number of inputs (i.e., 0 or 2) are active.

ODD-PARITY ELEMENT



The output is active (high) if an odd number of inputs (i.e., only 1 of the 2) are active.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package . . . . . 127°C/W
DB package . . . . . 158°C/W
PW package . . . . . 170°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC86A		SN74LVC86A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	9	0	9	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC86A			SN74LVC86A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			2.2			
		3 V	2.4			2.4			
	I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA	2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

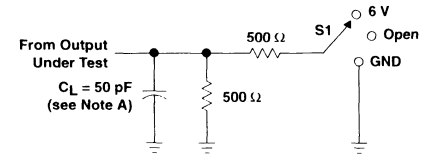
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC86A				SN74LVC86A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.6		5.6	1	4.6		5.6	ns
$t_{sk(o)}$‡				1*				1			ns

* On products not compliant to MIL-PRF-38535, this parameter is not production tested.
‡ Skew between any two outputs of the same package switching in the same direction.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

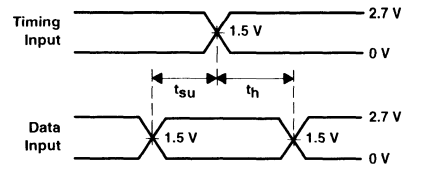
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	8.5	pF

PARAMETER MEASUREMENT INFORMATION

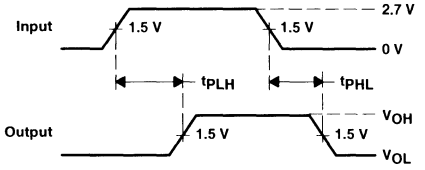


LOAD CIRCUIT

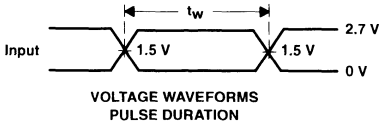
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



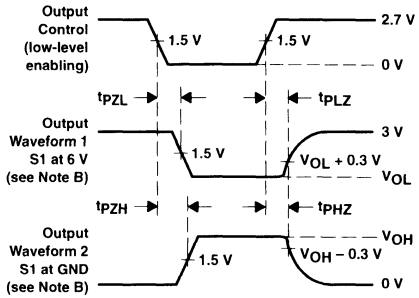
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



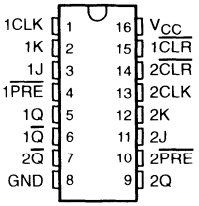
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This dual negative-edge-triggered J-K flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

A low level at the preset ($\overline{PRE}$) or clear ($\overline{CLR}$) inputs sets or resets the outputs, regardless of the levels of the other inputs. When $\overline{PRE}$ and $\overline{CLR}$ are inactive (high), data at the J and K inputs meeting the setup time requirements is transferred to the outputs on the negative-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the J and K inputs can be changed without affecting the levels at the outputs. The SN74LVC112A can perform as a toggle flip-flop by tying J and K high.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC112A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

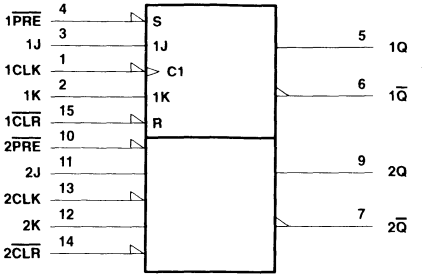
INPUTS					OUTPUTS	
$\overline{PRE}$	$\overline{CLR}$	CLK	J	K	Q	$\overline{Q}$
L	H	X	X	X	H	L
H	L	X	X	X	L	H
L	L	X	X	X	H†	H†
H	H	↓	L	L	Q_0	$\overline{Q}_0$
H	H	↓	H	L	H	L
H	H	↓	L	H	L	H
H	H	↓	H	H	Toggle	
H	H	H	X	X	Q_0	$\overline{Q}_0$

† The output levels in this configuration may not meet the minimum levels for V_{OH}. Furthermore, this configuration is unstable; that is, it does not persist when either $\overline{PRE}$ or $\overline{CLR}$ returns to its inactive (high) level.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

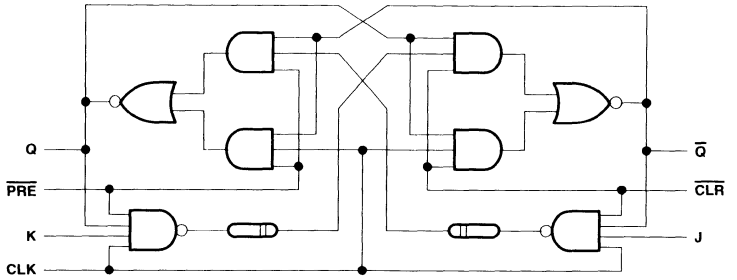
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each flip-flop (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 113°C/W
DB package ..... 131°C/W
PW package ..... 149°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		4.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		ns
t_{su}	Setup time	Data before CLK↓	3.1		2.3		ns
		$\overline{PRE}$ or $\overline{CLR}$ inactive	2.4		1.1		
t_h	Hold time, data after CLK↓		2.5		0.7		ns

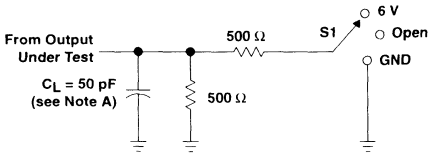
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
f_{max}			150			150		MHz
t_{pd}	$\overline{CLR}$ or $\overline{PRE}$	Q or $\overline{Q}$	1	3.4	4.8		5.5	ns
	CLK		1	3.5	5.9		7.1	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

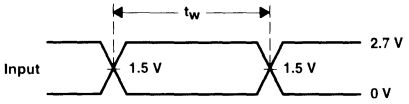
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 50 pF,	f = 10 MHz	24	pF

PARAMETER MEASUREMENT INFORMATION

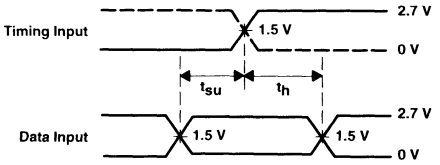


LOAD CIRCUIT

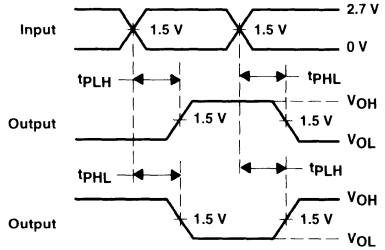
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



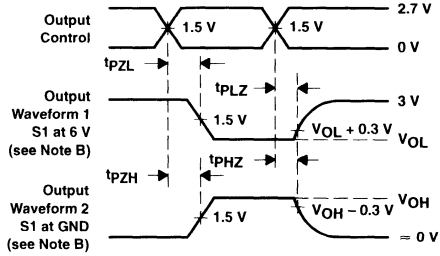
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



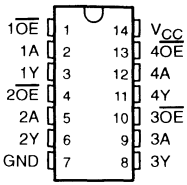
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Inputs Accept Voltages to 5.5 V**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple bus buffer gate is designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVC125A features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable ($\overline{OE}$) input is high.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC125A is characterized for operation from –40°C to 85°C.

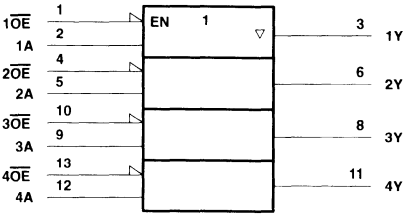
FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

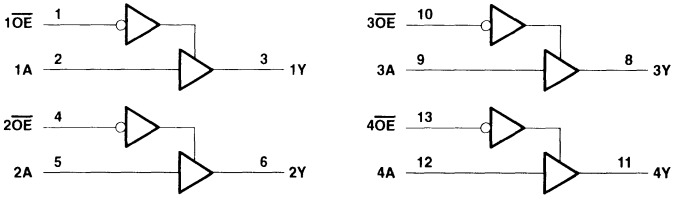
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stressratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	8	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF
C_o	V_O = V_{CC} or GND		3.3 V		5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

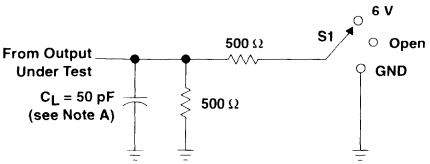
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.8		5.5	ns
t_{en}	$\overline{OE}$	Y	1	5.4		6.6	ns
t_{dis}	$\overline{OE}$	Y	1	4.6		5	ns
$t_{sk(o)}$‡				1			ns

‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

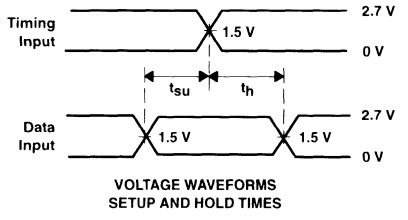
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	15	pF

PARAMETER MEASUREMENT INFORMATION

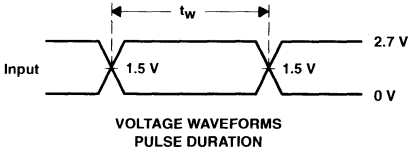


LOAD CIRCUIT

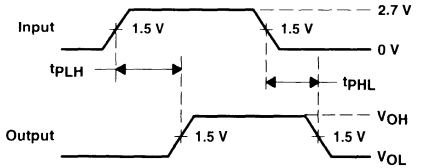
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



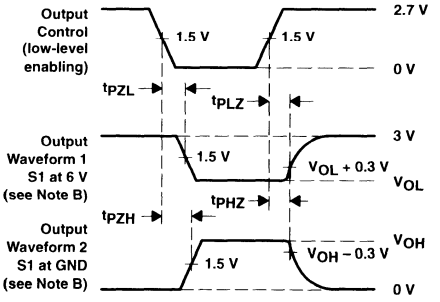
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



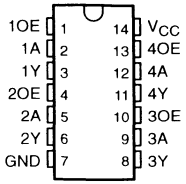
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Inputs Accept Voltages to 5.5 V**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple bus buffer gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC126A features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (OE) input is low.

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

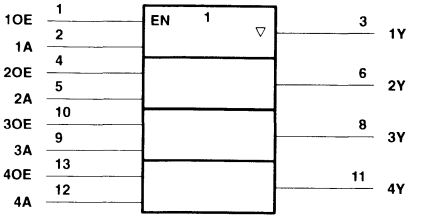
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC126A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

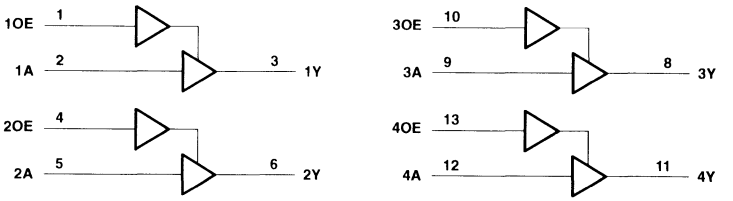
INPUTS		OUTPUT
OE	A	Y
H	H	H
H	L	L
L	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{OZ}	$V_O = V_{CC}$ or GND		3.6 V			±10	μA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	$V_I = V_{CC}$ or GND		3.3 V		4.5		pF
C_o	$V_O = V_{CC}$ or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

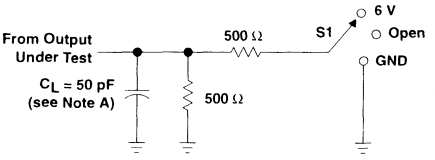
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.7		5.2	ns
t_{en}	OE	Y	1	5.7		6.3	ns
t_{dis}	OE	Y	1.3	6		6.7	ns
$t_{sk(o)}$‡				1			ns

‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

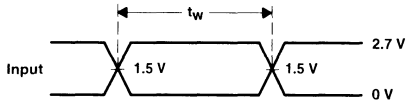
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	Outputs enabled	C_L = 50 pF, f = 10 MHz	22	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

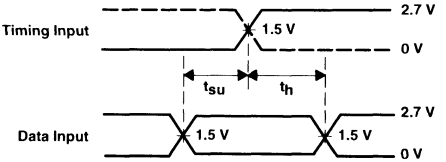


LOAD CIRCUIT

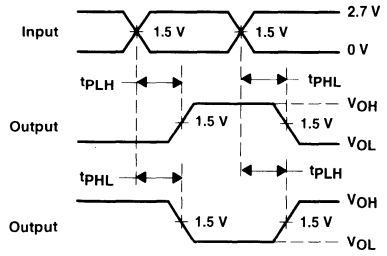
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



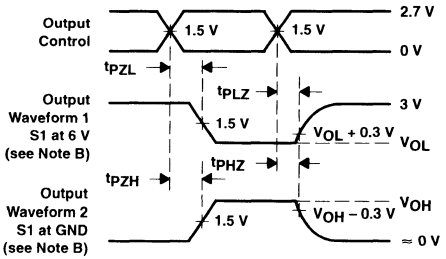
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



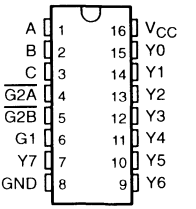
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

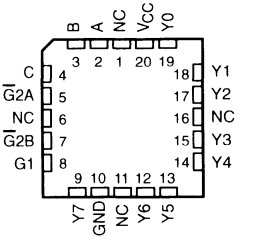
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK) and Flat (W) Packages, and DIPs (J)

SN54LVC138A . . . J OR W PACKAGE
SN74LVC138A . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVC138A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These 3-line to 8-line decoders/demultiplexers are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC138A are designed for high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, these decoders minimize the effects of system decoding. When employed with high-speed memories utilizing a fast enable circuit, the delay times of these decoders and the enable time of the memory are usually less than the typical access time of the memory. This means that the effective system delay introduced by the decoders is negligible.

The conditions at the binary-select inputs and the three enable inputs select one of eight output lines. Two active-low enable inputs and one active-high enable input reduce the need for external gates or inverters when expanding. A 24-line decoder can be implemented without external inverters and a 32-line decoder requires only one inverter. An enable input can be used as a data input for demultiplexing applications.

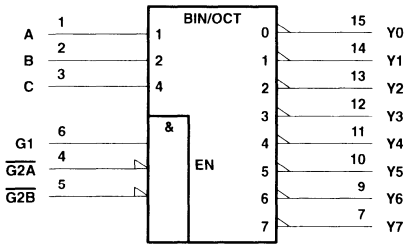
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

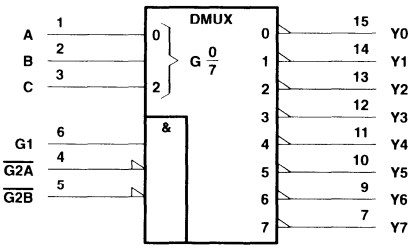
The SN54LVC138A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC138A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

ENABLE INPUTS			SELECT INPUTS			OUTPUTS							
G1	$\overline{G2A}$	$\overline{G2B}$	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	H	X	X	X	X	H	H	H	H	H	H	H	H
X	X	H	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	H	L	H	H	H	H
H	L	L	H	L	L	H	H	H	H	L	H	H	H
H	L	L	H	L	H	H	H	H	H	H	L	H	H
H	L	L	H	H	L	H	H	H	H	H	H	L	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

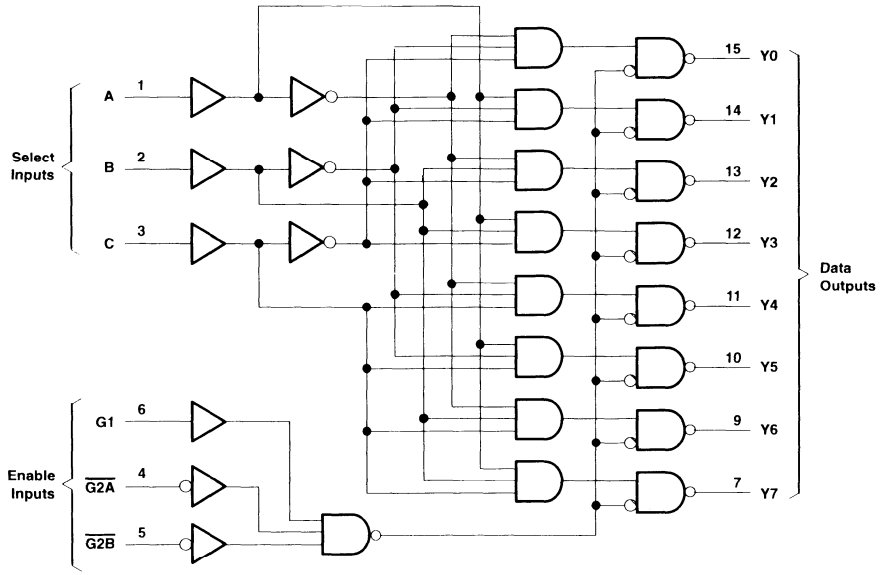
logic symbols (alternatives)†





† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, PW, and W packages.

logic diagram (positive logic)



Pin numbers shown are for the D, DB, J, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 113°C/W
DB package ..... 131°C/W
PW package ..... 149°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			SN54LVC138A		SN74LVC138A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	0	10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC138A			SN74LVC138A			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			2.2			
		3 V	2.4			2.4			
	I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA	2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4			0.4	
	I_{OL} = 24 mA	3 V			0.55			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5			±5	µA
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±10			±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5			5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

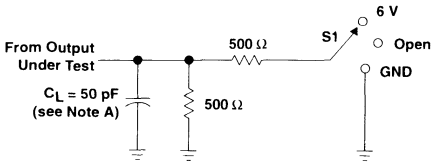
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC138A				SN74LVC138A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B or C	Y	1	6.7		7.9	1	6.7		7.9	ns
	$\overline{G2A}$ or $\overline{G2B}$		1	6.5		7.4	1	6.5		7.4	
	G1		1	5.8		6.4	1	5.8		6.4	
$t_{sk(o)}$†*				1				1			ns

* On products compliant to MIL-PRF-38535, this parameter does not apply.
† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

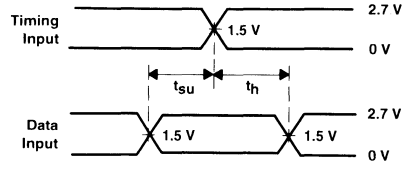
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	27	pF

PARAMETER MEASUREMENT INFORMATION

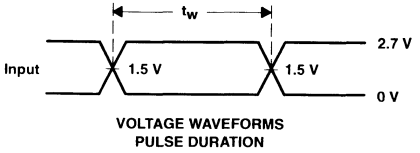


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

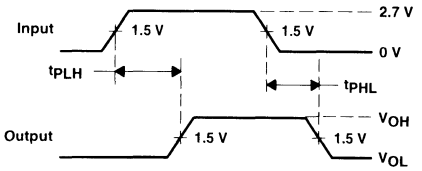
LOAD CIRCUIT



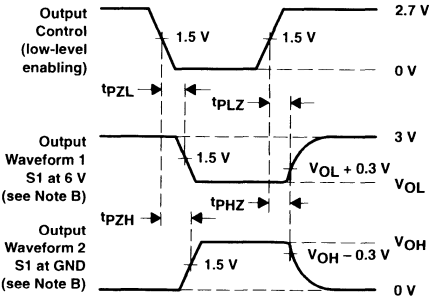
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

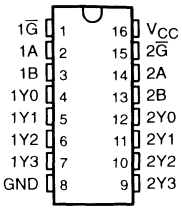
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

SCAS341E – MARCH 1994 – REVISED JANUARY 1998

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Inputs Accept Voltages to 5.5 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This dual 2-line to 4-line decoder/demultiplexer is designed for 2.7-V to 3.6-V V_{CC} operation.

The device comprises two individual 2-line to 4-line decoders in a single package. The active-low enable ($\overline{G}$) input can be used as a data line in demultiplexing applications. These decoders/demultiplexers feature fully buffered inputs, each of which represents only one normalized load to its driving circuit.

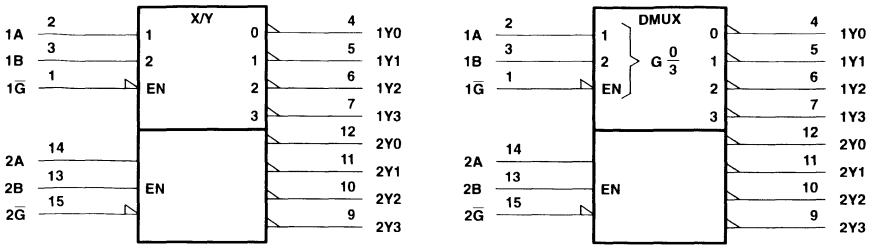
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC139A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each decoder/demultiplexer)

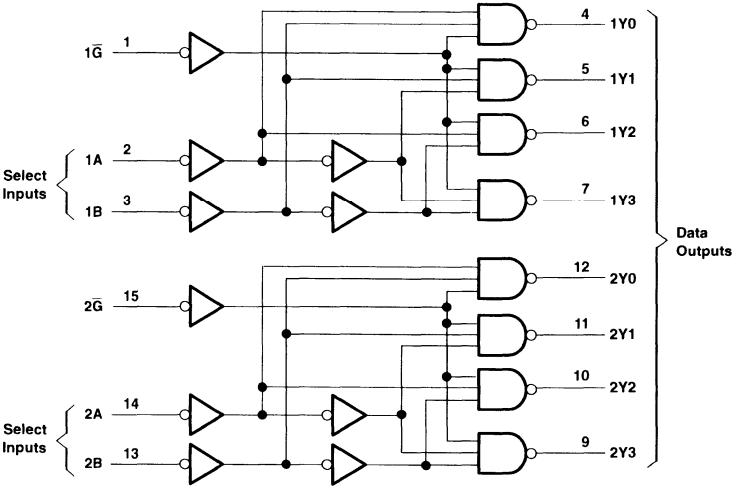
INPUTS			OUTPUTS			
$\overline{G}$	SELECT					
	B	A	Y3	Y2	Y1	Y0
L	L	L	H	H	H	L
L	L	H	H	H	L	H
L	H	L	H	L	H	H
L	H	H	L	H	H	H
H	X	X	H	H	H	H

logic symbols (alternatives)†



† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0) ..... –50 mA
Continuous output current, I_O ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 113°C/W
DB package ..... 131°C/W
PW package ..... 149°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall time		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	$V_I = V_{CC}$ or GND		3.3 V		5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	6.2		7.3	ns
	$\overline{G}$		1	4.7		5.2	
$t_{sk(o)}$‡				1		1	ns

‡ Skew between any two outputs of the same package switching in the same direction.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 0,	f = 10 MHz	30.5	pF

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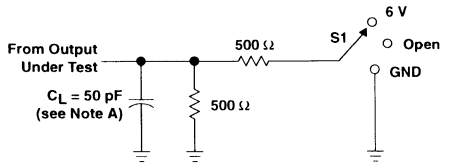
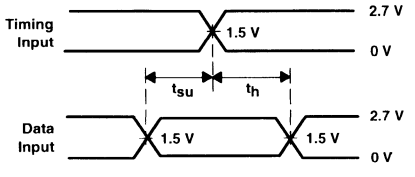
PARAMETER MEASUREMENT INFORMATION

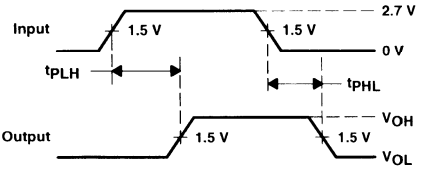


LOAD CIRCUIT

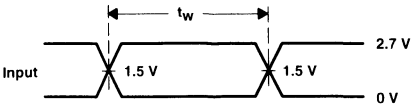
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



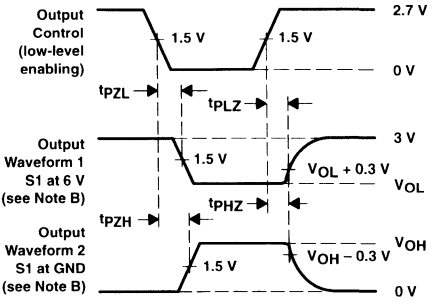
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

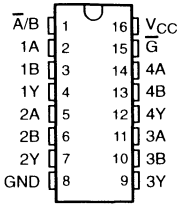
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

SCAS292D – JANUARY 1993 – REVISED JANUARY 1997

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-line to 1-line data selector/multiplexer is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC157A features a common strobe ($\overline{G}$) input. When the strobe is high, all outputs are low. When the strobe is low, a 4-bit word is selected from one of two sources and is routed to the four outputs. The device provides true data.

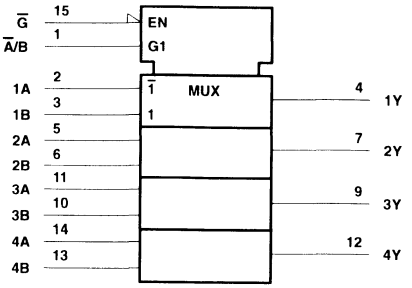
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC157A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

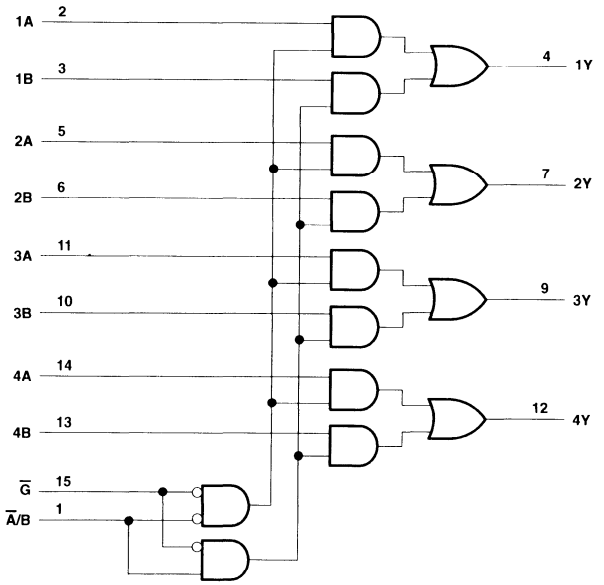
INPUTS				OUTPUT
$\overline{G}$	$\overline{A}$/B	A	B	Y
H	X	X	X	L
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package . . . . . 113°C/W
DB package . . . . . 131°C/W
PW package . . . . . 149°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	$V_I = V_{CC}$ or GND		3.3 V		5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

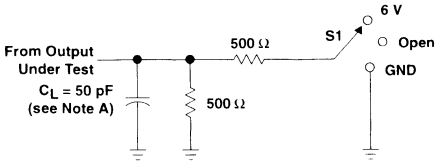
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	5.2		5.9	ns
	$\overline{A}$/B		1	6.8		8.1	
	$\overline{G}$		1	6.5		7.8	
$t_{sk(o)}$‡				1			ns

‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

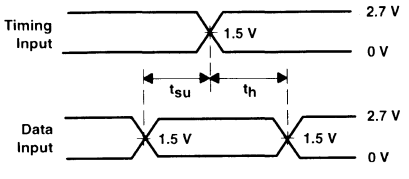
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	16	pF

PARAMETER MEASUREMENT INFORMATION

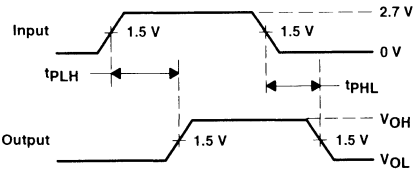


LOAD CIRCUIT

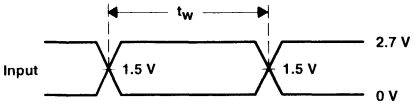
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



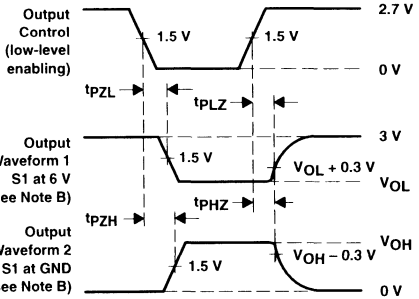
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



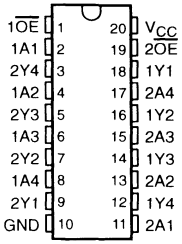
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC240A is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

This device is organized as two 4-bit buffers/drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

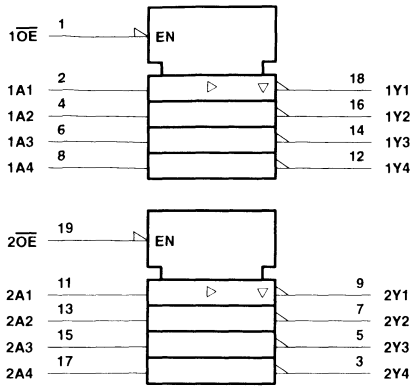
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC240A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

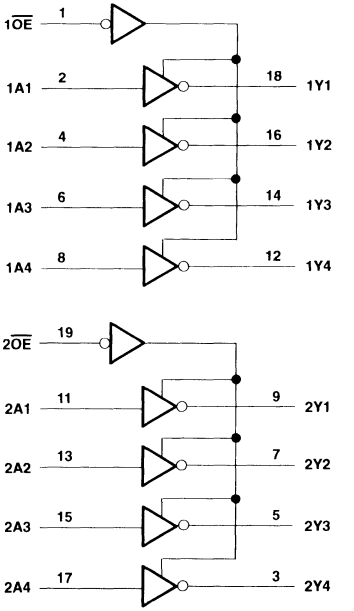
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	6	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			10	µA
	3.6 V ≤ V_I ≤ 5.5 V‡					10	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.3	6.5		7.5	ns
t_{en}	$\overline{OE}$	Y	1.1	8		9	ns
t_{dis}	$\overline{OE}$	Y	1.4	7		8	ns
$t_{sk(o)}$§				1			ns

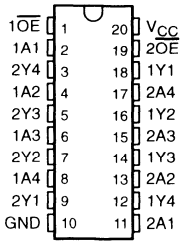
§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0, f = 10 MHz	32	pF
		Outputs disabled		3	

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Package Options Include Shrink Small-Outline (DB), Plastic Small-Outline (DW), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/line driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC244A is organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC244A is characterized for operation from –40°C to 85°C.

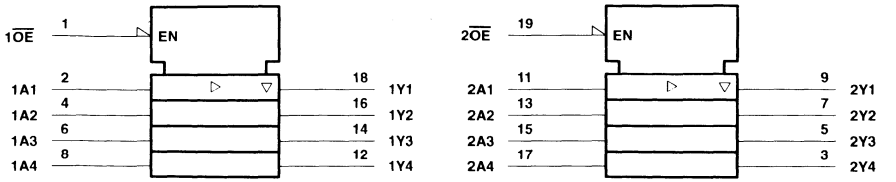
FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

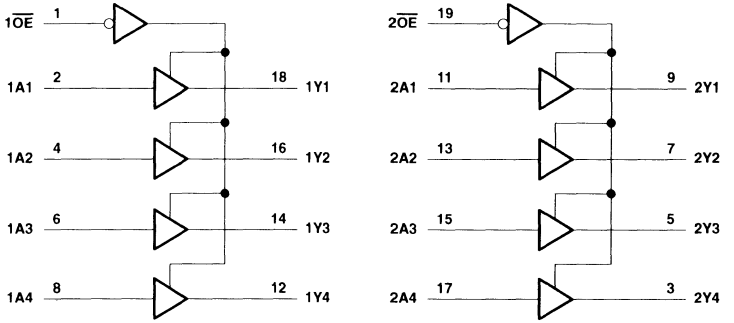
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DW package ..... 97°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			10	µA
	3.6 V ≤ V_I ≤ 5.5 V‡					10	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

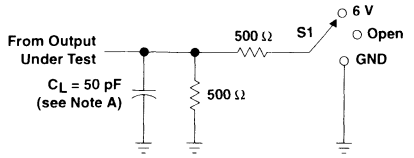
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	4.9		5.9	ns
t_{en}	$\overline{OE}$	Y	1.5	6.2		7.6	ns
t_{dis}	$\overline{OE}$	Y	1.5	6.5		7	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

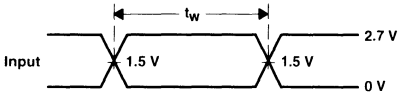
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0, f = 10 MHz	44	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

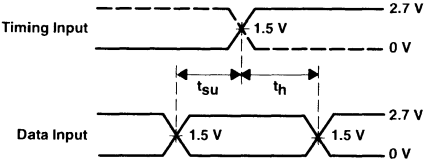


LOAD CIRCUIT

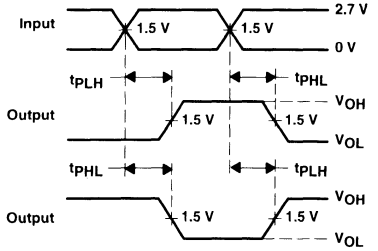
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



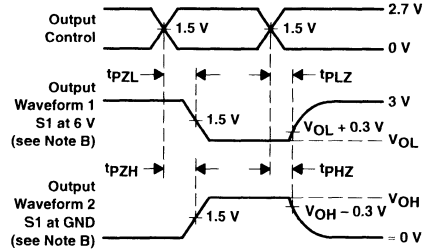
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



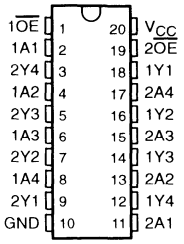
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O ~ 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

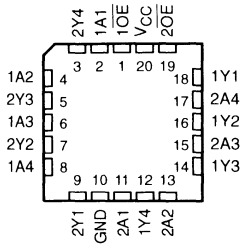
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Support Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Flat (W) Package, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

SN54LVCH244A . . . J OR W PACKAGE
SN74LVCH244A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVCH244A . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/line drivers are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVCH244A are organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, these devices pass data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

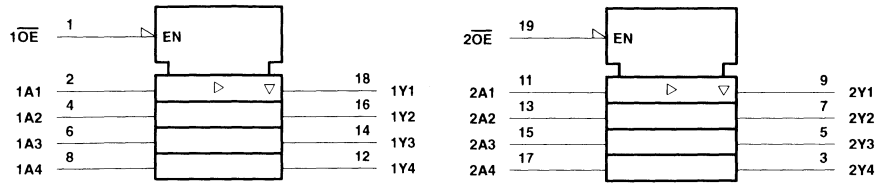
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVCH244A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVCH244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

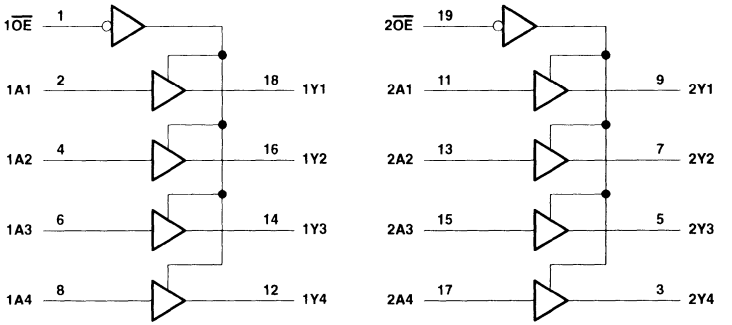
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVCH244A		SN74LVCH244A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	0	10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	SN54LVCH244A			SN74LVCH244A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			2.2			
			3 V	2.4			2.4			
	I_{OH} = –24 mA		3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 μA		2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4			0.4	
	I_{OL} = 24 mA		3 V			0.55			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±15			±5	μA
I_{off}	V_I or V_O = 5.5 V		0						±10	μA
$I_{I(hold)}$	V_I = 0.8 V		3 V	75			75			μA
	V_I = 2 V			–75			–75			
	V_I = 0 to 3.6 V‡		3..6 V			±500			±500	
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±15			±10	μA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			10			10	μA
	3.6 V ≤ V_I ≤ 5.5 V§					10			10	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		4	12		4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5	12		5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVCH244A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	6.5		7.5	ns
t_{en}	$\overline{OE}$	Y	1	8		9	ns
t_{dis}	$\overline{OE}$	Y	1	7		8	ns

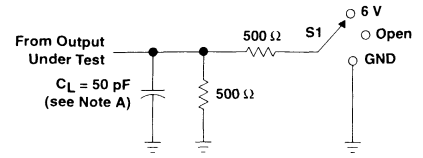
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LVCH244A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	4.9		5.9	ns
t_{en}	$\overline{OE}$	Y	1	6.2		7.6	ns
t_{dis}	$\overline{OE}$	Y	1.5	6.5		7	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

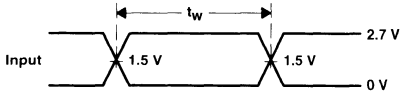
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0,	f = 10 MHz	47	pF
		Outputs disabled			2	

PARAMETER MEASUREMENT INFORMATION

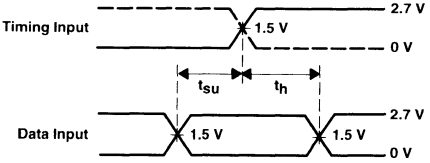


LOAD CIRCUIT

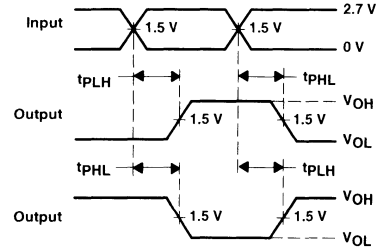
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



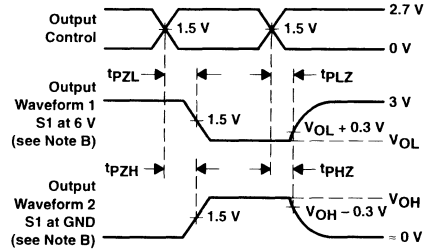
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



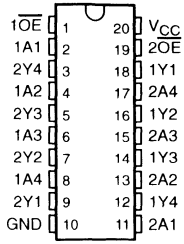
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/line driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC2244A is organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

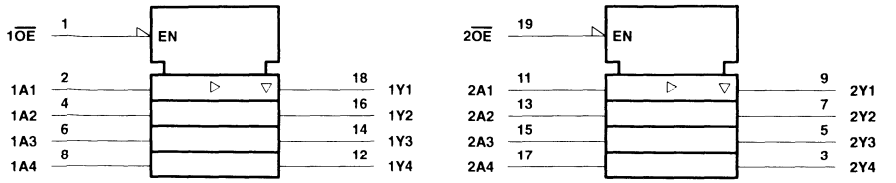
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC2244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

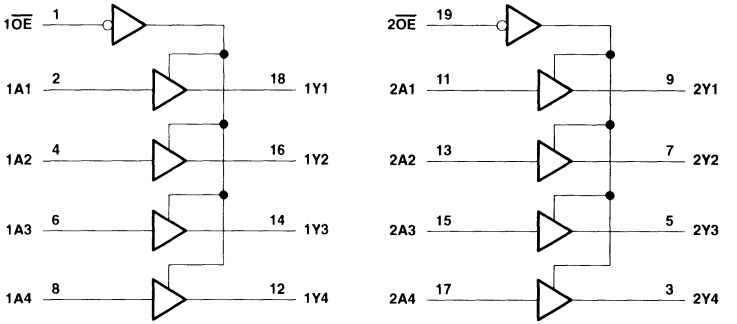
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DW package ..... 97°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–8	mA
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		8	mA
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –4 mA		2.7 V	2.2			
	I_{OH} = –6 mA		3 V	2.4			
	I_{OH} = –8 mA		2.7 V	2			
	I_{OH} = –12 mA		3 V	2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 4 mA		2.7 V			0.4	
	I_{OL} = 6 mA		3 V			0.55	
	I_{OL} = 8 mA		2.7 V			0.6	
	I_{OL} = 12 mA		3 V			0.8	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			10	µA
	3.6 V ≤ V_I ≤ 5.5 V‡					10	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

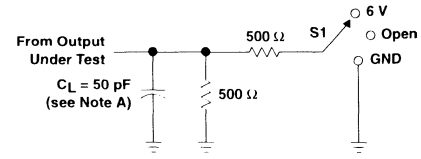
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	5.5		6.4	ns
t_{en}	$\overline{OE}$	Y	1	7.1		8.1	ns
t_{dis}	$\overline{OE}$	Y	1.5	6.8		7.3	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

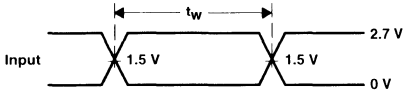
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0,	f = 10 MHz	46	pF
		Outputs disabled			2	

PARAMETER MEASUREMENT INFORMATION

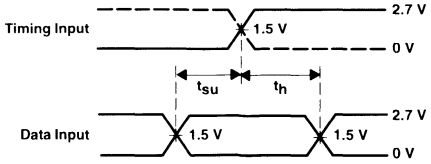


LOAD CIRCUIT

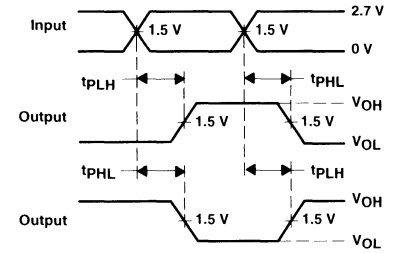
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



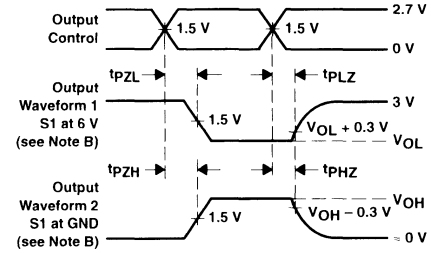
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



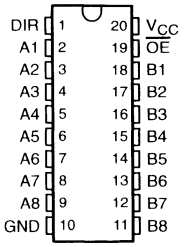
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC245A is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

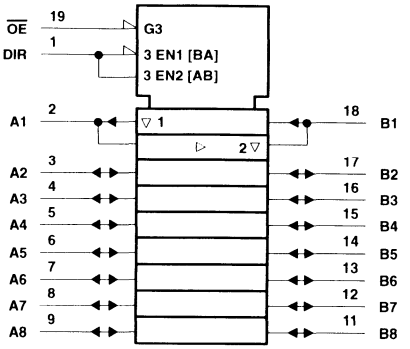
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

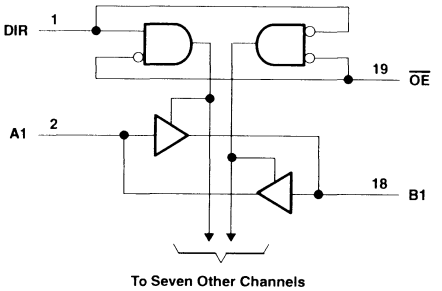
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}‡		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			10	µA
		3.6 V ≤ V_I ≤ 5.5 V§					10	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This applies in the disabled state only.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

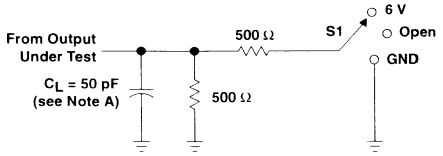
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	6.3		7.3	ns
t_{en}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
t_{dis}	$\overline{OE}$	A or B	1.7	7.5		8.5	ns
$t_{sk(o)}$¶				1			ns

¶ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

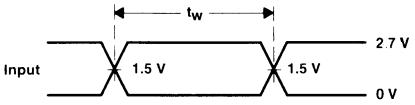
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	45	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

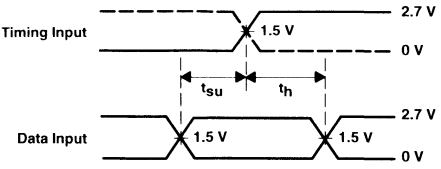


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

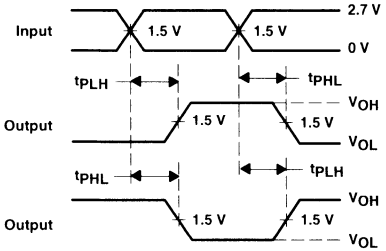
LOAD CIRCUIT



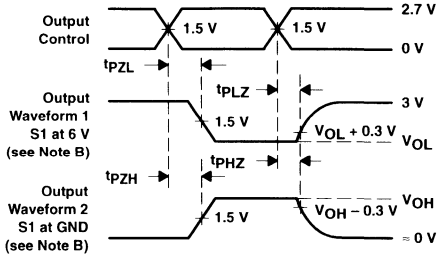
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



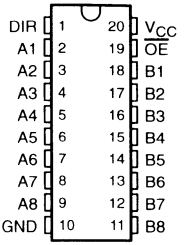
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

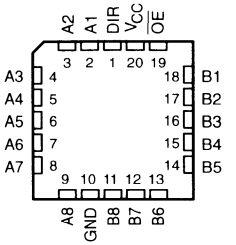
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Support Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

SN54LVCH245A . . . J OR W PACKAGE
SN74LVCH245A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVCH245A . . . FK PACKAGE
(TOP VIEW)



description

These octal bus transceivers are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVCH245A are designed for asynchronous communication between data buses. These devices transmit data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

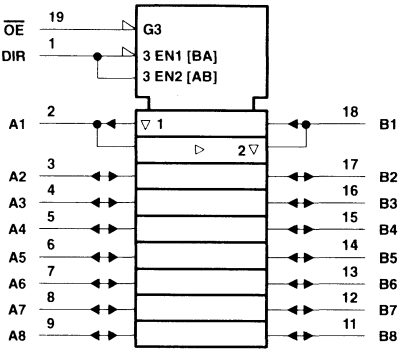
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVCH245A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVCH245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

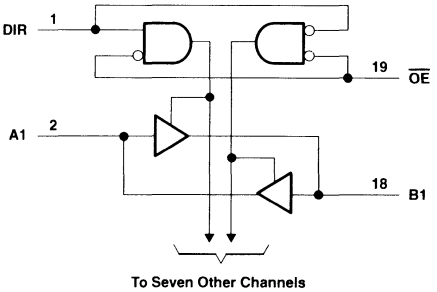
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVCH245A		SN74LVCH245A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	0	10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	SN54LVCH245A			SN74LVCH245A			UNIT
					MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}		I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			2.2			
				3 V	2.4			2.4			
		I_{OH} = –24 mA		3 V	2.2			2.2			
V_{OL}		I_{OL} = 100 μA		2.7 V to 3.6 V			0.2			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4			0.4	
		I_{OL} = 24 mA		3 V			0.55			0.55	
I_I	Control inputs	V_I = 0 to 5.5 V		3.6 V			±15			±5	μA
I_{off}		V_I or V_O = 5.5 V		0						±10	μA
$I_{I(hold)}$		V_I = 0.8 V		3 V	75			75			μA
		V_I = 2 V			–75			–75			
		V_I = 0 to 3.6 V‡		3..6 V			±500			±500	
I_{OZ}§		V_O = 0 to 5.5 V		3.6 V			±15			±10	μA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			10			10	μA
		3.6 V ≤ V_I ≤ 5.5 V¶	I_O = 0				10			10	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4	12		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		5.5	12		5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.
¶ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVCH245A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	7		8	ns
t_{en}	$\overline{OE}$	A or B	1	8.5		9.5	ns
t_{dis}	$\overline{OE}$	A or B	1	7.5		8.5	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

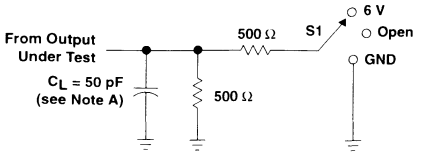
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LVCH245A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	6.3		7.3	ns
t_{en}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
t_{dis}	$\overline{OE}$	A or B	1.7	7.5		8.5	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

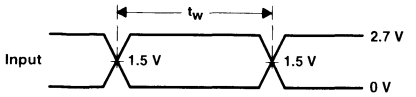
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	47	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

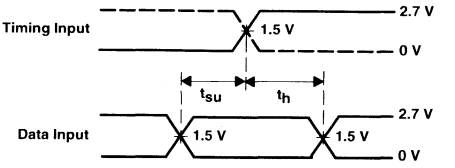


LOAD CIRCUIT

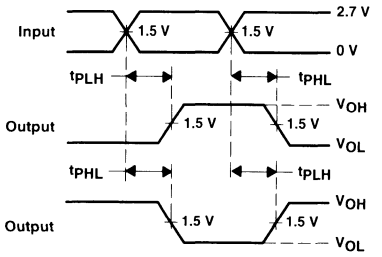
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



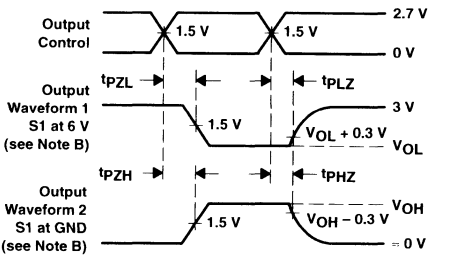
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



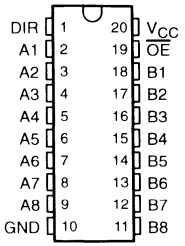
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- All Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCR2245A is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

All outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

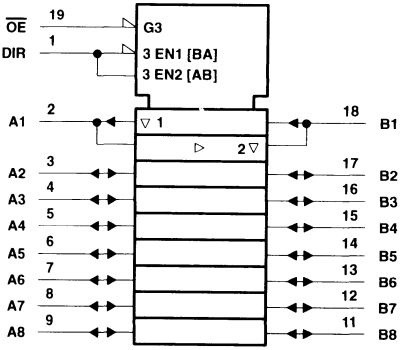
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVCR2245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

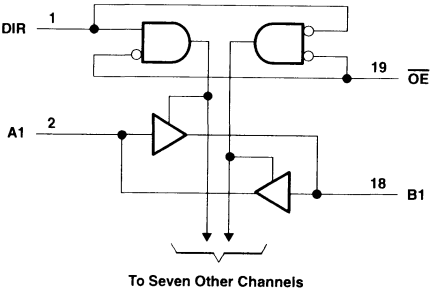
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–8	mA
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		8	mA
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER			V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA	2.7 V	2.2			
		I_{OH} = –6 mA	3 V	2.4			
		I_{OH} = –8 mA	2.7 V	2			
		I_{OH} = –12 mA	3 V	2			
V_{OL}		I_{OL} = 100 µA	2.7 V to 3.6 V			0.2	V
		I_{OL} = 4 mA	2.7 V			0.4	
		I_{OL} = 6 mA	3 V			0.55	
		I_{OL} = 8 mA	2.7 V			0.6	
		I_{OL} = 12 mA	3 V			0.8	
I_I	Control inputs	V_I = 0 to 5.5 V	3.6 V			±5	µA
I_{off}		V_I or V_O = 5.5 V	0			±10	µA
I_{OZ}‡		V_O = 0 to 5.5 V	3.6 V			±10	µA
I_{CC}		$V_I = V_{CC}$ or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	Control inputs	$V_I = V_{CC}$ or GND	3.3 V		4		pF
C_{io}	A or B ports	$V_O = V_{CC}$ or GND	3.3 V		5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

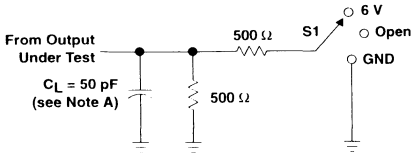
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	6.3		7.3	ns
t_{en}	$\overline{OE}$	A or B	1.5	8.2		9.5	ns
t_{dis}	$\overline{OE}$	A or B	1.7	7.8		8.5	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

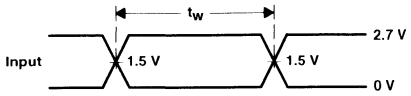
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	48	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

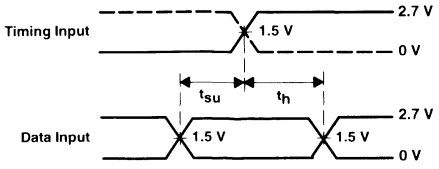


LOAD CIRCUIT

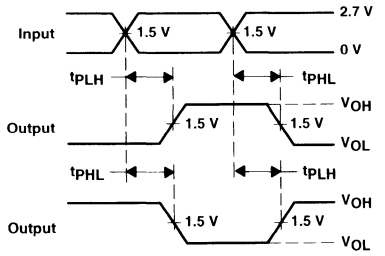
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



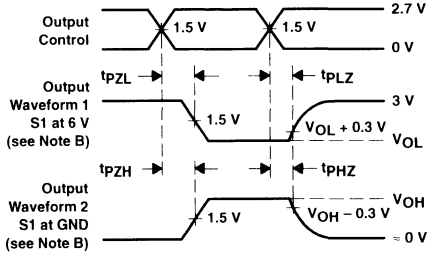
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



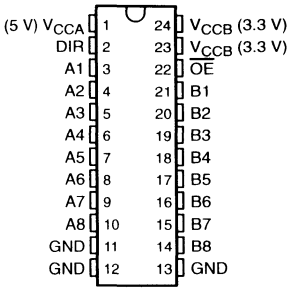
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- 3.3-V to 5-V Bidirectional Level Shifter
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 8-bit (octal) noninverting bus transceiver contains two separate supply rails; B port has V_{CCB}, which is set at 3.3 V, and A port has V_{CCA}, which is set at 5 V. This allows for translation from a 3.3-V to a 5-V environment, and vice versa.

The SN74LVC4245 is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

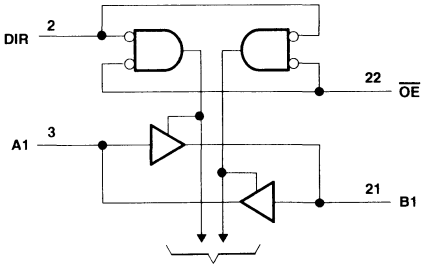
The SN74LVC4245 pinout allows the designer to switch to a normal all-3.3-V or all-5-V 20-pin '245 device without board re-layout. The designer uses the datapaths for pins 2 through 11 and 14 through 23 of the SN74LVC4245 to achieve the conventional '245 layout.

The SN74LVC4245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic diagram (positive logic)



PRODUCT PREVIEW

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absolute maximum ratings over operating free-air temperature range for V_{CCA} at 5 V (unless otherwise noted)†

Supply voltage range, V_{CCA}	–0.5 V to 6.5 V
Input voltage range, V_I (see Note 1)	–0.5 V to V_{CCA} + 0.5 V
Output voltage range, V_O (see Note 1)	–0.5 V to V_{CCA} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CCA})	–50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CCA})	±50 mA
Continuous output current, I_O (V_O = 0 to V_{CCA})	±50 mA
Continuous current through each V_{CCA} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 2): DB package	104°C/W
DW package	81°C/W
PW package	120°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. This value is limited to 6 V maximum.
2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range for V_{CCB} at 3.3 V (unless otherwise noted)†

Supply voltage range, V_{CCB}	–0.5 V to 4.6 V
Input voltage range, V_I (see Note 3): Except I/O ports	–0.5 V to 4.6 V
I/O ports	–0.5 V to V_{CCB} + 0.5 V
Output voltage range, V_O (see Note 3)	–0.5 V to V_{CCB} + 0.5 V
Input clamp current, I_{IK} (V_I < 0)	–50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CCB})	±50 mA
Continuous output current, I_O (V_O = 0 to V_{CCB})	±50 mA
Continuous current through V_{CCB} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 2): DB package	104°C/W
DW package	81°C/W
PW package	120°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.
3. This value is limited to 4.6 V maximum.

recommended operating conditions for V_{CCA} at 5 V (see Note 4)

		MIN	MAX	UNIT
V_{CCA}	Supply voltage	4.5	5.5	V
V_{IH}	High-level input voltage	2		V
V_{IL}	Low-level input voltage		0.8	V
V_I	Input voltage	0	V_{CCA}	V
V_O	Output voltage	0	V_{CCA}	V
I_{OH}	High-level output current		–24	mA
I_{OL}	Low-level output current		24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_A	Operating free-air temperature	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

recommended operating conditions for V_{CCB} at 3.3 V (see Note 4)

			MIN	MAX	UNIT
V_{CCB}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CCB} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CCB} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CCB}	V
V_O	Output voltage		0	V_{CCB}	V
I_{OH}	High-level output current	V_{CCB} = 2.7 V		–12	mA
		V_{CCB} = 3 V		–24	
I_{OL}	Low-level output current	V_{CCB} = 2.7 V		12	mA
		V_{CCB} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range for V_{CCA} = 5 V (unless otherwise noted) (see Note 5)

PARAMETER		TEST CONDITIONS	V_{CCA}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA	4.5 V	4.3			V
			5.5 V	5.3			
		I_{OH} = –24 mA	4.5 V	3.7			
			5.5 V	4.7			
V_{OL}		I_{OL} = 100 µA	4.5 V			0.2	V
			5.5 V			0.2	
		I_{OL} = 24 mA	4.5 V			0.55	
			5.5 V			0.55	
I_I	Control inputs	$V_I = V_{CCA}$ or GND	5.5 V			5	µA
I_{OZ}‡	A or B ports	$V_O = V_{CCA}$ or GND	5.5 V				µA
I_{CC}		$V_I = V_{CCA}$ or GND, I_O = 0	5.5 V				µA
ΔI_{CC}§		One input at 3.4 V, Other inputs at V_{CCA} or GND					µA
C_i	Control inputs	$V_I = V_{CCA}$ or GND	5 V				pF
C_{io}	A or B ports	$V_O = V_{CCA}$ or GND	5 V				pF

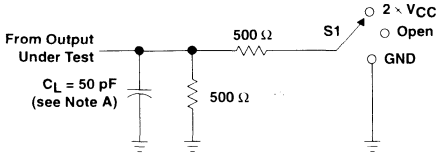
† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or the corresponding V_{CC}.
NOTE 5: V_{CCB} = 2.7 V to 3.6 V

electrical characteristics over recommended operating free-air temperature range for V_{CCB} = 3.3 V (unless otherwise noted) (see Note 6)

PARAMETER		TEST CONDITIONS	V_{CCB}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA	2.7 V	2.2			
			3 V	2.4			
		I_{OH} = –24 mA	3 V	2			
V_{OL}		I_{OL} = 100 µA	2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA	2.7 V			0.4	
		I_{OL} = 24 mA	3 V			0.55	
I_I	Control inputs	$V_I = V_{CCB}$ or GND	3.6 V			5	µA
I_{OZ}‡		$V_O = V_{CCB}$ or GND	3.6 V				µA
I_{CC}		$V_I = V_{CCB}$ or GND, I_O = 0	3.6 V				µA
ΔI_{CC}§		One input at V_{CCB} – 0.6 V, Other inputs at V_{CCB} or GND	2.7 V to 3.6 V				µA
C_i	Control inputs	$V_I = V_{CCB}$ or GND	3.3 V				pF
C_{io}	A or B ports	$V_O = V_{CCB}$ or GND	3.3 V				pF

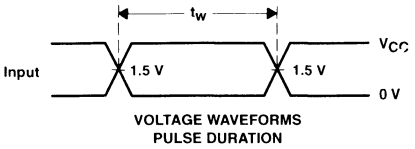
† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or the corresponding V_{CC}.
NOTE 6: V_{CCA} = 5 V ± 0.5 V

PARAMETER MEASUREMENT INFORMATION FOR THE A PORT

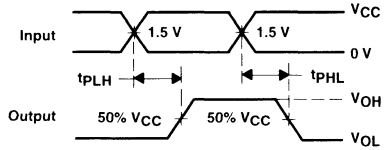


LOAD CIRCUIT

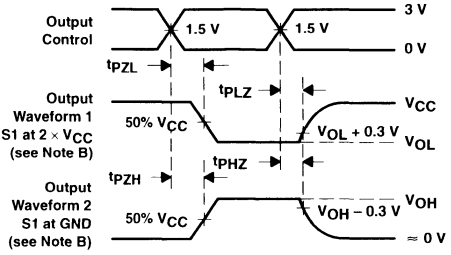
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
NONINVERTING OUTPUTS



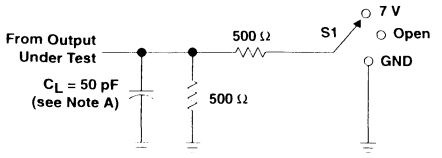
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

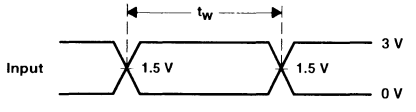
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION FOR THE B PORT

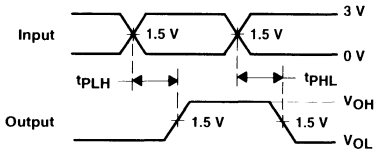


LOAD CIRCUIT

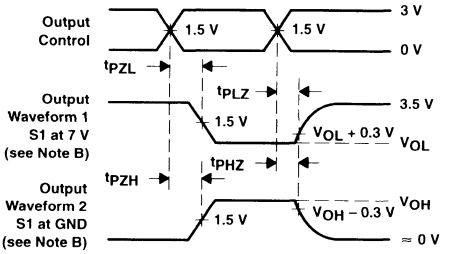
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: E. C_L includes probe and jig capacitance.
F. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
G. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
H. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

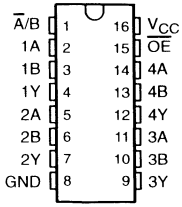
PRODUCT PREVIEW

SN74LVC257A
QUADRUPLE 2-LINE TO 1-LINE DATA SELECTOR/MULTIPLEXER WITH 3-STATE OUTPUTS

SCAS294D – JANUARY 1993 – REVISED JANUARY 1997

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-line to 1-line data selector/multiplexer is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC257A is designed to multiplex signals from 4-bit data sources to 4-output data lines in bus-organized systems. The 3-state outputs do not load the data lines when the output-enable ($\overline{OE}$) input is at a high logic level.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

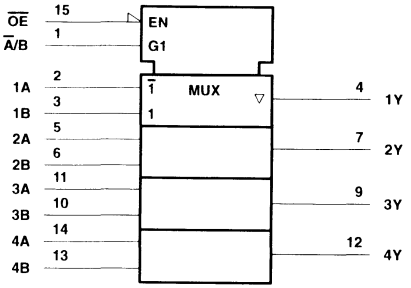
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC257A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

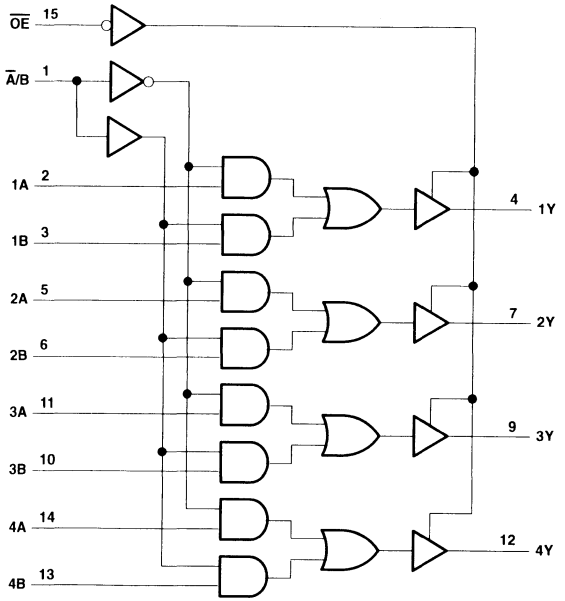
INPUTS				OUTPUT
$\overline{OE}$	$\overline{A}$/B	A	B	Y
H	X	X	X	Z
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package . . . . . 113°C/W
DB package . . . . . 131°C/W
PW package . . . . . 149°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF
C_o	V_O = V_{CC} or GND		3.3 V		5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

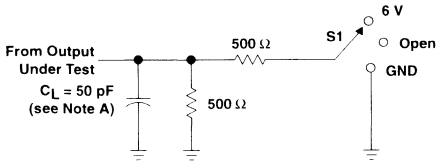
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	4.6		5.4	ns
	$\overline{A}$/B		1	6.4		7.5	
t_{en}	$\overline{OE}$	Y	1	5.6		6.7	ns
t_{dis}	$\overline{OE}$	Y	1	4.3		4.7	ns
$t_{sk(o)}$‡				1			ns

‡ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

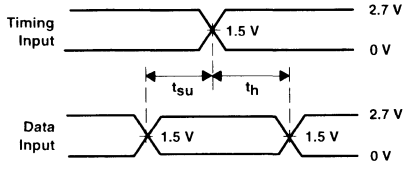
PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF,	f = 10 MHz	15.5	pF

PARAMETER MEASUREMENT INFORMATION

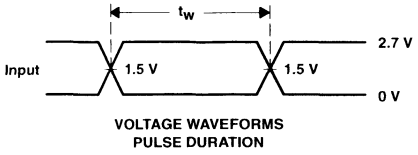


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

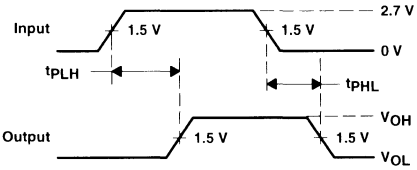
LOAD CIRCUIT



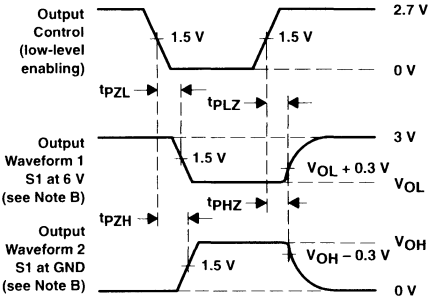
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



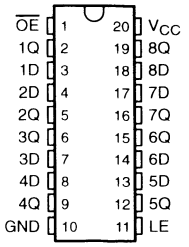
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

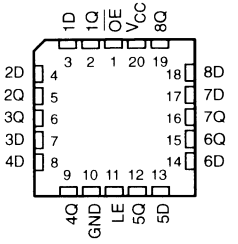
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Support Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) Dips**

SN54LVC373A . . . J OR W PACKAGE
SN74LVC373A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVC373A . . . FK PACKAGE
(TOP VIEW)



description

These octal transparent D-type latches are designed for 2.7-V to 3.6-V V_{CC} operation.

While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

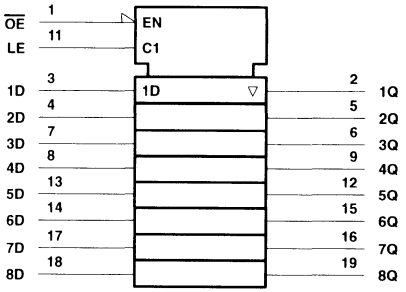
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVC373A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC373A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each latch)

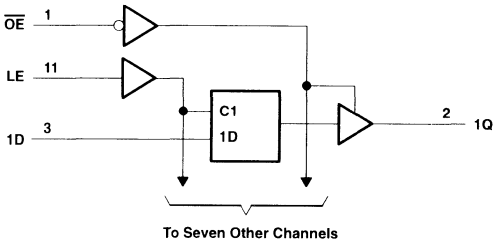
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC373A		SN74LVC373A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	0	10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	SN54LVC373A			SN74LVC373A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			2.2			
			3 V	2.4			2.4			
	I_{OH} = –24 mA		3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4			0.4	
	I_{OL} = 24 mA		3 V			0.55			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5			±5	µA
I_{off}	V_I or V_O = 5.5 V		0						±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±15			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			15			10	µA
	3.6 V ≤ V_I ≤ 5.5 V‡					15			10	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		4	12		4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5	12		5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		SN54LVC373A				SN74LVC373A				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE↓	2		2		2		2		ns
t_h	Hold time, data after LE↓	2		2		1.5		1.5		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

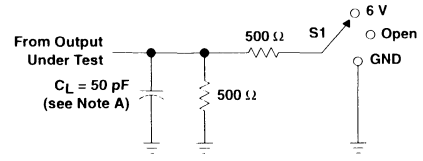
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC373A				SN74LVC373A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1	7.5		8.5	1.5	6.8		7.8	ns
	LE		1	8.5		9.5	2	7.6		8.2	
t_{en}	$\overline{OE}$	Q	1	7.7		8.7	1.5	7.7		8.7	ns
t_{dis}	$\overline{OE}$	Q	0.5	7		8	1.5	7		7.6	ns
$t_{sk(o)}$§				1				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

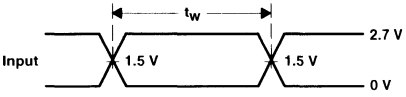
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 0,	f = 10 MHz	46	pF
		Outputs disabled			3	

PARAMETER MEASUREMENT INFORMATION

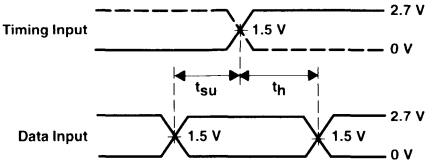


LOAD CIRCUIT

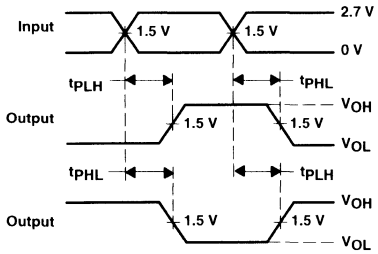
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



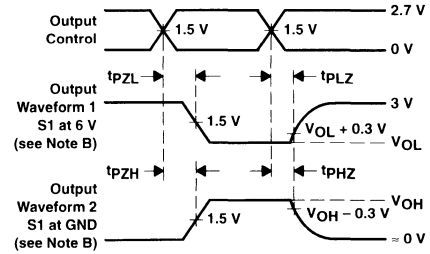
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



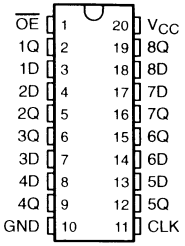
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

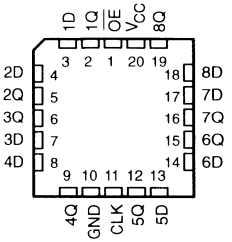
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Support Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs**

SN54LVC374A . . . J OR W PACKAGE
SN74LVC374A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVC374A . . . FK PACKAGE
(TOP VIEW)



description

These octal edge-triggered D-type flip-flops are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC374A feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. These devices are particularly suitable for implementing buffer registers, input/output (I/O) ports, bidirectional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

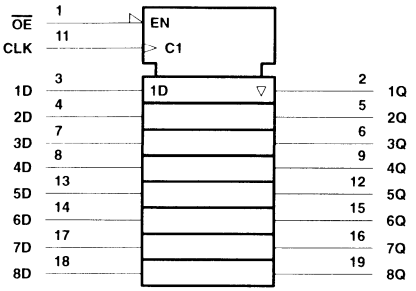
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVC374A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC374A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

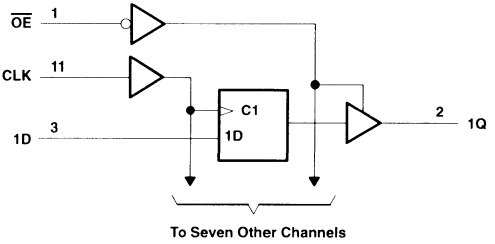
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC374A		SN74LVC374A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	0	10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	SN54LVC374A			SN74LVC374A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			2.2			
			3 V	2.4			2.4			
	I_{OH} = –24 mA		3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4			0.4	
	I_{OL} = 24 mA		3 V			0.55			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5			±5	µA
I_{off}	V_I or V_O = 5.5 V		0						±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±15			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			15			10	µA
	3.6 V ≤ V_I ≤ 5.5 V‡					15			10	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		4	12		4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5	12		5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		SN54LVC374A				SN74LVC374A				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	100	0	80	0	100	0	80	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	2		2		2		2		ns
t_h	Hold time, data after CLK↑	1.5		1.5		1.5		1.5		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

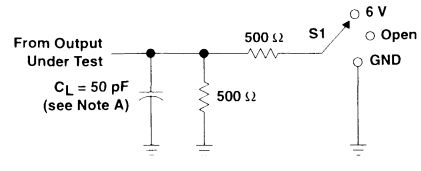
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC374A				SN74LVC374A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			100		80		100		80		MHz
t_{pd}	CLK	Q	1	8.5		9.5	1.5	7		8.1	ns
t_{en}	$\overline{OE}$	Q	1	8.5		9.5	1.5	7.5		8.5	ns
t_{dis}	$\overline{OE}$	Q	1	7		8	1.5	6.5		7.1	ns
$t_{sk(o)}$§				1				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

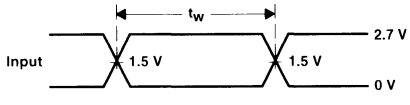
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 0,	f = 10 MHz	54.5	pF
		Outputs disabled			13.5	

PARAMETER MEASUREMENT INFORMATION

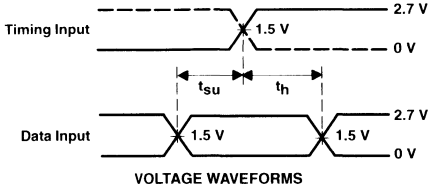


LOAD CIRCUIT

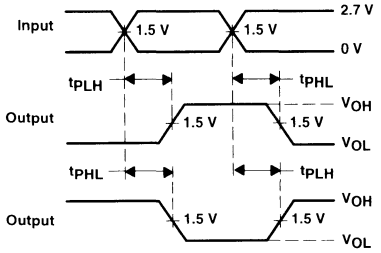
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



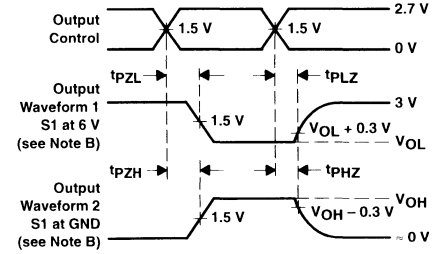
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



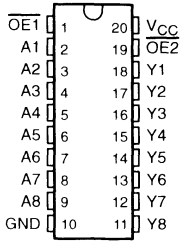
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

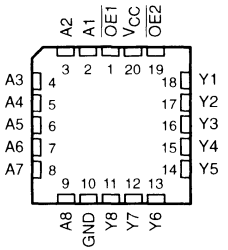
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs**

SN54LVC540A . . . J OR W PACKAGE
SN74LVC540A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVC540A . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/drivers are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC540A are ideal for driving bus lines or buffer memory address registers. These devices feature inputs and outputs on opposite sides of the package that facilitate printed circuit board layout.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

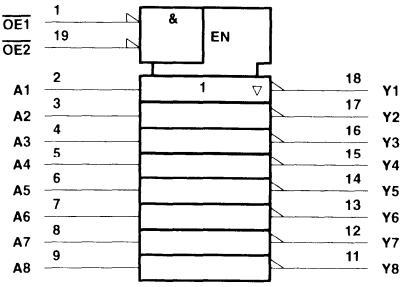
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LVC540A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC540A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

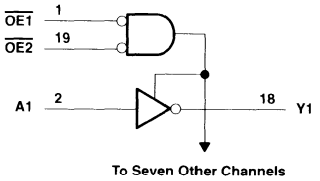
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DW package ..... 97°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC540A		SN74LVC540A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	SN54LVC540A			SN74LVC540A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			2.2			
			3 V	2.4			2.4			
	I_{OH} = –24 mA		3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4			0.4	
	I_{OL} = 24 mA		3 V			0.55			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5			±5	µA
I_{off}	V_I or V_O = 5.5 V		0			±30			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±15			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20			10	µA
	3.6 V ≤ V_I ≤ 5.5 V‡					20			10	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		4			4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5			5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

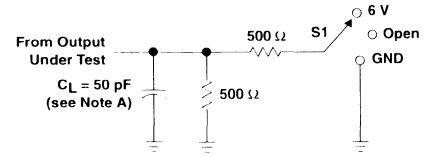
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC540A				SN74LVC540A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	5.3		7.1	1.4	5.3		7.1	ns
t_{en}	$\overline{OE}$	Y	1	6.6		8	1.1	6.6		8	ns
t_{dis}	$\overline{OE}$	Y	1	7.4		8.2	1.8	7.4		8.2	ns
$t_{sk(o)}$ *†								1			ns

* On products compliant with MIL-PRF-38535, this parameter does not apply.
† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

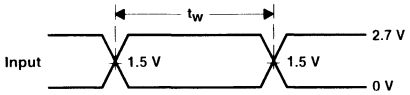
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0,	f = 10 MHz	31	pF
		Outputs disabled			3	

PARAMETER MEASUREMENT INFORMATION

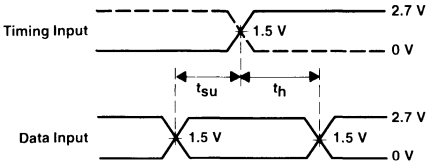


LOAD CIRCUIT

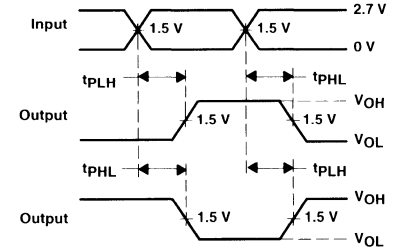
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



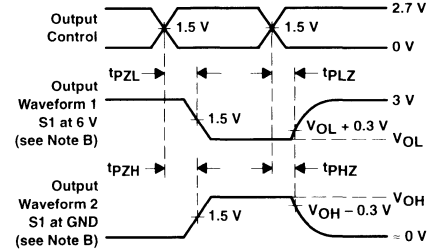
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



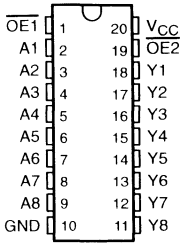
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

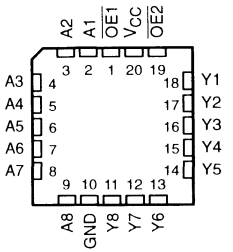
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs

SN54LVC541A . . . J OR W PACKAGE
SN74LVC541A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVC541A . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/drivers are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC541A are ideal for driving bus lines or buffering memory address registers. These devices feature inputs and outputs on opposite sides of the package to facilitate printed circuit board layout.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all eight outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

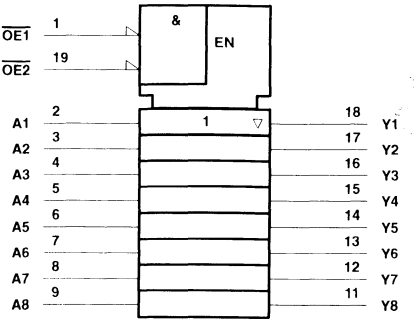
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN54LVC541A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC541A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

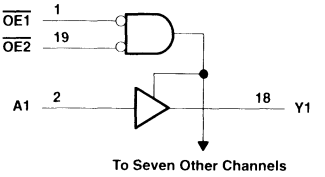
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DW package ..... 97°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC541A		SN74LVC541A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	SN54LVC541A			SN74LVC541A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			2.2			
			3 V	2.4			2.4			
	I_{OH} = –24 mA		3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 μA		2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4			0.4	
	I_{OL} = 24 mA		3 V			0.55			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5			±5	μA
I_{off}	V_I or V_O = 5.5 V		0			±30			±10	μA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±15			±10	μA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20			10	μA
	3.6 V ≤ V_I ≤ 5.5 V‡					20			10	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		4			4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5			5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

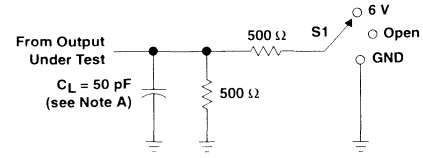
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC541A				SN74LVC541A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	5.1		5.6	1.5	5.1		5.6	ns
t_{en}	$\overline{OE}$	Y	1	7		7.5	1.5	7		7.5	ns
t_{dis}	$\overline{OE}$	Y	1	7		7.7	1.5	7		7.7	ns
$t_{sk(o)}$ *†								1			ns

* On products compliant with MIL-PRF-38535, this parameter does not apply.
† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

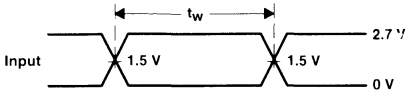
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0,	f = 10 MHz	33	pF
		Outputs disabled			2	

PARAMETER MEASUREMENT INFORMATION

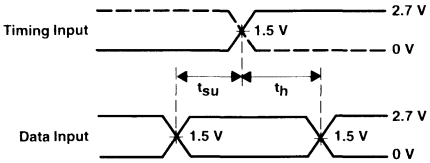


LOAD CIRCUIT

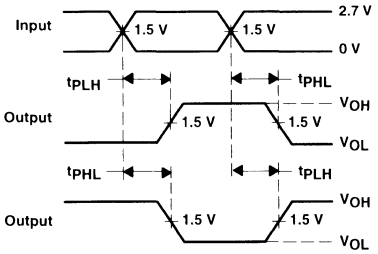
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



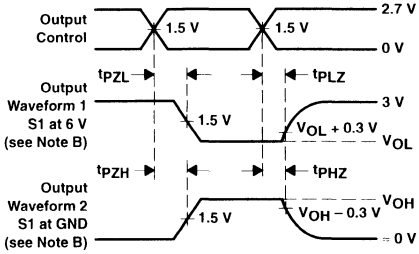
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



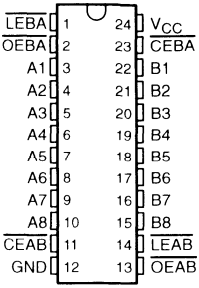
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal registered transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC543A contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ places the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow for B to A is similar to that of A to B, but uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

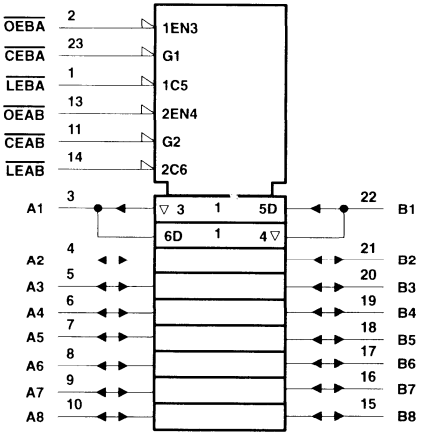
The SN74LVC543A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CEAB}$	LEAB	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

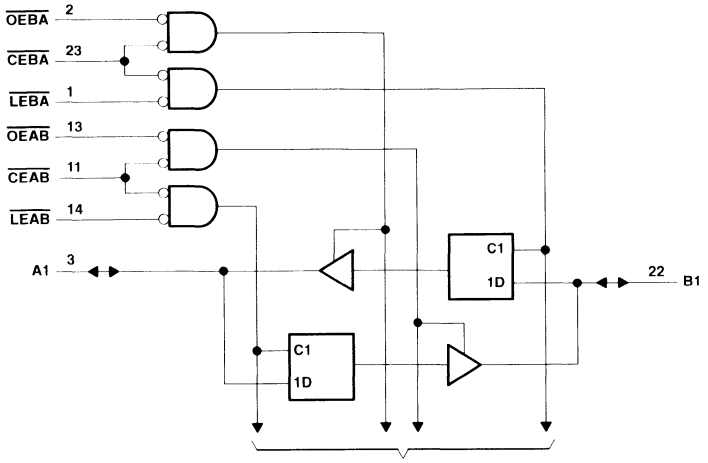
† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 104°C/W
DW package . . . . . 81°C/W
PW package . . . . . 120°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}‡		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			10	µA
		3.6 V ≤ V_I ≤ 5.5 V§					10	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration	3.3		3.3		ns
t_{su}	Setup time, data before $\overline{LE}$↑ or $\overline{CE}$↑	1.6		1.6		ns
t_h	Hold time, data after $\overline{LE}$↑ or $\overline{CE}$↑	2.1		2.1		ns

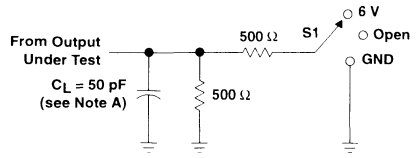
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	7		8	ns
	$\overline{LE}$		1.2	8.5		9.5	
t_{en}	$\overline{OE}$	A or B	1.3	7.7		9.2	ns
	$\overline{CE}$		1.3	8		9.3	
t_{dis}	$\overline{OE}$	A or B	1	7		7.5	ns
	$\overline{CE}$		1	7		7.5	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

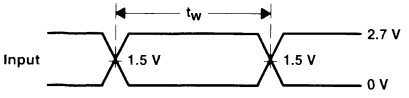
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0,	f = 10 MHz	49	pF
		Outputs disabled			6	

PARAMETER MEASUREMENT INFORMATION

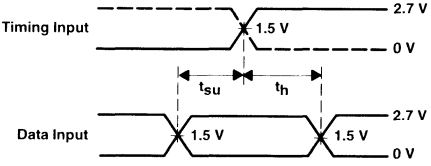


LOAD CIRCUIT

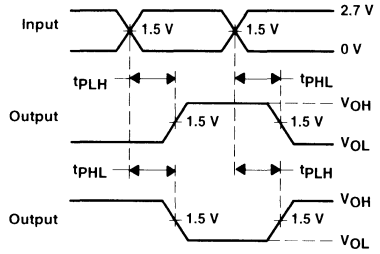
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



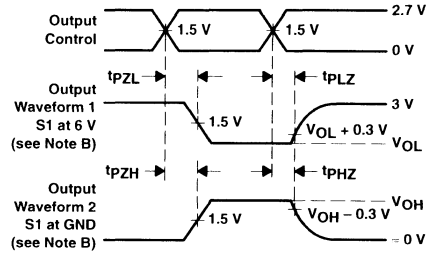
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



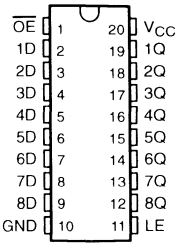
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

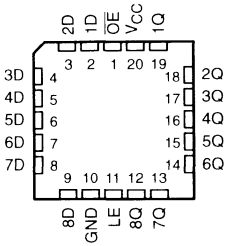
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs**

SN54LVC573A . . . J OR W PACKAGE
SN74LVC573A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVC573A . . . FK PACKAGE
(TOP VIEW)



description

These octal transparent D-type latches are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC573A feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing buffer registers, input/output (I/O) ports, bidirectional bus drivers, and working registers.

While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

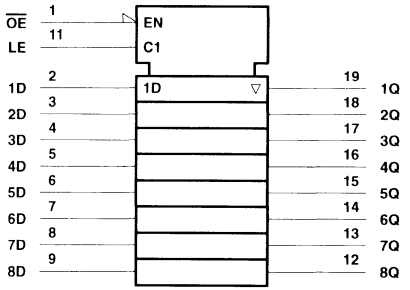
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN54LVC573A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC573A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each latch)

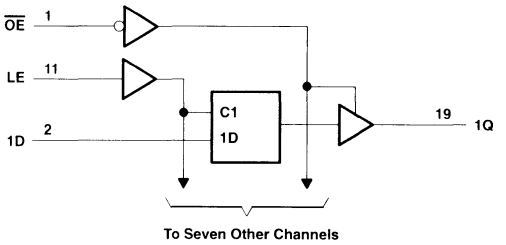
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC573A		SN74LVC573A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	6	0	6	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	SN54LVC573A			SN74LVC573A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			2.2			
			3 V	2.4			2.4			
	I_{OH} = –24 mA		3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4			0.4	
	I_{OL} = 24 mA		3 V			0.55			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5			±5	µA
I_{off}	V_I or V_O = 5.5 V		0			±50			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±15			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			10			10	µA
	3.6 V ≤ V_I ≤ 5.5 V‡					10			10	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		4			4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5			5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		SN54LVC573A				SN74LVC573A				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE↓	2		2		2		2		ns
t_h	Hold time, data after LE↓	2.5		2.5		1.5		1.5		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

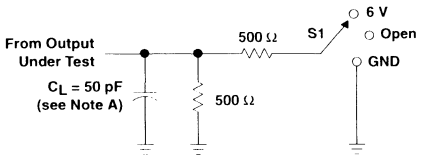
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC573A				SN74LVC573A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1	6.9		7.7	1.5	6.9		7.7	ns
	LE		1	7.7		8.4	2	7.7		8.4	
t_{en}	$\overline{OE}$	Q	1	6.7		8.5	1.5	6.7		8.5	ns
t_{dis}	$\overline{OE}$	Q	0.5	6.6		7	1.6	6.6		7	ns
$t_{sk(o)}$§								1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

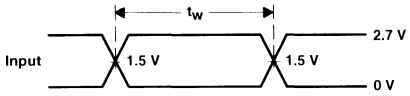
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 0, f = 10 MHz	37	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

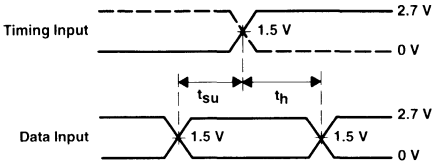


LOAD CIRCUIT

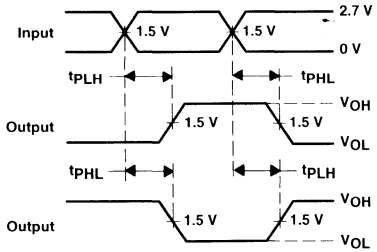
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



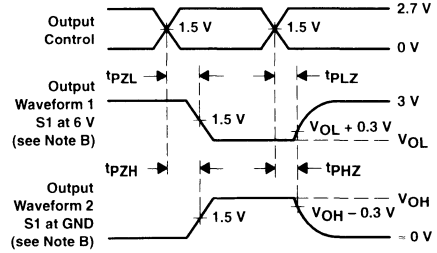
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



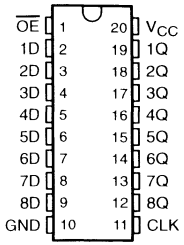
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

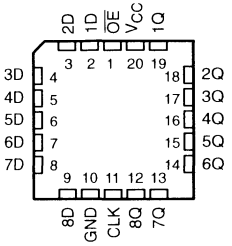
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Support Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic 300-mil DIPs (J)

SN54LVC574A . . . J OR W PACKAGE
SN74LVC574A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVC574A . . . FK PACKAGE
(TOP VIEW)



description

These octal edge-triggered D-type flip-flops are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC574A feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

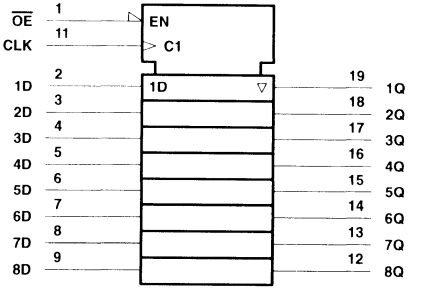
description (continued)

The SN54LVC574A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC574A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

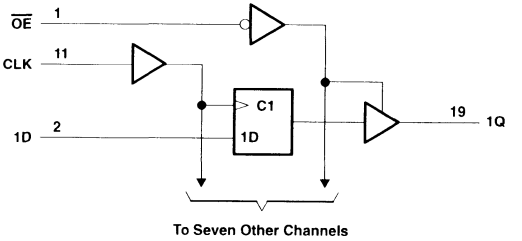
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC574A		SN74LVC574A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	6	0	6	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	SN54LVC574A			SN74LVC574A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			2.2			
			3 V	2.4			2.4			
	I_{OH} = –24 mA		3 V	2.2			2.2			
V_{OL}	I_{OL} = 100 μA		2.7 V to 3.6 V			0.2			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4			0.4	
	I_{OL} = 24 mA		3 V			0.55			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5			±5	μA
I_{off}	V_I or V_O = 5.5 V		0			±50			±10	μA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±15			±10	μA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			15			10	μA
	3.6 V ≤ V_I ≤ 5.5 V‡	I_O = 0	3.6 V			15			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		4			4		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.5			5.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		SN54LVC574A				SN74LVC574A				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	2		2		2		2		ns
t_h	Hold time, data after CLK↑	2		2		1.5		1.5		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

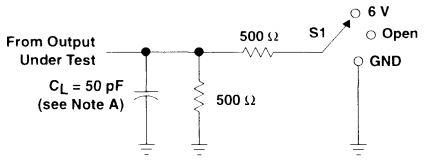
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC574A				SN74LVC574A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		150		MHz
t_{pd}	D	Q	1	7		8	2.2	7		8	ns
t_{en}	$\overline{OE}$	Q	1	7.5		9	1.5	7.5		8.5	ns
t_{dis}	$\overline{OE}$	Q	0.5	6.4		7	1.7	6.4		7	ns
$t_{sk(o)}$§								1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

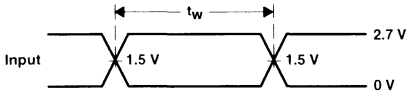
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 0,	f = 10 MHz	43	pF
		Outputs disabled			15	

PARAMETER MEASUREMENT INFORMATION

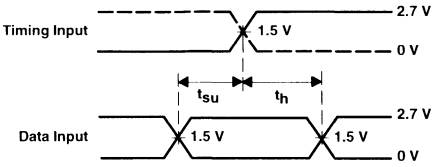


LOAD CIRCUIT

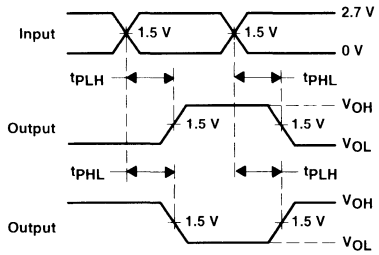
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



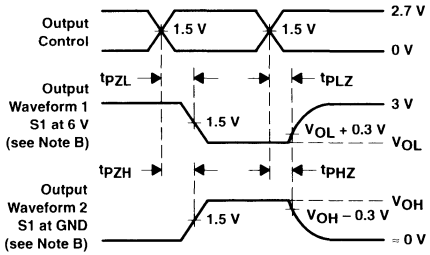
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



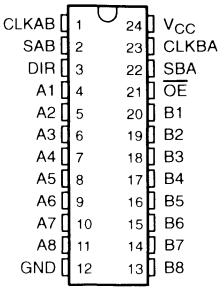
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

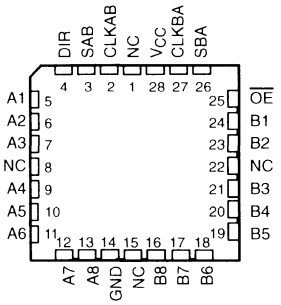
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Support Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-833, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW) Packages, and Ceramic Chip Carriers (FK)**

SN74LVC646A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVC646A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These octal bus transceivers and registers are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC646A devices consist of bus-transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that are performed with the 'LVC646A.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs control the transceiver functions. In the transceiver mode, data present at the high-impedance port is stored in either register or in both.

The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. DIR determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data is stored in one register and B data can be stored in the other register.

When an output function is disabled, the input function is still enabled and can be used to store and transmit data. Only one of the two buses, A or B, can be driven at a time.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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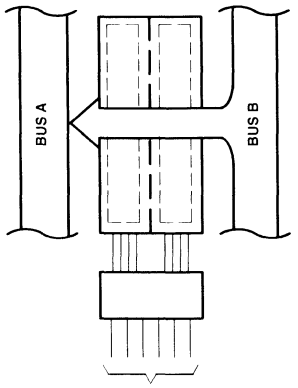
description (continued)

The SN54LVC646A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC646A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

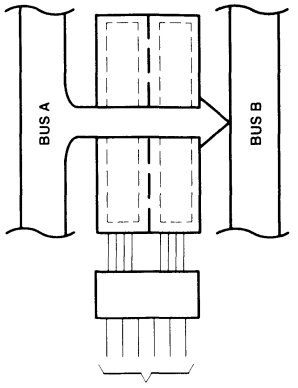
INPUTS						DATA I/O		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

† The data-output functions can be enabled or disabled by various signals at $\overline{OE}$ and DIR. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.



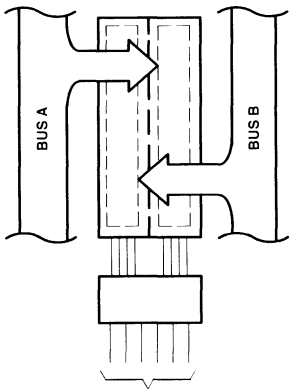
21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER BUS B TO BUS A



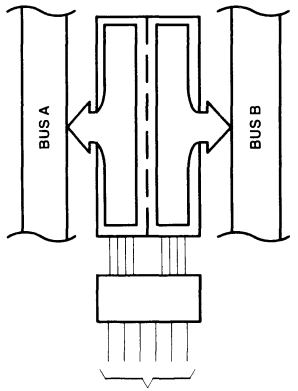
21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER BUS A TO BUS B



21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM A, B, OR A AND B

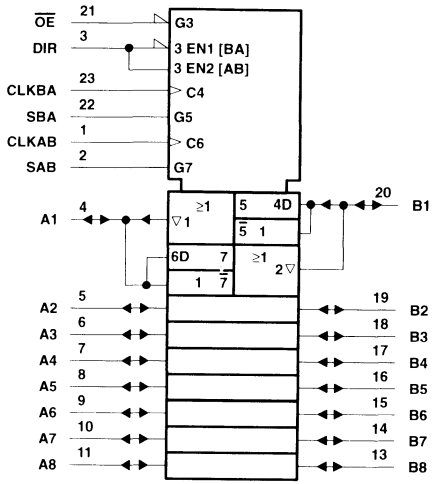


21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA TO A AND/OR B

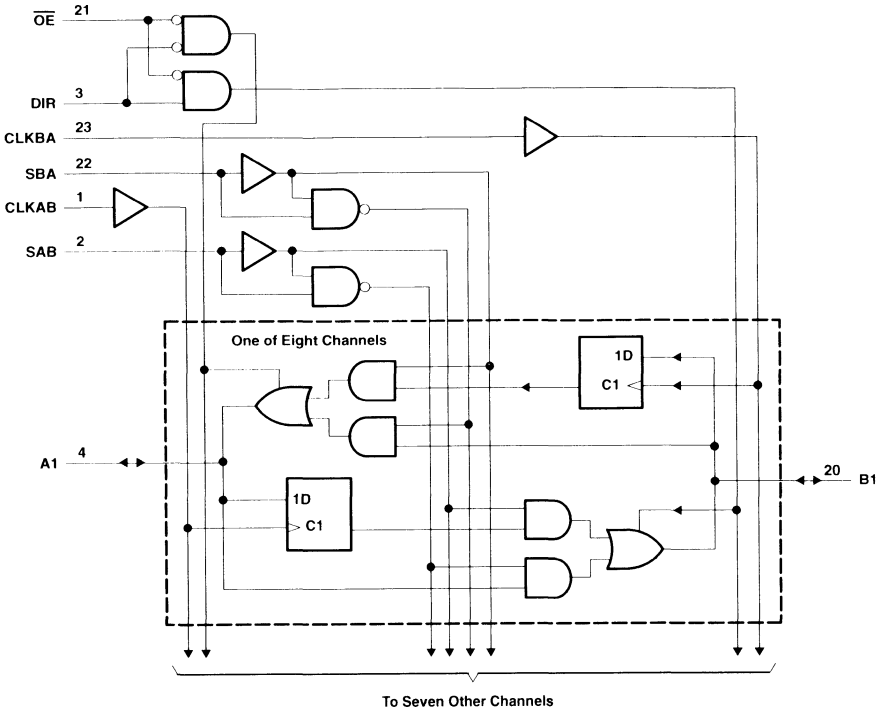
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, and PW packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 104°C/W
DW package ..... 81°C/W
PW package ..... 120°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC646A		SN74LVC646A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	0	10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	SN54LVC646A			SN74LVC646A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}		I_{OH} = –100 μA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
		I_{OH} = –12 mA	2.7 V	2.2			2.2			
			3 V	2.4			2.4			
		I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}		I_{OL} = 100 μA	2.7 V to 3.6 V			0.2			0.2	V
		I_{OL} = 12 mA	2.7 V			0.4			0.4	
		I_{OL} = 24 mA	3 V			0.55			0.55	
I_I		V_I = 0 to 5.5 V	3.6 V			±5			±5	μA
I_{off}		V_I or V_O = 5.5 V	0			±15			±10	μA
I_{OZ}‡		V_O = 0 to 5.5 V	3.6 V			±30			±10	μA
I_{CC}		V_I = V_{CC} or GND, I_O = 0	3.6 V			20			10	μA
		3.6 V ≤ $V_{I/O}$ ≤ 5.5 V§				20			10	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	μA
C_i	Control inputs	V_I = V_{CC} or GND	3.3 V		4.5			4.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND	3.3 V		7.5			7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

		SN54LVC646A				SN74LVC646A				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.5		1.6		1.5		1.6		ns
t_h	Hold time, data after CLK↑	1.7		1.7		1.7		1.7		ns

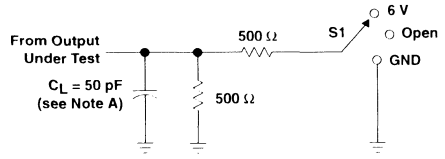
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC646A				SN74LVC646A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V + 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		150		MHz
t_{pd}	A or B	B or A	1	7.4		7.9	1.4	7.4		7.9	ns
	CLK	A or B	1	8.4		8.8	1.3	8.4		8.8	
	SBA or SAB		1	8.6		9.9	1.4	8.6		9.9	
t_{en}	$\overline{OE}$	A	1	8.2		10.2	1	8.2		10.2	ns
t_{dis}	$\overline{OE}$	A	1	7.5		8.9	1	7.5		8.9	ns
t_{en}	DIR	B	1	8.3		10.4	1.2	8.3		10.4	ns
t_{dis}	DIR	B	1	7.9		8.7	1.1	7.9		8.7	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

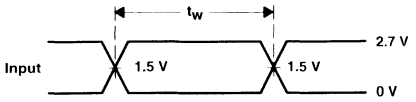
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0,	f = 10 MHz	75	pF
		Outputs disabled			9	

PARAMETER MEASUREMENT INFORMATION

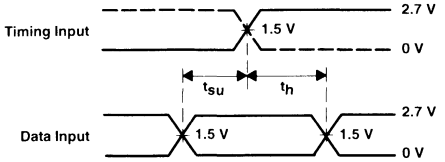


LOAD CIRCUIT

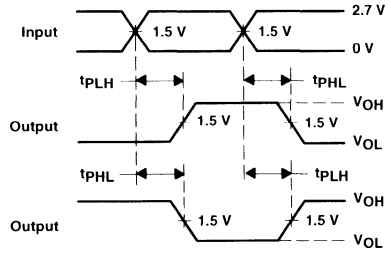
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



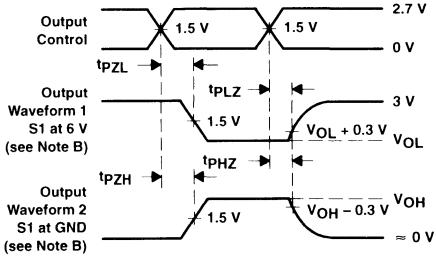
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



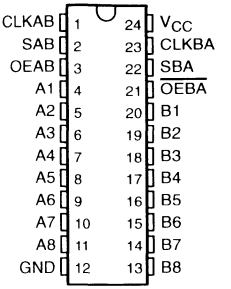
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

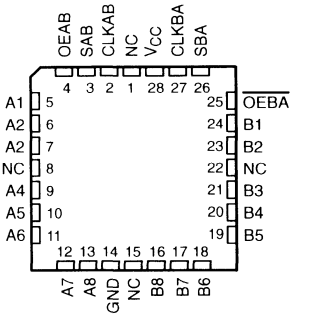
Figure 2. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Support Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-833, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW) Packages, and Ceramic Chip Carriers (FK)

SN74LVC652A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVC652A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These octal bus transceivers and registers are designed for 2.7-V to 3.6-V V_{CC} operation.

The 'LVC652A devices consist of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers.

Output-enable (OEAB and $\overline{\text{OEBA}}$) inputs are provided to control the transceiver functions. Select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. A low input selects real-time data, and a high input selects stored data. Figure 1 illustrates the four fundamental bus-management functions that are performed with the 'LVC652A.

Data on the A or B data bus, or both, is stored in the internal D-type flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs, regardless of the select- or enable-control pins. When SAB and SBA are in the real-time transfer mode, it is possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{\text{OEBA}}$. In this configuration, each output reinforces its input. When all other data sources to the two sets of bus lines are at high impedance, each set of bus lines remains at its last state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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description (continued)

To ensure the high-impedance state during power up or power down, $\overline{OEBA}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

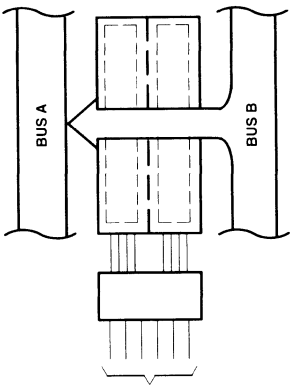
The SN54LVC652A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVC652A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

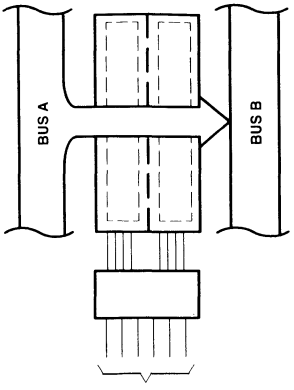
† The data-output functions can be enabled or disabled by a variety of level combinations at OEAB or $\overline{OEBA}$. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.

‡ Select control = L; clocks can occur simultaneously.
Select control = H; clocks must be staggered to load both registers.



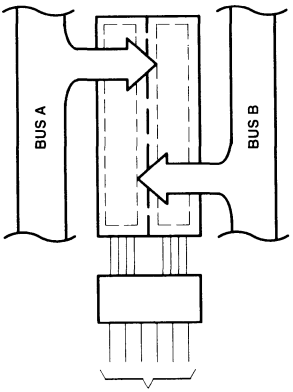
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER BUS B TO BUS A



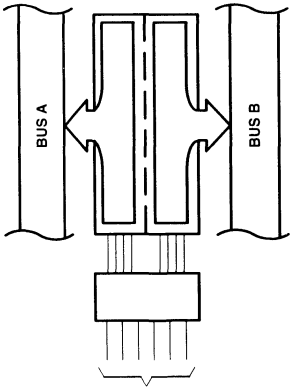
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER BUS A TO BUS B



3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM A, B, OR A AND B

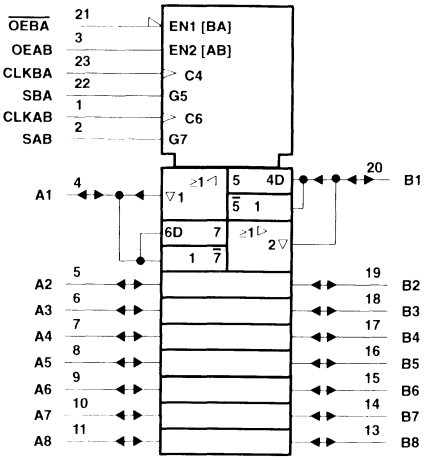


3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	L	H or L	H or L	H	H

TRANSFER STORED DATA TO A AND/OR B

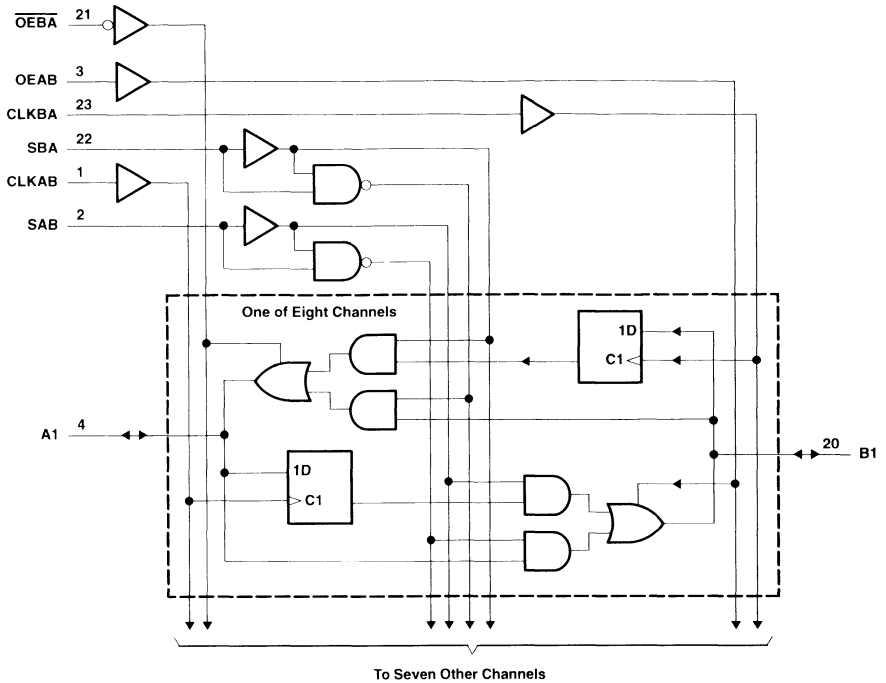
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, and PW packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0) ..... –50 mA
Continuous output current, I_O ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 104°C/W
DW package ..... 81°C/W
PW package ..... 120°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LVC652A		SN74LVC652A		UNIT
			MIN	MAX	MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	2	3.6	V
		Data retention only	1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3 state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12		–12	mA
		V_{CC} = 3 V		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12		12	mA
		V_{CC} = 3 V		24		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	5	0	5	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	SN54LVC652A			SN74LVC652A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}		I_{OH} = –100 µA	2.7 V to 3.6 V	V_{CC}–0.2			V_{CC}–0.2			V
		I_{OH} = –12 mA	2.7 V	2.2			2.2			
			3 V	2.4			2.4			
		I_{OH} = –24 mA	3 V	2.2			2.2			
V_{OL}		I_{OL} = 100 µA	2.7 V to 3.6 V			0.2			0.2	V
		I_{OL} = 12 mA	2.7 V			0.4			0.4	
		I_{OL} = 24 mA	3 V			0.55			0.55	
I_I		V_I = 0 to 5.5 V	3.6 V			±15			±5	µA
I_{off}		V_I or V_O = 5.5 V	0			±30			±10	µA
I_{OZ}‡		V_O = 0 to 5.5 V	3.6 V			±15			±10	µA
I_{CC}		V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	µA
		3.6 V ≤ $V_{I/O}$ ≤ 5.5 V,§ OEAB = GND				20			20	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500			500	µA
C_i	Control inputs	V_I = V_{CC} or GND	3.3 V		4.5			4.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND	3.3 V		7.5			7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

		SN54LVC652A				SN74LVC652A				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		100		80		100		80	MHz
t_w	Pulse duration	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.5		1.6		1.5		1.6		ns
t_h	Hold time, data after CLK↑	1.5		0.5		1.5		0.5		ns

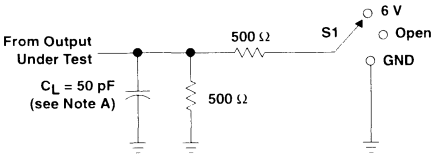
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVC652A				SN74LVC652A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			100		80		100		80		MHz
t_{pd}	A or B	B or A	1	7.4		7.8	1.5	7.4		7.8	ns
	CLK	A or B	1	8		8.4	1.5	8		8.4	
	SAB or SBA	B or A	1	8.7		9.6	1.5	8.7		9.6	
t_{en}	$\overline{OEBA}$	A	1	7.4		8.9	1.5	7.4		8.9	ns
t_{dis}	$\overline{OEBA}$	A	1	7.5		8.1	1.5	7.5		8.1	ns
t_{en}	OEAB	B	1	7.1		8.6	1.5	7.1		8.6	ns
t_{dis}	OEAB	B	1	7.4		7.7	1.5	7.4		7.7	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

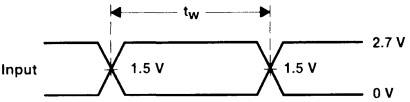
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	84	pF
		Outputs disabled		9.5	

PARAMETER MEASUREMENT INFORMATION

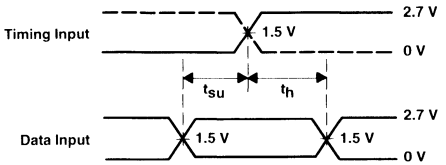


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

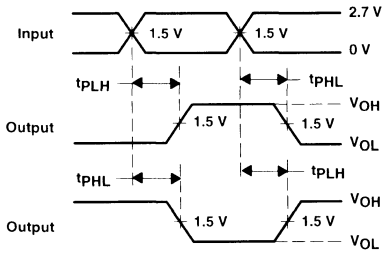
LOAD CIRCUIT



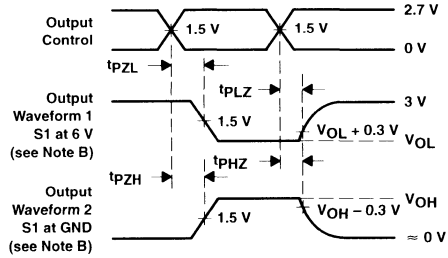
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



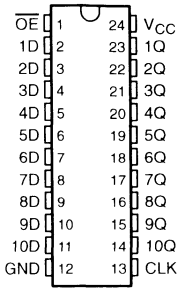
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit bus-interface flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC821A features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing wider buffer registers, I/O ports, bidirectional bus drivers with parity, and working registers.

The ten flip-flops are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the ten outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

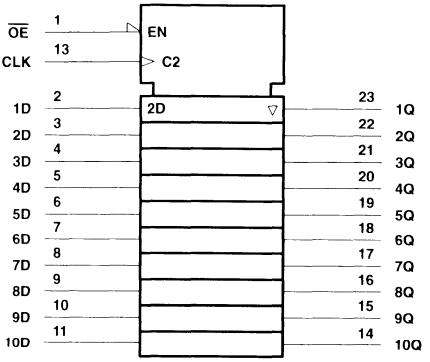
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC821A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

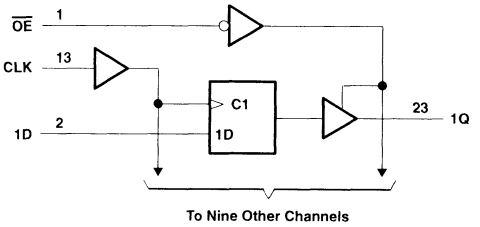
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 104°C/W
DW package . . . . . 81°C/W
PW package . . . . . 120°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			10	µA
		3.6 V ≤ V_I ≤ 5.5 V‡					10	
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	Control	V_I = V_{CC} or GND		3.3 V		5		pF
	Data					4		
C_o		V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		ns
t_{su}	Setup time, data before CLK	1.9		1.9		ns
t_h	Hold time, data after CLK	1.5		1.5		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

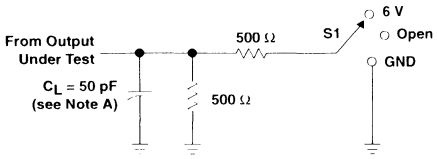
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			150		150		MHz
t_{pd}	CLK	Q	2.2	7.3		8.5	ns
t_{en}	$\overline{OE}$	Q	1.3	7.6		8.8	ns
t_{dis}	$\overline{OE}$	Q	1.6	6.2		6.8	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

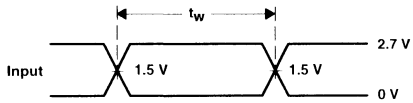
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 0 pF,	f = 10 MHz	65	pF
		Outputs disabled			48	

PARAMETER MEASUREMENT INFORMATION

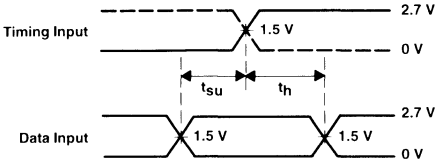


LOAD CIRCUIT

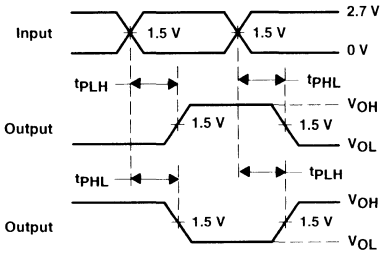
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



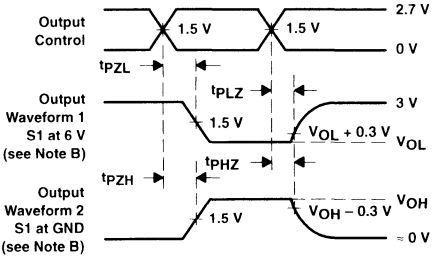
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



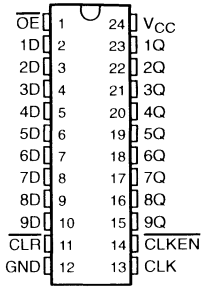
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 9-bit bus-interface flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC823A is designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing wider buffer registers, I/O ports, bidirectional bus drivers with parity, and working registers.

With the clock-enable ($\overline{CLKEN}$) input low, the nine D-type edge-triggered flip-flops enter data on the low-to-high transitions of the clock. Taking $\overline{CLKEN}$ high disables the clock buffer, latching the outputs. This device has noninverting data (D) inputs. Taking the clear ($\overline{CLR}$) input low causes the nine Q outputs to go low, independently of the clock.

A buffered output-enable ($\overline{OE}$) input can be used to place the nine outputs in either a normal logic state (high or low logic levels) or a high-impedance state. $\overline{OE}$ does not affect the internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

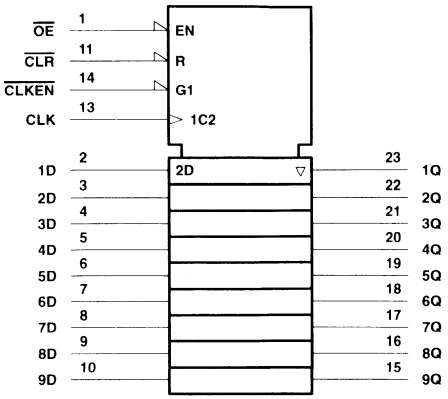
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC823A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

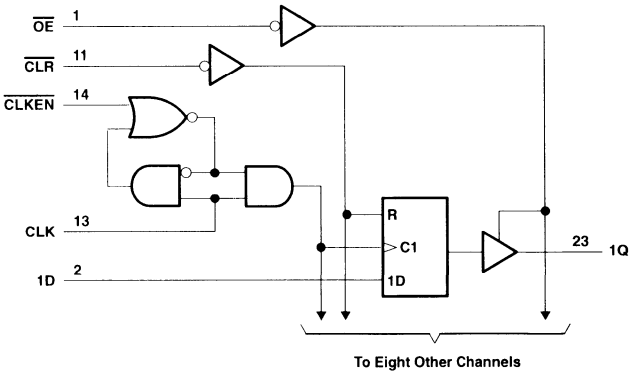
INPUTS					OUTPUT
$\overline{OE}$	$\overline{CLR}$	$\overline{CLKEN}$	CLK	D	Q
L	L	X	X	X	L
L	H	L	↑	H	H
L	H	L	↑	L	L
L	H	H	X	X	Q_0
H	X	X	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
ee Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 104°C/W
DW package ..... 81°C/W
PW package ..... 120°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 0 to 5.5 V		3.6 V			±5	μA
I_{off}		V_I or V_O = 5.5 V		0			±10	μA
I_{OZ}		V_O = 0 to 5.5 V		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			10	μA
		3.6 V ≤ V_I ≤ 5.5 V‡					10	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
	Data inputs					4		
C_o		V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	MHz
t_w	Pulse duration	$\overline{CLR}$ low	3.3		3.3		ns
		CLK high or low	3.3		3.3		
t_{su}	Setup time	$\overline{CLR}$ inactive before CLK↑	1		1		ns
		Data before CLK↑	1.3		1.3		
		$\overline{CLKEN}$ low before CLK↑	1.8		1.8		
t_h	Hold time	Data after CLK↑	2		2		ns
		$\overline{CLKEN}$ low after CLK↑	1.3		1.3		

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

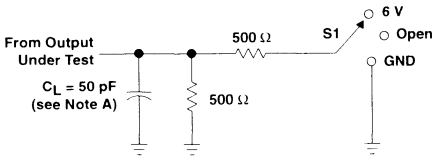
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			150		150		MHz
t_{pd}	CLK	Q	1.4	8		8.9	ns
	$\overline{CLR}$		2.5	7.9		8.8	
t_{en}	$\overline{OE}$	Q	1.6	7.2		8.3	ns
t_{dis}	$\overline{OE}$	Q	1.1	6		7.1	ns
$t_{sk(o)}$				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

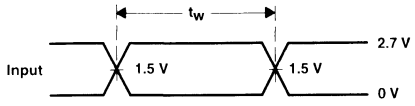
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 0, f = 10 MHz	59	pF
		Outputs disabled		46	

PARAMETER MEASUREMENT INFORMATION

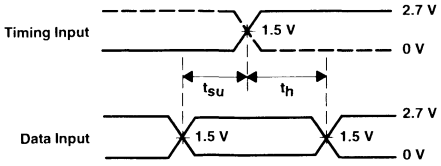


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

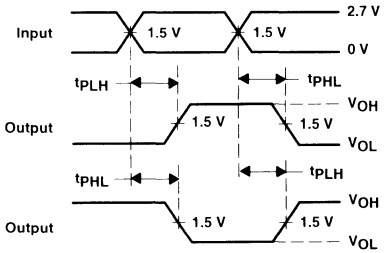
LOAD CIRCUIT



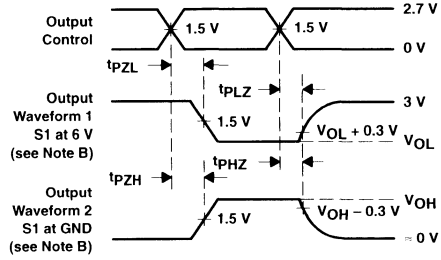
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



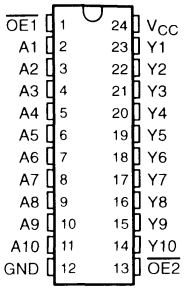
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit buffer/bus driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC827A provides a high-performance bus interface for wide data paths or buses carrying parity.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all ten outputs are in the high-impedance state. The SN74LVC827A provides true data at its outputs.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

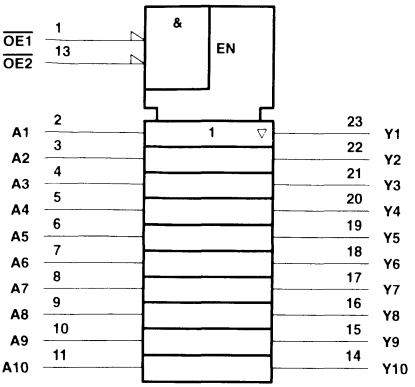
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC827A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

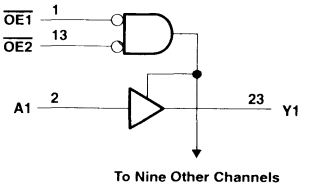
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 104°C/W
DW package ..... 81°C/W
PW package ..... 120°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 0 to 5.5 V		3.6 V			±5	μA
I_{off}		V_I or V_O = 5.5 V		0			±10	μA
I_{OZ}		V_O = 0 to 5.5 V		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			10	μA
		3.6 V ≤ V_I ≤ 5.5 V‡					10	
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	Control	V_I = V_{CC} or GND		3.3 V		5		pF
	Data					4		
C_o		V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

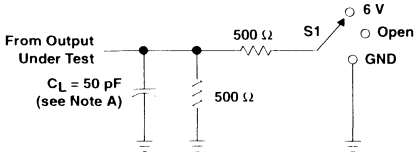
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	6.7		7.1	ns
t_{en}	$\overline{OE}$	Y	1	7.3		8.5	ns
t_{dis}	$\overline{OE}$	Y	1.8	6.7		7.3	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

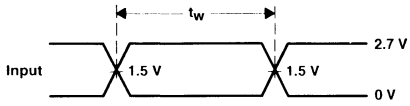
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0, f = 10 MHz	24	pF
		Outputs disabled		5	

PARAMETER MEASUREMENT INFORMATION

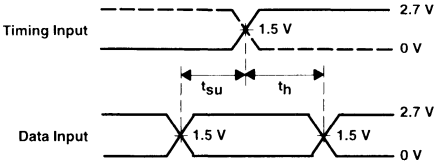


LOAD CIRCUIT

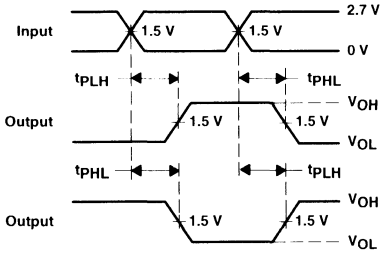
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



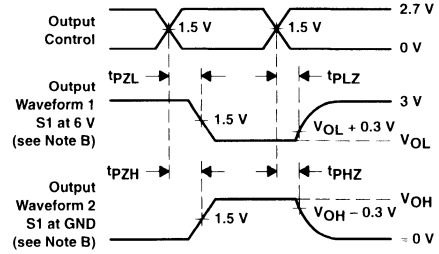
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



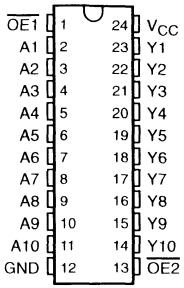
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit buffer/bus driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC828A provides a high-performance bus interface for wide datapaths or buses carrying parity.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all ten outputs are in the high-impedance state. The SN74LVC828A provides inverting data at its outputs.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

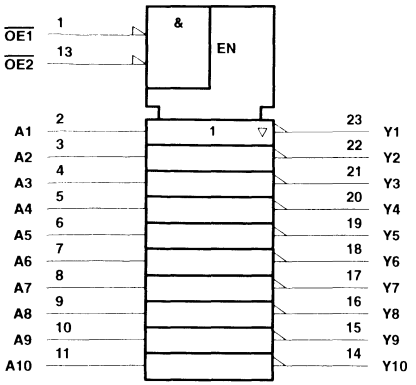
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC828A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

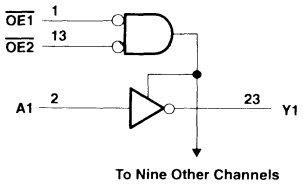
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 104°C/W
DW package ..... 81°C/W
PW package ..... 120°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	μA
I_{off}	V_I or V_O = 5.5 V		0			±10	μA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	μA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			10	μA
	3.6 V ≤ V_I ≤ 5.5 V‡					10	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF
C_o	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

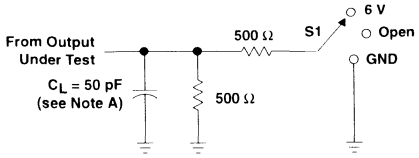
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	6.7		7.1	ns
t_{en}	$\overline{OE}$	Y	1	7.3		8.5	ns
t_{dis}	$\overline{OE}$	Y	1.8	6.7		7.3	ns
$t_{sk(o)}$ †				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

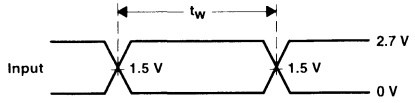
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0,	f = 10 MHz	24	pF
		Outputs disabled			7	

PARAMETER MEASUREMENT INFORMATION

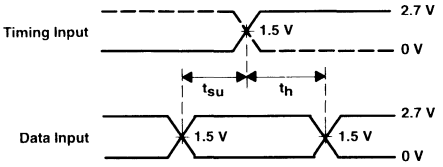


LOAD CIRCUIT

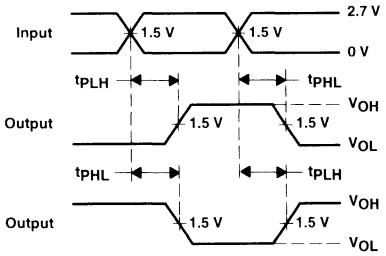
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



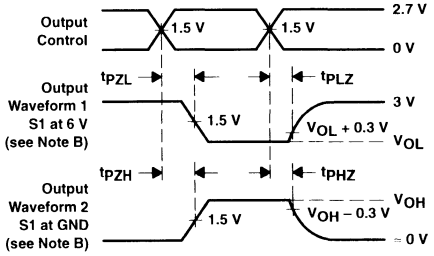
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



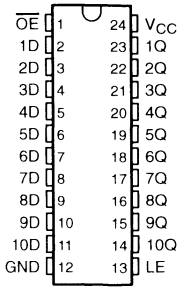
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit bus-interface D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC841A is designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The ten latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the ten outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

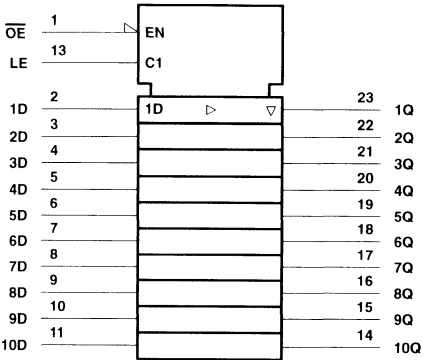
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC841A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

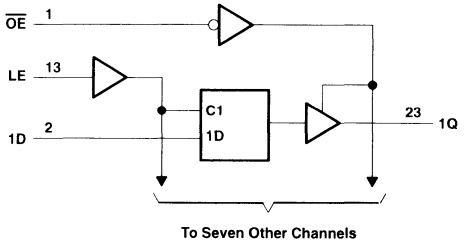
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 104°C/W
DW package . . . . . 81°C/W
PW package . . . . . 120°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			10	µA
	3.6 V ≤ V_I ≤ 5.5 V‡					10	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF
C_o	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration	3.3		3.3		ns
t_{su}	Setup time, data before LE↓	2.1		2.1		ns
t_h	Hold time, data after LE↓	1		1		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

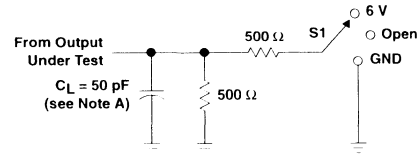
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	D	Q	2.4	6.7		7.5	ns
	LE		2.7	7.6		8.6	
t_{en}	$\overline{OE}$	Q	1.3	7.2		8.5	ns
t_{dis}	$\overline{OE}$	Q	1.9	5.9		6.6	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

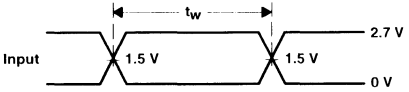
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 0, f = 10 MHz	25	pF
		Outputs disabled		6	

PARAMETER MEASUREMENT INFORMATION

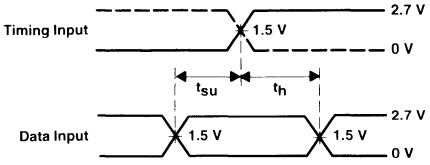


LOAD CIRCUIT

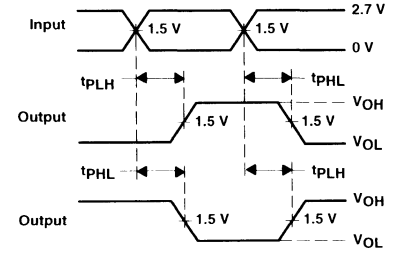
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



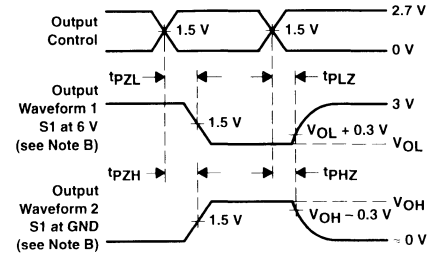
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



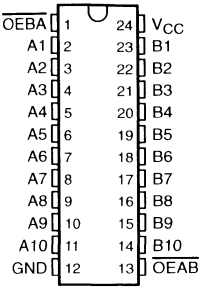
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC861A is designed for asynchronous communication between data buses. The control-function implementation allows for maximum flexibility in timing.

This device allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic levels at the output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) inputs.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

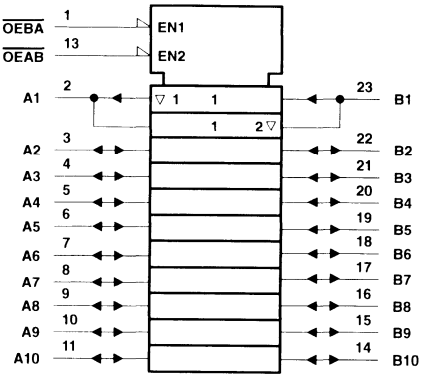
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC861A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

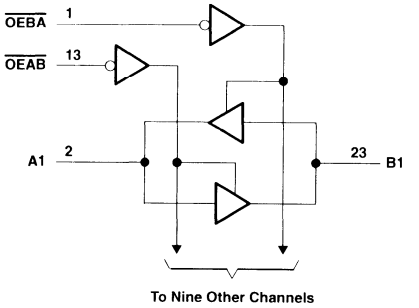
INPUTS		OPERATION
$\overline{OEAB}$	$\overline{OEBA}$	
L	H	A data to B bus
H	L	B data to A bus
H	H	Isolation
L	L	Latch A and B (A = B)

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 104°C/W
DW package . . . . . 81°C/W
PW package . . . . . 120°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}‡		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		$V_I = V_{CC}$ or GND	I_O = 0	3.6 V			10	µA
		3.6 V ≤ V_I ≤ 5.5 V§					10	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	µA
C_i	Control inputs	$V_I = V_{CC}$ or GND		3.3 V		5		pF
C_{io}	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This applies in the disabled state only.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

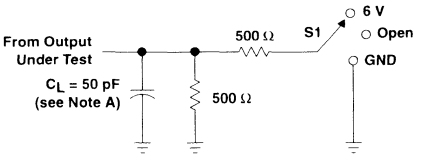
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.3	6.4		6.8	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	7		8.2	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1.7	5.9		6.6	ns
$t_{sk(o)}$¶				1			ns

¶ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

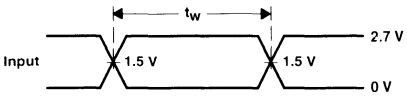
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	29	pF
		Outputs disabled		5	

PARAMETER MEASUREMENT INFORMATION

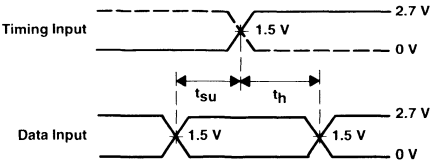


LOAD CIRCUIT

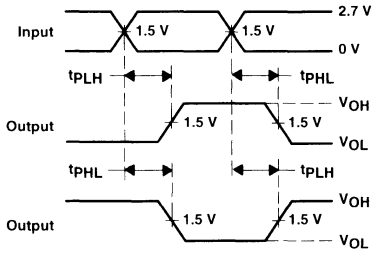
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



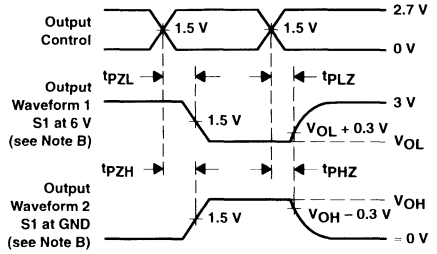
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



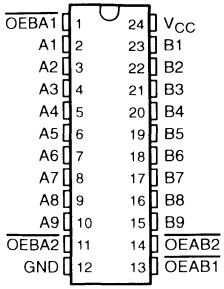
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 9-bit bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC863A is designed for asynchronous communication between data buses. The control-function implementation allows for maximum flexibility in timing.

This device allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic levels at the output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) inputs.

The outputs are in the high-impedance state during power-up and power-down conditions. The outputs remain in the high-impedance state while the device is powered down.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

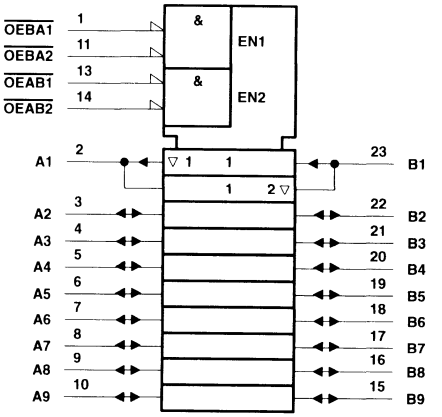
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC863A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

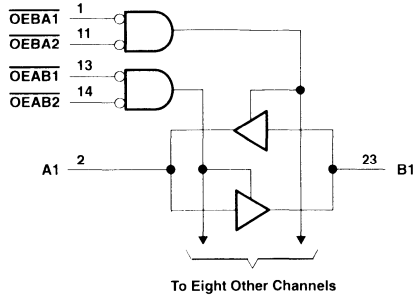
INPUTS				OPERATION
$\overline{OEAB1}$	$\overline{OEAB2}$	$\overline{OEBA1}$	$\overline{OEBA2}$	
L	L	L	L	Latch A and B
L	L	H	X	A to B
L	L	X	H	
H	X	L	L	B to A
X	H	L	L	
H	X	H	X	Isolation
H	X	X	H	
X	H	X	H	
X	H	H	X	

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 104°C/W
DW package . . . . . 81°C/W
PW package . . . . . 120°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 0 to 5.5 V		3.6 V			±5	μA
I_{off}		V_I or V_O = 5.5 V		0			±10	μA
I_{OZ}‡		V_O = 0 to 5.5 V		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			10	μA
		3.6 V ≤ V_I ≤ 5.5 V§					10	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This applies in the disabled state only.

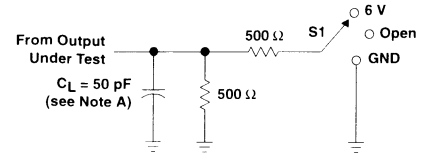
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.7	6.1		6.8	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1.2	7.2		8.3	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	2	6.3		7	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

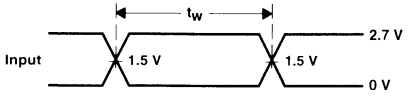
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	27	pF
		Outputs disabled		5	

PARAMETER MEASUREMENT INFORMATION

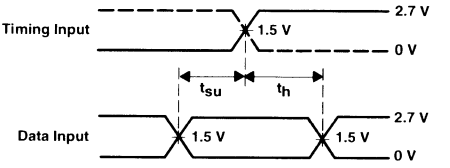


LOAD CIRCUIT

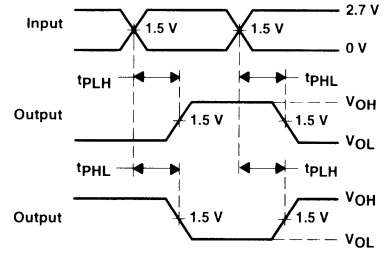
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



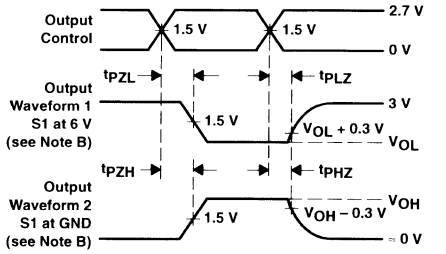
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



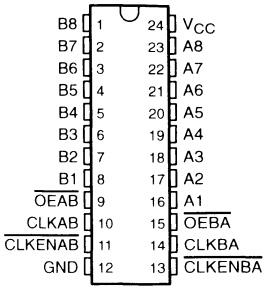
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal bus transceiver and register is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC2952A consists of two 8-bit back-to-back registers that store data flowing in both directions between two bidirectional buses. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input, provided that the clock-enable ($\overline{\text{CLKENAB}}$ or $\overline{\text{CLKENBA}}$) input is low. Taking the output-enable ($\overline{\text{OEAB}}$ or $\overline{\text{OEBA}}$) input low accesses the data on either port.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC2952A is characterized for operation from –40°C to 85°C.

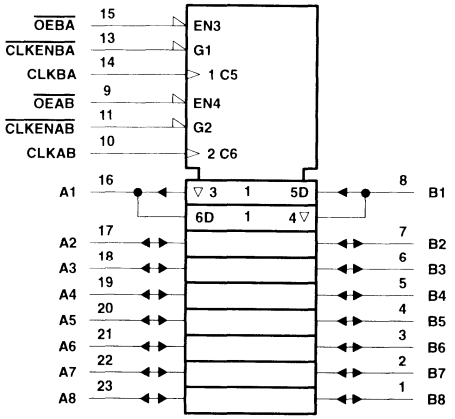
FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{\text{CLKENAB}}$	CLKAB	$\overline{\text{OEAB}}$	A	B
H	X	L	X	B_0‡
X	H or L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

† A-to-B data flow is shown; B-to-A data flow is similar, but uses $\overline{\text{CLKENBA}}$, CLKBA, and $\overline{\text{OEBA}}$.

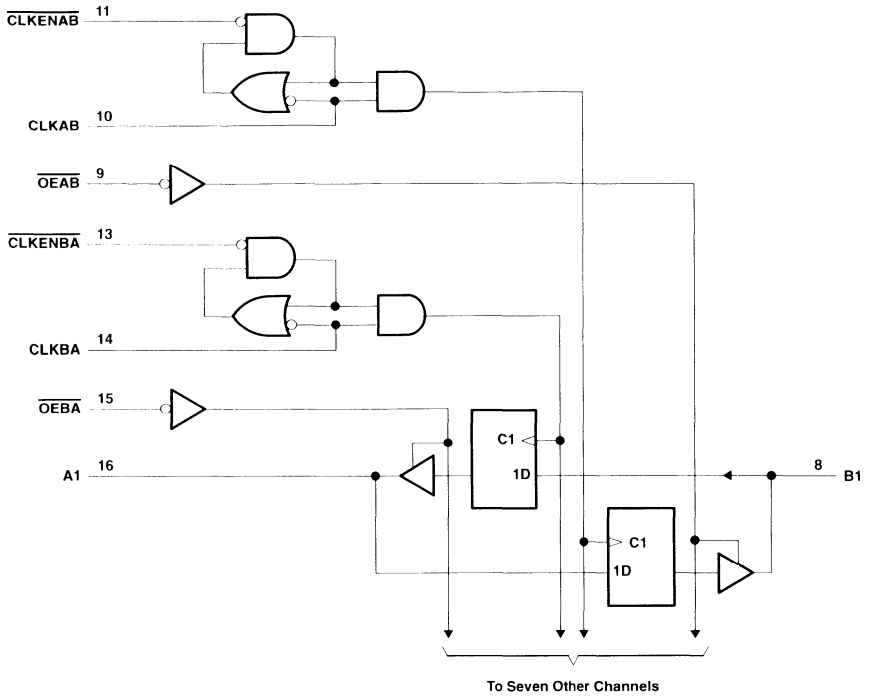
‡ Level of B before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 104°C/W
DW package . . . . . 81°C/W
PW package . . . . . 120°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended oprating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}‡		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			10	µA
		3.6 V ≤ V_I ≤ 5.5 V§					10	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8.5		pF

† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		ns
t_{su}	Setup time	Data before CLK high	1.3		1.7		ns
		$\overline{CLKEN}$ before CLK high	1.1		1.3		
t_h	Hold time	Data after CLK high	1.1		1.8		ns
		$\overline{CLKEN}$ after CLK high	1.1		1.4		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

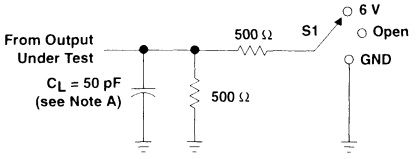
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			150		150		MHz
t_{pd}	CLKAB or CLKBA	B or A	1	8.2		8.8	ns
t_{en}	$\overline{OE}$	A or B	1	7.8		9	ns
t_{dis}	$\overline{OE}$	A or B	1	7.8		8.8	ns
$t_{sk(o)}$¶				1			ns

¶ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

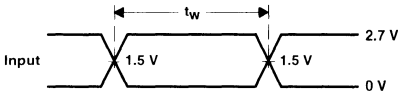
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	79	pF
		Outputs disabled		41	

PARAMETER MEASUREMENT INFORMATION

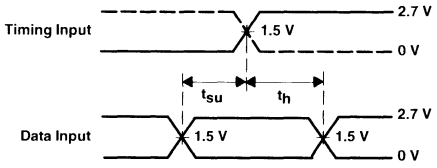


LOAD CIRCUIT

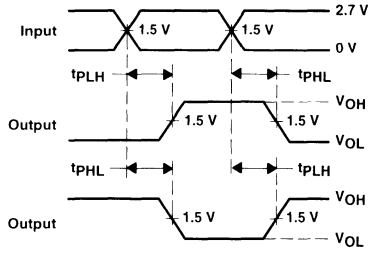
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



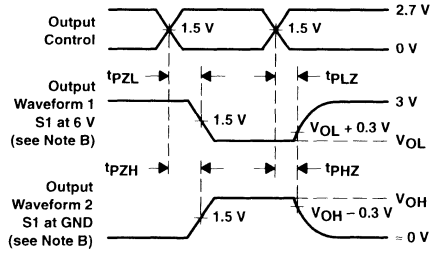
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

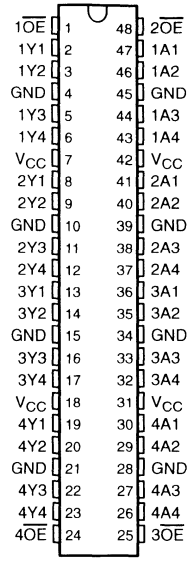
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

Contents

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16240A is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. This device provides inverting outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

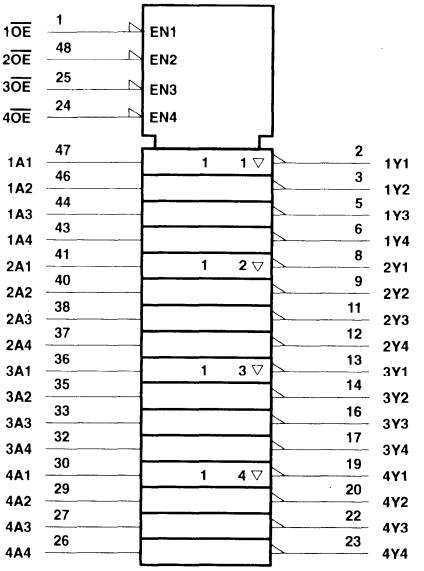
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVCH16240A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

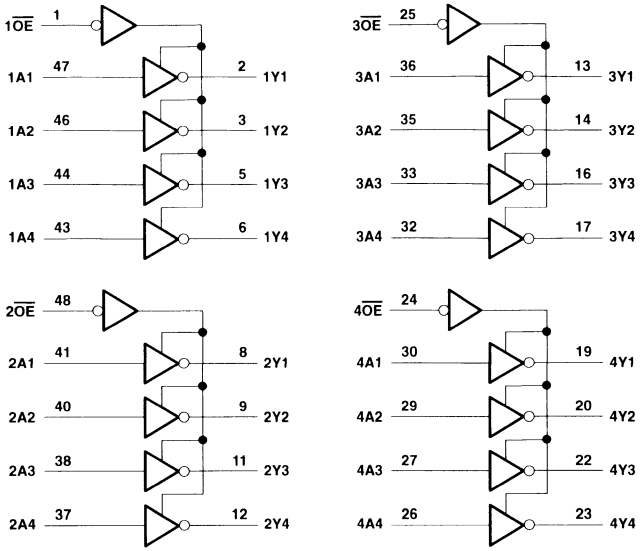
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.8 V		3 V	75			µA
	V_I = 2 V		3 V	–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}	V_O = 0 to 5.5 V		2.7 V to 3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
	3.6 V ≤ V_I ≤ 5.5 V§					20	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF
C_o	V_O = V_{CC} or GND		3.3 V		6		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ This applies in the disabled state only.

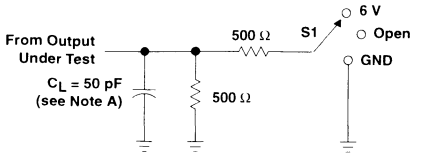
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.2		5	ns
t_{en}	$\overline{OE}$	Y	1.5	4.7		5.8	ns
t_{dis}	$\overline{OE}$	Y	1.5	5.9		6.6	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

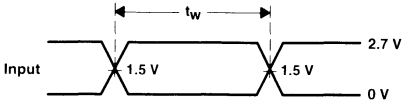
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0,	f = 10 MHz	34	pF
		Outputs disabled			3	

PARAMETER MEASUREMENT INFORMATION

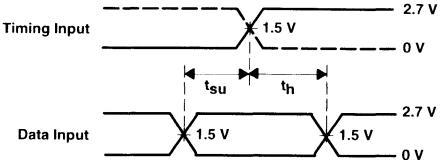


LOAD CIRCUIT

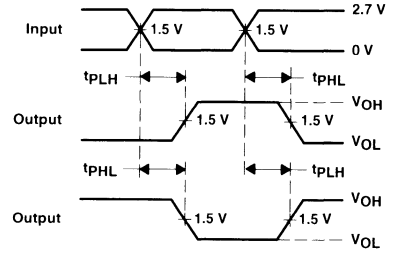
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



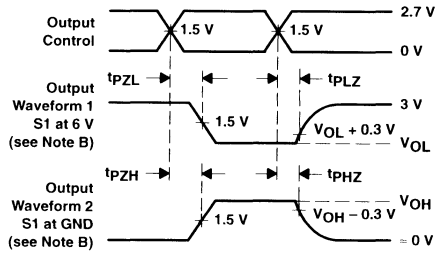
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
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- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Outputs, Permitting Live Insertion**
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- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
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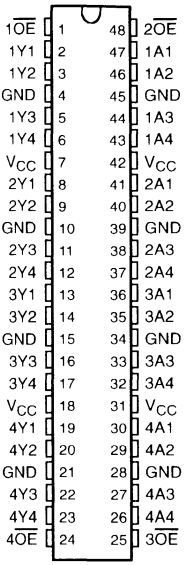
DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC16244A is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

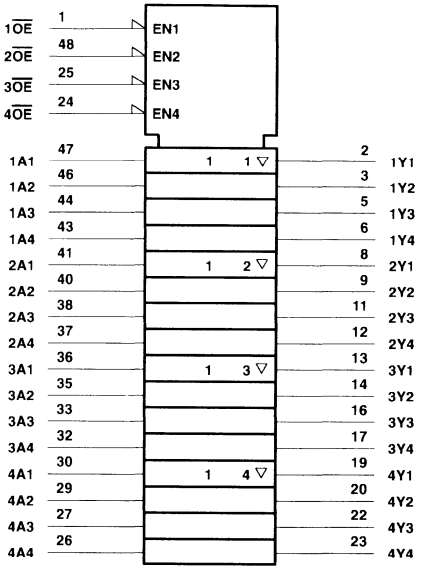
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC16244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

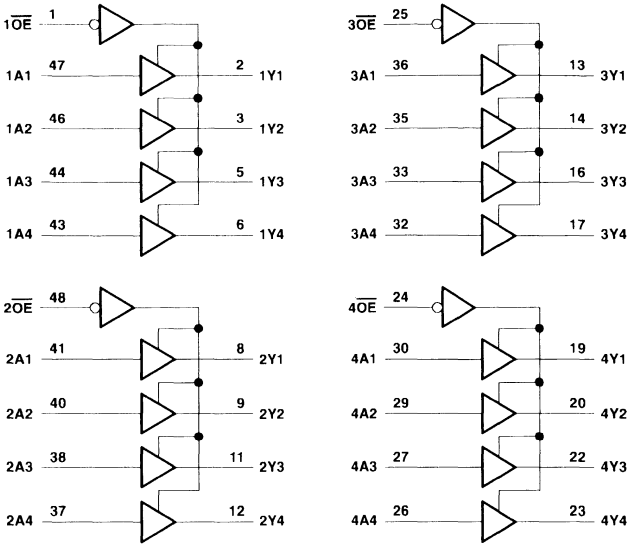
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0) ..... –50 mA
Continuous output current, I_O ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
	3.6 V ≤ V_I ≤ 5.5 V‡					20	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5.5		pF
C_o	V_O = V_{CC} or GND		3.3 V		6		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

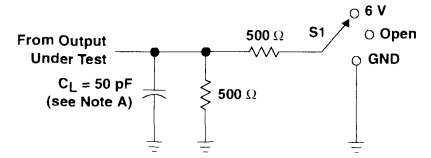
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.1	4.1		4.7	ns
t_{en}	$\overline{OE}$	Y	1	4.6		5.8	ns
t_{dis}	$\overline{OE}$	Y	1.8	5.8		6.2	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

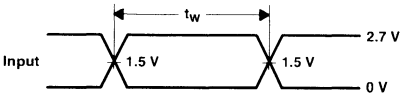
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0, f = 10 MHz	34	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

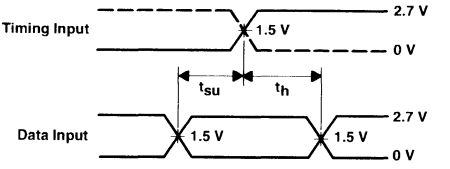


LOAD CIRCUIT

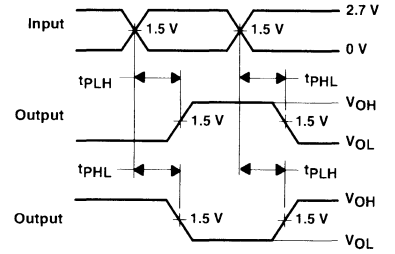
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



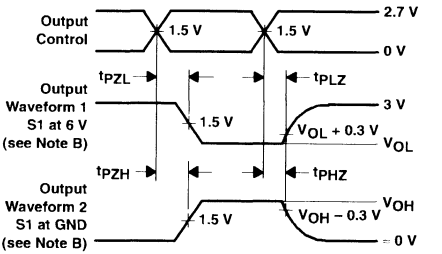
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
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LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
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C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
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E. t_{PZL} and t_{PZH} are the same as t_{en}.
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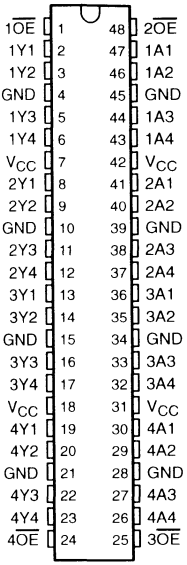
DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16244A is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

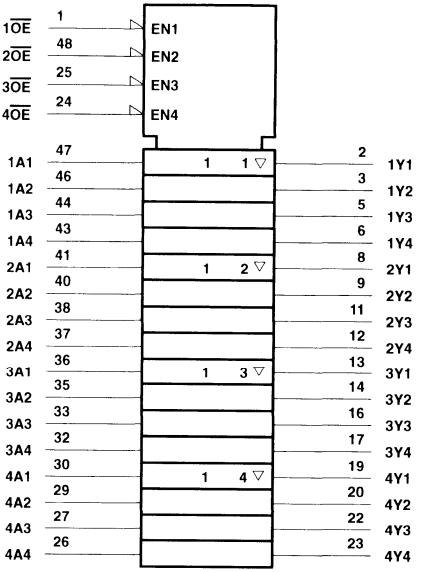
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVCH16244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

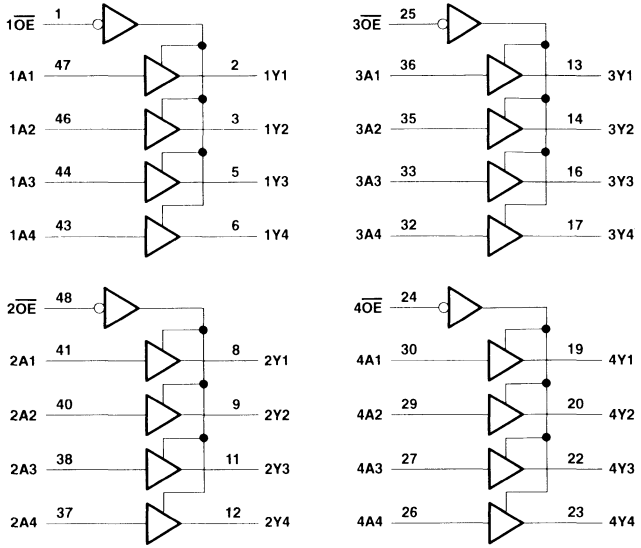
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC} –0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
$I_{I(hold)}$	V_I = 0.8 V		3 V	75			µA
	V_I = 2 V		3 V	–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
	3.6 V ≤ V_I ≤ 5.5 V§					20	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5.5		pF
C_o	V_O = V_{CC} or GND		3.3 V		6		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

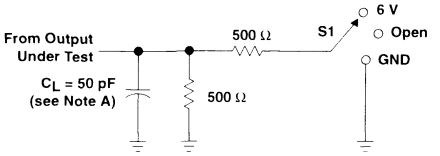
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.1	4.1		4.7	ns
t_{en}	$\overline{OE}$	Y	1	4.6		5.8	ns
t_{dis}	$\overline{OE}$	Y	1.8	5.8		6.2	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

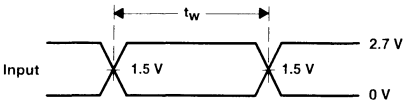
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	34	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

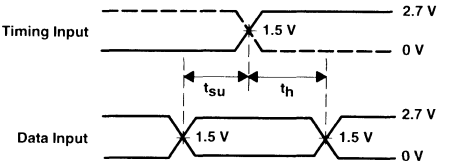


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

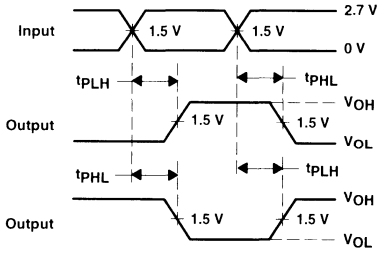
LOAD CIRCUIT



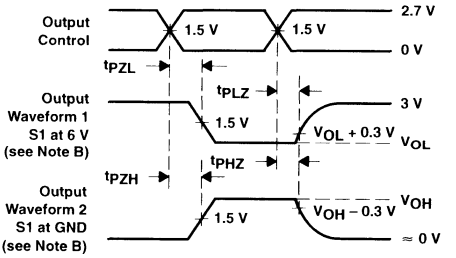
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



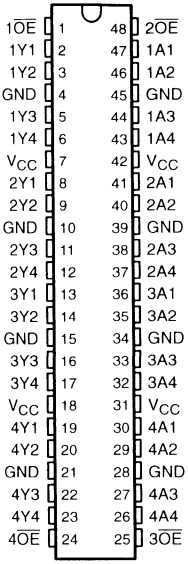
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH162244A is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

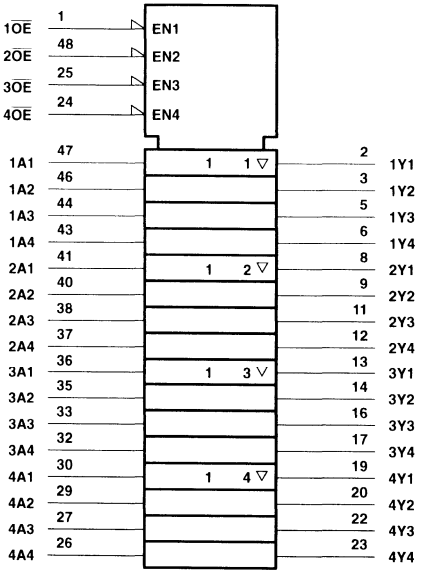
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVCH162244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

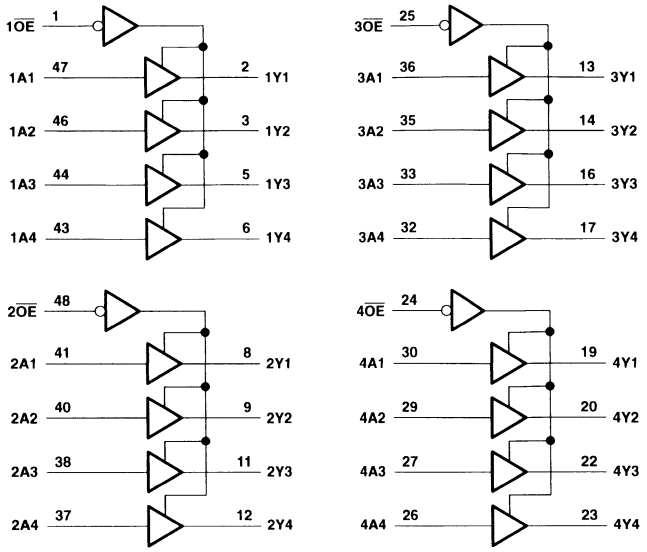
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–8	mA
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		8	mA
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC} –0.2			V
	I_{OH} = –4 mA		2.7 V	2.2			
	I_{OH} = –6 mA		3 V	2.4			
	I_{OH} = –8 mA		2.7 V	2			
	I_{OH} = –12 mA		3 V	2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 4 mA		2.7 V			0.4	
	I_{OL} = 6 mA		3 V			0.55	
	I_{OL} = 8 mA		2.7 V			0.6	
	I_{OL} = 12 mA		3 V			0.8	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
$I_{I(hold)}$	V_I = 0.8 V		3 V	75			µA
	V_I = 2 V		3 V	–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
	3.6 V ≤ V_I ≤ 5.5 V§					20	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5.5		pF
C_o	V_O = V_{CC} or GND		3.3 V		6		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ This applies in the disabled state only.

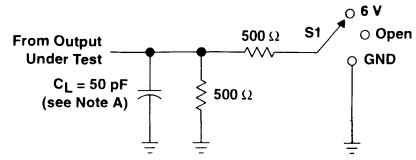
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.1	4.4		5.6	ns
t_{en}	$\overline{OE}$	Y	1	5.5		6.9	ns
t_{dis}	$\overline{OE}$	Y	1.8	6.3		6.8	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

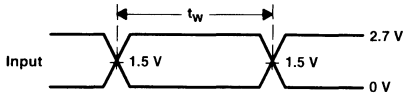
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0,	f = 10 MHz	35	pF
		Outputs disabled			4	

PARAMETER MEASUREMENT INFORMATION

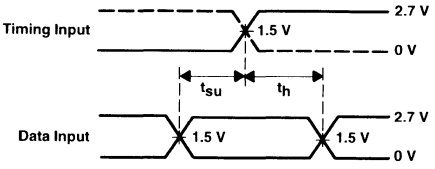


LOAD CIRCUIT

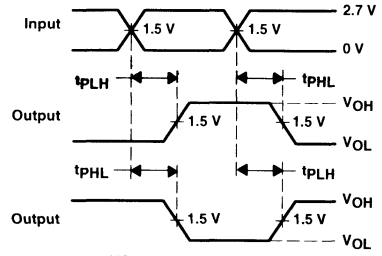
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



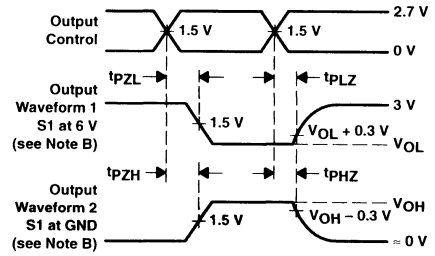
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



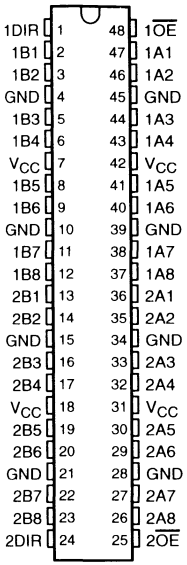
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC16245A is designed for asynchronous communication between data buses. The control-function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

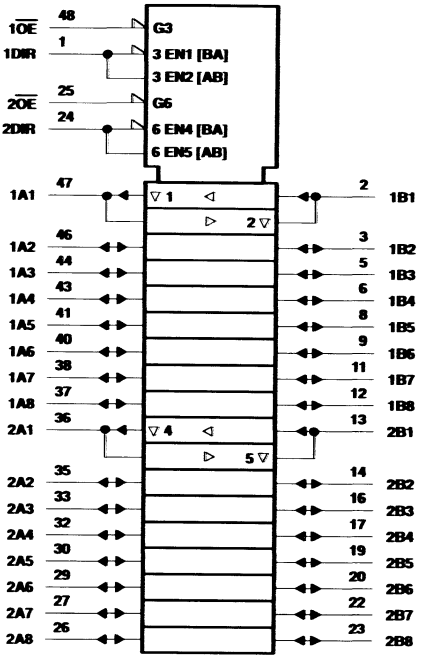
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC16245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

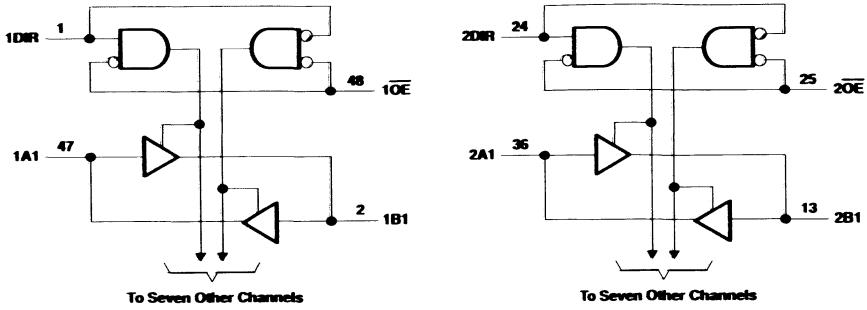
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	5	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	V_I = 0 to 5.5 V		3.6 V			±5	µA
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}‡		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
		3.6 V ≤ V_I ≤ 5.5 V§					20	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current, but not $I_{I(hold)}$.
§ This applies in the disabled state only.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	4		4.7	ns
t_{en}	$\overline{OE}$	A or B	1.5	5.5		6.7	ns
t_{dis}	$\overline{OE}$	A or B	1.5	6.6		7.1	ns
$t_{sk(o)}$†				1			ns

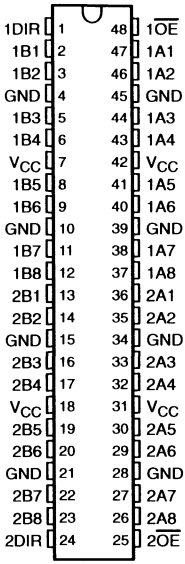
† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0,	f = 10 MHz	38	pF
		Outputs disabled			4	

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16245A is designed for asynchronous communication between data buses. The control-function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

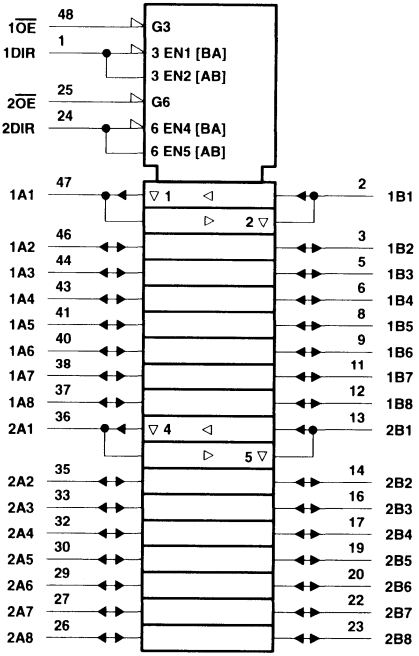
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVCH16245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

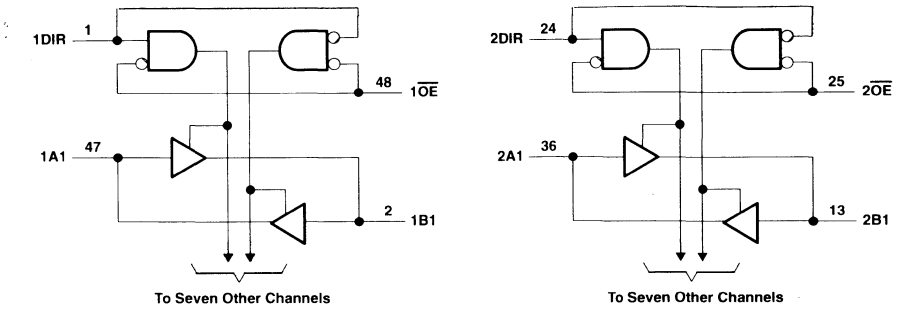
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	5	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	V_I = 0 to 5.5 V		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.8 V		3 V	75			µA
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}§		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
		3.6 V ≤ V_I ≤ 5.5 V¶					20	
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current, but not $I_{I(hold)}$.
¶ This applies in the disabled state only.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

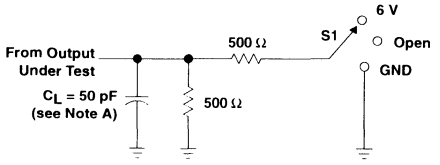
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	4		4.7	ns
t_{en}	$\overline{OE}$	A or B	1.5	5.5		6.7	ns
t_{dis}	$\overline{OE}$	A or B	1.5	6.6		7.1	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

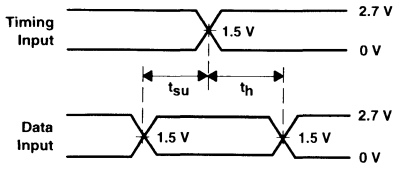
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	40	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

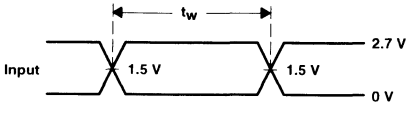


LOAD CIRCUIT

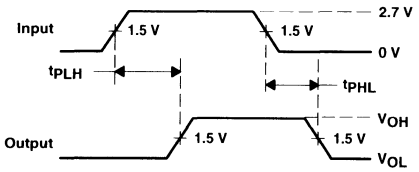
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



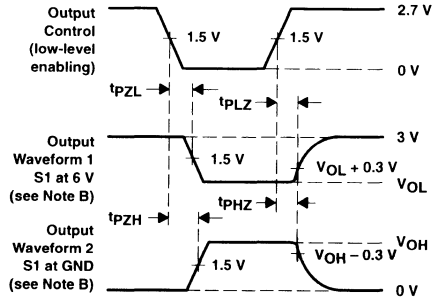
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



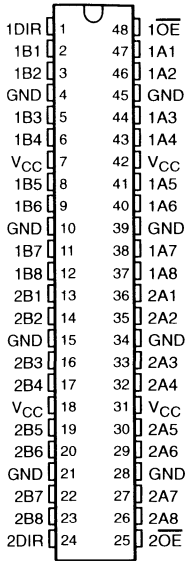
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- Member of the Texas Instruments *Widebus*™ Family
- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- All Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCHR162245A is designed for asynchronous communication between data buses. The control-function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

All outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

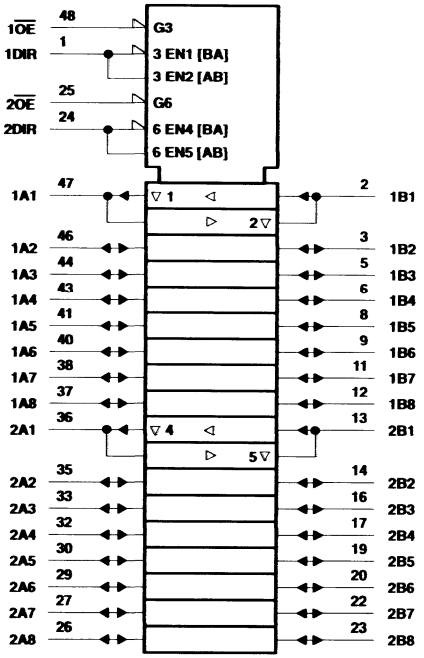
description (continued)

The SN74LVCHR162245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

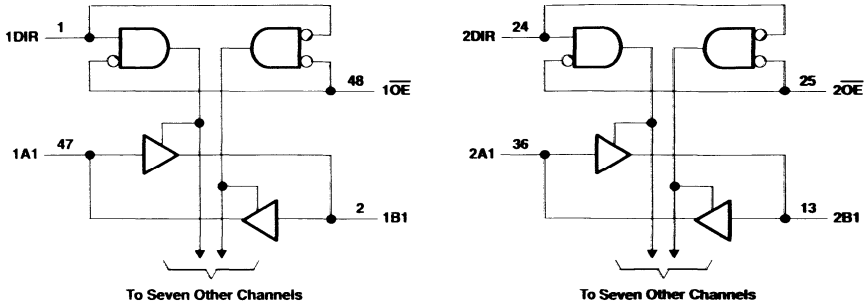
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 97°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–8	mA
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		8	mA
		V_{CC} = 3 V		12	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA		2.7 V	2.2			
		I_{OH} = –6 mA		3 V	2.4			
		I_{OH} = –8 mA		2.7 V	2			
		I_{OH} = –12 mA		3 V	2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 4 mA		2.7 V			0.4	
		I_{OL} = 6 mA		3 V			0.55	
		I_{OL} = 8 mA		2.7 V			0.6	
		I_{OL} = 12 mA		3 V			0.8	
I_I		V_I = 0 to 5.5 V		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.8 V		3 V	75			µA
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}§		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
		3.6 V ≤ V_I ≤ 5.5 V¶					20	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.
¶ This applies in the disabled state only.

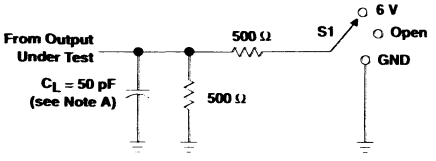
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	4.8		5.7	ns
t_{en}	$\overline{OE}$	A or B	1.5	6.3		7.9	ns
t_{dis}	$\overline{OE}$	A or B	2.2	7.4		8.3	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

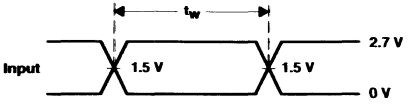
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0,	f = 10 MHz	39	pF
		Outputs disabled			4	

PARAMETER MEASUREMENT INFORMATION

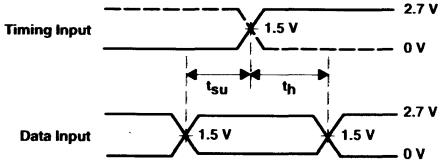


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

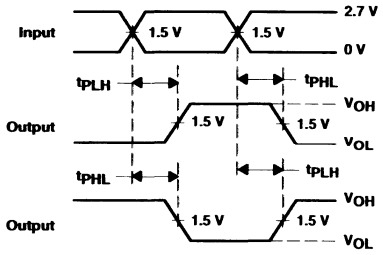
LOAD CIRCUIT



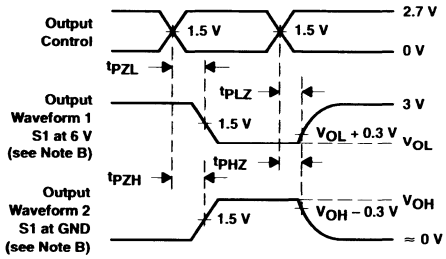
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



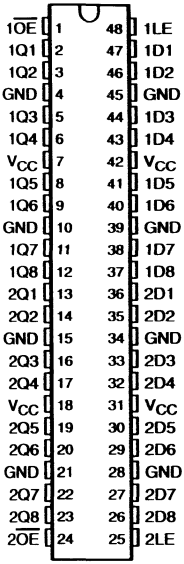
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit transparent D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16373A is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. It can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

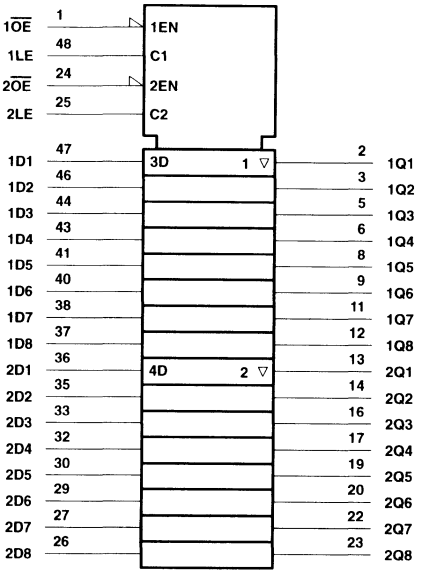
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVCH16373A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

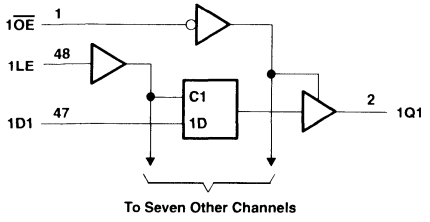
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

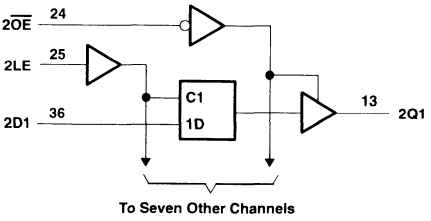
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . **94°C/W**
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.8 V		3 V	75			µA
	V_I = 2 V		3 V	–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
	3.6 V ≤ V_I ≤ 5.5 V§					20	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF
C_o	V_O = V_{CC} or GND		3.3 V		6.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3.3		3.3		ns
t_{su}	Setup time, data before LE↓	1.7		1.7		ns
t_h	Hold time, data after LE↓	1.2		1.2		ns

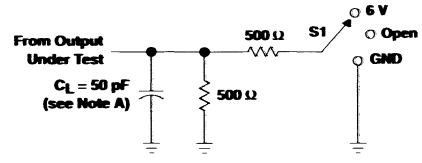
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1.6	4.2		4.9	ns
	LE		2.1	4.6		5.3	
t_{en}	$\overline{OE}$	Q	1.3	4.7		5.7	ns
t_{dis}	$\overline{OE}$	Q	2.5	5.9		6.3	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

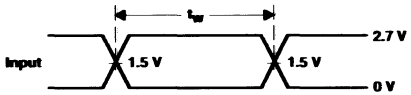
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 0,	f = 10 MHz	39	pF
		Outputs disabled			6	

PARAMETER MEASUREMENT INFORMATION

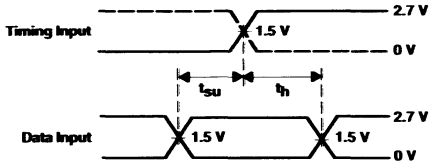


LOAD CIRCUIT

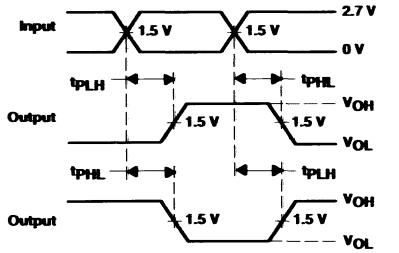
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



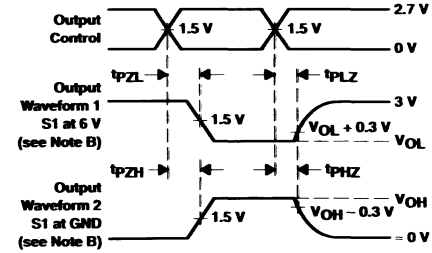
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



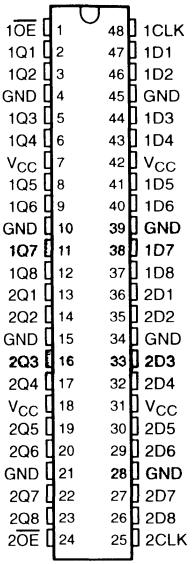
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit edge-triggered D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16374A is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (CLK) input, the Q outputs of the flip-flop take on the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

description (continued)

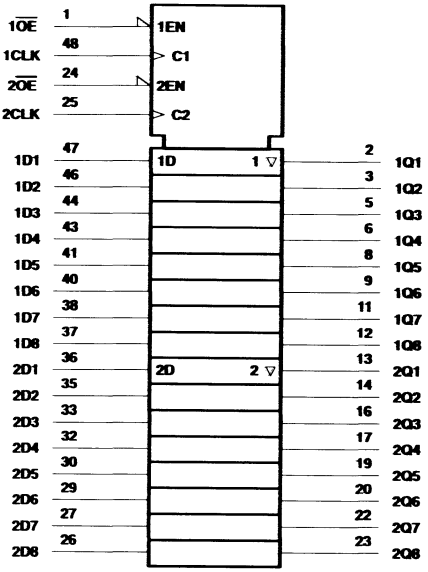
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVCH16374A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

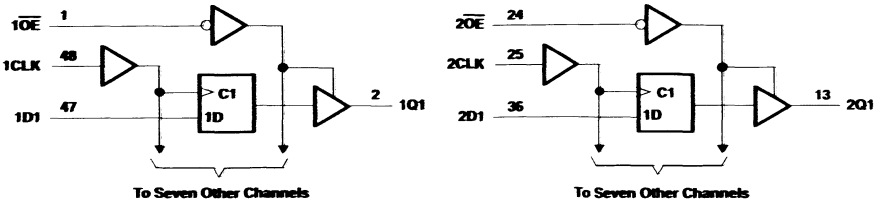
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 89°C/W
DL package ..... 94°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 0 to 5.5 V		3.6 V			±5	μA
$I_{I(hold)}$	Data inputs	V_I = 0.8 V		3 V	75			μA
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}		V_I or V_O = 5.5 V		0			±10	μA
I_{OZ}		V_O = 0 to 5.5 V		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			20	μA
		3.6 V ≤ V_I ≤ 5.5 V§					20	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	μA
C_i		V_I = V_{CC} or GND		3.3 V		5		pF
C_o		V_O = V_{CC} or GND		3.3 V		6.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.9		1.9		ns
t_h	Hold time, data after CLK↑	1.1		1.1		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

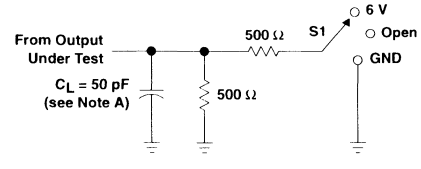
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			150		150		MHz
t_{pd}	CLK	Q	1.5	4.5		4.9	ns
t_{en}	$\overline{OE}$	Q	1.5	4.6		5.3	ns
t_{dis}	$\overline{OE}$	Q	1.5	5.5		6.1	ns
$t_{sk(o)}$¶				1			ns

¶ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

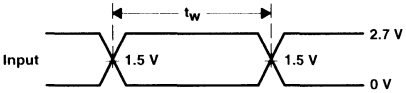
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 0, f = 10 MHz	58	pF
		Outputs disabled		24	

PARAMETER MEASUREMENT INFORMATION

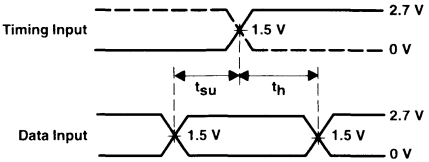


LOAD CIRCUIT

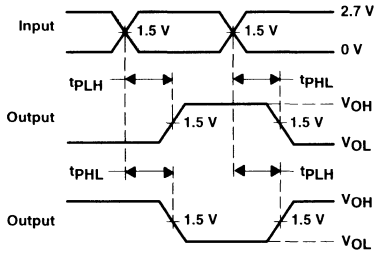
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



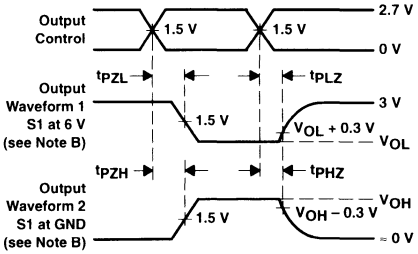
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



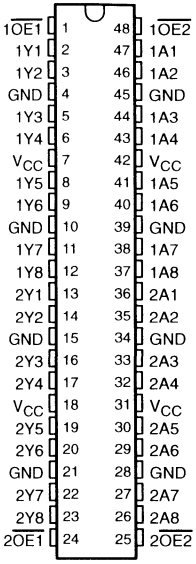
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin-Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation, and provides a high-performance bus interface for wide data paths.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all corresponding outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

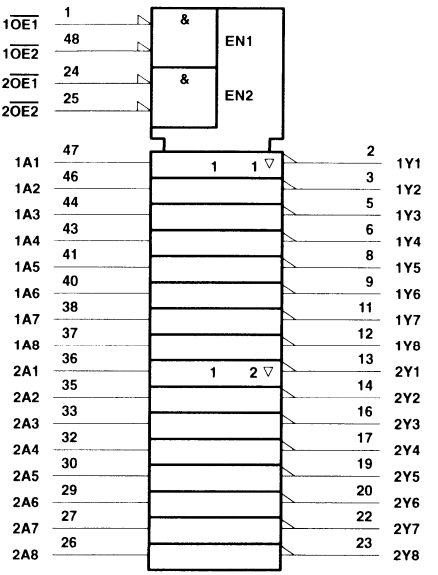
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVCH16540A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

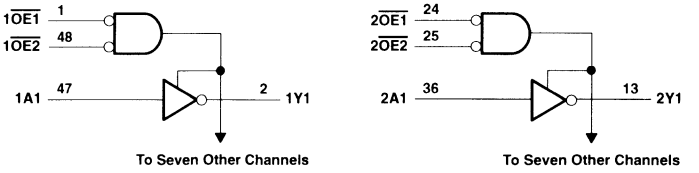
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.8 V		3 V	75			µA
	V_I = 2 V		3 V	–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
	3.6 V ≤ V_I ≤ 5.5 V§					20	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF
C_o	V_O = V_{CC} or GND		3.3 V		6.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ This applies in the disabled state only.

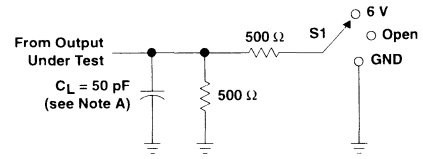
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	3.7		4.5	ns
t_{en}	$\overline{OE}$	Y	1.5	4.8		5.9	ns
t_{dis}	$\overline{OE}$	Y	1.6	5.9		6.3	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

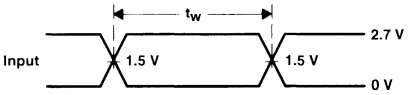
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0,	f = 10 MHz	34	pF
		Outputs disabled			2	

PARAMETER MEASUREMENT INFORMATION

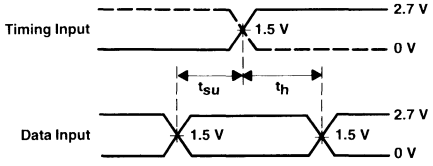


LOAD CIRCUIT

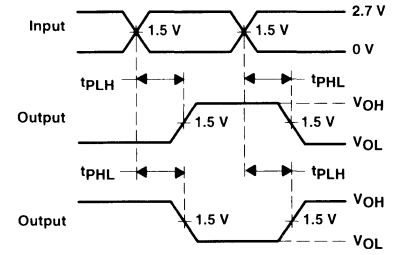
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



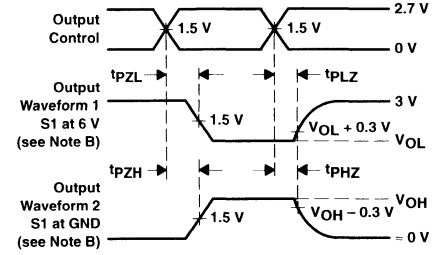
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



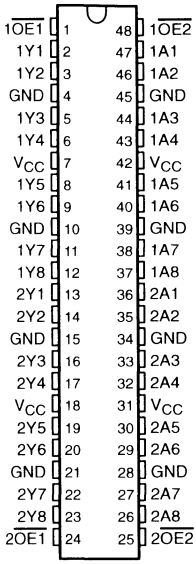
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Thin-Shrink Small-Outline (DGG) and Plastic 300-mil Shrink Small-Outline (DL) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16541A is a noninverting 16-bit buffer composed of two 8-bit sections with separate output-enable signals. For either 8-bit buffer section, the two output-enable ($1\overline{OE1}$ and $1\overline{OE2}$ or $2\overline{OE1}$ and $2\overline{OE2}$) inputs must be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 8-bit buffer section are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

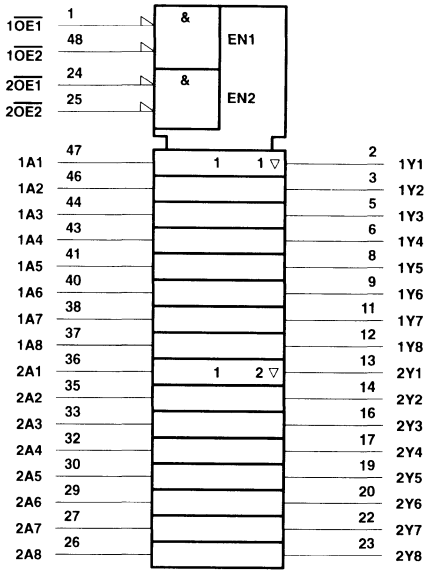
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVCH16541A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

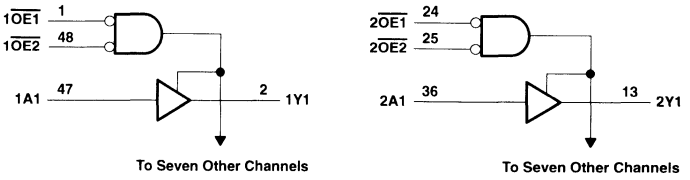
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 89°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 0 to 5.5 V		3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.8 V		3 V	75			µA
	V_I = 2 V		3 V	–75			
	V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}	V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}	V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
	3.6 V ≤ V_I ≤ 5.5 V§					20	
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF
C_o	V_O = V_{CC} or GND		3.3 V		6.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ This applies in the disabled state only.

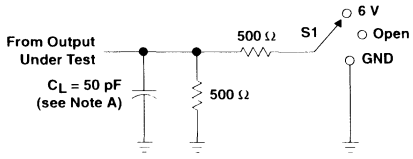
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.1	4.2		5	ns
t_{en}	$\overline{OE}$	Y	1.5	5.6		6.9	ns
t_{dis}	$\overline{OE}$	Y	1.9	6.8		7.4	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

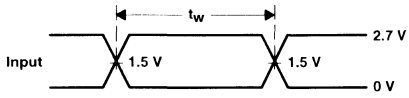
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 0,	f = 10 MHz	35	pF
		Outputs disabled			4	

PARAMETER MEASUREMENT INFORMATION

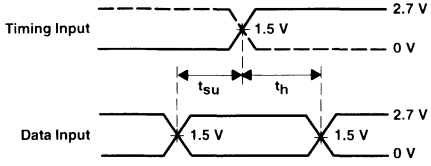


LOAD CIRCUIT

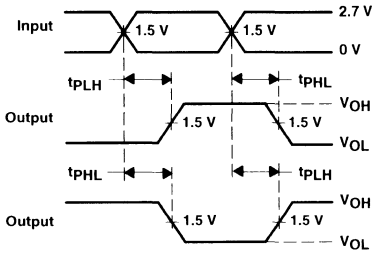
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



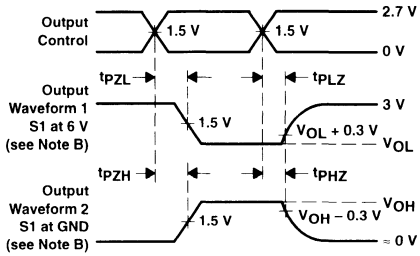
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



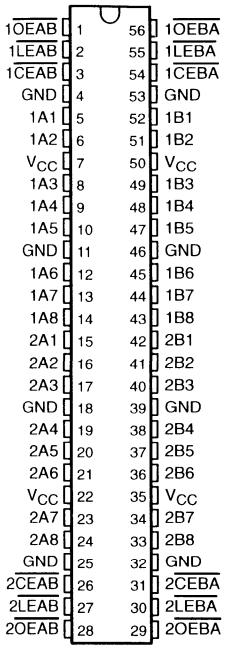
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit registered transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16543A can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ puts the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar, but requires using the $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$ inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

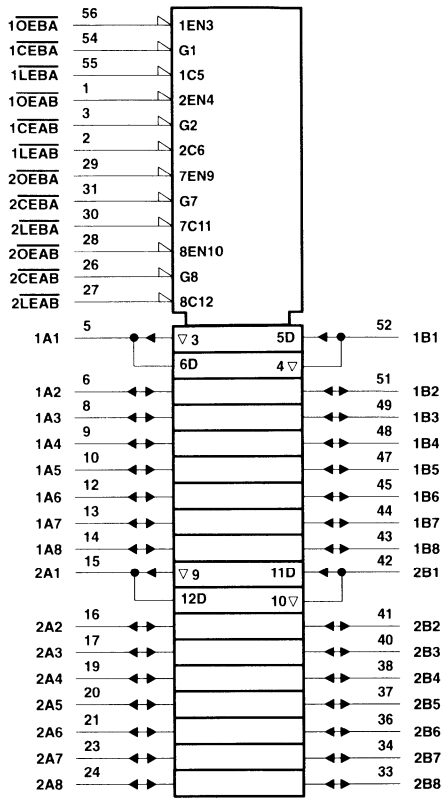
The SN74LVCH16543A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE† (each 8-bit section)

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

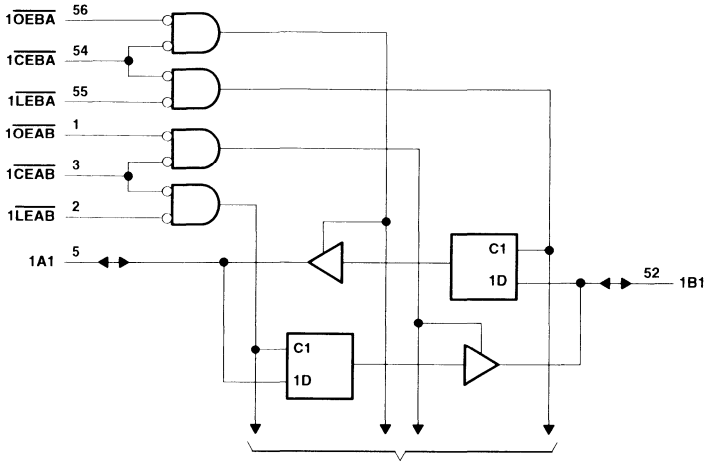
† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

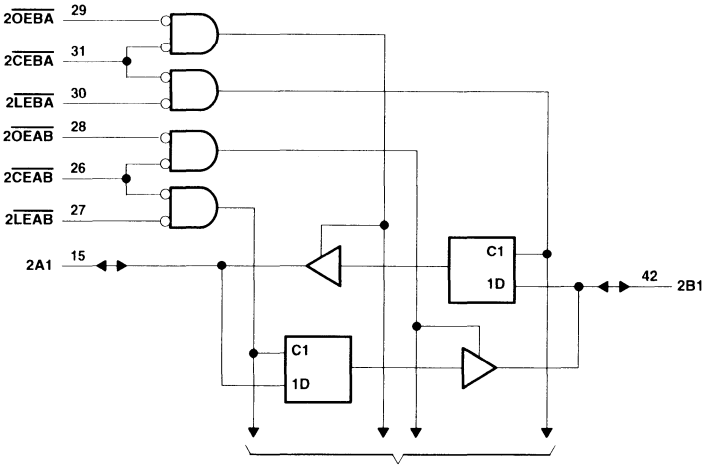
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

§ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	V_I = 0 to 5.5 V		3.6 V			±5	μA
$I_{I(hold)}$	A or B ports	V_I = 0.8 V		3 V	75			μA
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}		V_I or V_O = 5.5 V		0			±10	μA
I_{OZ}§		V_O = 0 to 5.5 V		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			20	μA
		3.6 V ≤ V_I ≤ 5.5 V¶					20	
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current, but not $I_{I(hold)}$.
¶ This applies in the disabled state only.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, $\overline{LE}$ or $\overline{CE}$ low	3.3		3.3		ns
t_{su}	Setup time, data before $\overline{LE}$ or $\overline{CE}$↓	1.1		1.1		ns
t_h	Hold time, data after $\overline{LE}$ or $\overline{CE}$↓	1.9		1.9		ns

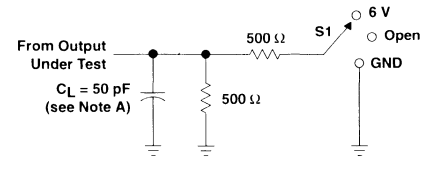
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.2	5.4		6.1	ns
	$\overline{LE}$	A or B	1.5	6.1		7.4	
t_{en}	$\overline{CE}$	A or B	1.2	6.6		7.9	ns
t_{dis}			1.5	6.6		7.1	
t_{en}	$\overline{OE}$	A or B	1	6.3		7.6	ns
t_{dis}			1.5	6.3		6.9	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

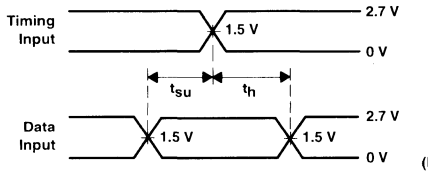
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	44	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

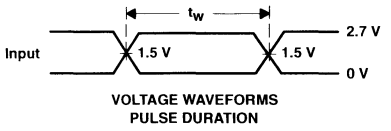


LOAD CIRCUIT

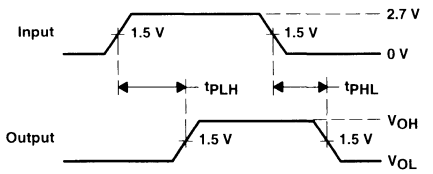
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



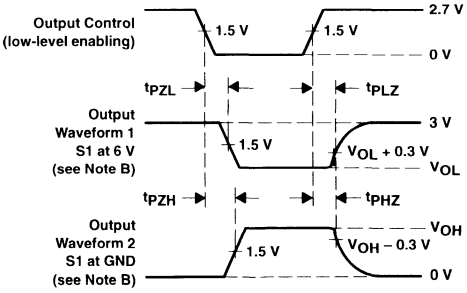
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



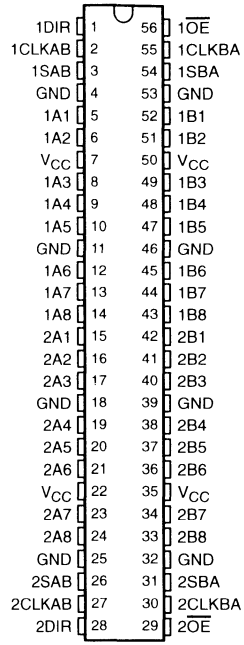
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit bus transceiver and register is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16646A can be used as two 8-bit transceivers or one 16-bit transceiver. The device consists of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers.

Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74LVCH16646A.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs control the transceiver functions. In the transceiver mode, data present at the high-impedance port can be stored in either register or in both. The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. DIR determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data can be stored in one register and/or B data can be stored in the other register.

description (continued)

When an output function is disabled, the input function is still enabled and can be used to store and transmit data. Only one of the two buses, A or B, can be driven at a time.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

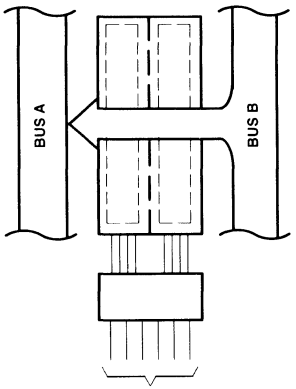
Active bus-hold circuitry holds unused or floating data inputs at a valid logic level.

The SN74LVCH16646A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

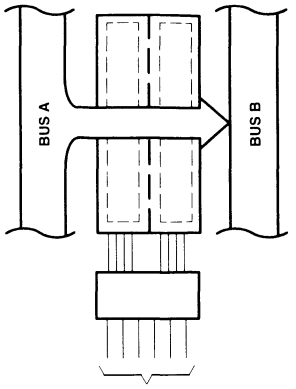
INPUTS						DATA I/O†		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
X	X	↑	X	X	X	Input	Unspecified	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input	Input	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B Bus
L	H	H or L	X	H	X	Input	Output	Stored A data to bus

† The data-output functions may be enabled or disabled by various signals at $\overline{OE}$ or DIR. Data-input functions are always enabled, i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.



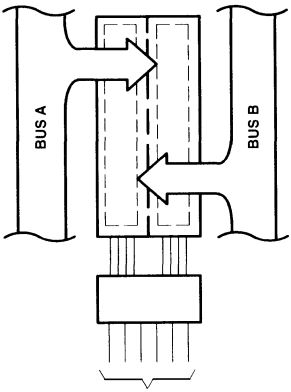
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



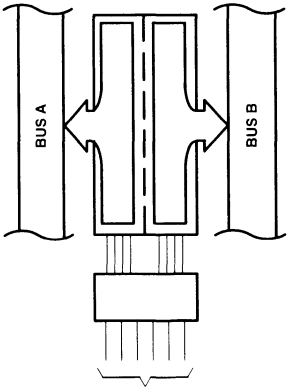
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B

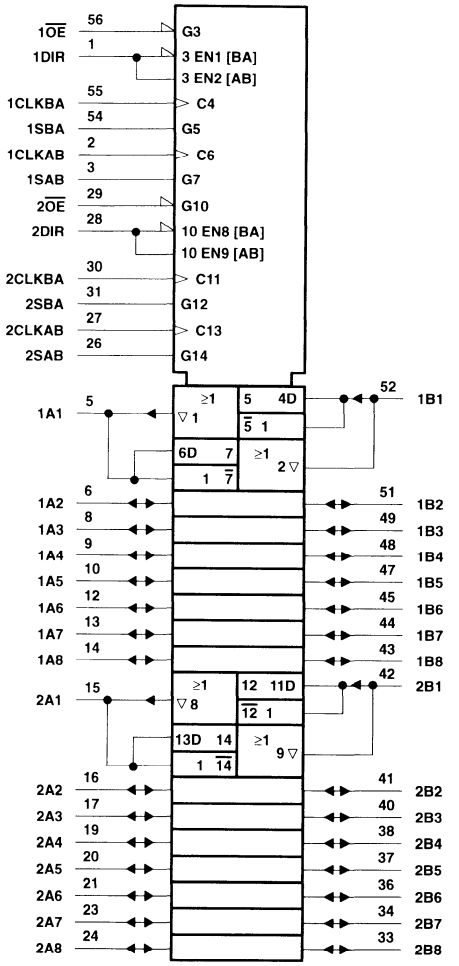


$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA
TO A AND/OR B

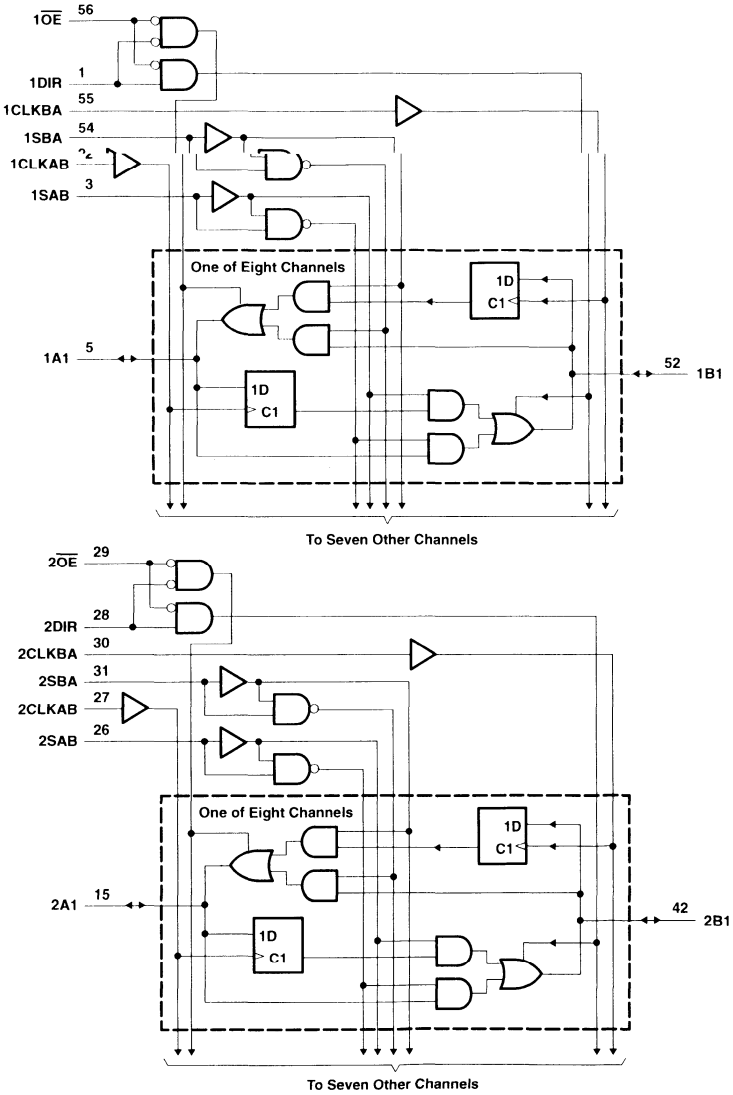
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	V_I = 0 to 5.5 V		3.6 V			±5	µA
$I_{I(hold)}$	A or B ports	V_I = 0.8 V		3 V	75			µA
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}§		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
		3.6 V ≤ V_I ≤ 5.5 V¶					20	
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current, but not $I_{I(hold)}$.
¶ This applies in the disabled state only.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 2)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high or low	2.9		3.2		ns
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑	Data high or low	0.3		0		ns

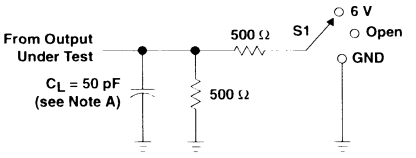
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			150		150		MHz
t_{pd}	A or B	B or A	1.3	5.7		6.8	ns
	CLKAB or CLKBA	A or B	1.8	6.7		7.9	
	SAB or SBA		1.7	7.7		9.2	
t_{en}	$\overline{OE}$	A or B	1.3	6.9		8.5	ns
t_{dis}			2.1	6.9		7.7	
t_{en}	DIR	A or B	1.4	7.2		8.5	ns
t_{dis}			2	7		7.8	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

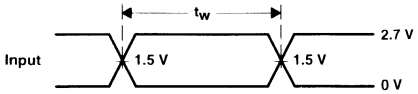
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0,	f = 10 MHz	60	pF
		Outputs disabled			12	

PARAMETER MEASUREMENT INFORMATION

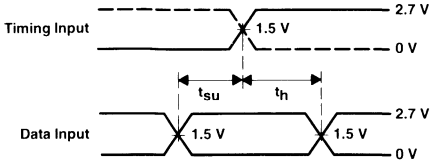


LOAD CIRCUIT

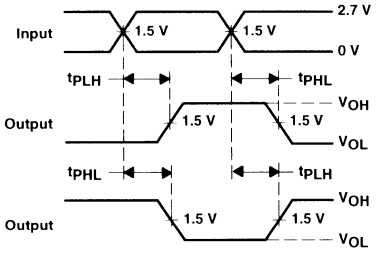
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



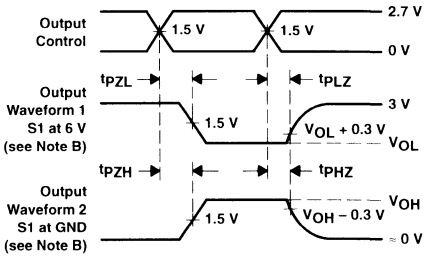
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



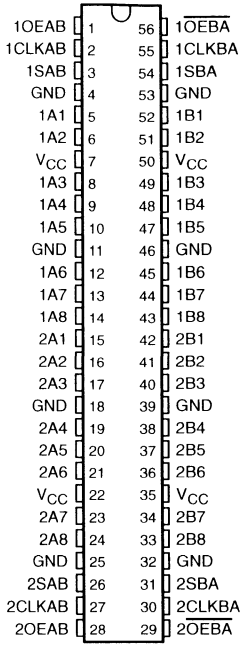
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit bus transceiver and register is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16652A consists of D-type flip-flops and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers. The device can be used as two 8-bit transceivers or one 16-bit transceiver.

Complementary output-enable (OEAB and $\overline{\text{OEBA}}$) inputs control the transceiver functions. Select-control (SAB and SBA) inputs select whether real-time or stored data is transferred. A low input level selects real-time data, and a high input level selects stored data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74LVCH16652A.

description (continued)

Data on the A or B bus, or both, can be stored in the internal D flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs regardless of the levels on the select-control or output-enable inputs. When SAB and SBA are in the real-time transfer mode, it is also possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{\text{OEBA}}$. In this configuration, each output reinforces its input. When all other data sources to the two sets of bus lines are at high impedance, each set of bus lines remains at its last level configuration.

To ensure the high-impedance state during power up or power down, $\overline{\text{OEBA}}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

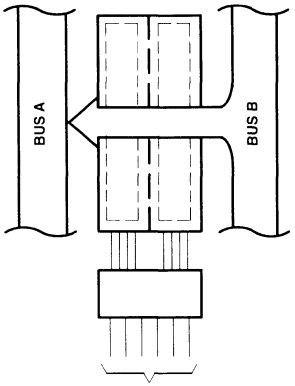
Active bus-hold circuitry holds unused or floating data inputs at a valid logic level.

The SN74LVCH16652A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

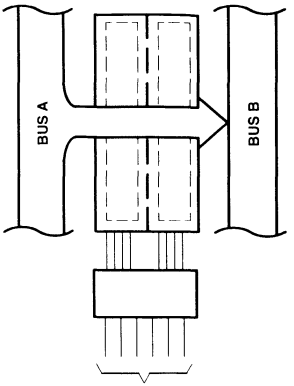
INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

† The data-output functions may be enabled or disabled by a variety of level combinations at OEAB or $\overline{\text{OEBA}}$. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.
‡ Select control = L; clocks can occur simultaneously.
Select control = H; clocks must be staggered to load both registers.



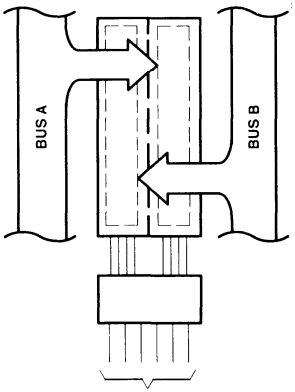
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



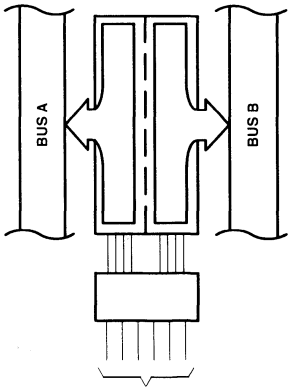
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B

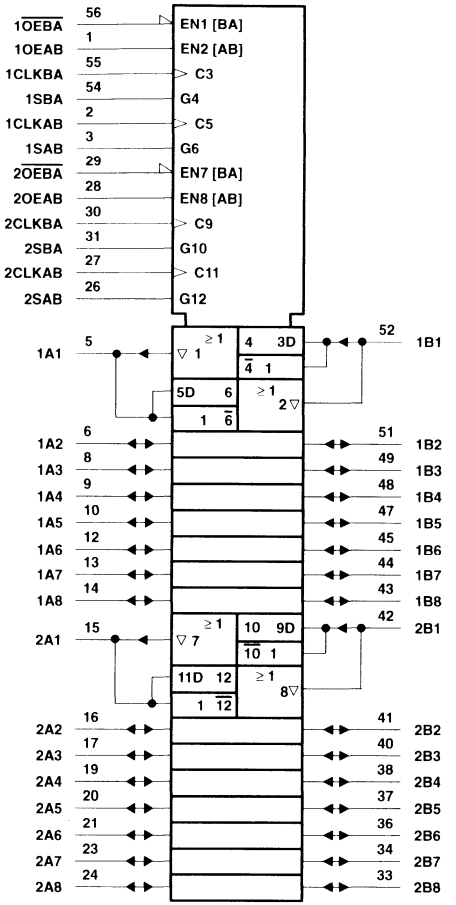


OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	L	H or L	H or L	H	H

TRANSFER STORED DATA
TO A AND/OR B

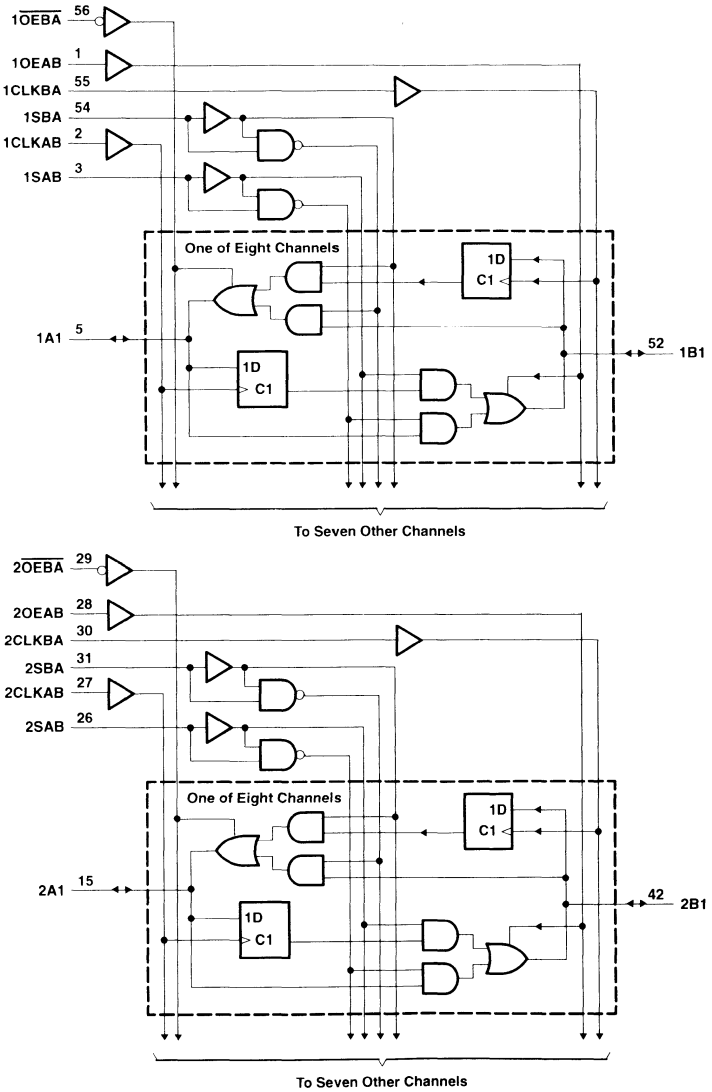
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package ..... 81°C/W
DL package ..... 74°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	V_I = 0 to 5.5 V		3.6 V			±5	µA
$I_{I(hold)}$	A or B ports	V_I = 0.8 V		3 V	75			µA
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}§		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
		3.6 V ≤ V_I ≤ 5.5 V¶					20	
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.
¶ This applies in the disabled state only.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			150		150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high or low	3		3.4		ns
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑	Data high or low	0.2		0		ns

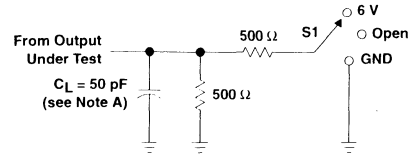
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			150		150		MHz
t_{pd}	A or B	B or A	1.4	6.3		6.4	ns
	CLKAB or CLKBA	A or B	2.4	6.4		7.3	
	SAB or SBA	B or A	1.9	7.4		8.8	
t_{en}	$\overline{OE}$ or OE	A or B	1.6	6.3		6.6	ns
t_{dis}	$\overline{OE}$ or OE	A or B	1.2	6.2		6.6	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

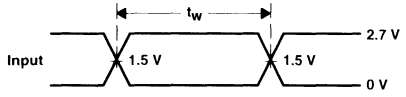
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0,	f = 10 MHz	55	pF
		Outputs disabled			12	

PARAMETER MEASUREMENT INFORMATION

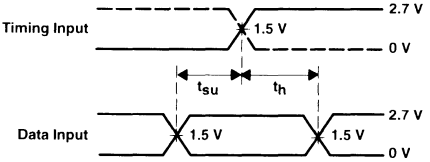


LOAD CIRCUIT

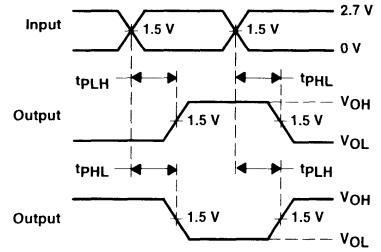
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



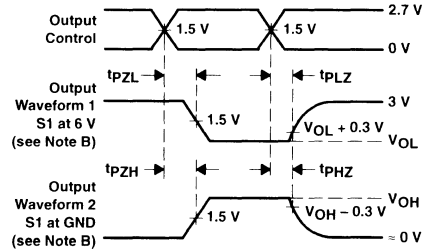
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



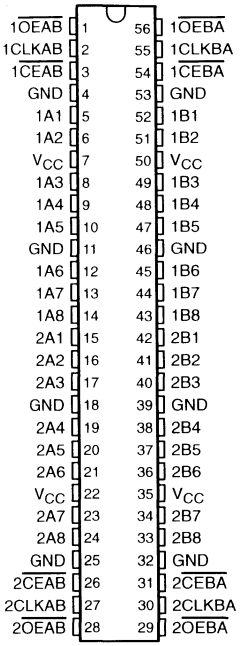
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR < 10 MHz, Z_O = 50 Ω, t_r < 2.5 ns, t_f < 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit registered transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16952A contains two sets of D-type flip-flops for temporary storage of data flowing in either direction. It can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input, provided that the clock-enable ($\overline{CEAB}$ or $\overline{CEBA}$) input is low. Taking the output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) input low accesses the data on either port.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

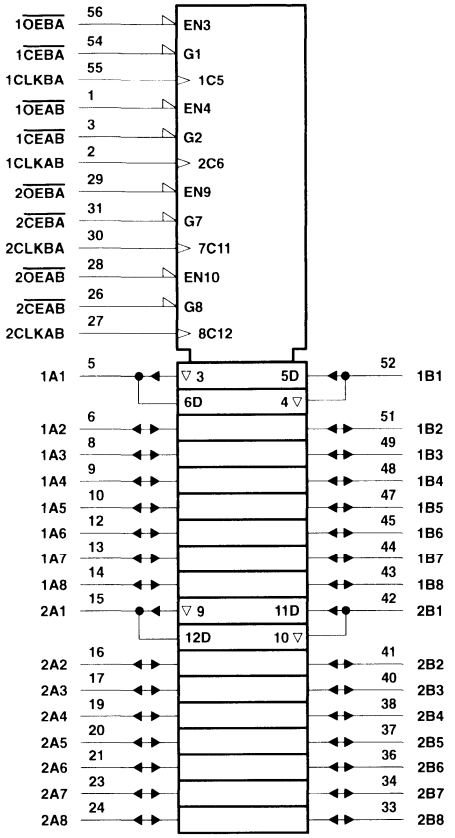
The SN74LVCH16952A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CEAB}$	CLKAB	$\overline{OEAB}$	A	B
H	X	L	X	B_0‡
X	L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

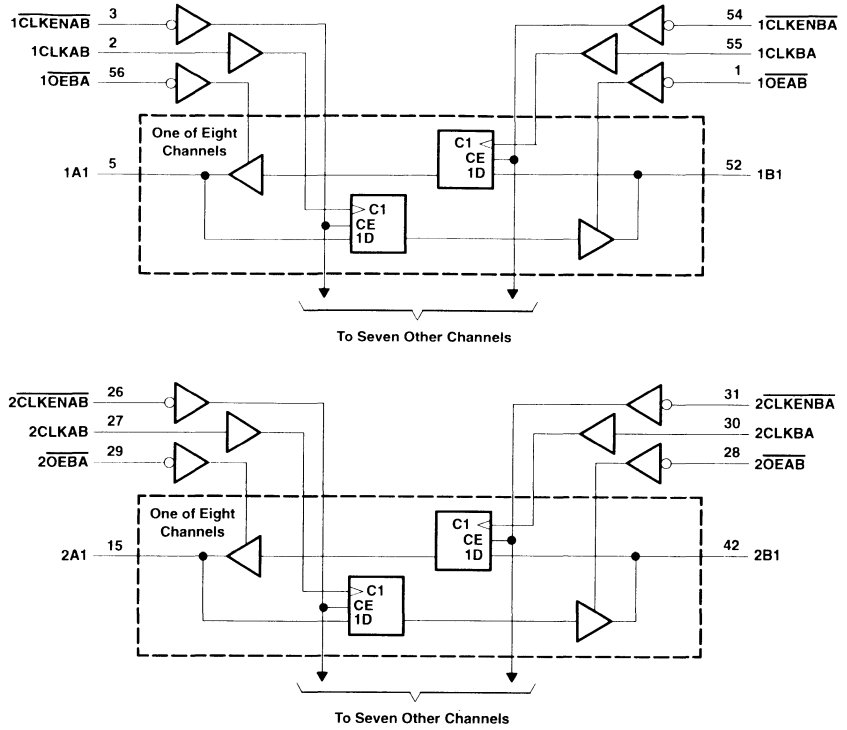
† A-to-B data flow is shown; B-to-A data flow is similar, but uses $\overline{CEBA}$, CLKBA, and $\overline{OEBA}$.
‡ Level of B before the indicated steady-state input conditions were established

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) (see Note 2) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		2.7 V to 3.6 V			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	V_I = 0 to 5.5 V		3.6 V			±5	µA
$I_{I(hold)}$	A or B ports	V_I = 0.8 V		3 V	75			µA
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}§		V_O = 0 to 5.5 V		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			20	µA
		3.6 V ≤ V_I ≤ 5.5 V¶					20	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		3 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current, but not $I_{I(hold)}$.
¶ This applies in the disabled state only.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		ns
t_{su}	Setup time	Data before CLK↑	2.8		3.4		ns
		$\overline{CE}$ before CLK↑	1.4		1.8		
t_h	Hold time	Data after CLK↑	0.5		0.5		ns
		$\overline{CE}$ after CLK↑	1.9		1.1		

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

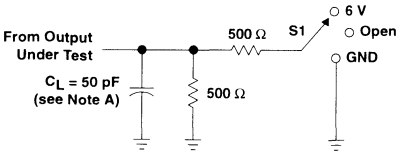
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			150		150		MHz
t_{pd}	CLKAB or CLKBA	B or A	1.6	6.6		7.6	ns
t_{en}	$\overline{OE}$	A or B	1.1	6.6		8	ns
t_{dis}	$\overline{OE}$	A or B	1.9	6.7		7.1	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

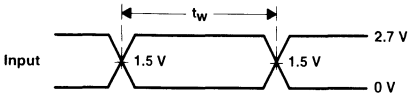
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0,	f = 10 MHz	87	pF
		Outputs disabled			43	

PARAMETER MEASUREMENT INFORMATION

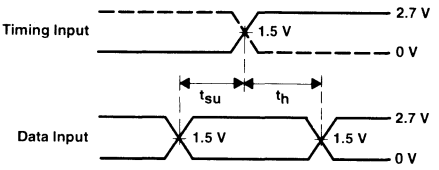


LOAD CIRCUIT

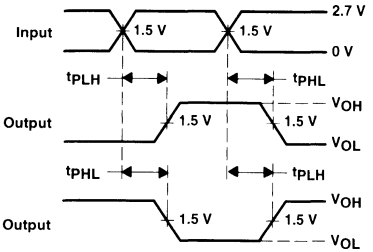
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



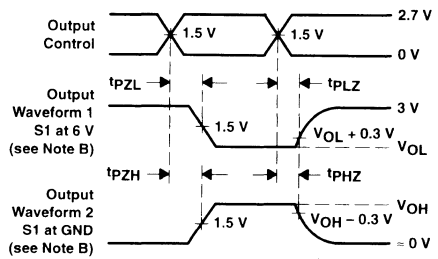
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

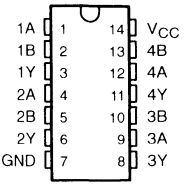
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

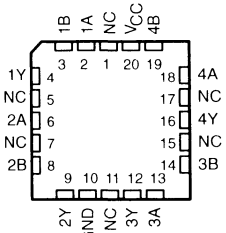
Contents

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (D, NS), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs

SN54LV00A . . . J OR W PACKAGE
SN74LV00A . . . D, DB, DGV, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV00A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These quadruple 2-input positive-NAND gates are designed for 2-V to 5.5-V V_{CC} operation.

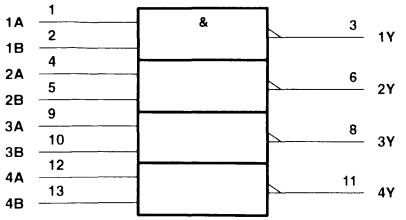
The 'LV00A perform the Boolean function $Y = \overline{A \bullet B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

The SN54LV00A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV00A is characterized for operation from –40°C to 85°C.

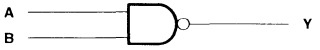
FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

logic symbol†



logic diagram, each gate (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, DGV, J, NS, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) ..... ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
DGV package ..... 182°C/W
NS package ..... 127°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV00A		SN74LV00A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 3 V to 3.6 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 4.5 V to 5.5 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 3 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 2.7 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–6		–6	
		V_{CC} = 4.5 V to 5.5 V		–12		–12	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		6		6	
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V	0	200	0	200	ns/V
		V_{CC} = 3 V to 3.6 V	0	100	0	100	
		V_{CC} = 4.5 V to 5.5 V	0	20	0	20	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV00A			SN74LV00A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –50 μA	2 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
	I_{OH} = –2 mA	2.3 V	2			2			
	I_{OH} = –6 mA	3 V	2.48			2.48			
	I_{OH} = –12 mA	4.5 V	3.8			3.8			
V_{OL}	I_{OL} = 50 μA	2 V to 5.5 V			0.1			0.1	V
	I_{OL} = 2 mA	2.3 V			0.4			0.4	
	I_{OL} = 6 mA	3 V			0.44			0.44	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	5.5 V			±1			±1	μA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	5.5 V			20			20	μA
I_{off}	V_O = 5.5 V	0 V			5			5	μA
C_i	V_I = V_{CC} or GND	3.3 V		3.4			3.4		pF
		5 V		3.4			3.4		

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV00A		SN74LV00A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		7.1	12.9	1	16	1	15	ns
t_{pd}	A	Y	C_L = 50 pF		9.6	16.6	1	21	1	20	ns

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV00A		SN74LV00A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		5	7.9	1	10.5	1	9.5	ns
t_{pd}	A	Y	C_L = 50 pF		6.9	11.4	1	14	1	13	ns

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV00A		SN74LV00A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		3.6	5.5	1	7.5	1	6.5	ns
t_{pd}	A	Y	C_L = 50 pF		4.9	7.5	1	9.5	1	8.5	ns

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

noise characteristics, V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C (see Note 5)

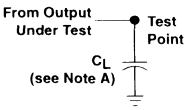
PARAMETER		SN74LV00A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.2	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–0.1	–0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		3.1		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 5: Characteristics are for surface-mount packages only.

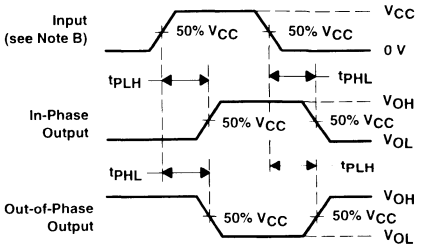
operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS		V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF,	f = 10 MHz	3.3 V	9.5	pF
				5 V	11	

PARAMETER MEASUREMENT INFORMATION



LOAD CIRCUIT



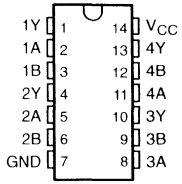
VOLTAGE WAVEFORMS
DELAY TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
C. The outputs are measured one at a time with one transition per measurement.
D. t_{PLH} and t_{PHL} are the same as t_{pd}.

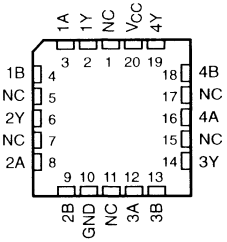
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC* ™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs

SN54LV02 . . . J OR W PACKAGE
SN74LV02 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LV02 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These quadruple 2-input positive-NOR gates are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LV02 perform Boolean function $Y = \overline{A + B}$ or $Y = \overline{A} \bullet \overline{B}$ in positive logic.

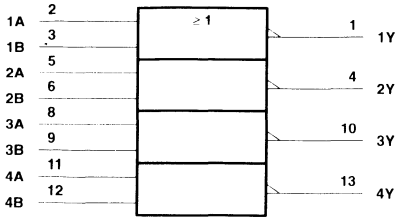
The SN74LV02 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LV02 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV02 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

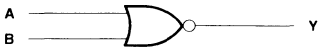
INPUTS		OUTPUT
A	B	Y
H	X	L
X	H	L
L	L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, PW, and W packages.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV02		SN74LV02		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		–6		–6	mA
		V_{CC} = 4.5 V to 5.5 V		–12		–12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		6		6	mA
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LV02			SN74LV02			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC} – 0.2			V_{CC} – 0.2			V
	I_{OH} = –6 mA	3 V	2.4			2.4			
	I_{OH} = –12 mA	4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2			0.2	V
	I_{OL} = 6 mA	3 V			0.4			0.4	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±1			±1	µA
		5.5 V			±1			±1	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	µA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		2.5			2.5		pF
		5 V		2.5			2.5		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV02								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		5	10		8	13		16	ns

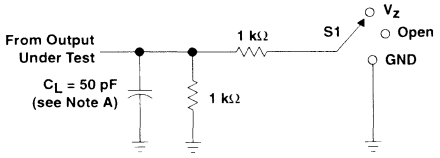
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV02								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		5	10		8	13		16	ns

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	3.3 V	16	pF
			5 V	20	

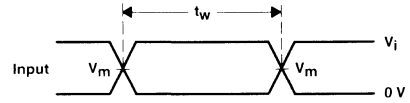
PARAMETER MEASUREMENT INFORMATION



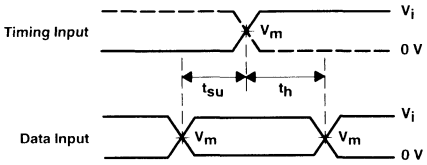
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_z
t_{PHZ}/t_{PZH}	GND

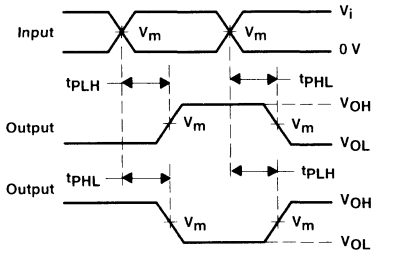
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



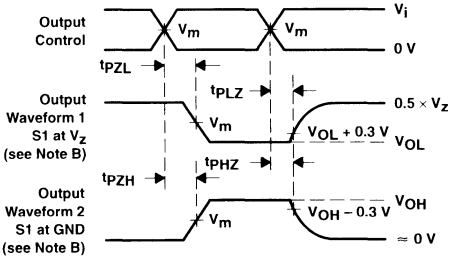
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



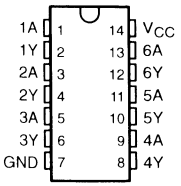
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

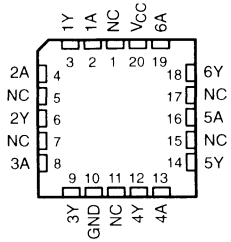
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (D, NS), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs**

SN54LV04A . . . J OR W PACKAGE
SN74LV04A . . . D, DB, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV04A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These hex inverters are designed for 2-V to 5.5-V V_{CC} operation.

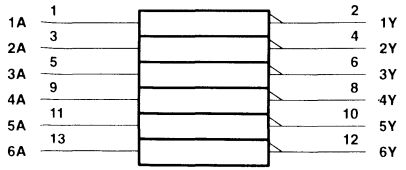
The 'LV04A contain six independent inverters. These devices perform the Boolean function $Y = \overline{A}$.

The SN54LV04A is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74LV04A is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each inverter)

INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, J, NS, PW, and W packages.

logic diagram, each inverter (positive logic)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
NS package ..... 127°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV04A		SN74LV04A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 3 V to 3.6 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 4.5 V to 5.5 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 3 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 2.7 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–6		–6	
		V_{CC} = 4.5 V to 5.5 V		–12		–12	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		6		6	
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V	0	200	0	200	ns/V
		V_{CC} = 3 V to 3.6 V	0	100	0	100	
		V_{CC} = 4.5 V to 5.5 V	0	20	0	20	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV04A			SN74LV04A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –50 μA	2 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
	I_{OH} = –2 mA	2.3 V	2			2			
	I_{OH} = –6 mA	3 V	2.48			2.48			
	I_{OH} = –12 mA	4.5 V	3.8			3.8			
V_{OL}	I_{OL} = 50 μA	2 V to 5.5 V			0.1			0.1	V
	I_{OL} = 2 mA	2.3 V			0.4			0.4	
	I_{OL} = 6 mA	3 V			0.44			0.44	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	$V_I = V_{CC}$ or GND	5.5 V			±1			±1	μA
I_{CC}	$V_I = V_{CC}$ or GND, I_O = 0	5.5 V			20			20	μA
I_{off}	V_O = 5.5 V	0 V			5			5	μA
C_i	$V_I = V_{CC}$ or GND	3.3 V		2.3			2.3		pF
		5 V		2.3			2.3		

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV04A		SN74LV04A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		7.1	11.7			1	14	ns
t_{pd}	A	Y	C_L = 50 pF		10	15.5			1	18	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV04A		SN74LV04A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		5.1	7.1	1	8.5	1	8.5	ns
t_{pd}	A	Y	C_L = 50 pF		7.3	10.6	1	12	1	12	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV04A		SN74LV04A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		3.6	5.5	1	6.5	1	6.5	ns
t_{pd}	A	Y	C_L = 50 pF		5.1	7.5	1	8.5	1	8.5	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

noise characteristics, C_L = 50 pF, T_A = 25°C (see Note 6)

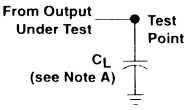
PARAMETER		SN74LV04A V_{CC} = 3.3 V			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.26	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–.01	–0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		3.1		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 5: Characteristics are for surface-mount packages only. These parameters are warranted but not production tested.

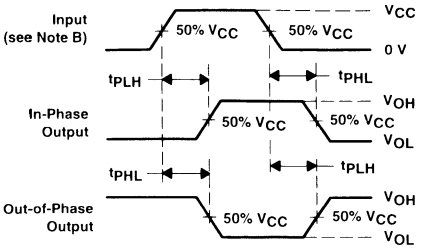
operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	9.6	pF
			5 V	11.4	

PARAMETER MEASUREMENT INFORMATION



LOAD CIRCUIT



VOLTAGE WAVEFORMS
DELAY TIMES

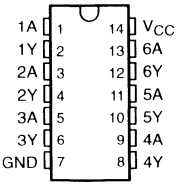
NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
C. The outputs are measured one at a time with one transition per measurement.
D. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

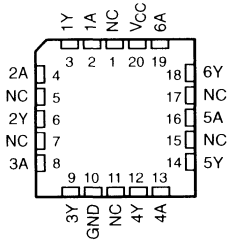
SCLS185B – FEBRUARY 1993 – REVISED APRIL 1996

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs

SN54LVU04 . . . J OR W PACKAGE
SN74LVU04 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVU04 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These hex inverters are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LVU04 contain six independent inverters with unbuffered outputs. These devices perform the Boolean function $Y = \overline{A}$.

The SN74LVU04 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVU04 is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74LVU04 is characterized for operation from −40°C to 85°C.

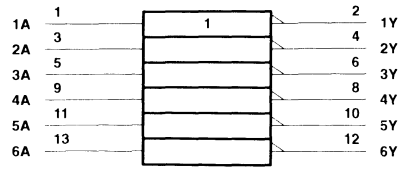
FUNCTION TABLE
(each inverter)

INPUT A	OUTPUT Y
H	L
L	H

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

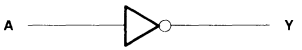
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, J, PW and W packages.

logic diagram, each inverter (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) ..... ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LVU04		SN74LVU04		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2.4		2.4		V
		V_{CC} = 4.5 V to 5.5 V	3.55		3.55		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.5		0.5	V
		V_{CC} = 4.5 V to 5.5 V		0.8		0.8	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		−6		−6	mA
		V_{CC} = 4.5 V to 5.5 V		−12		−12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		6		6	mA
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	SN54LVU04			SN74LVU04			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	$V_I = V_{IL}$,	$I_{OH} = -100\ \mu A$	MIN to MAX	$V_{CC}-0.5$			$V_{CC}-0.5$			V
	V_I = GND,	$I_{OH} = -6$ mA	3 V	2.4			2.4			
	V_I = GND,	$I_{OH} = -12$ mA	4.5 V	3.6			3.6			
V_{OL}	$V_I = V_{IH}$,	$I_{OL} = 100\ \mu A$	MIN to MAX			0.5			0.5	V
	$V_I = V_{CC}$,	$I_{OL} = 6$ mA	3 V			0.4			0.4	
	$V_I = V_{CC}$,	$I_{OL} = 12$ mA	4.5 V			0.55			0.55	
I_I	$V_I = V_{CC}$ or GND		3.6 V			±1			±1	µA
			5.5 V			±1			±1	
I_{CC}	$V_I = V_{CC}$ or GND,	$I_O = 0$	3.6 V			20			20	µA
			5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		3 V to 3.6 V			500			500	µA
C_i	$V_I = V_{CC}$ or GND		3.3 V		7			7		pF
			5 V		7.5			7.5		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVU04								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		5	10		8	13		13	ns

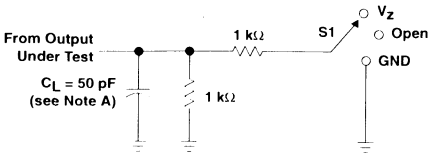
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LVU04								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		5	10		8	13		13	ns

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF, f = 10 MHz	3.3 V	7	pF
			5 V	12	

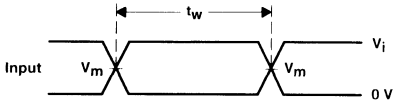
PARAMETER MEASUREMENT INFORMATION



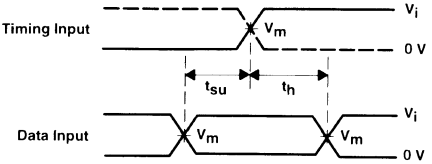
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_Z
t_{PHZ}/t_{PZH}	GND

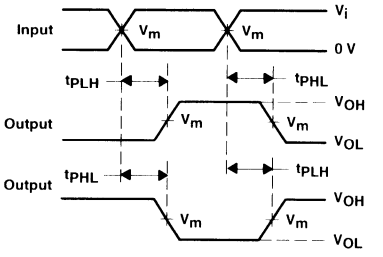
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



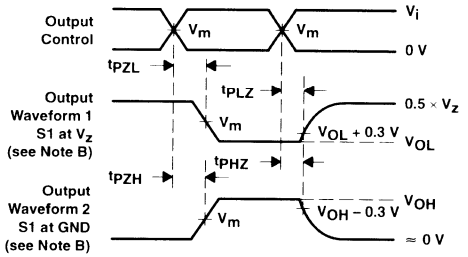
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



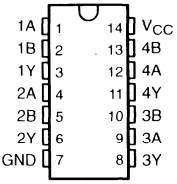
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

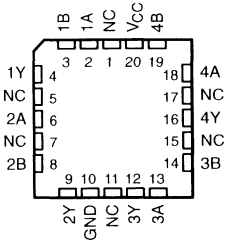
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (D, NS), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs

SN54LV08A . . . J OR W PACKAGE
SN74LV08A . . . D, DB, DGV, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV08A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These quadruple 2-input positive-AND gates are designed for 2-V to 5.5-V V_{CC} operation.

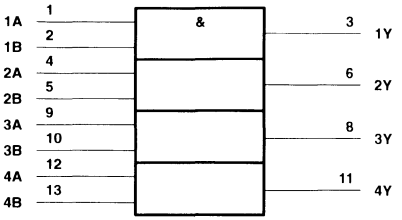
The 'LV08A perform Boolean function $Y = A \cdot B$ or $Y = \overline{\overline{A} + \overline{B}}$ in positive logic.

The SN54LV08A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV08A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	H	H
L	X	L
X	L	L

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, DGV, J, NS, PW, and W packages.

logic diagram, each gate (positive logic)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC}		−0.5 V to 7 V
Input voltage range, V_I (see Note 1)		−0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2)		−0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$)		±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)		±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})		±25 mA
Continuous current through V_{CC} or GND		±50 mA
Package thermal impedance, θ_{JA} (see Note 3):	D package	127°C/W
	DB package	158°C/W
	DGV package	182°C/W
	NS package	127°C/W
	PW package	170°C/W
Storage temperature range, T_{stg}		−65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV08A		SN74LV08A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 3 V to 3.6 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 4.5 V to 5.5 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 3 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 2.7 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–6		–6	
		V_{CC} = 4.5 V to 5.5 V		–12		–12	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		6		6	
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V	0	200	0	200	ns/V
		V_{CC} = 3 V to 3.6 V	0	100	0	100	
		V_{CC} = 4.5 V to 5.5 V	0	20	0	20	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV08A			SN74LV08A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –50 μA	2 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
	I_{OH} = –2 mA	2.3 V	2			2			
	I_{OH} = –6 mA	3 V	2.48			2.48			
	I_{OH} = –12 mA	4.5 V	3.8			3.8			
V_{OL}	I_{OL} = 50 μA	2 V to 5.5 V			0.1			0.1	V
	I_{OL} = 2 mA	2.3 V			0.4			0.4	
	I_{OL} = 6 mA	3 V			0.44			0.44	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	$V_I = V_{CC}$ or GND	5.5 V			±1			±1	μA
I_{CC}	$V_I = V_{CC}$ or GND, I_O = 0	5.5 V			20			20	μA
I_{off}	V_O = 5.5 V	0 V			5			5	μA
C_i	$V_I = V_{CC}$ or GND	3.3 V		3.4			3.4		pF
		5 V		3.4			3.4		

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV08A		SN74LV08A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		7.9	13.8	1	17	1	16	ns
t_{pd}	A	Y	C_L = 50 pF		10.5	17.3	1	21	1	20	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV08A		SN74LV08A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		5.6	8.8	1	11.5	1	10.5	ns
t_{pd}	A	Y	C_L = 50 pF		7.5	12.3	1	15	1	14	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV08A		SN74LV08A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		4.1	5.9	1	8	1	7	ns
t_{pd}	A	Y	C_L = 50 pF		5.5	7.9	1	10	1	9	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

noise characteristics, V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C (see Note 5)

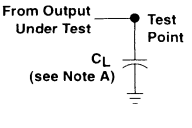
PARAMETER		SN74LV08A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.2	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–0.1	–0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		3.1		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 5: Characteristics are for surface-mount packages only. These parameters are warranted but not production tested.

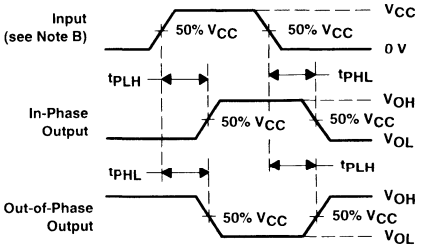
operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	9.5	pF
			5 V	11	

PARAMETER MEASUREMENT INFORMATION



LOAD CIRCUIT



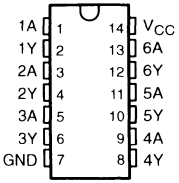
VOLTAGE WAVEFORMS
DELAY TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
C. The outputs are measured one at a time with one transition per measurement.
D. t_{PLH} and t_{PHL} are the same as t_{pd}.

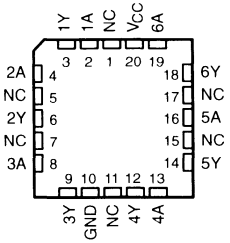
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (D, NS), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV14A . . . J OR W PACKAGE
SN74LV14A . . . D, DB, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV14A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These hex Schmitt-trigger inverters are designed for 2-V to 5.5-V V_{CC} operation.

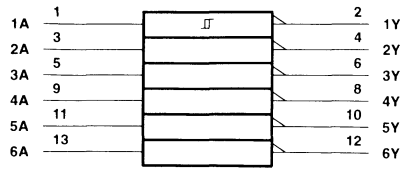
The 'LV14A contain six independent inverters. These devices perform the Boolean function $Y = \overline{A}$.

The SN54LV14A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV14A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

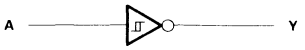
INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, J, NS, PW, and W packages.

logic diagram, each inverter (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
NS package ..... 127°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stressratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV14A		SN74LV14A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 3 V to 3.6 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 4.5 V to 5.5 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 3 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 2.7 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–6		–6	
		V_{CC} = 4.5 V to 5.5 V		–12		–12	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		6		6	
		V_{CC} = 4.5 V to 5.5 V		12		12	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV14A			SN74LV14A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{T+} Positive-going threshold		2.5 V			1.75			1.75	V
		3.3 V			2.31			2.31	
		5 V			3.5			3.5	
V_{T-} Negative-going threshold		2.5 V	0.75			0.75			V
		3.3 V	0.99			0.99			
		5 V	1.5			1.5			
ΔV_T Hysteresis ($V_{T+} - V_{T-}$)		2.5 V	0.25		1	0.25		1	V
		3.3 V	0.33		1.32	0.33		1.32	
		5 V	0.5		2	0.5		2	
V_{OH}	$I_{OH} = -50\ \mu A$	2 V to 5.5 V	$V_{CC} - 0.1$			$V_{CC} - 0.1$			V
	$I_{OH} = -2$ mA	2.3 V	2			2			
	$I_{OH} = -6$ mA	3 V	2.48			2.48			
	$I_{OH} = -12$ mA	4.5 V	3.8			3.8			
V_{OL}	$I_{OL} = 50\ \mu A$	2 V to 5.5 V			0.1			0.1	V
	$I_{OL} = 2$ mA	2.3 V			0.4			0.4	
	$I_{OL} = 6$ mA	3 V			0.44			0.44	
	$I_{OL} = 12$ mA	4.5 V			0.55			0.55	
I_I	$V_I = V_{CC}$ or GND	5.5 V			±1			±1	μA
I_{CC}	VI = VCC or GND, $I_O = 0$	5.5 V			20			20	μA
I_{off}	$V_O = 5.5$ V	0 V			5			5	μA
C_i	$V_I = V_{CC}$ or GND	3.3 V		2.3			2.3		pF
		5 V		2.3			2.3		

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV14A		SN74LV14A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		10.2	19.7	1	22	1	22	ns
t_{pd}	A	Y	C_L = 50 pF		13.3	24	1	27	1	27	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV14A		SN74LV14A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		7.3	12.8	1	15.9	1	15	ns
t_{pd}	A	Y	C_L = 50 pF		9.6	16.3	1	19.4	1	18.5	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV14A		SN74LV14A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		5.1	8.6	1	10	1	10	ns
t_{pd}	A	Y	C_L = 50 pF		6.7	10.6	1	12	1	12	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

noise characteristics, C_L = 50 pF, T_A = 25°C (see Note 6)

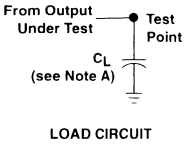
PARAMETER		SN74LV14A V_{CC} = 3.3 V			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.22	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–0.1	–0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		3.1		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 5: Characteristics are for surface-mount packages only. These parameters are warranted but not production tested.

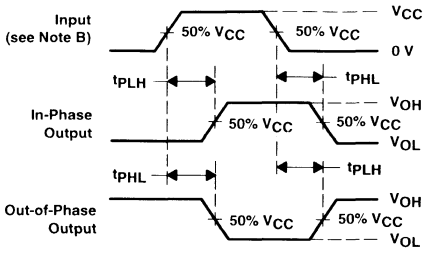
operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	8.8	pF
			5 V	9.6	

PARAMETER MEASUREMENT INFORMATION



LOAD CIRCUIT



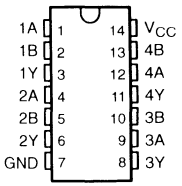
VOLTAGE WAVEFORMS
DELAY TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
C. The outputs are measured one at a time with one transition per measurement.
D. t_{PLH} and t_{PHL} are the same as t_{pd}.

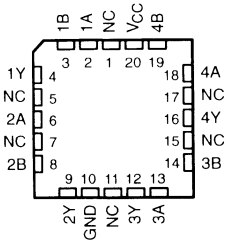
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (D, NS), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV32A . . . J OR W PACKAGE
SN74LV32A . . . D, DB, DGV, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV32A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These quadruple 2-input positive-OR gates are designed for 2-V to 5.5-V V_{CC} operation.

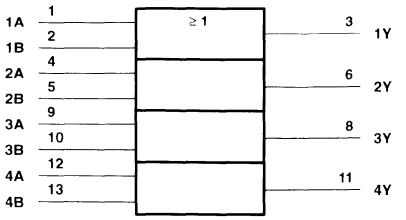
The 'LV32A perform the Boolean function $Y = A + B$ or $Y = \overline{\overline{A} \cdot \overline{B}}$ in positive logic.

The SN54LV32A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV32A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	X	H
X	H	H
L	L	L

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, DGV, J, NS, PW, and W packages.

logic diagram, each gate (positive logic)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) ..... ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
DGV package ..... 182°C/W
N package ..... 127°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV32A		SN74LV32A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 3 V to 3.6 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 4.5 V to 5.5 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 3 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 2.7 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–6		–6	
		V_{CC} = 4.5 V to 5.5 V		–12		–12	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		6		6	
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V	0	200	0	200	ns/V
		V_{CC} = 3 V to 3.6 V	0	100	0	100	
		V_{CC} = 4.5 V to 5.5 V	0	20	0	20	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV32A			SN74LV32A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –50 μA	2 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
	I_{OH} = –2 mA	2.3 V	2			2			
	I_{OH} = –6 mA	3 V	2.48			2.48			
	I_{OH} = –12 mA	4.5 V	3.8			3.8			
V_{OL}	I_{OL} = 50 μA	2 V to 5.5 V			0.1			0.1	V
	I_{OL} = 2 mA	2.3 V			0.4			0.4	
	I_{OL} = 6 mA	3 V			0.44			0.44	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	5.5 V			±1			±1	μA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	5.5 V			20			20	μA
I_{off}	V_O = 5.5 V	0 V			5			5	μA
C_i	V_I = V_{CC} or GND	3.3 V		3.4			3.4		pF
		5 V		3.4			3.4		

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV32A		SN74LV32A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		7.1	12.8	1	16	1	15	ns
t_{pd}	A	Y	C_L = 50 pF		9.6	16.2	1	20	1	19	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV32A		SN74LV32A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		5	7.9	1	9.5	1	9.5	ns
t_{pd}	A	Y	C_L = 50 pF		6.9	11.4	1	13	1	13	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV32A		SN74LV32A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		3.6	5.5	1	6.5	1	6.5	ns
t_{pd}	A	Y	C_L = 50 pF		4.9	7.5	1	8.5	1	8.5	ns

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

noise characteristics, V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C (see Note 5)

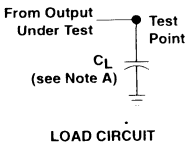
PARAMETER		SN74LV32A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.2	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–0.1	–0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		3.1		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 5: Characteristics are for surface-mount packages only. These parameters are warranted but not production tested.

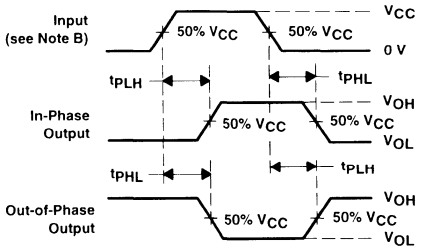
operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	9.5	pF
			5 V	11	

PARAMETER MEASUREMENT INFORMATION



LOAD CIRCUIT



VOLTAGE WAVEFORMS
DELAY TIMES

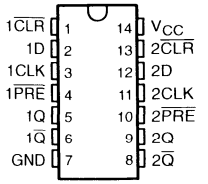
NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
C. The outputs are measured one at a time with one transition per measurement.
D. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

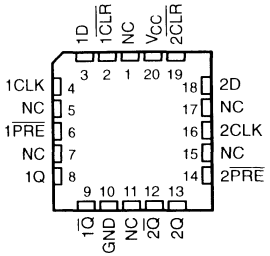
SCLS381A – AUGUST 1997 – REVISED OCTOBER 1997

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (D, NS), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Package, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV74A . . . J OR W PACKAGE
SN74LV74A . . . D, DB, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV74A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These dual positive-edge-triggered D-type flip-flops are designed for 2-V to 5.5-V V_{CC} operation.

A low level at the preset ($\overline{PRE}$) or clear ($\overline{CLR}$) inputs sets or resets the outputs, regardless of the levels of the other inputs. When $\overline{PRE}$ and $\overline{CLR}$ are inactive (high), data at the data (D) inputs meeting the setup-time requirements is transferred to the outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the D input can be changed without affecting the levels at the outputs.

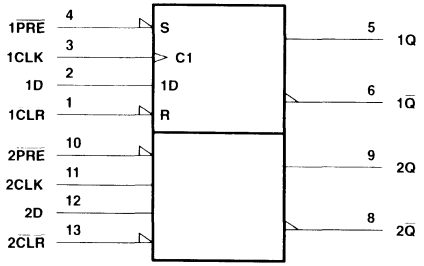
The SN54LV74A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV74A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUTS	
PRE	CLR	CLK	D	Q	$\overline{Q}$
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H†	H†
H	H	↑	H	H	L
H	H	↑	L	L	H
H	H	L	X	Q_0	$\overline{Q}_0$

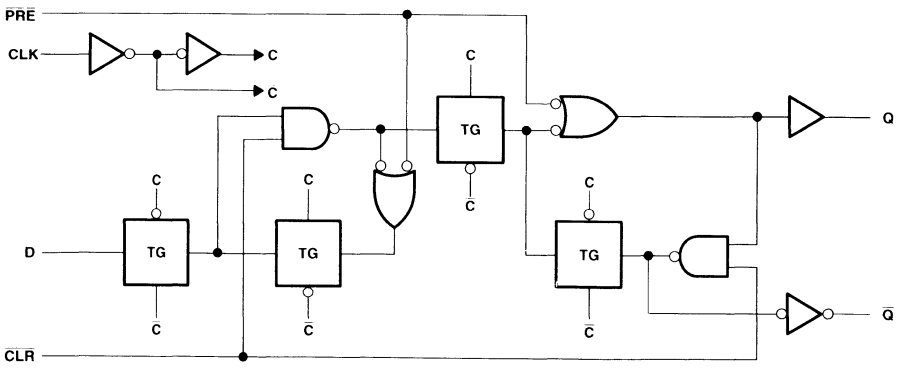
† This configuration is unstable; that is, it does not persist when $\overline{PRE}$ or $\overline{CLR}$ returns to its inactive (high) level.

logic symbol‡



‡ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, J, NS, PW, and W packages.

logic diagram, each flip-flop (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Package thermal impedance, θ_{JA} (see Note 3): D package ..... 127°C/W
DB package ..... 158°C/W
NS package ..... 127°C/W
PW package ..... 170°C/W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV74A		SN74LV74A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 3 V to 3.6 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 4.5 V to 5.5 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 3 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 4.5 V to 5.5 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–6		–6	
		V_{CC} = 4.5 V to 5.5 V		–12		–12	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		6		6	
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V	0	200	0	200	ns/V
		V_{CC} = 3 V to 3.6 V	0	100	0	100	
		V_{CC} = 4.5 V to 5.5 V	0	20	0	20	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV74A			SN74LV74A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –50 μA	2 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
	I_{OH} = –2 mA	2.3 V	2			2			
	I_{OH} = –6 mA	3 V	2.48			2.48			
	I_{OH} = –12 mA	4.5 V	3.8			3.8			
V_{OL}	I_{OL} = 50 μA	2 V to 5.5 V			0.1			0.1	V
	I_{OL} = 2 mA	2.3 V			0.4			0.4	
	I_{OL} = 6 mA	3 V			0.44			0.44	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	5.5 V			±1			±1	μA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	5.5 V			20			20	μA
I_{off}	V_O = 5.5 V	0 V			5			5	μA
C_i	V_I = V_{CC} or GND	3.3 V		2.1			2.1		pF
		5 V		2.1			2.1		

timing requirements over recommended operating free-air temperature, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER			T_A = 25°C	SN54LV74A	SN74LV74A	UNIT
			MIN MAX	MIN MAX	MIN MAX	
t_w	Pulse duration	$\overline{PRE}$ or $\overline{CLR}$ low	8	9	9	ns
		CLK	8	9	9	
t_{su}	Setup time before CLK↑	Data	8	9	9	ns
		$\overline{PRE}$ or $\overline{CLR}$ inactive	7	7	7	
t_h	Hold time, data after CLK↑		0.5	0.5	0.5	ns

timing requirements over recommended operating free-air temperature, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER			T_A = 25°C	SN54LV74A	SN74LV74A	UNIT
			MIN MAX	MIN MAX	MIN MAX	
t_w	Pulse duration	$\overline{PRE}$ or $\overline{CLR}$ low	6	7	7	ns
		CLK	6	7	7	
t_{su}	Setup time before CLK↑	Data	6	7	7	ns
		$\overline{PRE}$ or $\overline{CLR}$ inactive	5	5	5	
t_h	Hold time, data after CLK↑		0.5	0.5	0.5	ns

timing requirements over recommended operating free-air temperature, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER			T_A = 25°C		SN54LV74A		SN74LV74A		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration	$\overline{PRE}$ or $\overline{CLR}$ low	5		5		5		ns
		CLK	5		5		5		
t_{su}	Setup time before CLK↑	Data	5		5		5		ns
		$\overline{PRE}$ or $\overline{CLR}$ inactive	3		3		3		
t_h	Hold time, data after CLK↑		0.5		0.5		0.5		ns

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV74A		SN74LV74A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f_{max}			C_L = 15 pF*	50	100		40		40		MHz
			C_L = 50 pF	30	70		25		25		
t_{pd}*	$\overline{PRE}$ or $\overline{CLR}$	Q or Q	C_L = 15 pF		9.8	14.8	1	17	1	17	ns
	CLK				11.1	16.4	1	19	1	19	
t_{pd}	$\overline{PRE}$ or $\overline{CLR}$	Q or Q	C_L = 50 pF		13	17.4	1	20	1	20	ns
	CLK				14.2	20	1	23	1	23	

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV74A		SN74LV74A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f_{max}			C_L = 15 pF*	80	140		70		70		MHz
			C_L = 50 pF	50	90		45		45		
t_{pd}*	$\overline{PRE}$ or $\overline{CLR}$	Q or Q	C_L = 15 pF		6.9	12.3	1	14.5	1	14.5	ns
	CLK				7.9	11.9	1	14	1	14	
t_{pd}	$\overline{PRE}$ or $\overline{CLR}$	Q or Q	C_L = 50 pF		9.2	15.8	1	18	1	18	ns
	CLK				10.2	15.4	1	17.5	1	17.5	

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV74A		SN74LV74A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f_{max}			C_L = 15 pF*	130	180		110		110		MHz
			C_L = 50 pF	90	140		75		75		
t_{pd}*	$\overline{PRE}$ or $\overline{CLR}$	Q or Q	C_L = 15 pF		5	7.7	1	9	1	9	ns
	CLK				5.6	7.3	1	8.5	1	8.5	
t_{pd}	$\overline{PRE}$ or $\overline{CLR}$	Q or Q	C_L = 50 pF		6.6	9.7	1	11	1	11	ns
	CLK				7.2	9.3	1	10.5	1	10.5	

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

noise characteristics, V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C (see Note 5)

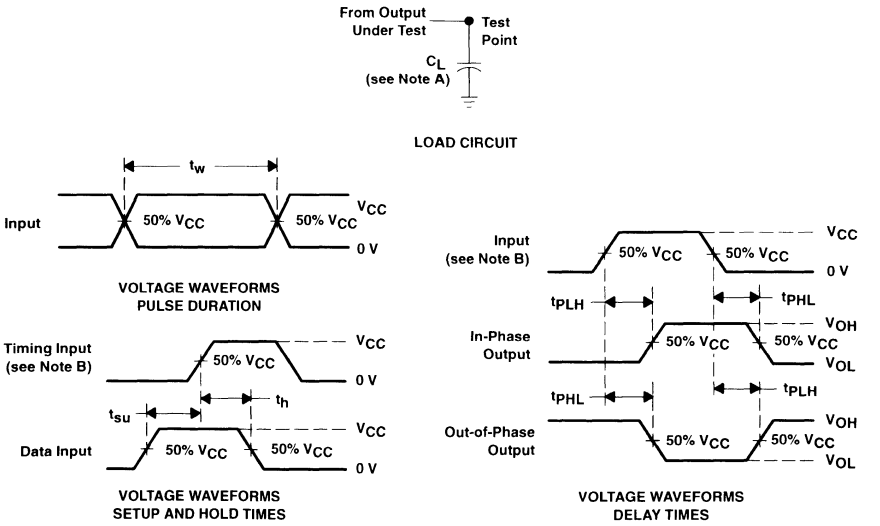
PARAMETER		SN74LV74A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.1	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–0.04	–0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		3.2		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 5: Characteristics are for surface-mount packages only.

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	21	pF
			5 V	23	

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 3 ns, t_f ≤ 3 ns.
C. The outputs are measured one at a time with one transition per measurement.
D. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- ESD Protection Exceeds 2000 V per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs

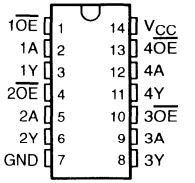
description

These quadruple bus buffer gates are designed for 2.7-V to 5.5-V V_{CC} operation.

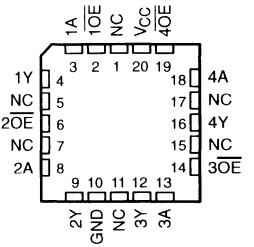
The 'LV125 feature independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable ($\overline{OE}$) input is high.

The SN54LV125 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV125 is characterized for operation from –40°C to 85°C.

SN54LV125 . . . J OR W PACKAGE
SN74LV125 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LV125 . . . FK PACKAGE
(TOP VIEW)

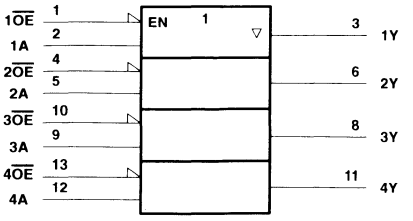


NC – No internal connection

FUNCTION TABLE
(each buffer)

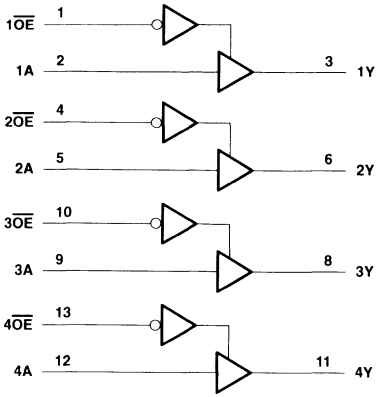
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, J, PW, and W packages.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Operating free-air temperature range, T_A ..... −40°C to 85°C
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV125		SN74LV125		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		−8		−8	mA
		V_{CC} = 4.5 V to 5.5 V		−16		−16	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		8		8	mA
		V_{CC} = 4.5 V to 5.5 V		16		16	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LV125			SN74LV125			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{OH}	I_{OH} = −100 µA	MIN to MAX‡	V_{CC}−0.2			V_{CC}−0.2			V
	I_{OH} = −8 mA	3 V	2.4			2.4			
	I_{OH} = −16 mA	4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 µA	MIN to MAX‡			0.2			0.2	V
	I_{OL} = 8 mA	3 V			0.4			0.4	
	I_{OL} = 16mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±1			±1	µA
		5.5 V			±1			±1	
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±5			±5	µA
		5.5 V			±5			±5	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	µA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		3.5			3.5		pF
		5 V		3.5			3.5		
C_o	V_O = V_{CC} or GND	3.3 V		8			8		pF
		5 V		8			8		

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV125								UNIT
			V_{CC} = 5.5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP†	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{pd}	A	Y		7	18		9	19		23	ns
t_{en}	$\overline{OE}$	Y		5	19		7	25		31	ns
t_{dis}	$\overline{OE}$	Y		7	17		9	23		28	ns

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

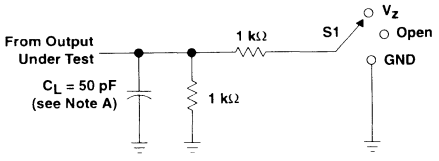
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV125								UNIT
			V_{CC} = 5.5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP†	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{pd}	A	Y		7	18		9	19		23	ns
t_{en}	$\overline{OE}$	Y		5	19		7	25		31	ns
t_{dis}	$\overline{OE}$	Y		7	17		9	23		28	ns

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	3.3 V	45	pF
		Outputs disabled			5	
		Outputs enabled		5 V	48	pF
		Outputs disabled			5	

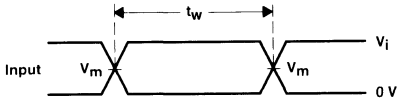
PARAMETER MEASUREMENT INFORMATION



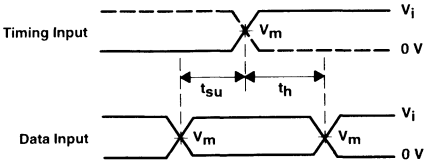
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_Z
t_{PHZ}/t_{PZH}	GND

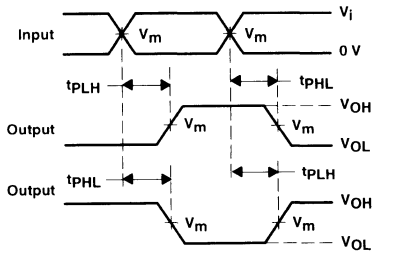
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



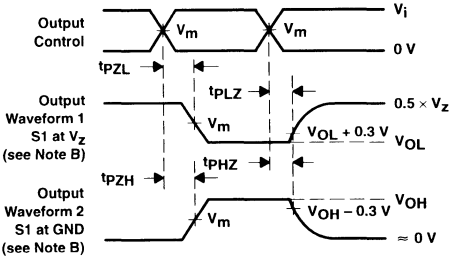
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

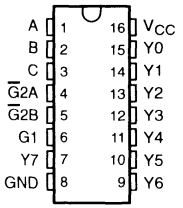
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

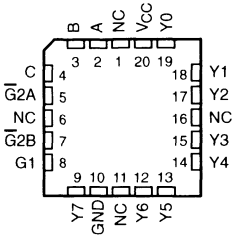
SCLS190D – FEBRUARY 1993 – REVISED JULY 1996

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV138 . . . J OR W PACKAGE
SN74LV138 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LV138 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These 3-line to 8-line decoders/demultiplexers are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LV138 are designed for high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, this decoder can be used to minimize the effects of system decoding. When employed with high-speed utilizing a fast enable circuit, the delay times of this decoder and the enable time of the memory are usually less than the typical access time of the memory. This means that the effective system delay introduced by the decoder is negligible.

The conditions at the binary-select inputs and the three enable inputs select one of eight output lines. Two active-low and one active-high enable inputs reduce the need for external gates or inverters when expanding. A 24-line decoder can be implemented without external inverters and a 32-line decoder requires only one inverter. An enable input can be used as a data input for demultiplexing applications.

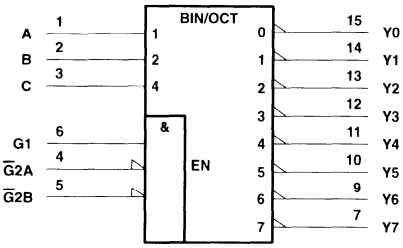
The SN74LV138 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

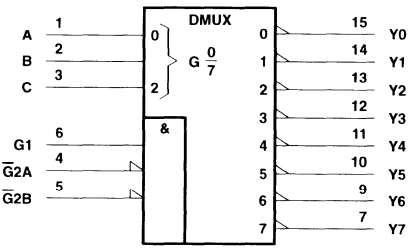
The SN54LV138 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV138 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

ENABLE INPUTS			SELECT INPUTS			OUTPUTS							
G1	$\overline{G2A}$	$\overline{G2B}$	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	H	X	X	X	X	H	H	H	H	H	H	H	H
X	X	H	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	H	L	H	H	H	H
H	L	L	H	L	L	H	H	H	H	L	H	H	H
H	L	L	H	L	H	H	H	H	H	H	L	H	H
H	L	L	H	H	L	H	H	H	H	H	H	L	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

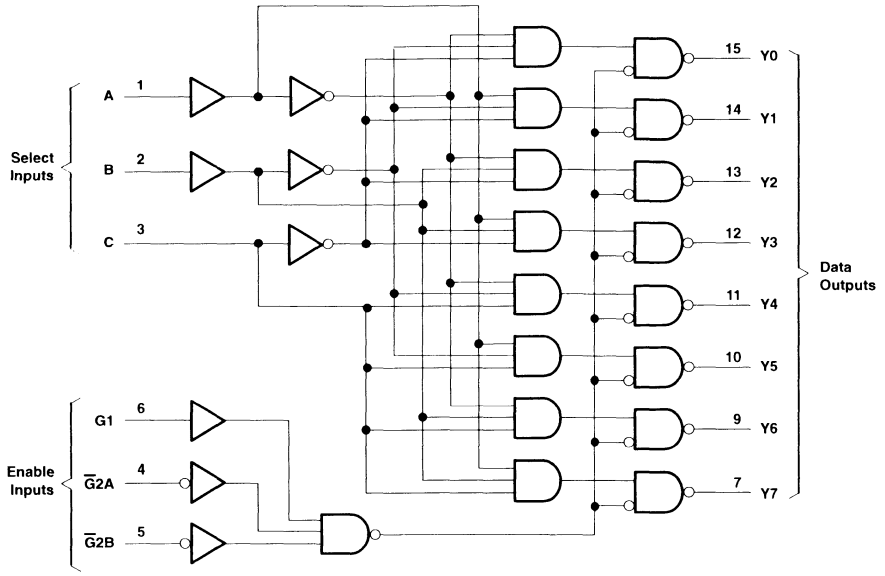
logic symbols (alternatives)†





† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, J, PW, and W packages.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) ..... ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV138		SN74LV138		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		−6		−6	mA
		V_{CC} = 4.5 V to 5.5 V		−12		−12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		6		6	mA
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	SN54LV138			SN74LV138			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –6 mA		3 V	2.4			2.4			
	I_{OH} = –12 mA		4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2			0.2	V
	I_{OL} = 6 mA		3 V			0.4			0.4	
	I_{OL} = 12 mA		4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND		3.6 V			±1			±1	µA
			5.5 V			±1			±1	
I_{CC}	V_I = V_{CC} or GND	I_O = 0	3.6 V			20			20	µA
			5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V	Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		2.5			2.5		pF
			5 V		2.1			2.1		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV138								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y		8	16		10	21		26	ns
	Enable			8	19		10	23		29	

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

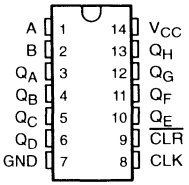
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV138								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y		8	16		10	21		26	ns
	Enable			8	19		10	23		29	

operating characteristics, T_A = 25°C

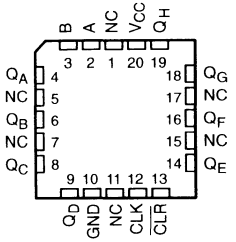
PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per channel	C_L = 50 pF, f = 10 MHz	3.3 V	47	pF
			5 V	49	

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs

SN54LV164 . . . J OR W PACKAGE
SN74LV164 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LV164 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These 8-bit parallel-out serial shift registers are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LV164 feature AND-gated serial (A and B) inputs and an asynchronous clear ($\overline{CLR}$) input. The gated serial inputs permit complete control over incoming data as a low at either input inhibits entry of the new data and resets the first flip-flop to the low level at the next clock pulse. A high-level input enables the other input, which then determines the state of the first flip-flop. Data at the serial inputs can be changed while the clock is high or low, provided the minimum setup time requirements are met. Clocking occurs on the low-to-high-level transition of the clock (CLK) input.

The SN74LV164 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LV164 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV164 is characterized for operation from –40°C to 85°C.

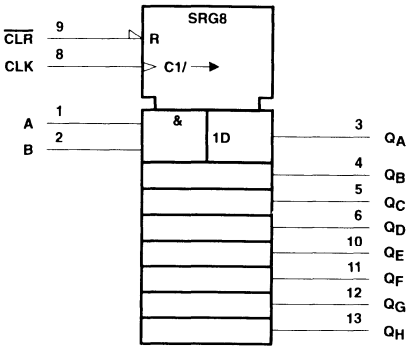
FUNCTION TABLE

INPUTS				OUTPUTS		
$\overline{CLR}$	CLK	A	B	Q_A	$Q_B \ldots Q_H$	
L	X	X	X	L	L	L
H	L	X	X	Q_{A0}	Q_{B0}	Q_{H0}
H	↑	H	H	H	Q_{An}	Q_{Gn}
H	↑	L	X	L	Q_{An}	Q_{Gn}
H	↑	X	L	L	Q_{An}	Q_{Gn}

Q_{A0}, Q_{B0}, Q_{H0} = the level of Q_A, Q_B, or Q_H, respectively, before the indicated steady-state inputs conditions were established

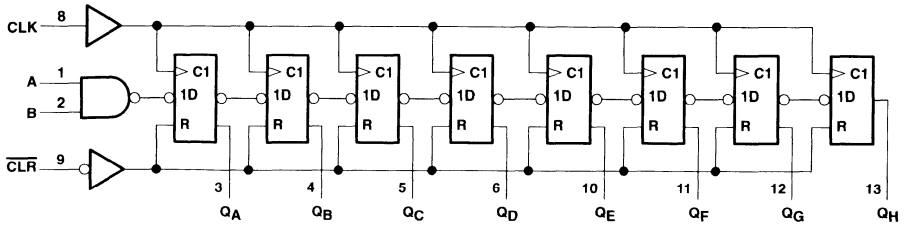
Q_{An}, Q_{Gn} = the level of Q_A or Q_G before the most recent ↑ transition of the clock: indicates a 1-bit shift

logic symbol†

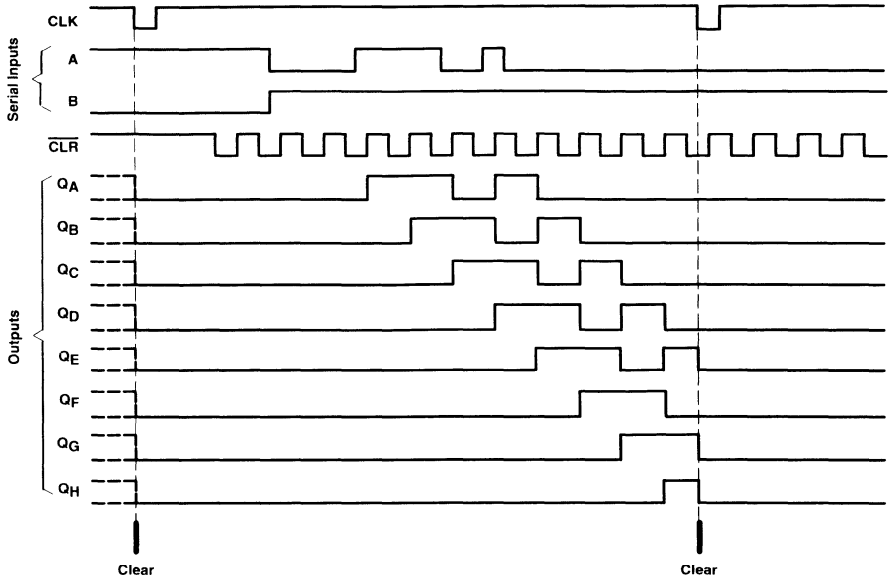


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, J, PW, and W packages.

logic diagram (positive logic)



typical clear, shift, and clear sequences



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV164		SN74LV164		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		–6		–6	mA
		V_{CC} = 4.5 V to 5.5 V		–12		–12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		6		6	mA
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LV164			SN74LV164			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC} – 0.2			V_{CC} – 0.2			V
	I_{OH} = –6 mA	3 V	2.4			2.4			
	I_{OH} = –12 mA	4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2			0.2	V
	I_{OL} = 6 mA	3 V			0.4			0.4	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±1			±1	µA
		5.5 V			±1			±1	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	µA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		2.5			2.5		pF
		5 V		3			3		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN54LV164						UNIT
			V_{CC} = 5.5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	40	0	35	0	30	MHz
t_w	Pulse duration	$\overline{CLR}$ low	14		16		18		ns
		CLK high or low	14		16		18		
t_{su}	Setup time, data before CLK↑	Data	8		10		12		ns
		$\overline{CLR}$ inactive	5		6		7		
t_h	Hold time, data after CLK↑		3		3		3		ns

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN74LV164						UNIT
			V_{CC} = 5.5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	40	0	35	0	30	MHz
t_w	Pulse duration	$\overline{CLR}$ low	14		16		18		ns
		CLK high or low	14		16		18		
t_{su}	Setup time, data before CLK↑	Data	8		10		12		ns
		$\overline{CLR}$ inactive	5		6		7		
t_h	Hold time, data after CLK↑		3		3		3		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV164								UNIT
			V_{CC} = 5.5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			40	90		35	75		30		MHz
t_{pd}	CLK	Q		10	20		14	26		32	ns
t_{PHL}	$\overline{CLR}$	Q		12	20		16	26		32	ns

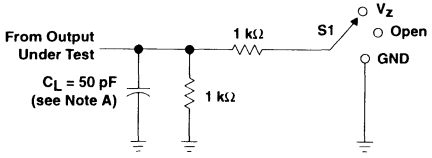
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV164								UNIT
			V_{CC} = 5.5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			40	90		35	75		30		MHz
t_{pd}	CLK	Q		10	20		14	26		32	ns
t_{PHL}	$\overline{CLR}$	Q		12	20		16	26		32	ns

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	TYP	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	74	pF
			5 V	75	

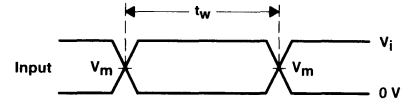
PARAMETER MEASUREMENT INFORMATION



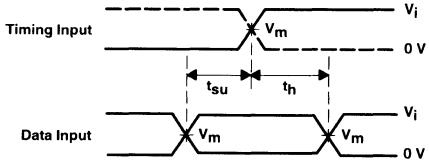
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_z
t_{PHZ}/t_{PZH}	GND

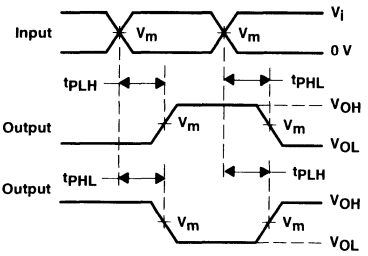
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



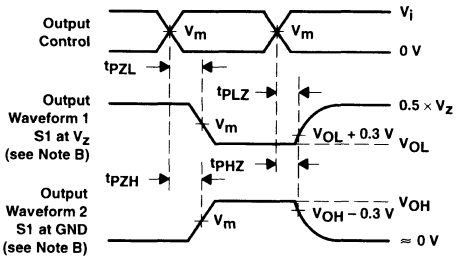
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



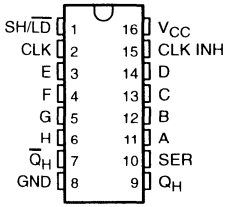
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

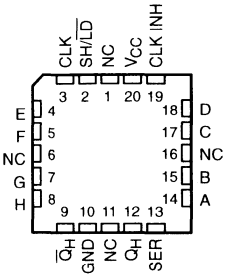
Figure 1. Load Circuit and Voltage Waveforms

- **EPIC™ (Enhanced-Performance Implanted CMOS) 2-μ Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) < 2 V at V_{CC}, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV165 . . . J OR W PACKAGE
SN74LV165 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LV165 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

The 'LV165 parallel-load, 8-bit shift registers are designed for 2.7-V to 5.5-V V_{CC} operation.

When the device is clocked, data is shifted toward the serial output Q_H. Parallel-in access to each stage is provided by eight individual direct data inputs that are enabled by a low level at the SH/$\overline{LD}$ input. The 'LV165 feature a clock inhibit function and a complemented serial output $\overline{Q}_H$.

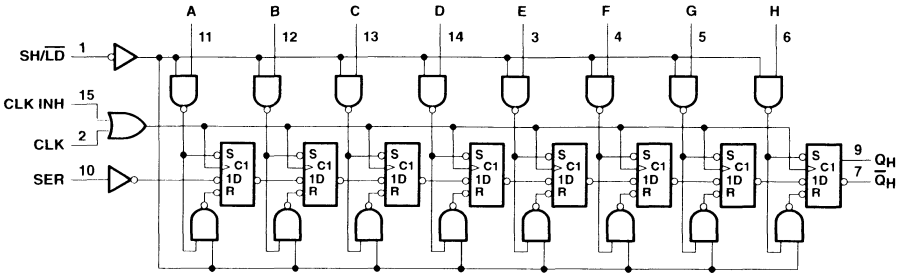
Clocking is accomplished by a low-to-high transition of the clock (CLK) input while SH/$\overline{LD}$ is held high and clock inhibit (CLK INH) is held low. The functions of the CLK and CLK INH inputs are interchangeable. Since a low CLK input and a low-to-high transition of CLK INH accomplishes clocking, CLK INH should be changed to the high level only while CLK is high. Parallel loading is inhibited when SH/$\overline{LD}$ is held high. The parallel inputs to the register are enabled while SH/$\overline{LD}$ is held low independently of the levels of CLK, CLK INH, or SER.

The SN54LV165 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV165 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

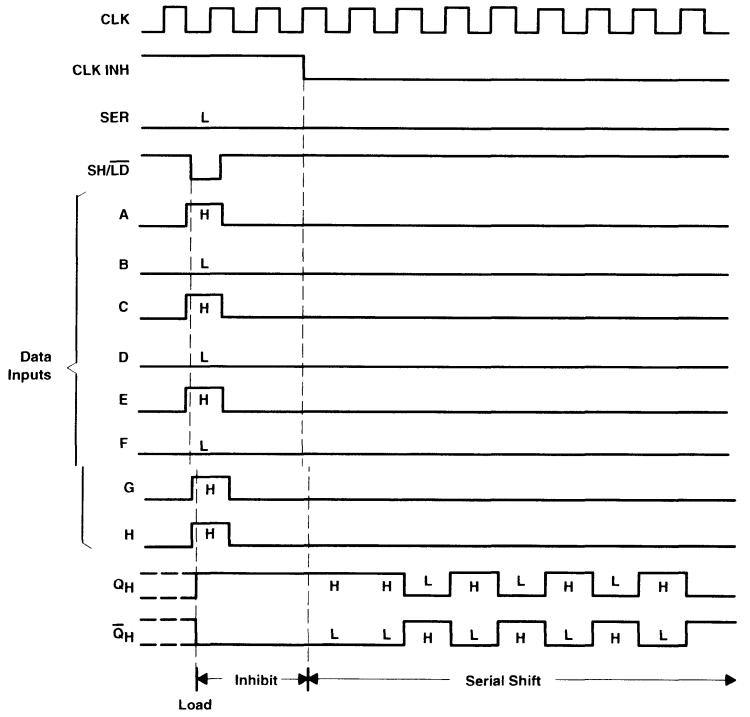
INPUTS			OPERATION
SH/$\overline{LD}$	CLK	CLK INH	
L	X	X	Parallel load
H	H	X	Q_0
H	X	H	Q_0
H	L	↑	Shift
H	↑	L	Shift

logic diagram (positive logic)



Pin numbers shown are for D, DB, J, PW, and W packages.

typical shift, load, and inhibit sequences



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) . . . . . ± 20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ± 50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ± 25 mA
Continuous current through V_{CC} or GND . . . . . ± 50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package . . . . . 1.30 W
DB package . . . . . 0.55 W
PW package . . . . . 0.5 W
Storage temperature range, T_{stg} . . . . . −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV165		SN74LV165		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		−6		−6	mA
		V_{CC} = 4.5 V to 5.5 V		−12		−12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		6		6	mA
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LV165			SN74LV165			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –6 mA	3 V	2.4			2.4			
	I_{OH} = –12 mA	4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2			0.2	V
	I_{OL} = 6 mA	3 V			0.4			0.4	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±1			±1	µA
		5.5 V			±1			±1	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	µA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		2.5			2.5		pF
		5 V		3			3		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN54LV165						UNIT
			V_{CC} = 5.5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	50	0	40	0	30	MHz
t_w	Pulse duration	$\overline{CLK}$ high or low	14		18		22		ns
		SH/$\overline{LD}$ low	14		18		22		
t_{su}	Setup time	SH/$\overline{LD}$ high before $\overline{CLK}$↑	10		13		17		ns
		SER before $\overline{CLK}$↑	8		11		14		
		CLK INH before $\overline{CLK}$↑	10		12		15		
		Data before SH/$\overline{LD}$↑	8		12		17		
t_h	Hold time	SER data after $\overline{CLK}$↑	6		6		5		ns
		Parallel data after SH/$\overline{LD}$↑	6		6		5		

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN74LV165						UNIT
			V_{CC} = 5.5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	50	0	40	0	30	MHz
t_w	Pulse duration	$\overline{CLK}$ high or low	14		18		22		ns
		SH/$\overline{LD}$ low	14		18		22		
t_{su}	Setup time	SH/$\overline{LD}$ high before $\overline{CLK}\uparrow$	10		13		17		ns
		SER before $\overline{CLK}\uparrow$	8		11		14		
		CLK INH before $\overline{CLK}\uparrow$	10		12		15		
		Data before SH/$\overline{LD}\uparrow$	8		12		17		
t_h	Hold time	SER data after $\overline{CLK}\uparrow$	6		6		5		ns
		Parallel data after SH/$\overline{LD}\uparrow$	6		6		5		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV165								UNIT
			V_{CC} = 5.5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			50	90		40	75		30		MHz
t_{pd}	CLK	Q_H or $\overline{Q}_H$		20	24		20	38		47	ns
	SH/$\overline{LD}$			19	24		19	36		44	
	H			15	20		15	29		36	

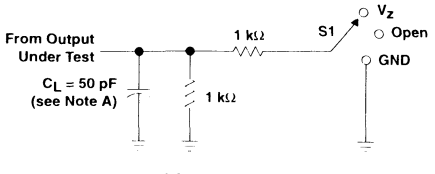
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV165								UNIT
			V_{CC} = 5.5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			50	90		40	75		30		MHz
t_{pd}	CLK	Q_H or $\overline{Q}_H$		20	24		20	38		47	ns
	SH/$\overline{LD}$			19	24		19	36		44	
	H			15	20		15	29		36	

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	33	pF
			5 V	57	

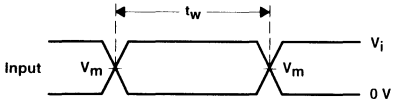
PARAMETER MEASUREMENT INFORMATION



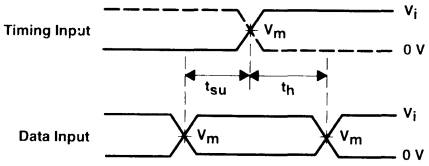
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_z
t_{PHZ}/t_{PZH}	GND

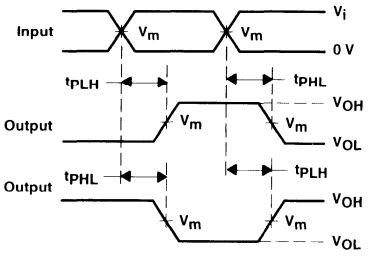
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



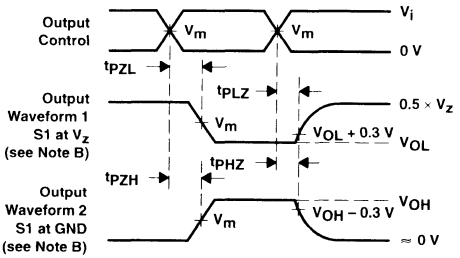
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



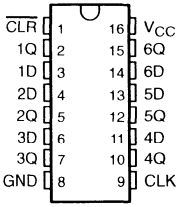
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

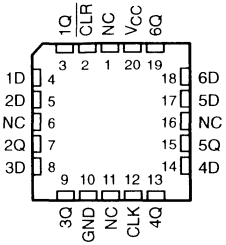
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs

SN54LV174 . . . J OR W PACKAGE
SN74LV174 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LV174 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These hex D-type flip-flops are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LV174 are monolithic positive-edge-triggered flip-flops with a direct clear ($\overline{CLR}$) input. Information at the data (D) inputs meeting the setup time requirements is transferred to the outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going edge of the clock pulse. When the clock (CLK) input is at either the high or low level, the D-input signal has no effect at the output.

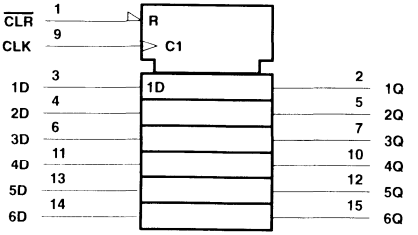
The SN74LV174 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LV174 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV174 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

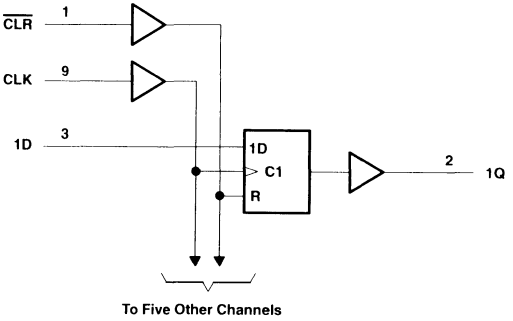
INPUTS			OUTPUT
$\overline{CLR}$	CLK	D	Q
L	X	X	L
H	↑	H	H
H	↑	L	L
H	L	X	Q_0

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for D, DB, J, PW, and W packages.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) ..... ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV174		SN74LV174		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		−6		−6	mA
		V_{CC} = 4.5 V to 5.5 V		−12		−12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		6		6	mA
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LV174			SN74LV174			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC} – 0.2			V_{CC} – 0.2			V
	I_{OH} = –6 mA	3 V	2.4			2.4			
	I_{OH} = –12 mA	4.5	3.6			3.6			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2			0.2	V
	I_{OL} = 6 mA	3 V			0.4			0.4	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±1			±1	µA
		5.5 V			±1			±1	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	µA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		2.5			2.5		pF
		5 V		3			3		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN54LV174						UNIT
			V_{CC} = 5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	40	0	30	0	24	MHz
t_w	Pulse duration	$\overline{CLR}$ low	12		18		22		ns
		CLK high or low	12		18		22		
t_{su}	Setup time before CLK↑	Data	10		12		14		ns
		$\overline{CLR}$ inactive	3		3		3		
t_h	Hold time, data after CLK↑		3		3		3		ns

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN74LV174						UNIT
			V_{CC} = 5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	40	0	30	0	24	MHz
t_w	Pulse duration	$\overline{CLR}$ low	12		18		22		ns
		CLK high or low	12		18		22		
t_{su}	Setup time before CLK↑	Data	10		12		14		ns
		$\overline{CLR}$ inactive	3		3		3		
t_h	Hold time, data after CLK↑		3		3		3		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV174								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			40	90		30	80		24		MHz
t_{pd}	$\overline{CLR}$	Q		9	18		12	23		28	ns
	CLK			8	20		13	29		36	

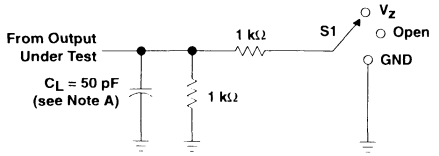
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV174								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			40	90		30	80		24		MHz
t_{pd}	$\overline{CLR}$	Q		9	18		12	23		28	ns
	CLK			8	20		13	29		36	

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	C_L = 50 pF, f = 10 MHz	3.3 V	24	pF
			5 V	52	

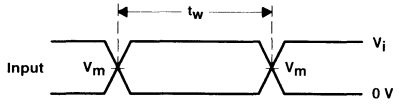
PARAMETER MEASUREMENT INFORMATION



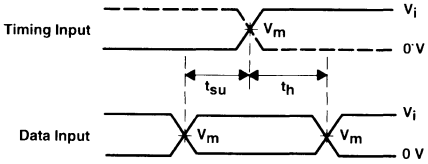
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_z
t_{PHZ}/t_{PZH}	GND

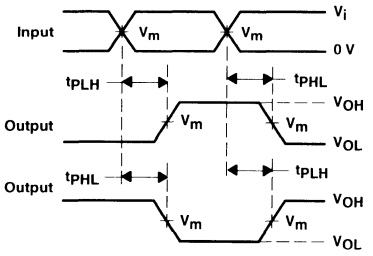
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



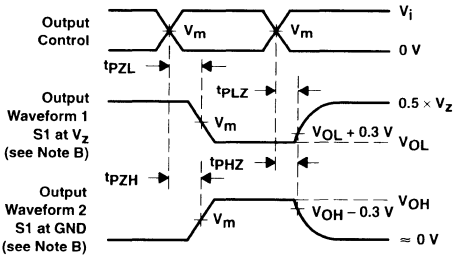
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



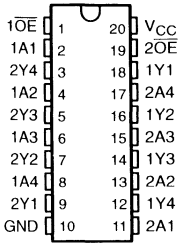
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

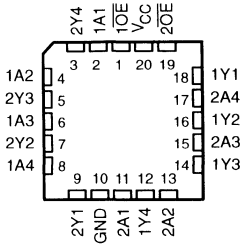
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW, NS), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs

SN54LV240A . . . J OR W PACKAGE
SN74LV240A . . . DB, DGV, DW, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV240A . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/drivers are designed for 2-V to 5.5-V V_{CC} operation.

The 'LV240A are designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

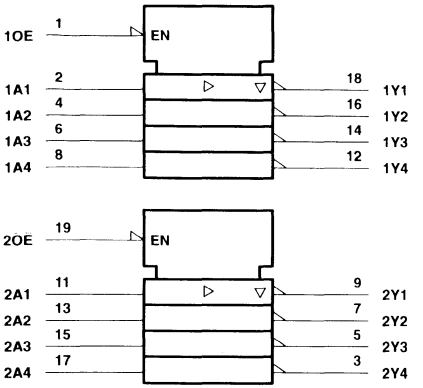
The 'LV240A are organized as two 4-bit buffers/line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

The SN54LV240A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV240A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

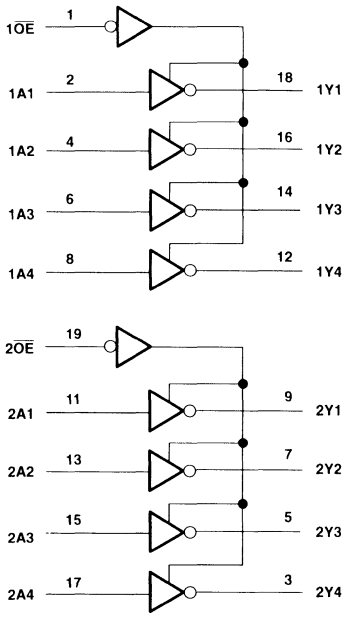
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Output voltage range applied in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range applied in high-impedance or power-off state, V_O (see Note 1) ..... −0.5 V to 7 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) ..... ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DGV package ..... 146°C/W
DW package ..... 97°C/W
NS package ..... 100°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV240A		SN74LV240A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IeH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	V_{CC} × 0.7		V_{CC} × 0.7		
		V_{CC} = 3 V to 3.6 V	V_{CC} × 0.7		V_{CC} × 0.7		
		V_{CC} = 4.5 V to 5.5 V	V_{CC} × 0.7		V_{CC} × 0.7		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		V_{CC} × 0.3		V_{CC} × 0.3	
		V_{CC} = 3 V to 3.6 V		V_{CC} × 0.3		V_{CC} × 0.3	
		V_{CC} = 2.7 V to 3.6 V		V_{CC} × 0.3		V_{CC} × 0.3	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3-state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–8		–8	
		V_{CC} = 4.5 V to 5.5 V		–16		–16	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		8		8	
		V_{CC} = 4.5 V to 5.5 V		16		16	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V	0	200	0	200	ns/V
		V_{CC} = 3 V to 3.6 V	0	100	0	100	
		V_{CC} = 4.5 V to 5.5 V	0	20	0	20	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV240A			SN74LV240A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –50 µA	2 V to 5.5 V	V_{CC}–0.1			V_{CC}–0.1			V
	I_{OH} = –2 mA	2.3 V	2			2			
	I_{OH} = –8 mA	3 V	2.48			2.48			
	I_{OH} = –16 mA	4.5 V	3.8			3.8			
V_{OL}	I_{OL} = 50 µA	2 V to 5.5 V			0.1			0.1	V
	I_{OL} = 2 mA	2.3 V			0.4			0.4	
	I_{OL} = 8 mA	3 V			0.44			0.44	
	I_{OL} = 16 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	5.5 V			±1			±1	µA
I_{OZ}	V_O = V_{CC} or GND	5.5 V			±5			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	5.5 V			20			20	µA
I_{off}	V_O = 5.5 V	0 V			20			20	µA
C_i	V_I = V_{CC} or GND	3.3 V		2.3			2.3		pF
		5 V		2.3			2.3		

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV240A		SN74LV240A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		6.3	11.6	1	14	1	14	ns
t_{en}*	$\overline{OE}$	Y			8.5	14.6	1	17	1	17	
t_{dis}*	$\overline{OE}$	Y			9.7	14.1	1	16	1	16	
t_{pd}	A	Y	C_L = 50 pF		8.2	14.4	1	17	1	17	ns
t_{en}	$\overline{OE}$	Y			10.3	17.8	1	21	1	21	
t_{dis}	$\overline{OE}$	Y			14.2	19.2	1	21	1	21	

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV240A		SN74LV240A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		4.6	7.5	1	9	1	9	ns
t_{en}*	$\overline{OE}$	Y			6.2	10.6	1	12.5	1	12.5	
t_{dis}*	$\overline{OE}$	Y			8.3	12.5	1	13.5	1	13.5	
t_{pd}	A	Y	C_L = 50 pF		5.9	11	1	12.5	1	12.5	ns
t_{en}	$\overline{OE}$	Y			7.5	14.1	1	16	1	16	
t_{dis}	$\overline{OE}$	Y			11.8	15	1	17	1	17	

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV240A		SN74LV240A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		3.4	5.5	1	6.5	1	6.5	ns
t_{en}*	$\overline{OE}$	Y			4.6	7.3	1	8.5	1	8.5	
t_{dis}*	$\overline{OE}$	Y			7.4	12.2	1	13.5	1	13.5	
t_{pd}	A	Y	C_L = 50 pF		4.4	7.5	1	8.5	1	8.5	ns
t_{en}	$\overline{OE}$	Y			5.6	9.3	1	10.5	1	10.5	
t_{dis}	$\overline{OE}$	Y			9.7	14.2	1	15.5	1	15.5	

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

output-skew characteristics, C_L = 50 pF (see Note 5)

PARAMETER		V_{CC}	SN74LV240A			UNIT
			T_A = 25°C		MIN	MAX	
			MIN	MAX			
$t_{sk(o)}$	Output skew	2.3 V to 2.7 V	2		2	ns
		3 V to 3.6 V	1.5		1.5	ns
		4.5 V to 5.5 V	1		1	ns

NOTE 5: Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

noise characteristics, V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C (see Note 6)

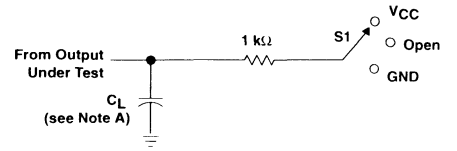
PARAMETER		SN74LV240A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.56		V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		−0.49		V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		2.82		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 6: Characteristics are for surface-mount packages only. These parameters are warranted but not production tested.

operating characteristics, T_A = 25°C

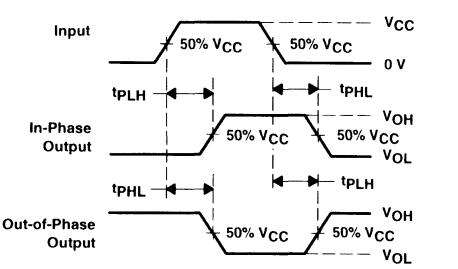
PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	14	pF
			5 V	16	

PARAMETER MEASUREMENT INFORMATION

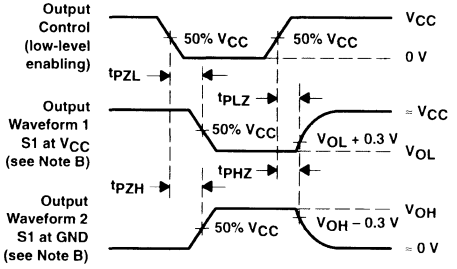


LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



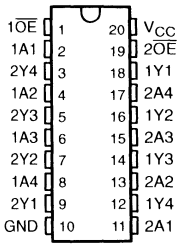
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

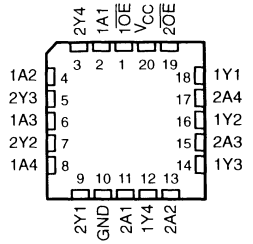
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW, NS), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs

SN54LV244A . . . J OR W PACKAGE
SN74LV244A . . . DB, DGV, DW, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV244A . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/line drivers are designed for 2-V to 5.5-V V_{CC} operation.

The 'LV244A are designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

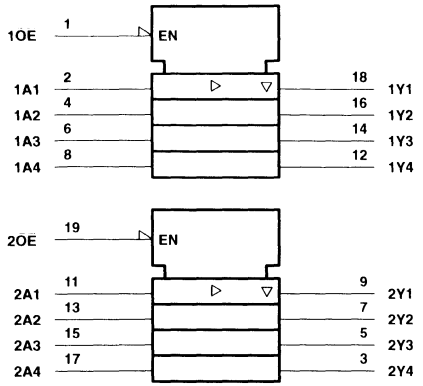
The 'LV244A are organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the output is in the high-impedance state.

The SN54LV244A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

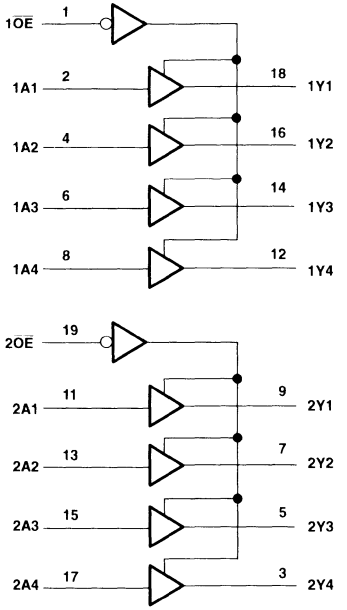
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Output voltage range applied in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range applied in high-impedance or power-off state, V_O (see Note 1) ..... −0.5 V to 7 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package ..... 115°C/W
DGV package ..... 146°C/W
DW package ..... 97°C/W
NS package ..... 100°C/W
PW package ..... 128°C/W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV244A		SN74LV244A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 3 V to 3.6 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 4.5 V to 5.5 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 3 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 2.7 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3-state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–8		–8	
		V_{CC} = 4.5 V to 5.5 V		–16		–16	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		8		8	
		V_{CC} = 4.5 V to 5.5 V		16		16	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V	0	200	0	200	ns/V
		V_{CC} = 3 V to 3.6 V	0	100	0	100	
		V_{CC} = 4.5 V to 5.5 V	0	20	0	20	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV244A			SN74LV244A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = −50 μA	2 V to 5.5 V	V_{CC} − 0.1			V_{CC} − 0.1			V
	I_{OH} = −2 mA	2.3 V	2			2			
	I_{OH} = −8 mA	3 V	2.48			2.48			
	I_{OH} = −16 mA	4.5 V	3.8			3.8			
V_{OL}	I_{OL} = 50 μA	2 V to 5.5 V			0.1			0.1	V
	I_{OL} = 2 mA	2.3 V			0.4			0.4	
	I_{OL} = 8 mA	3 V			0.44			0.44	
	I_{OL} = 16 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	5.5 V			±1			±1	μA
I_{OZ}	V_O = V_{CC} or GND	3.6 V							μA
		5.5 V			±5			±5	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	5.5 V			20			20	μA
I_{off}	V_O = 5.5 V	0 V			20			20	μA
C_i	V_I = V_{CC} or GND	3.3 V		2.3			2.3		pF
		5 V		2.3			2.3		

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV244A		SN74LV244A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		7.5	12.5	1	15	1	15	ns
t_{en}*	$\overline{OE}$	Y			8.9	14.6	1	17	1	17	
t_{dis}*	$\overline{OE}$	Y			9.1	14.1	1	16	1	16	
t_{pd}	A	Y	C_L = 50 pF		9.5	15.3	1	18	1	18	ns
t_{en}	$\overline{OE}$	Y			10.8	17.8	1	21	1	21	
t_{dis}	$\overline{OE}$	Y			13.4	19.2	1	21	1	21	

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV244A		SN74LV244A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		5.4	8.4	1	10	1	10	ns
t_{en}*	$\overline{OE}$	Y			6.3	10.6	1	12.5	1	12.5	
t_{dis}*	$\overline{OE}$	Y			7.6	11	1	13	1	13	
t_{pd}	A	Y	C_L = 50 pF		6.8	11.9	1	13.5	1	13.5	ns
t_{en}	$\overline{OE}$	Y			7.8	14.1	1	16	1	16	
t_{dis}	$\overline{OE}$	Y			11	16	1	18	1	18	

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV244A		SN74LV244A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		3.9	5.5	1	6.5	1	6.5	ns
t_{en}*	$\overline{OE}$	Y			4.5	7.3	1	8.5	1	8.5	
t_{dis}*	$\overline{OE}$	Y			6.5	12.2	1	13.5	1	13.5	
t_{pd}	A	Y	C_L = 50 pF		4.9	7.5	1	8.5	1	8.5	ns
t_{en}	$\overline{OE}$	Y			5.6	9.3	1	10.5	1	10.5	
t_{dis}	$\overline{OE}$	Y			8.8	14.2	1	15.5	1	15.5	

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

output-skew characteristics, C_L = 50 pF (see Note 5)

PARAMETER		V_{CC}	SN74LV244A			UNIT
			T_A = 25°C		MIN	MAX
			MIN	MAX		
$t_{sk(o)}$	Output skew	2.3 V to 2.7 V	2		2	ns
		3 V to 3.6 V	1.5		1.5	ns
		4.5 V to 5.5 V	1		1	ns

NOTE 5: Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

noise characteristics, V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C (see Note 6)

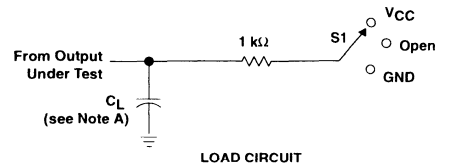
PARAMETER		SN74LV244A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.55		V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–0.5		V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		2.9		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 6: Characteristics are for surface-mount packages only. These parameters are warranted but not production tested.

operating characteristics, T_A = 25°C

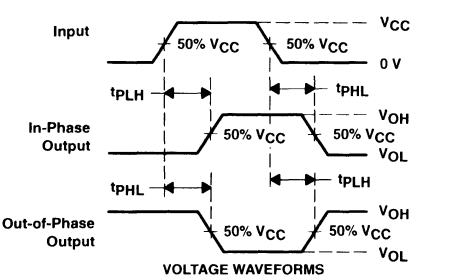
PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	14	pF
			5 V	16	

PARAMETER MEASUREMENT INFORMATION

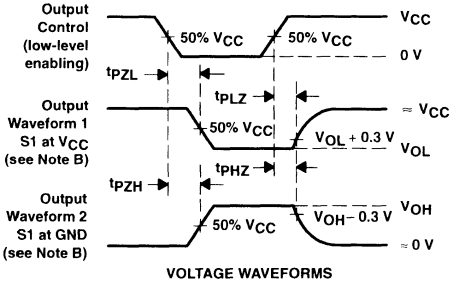


LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



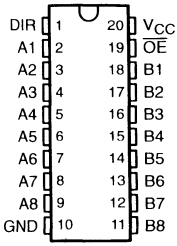
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

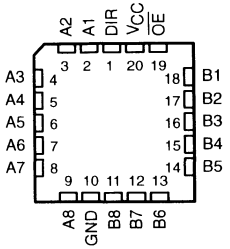
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW, NS), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs

SN54LV245A . . . J OR W PACKAGE
SN74LV245A . . . DB, DW, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV245A . . . FK PACKAGE
(TOP VIEW)



description

These octal bus transceivers are designed for 2-V to 5.5-V V_{CC} operation.

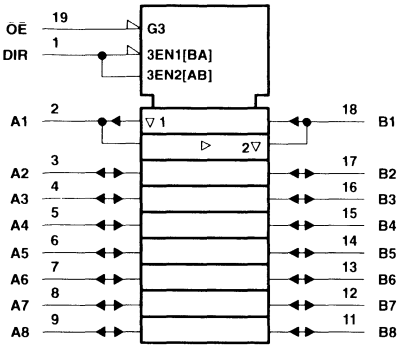
The 'LV245A are designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

The SN54LV245A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

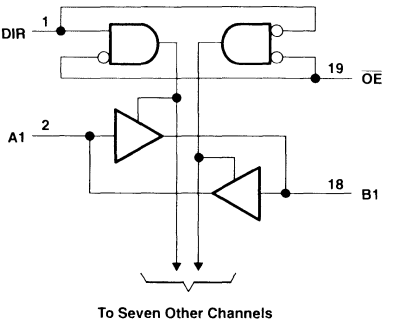
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC}	−0.5 V to 7 V
Input voltage range, V_I: Except I/O ports (see Note 1)	−0.5 V to 7 V
I/O ports (see Notes 1 and 2)	−0.5 V to V_{CC} + 0.5 V
Output voltage range applied in the high or low state, V_O (see Notes 1 and 2)	−0.5 V to V_{CC} + 0.5 V
Output voltage range applied in high-impedance or power-off state, V_O (see Note 1)	−0.5 V to 7 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$)	±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)	±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	±35 mA
Continuous current through V_{CC} or GND	±70 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package	115°C/W
DW package	97°C/W
NS package	100°C/W
PW package	128°C/W
Storage temperature range, T_{stg}	−65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV245A		SN74LV245A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	V_{CC} × 0.7		V_{CC} × 0.7		
		V_{CC} = 3 V to 3.6 V	V_{CC} × 0.7		V_{CC} × 0.7		
		V_{CC} = 4.5 V to 5.5 V	V_{CC} × 0.7		V_{CC} × 0.7		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		V_{CC} × 0.3		V_{CC} × 0.3	
		V_{CC} = 3 V to 3.6 V		V_{CC} × 0.3		V_{CC} × 0.3	
		V_{CC} = 2.7 V to 3.6 V		V_{CC} × 0.3		V_{CC} × 0.3	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3-state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–8		–8	
		V_{CC} = 4.5 V to 5.5 V		–16		–16	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		8		8	
		V_{CC} = 4.5 V to 5.5 V		16		16	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V	0	200	0	200	ns/V
		V_{CC} = 3 V to 3.6 V	0	100	0	100	
		V_{CC} = 4.5 V to 5.5 V	0	20	0	20	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	SN54LV245A			SN74LV245A			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}		I_{OH} = –50 μA	2 V to 5.5 V	V_{CC}–0.1			V_{CC}–0.1			V
		I_{OH} = –2 mA	2.3 V	2			2			
		I_{OH} = –8 mA	3 V	2.48			2.48			
		I_{OH} = –16 mA	4.5 V	3.8			3.8			
V_{OL}		I_{OL} = 50 μA	2 V to 5.5 V			0.1			0.1	V
		I_{OL} = 2 mA	2.3 V			0.4			0.4	
		I_{OL} = 8 mA	3 V			0.44			0.44	
		I_{OL} = 16 mA	4.5 V			0.55			0.55	
I_I		V_I = V_{CC} or GND	5.5 V			±1			±1	μA
I_{OZ}		V_O = V_{CC} or GND	5.5 V			±5			±5	μA
I_{CC}		V_I = V_{CC} or GND, I_O = 0	5.5 V			20			20	μA
I_{off}		V_O = 5.5 V	0 V			5			5	μA
C_i	Control inputs	V_I = V_{CC} or GND	3.3 V		2.4			2.4		pF
			5 V		2.4			2.4		
C_{io}	A or B port	V_O = V_{CC} or GND	3.3 V		5.4			5.4		pF
			5 V		5.4			5.4		

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV245A		SN74LV245A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A or B	B or A	C_L = 15 pF		8.3	13	1	15	1	15	ns
t_{en}*	$\overline{OE}$	A or B			11.8	19.9	1	22	1	22	
t_{dis}*	$\overline{OE}$	A or B			11.8	18.1	1	20	1	20	
t_{pd}	A or B	B or A	C_L = 50 pF		11.2	15.9	1	18	1	18	ns
t_{en}	$\overline{OE}$	A or B			14.1	22.7	1	26	1	26	
t_{dis}	$\overline{OE}$	A or B			17.6	23.1	1	25	1	25	

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV245A		SN74LV245A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A or B	B or A	C_L = 15 pF		5.9	8.4	1	10	1	10	ns
t_{en}*	$\overline{OE}$	A or B			8.2	13.2	1	15.5	1	15.5	
t_{dis}*	$\overline{OE}$	A or B			9.6	16.5	1	19.5	1	19.5	
t_{pd}	A or B	B or A	C_L = 50 pF		7.9	11.9	1	13.5	1	13.5	ns
t_{en}	$\overline{OE}$	A or B			9.9	16.7	1	19	1	19	
t_{dis}	$\overline{OE}$	A or B			13.9	19.8	1	22	1	22	

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV245A		SN74LV245A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A or B	B or A	C_L = 15 pF		4.3	5.5	1	6.5	1	6.5	ns
t_{en}*	$\overline{OE}$	A or B			5.7	8.5	1	10.6	1	10	
t_{dis}*	$\overline{OE}$	A or B			7.8	12.8	1	14.7	1	14.2	
t_{pd}	A or B	B or A	C_L = 50 pF		5.6	7.5	1	8.5	1	8.5	ns
t_{en}	$\overline{OE}$	A or B			7	10.6	1	12	1	12	
t_{dis}	$\overline{OE}$	A or B			10.9	14.7	1	16		16	

* On products compliant to MIL-PRF-38535, this parameter is warranted but not production tested.

output-skew characteristics, C_L = 50 pF (see Note 5)

PARAMETER		V_{CC}	SN74LV245A			UNIT
			T_A = 25°C		MIN	MAX
			MIN	MAX		
$t_{sk(o)}$	Output skew	2.3 V to 2.7 V		2		2	ns
		3 V to 3.6 V		1.5		1.5	ns
		4.5 V to 5.5 V		1		1	ns

NOTE 5: Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

noise characteristics, V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C (see Note 6)

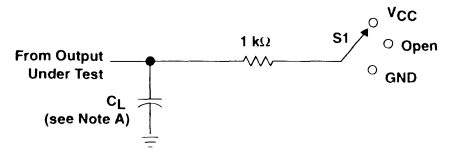
PARAMETER		SN74LV245A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.45		V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–0.45		V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		2.94		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 6: Characteristics are for surface-mount packages only. These parameters are warranted but not production tested.

operating characteristics, T_A = 25°C

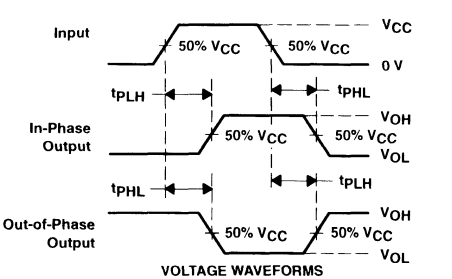
PARAMETER			TEST CONDITIONS		V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF,	f = 10 MHz	3.3 V	20	pF
		Outputs enabled			5 V	25	

PARAMETER MEASUREMENT INFORMATION

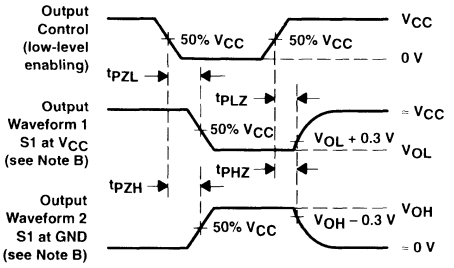


LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



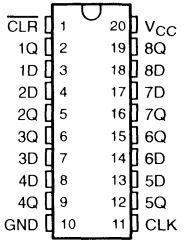
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

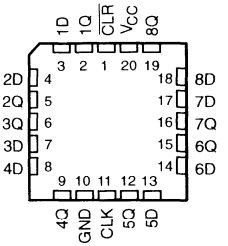
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV273 . . . J OR W PACKAGE
SN74LV273 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LV273 . . . FK PACKAGE
(TOP VIEW)



description

These octal D-type flip-flops are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LV273 are positive-edge-triggered flip-flops with direct clear ($\overline{CLR}$) input. Information at the data (D) inputs meeting the setup time requirements is transferred to the Q outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock (CLK) input is at either the high or low level, the D-input signal has no effect at the output.

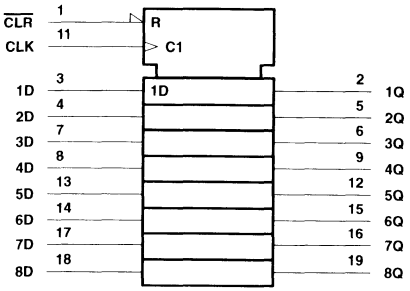
The SN74LV273 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LV273 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV273 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

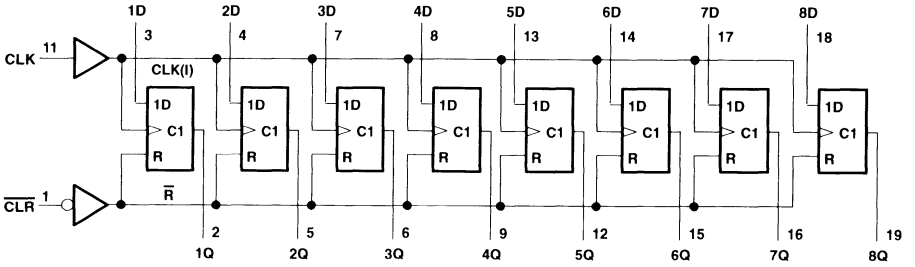
INPUTS			OUTPUT
$\overline{CLR}$	CLK	D	Q
L	X	X	L
H	↑	H	H
H	↑	L	L
H	L	X	Q_0

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for DB, DW, J, PW, and W packages.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) ..... ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV273		SN74LV273		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		−6		−6	mA
		V_{CC} = 4.5 V to 5.5 V		−12		−12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		6		6	mA
		V_{CC} = 4.5 V to 5.5 V		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	SN54LV273			SN74LV273			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –6 mA		3 V	2.4			2.4			
	I_{OH} = –12 mA		4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2			0.2	V
	I_{OL} = 6 mA		3 V			0.4			0.4	
	I_{OL} = 12 mA		4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND		3.6 V			±1			±1	μA
			5.5 V			±1			±1	
I_{OZ}	V_O = V_{CC} or GND,	I_O = 0	3.6 V			±5			±5	μA
			5.5 V			±5			±5	
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20			20	μA
			5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		3 V to 3.6 V			500			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		2.5			2.5		pF
			5 V		3			3		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN54LV273						UNIT
			V_{CC} = 5.5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	60	0	50	0	40	MHz
t_w	Pulse duration	$\overline{CLR}$ low	6		10		12		ns
		CLK high or low	7		10		12		
t_{su}	Setup time before CLK↑	Data	8		12		14		ns
		$\overline{CLR}$ inactive	2		2		2		
t_h	Hold time, data after CLK↑		3		2		2		ns

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN74LV273						UNIT
			V_{CC} = 5.5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	60	0	50	0	40	MHz
t_w	Pulse duration	$\overline{CLR}$ low	6		10		12		ns
		CLK high or low	7		10		12		
t_{su}	Setup time before CLK↑	Data	8		12		14		ns
		$\overline{CLR}$ inactive	2		2		2		
t_h	Hold time, data after CLK↑		3		2		2		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV273								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			60	100		50	80		40		MHz
t_{pd}	CLK	Q		11	16		16	22		26	ns
t_{PHL}	$\overline{CLR}$	Q		13	22		14	24		30	ns

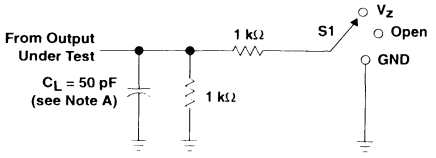
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV273								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			60	100		50	80		40		MHz
t_{pd}	CLK	Q		11	16		16	22		26	ns
t_{PHL}	$\overline{CLR}$	Q		13	22		14	24		30	ns

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	C_L = 50 pF, f = 10 MHz	3.3 V	32	pF
			5 V	41	

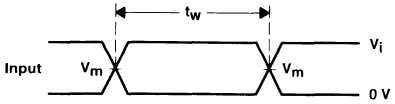
PARAMETER MEASUREMENT INFORMATION



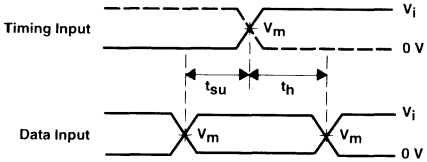
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_z
t_{PHZ}/t_{PZH}	GND

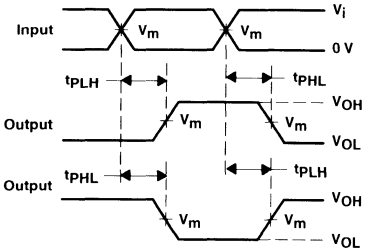
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



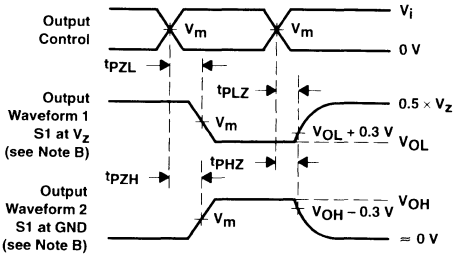
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



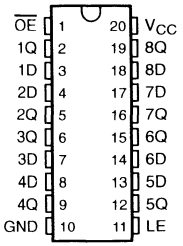
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

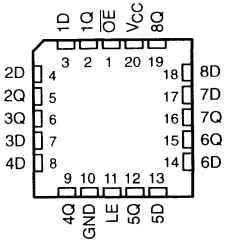
Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs

SN54LV373 . . . J OR W PACKAGE
SN74LV373 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LV373 . . . FK PACKAGE
(TOP VIEW)



description

These octal transparent D-type latches are designed for 2.7-V to 5.5-V V_{CC} operation.

While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

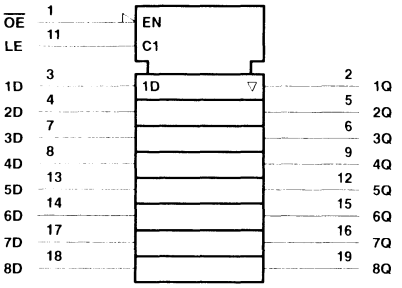
The SN74LV373 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LV373 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV373 is characterized for operation from –40°C to 85°C.

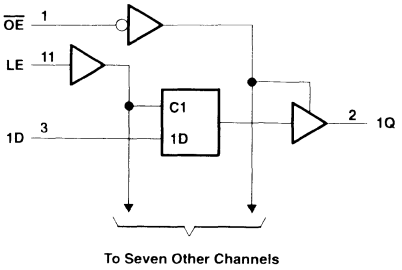
FUNCTION TABLE
(each latch)

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for DB, DW, J, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV373		SN74LV373		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		–8		–8	mA
		V_{CC} = 4.5 V to 5.5 V		–16		–16	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		8		8	mA
		V_{CC} = 4.5 V to 5.5 V		16		16	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LV373			SN74LV373			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = –8 mA	3 V	2.4			2.4			
	I_{OH} = –16 mA	4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2			0.2	V
	I_{OL} = 8 mA	3 V			0.4			0.4	
	I_{OL} = 16 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±1			±1	µA
		5.5 V			±1			±1	
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±5			±5	µA
		5.5 V			±5			±5	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	µA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		2.5			2.5		pF
		5 V		3			3		
C_o	V_O = V_{CC} or GND	3.3 V		7			7		pF
		5 V		7.5			7.5		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN54LV373						UNIT
			V_{CC} = 5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high		10		10		8		ns
t_{su}	Setup time, data before LE↓	High or low	4		6		6		ns
t_h	Hold time, data after LE↓	High or low	6		6		6		ns

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN74LV373						UNIT
			V_{CC} = 5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high		10		10		8		ns
t_{su}	Setup time, data before LE↓	High or low	4		6		6		ns
t_h	Hold time, data after LE↓	High or low	6		6		6		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV373								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	D	Q		8	16		11	22		28	ns
	LE			11	19		15	25		26	
t_{en}	$\overline{OE}$	Q		15	23		15	27		28	ns
t_{dis}	$\overline{OE}$	Q		15	23		15	27		28	ns

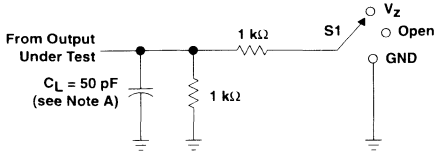
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV373								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	D	Q		8	16		11	22		28	ns
	LE			11	19		15	25		26	
t_{en}	$\overline{OE}$	Q		15	23		15	27		28	ns
t_{dis}	$\overline{OE}$	Q		15	23		15	27		28	ns

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 50 pF, f = 10 MHz	3.3 V	47	pF
		Outputs disabled			29	
		Outputs enabled		5 V	112	
		Outputs disabled			62	

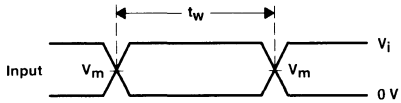
PARAMETER MEASUREMENT INFORMATION



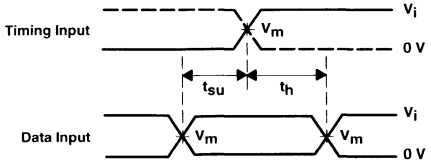
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_Z
t_{PHZ}/t_{PZH}	GND

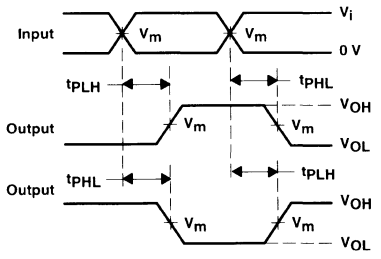
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



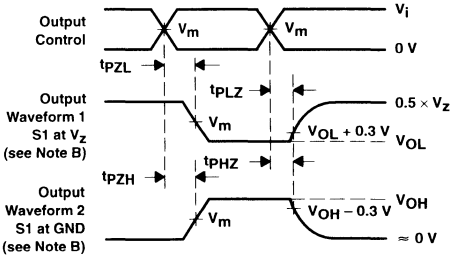
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



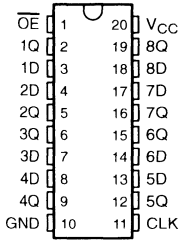
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

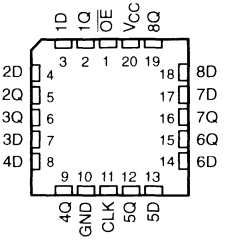
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV374 . . . J OR W PACKAGE
SN74LV374 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LV374 . . . FK PACKAGE
(TOP VIEW)



description

These octal edge-triggered D-type flip-flops are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LV374 feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either as normal logic state (high or low logic levels) or high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

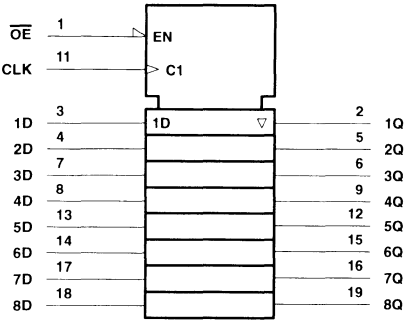
The SN74LV374 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LV374 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

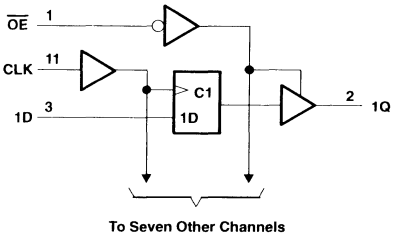
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for DB, DW, J, PW, and W packages.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV374		SN74LV374		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		−8		−8	mA
		V_{CC} = 4.5 V to 5.5 V		−16		−16	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		8		8	mA
		V_{CC} = 4.5 V to 5.5 V		16		16	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LV374			SN54LV374			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = −100 μA	MIN to MAX	V_{CC}−0.2			V_{CC}−0.2			V
	I_{OH} = −8 mA	3 V	2.4			2.4			
	I_{OH} = −16 mA	4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 μA	MIN to MAX			0.2			0.2	V
	I_{OL} = 8 mA	3 V			0.4			0.4	
	I_{OL} = 16 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±1			±1	μA
		5.5 V			±1			±1	
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±5			±5	μA
		5.5 V			±5			±5	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	μA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	μA
C_i	V_I = V_{CC} or GND	3.3 V		2.5			2.5		pF
		5 V		3			3		
C_o	V_O = V_{CC} or GND	3.3 V		7			7		pF
		5 V		8			8		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN54LV374						UNIT
			V_{CC} = 5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	45	0	40	0	35	MHz
t_w	Pulse duration, CLK high or low		9		10		13		ns
t_{su}	Setup time before CLK↑	High or low	7		10		11		ns
t_h	Hold time, data after CLK↑		3		2		2		ns

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN74LV374						UNIT
			V_{CC} = 5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	45	0	40	0	35	MHz
t_w	Pulse duration, CLK high or low		9		10		13		ns
t_{su}	Setup time before CLK↑	High or low	7		10		11		ns
t_h	Hold time, data after CLK↑		3		2		2		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV374								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			45	80		40	70		35		MHz
t_{pd}	CLK	Q		11	19		15	24		29	ns
t_{en}	$\overline{OE}$	Q		10	20		13	24		28	ns
t_{dis}	$\overline{OE}$	Q		8	21		12	24		29	ns

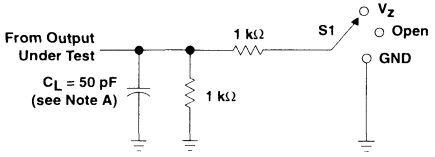
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV374								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			45	80		40	70		35		MHz
t_{pd}	CLK	Q		11	19		15	24		29	ns
t_{en}	$\overline{OE}$	Q		10	20		13	24		28	ns
t_{dis}	$\overline{OE}$	Q		8	21		12	24		29	ns

operating characteristics, $T_A = 25°C$

PARAMETER			TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 50 pF, f = 10 MHz	3.3 V	52	pF
		Outputs disabled			34	
		Outputs enabled		5 V	60	
		Outputs disabled			35	

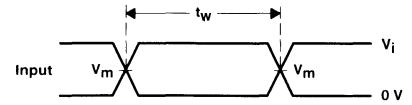
PARAMETER MEASUREMENT INFORMATION



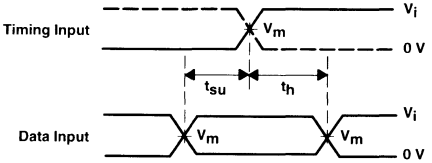
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_z
t_{PHZ}/t_{PZH}	GND

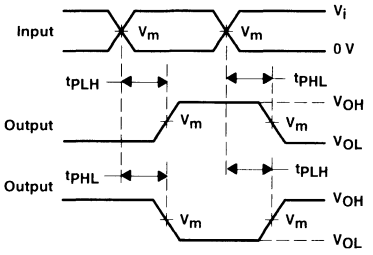
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



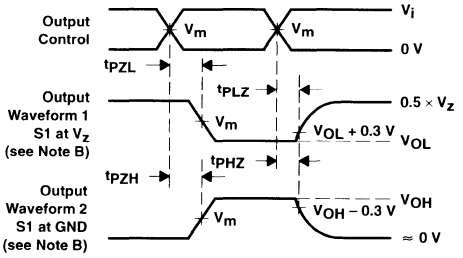
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



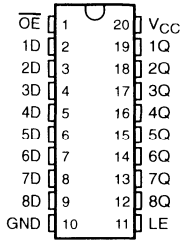
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

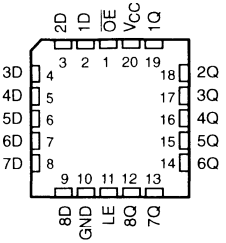
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV573 . . . J OR W PACKAGE
SN74LV573 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LV573 . . . FK PACKAGE
(TOP VIEW)



description

These octal transparent D-type latches are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LV573 feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

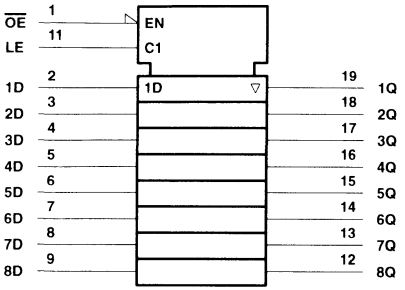
The SN74LV573 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LV573 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV573 is characterized for operation from –40°C to 85°C.

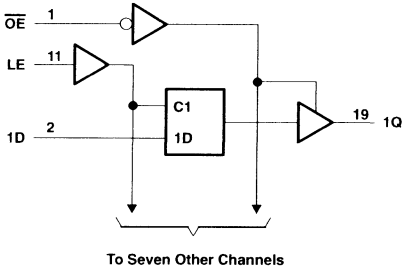
FUNCTION TABLE
(each latch)

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for DB, DW, J, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV573		SN74LV573		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		–8		–8	mA
		V_{CC} = 4.5 V to 5.5 V		–16		–16	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		8		8	mA
		V_{CC} = 4.5 V to 5.5 V		16		16	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LV573			SN74LV573			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –100 μA	MIN to MAX	V_{CC}–0.2			V_{CC}–0.2			V
	I_{OH} = – 8 mA	3 V	2.4			2.4			
	I_{OH} = – 16 mA	4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 μA	MIN to MAX			0.2			0.2	V
	I_{OL} = 8 mA	3 V			0.4			0.4	
	I_{OL} = 16 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±1			±1	μA
		5.5 V			±1			±1	
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±5			±5	μA
		5.5 V			±5			±5	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	μA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	μA
C_i	V_I = V_{CC} or GND	3.3 V		2.5			2.5		pF
		5 V		3			3		
C_o	V_O = V_{CC} or GND	3.3 V		7			7		pF
		5 V		10			10		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

		SN54LV573						UNIT
		V_{CC} = 5.5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	9		12		14		ns
t_{su}	Setup time, data before LE↓	4		6		7		ns
t_h	Hold time, data after LE↓	4		6		6		ns

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

		SN74LV573						UNIT
		V_{CC} = 5.5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	9		12		14		ns
t_{su}	Setup time, data before LE↓	4		6		7		ns
t_h	Hold time, data after LE↓	4		6		6		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV573								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	D	Q		9	19		13	23		29	ns
	LE			12	21		19	25		31	
t_{en}	$\overline{OE}$	Q		11	18		16	22		28	ns
t_{dis}	$\overline{OE}$	Q		15	21		21	28		29	ns

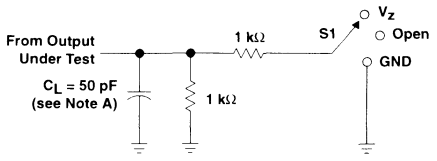
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV573								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	D	Q		9	19		13	23		29	ns
	LE			12	21		19	25		31	
t_{en}	$\overline{OE}$	Q		11	18		16	22		28	ns
t_{dis}	$\overline{OE}$	Q		15	21		21	28		29	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

PARAMETER			TEST CONDITIONS	VCC	TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 50 pF, f = 10 MHz	3.3 V	30	pF
		Outputs disabled			14	
		Outputs enabled		5 V	36	
		Outputs disabled			16	

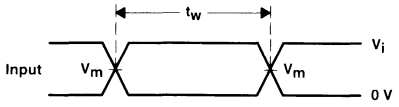
PARAMETER MEASUREMENT INFORMATION



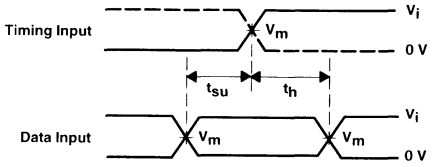
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_z
t_{PHZ}/t_{PZH}	GND

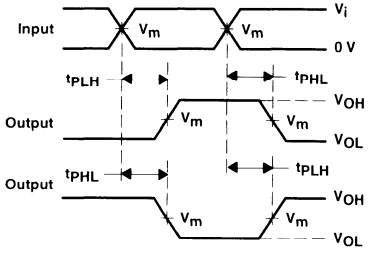
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



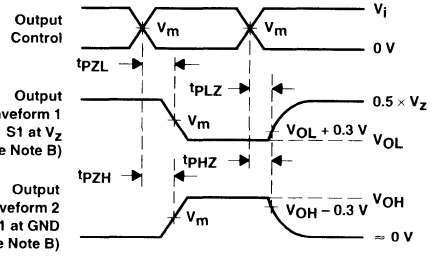
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



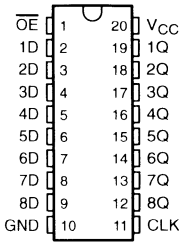
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

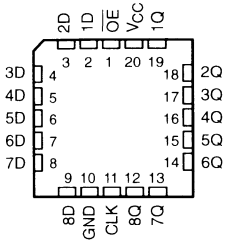
Figure 1. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV574 . . . J OR W PACKAGE
SN74LV574 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LV574 . . . FK PACKAGE
(TOP VIEW)



description

These octal edge-triggered D-type flip-flops are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LV574 feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

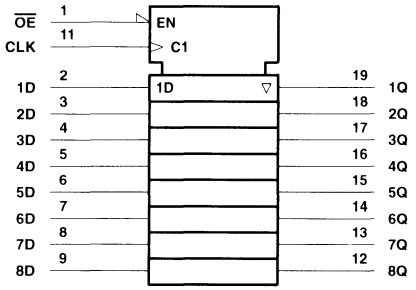
The SN74LV574 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LV574 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV574 is characterized for operation from –40°C to 85°C.

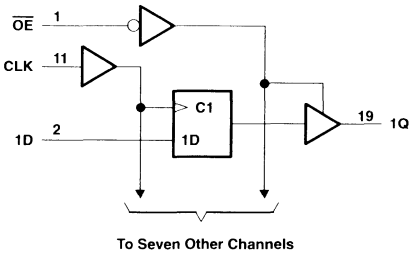
FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for DB, DW, J, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

recommended operating conditions (see Note 4)

			SN54LV574		SN74LV574		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		2		V
		V_{CC} = 4.5 V to 5.5 V	3.15		3.15		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V		1.65		1.65	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		–8		–8	mA
		V_{CC} = 4.5 V to 5.5 V		–16		–16	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		8		8	mA
		V_{CC} = 4.5 V to 5.5 V		16		16	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	100	0	100	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	SN54LV574			SN74LV574			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC} – 0.2			V_{CC} – 0.2			V
	I_{OH} = – 8 mA	3 V	2.4			2.4			
	I_{OH} = – 16 mA	4.5	3.6			3.6			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2			0.2	V
	I_{OL} = 8 mA	3 V			0.4			0.4	
	I_{OL} = 16 mA	4.5 V			0.55			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±1			±1	µA
		5.5 V			±1			±1	
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±5			±5	µA
		5.5 V			±5			±5	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20			20	µA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		2.5			2.5		pF
		5 V		3			3		
C_o	V_O = V_{CC} or GND	3.3 V		7			7		pF
		5 V		10			10		

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN54LV574						UNIT
			V_{CC} = 5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			50		40		30	MHz
t_w	Pulse duration, CLK high or low		8		12		14		ns
t_{su}	Setup time before CLK↑	High or low	5		8		9		ns
t_h	Hold time, data after CLK↑		4		3		3		ns

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			SN74LV574						UNIT
			V_{CC} = 5 V ± 0.5 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			50		40		30	MHz
t_w	Pulse duration, CLK high or low		8		12		14		ns
t_{su}	Setup time before CLK↑	High or low	5		8		9		ns
t_h	Hold time, data after CLK↑		4		3		3		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV574								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			50	70		40	50		30		MHz
t_{pd}	CLK	Q		12	17		17	24		26	ns
t_{en}	$\overline{OE}$	Q		11	17		16	22		25	ns
t_{dis}	$\overline{OE}$	Q		14	19		18	27		28	ns

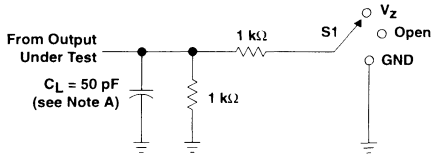
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV574								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
f_{max}			50	70		40	50		30		MHz
t_{pd}	CLK	Q		12	17		17	24		26	ns
t_{en}	$\overline{OE}$	Q		11	17		16	22		25	ns
t_{dis}	$\overline{OE}$	Q		14	19		18	27		28	ns

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 50 pF, f = 10 MHz	3.3 V	40	pF
		Outputs disabled			22	
		Outputs enabled		5 V	44	
		Outputs disabled			24	

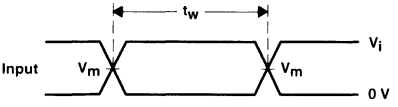
PARAMETER MEASUREMENT INFORMATION



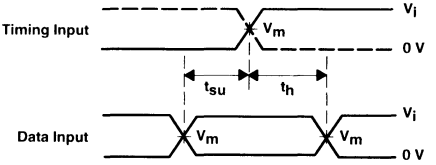
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_z
t_{PHZ}/t_{PZH}	GND

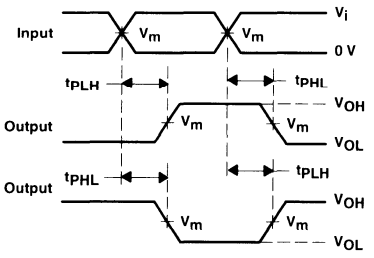
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	0.5 × V_{CC}	1.5 V
V_i	V_{CC}	2.7 V
V_z	2 × V_{CC}	6 V



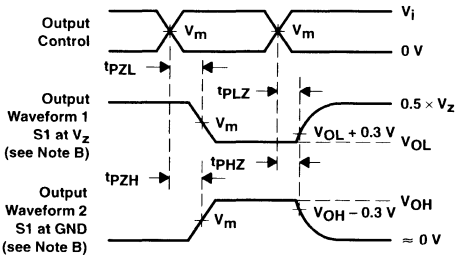
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

Low-Voltage-Logic-Families

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Literature Number: SCVAE01A
Date: April, 28th 1997

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Low-Voltage-Logic-Families

ABSTRACT

This report concerns the new families of logic integrated circuits designed for a supply voltage of 3.3V, with suffixes LV, LVC, ALVC, LVT and ALB. The new technology of these circuits is first presented and explained; this is followed by a description of their electrical behavior under both DC and AC conditions.

1 Introduction

At the beginning of the sixties TTL logic became established as the preferred technology for digital signal processing. Since the breakdown voltage of the multi-emitter inputs used at that time was about 5.5V, the decision was taken to use a 5V-supply voltage. Since then 5V has become the standard for supply voltages with digital components.

	'HC245		'AHC245		'AC245	
	V_{CC}=4.5V	V_{CC}=2.0V	V_{CC}=4.5V	V_{CC}=3.3V	V_{CC}=4.5V	V_{CC}=3.3V
t_{PLH} TYP A⇨B / B⇨A	15 ns	40 ns	5.5 ns	8.3 ns	3.5 ns	5 ns
t_{PLH} MAX A⇨B / B⇨A	26 ns	130 ns	8.5 ns	13.5 ns	7 ns	9 ns
V_{OH} specified up to	-6 mA	-20 µA	-8 mA	-4 mA	-24 mA	-12 mA
V_{OL} specified up to	6 mA	20 µA	8 mA	4 mA	24 mA	12 mA

Table 1: Parameter changes within logic families HC, AC and AHC at reduced supply voltage

A number of different requirements have meanwhile driven the demand for a reduced supply voltage:

- ⇨ The reduction of the horizontal and vertical wafer geometries of modern semiconductors has now reached an order of magnitude that demands lower voltages to sustain device reliability. In particular, the high field strength with 5V operation represents an increase of stress that can lead to the breakdown of the gate oxide. The result is a short circuit of the CMOS transistor, which would make the component useless.
- ⇨ The demand for a further reduction in power consumption comes mostly from manufacturers of battery operated equipment. The power consumption results principally from capacitive loads, the operating frequency, and from the supply voltage. While the capacitances of the load and the operating frequency have a linear effect on power consumption, the consumption depends on the square of the supply voltage.
- ⇨ Lower power consumption however also reduces the generation of heat in subassemblies, and so can obviate the need for cooling fans, and simultaneously improve the reliability of the components. Lower temperatures also allow an increase in the density of integration of components. For this reason, many DRAM's operate these days internally with 3.3V, and their input and output signal levels are simply made to be compatible with their external 5V environment.

The logic families HC, AHC and AC can already be operated with a supply voltage of much less than 5V. With the HC and AHC family, the supply voltage is specified down to 2V in the data book; with the AC, down to 3V. The longer delay time and the reduced drive capability are however disadvantages of using a lower supply voltage which must be

taken into account. Table 1shows several examples from the data book. In order to achieve a high speed and high drive capability despite a low supply voltage, it was necessary to develop new logic families.

2 Technology

The components in the logic families LV, LVC, ALVC and LVT and ALB were developed for a typical supply voltage of 3.3V. Four of the five families have, however, functions corresponding to those in the families with 5V supply voltage (Table 2), whereby their internal circuit structures and electrical characteristics conform basically to those of their 5V "relatives".

	LV	LVC	ALVC	LVT	ALB
Corresponding family with 5V supply voltage	HC	AC	≈AC	BCT and ABT	N/A
Process	CMOS 2.0 µm	CMOS 0.8 µm	CMOS 0.6 µm	BiCMOS 0.8 µm	BiCMOS 0.6 µm
Minimum supply voltage to ensure correct operation	2V	2.7V	2.3V	2.7V	3.0V
Power on Demand	Not needed	Not needed	Not needed	✓	
Bus Hold		LVCH	ALVCH	LVTH	
Power-Up Tristate				LVTZ and LVTH	
Inputs TTL-compatible	✓	✓	✓	✓	✓
Inputs tolerate 5V TTL		✓		✓	
Outputs TTL-compatible	✓	✓	✓	✓	✓

Table 2: Characteristics of the families LV, LVC, ALVC, LVT and ALB

The families LV, LVC and ALVC use pure CMOS processes, and show the typical characteristics of CMOS circuits. LVT is based on the BiCMOS process technology. The input circuit and internal logic is implemented with CMOS components, and the output stage with bipolar transistors. As a result of this BiCMOS technology, the characteristics of CMOS (low static power consumption) are combined with those of bipolar technology (namely, high drive power, improved dynamic power consumption and the highest speed).

2.1 Power-on-Demand

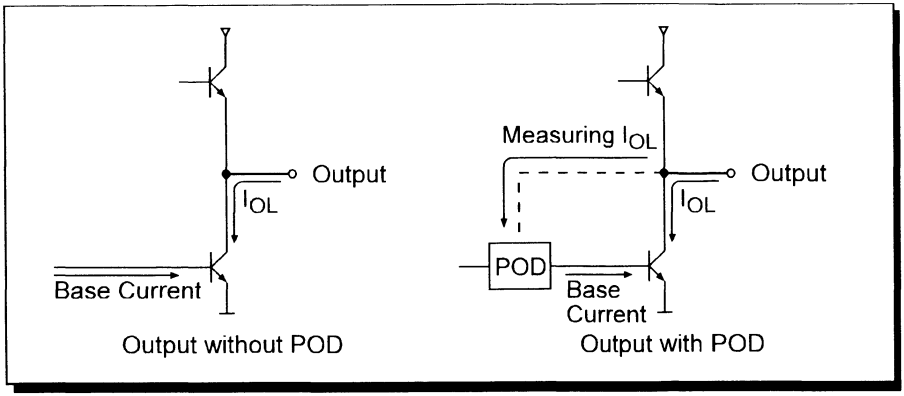


Figure 1: Output with and without Power on Demand (POD).

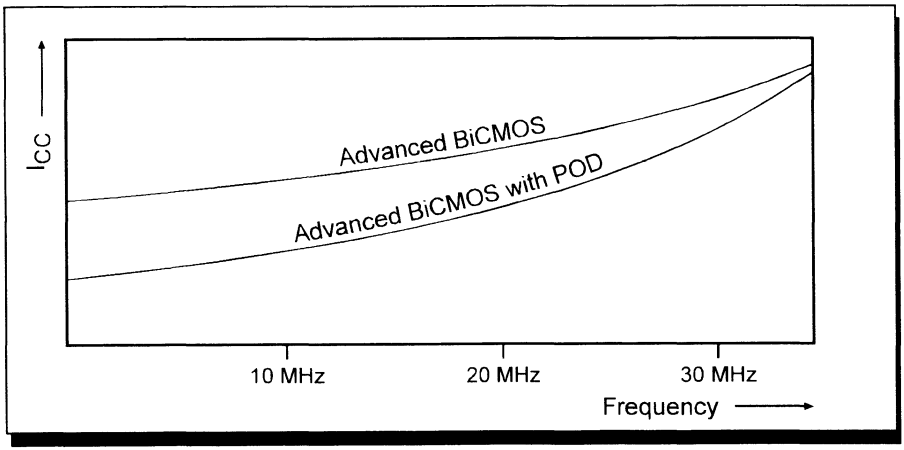


Figure 2: Supply current behavior versus frequency with and without Power-on-Demand (POD) circuit

A BiCMOS circuit, such as the LVT, has the highest power consumption when the output is in the 'L' state. The supply current is then mainly required in order to supply the Pull-Down transistor with base current. In order to reduce this current still further with battery-powered equipment, the "Power-on-Demand" (POD) circuit has been developed. This measures the current flowing into the output and then supplies the necessary base current (Figure 1). As a result of this, the supply current of the circuit I_{CCL}, and consequently the power consumption, are drastically reduced at lower frequencies (Figure 2).

2.2 Bus Hold Circuit

With fast circuits having CMOS inputs, an open input or a very slowly changing edge can cause oscillation of the component. With this oscillation the power dissipation of the component increases significantly, and under worse case condition this can result in destruction.

For this reason bus lines must always be held at a defined logic level. This is no problem with unidirectional lines, since the driver always supplies all inputs connected to it with a valid logic level. If however with bi-directional bus lines all drivers are in a high impedance state, then a voltage level will be established which is determined by the leakage currents of the components that are connected to that bus line. In this situation a defined logic level can no longer be assumed. The inputs connected to this bus line now behave as open circuit inputs, and in the worst case a destruction of the component may result.

If it is not possible to keep an inactive state of the bus short enough that, during this period, no damaging voltages can build up, then it is usual to seek help with "pull-up" resistors or with split-resistor bus terminations, each consisting of a resistor connected to V_{CC} and GND. However, these resistors increase significantly both the loading of the outputs and the current drain of the complete system.

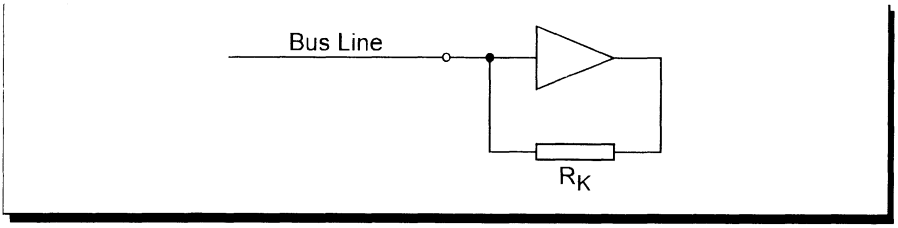


Figure 3: Bus Hold Circuit

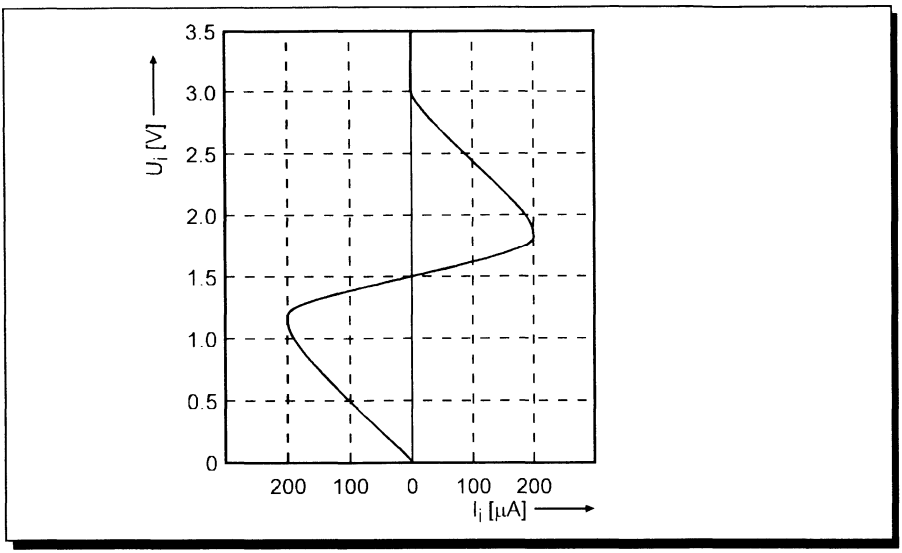


Figure 4: Typical input characteristic of a Bus Hold Circuit

A more elegant method of supplying inactive bus lines with a defined level is to make use of a so-called "Bus Hold Circuit" (Figure 3). In this circuit, the output of a non-inverting driver is fed back to the input with a resistor. In this way a bistable circuit ("LATCH") results, which is connected to the bus line. This circuit always holds the bus line during an inactive phase in the previous logic state. With an appropriate choice of the feedback resistor an extremely low loading of the bus line results, and a possible charge transfer of the bus line when entering the inactive state can also be avoided. The characteristics of a Bus Hold Circuit are shown in Figure 4. A detailed discussion of the Bus Hold Circuit can be found in the Application Report "Bus Hold Circuits" [1] from TEXAS INSTRUMENTS.
In order to reduce the necessary component count, TEXAS INSTRUMENTS has integrated the Bus Hold Circuit into the inputs of the LVC-Widebus™, ALVC and LVT families.

2.3 Power-Up-Tristate

If in an electronic system it is necessary to switch off the supply voltage to individual subsystems, whilst the complete system continues to operate normally, then the following circuit properties are necessary:

- ⇨ The inputs and outputs of all circuits that are connected to a bus and switched off must be at high impedance, if the supply voltage is 0V.
- ⇨ If the supply voltage goes below the value necessary to ensure correct operation of the component, then the output must be at high impedance. This is necessary in order not to interfere with the active part of the system during the power-up or power-down phase.

All purely bipolar outputs with NPN transistors fulfill the requirement of being at a high impedance when the supply voltage is switched off, since a bipolar transistor is only at low impedance when a base current is flowing, or a diode path is connected in a forward direction. A supply voltage of 0V can however no longer supply a base current, and with an NPN pull-up transistor all diode paths are blocked. Also, since the breakdown voltages of these diodes will not be reached with TTL signals, these outputs will be at a high impedance.
Additional steps must be taken in order to fulfill the second requirement of a defined power-down behavior. With the LVTZ and LVTH components a special circuit (Power-Up Tristate) has been incorporated which controls the supply

voltage. If the supply voltage falls below about 1.8V, then the output stages will be at a high impedance. In this way a defined power-down and power-on behavior is assured.

2.4 CMOS Pull-Up

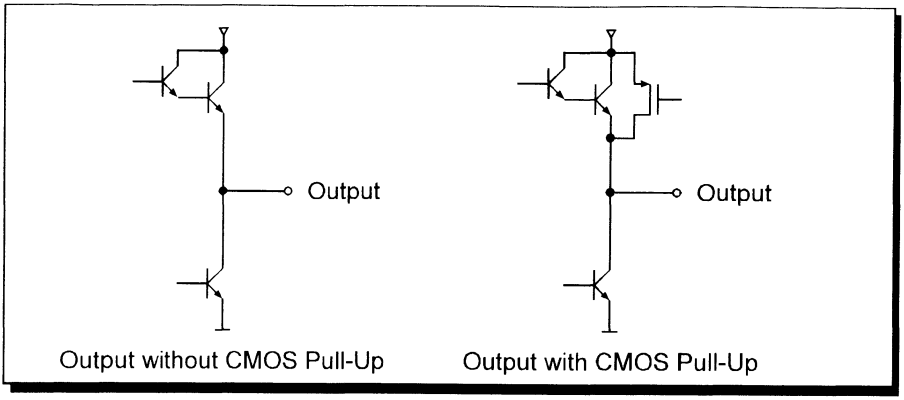


Figure 5: LVT output with and without CMOS pull-up

A bipolar TTL output stage, as shown in Figure 5, has the property that, with a 5V supply voltage in the HIGH state, an output voltage of a maximum of

$$V_{CC} - (2 \times V_{BE}) = 5V - (2 \times 0.7V) = 3.6V$$

can be reached. If an output stage of this kind is used with a 3.3V supply voltage, then the maximum possible level is

$$V_{CC} - (2 \times V_{BE}) = 3.3V - (2 \times 0.7V) = 1.9V$$

Since no TTL compatible output level can be attained with $V_{oh} = 1.9V$, an additional parallel CMOS pull-up transistor has been incorporated in the LVT family (Figure 5). This transistor allows an output voltage of almost V_{CC}, whilst the bipolar transistor takes over the high currents during the switching process. In this way, the bipolar output stage shows 'RAIL-TO-RAIL' switching behavior, and is compatible with the logic levels of the 5V TTL families and the 3.3V CMOS components.

The newer generation of bipolar output stages (ABT and LVT) are also supplied with an auxiliary CMOS transistor parallel to the bipolar pull-down transistor. The reason for this is not to extend the voltage swing, but to improve the switching performance, mostly with respect to switching speed.

2.5 Analog Buffer/Driver Circuit ALB

One feature of ALB devices is that analog circuitry in order to achieve maximum speed of the digital driver. As shown in Figure 6, every digital circuit operates with an input threshold voltage, which triggers an output signal change whenever that threshold is crossed in either direction. There is one disadvantage however, in that a certain delay t_a occurs until the rising input signal edge has reached this threshold. The driver reacts only after this threshold has been crossed, and after another delay t_b will toggle the output into the opposite state. In addition to the propagation delay of the driver there is another time t_c that passes until the rising output signal edge has reached the threshold. The cumulative propagation delay of the driver circuit then calculates as follows:

$$t_d = t_a + t_b + t_c$$

In an analog driver circuit the output state will change immediately with any voltage change at the input, even when this voltage swing is not within the range of the threshold voltage. The propagation delay t_a of digital circuits (see Figure 6) therefore does not occur, which reduces the device propagation delay to

$$t_d = t_b + t_c$$

In this case the waveform of the input signal is directly transferred to the output. The control signals of ALB circuits such as OUTPUT ENABLE are implemented as TTL-compatible digital inputs and switch at a threshold voltage of 1,5V.

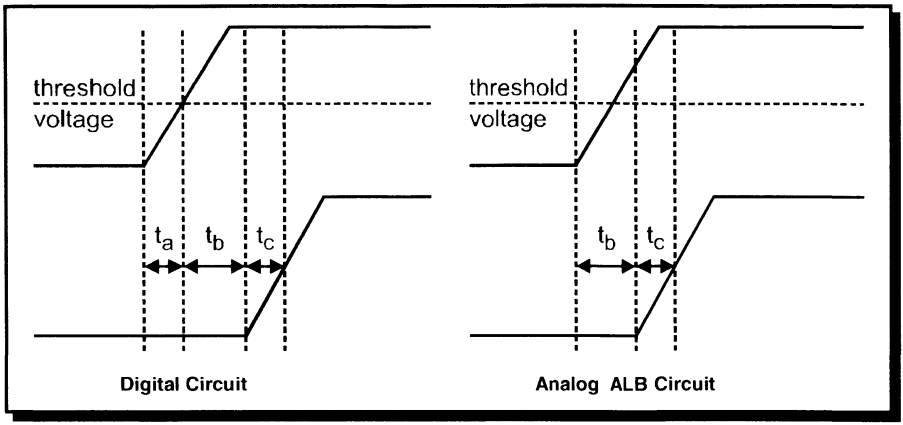


Figure 6: Speed comparison of a conventional digital circuit to a linear circuit as used in ALB devices

2.6 ESD Protection Circuits at the Inputs and Outputs

2.6.1 LV-Family

As a protection against electrostatic discharge (ESD = ELECTROSTATIC DISCHARGE) the circuits in the LV family from TEXAS INSTRUMENTS are provided with protective circuitry at the inputs and outputs (Figure 7):

- ⇨ The inputs are protected against positive overvoltages by a diode to V_{CC}; two NPN transistors provide protection against negative overvoltages. An additional resistor at the input limits the input current.
- ⇨ The protection of the outputs against positive and negative overvoltages is provided by two diodes, one connected to V_{CC} and one to GND.

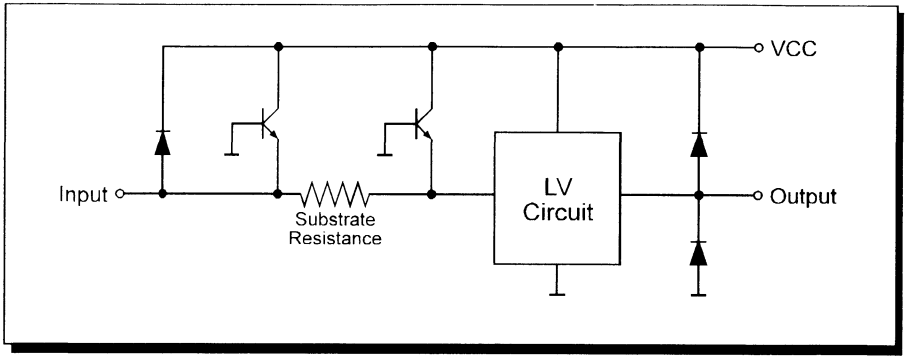


Figure 7: ESD protection circuitry in LV circuits

2.6.2 LVC-Family

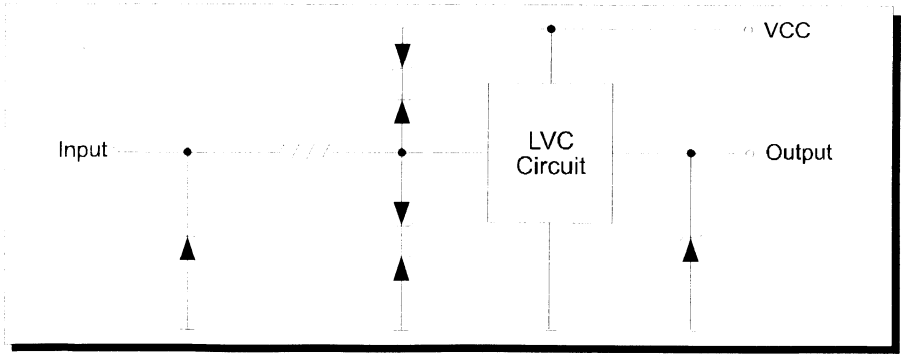


Figure 8: ESD protection circuitry in LVC circuits

With LVC components the following precautions have been taken to provide protection of the circuits against electrostatic discharge - see Figure 8:

- The protection of the CMOS inputs against positive overvoltages is provided by two Zener diodes (Z-Diode) connected back-to-back in series. Negative overvoltages are limited by a Z-Diode and also by Z-Diodes connected back-to-back in series.
- The protection of the outputs against positive and negative overvoltages is assured by a diode to V_{CC} and a Z-Diode to GND.

2.6.3 ALVC-Family

The ESD protection of ALVC devices is accomplished by following measures (Figure 9):

- A Z-Diode and two back-to-back Z-Diodes in series undertake the protection of the CMOS inputs against positive overvoltages. Negative overvoltages are limited by a Z-Diode, and also by back-to-back Z-Diodes in series.
- The protection of the outputs against positive and negative overvoltages is provided by a diode to V_{CC} and a Z-Diode to GND.

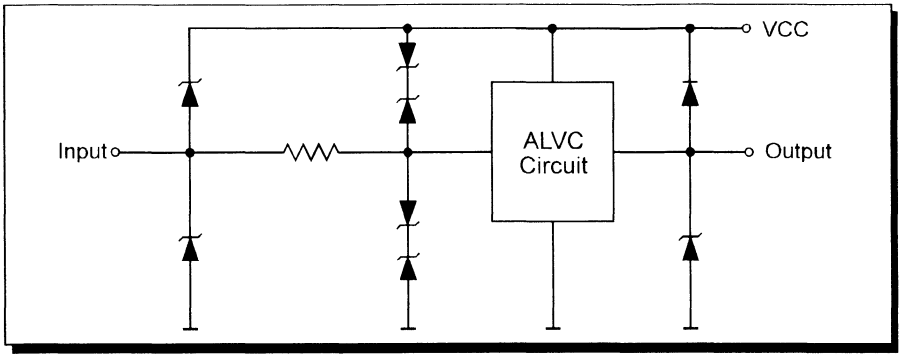


Figure 9: ESD protection circuitry in ALVC circuits

2.6.4 LVT-Family

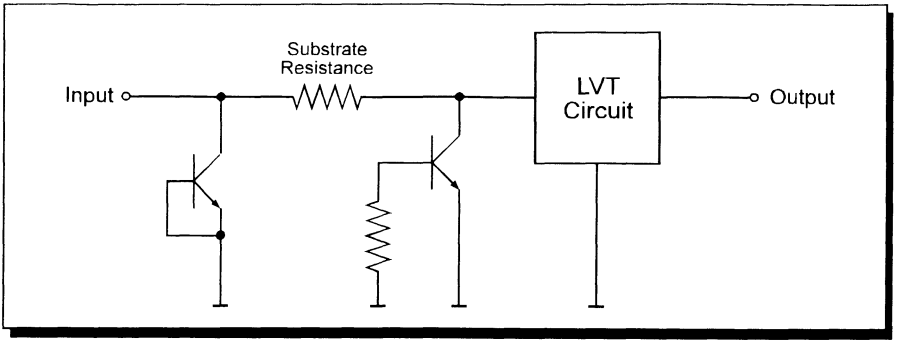


Figure 10: ESD protection circuitry in LVT circuits

LVT components are protected against electrostatic discharge with the following circuitry (Figure 10):

- ⇨ The protection of the CMOS inputs is provided by two NPN transistors. An additional resistor at the input limits the input current.
- ⇨ ESD protection is not necessary for the high-power transistors in the bipolar output stage.

2.6.5 ALB-Family

The ESD protection of ALB components closely resembles that of the ALVC family (Figure 11):

- ⇨ A diode to GND and a diode to V_{CC} undertake the protection of the CMOS inputs against positive overvoltages.
- ⇨ The protection of the outputs against positive and negative overvoltages is provided by a diode to V_{CC} and a Z-Diode to GND.

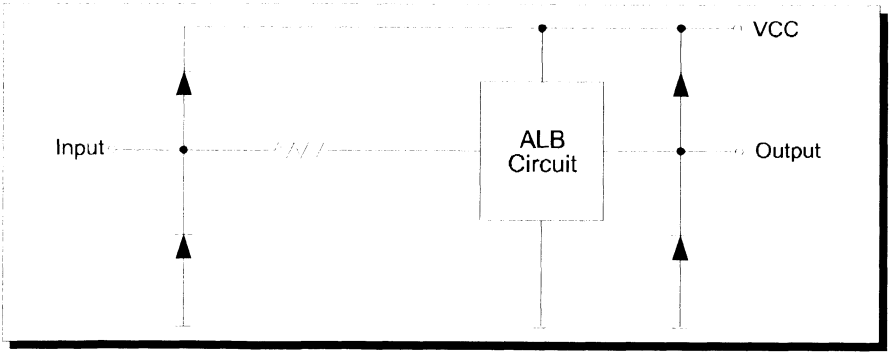


Figure 11: ESD protection in ALB circuits

3 Electrical Behavior

The electrical characteristics of the families LV, LVC, ALVC and LVT are basically similar to those of their 5V "relatives" (Table 3). ALB circuits provide analog circuitry see chapter 2.5) and therefore have no counterpart within the 5V families.

		LV	LVC	ALVC	LVT	ALB
V_{CC}		2.7V..5.5V	2.7V..3.6V	2.3V..3.6V	2.3V..3.6V	3.0V..3.6V
Input Threshold Voltage		V_{CC} / 2 typ.=1.65 V	V_{CC} / 2 typ.=1.65 V	V_{CC} / 2 typ.=1.65 V	1.4V	None
Output Voltage	V_{OH}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_i - 0.2 V
	V_{OL}	0V	0V	0V	0V	V_i + 0.2 V
Output Current	I_{OH}	-8 mA	-24 mA	-24 mA	-32 mA	-25 mA
	I_{OL}	8 mA	24 mA	24 mA	64 mA	25 mA
Inputs and Outputs tolerate 5 V			✓		✓	
Power on Demand		Not Needed	Not Needed	Not Needed	✓	
Bus Hold			LVCH	ALVCH	LVTH	
Power-Up-Tristate					LVTZ and LVTH	
Maximum Static Current Consumption	I_{OH}	20 µA	20 µA	40 µA	190 µA	5.6 mA per Buffer
	I_{OZ}	20 µA	20 µA	40 µA	190 µA	0.8 mA
	I_{OL}	20 µA	20 µA	40 µA	5 mA	5.6 mA per Buffer
Typical Propagation Delay		9.0 ns	4.0 ns	2.2 ns	2.4 ns	
Maximum Propagation Delay		14.0 ns	6.5 ns	4.0 ns	3.9 ns	

Table 3: Typical electrical characteristics of a Bus Driver

3.1 Inputs and Outputs

3.1.1 Switching Threshold

Whereas the LV, LVC and ALVC families (being pure CMOS) show the voltage levels, which are typical for CMOS, the LVT has been designed as a BiCMOS family with TTL-compatible voltage levels. Figure 12 shows the definitions of the input and output levels together with the typical switching thresholds of the inputs.

Due to its analog circuit technique (see chapter 2.5), an ALB device does not have an input threshold voltage. The input signal is amplified by an analog circuitry, and each input voltage change translates directly to a corresponding change in output level. When these inputs are driven by TTL-compatible logic such as LVT or the 5-Volt TTL families, then the ALB device will correspond with TTL-compatible signal swings.

Table 4 explains which logic families are suitable for driving the inputs of which other families.

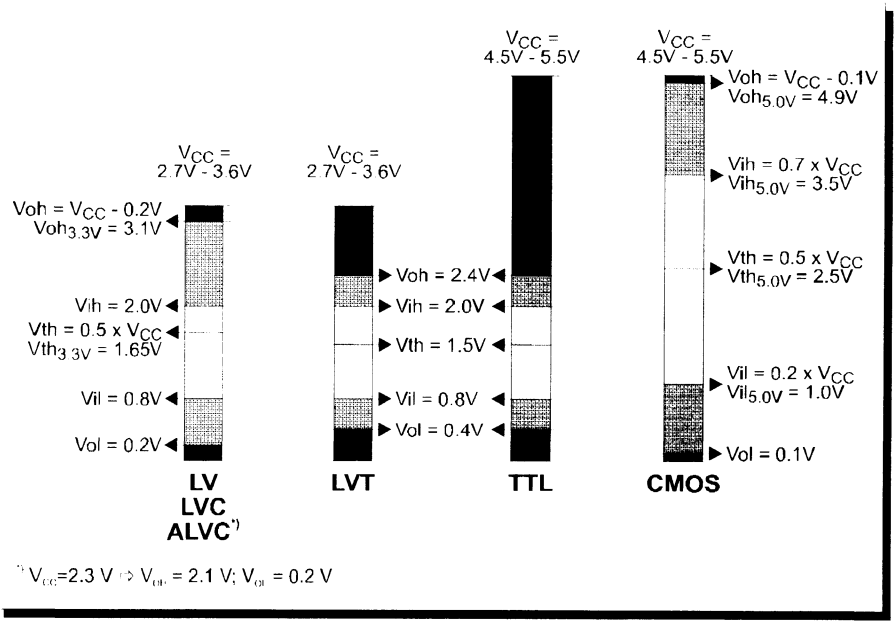


Figure 12: Definition of the voltage level for inputs (V_{il}, V_{ih}), outputs (V_{ol}, V_{oh}) and the switching threshold (V_{th}), of the families LV, LVC, ALVC, LVT and ALB in comparison with TTL-compatible and 5V CMOS families.

		Output						
		LV	**LVC**	**ALVC**	**LVT**	**ALB**	**TTL**	**5V CMOS**
Input	**LV**	✓	✓	✓	✓	✓	✓	level shifter
	LVC	✓	✓	✓	✓	✓	✓	✓
	ALVC	✓	✓	✓	✓	✓	✓	level shifter
	LVT	✓	✓	✓	✓	✓	✓	✓
	ALB	✓	✓	✓	✓	✓	✓	level shifter
	TTL	✓	✓	✓	✓	✓	✓	✓
	5V CMOS	level shifter	pull-up to 5V	level shifter	pull-up to 5V	level shifter	pull-up to 5V	✓

Table 4: Compatibility of the inputs and outputs of the logic families LV, LVC, ALVC, LVT and ALB in comparison with TTL-compatible and 5V CMOS families.

3.1.2 Connection to 5V CMOS

The connection of the LOW VOLTAGE families to 5V CMOS circuits is only possible in one direction: that is, 5V CMOS outputs can drive LVC and LVT inputs, but none of the LOW VOLTAGE families is able to supply the necessary voltage level for 5V CMOS inputs. For this reason the SN74LVC4245, SN74ALVC164245 and SN74ALVCC4245 SN74ALVC164245 were developed: these are special components for use as an interface between LOW VOLTAGE families and 5V CMOS circuits.

The SN74LVC4245 and SN74ALVC164245 establish a connection between 3.3V and 5V systems. The pin layout was designed such that they are directly replaceable by the standard components SN74xxx245 and SN74xx16245 without the need for changes in PCB layout (see Figure 13). The SN74LVC4245 is designed to support both a 3.3V to 5V adaptation as well as pure 3V systems. The supply voltages connected to it define the device behavior. Applying two different supply voltages (3.3V/5V) will make the device behave like a level shifter. Using 3.3V at all V_{CC} inputs will turn it into a 3.3V bus driver circuit. This feature allows the design of printed circuit boards that operate both in 5V-CMOS and TTL compatible systems without having to replace a device.

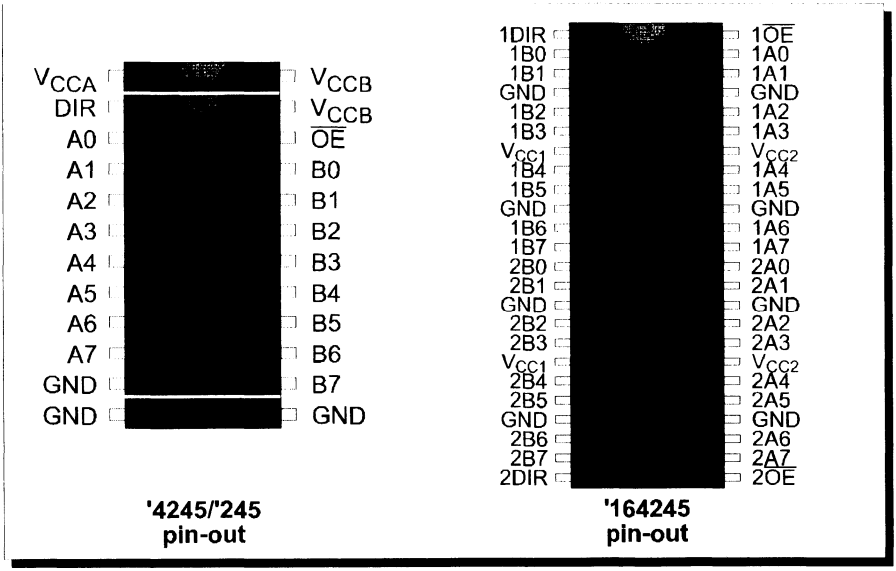


Figure 13: Pinout of SN74LVC4245, SN74xxx245 and SN74ALVC164245

3.1.3 DC Characteristics

The measurements of the output characteristics were done across a load current ranging from –200mA to +200mA. This range, however, can only be covered by means of special test conditions. Under normal operating conditions the maximum load currents as specified in the data sheets apply. During switching in dynamic mode, however, the outputs may momentarily carry currents almost as great. These current peaks do not harm the device.

3.1.3.1 DC characteristic of LV circuits

The inputs of the LV circuits (Figure 14) show the same behavior as circuits of the HC family and are influenced by the two diode paths connected to GND and V_{CC} Figure 14 and Figure 15). Accordingly, with input voltages which are negative or beyond V_{CC}, diode characteristics can be observed. 5V CMOS High-levels can not be applied to the inputs of these devices.

The outputs of the LV family clearly display a characteristic typical of its CMOS output transistors: A straight-line resistor characteristic changes with increasing voltage-drop into that of a constant current source. The diodes against V_{CC} and GND limit the voltage swing to max. V_{CC}+0,7 V and -0,7 V

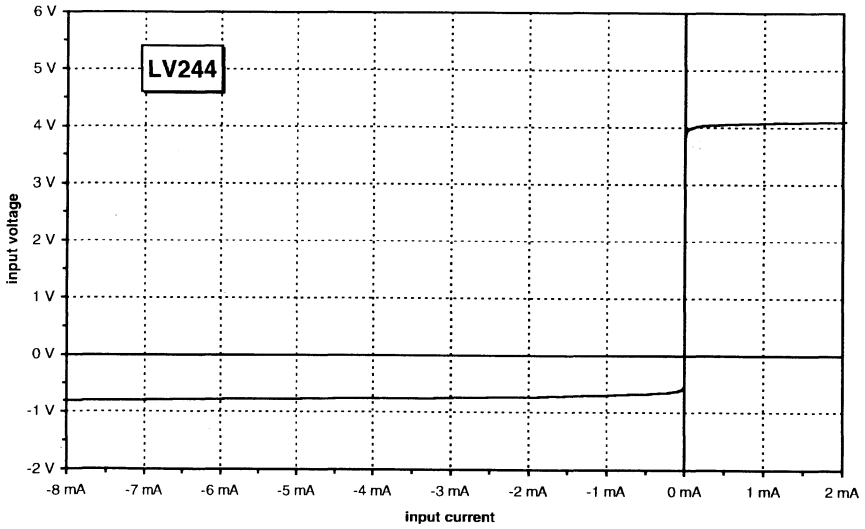


Figure 14: Input Characteristics of the SN74LV244

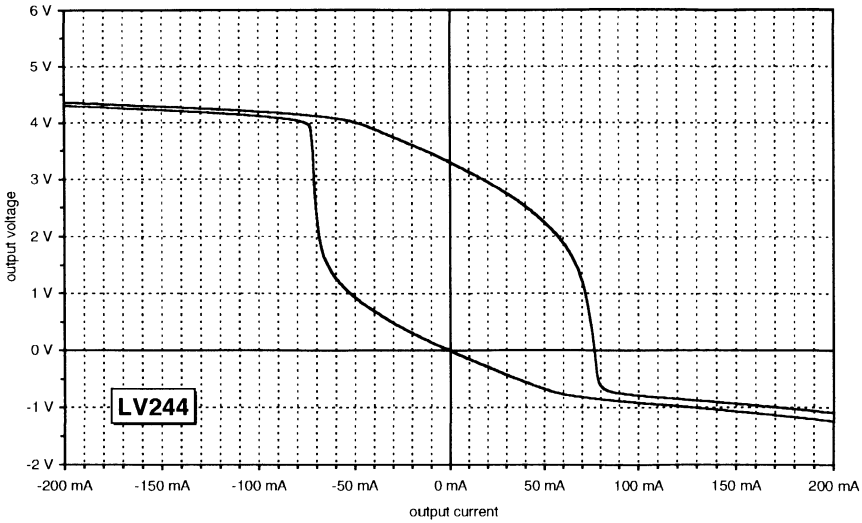


Figure 15: Output Characteristics of the SN74LV244

3.1.3.2 DC Characteristic of LVC Circuits

The input characteristic of LVC-series devices is determined by the diode characteristic of its ESD protection circuitry, however only at negative voltages. The positive voltage range of LVCH circuits between 0V and 3V is defined by the bus-hold circuit (similar to LVT, see Figure 20). LVC circuits have no bus-hold circuitry and therefore always remain at high-impedance for voltages above 0V. At higher input voltages both the LVC and LVCH circuits remain at high-impedance.

The outputs of LVC-family devices behave like typical CMOS circuits. Since these do not have the diode to V_{CC} as their LV counterparts, the positive voltages are not limited to V_{CC} + 0.7 V .

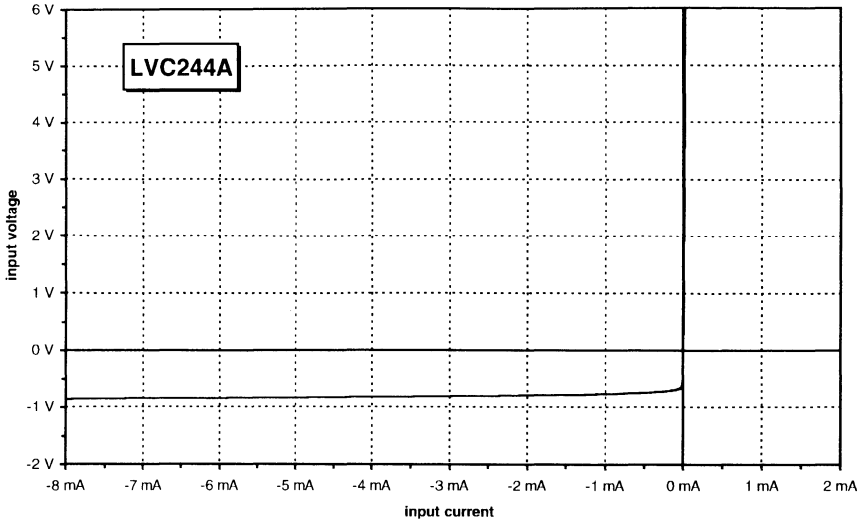


Figure 16: Input Characteristic of the SN74LVC244A

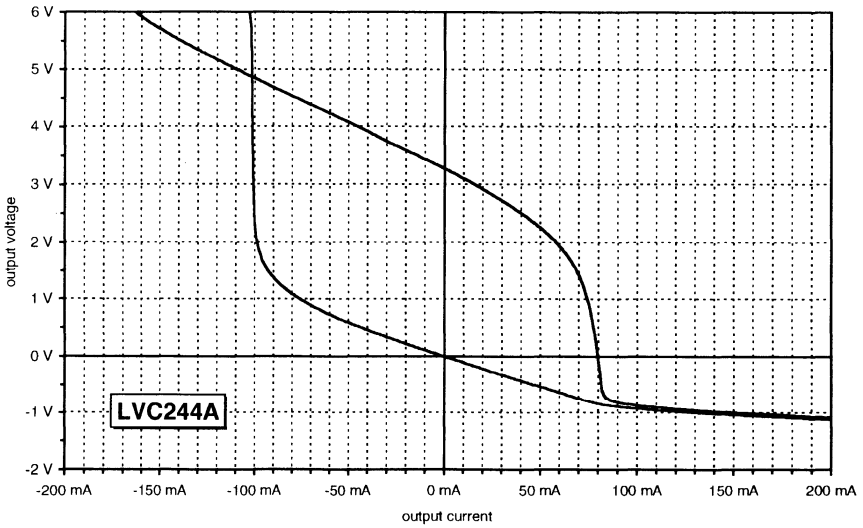


Figure 17: Output Characteristics of the SN74LVC244A

3.1.3.3 DC Characteristic of ALVC Circuits

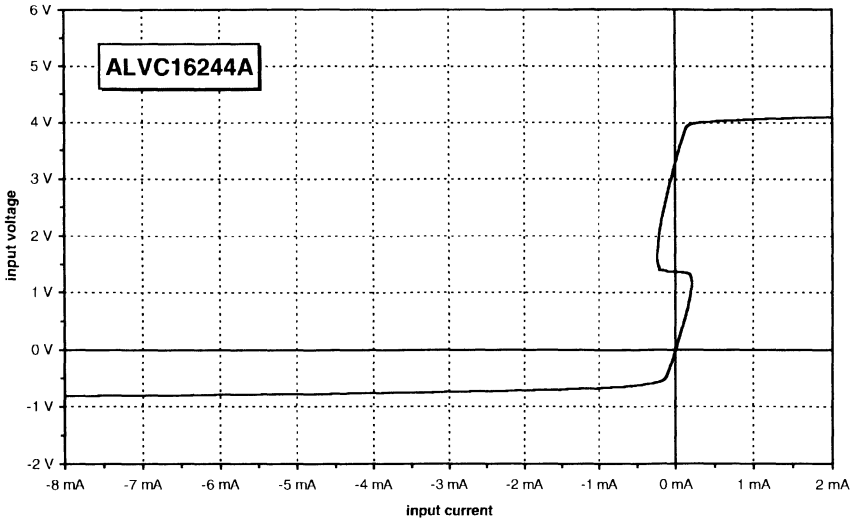


Figure 18: Input characteristic of the SN74ALVC16244A

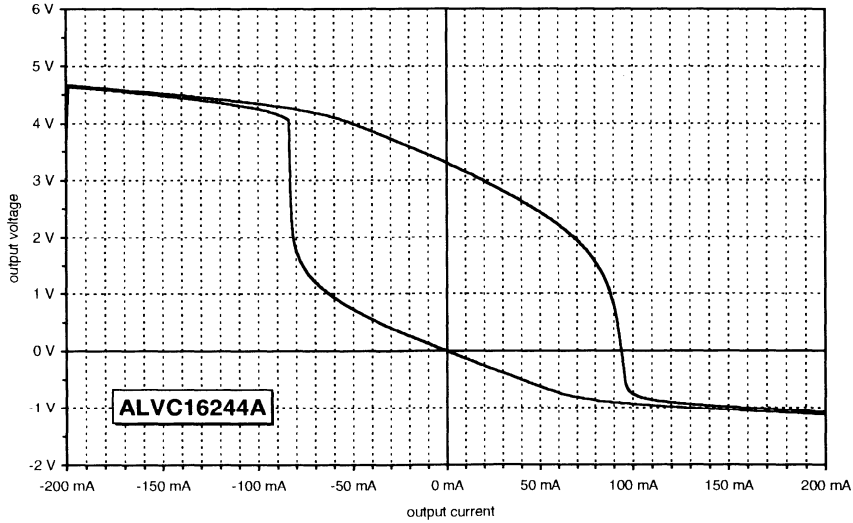


Figure 19: Output Characteristic of the SN74ALVC16244A

The diode paths to GND and V_{CC} determine the output characteristic of the ALVC devices (Figure 18and Figure 19) and show the same behavior as circuits of the LV family. Accordingly, negative input voltages and voltages beyond V_{CC} each display a diode characteristic. 5V CMOS High-levels may also not be applied to these circuits. The input clearly displays a bus-hold circuit characteristic for input voltages between)V and V_{CC}.

3.1.3.4 DC Characteristic of LVT Circuits

The bus-hold circuitry is the typical feature of LVTH inputs (Figure 20). Diodes have been included both at inputs and outputs only to GND. Input voltages beyond V_{CC} therefore pose no problem for LVT circuits. At High-level above –80 mA the bipolar output of the LVT circuit (Figure 21) displays a CMOS characteristic curve typical of the CMOS Pull-up transistor (see chapter 2.4). The characteristic of a bipolar transistor can be observed at currents below –80 mA and at low-level.

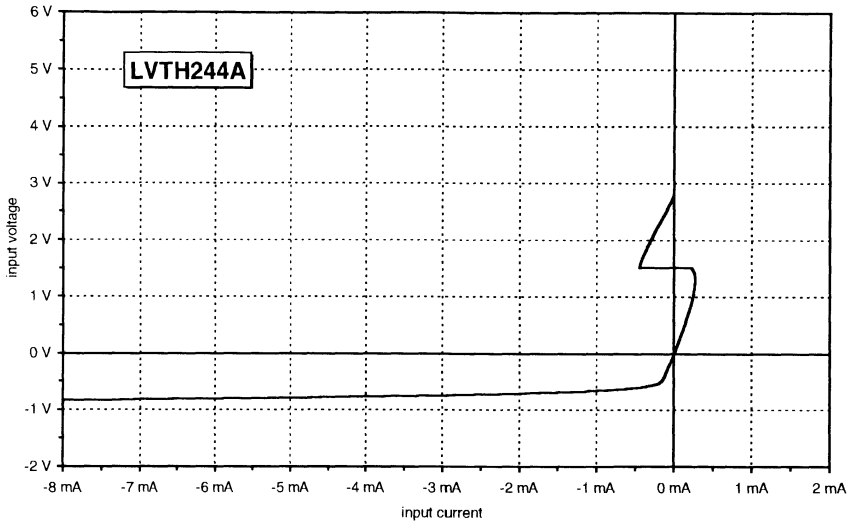


Figure 20: Input characteristic of the SN74LVTH244A

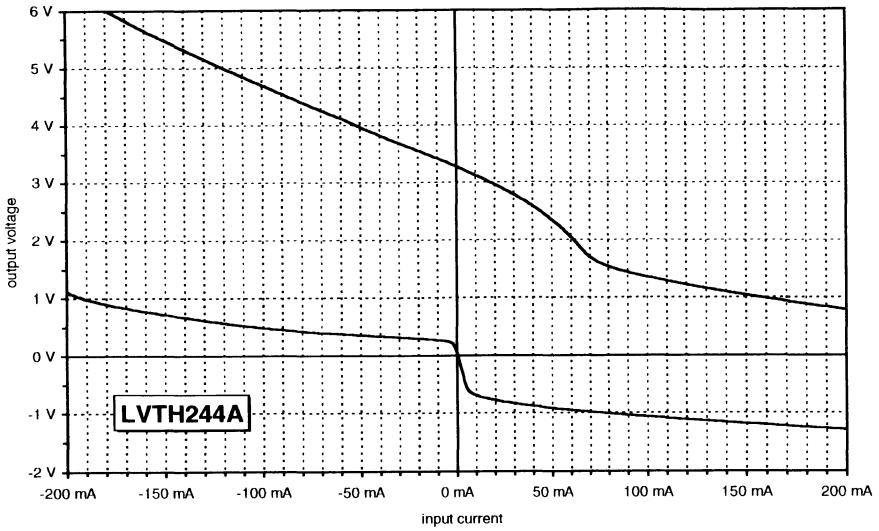


Figure 21: Input characteristic of the SN74LVTH244A

3.1.3.5 DC-Characteristic of ALB Circuits

Due to their analog circuitry, the characteristics of ALB devices differ from those of the popular bipolar device families. The influence of diodes against GND and V_{CC} can also be observed at the inputs (Figure 22). The outputs display the typical characteristic curves of a pure bipolar output stage with diodes to V_{CC} and GND (Figure 23).

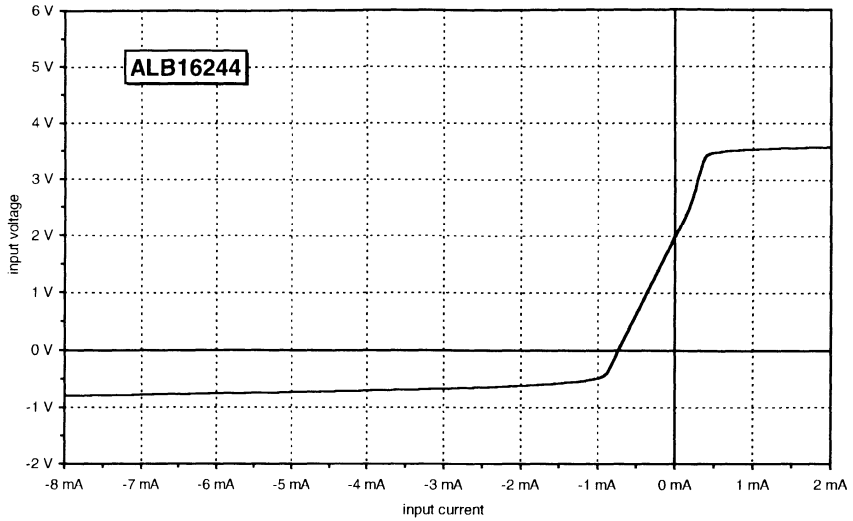


Figure 22: Input characteristic of the SN74ALB16244

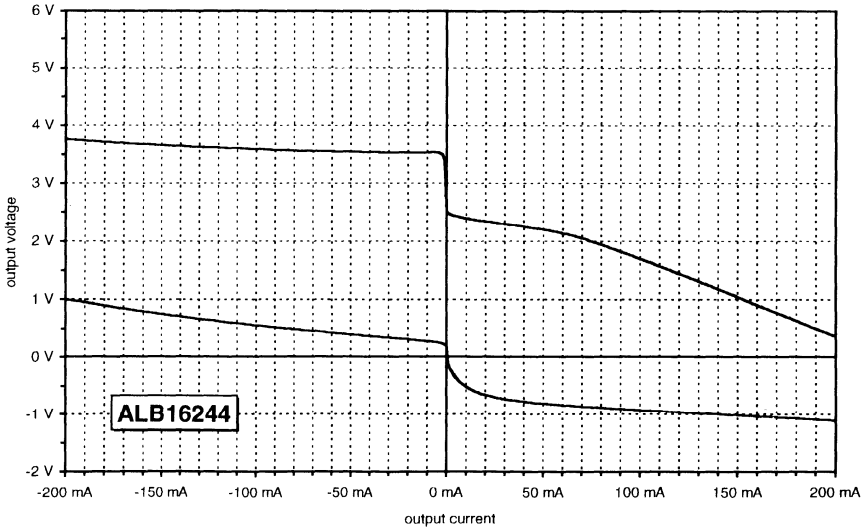


Figure 23: Output Characteristic of the SN74ALB16244

3.2 No Supply Voltage

In systems where the supply voltage is sometimes switched off, the behavior of the component at V_{CC} = 0V is of interest. The five circuit families show significantly different behavior in this respect.

3.2.1 LV without Supply Voltage

The ESD protection circuitry used with LV circuits (Figure 7) has the result that the voltages at the inputs and outputs never can be higher than one diode forward voltage drop above the voltage of the supply. With a supply voltage of 0V it is therefore not possible to apply a voltage of more than about +0.7V to the inputs and outputs, without thereby damaging the component (Figure 24 and Figure 25). LV circuits are therefore not suitable fur use in systems where the supply voltage is sometimes switched off.

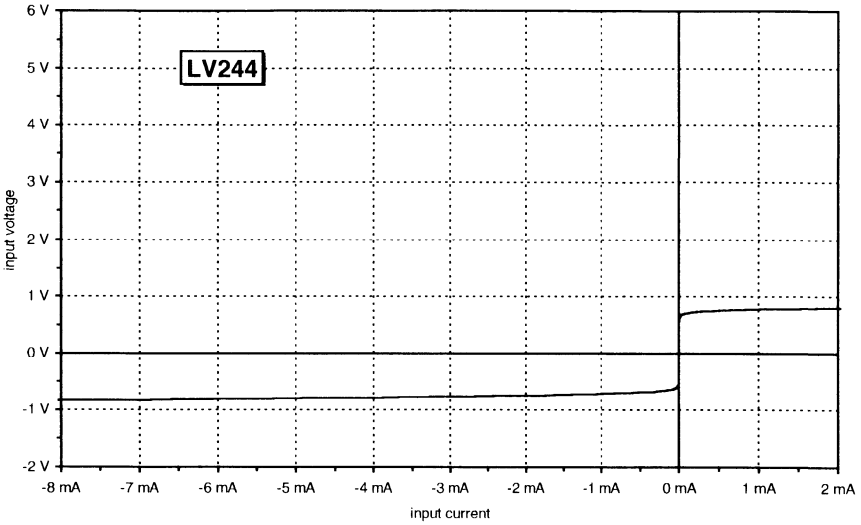


Figure 24: Input Characteristics of the SN74LV244 at V_{CC} = 0V

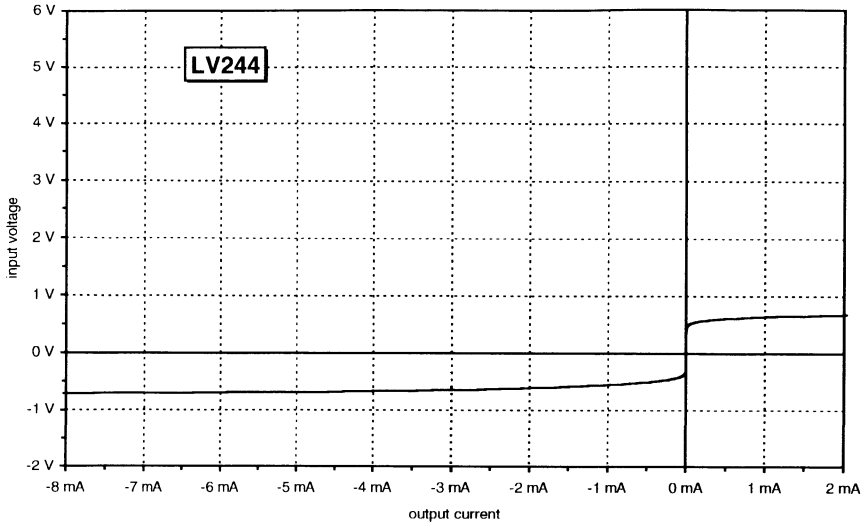


Figure 25: Output Characteristics of the SN74LV244 at V_{CC} = 0V

3.2.2 LVC without Supply voltage

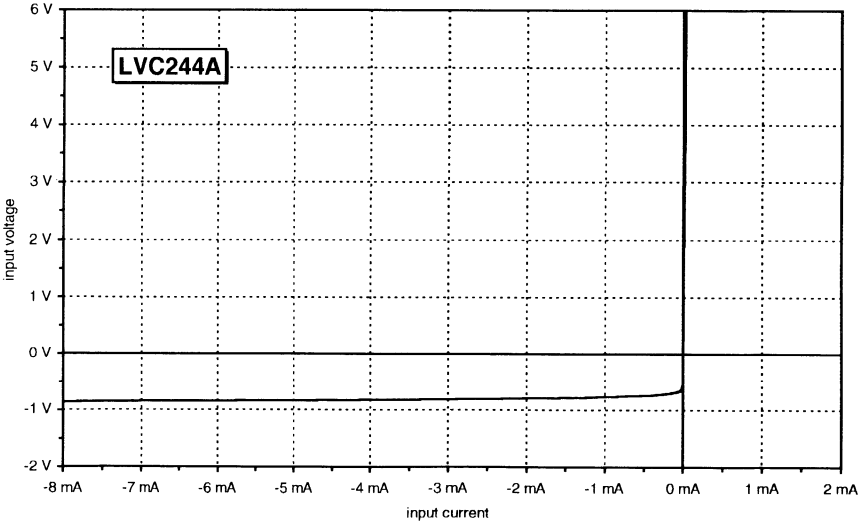


Figure 26: Input Characteristic of the SN74LVC244 at V_{CC} = 0V

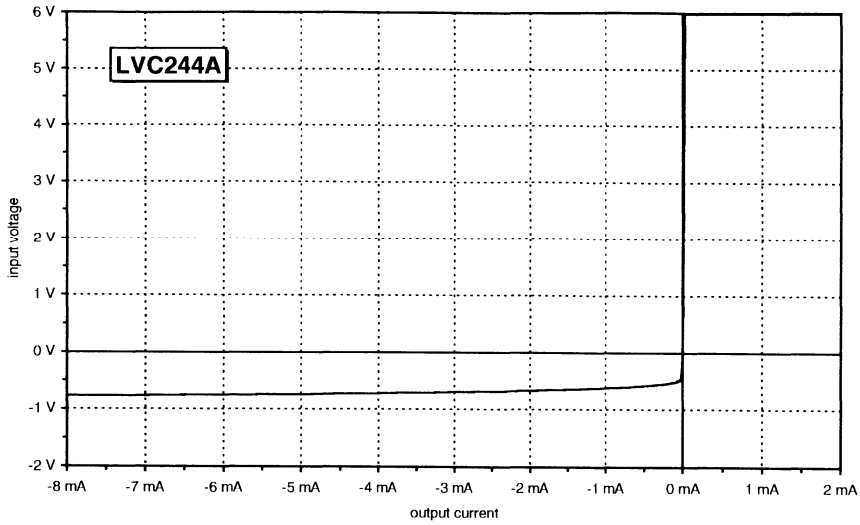


Figure 27: Output Characteristic of the SN74LVC16244 at V_{CC} = 0V

The ESD protection circuitry used for the inputs and outputs has no diode paths connected to Vcc, in contrast to the LV circuits. The inputs and outputs are therefore at high impedance in a positive voltage range (Figure 26 and Figure 27). The LVC devices are therefore suitable for systems that are partially switched off.

3.2.3 ALVC without Supply Voltage

As a result of the diode paths to VCC and GND within its ESD protection circuitry (Figure 9), the ALVC family has the same behavior as the LV family. At a supply voltage of 0V it is not possible to apply a voltage of more than about +0.7V to the inputs or outputs without damaging the component (Figure 28 and Figure 29). ALVC circuits must therefore not be used in systems where the supply voltage is sometimes switched off.

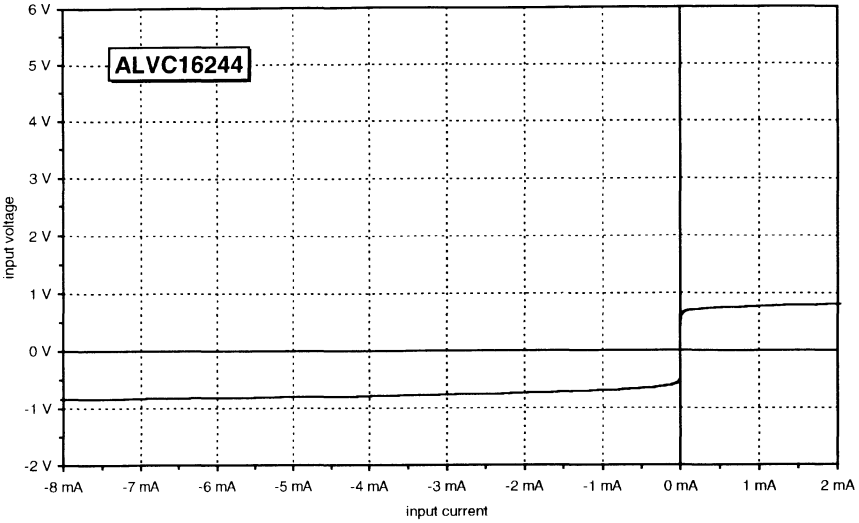


Figure 28: Input Characteristic of the SN74ALVC16244A at V_{CC} = 0V

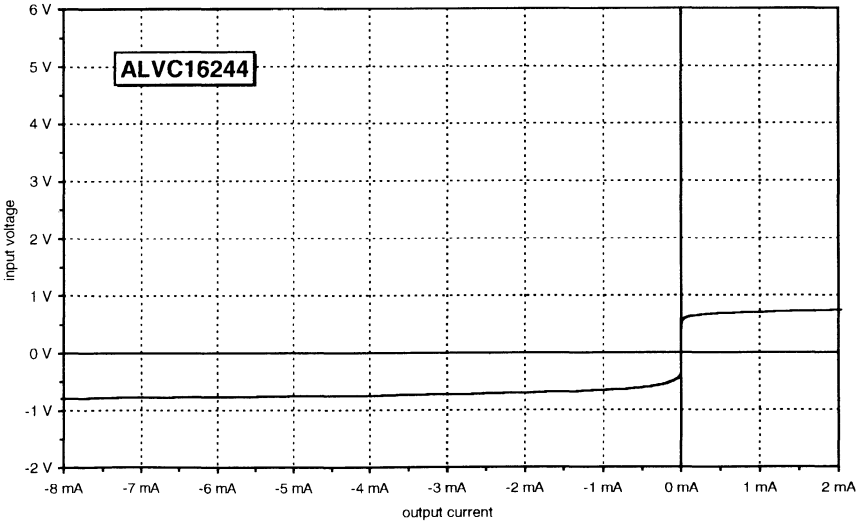


Figure 29: Output Characteristic of the SN74ALVC16244A at V_{CC} = 0V

3.2.4 LVT without Supply Voltage

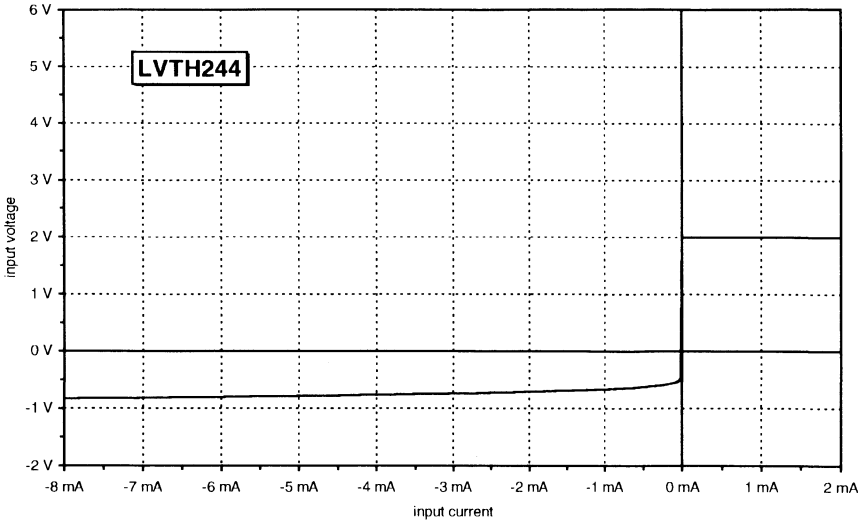


Figure 30: Input Characteristic of the SN74LVTH244A at V_{CC} = 0V

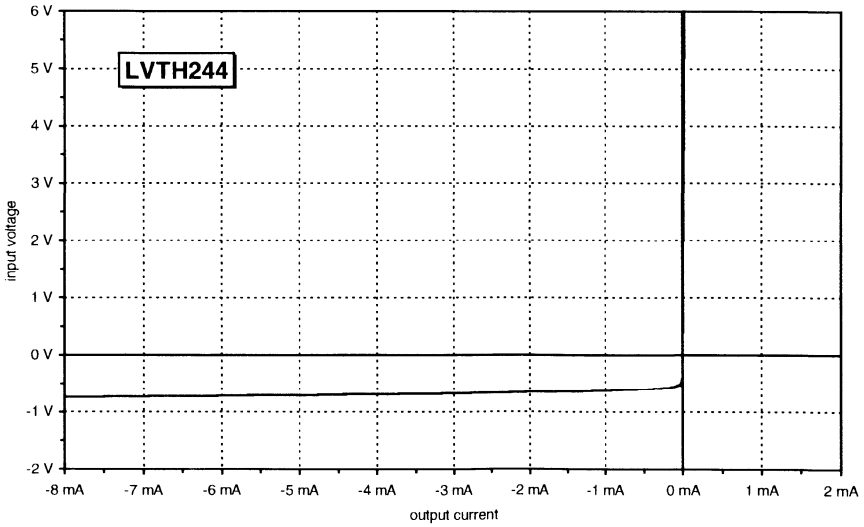


Figure 31: Output Characteristic of the SN74LVTH244A at V_{CC} = 0 V

As is typical with CMOS, the inputs with positive voltages are at a high impedance, since the ESD protection circuitry will also not be at a low impedance under these conditions (Figure 30). As a result of the bipolar output stage the outputs of LVT circuits will be at a high impedance, if the supply voltage is 0V (Figure 31). The LVTZ parts are provided with a Power-Up Tristate circuit, which puts the outputs in a high impedance state when V_{CC} drops below a level where proper operation can no longer be maintained. A defined behavior of the component is therefore also assured during the period when the supply voltage is being switched on and off.

3.2.5 ALB Without Supply Voltage

ALB circuits are supplied with diode paths to V_{CC} and GND. They are therefore not suitable for partially powered-down systems (Figure 32 and Figure 33).

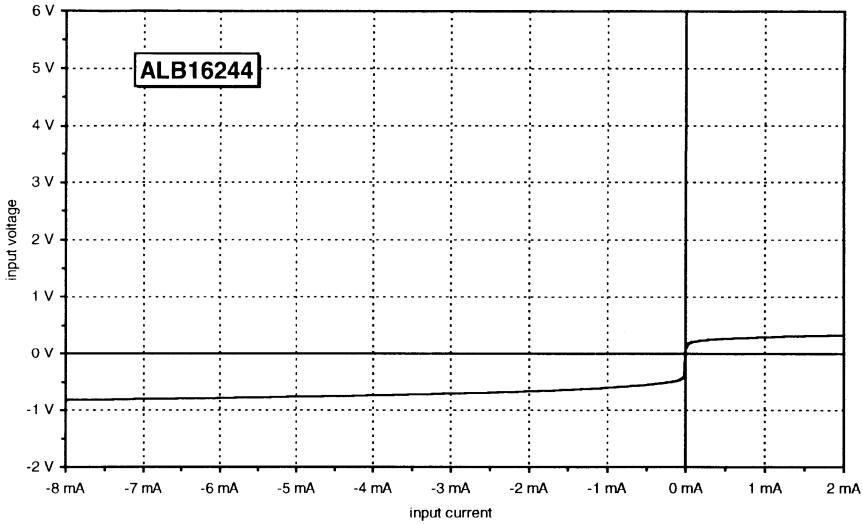


Figure 32: Input characteristic of the SN74ALB16244 at V_{CC} = 0V

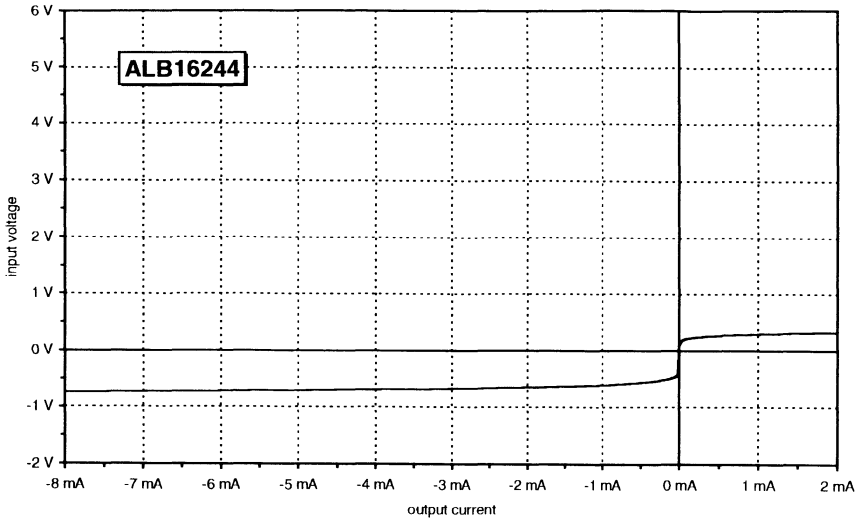


Figure 33: Output characteristic of the SN74ALB16244 at V_{CC} = 0V

3.3 Power Consumption

The power consumption of digital CMOS circuits increases linearly with increasing clock rates. This increase is much less significant with bipolar circuits. As the LVT is a BiCMOS family, and therefore has both CMOS and bipolar elements, this family displays a mixed behavior.

3.3.1 Static Power Consumption

Table 5 uses the '244 as an example to show the static power consumption of the four families LV, LVC, ALVC, LVT and ALB as it is guaranteed in the data sheets. The typical current consumption of these components is considerably less than this guaranteed value.

The CMOS feature of an extremely low static power consumption is demonstrated clearly by the three representatives of the pure CMOS families: LV244, LVC244A and ALVC16244A. Their supply current is a maximum of 10µA to 500µA, corresponding to a maximum power consumption of 33 µW to 1.65 mW. If the outputs are in a high impedance state, then their power consumption is reduced to a maximum of 33 µW to 72 µW.

As a typical representative of a BiCMOS family, the 'LVT244A shows a significantly higher static power consumption than the pure CMOS families. On the other hand, the maximum value of 16.5 mW is still comparatively low. With high impedance outputs, the maximum power consumption is reduced to 627 µW. In comparison, the maximum power consumption of a pure 5V bipolar device such as the SN74F244 ranges at astronomical values between 400 mW and 450 mW.

Due to its linear circuit technology the static power consumption of an ALB16244 device is far above that of digitally operating circuits. This is the price to pay for the uncompromising circuit design optimized for maximum speed. At high speeds, however, the dynamic power consumption of ALB circuits remains less than that of other circuit families (see Figure 40).

	Test Conditions		LV244	LVC244A	ALVC16244A	LVTH244A	ALB16244
I_{CC}	V_{CC} = 3.6V	Outputs high	max. 20 µA	max. 10 µA	max. 40 µA	max. 190 µA	max. 89.6 mA
	$V_I = V_{CC}$ or GND	Outputs low	max. 20 µA	max. 10 µA	max. 40 µA	max. 5 mA	max. 89.6 mA
	I_O = 0	Outputs disabled	max. 20 µA	max. 10 µA	max. 40 µA	max. 190 µA	max. 0.8 mA
ΔI_{CC}	V_{CC} = 3.0 V to 3.6 V one input at V_{CC} - 0.6 V other inputs at V_{CC} or GND		max. 500 µA	max. 500 µA	max.500 µA	max. 200 µA	max.750 µA

Table 5: Static Power Consumption of the 'LV244, 'LVC244A, 'ALVC16244A, 'LVTH244A, and 'ALB16244

Figure 34 shows a CMOS input stage, as used in CMOS and BiCMOS circuits. If the input voltage is the same as the supply voltage, then the P channel transistor is not conducting, and almost no current flows from V_{CC} to GND. Similarly, the N channel transistor will stop conducting at an input voltage of 0V. If the input voltage is not at the same potential as the supply voltage or GND, then the transistors of this input stage will operate in a linear region, and both transistors will be more or less conducting. As a result of this situation, the power consumption in static and dynamic operation increases, if the input level is not the same as the supply voltage or the GND potential. The parameter ΔI_{CC} in data books takes this fact into account. The linear input circuitry of an ALB device significantly differs in this respect from the fully digital circuit families. The ALB supply current remains at 0 mA for all input voltages when its outputs are switched into high impedance. The corresponding typical characteristics are shown in Figure 35 to Figure 39.

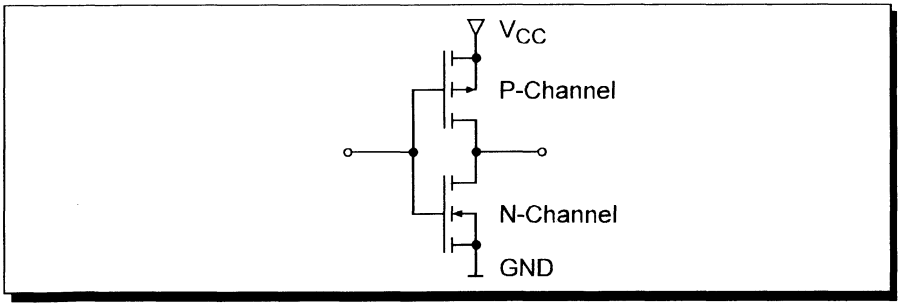


Figure 34: CMOS or BiCMOS input stage circuit

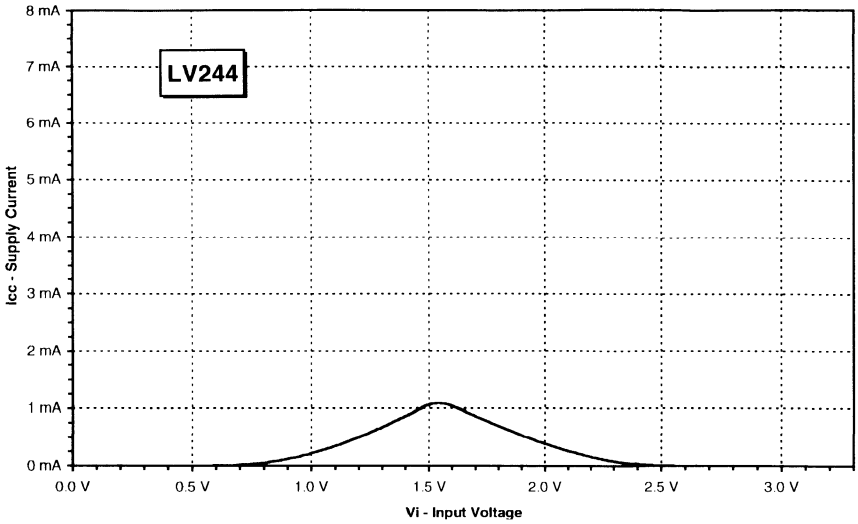


Figure 35: Current consumption vs. input voltage of LV

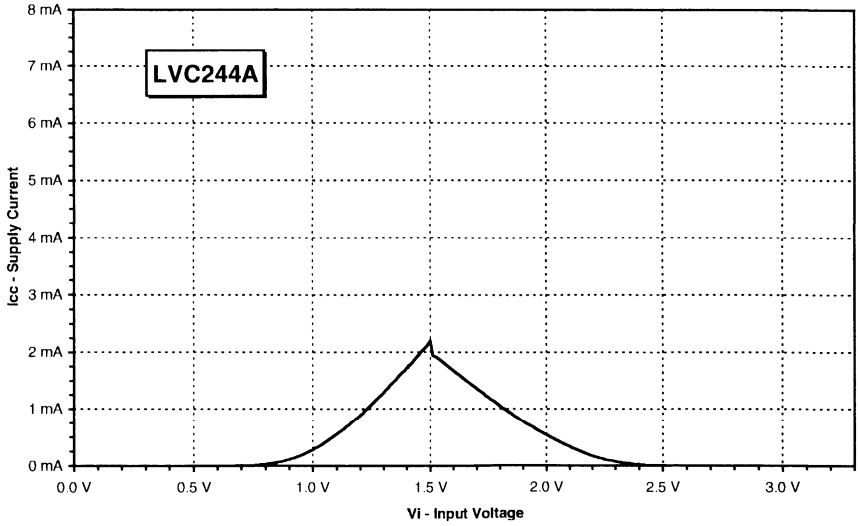


Figure 36: Current consumption vs. input voltage of LVC

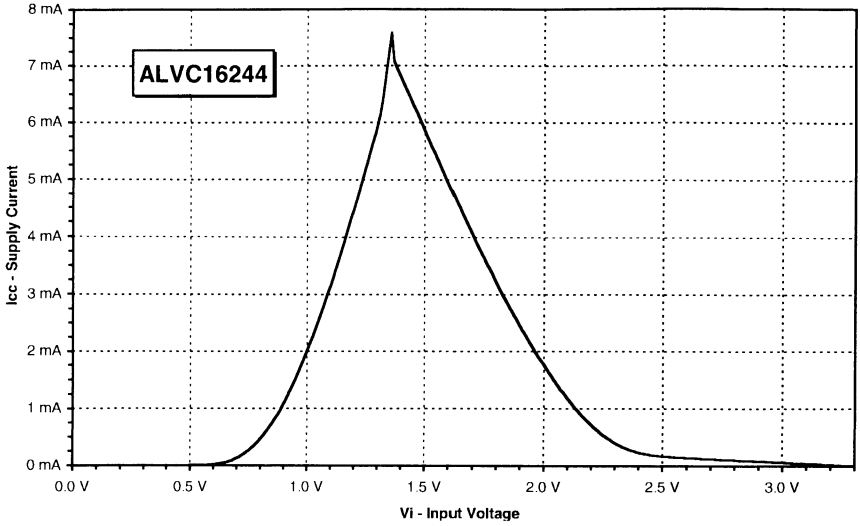


Figure 37: Current consumption vs. input voltage of ALVC

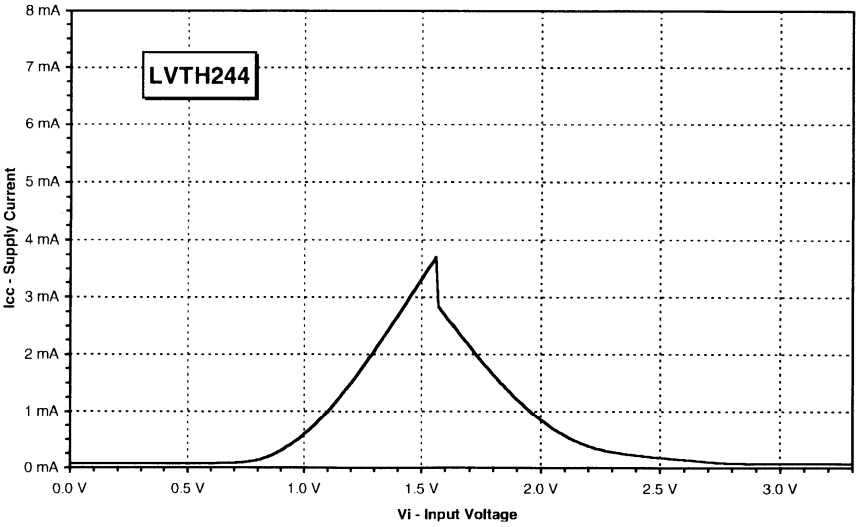


Figure 38: Current consumption vs. input voltage of LVT

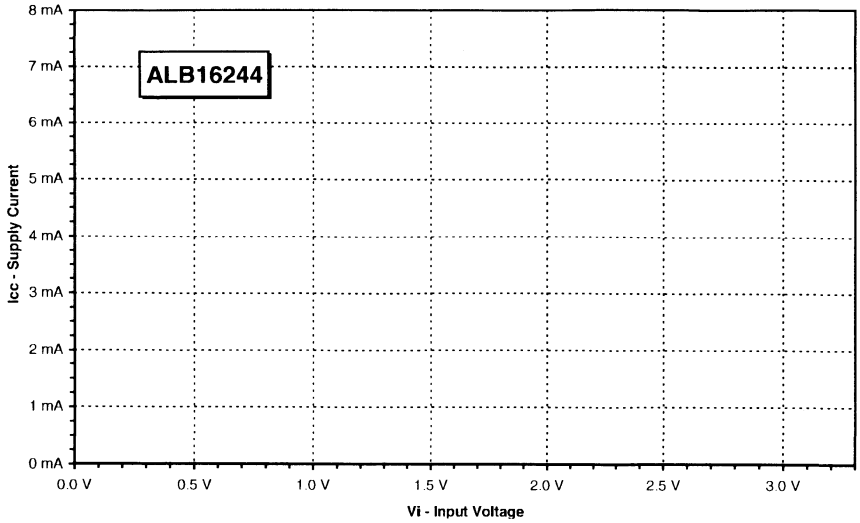


Figure 39: Current consumption vs. input voltage of ALB (I_{CC} = 0 mA across all input voltages)

3.3.2 Dynamic Power Consumption

With all five logic families the power consumption increases with operating frequency (Figure 40). This increase in power consumption partly results from the fact that internal capacitances need to be continuously charged and discharged, and partly because current "spikes" are generated when the output transistors are switched on and off (see chapter 3.3.1). In order to evaluate the power consumption of the bus driver alone, the curves in Figure 40 were measured without output load. The dynamic power consumption will increase when the outputs are connected to a load circuit.

The digitally operating families show a typical CMOS behavior: Linear increase of supply current with increasing frequency. The ALB device with its analog circuitry will display significant power consumption already in quiescent mode. However, it will increase only marginally with frequency. At high frequencies, ALB devices consume even less power than devices of other circuit families.

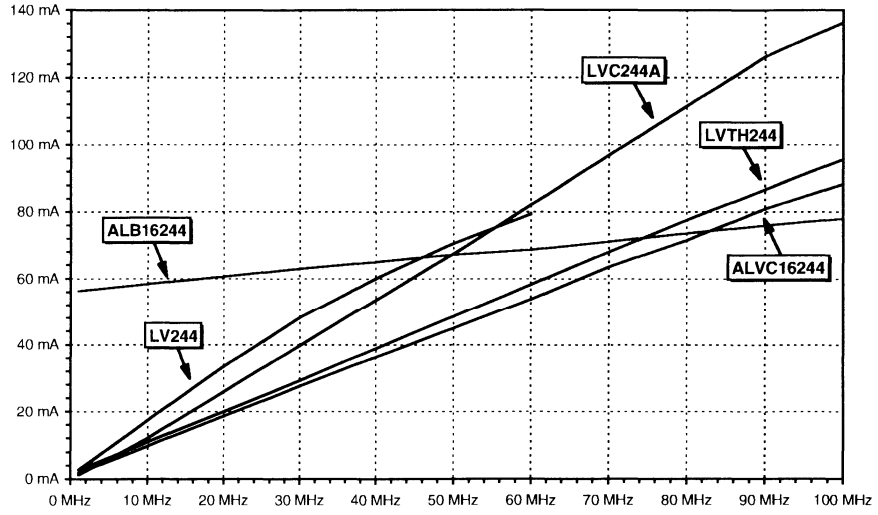


Figure 40: Open-circuit power consumption versus frequency

3.4 Dynamic Behavior

3.4.1 Input Signal Switching Speed

The inputs of the LVC, ALVC and ALB circuit families are supplied with Schmitt-Trigger circuit stages. While these reduce a devices sensitivity to distortions that may occur within a rising or falling edge, they are not suitable to handle extremely slow edges. A certain minimum edge steepness is therefore required for these devices. The values listed in Table 6 are to be understood as describing an input slope steepness that guarantees proper logic operation of these devices. SN74ALB-type devices operate with linear circuitry and will exactly reproduce a slowly rising input signal slope at their output.

Wherever slow input signal slopes need to be processed by logic gates it is necessary to select those with Schmitt-Trigger inputs, as these have been specifically designed for this purpose. Figure 41 shows the signal waveforms for an SN74LVC14 with an input signal switching within 1 ms, while Figure 42 displays the results of the same measurement as characteristic of V_{IN} over V_{OUT}.

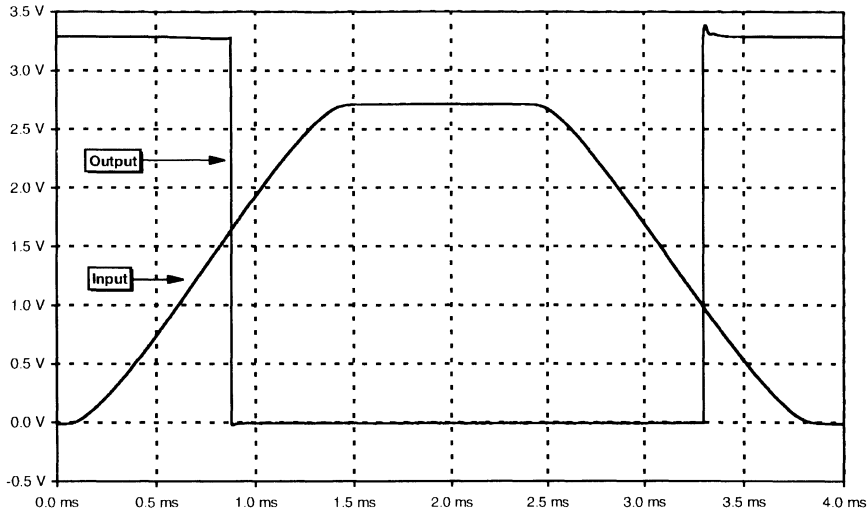


Figure 41: SN74LVC14 input signal waveform diagram with a 1 ms input slope

Series	V_{cc}	U_{il}max	U_{ih}min	U_s	dt/du
SN74LV	2.7 V..5.5 V	0,8 V	2,0 V	≈ 1,5 V	100 ns/V
SN74LVC	2.7 V..3.6 V	0,8 V	2,0 V	≈ 1,5 V	10 ns/V
SN74ALVC	2.3 V..3.6 V	0,8 V	2,0 V	≈ 1,5 V	10 ns/V
SN74LVT	2.3 V..3.6 V	0,8 V	2,0 V	1,4 V	10 ns/V
SN74ALB	3.0 V..3.6 V	0,8 V	2,0 V	-	-

Table 6: Required signal transition speeds of logic circuits

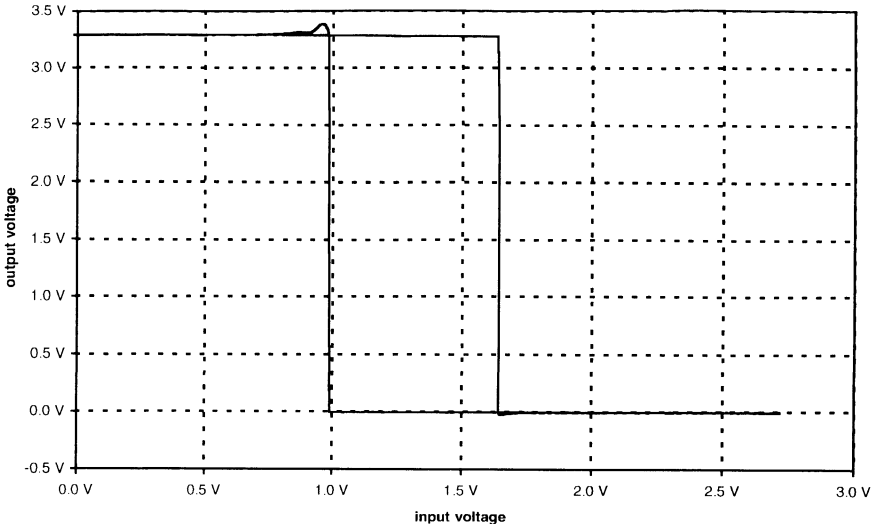


Figure 42: Input Schmitt-trigger hysteresis of the SN74LVC14

3.4.2 Speed

The maximum propagation delay times guaranteed in the data sheets (Table 7) show that LV devices are by far the slowest of the 3.3V families. Typical values and the correlation of propagation delay time to the number of switched outputs are shown in Figure 43 and Figure 44. Since ALVC and ALB are only available in the Widebus™ package, the beneficial features of this package come to play in these measurements. For this reason a Widebus™ packaged LVC16244A was also included in the comparison, while this device shows nearly identical behavior to ALVC16244A and ALB16244. In this case it becomes evident that the package influences this measurement more than the electrical features of the individual logic family.

	from	to	LV244	LVC244A	ALVC16244A	LVTH244A	ALB16244
t_{PLH}	A	Y	max. 14 ns	max. 6,5 ns	max. 3,6 ns	max. 3,5 ns	max. 2,0 ns
t_{PHL}	A	Y	max. 14 ns	max. 6,5 ns	max. 3,6 ns	max. 3,3 ns	max. 2,0 ns

Table 7: Data sheet values for propagation delay of the LV244, LVC244A, ALVC16244A, LVTH244A and ALB16244 devices at V_{CC} = 3,3 V ± 0,3 V and within temperatures ranging from -40 °C to +85 °C.

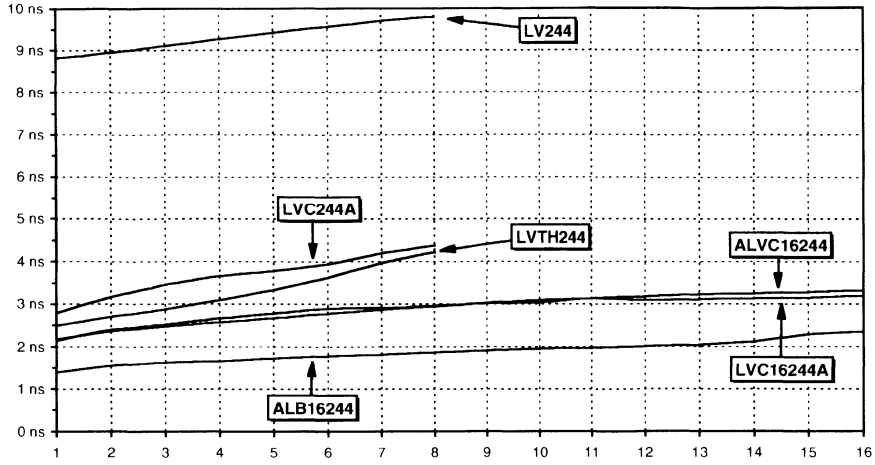


Figure 43:Propagation delay time t_{PLH} versus number of switching outputs

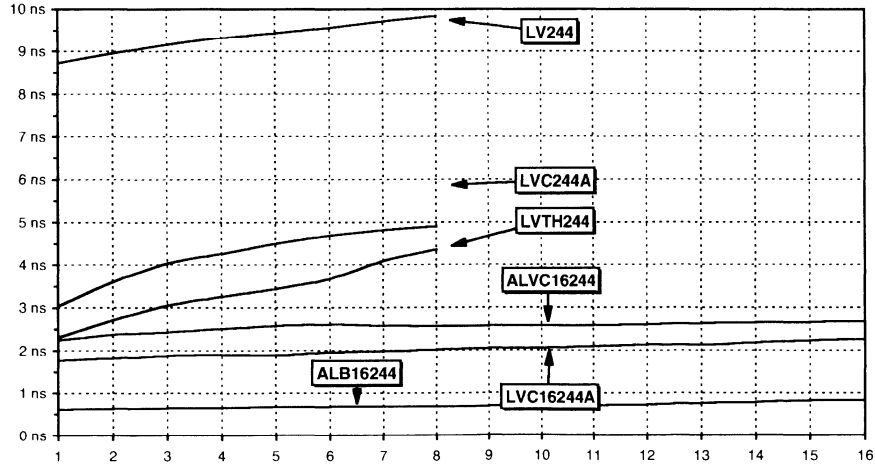


Figure 44: Propagation delay time t_{PHL} versus number of switching outputs

3.4.3 Characteristic Curves

Figure 45 and Figure 46 show typical characteristic curves of the five logic families LV, LVC, ALVC, LVT and ALB for a '244 bus driver function. The curves were measured at the outputs with a load of 500 Ω and 50 pF connected to GND in parallel. The different delay times and steepness of the edges can be clearly seen. The slowest family LV has a significantly longer rise and fall time than the two fastest digital families ALVC and LVT. As expected, the ALB family device is fastest. It is clearly visible that this device operates with analog circuitry, as no threshold voltage must be reached to cause an output signal transition. Because of the fast edges of the LVC, ALVC, LVT and ALB families, more attention must be paid to line theory topics such as reflections with these components when designing circuit boards than with the LV family.

	LV244	LVC244A	ALVC16244A	LVTH244A	ALB16244
Rise Time (10% - 90%)	5,9 ns	3,4 ns	2,4 ns	2,9 ns	1,7 ns
Fall Time (90% - 10%)	4,8 ns	3,0 ns	2,2 ns	1,9 ns	1,5 ns

Table 8 Typical Rise and Fall Times at V_{CC}=3.3V and 25ºC.

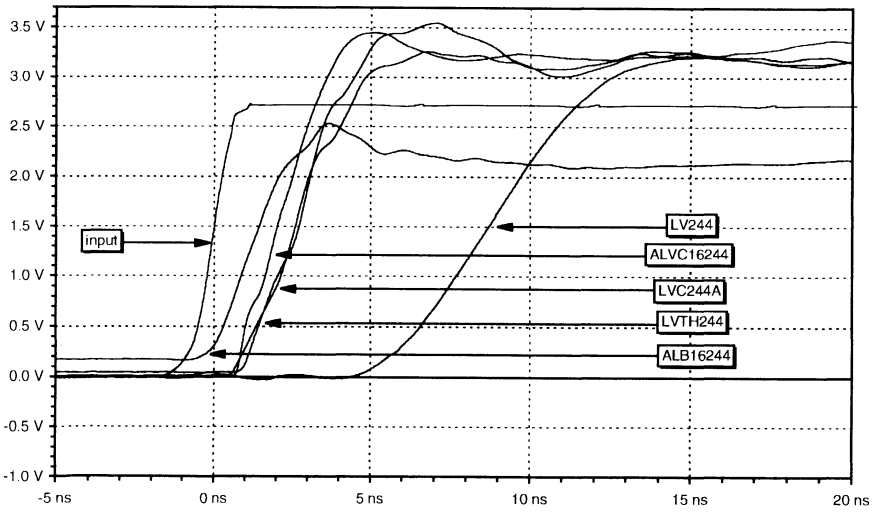


Figure 45: Rising edge diagrams of LV244, LVC244A, 'ALVC16244, LVTH244A and ALB16244 for a load of 500 Ω and 50 pF to GND

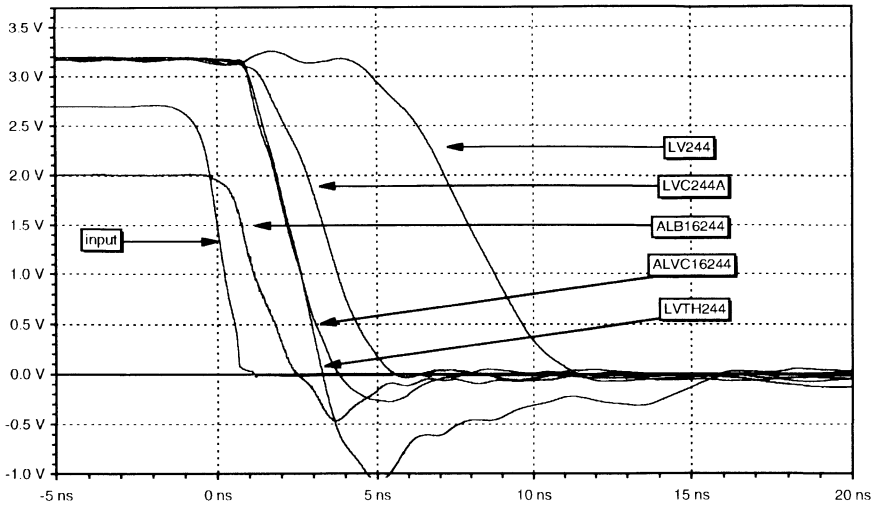


Figure 46: Falling edge diagrams of LV244, LVC244A, 'ALVC16244, LVTH244A and ALB16244 for a load of 500 Ω and 50 pF to GND

4 Summary

When low power consumption or high speeds are required, then there is no choice but to lower supply voltage. Conventional CMOS logic families such as HC and AC already allow operation at very low supply voltages. However, this will severely limit the performance features of these devices. The logic families LV, LVC, ALVC, LVT and ALB have been specifically designed for 3,3V operation and deliver 5V performance characteristics at 3,3V supply voltage. TEXAS INSTRUMENTS currently offers five logic families and therefore can provide a solution for every requirement:

- ⇨ LV, which at 3.3V has the characteristics of the 5V family HCMOS.
- ⇨ LVC and ALVC, which correspond to the 5V family AC, and are therefore significantly faster than the LVC.
- ⇨ LVT, which as a BiCMOS family provides the characteristics of ABT:
  - TTL-compatible input and output levels
  - High speed and
  - High drive capability.
- ⇨ ALB with its analog circuitry is definitely designed for highest speeds.

Literature:

[1] "Bus Hold Circuits" Application Note, Texas Instruments,
TI Literature Code SDZAE15, TID Application note # EB209

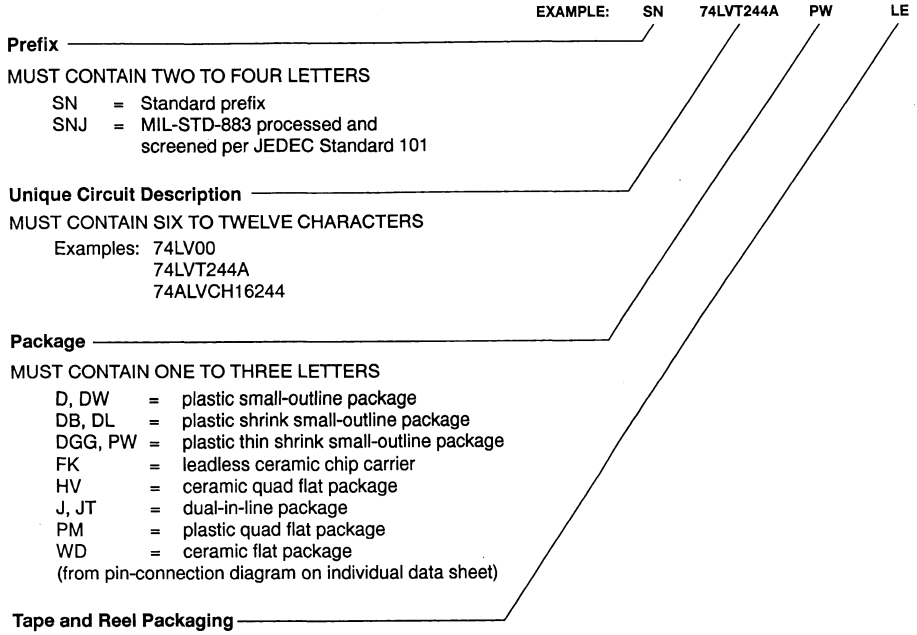
[2] CD-ROM "Logic Application Reports and Product Selection Guide", Texas Instruments,
TI Literature Code SDZDE01A

[3] Data Book "Low Voltage Logic Data Book", Texas Instruments 1996.
TI Literature Code SCBD003B

Contents

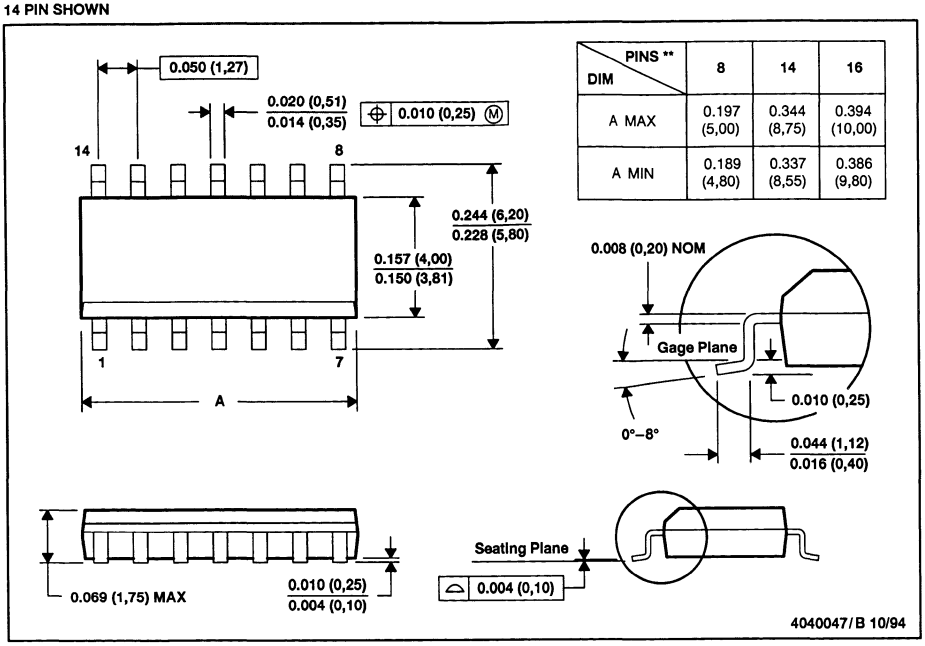
Electrical characteristics presented in this data book, unless otherwise noted, apply for the circuit type(s) listed in the page heading regardless of package. The availability of a circuit function in a particular package is denoted by an alphabetical reference above the pin-connection diagram(s). These alphabetical references refer to mechanical outline drawings shown in this section.

Factory orders for circuits described in this catalog should include a three-part type number as explained in the following example.



D (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14 PIN SHOWN

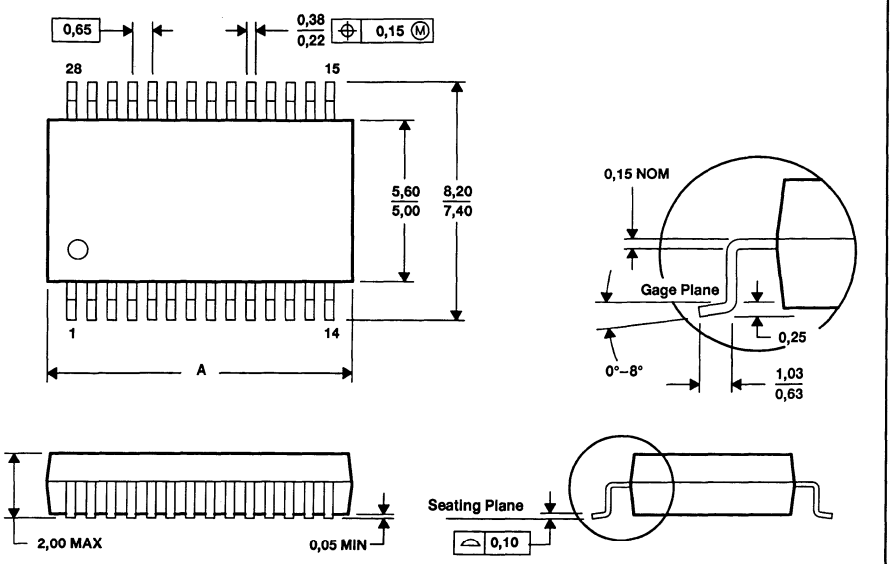


DIM \ PINS **	8	14	16
A MAX	0.197 (5,00)	0.344 (8,75)	0.394 (10,00)
A MIN	0.189 (4,80)	0.337 (8,55)	0.386 (9,80)

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Four center pins are connected to die mount pad.
E. Falls within JEDEC MS-012

DB (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

28 PIN SHOWN



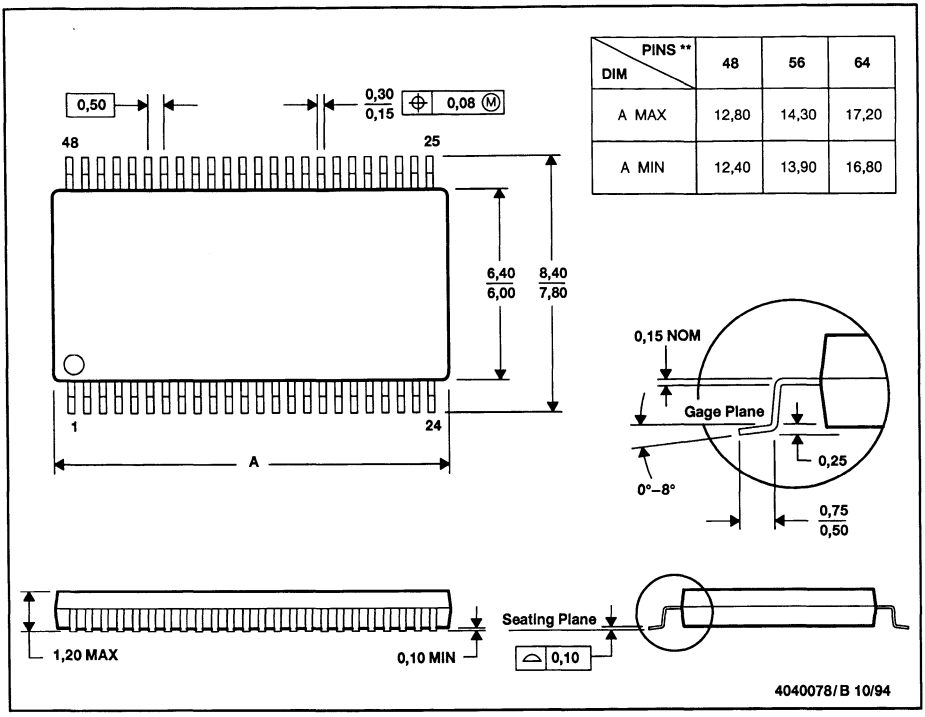
DIM \ PINS **	14	16	20	24	28	30	38
A MAX	6,50	6,50	7,50	8,50	10,50	10,50	12,90
A MIN	5,90	5,90	6,90	7,90	9,90	9,90	12,30

4040065 / B 10/94

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-150

DGG (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

48 PIN SHOWN

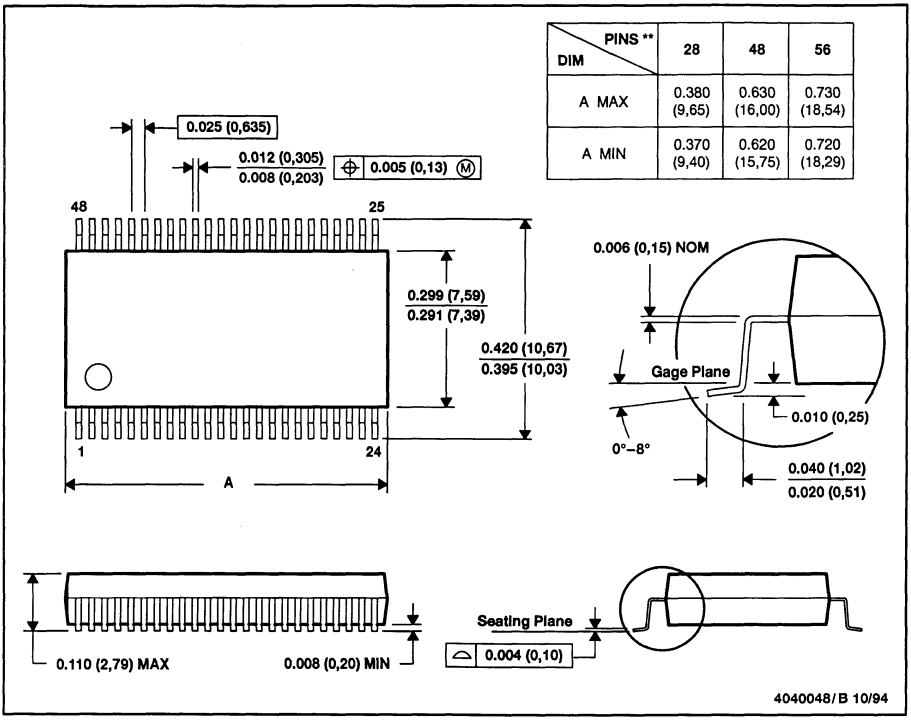


DIM \ PINS **	48	56	64
A MAX	12,80	14,30	17,20
A MIN	12,40	13,90	16,80

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.

DL (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

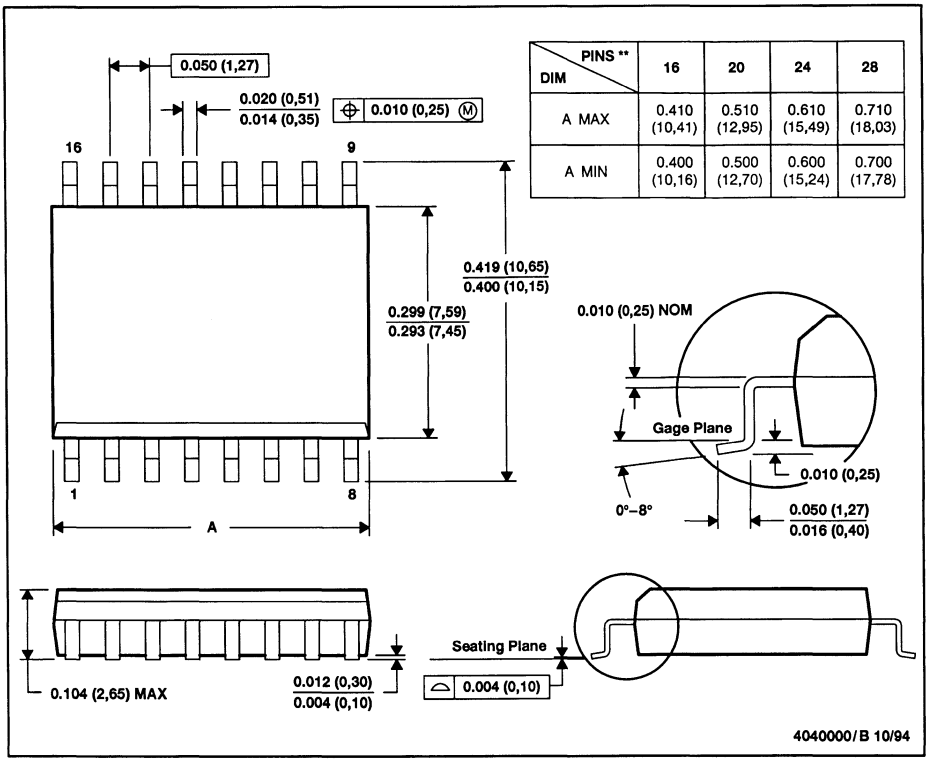
48 PIN SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

DW (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

16 PIN SHOWN

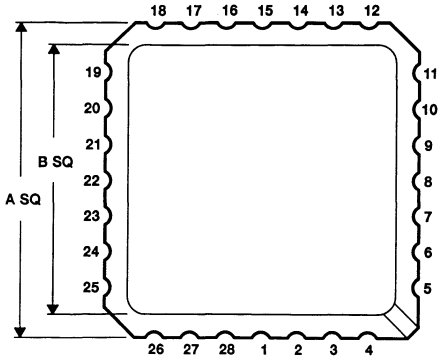


DIM \ PINS **	16	20	24	28
A MAX	0.410 (10,41)	0.510 (12,95)	0.610 (15,49)	0.710 (18,03)
A MIN	0.400 (10,16)	0.500 (12,70)	0.600 (15,24)	0.700 (17,78)

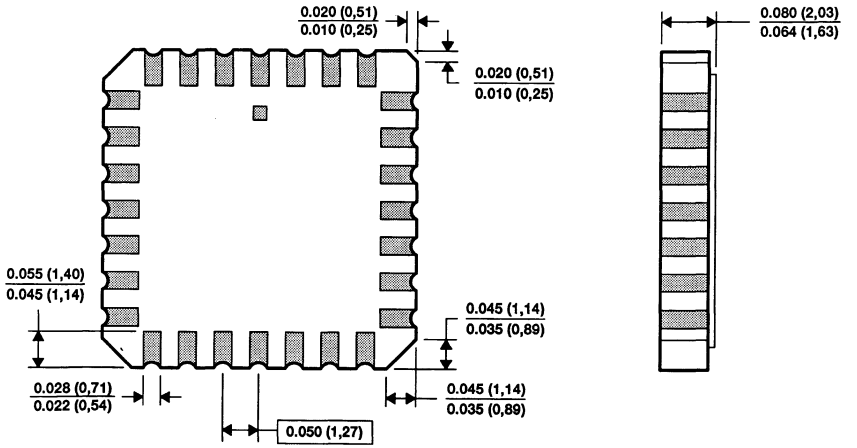
NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS-013

FK (S-CQCC-N)** **LEADLESS CERAMIC CHIP CARRIER**

28 TERMINAL SHOWN



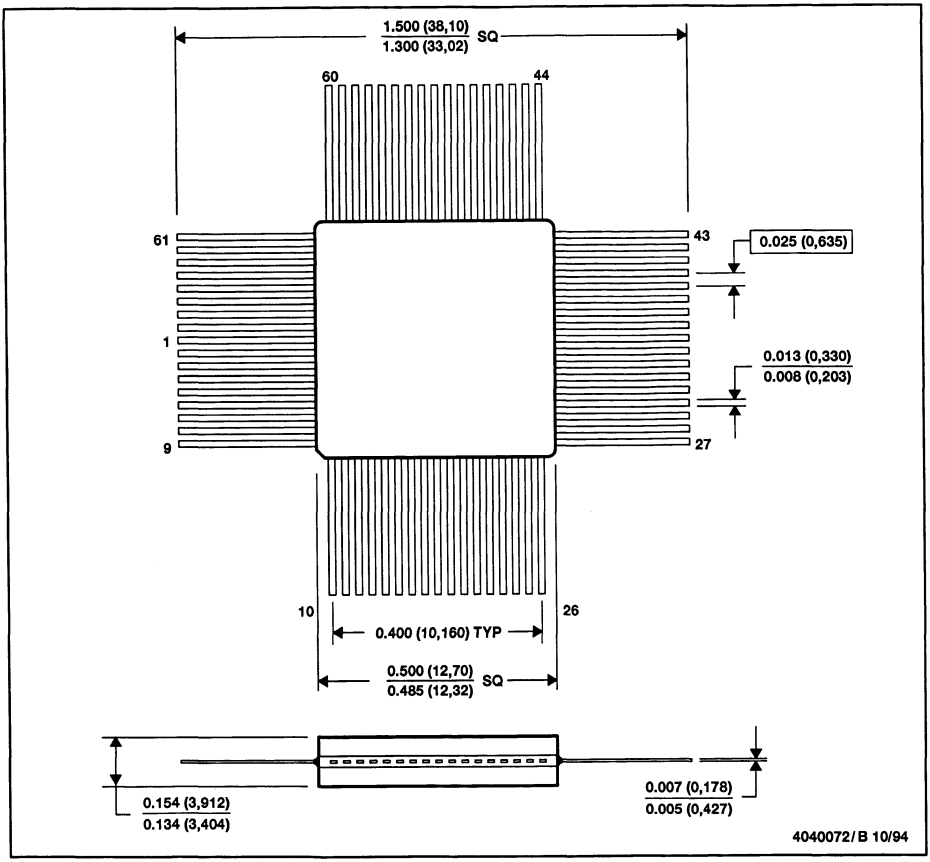
NO. OF TERMINALS **	A		B	
	MIN	MAX	MIN	MAX
20	0.342 (8,69)	0.358 (9,09)	0.307 (7,80)	0.358 (9,09)
28	0.422 (11,23)	0.458 (11,63)	0.406 (10,31)	0.458 (11,63)
44	0.640 (16,26)	0.660 (16,76)	0.495 (12,58)	0.560 (14,22)
52	0.730 (18,78)	0.761 (19,32)	0.485 (12,58)	0.560 (14,22)
68	0.938 (23,83)	0.962 (24,43)	0.850 (21,6)	0.858 (21,8)
84	1.141 (28,99)	1.165 (29,59)	1.047 (26,6)	1.063 (27,0)



4040140/B 10/94

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a metal lid.
D. The terminals are gold plated.
E. Falls within JEDEC MS-004

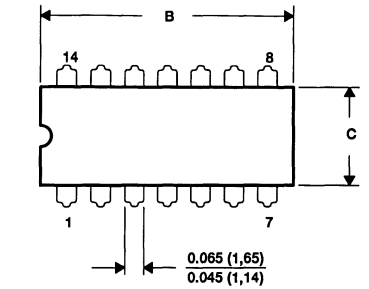
HV (S-GDFP-F68) **CERAMIC QUAD FLATPACK**



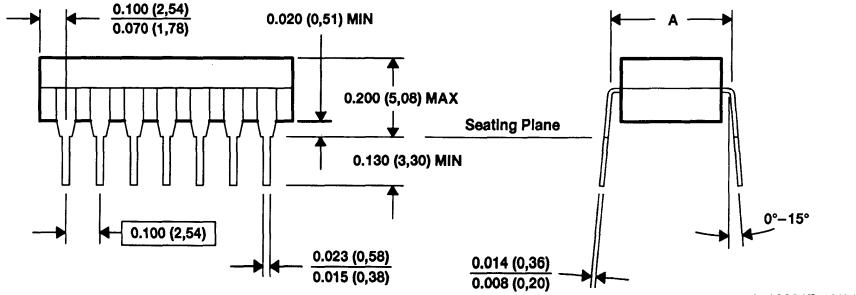
NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.

J (R-GDIP-T)** **CERAMIC DUAL-IN-LINE PACKAGE**

14 PIN SHOWN



DIM \ PINS **	14	16	18	20	22
A MAX	0.310 (7,87)	0.310 (7,87)	0.310 (7,87)	0.310 (7,87)	0.410 (10,41)
A MIN	0.290 (7,37)	0.290 (7,37)	0.290 (7,37)	0.290 (7,37)	0.390 (9,91)
B MAX	0.785 (19,94)	0.785 (19,94)	0.910 (23,10)	0.975 (24,77)	1.100 (28,00)
B MIN	0.755 (19,18)	0.755 (19,18)	—	0.930 (23,62)	—
C MAX	0.280 (7,11)	0.300 (7,62)	0.300 (7,62)	0.300 (7,62)	0.388 (9,65)
C MIN	0.245 (6,22)	0.245 (6,22)	0.245 (6,22)	0.245 (6,22)	—

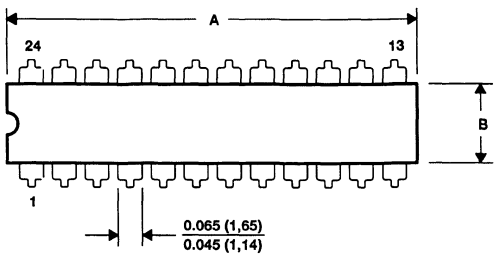


4040083/B 10/94

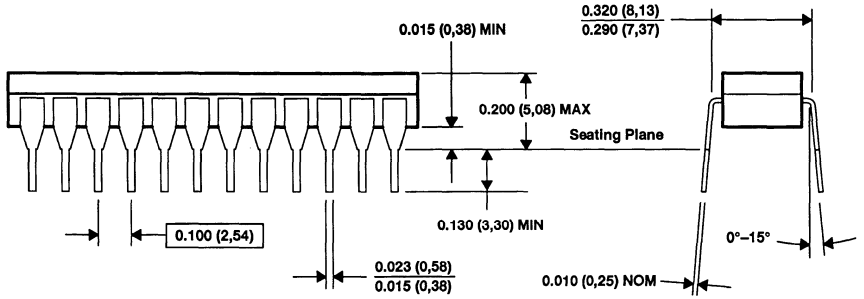
NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
E. Falls within MIL-STD-1835 GDIP1-T14, GDIP1-T16, GDIP1-T18, GDIP1-T20, and GDIP1-T22

JT (R-GDIP-T)** **CERAMIC DUAL-IN-LINE PACKAGE**

24 PIN SHOWN



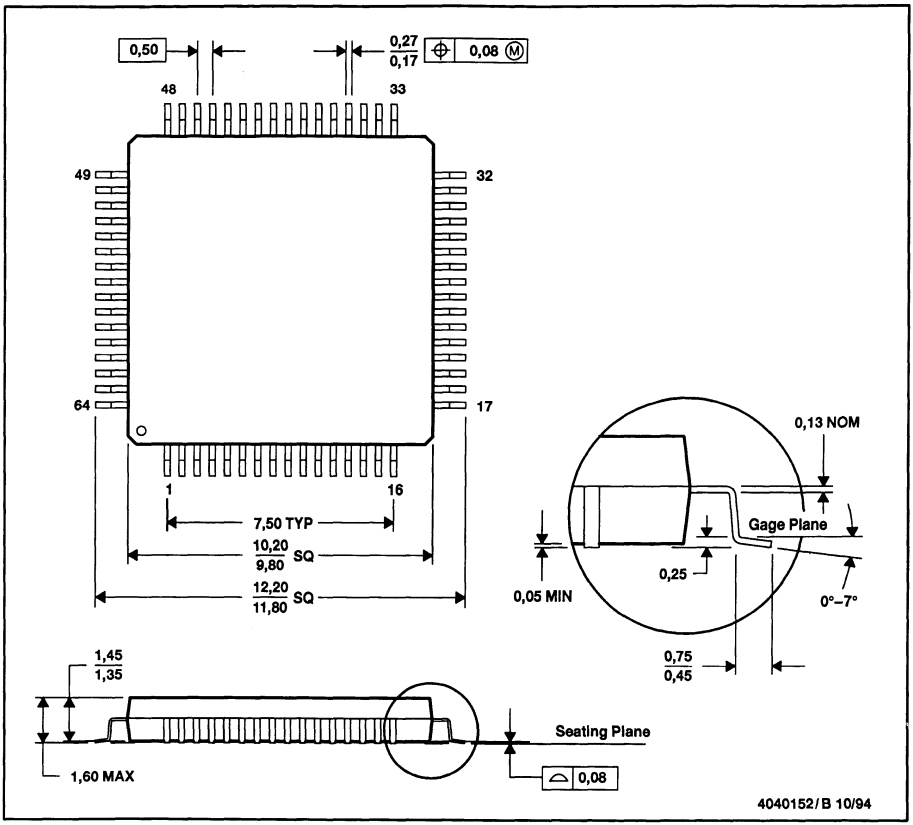
DIM \ PINS**	24	28
A MAX	1.280 (32,51)	1.460 (37,08)
A MIN	1.240 (31,50)	1.440 (36,58)
B MAX	0.300 (7,62)	0.291 (7,39)
B MIN	0.245 (6,22)	0.285 (7,24)



4040110/B 10/94

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
E. Falls within MIL-STD-1835 GDIP-T24 and GDIP-T28 and JEDEC MO-058AA and MO-058AB

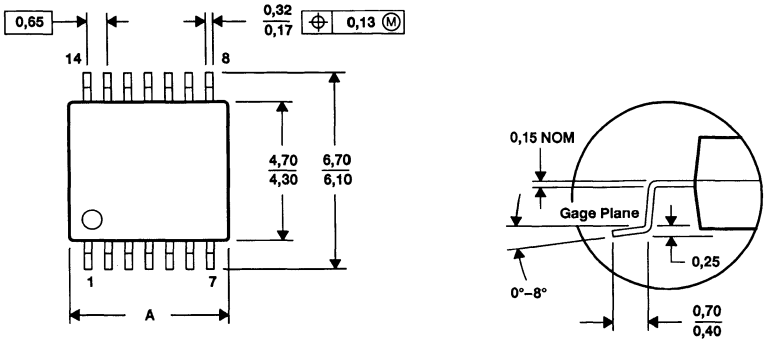
PM (S-PQFP-G64) PLASTIC QUAD FLATPACK



NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Falls within JEDEC MO-136

PW (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14 PIN SHOWN



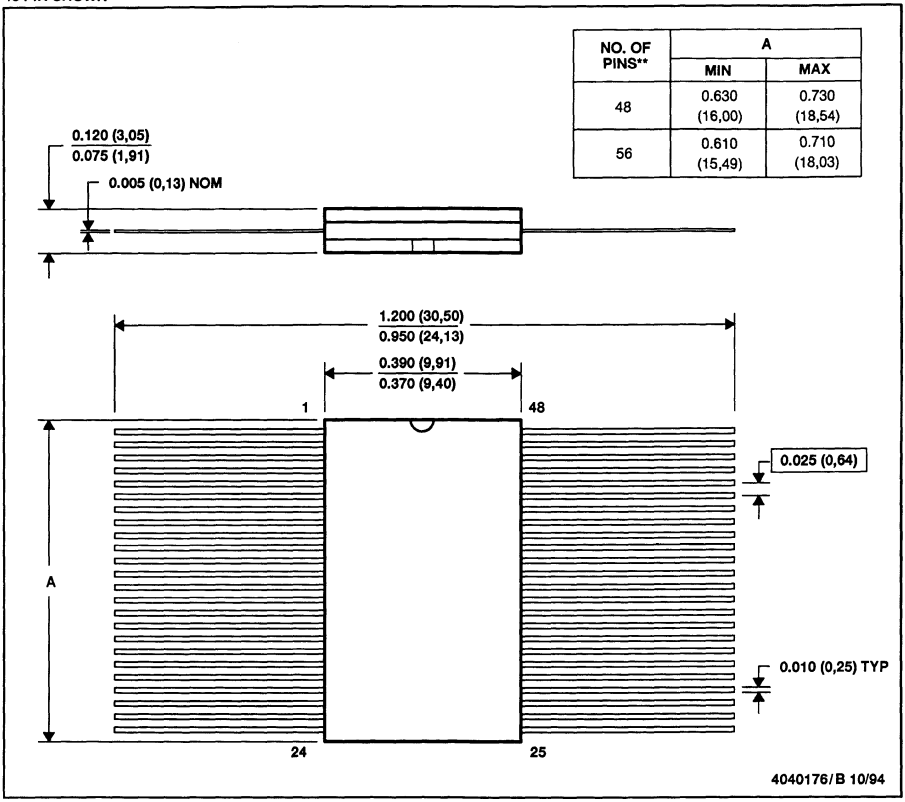
DIM \ PINS **	8	14	16	20	24	28
A MAX	3,30	5,30	5,30	6,80	8,10	10,00
A MIN	2,90	4,90	4,90	6,40	7,70	9,60

4040064/B 10/94

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

WD (R-GDFP-F)** **CERAMIC DUAL FLATPACK**

48 PIN SHOWN



NO. OF PINS**	A	
	MIN	MAX
48	0.630 (16,00)	0.730 (18,54)
56	0.610 (15,49)	0.710 (18,03)

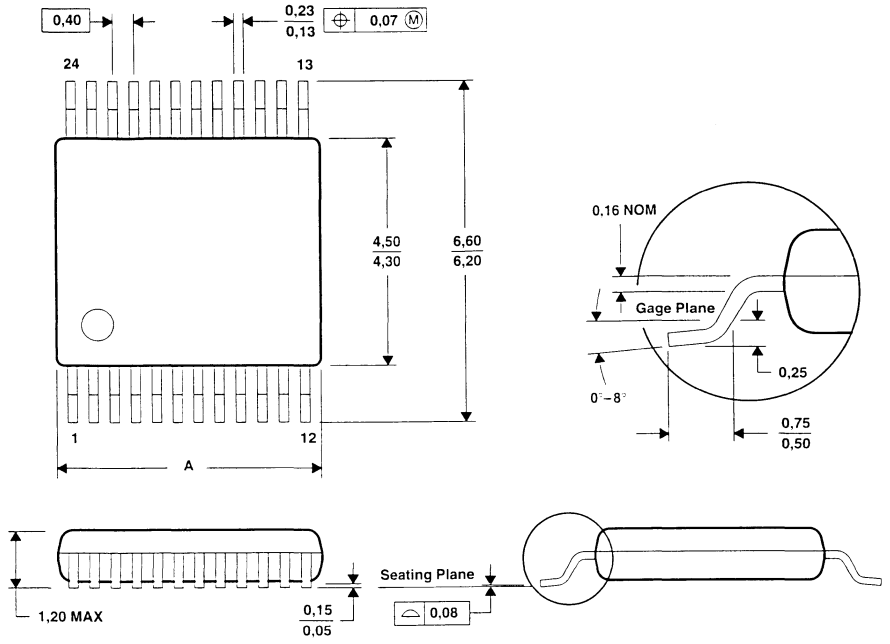
NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for pin identification only.
E. Falls within MIL-STD-1835: GDFP1-F48 and JEDEC MO-146AA
GDFP1-F56 and JEDEC MO-146AB

MPDS006A – JANUARY 1997

DGV (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

24 PIN SHOWN



DIM \ PINS **	14	16	20	24	48	56
A MAX	3,70	3,70	5,10	5,10	9,80	11,40
A MIN	3,50	3,50	4,90	4,90	9,60	11,20

4073251/B 03/97

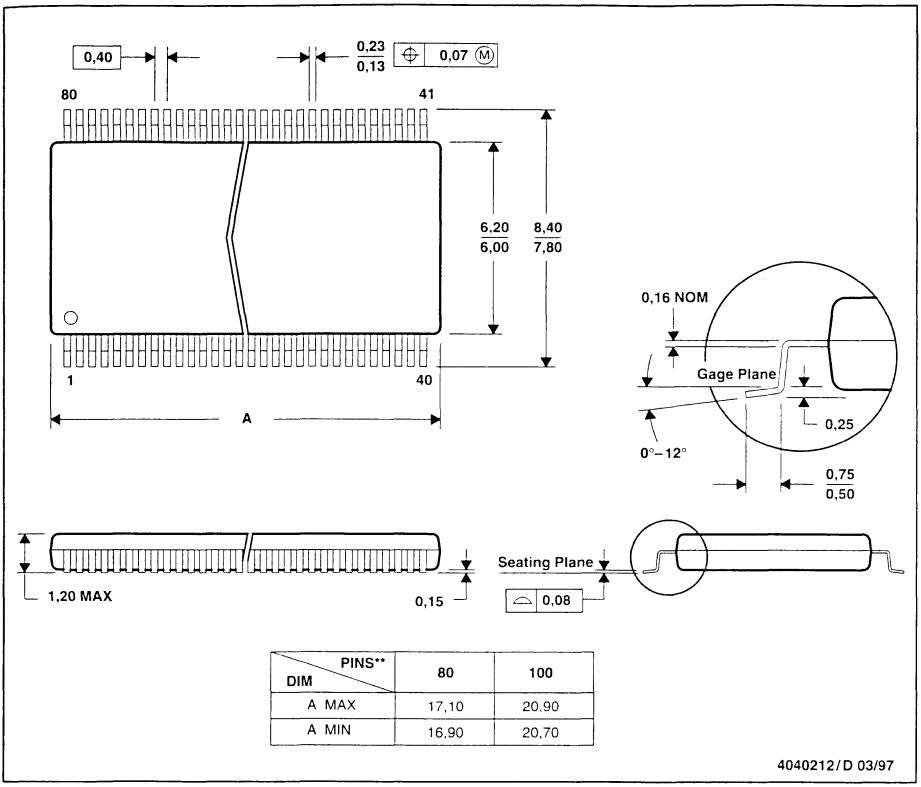
NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
D. The 24 and 28 pin fall within JEDEC MO-153 and the 14, 16, 20, 56 pins fall within JEDEC MO-194.

MTSS005D – JANUARY 1997

DBB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

80 PIN SHOWN



DIM \ PINS**	80	100
A MAX	17,10	20,90
A MIN	16,90	20,70

4040212/D 03/97

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. The 80 pin falls within JEDEC MO-153 and the 100 pin falls within JEDEC MO-194.

NOTES

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